DISCRETE SEMICONDUCTORS

Diodes

BOOK SC01 1989

Philips Components

PHILIPS

PHILIPS

DIODES

SELECTION GUIDE

SMALL-SIGNAL DIODES

General purpose and high-speed switching

type	case	V_R V	I_F mA	I_{FRM} mA	t_{rr} ns	C_d pF	V_F at V	I_F mA	page
BA220	DO-35	10	200	400	4	2.5	0.95	100	65
BA316	DO-35	10	100	225	4	2	1.1	100	87
BAX14	DO-35	20	500	2000	50	35	1.0	300	265
BA221	DO-35	30	200	400	4	2.5	1.05	200	69
BA317	DO-35	30	100	225	4	2	1.1	100	87
BAS15	DO-34	50	100	225	4	2	1.1	100	113
BA318	DO-35	50	100	225	4	2	1.1	100	87
PMLL4150	SOD80	50	300	600	6	2.5	1.0	200	771
PMLL4151	SOD80	50	200	450	2	2	1.0	50	771
PMLL4153	SOD80	50	200	450	2	2	0.88	20	771
1N4150	DO-35	50	300	600	6	2.5	1.0	200	801
1N4151	DO-35	50	200	450	2	2	1.0	50	801
1N4153	DO-35	50	200	450	2	2	0.88	20	801
BAV18	DO-35	50	250	625	50	5	1.25	200	207
BAV100	SOD80	50	250	625	50	1.5	1.25	200	231
BAV105	SOD80	60	300	600	6	2.5	1.00	200	239
BAS56*	SOT143	60	200	600	6	2.5	1.25	500	161
BAV10	DO-35	60	300	600	6	2.5	1.25	500	199
BAV74*	SOT23	50	250	250	4	2	1.0	100	223
BAV99*	SOT23	70	250	250	6	1.5	1.25	150	227
BAW56*	SOT23	70	250	250	6	2	1.25	150	247
PMLL4148	SOD80	75	200	450	4	4	1.0	10	767
PMLL4446	SOD80	75	200	450	4	4	1.0	10	767
PMLL4448	SOD80	75	200	450	4	4	1.0	10	767
1N914	DO-35	75	75	225	4	4	1.0	10	785
1N916	DO-34	75	75	225	4	2	1.0	10	785
1N4148	DO-35	75	200	450	4	4	1.0	10	797
1N4446	DO-35	75	200	450	4	4	1.0	20	797
1N4448	DO-35	75	200	450	4	4	1.0	100	797
1N4531	DO-34	75	200	450	4	4	1.0	10	805
1N4532	DO-34	75	200	450	2	2	1.0	10	805
BAW62	DO-35	75	200	450	4	2	1.0	100	251
BAS32	SOD80	75	200	450	4	2	1.0	100	135
BAS32L	SOD80	75	200	450	4	2	1.0	100	143
BAS16	SOT23	75	250	250	6	2	1.25	150	117
BAX18	DO-35	75	500	2000	6	35	1.0	300	271
BAX12	DO-35	90	400	800	—	35	1.25	400	259
BAS29	SOT23	90	250	600	50	35	1.25	400	133
BAS31*	SOT23	90	250	600	50	35	1.25	400	133
BAS35*	SOT23	90	250	600	50	35	1.25	400	133
BAS45L	SOD80	125	225	450	50	8	1.0	100	157
BAV19	DO-35	100	250	625	—	5	1.25	200	207
BAV101	SOD80	100	250	625	50	5	1.25	200	231
BAY80	DO-35	120	250	625	50	6	1.0	100	277
BAV102	SOD80	150	250	625	50	5	1.25	200	231
BAV20	DO-35	150	250	625	50	5	1.25	200	207
BAV23*	SOT143	200	200	625	50	5	1.25	200	215
BAV21	DO-35	200	250	625	50	5	1.25	200	207
BAV103	SOD80	200	250	625	50	5	1.25	200	231
BAS11	DO-35	300	350	2000	1000	15	1.1	300	107

SMALL-SIGNAL DIODES

General purpose and high-speed switching (continued)

type	case	V_R V	I_F mA	I_{FRM} mA	t_{rr} ns	C_d pF	V_F V	at I_F mA	page
PMBD2835	SOT23	30	100	–	15	4	1.0	50	743
PMBD2836	SOT23	70	100	–	15	4	1.0	50	743
PMBD2837	SOT23	30	150	300	15	4	1.0	50	747
PMBD2838	SOT23	50	150	300	15	4	1.0	50	747
PMBD914	SOT23	70	200	–	15	4	1.0	10	739
PMBD6050	SOT23	70	100	–	15	2.5	1.1	100	751
PMBD6100	SOT23	70	200	–	15	2.5	1.1	100	755
PMBD7000	SOT23	100	200	–	15	1.5	1.1	100	759

1) at $V_R = 0$ V and f = 1 MHz 2) V_{RRM}

* double diode

All maximum values

TUNER DIODES

Variable capacitance diodes

type	case	V_R V	I_F mA	C_d pF	at V_R V	C_d ratio	at V_R . V/..V	page
AFC								
BB417	DO-34	20	20	8-11	4	2-5	4/15	307
BB119	DO-35	15	200	20-25	4	> 1.3	4/10	281
FM radio								
BB204G	TO-92	30	100	34-39	3	2.5-2.8	3/30	287
BB204B*	TO-92	30	100	37-42	3	2.5-2.8	3/30	287
BB804	SOT23	20	50	42-47.5	2	1.7	2/8	309
AM radio								
BB112	SOD69	12	50	440-540	1	> 18	1/9	279
BB130	SOD69	30	50	450-550	1	> 23	1/28	285
BB212*	TO-92	12	100	500-620	0.5	> 22.5	0.5/8	291
VHF television								
BB809	DO-34	28	20	39-46	1	8-10	1/28	311
BB909A	DO-34	32	20	> 31	1	12-15	1/28	315
BB909B	DO-34	32	20	> 33.5	1	12-15	1/28	315
BB910	DO-34	32	10	> 38	,5	> 14	,5/28	319
BB911	DO-34	32	10	> 63	,5	> 21	,5/28	321
UHF television								
BB405B	DO-34	28	20	> 15.5	1	4.8-5.8	3/25	303

type	case	V_R V	I_F mA	C_d at pF	V_R V	C_d ratio at V_R	.V/..V	page
Varicaps for surface mounting								
BB215	SOD80	30	10	< 18	1	> 8.3	1/28	295
BB219	SOD80	30	10	> 31	1	12-15	1/28	297
BB240	SOD80	32	10	> 38	,5	> 14	,5/28	299
BB241	SOD80	32	10	> 63	,5	> 21	,5/28	301
BBY31	SOT23	28	50	typ. 17.5	1	typ. 5	3/25	323
BBY39	SOT23	30	10	typ. 11	3	> 7.6	3/28	327
BBY40	SOT23	28	20	26-32	3	5.0-6.5	3/25	329
BBY42	SOT23	32	50	> 31	1	12-16	1/28	333
BBY62*	SOT143	30	50	typ. 17.5	1	typ. 5	3/25	335

* Double diode.

Band switching diodes

type	case	V_R V	I_F mA	Cd pF	at V_R V	r_D Ω	at I_F mA	and f MHz	page
AM radio									
BA223	DO-34	20	50	< 3.5	6	< 1.5	10	1	73
BA423	DO-34	20	50	< 2.5	3	< 1.2	10	1	95
VHF television									
BA482	DO-34	35	100	< 1.2	3	< 0.7	3	200	101
BA483	DO-34	35	100	< 1.0	3	< 1.2	3	200	101
BA484	DO-34	35	100	< 1.6	3	< 1.2	3	200	101
BA682	SOD80	35	100	> 1.25	3	> 0.7	3	200	105
BAT18	SOT23	35	100	< 1.0	20	< 0.7	5	200	173

UHF mixer Schottky-barrier diode

type	case	V_R V	I_F mA	C_d pF	at V_R V	V_F mV	at I_F mA	page
BA481	DO-34	4	30	< 1;1	0	450	1	99

FM DETECTOR DIODE

type	case	V_R V	I_F mA	C_d pF	at V_R V	and f MHz	V_F at I_F = 10 μA mV	page
BA281	DO-35	50	200	1.2	0	1	360-420	77

LOW LEAKAGE DIODES

type	case	V_R V	I_R pA	at V_R	C_d at V_R = 0 and f = 1 MHz pF	page
BAS45	DO-34	125	1000		8	153
BAV45	TO-18	20	10		1.3	217

SCHOTTKY-BARRIER SWITCHING DIODES

type	case	V_R V	I_F mA	C_d pF	at V_R V	t_{rr} ns	V_F mV	at I_F mA	page
BAS85	SOD80	30	200	10	1	5.0	400	10	165
BAT17	SOT23	4	30	< 10	0	–	< 450	1	169
BYV10-20	DO-41	20	1000	220	0	–	< 390	100	531
BYV10-30	DO-41	30	1000	220	0	–	< 390	100	531
BYV10-40	DO-41	40	1000	220	0	–	< 390	100	531
BAT54	SOT23	30	200	<1.0	1	5	< 320	1	177
BAT54ACS	SOT23	30	200	< 10	1	5	< 320	1	181
BAT74	SOT143	30	200	<1.0	1	5	< 320	1	183
BAT81	DO-34	40	30	<1.6	1	1	< 410	1	187
BAT82	DO-34	50	30	<1.6	1	1	< 410	1	187
BAT83	DO-34	60	30	<1.6	1	1	< 410	1	187
BAT85	DO-34	30	200	< 10	1	5	< 320	1	191
BAT86	DO-34	50	200	< 8	1	4	< 380	1	195

* Double diode.

VOLTAGE REGULATOR DIODES

STABISTORS (used in forward direction)

type	case	typical V_F at I_F = 1 mA (V)	typical V_F at I_F = 5 mA (V)	typical V_F at I_F = 10 mA (V)	V_R V_{RRM} (V)	I_{FRM} (mA)	S_F typ. (mV/K)	at I_F (mA)	r_{diff} max. (Ω)	at I_F (mA)	page
BAX14	DO-35	0.55	0.62	0.65	40	2000	−2.2	1	6	10	265
BA220	DO-35	0.58	0.66	0.70	10	400	−2.2	1	7	10	65
BA315	DO-35	0.62	0.70	0.75	5	225	−2.1	1	7	10	83
BA314	DO-35	0.72	0.77	0.79	4	250	−1.8	1	6	10	79
BAS17	SOT23	0.72	0.77	0.79	4	250	−1.8	1	—		121
BZV86	SOD27	—	2.0	—	10	250	−6.0	5	30	5	689
BZX75	DO-7	1.75	—	1.99	5	250	−5.0	10	9	10	707

VOLTAGE REGULATORS (for high-power voltage regulators see Handbook Power diodes)

type	case	working voltage E24 range (V)	working voltage tol. (%)	I_{FRM} (mA)	P_{tot} (W)	at T_{tp} (T_{amb}) (°C)	P_{ZSM} at T_j = 25 °C, t_p = 100 µs (W)	page
BZV37	DO-34	6.5	5	—	0.4	(50)	40	633
BZX55 series	DO-35	2.4 to 75	5	250	0.5	50	40	703
BZX79 series	DO-35	2.4 to 75	2 or 5	250	0.5	50	40	711
BZX84 series	SOT23	2.4 to 75	5	250	0.35	(25)	—	727
BZV55 series	SOD80	2.4 to 75	5	250	0.5	(50)	30 (T_j = 150 °C)	647
PMLL5225B to PMLL5267B	SOD80	3.0 to 75	5	250	0.5	(75)	10 (T_j = 55 °C)	775
1N5225B to 1N5267B	DO-35	3.0 to 75	5	250	0.5	(75)	10 (T_j = 55 °C)	821
BZV49 series	SOT89	2.4 to 75	5	250	1	(25)	40	637
BZV85 series	DO-41	3.6 to 75	5	250	1.3	55	60	677
BZD23 series	SOD81	7.5 to 270	5	—	2.5	25	300	611
BZD27 series	SOD87	7.5 to 270	5	—	2.3	105	300	617
BZT03 series	SOD57	7.5 to 270	5	—	3.25	25	600	623
BZW03 series	SOD64	7.5 to 270	5	—	6	25	1000	693
BZV60 series	SOD68	2.4 to 75	2 or 5	250	0.5	50	30	661
PMBZ5226B to PMBZ5257B	SOT23	3.3 to 33	5	250	0.3	25	—	763

VOLTAGE REFERENCE DIODES

type	case	ref. volt. at I_Z min. V	nom. V	max. V	mA	I_{ZM} mA	$\lvert S_Z \rvert$ %/K	at I_Z mA	r_{diff} max. Ω	at I_Z mA	page
1N821; A	DO-34	5.89	6.2	6.51	7.5	50	< 0.01	7.5	15(10)	7.5	779
1N823; A							< 0.005		(A-version)		779
1N825; A							< 0.002				779
1N827; A							< 0.001				779
1N829; A							< 0.0005				779
BZV10	DO-34	6.17	6.5	6.82	2.0	50	< 0.01	2.0	50	2.0	629
BZV11							< 0.005				629
BZV12							< 0.002				629
BZV13							< 0.001				629
BZV14							< 0.0005				629
BZV80	SOD80	5.89	6.2	6.51	7.5	50	< 0.01	7.5	15	7.5	675
BZV81							< 0.0005				675

TRANSIENT SUPPRESSOR DIODES

type	case	V_R V	$V_{(CL)R}$ V	I_{RSM} A	P_{RSM} W	page
BZD23 series	SOD81	7.5 to 270	11.3 to 707	13.3 to 0.21	300	611
BZD27 series	SOD87	7.5 to 270	11.3 to 707	13.3 to 0.21	300	617
BZW14	SOD64	12	28	50		699
BZT03 series	SOD57	6.2 to 220	11.3 to 707	26.5 to 0.42	600	623
BZW03 series	SOD64	6.2 to 220	11.3 to 707	44.2 to 0.7	1000	693

RECTIFIER DIODES

General purpose diodes

type	case	$I_{F(AV)}$ A	I_{FRM} A	V_{RRM} V	I_{FSM} A	V_F V	at I_F A	page
1N4001ID	SOD81	1.0	10	50	20	1.1	1.0	789
1N4002ID	SOD81	1.0	10	100	20	1.1	1.0	789
1N4003ID	SOD81	1.0	10	200	20	1.1	1.0	789
1N4004ID	SOD81	1.0	10	400	20	1.1	1.0	789
1N4005ID	SOD81	1.0	10	600	20	1.1	1.0	789
1N4006ID	SOD81	1.0	10	800	20	1.1	1.0	789
1N4007ID	SOD81	1.0	10	1000	20	1.1	1.0	789
1N4001G	SOD81	1.0	10	50	30	1.1	1.0	793
1N4002G	SOD81	1.0	10	100	30	1.1	1.0	793
1N4003G	SOD81	1.0	10	200	30	1.1	1.0	793
1N4004G	SOD81	1.0	10	400	30	1.1	1.0	793
1N4005G	SOD81	1.0	10	600	30	1.1	1.0	793
1N4006G	SOD81	1.0	10	800	30	1.1	1.0	793
1N4007G	SOD81	1.0	10	1000	30	1.1	1.0	793

Efficiency diodes

type	case	$I_{F(AV)}$ A	I_{FWM} A	V_{RRM} V	I_{FRM} A	t_d μs	t_{tot} μs	V_F V	at I_F A	page
BY588	SOD57	1.5	–	50	10	>0.7	–	1.6	3	393
BY458	SOD57	–	4	1200	8	–	20	1.6	3	363
BY228	SOD64	–	5	1500	10	–	20	1.5	5	349
BY328	SOD64	–	6	1400	10	–	13	1.45	5	353
BY438	SOD64	–	5	1200	10	–	20	1.5	5	359
BYX10G	SOD57	1.2	–	1600	5	–	–	1.5	2	601

Controlled avalanche

type	case	$I_{F(AV)}$ A	V_{RRM} V	V_R V	I_{FRM} A	I_{FSM} A	V_F V	at I_F A	page
BYD11D	SOD91	0.58	200	200	–	10	1.1	1	447
BYD11G	SOD91	0.58	400	400	–	10	1.1	1	447
BYD11J	SOD91	0.58	600	600	–	10	1.1	1	447
BYD11K	SOD91	0.58	800	800	–	10	1.1	1	447
BYD11M	SOD91	0.58	1000	1000	–	10	1.1	1	447
BYD13D	SOD81	1.4	200	200	5.5	20	1.05	1	451
BYD13G	SOD81	1.4	400	400	5.5	20	1.05	1	451
BYD13J	SOD81	1.4	600	600	5.5	20	1.05	1	451
BYD13K	SOD81	1.4	800	800	5.5	20	1.05	1	451
BYD13M	SOD81	1.4	1000	1000	5.5	20	1.05	1	451
BYD14D	SOD84	2.0	200	200	5.5	50	1.15	3	457
BYD14G	SOD84	2.0	400	400	5.5	50	1.15	3	457
BYD14J	SOD84	2.0	600	600	5.5	50	1.15	3	457
BYD14K	SOD84	2.0	800	800	5.5	50	1.15	3	457
BYD14M	SOD84	2.0	1000	1000	5.5	50	1.15	3	457
BYD17D	SOD87	1.5	200	200	5.5	20	1.05	1	463
BYD17G	SOD87	1.5	400	400	5.5	20	1.05	1	463
BYD17J	SOD87	1.5	600	600	5.5	20	1.05	1	463
BYD17K	SOD87	1.5	800	800	5.5	20	1.05	1	463
BYD17M	SOD87	1.5	1000	1000	5.5	20	1.05	1	463
BY527	SOD57	2.0	1250	800	12	50	1.65	10	379
BY627	SOD84	2.0	1250	800	20	50	1.15	3	409
BYW54	SOD57	2.0	600	600	12	50	1.65	10	577
BYW55	SOD57	2.0	800	800	12	50	1.65	10	577
BYW56	SOD57	2.0	1000	1000	12	50	1.65	10	577
1N5059	SOD57	2.0	200	200	12	50	1.15	2.5	813
1N5060	SOD57	2.0	400	400	12	50	1.15	2.5	813
1N5061	SOD57	2.0	600	600	12	50	1.15	2.5	813
1N5062	SOD57	2.0	800	800	12	50	1.15	2.5	813
BYM56A	SOD64	3.5	200	200	20	80	1.25	5	525
BYM56B	SOD64	3.5	400	400	20	80	1.25	5	525
BYM56C	SOD64	3.5	600	600	20	80	1.25	5	525
BYM56D	SOD64	3.5	800	800	20	80	1.25	5	525
BYM56E	SOD64	3.5	1000	1000	20	80	1.25	5	525

Avalanche fast soft-recovery

type	case	$I_{F(AV)}$ A	V_{RRM} V	V_R V	I_{FRM} A	I_{FSM} A	t_{rr} ns	V_F V	at I_F A	page
BYD31D	SOD91	0.5	200	200	–	10	250	1.44	1	471
BYD31G	SOD91	0.5	400	400	–	10	250	1.44	1	471
BYD31J	SOD91	0.5	600	600	–	10	250	1.44	1	471
BYD33D	SOD81	1.3	200	200	12	20	250	1.3	1	475
BYD33G	SOD81	1.3	400	400	12	20	250	1.3	1	475
BYD33J	SOD81	1.3	600	600	12	20	250	1.3	1	475
BYD33K	SOD81	1.3	600	600	12	20	300	1.3	1	475
BYD33M	SOD81	1.3	600	600	12	20	300	1.3	1	475
BYD34D	SOD84	1.8	200	200	17	45	250	1.4	3	481
BYD34G	SOD84	1.8	400	400	17	45	250	1.4	3	481

Avalanche fast soft-recovery (continued)

type	case	$I_{F(AV)}$ A	V_{RRM} V	V_R V	I_{FRM} A	I_{FSM} A	t_{rr} ns	V_F at V	I_F A	page
BYD34J	SOD84	1.8	600	600	17	45	250	1.4	3	481
BYD34K	SOD84	1.8	800	800	17	45	300	1.4	3	481
BYD34M	SOD84	1.8	1000	1000	17	45	300	1.4	3	481
BYD37D	SOD87	1.5	200	200	12	20	250	1.3	1	485
BYD37G	SOD87	1.5	400	400	12	20	250	1.3	1	485
BYD37J	SOD87	1.5	600	600	12	20	250	1.3	1	485
BYD37K	SOD87	1.5	800	800	12	20	300	1.3	1	485
BYD37M	SOD87	1.5	1000	1000	12	20	300	1.3	1	485
BYV95A	SOD57	1.5	200	200	10	35	250	1.6	3	561
BYV95B	SOD57	1.5	400	400	10	35	250	1.6	3	561
BYV95C	SOD57	1.5	600	600	10	35	250	1.6	3	561
BYV96D	SOD57	1.5	800	800	10	35	300	1.6	3	569
BYV96E	SOD57	1.5	1000	1000	10	35	300	1.6	3	569
BYW95A	SOD64	3.0	200	200	15	70	250	1.5	5	585
BYW95B	SOD64	3.0	400	400	15	70	250	1.5	5	585
BYW95C	SOD64	3.0	600	600	15	70	250	1.5	5	585
BYW96D	SOD64	3.0	800	800	15	70	300	1.5	5	593
BYW96E	SOD64	3.0	1000	1000	15	70	300	1.5	5	593
1N4933*	SOD84	1.5	50	50	–	30	200	1.2	3.14	809
1N4934*	SOD84	1.5	100	100	–	30	200	1.2	3.14	809
1N4935*	SOD84	1.5	200	200	–	30	200	1.2	3.14	809
1N4936*	SOD84	1.5	400	400	–	30	200	1.2	3.14	809
1N4937*	SOD84	1.5	600	600	–	30	200	1.2	3.14	809

* Not an avalanche type.

All values are maximum.

Very fast recovery (including epitaxial avalanche)

type	case	$I_{F(AV)}$ A	V_{RRM} V	V_R V	I_{FRM} A	I_{FSM} A	t_{rr} ns	V_F at V	I_F A	page
BYV26A	SOD57	1.0	200	200	10	20	30	2.5	1	533
BYV26B	SOD57	1.0	400	400	10	20	30	2.5	1	533
BYV26C	SOD57	1.0	600	600	10	20	30	2.5	1	533
BYV26D	SOD57	1.0	800	800	10	20	75	2.5	1	533
BYV26E	SOD57	1.0	1000	1000	10	20	75	2.5	1	533
BYV36A	SOD57	1.6	200	200	10	30	100	1.35	1	553
BYV36B	SOD57	1.6	400	400	10	30	100	1.35	1	553
BYV36C	SOD57	1.6	600	600	10	30	100	1.35	1	553
BYV36D	SOD57	1,5	800	800	9	30	150	1.45	1	553
BYV36E	SOD57	1.5	1000	1000	9	30	150	1.45	1	553
BYD73A	SOD81	1.75	50	50	15	25	25	0.95	1	491
BYD73B	SOD81	1.75	100	100	15	25	25	0.95	1	491
BYD73C	SOD81	1.75	150	150	15	25	25	0.95	1	491
BYD73D	SOD81	1.75	200	200	15	25	25	0.95	1	491
BYD73E	SOD81	1.7	250	250	13	25	50	1.05	1	491
BYD73F	SOD81	1.7	300	300	13	25	50	1.05	1	491
BYD73G	SOD81	1.7	400	400	13	25	50	1.05	1	491
BYD74A	SOD84	2.4	50	50	13	50	25	0.94	2	497
BYD74B	SOD84	2.4	100	100	13	50	25	0.94	2	497
BYD74C	SOD84	2.4	150	150	13	50	25	0.94	2	497
BYD74D	SOD84	2.4	200	200	13	50	25	0.94	2	497
BYD74E	SOD84	2.15	250	250	12	50	50	1.05	2	497
BYD74F	SOD84	2.15	300	300	12	50	50	1.05	2	497
BYD74G	SOD84	2.15	400	400	12	50	50	1.05	2	497
BYD77A	SOD87	2.0	50	50	15	25	25	0.95	1	507
BYD77B	SOD87	2.0	100	100	15	25	25	0.95	1	507
BYD77C	SOD87	2.0	150	150	15	25	25	0.95	1	507
BYD77D	SOD87	2.0	200	200	15	25	25	0.95	1	507
BYD77E	SOD87	1.85	250	250	13	25	50	1.05	1	507
BYD77F	SOD87	1.85	300	300	13	25	50	1.05	1	507
BYD77G	SOD87	1.85	400	400	13	25	50	1.05	1	507
BYM26A	SOD64	2.3	200	200	8	45	30	2.65	2	511
BYM26B	SOD64	2.3	400	400	8	45	30	2.65	2	511
BYM26C	SOD64	2.3	600	800	8	45	30	2.65	2	511
BYM26D	SOD64	2.3	800	800	8	45	75	2.65	2	511
BYM26E	SOD64	2.3	1000	1000	8	45	75	2.65	2	511
BYM36A	SOD64	3.0	200	200	8	45	100	1.6	3	517
BYM36B	SOD64	3.0	400	400	37	65	100	1.6	3	517
BYM36C	SOD64	3.0	600	800	37	65	100	1.6	3	517
BYM36D	SOD64	2.9	800	800	33	65	150	1.78	3	517
BYM36E	SOD64	2.9	1000	1000	33	65	150	1.78	3	517
BYV27-50	SOD57	2.0	50	50	15	50	25	1.07	3	539
BYV27-100	SOD57	2.0	100	100	15	50	25	1.07	3	539
BYV27-150	SOD57	2.0	150	150	15	50	25	1.07	3	539
BYV27-200	SOD57	2.0	200	200	15	50	25	1.07	3	539
BYV28-50	SOD64	3.5	50	50	25	90	30	1.1	5	547
BYV28-100	SOD64	3.5	100	100	25	90	30	1.1	5	547
BYV28-150	SOD64	3.5	150	150	25	90	30	1.1	5	547
BYV28-200	SOD64	3.5	200	200	25	90	30	1.1	5	547

E.H.T. soft recovery

type	case	$I_{F(AV)}$ mA	V_{RRM} kV	V_{RW} kV	page
BY584	SOD61	85	1.8	1.5	387
BY505	SOD61	85	2.2	2.0	371
BY614	SOD61	50	2.2	2.0	401
BYX90G	SOD83	550	7.5	6	605
BY705	SOD61	20	5	4	415
BY706	SOD61	20	6	5	415
BY707	SOD61	4	9	8	419
BY708	SOD61	4	12	10	419
BY709	SOD61	4	14	12	419
BY509	SOD61	4	15	11.5	375
BY609	SOD61	4	15	12	397
BY610	SOD61	4	17	12	397
BY619	SOD61	4	15	12	405
BY620	SOD61	4	17	12	405
BY710	SOD61	3	17	14	423
BY711	SOD61	3	19	16	423
BY712	SOD61	3	22	18	427
BY713	SOD61	3	24	20	427
BY714	SOD61	3	30	24	427
BY715	SOD61	20	5	4	431
BY716	SOD61	20	6	5	431
BY717	SOD61	4	10	9	435
BY718	SOD61	4	12	10	435
BY719	SOD61	3	14	12	435
BY720	SOD61	3	17	14	439
BY721	SOD61	3	19	16	439
BY722	SOD61	3	22	18	443
BY723	SOD61	3	24	20	443
BY724	SOD61	3	30	24	443

All values are maximum.

HIGH-VOLTAGE TRIPLER UNITS

type	$V_{i(p-p)}$ kV	V_{OM} kV	I_O mA	$I_{i(D6)}$ mA	R_i kΩ typ.	C_i pF typ.	page
BG2000-641-004	10	27.5	1.7	4	500	10	337
BG2097-641	10	27.5	1.7	4	500	10	343
BG2097-642	10	27.5	1.7	4	500	10	343

TYPE NUMBER SURVEY

* Series.

* Series.

PRO ELECTRON TYPE DESIGNATION CODE FOR SEMICONDUCTOR DEVICES

This type designation code applies to discrete semiconductor devices – as opposed to integrated circuits –, multiples of such devices and semiconductor chips.

"Although not all type numbers accord with the Pro Electron system, the following explanation is given for the ones that do."

A basic type number consists of:

TWO LETTERS FOLLOWED BY A SERIAL NUMBER

FIRST LETTER

The first letter gives information about the material used for the active part of the devices.

A. GERMANIUM or other material with band gap of 0,6 to 1,0 eV.
B. SILICON or other material with band gap of 1,0 to 1,3 eV.
C. GALLIUM-ARSENIDE or other material with band gap of 1,3 eV or more.
R. COMPOUND MATERIALS (e.g. Cadmium-Sulphide).

SECOND LETTER

The second letter indicates the function for which the device is primarily designed.

A. DIODE; signal, low power
B. DIODE; variable capacitance
C. TRANSISTOR; low power, audio frequency ($R_{th\ j\text{-}mb} > 15$ K/W)
D. TRANSISTOR; power, audio frequency ($R_{th\ j\text{-}mb} \leq 15$ K/W)
E. DIODE; tunnel
F. TRANSISTOR; low power, high frequency ($R_{th\ j\text{-}mb} > 15$ K/W)
G. MULTIPLE OF DISSIMILAR DEVICES – MISCELLANEOUS; e.g. oscillator
H. DIODE; magnetic sensitive
L. TRANSISTOR; power, high frequency ($R_{th\ j\text{-}mb} \leq 15$ K/W)
N. PHOTO-COUPLER
P. RADIATION DETECTOR; e.g. high sensitivity phototransistor
Q. RADIATION GENERATOR; e.g. light-emitting diode (LED)
R. CONTROL AND SWITCHING DEVICE; e.g. thyristor, low power ($R_{th\ j\text{-}mb} > 15$ K/W)
S. TRANSISTOR; low power, switching ($R_{th\ j\text{-}mb} > 15$ K/W)
T. CONTROL AND SWITCHING DEVICE; e.g. thyristor, power ($R_{th\ j\text{-}mb} \leq 15$ K/W)
U. TRANSISTOR; power, switching ($R_{th\ j\text{-}mb} \leq 15$ K/W)
X. DIODE: multiplier, e.g. varactor, step recovery
Y. DIODE; rectifying, booster
Z. DIODE; voltage reference or regulator (transient suppressor diode, with third letter W)

SERIAL NUMBER

Three figures, running from 100 to 999, for devices primarily intended for consumer equipment.*
One letter (Z, Y, X, etc.) and two figures, running from 10 to 99, for devices primarily intended for industrial/professional equipment.*
This letter has no fixed meaning except W, which is used for transient suppressor diodes.

VERSION LETTER

It indicates a minor variant of the basic type either electrically or mechanically. The letter never has a fixed meaning, except letter R, indicating reverse voltage, e.g. collector to case or anode to stud.

SUFFIX

Sub-classification can be used for devices supplied in a wide range of variants called associated types. Following sub-coding suffixes are in use:

1. VOLTAGE REFERENCE and VOLTAGE REGULATOR DIODES: *ONE LETTER and ONE NUMBER*
   The LETTER indicates the nominal tolerance of the Zener (regulation, working or reference) voltage
   A. 1% (according to IEC 63: series E96)
   B. 2% (according to IEC 63: series E48)
   C. 5% (according to IEC 63: series E24)
   D. 10% (according to IEC 63: series E12)
   E. 20% (according to IEC 63: series E6)
   The number denotes the typical operating (Zener) voltage related to the nominal current rating for the whole range.
   The letter 'V' is used instead of the decimal point.

2. TRANSIENT SUPPRESSOR DIODES: *ONE NUMBER*
   The NUMBER indicates the maximum recommended continuous reversed (stand-off) voltage V_R. The letter 'V' is used as above.

3. CONVENTIONAL and CONTROLLED AVALANCHE RECTIFIER DIODES and THYRISTORS: *ONE NUMBER*
   The NUMBER indicates the rated maximum repetitive peak reverse voltage (V_{RRM}) or the rated repetitive peak off-state voltage (V_{DRM}), whichever is the lower. Reversed polarity is indicated by letter R, immediately after the number.

4. RADIATION DETECTORS: *ONE NUMBER,* preceded by a hyphen (–)
   The NUMBER indicates the depletion layer in μm. The resolution is indicated by a version LETTER.

5. ARRAY OF RADIATION DETECTORS and GENERATORS: *ONE NUMBER,* preceded by a stroke (/).
   The NUMBER indicates how many basic devices are assembled into the array.

* When these serial numbers are exhausted the serial number for consumer types may be extended to four figures, and that for industrial types to three figures.

RATING SYSTEMS

The rating systems described are those recommended by the International Electrotechnical Commission (IEC) in its Publication 134.

DEFINITIONS OF TERMS USED

Electronic device. An electronic tube or valve, transistor or other semiconductor device.

Note
This definition excludes inductors, capacitors, resistors and similar components.

Characteristic. A characteristic is an inherent and measurable property of a device. Such a property may be electrical, mechanical, thermal, hydraulic, electro-magnetic, or nuclear, and can be expressed as a value for stated or recognized conditions. A characteristic may also be a set of related values, usually shown in graphical form.

Bogey electronic device. An electronic device whose characteristics have the published nominal values for the type. A bogey electronic device for any particular application can be obtained by considering only those characteristics which are directly related to the application.

Rating. A value which establishes either a limiting capability or a limiting condition for an electronic device. It is determined for specified values of environment and operation, and may be stated in any suitable terms.

Note
Limiting conditions may be either maxima or minima.

Rating system. The set of principles upon which ratings are established and which determine their interpretation.

Note
The rating system indicates the division of responsibility between the device manufacturer and the circuit designer, with the object of ensuring that the working conditions do not exceed the ratings.

ABSOLUTE MAXIMUM RATING SYSTEM

Absolute maximum ratings are limiting values of operating and environmental conditions applicable to any electronic device of a specified type as defined by its published data, which should not be exceeded under the worst probable conditions.

These values are chosen by the device manufacturer to provide acceptable serviceability of the device, taking no responsibility for equipment variations, environmental variations, and the effects of changes in operating conditions due to variations in the characteristics of the device under consideration and of all other electronic devices in the equipment.

The equipment manufacturer should design so that, initially and throughout life, no absolute maximum value for the intended service is exceeded with any device under the worst probable operating conditions with respect to supply voltage variation, equipment component variation, equipment control adjustment, load variations, signal variation, environmental conditions, and variations in characteristics of the device under consideration and of all other electronic devices in the equipment.

DESIGN MAXIMUM RATING SYSTEM

Design maximum ratings are limiting values of operating and environmental conditions applicable to a bogey electronic device of a specified type as defined by its published data, and should not be exceeded under the worst probable conditions.

These values are chosen by the device manufacturer to provide acceptable serviceability of the device, taking responsibility for the effects of changes in operating conditions due to variations in the characteristics of the electronic device under consideration.

The equipment manufacturer should design so that, initially and throughout life, no design maximum value for the intended service is exceeded with a bogey device under the worst probable operating conditions with respect to supply voltage variation, equipment component variation, variation in characteristics of all other devices in the equipment, equipment control adjustment, load variation, signal variation and environmental conditions.

DESIGN CENTRE RATING SYSTEM

Design centre ratings are limiting values of operating and environmental conditions applicable to a bogey electronic device of a specified type as defined by its published data, and should not be exceeded under normal conditions.

These values are chosen by the device manufacturer to provide acceptable serviceability of the device in average applications, taking responsibility for normal changes in operating conditions due to rated supply voltage variation, equipment component variation, equipment control adjustment, load variation, signal variation, environmental conditions, and variations in the characteristics of all electronic devices.

The equipment manufacturer should design so that, initially, no design centre value for the intended service is exceeded with a bogey electronic device in equipment operating at the stated normal supply voltage.

LETTER SYMBOLS FOR RECTIFIER DIODES, THYRISTORS, TRIACS AND BREAKOVER DIODES

LETTER SYMBOLS FOR CURRENTS, VOLTAGES AND POWERS

Basic letters: – The basic letters to be used are:

I, i = current V, v = voltage P, p = power

Lower-case basic letters shall be used for the representation of instantaneous values which vary with time. In all other instances upper-case letters shall be used.

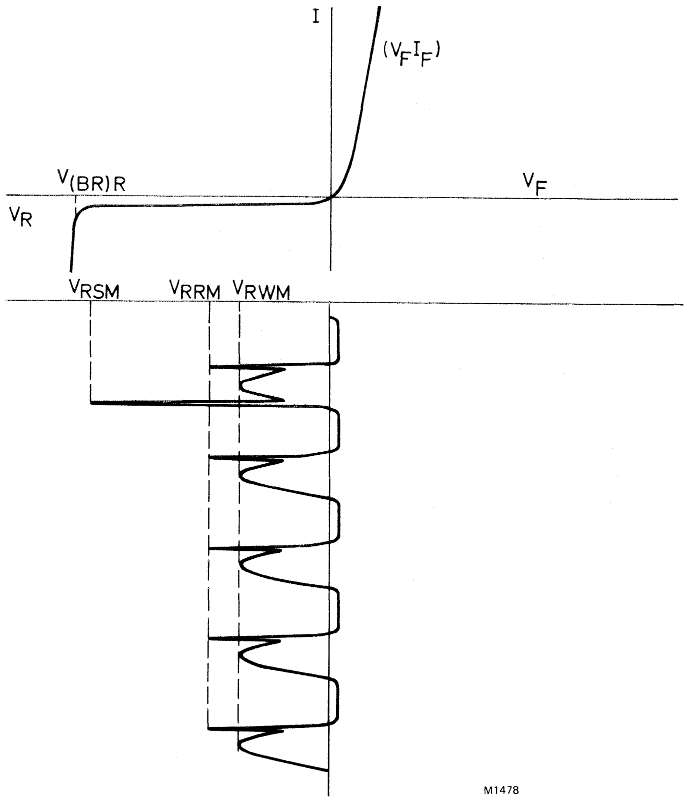
Subscripts

amb	Ambient
(AV), (av)	Average value
(BO)	Breakover
(BR)	Breakdown
case	Case
C	Controllable
D,d	Forward off-state [1]), non-triggered (gate voltage or current)
F,f	Forward [1]), fall
G,g	Gate terminal
H	Holding
I,i	Input
J,j	Junction
L	Latching
M,m	Peak or crest value
min	Minimum
O,o	Output, open circuit
(OV)	Overload
P,p	Pulse
Q,q	Turn-off
R,r	As first subscript: reverse, rise As second subscript: repetitive, recovery
(RMS), (rms)	R.M.S. value
S,s	As first subscript: storage, stray, series, source, switching ← As second subscript: non-repetitive
stg	Storage
T,t	Forward on-state [1]), triggered (gate voltage or current)
th	Thermal
(TO)	Threshold
tot	Total
W	Working
Z	Reference or regulator (i.e. zener)

For power rectifier diodes, thyristors and triacs, the terminals are **not** indicated in the subscript, except for the gate-terminal of thyristors and triacs.

[1]) For the anode-cathode voltage of thyristors and triacs, F is replaced either by D or T, to distinguish between 'off-state' (non-triggered) and 'on-state' (triggered).

Example of the use of letter symbols



Simplified rectifier characteristic together with an anode-cathode voltage as a function of time.

Upper-case subscripts shall be used for the indication of:

a) continuous (d.c.) values (without signal)

Example I_B

b) instantaneous total values

Example i_B

c) average total values

Example $I_{B(AV)}$

d) peak total values

Example I_{BM}

e) root-mean-square total values

Example $I_{B(RMS)}$

Lower-case subscripts shall be used for the indication of values applying to the varying component alone:

a) instantaneous values

Example i_b

b) root-mean-square values

Example $I_{b(rms)}$

c) peak values

Example I_{bm}

d) average values

Example $I_{b(av)}$

Note:

If more than one subscript is used, subscript for which both styles exist shall either be all upper-case or all lower-case.

Additional rules for subscripts

Subscripts for currents

Transistors: If it is necessary to indicate the terminal carrying the current, this should be done by the first subscript (conventional current flow from the external circuit into the terminal is positive).

Examples: I_B, i_B, i_b, I_{bm}

Diodes: To indicate a forward current (conventional current flow into the anode terminal) the subscript F or f should be used; for a reverse current (conventional current flow out of the anode terminal) the subscript R or r should be used.

Examples: I_F, I_R, i_F, $I_{f(rms)}$

Subscripts for voltages

Transistors: If it is necessary to indicate the points between which a voltage is measured, this should be done by the first two subscripts. The first subscript indicates the terminal at which the voltage is measured and the second the reference terminal or the circuit node. Where there is no possibility of confusion, the second subscript may be omitted.

Examples: V_{BE}, v_{BE}, v_{be}, V_{bem}

Diodes: To indicate a forward voltage (anode positive with respect to cathode), the subscript F or f should be used; for a reverse voltage (anode negative with respect to cathode) the subscript R or r should be used.

Examples: V_F, V_R, v_F, V_{rm}

Subscripts for four-pole matrix parameters

The first letter subscript (or double numeric subscript) indicates input, output, forward transfer or reverse transfer

Examples: h_i (or h_{11})
h_o (or h_{22})
h_f (or h_{21})
h_r (or h_{12})

A further subscript is used for the identification of the circuit configuration. When no confusion is possible, this further subscript may be omitted.

Examples: h_{fe} (or h_{21e}), h_{FE} (or h_{21E})

Distinction between real and imaginary parts

If it is necessary to distinguish between real and imaginary parts of electrical parameters, no additional subscripts should be used. If basic symbols for the real and imaginary parts exist, these may be used.

Examples: $Z_i = R_i + jX_i$
$y_{fe} = g_{fe} + jb_{fe}$

If such symbols do not exist or if they are not suitable, the following notation shall be used:

Examples: Re (h_{ib}) etc. for the real part of h_{ib}
Im (h_{ib}) etc. for the imaginary part of h_{ib}

QUALITY CONFORMANCE AND RELIABILITY

In addition to 100% testing of all major device parameters in the production department, independently controlled statistical sampling for conformance and reliability takes place using BS6001 'Sampling Procedures and Tables'. BS6001 is consistent with MIL–STD–105D. DEF131A, IS02859, CA–C–115.

The market demand for a continuously improving product quality is being met by the annual updating of formal quality improvement plans.

The 'Defect free' and 'Right first time' concepts are applied regularly as part of an overall quality programme covering all aspects of device quality from initital design to final production. These concepts, together with the quality assurance requirements, embrace all the principles outlined in DEF STAN 05–21, AQAP–1, and BS5750 Pt1.

CONFORMANCE

The Company actively promote a policy of customer cooperation to determine their quality problems and future requirements. This cooperation is often in the form of a 'ppm' activity. The 'ppm' is a measure of conformance of the outgoing product, and is expressed as the number of reject devices found per million of products delivered (e.g. a process average of 0,01% = 100 ppm). Mutually agreed ppm targets are set, and a programme of quality improvement work initiated.

In addition to the above, special inspection and/or test procedures are available, following consultation with the customer and the agreement of a special specification.

RELIABILITY

'Screening', or 'Burn-in' procedures are also available, based on the requirements of CECC 50 000.

CECC 50 000 offers a choice of four screening sequences: 'A', 'B', 'C', 'D'. The Company's standard 'Hi-rel' procedure offers a combination of 'C' and 'D' sequences.

Sequence 'C'

1. High temperature storage – 24 hours minimum.
2. Rapid change of temperature – as detailed in agreed specification.
3. Sealing – fine leak test.
   – gross leak test.
4. Functional electrical characteristics – within group 'A' limits.

Sequence 'D'

1. 'Burn-in' – high-voltage reverse bias, 48 hours duration. Conditions as specified in CECC 50 000.
2. Post 'Burn-in' measurements – functional electrical characteristics, within group 'A' limits.

Other 'Hi-rel', 'Burn-in', or Screening' procedures may be available on request.

RECTIFIER DIODES

REVERSE RECOVERY

When a semiconductor rectifier diode has been conducting in the forward direction sufficiently long to establish the steady state, there will be a charge due to minority carriers present. Before the device can block in the reverse direction this charge must be extracted. This extraction takes the form of a transient reverse current and this, together with the reverse bias voltage results in additional power dissipation which reduces the rectification efficiency. At sine-wave frequencies up to about 400 Hz these effects can often be ignored, but at higher frequencies and for square waves the switching losses must be considered.

Stored charge

The area under the I_R- time curve is known as the stored charge (Q_s) and is normally quoted in micro- or nanocoulombs. Low stored charge devices are preferred for fast switching applications.

Reverse recovery time

Another parameter which can be used to determine the speed of the rectifier is the reverse recovery time (t_{rr}). This is measured from the instant the current passes through zero (from forward to reverse) to the instant the current recovers to 10% of its peak reverse value. Low reverse recovery times are associated with low stored charge devices.

The conditions which need to be specified are:

a. Steady-state forward current (I_F); high currents increase recovery time.
b. Reverse bias voltage (V_R); low reverse voltage increases recovery time.
c. Rate of fall of anode current (dI_F/dt); high rates of fall reduce recovery time, but increase stored charge.
d. Junction temperature (T_j); high temperatures increase both recovery time and stored charge.

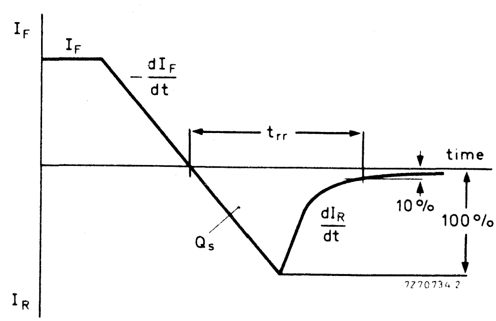


Fig. 1 Waveform showing the reverse recovery aspects.

REVERSE RECOVERY

Softness of recovery

In many switching circuits it is not just the magnitude but the shape of the reverse recovery characteristic that is important. If the positive-going edge of the characteristic has a fast rise time (as in a so-called 'snap-off' device) this edge may cause conducted or radiated r.f.i., or it may generate high voltages across inductors which may be in series with the rectifier. The maximum slope of the reverse recovery current (dI_R/dt) is quoted as a measure of the 'softness' of the characteristic. Low values are less liable to give r.f.i. problems. The measurement conditions which need to be specified are as above. When stored charges are very low, e.g. for epitaxial and Schottky-barrier rectifier diodes,this softness characteristic can be ignored.

DOUBLE-DIFFUSED RECTIFIER DIODES

A single-diffused diode with a two layer p-n structure cannot combine a high forward current density with a high reverse blocking voltage.

A way out of this dilemma is provided by the three layer double-diffused structure. A lightly doped silicon layer, called the base, is sandwiched between highly doped diffused p^+ and n^+ outer layers giving a p^+ —pn^+ or p^+ —nn^+ layer. Generally, the base gives the diode its high reverse voltage, and the two diffused regions give the high forward current rating.

Although double-diffused diodes are highly efficient, a slight compromise is still necessary. Generally, for a given silicon chip area, the thicker the base layer the higher the V_R and the lower the I_F. Reverse switching characteristics also determine the base design. Fast recovery diodes usually have n-type base regions to give 'soft' recovery. Other diodes have the base type, n or p, chosen to meet their specific requirements.

ULTRA FAST RECTIFIER DIODES

Ultra fast rectifier diodes, made by epitaxial technology, are intended for use in applications where low conduction and switching losses are of paramount importance and relatively low reverse voltage (V_{RRM} = 400 V) is required: e.g., switched-mode power supplies operating at frequencies of about 50 kHz.

The use of epitaxial technology means that there is very close control over the almost ideal diffusion profile and base width giving very high carrier injection efficiencies leading to lower conduction losses than conventional technology permits. The well defined diffusion profile also allows a tight control of stored minority carriers in the base region, so that very fast turn-off times can be achieved. The range of devices also has a soft reverse recovery and a low forward recovery voltage.

SWITCHING LOSSES (see also Fig.3)

The product of transient reverse current and reverse bias voltage is a power dissipation, most of which occurs during the fall time. In repetitive operation an average power can be calculated. This is then added to the forward dissipation to give the total power. The peak value of transient reverse current is known as I_{RRM}.

The conditions which need to be specified are:

a. Forward current (I_F); high currents increase switching losses.
b. Rate of fall of anode current (dI_F/dt); high rates of fall increase switching losses. This is particularly important in square-wave operation. Power losses in sine-wave operation for a given frequency are considerably less due to the much lower dI_F/dt.
c. Frequency (f); high frequency means high losses.
d. Reverse bias voltage (V_R); high reverse bias means high losses.
e. Junction temperature (T_j); high temperature means high losses.

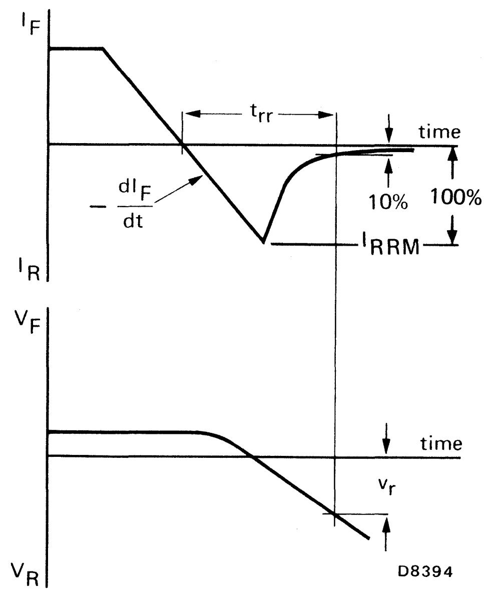


Fig.2 Waveforms showing the reverse switching losses aspects.

PRO ELECTRON COLOUR CODING SYSTEM FOR PROFESSIONAL SMALL SIGNAL DIODES

Letter combination - background colour

BAV - green
BAW - blue
BAX - black
BAS - orange
BAT - yellow

Figure combination - colour bands

0 - black
1 - brown
2 - red
3 - orange
4 - yellow
5 - green
6 - blue
7 - violet
8 - grey
9 - white

The cathode side is indicated by a broad band which is at the same time the first digit of the figure combination.

Note: For BA types see individual type publications.

JEDEC assigned type numbers

(EIA-standard RS-236-B; June, 1963)

1. Prefix identification

   The prefix identification consisting of a first number symbol and the letter "N" shall not be indicated in the coding.

2. Banding systems

   The sequence number consisting of a two, three, or four digit number after the letter "N" may be coded as follows:

   2.1 Two-digit sequence numbers shall consist of a first black band and the sequence number in second and third bands of the colours indicated in Table 1. If a suffix letter is required, it shall be indicated with a fourth band as indicated in Table 1.

   2.2 Three-digit sequence numbers shall consist of the sequence number in first, second, and third bands of the colours indicated in Table 1. If a suffix letter is required, it shall be indicated with a fourth band as indicated in Table 1.

   2.3 Four-digit sequence numbers shall consist of the sequence number in four bands of the colours indicated in Table 1.
   If a suffix letter is required it shall be indicated as the fifth band.

3. Cathode identification and reading sequence

   3.1 A double-width band shall be used as the first band reading from cathode to anode ends.

   3.2 An alternative method is provided where equal width bands may be used. The bands shall be clearly grouped toward the cathode end, and shall be read from cathode to anode ends.

   3.3 Either of the above colour banding methods may be used in stead of the cathode designating symbol or other marking.

4. Colour bands

   The sequence numbers of the type numbers and suffix letters shall be indicated by the colours in Table 1.

TABLE 1

NUMBER	COLOUR	SUFFIX LETTER
0	black	not applicable
1	brown	A
2	red	B
3	orange	C
4	yellow	D
5	green	E
6	blue	F
7	violet	G
8	grey	H
9	white	J

TAPE AND REEL SPECIFICATION

Semiconductors in SOT-23, SOT-143 and SOT-89 encapsulations can be delivered in reel packing for aotomatic placement on hybrid circuits and printed circuit boards. The devices are placed with the mounting side downwards in compartments.

A separate cross-section for SOD-80 encapsulation is given in Fig. 3.

A separate reel packing for SOT-89 encapsulation is given in Fig. 4.

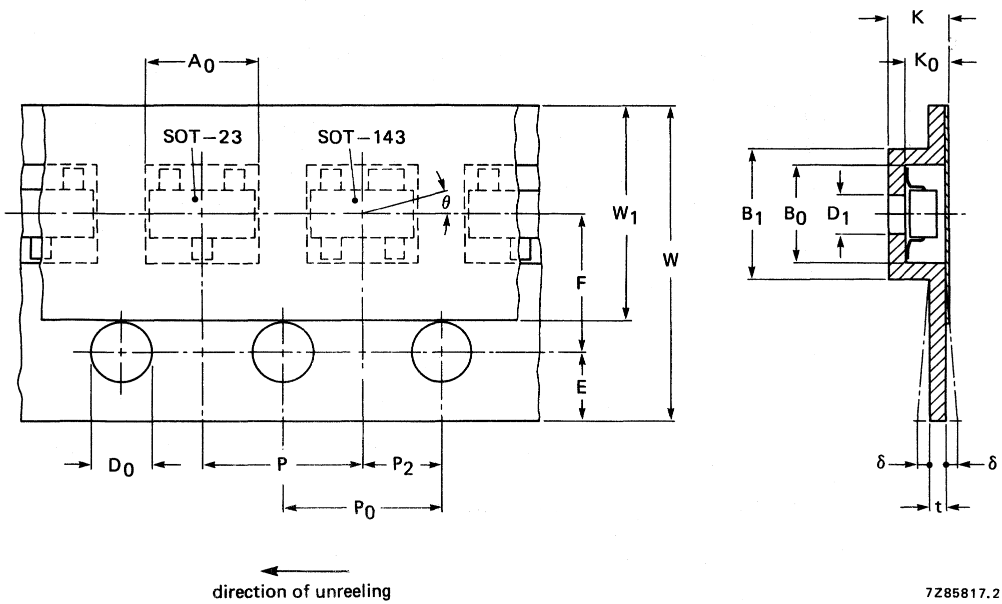


Fig. 1 Configuration of bandolier. Dimensions in mm.

Compartment			tol.
length	A_0	component length	+0,2
width	B_0	component width	+0,2
depth	K_0	0,95	+0,2
width outside	B_1	3,3	max.
pitch	P	4,0	±0,1
deviation	Θ	15°	max.
hole diameter	D_1	1	min.
Sprocket hole			
diameter	D_0	1,5	+0,1
pitch	P_0	4,0	±0,1
distance	E	1,75	±0,1
cumulative (10) pitch error		±0,1	

Centre line dimensions			tol.
length direction	P_2	2,0	±0,05
width direction	F	3,5	±0,05
Fixing tape			
width	W_1	5,5	±0,25
thickness	—	0,1	max.
Carrier tape			
width	W	8,0	± 0,2
bending	δ	0,3	max.
thickness	t	0,4	max.
Overall thickness	K	1,5	max.

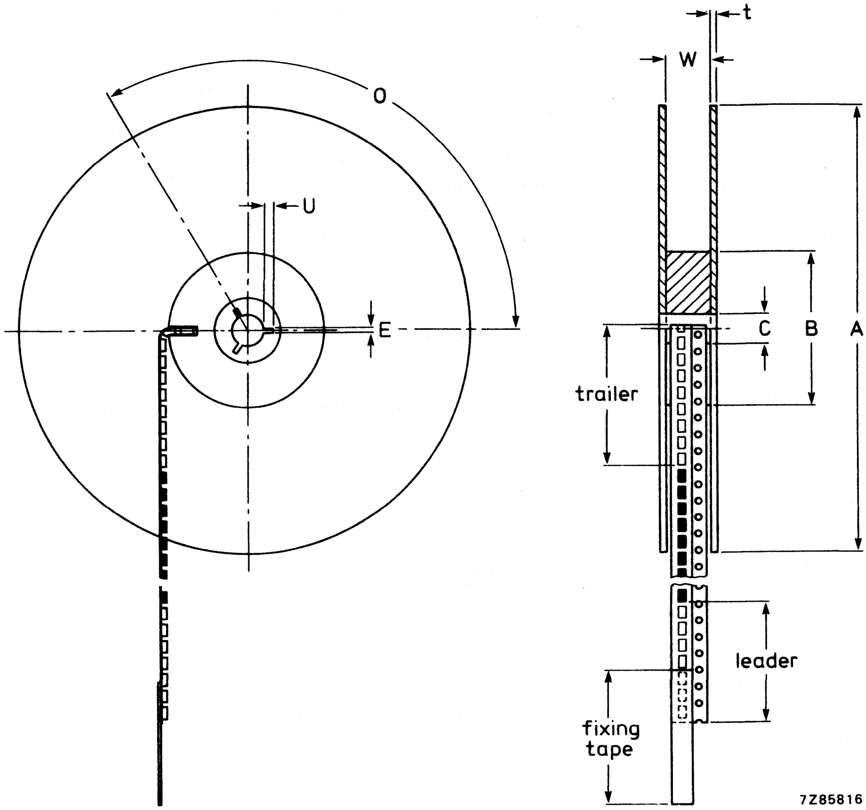


Fig. 2 Configuration of reel and flange (dimensions in mm).

Flange			tol.
diameter	A	180	+0 −2
thickness	t	1,5	+0,5 −0,1
space between flanges	W	9,5	±0,5

Hub			tol.
diameter	B	62	±1,5
spindle hole	C	12,75	+0,15 −0
key slit			
width	E	2	±0,5
depth	U	4	±0,5
location	O	120	degrees

Amount of devices per reel

The bandolier of a 180 mm reel contains at least 3000 devices with no more than 15 empty compartments (0,5%). Three consecutive empty places might be found provided this gap is followed by 6 consecutive devices.

The carrier tape (leader) starts with at least 75 empty positions (equivalent to 300 mm); the covering foil is at least 300 mm. In order to fix the carrier tape a self-adhesive tape of 20 to 50 mm is applied.

At the end of the bandolier (trailer) at least 75 empty positions (equivalent to a length of 300 mm) and 300 mm foil. For fixing onto the reel a self-adhesive tape of 20 to 50 mm is applied.

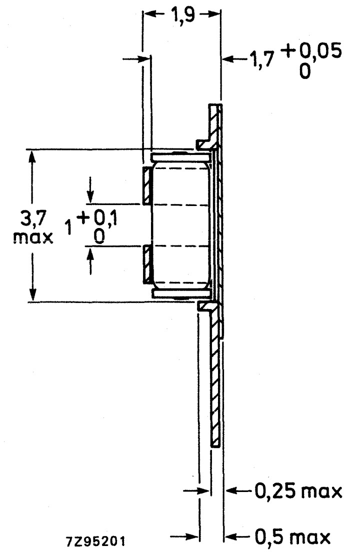


Fig. 3 Cross-sectional view of bandolier with SOD-80 devices.

Note: Testing of SOD-80 devices is possible in this tape.Total number of devices per reel is 2500.

HANDBOOK S1 PACKING

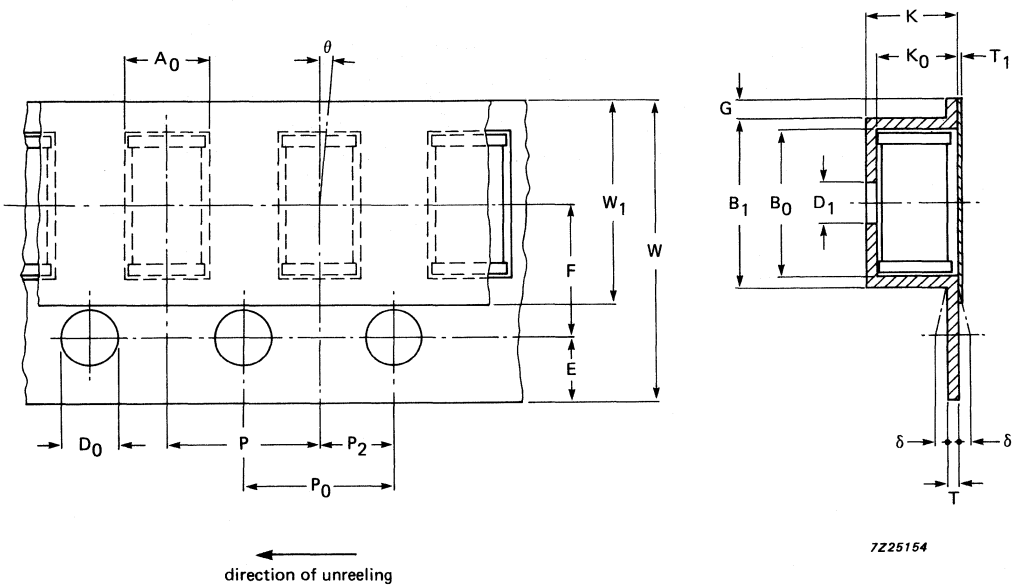


Fig. 4 Cross-sectional view of bandolier with SOD-87 devices.

Note: Testing of SOD-87 devices is not possible in this tape. Total number of devices per reel is 2000.

Compartment			tolerance
length	A_0	2.1	+ 0.3
width	B_0	3.8	min.
depth	K_0	2.1	+ 0.3
width outside	B_1	4.5	max.
pitch	P	4.0	± 0.1
deviation	θ	± 5°	max.
hole diameter	D_1	1.0	+ 0.1
Sprocket hole			
diameter	D_0	1.5	+ 0.1
pitch	P_0	4.0	± 0.1
distance	E	1.75	± 0.1
cumulative (10) pitch error		± 0.1	

Centre line dimensions			tolerance
length direction	P_2	2.0	± 0.05
width direction	F	3.5	± 0.1
Fixing tape			
width	W_1	5.5	max.
thickness	T_1	0.1	max
Carrier tape			
width	W	8	± 0.2
bending	δ	0.3	max.
thickness	T	0.4	max.
Overall thickness	K	2.5	max.

BANDOLIER AND REEL SPECIFICATION FOR AXIAL-LEADED DIODES

This specification concerns all axial-leaded diodes in this handbook.

The taped and reeled products fulfil the requirements of IEC 286-1: Tape packaging of components with axial leads on continuous tapes.

Dimensions in mm

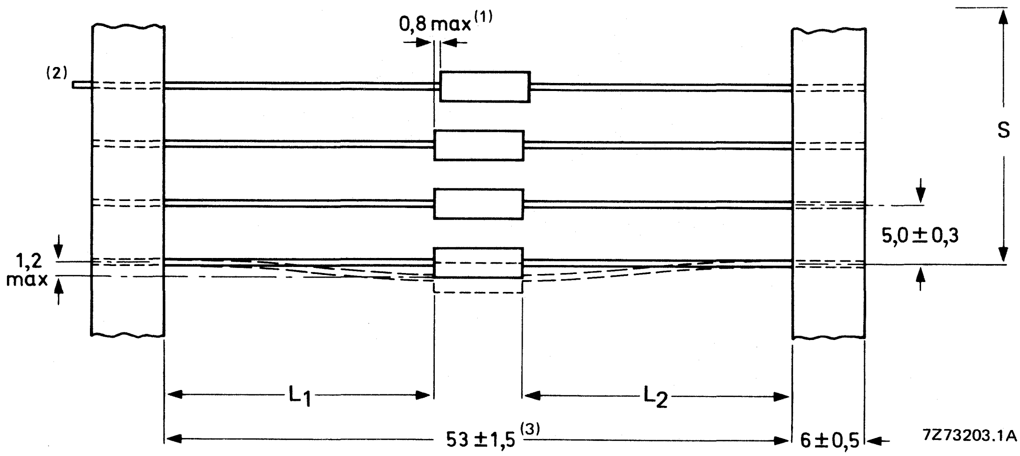


Fig. 1 Configuration of bandolier.

The red tape indicates the diode cathode side.

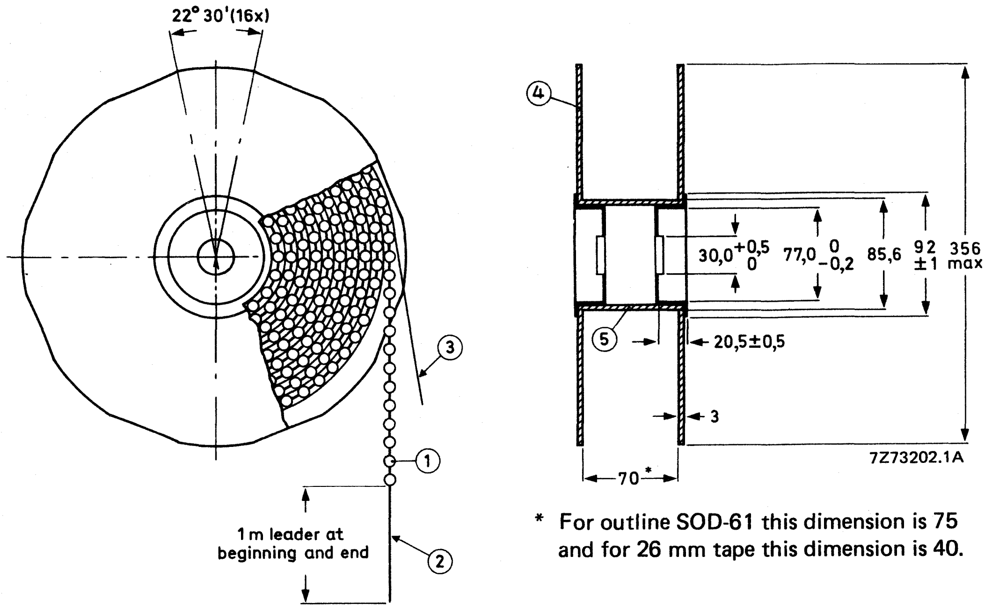
1. Displacement between any two diodes; for DO-34 maximum 0,4.
2. No protruding ends of lead except for BZX75 series maximum 1,2.
3. For outline SOD-61 this dimension is 58 ± 2 and for 26 mm tape this dimension is $26^{+1,5}_{-0}$

The cumulative space (S) measured over ten spacings = 50 ± 2; for 26 mm: 20 spacings (= 100 ± 2).

The diodes are centred so that $| L_1 - L_2 | \leqslant 1,2$ mm.

A black marker is printed on the white tape of the bandolier every 50 diodes.

The axial taping specification described above is compatible with automatic insertion equipment as manufactured by Universal, U.S.M. (Dynapert) and M.E.I. (Panasert).



* For outline SOD-61 this dimension is 75 and for 26 mm tape this dimension is 40.

Fig. 2 Reel dimensions (mm) for axial-leaded components.

(1) Diode
(2) Bandolier
(3) Paper
(4) Flange
(5) Cylinder

outline		quantity per reel, 52 mm tape
SOD-7	DO-7	7 000
SOD-27	DO-35	10 000 (B-zeners: 5000); see also Fig. 3
SOD-57	–	5 000
SOD-61	–	7 000 (additional packing in aluminium bag)
SOD-64	–	4 000
SOD-66	DO-41	5 000
SOD-68	DO-34	10 000; see also Fig. 3
SOD-81	–	5 000
SOD-84	–	5 000
SOD-91	–	10 000

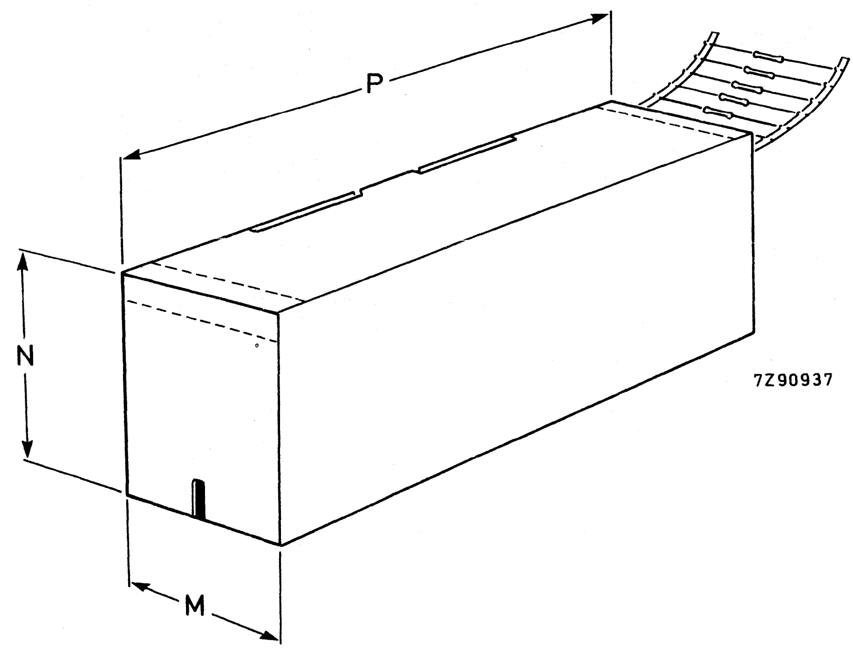


Fig. 3.

DO-34 and DO-35 axial-leaded components on 26 mm tape in ammo-boxes. Quantity: 5000 diodes per box. When ordering on 52 mm reel the last 3 digits of the catalogue number are 113: when ordering on 26 mm tape in ammo-pack the last 3 digits are 143.

	DO-34	DO-35
P	254	254 mm
N	63	77 mm
M	50	50 mm

BANDOLIER AND REEL SPECIFICATION FOR RADIAL-TAPED DIODES

Dimensions in mm

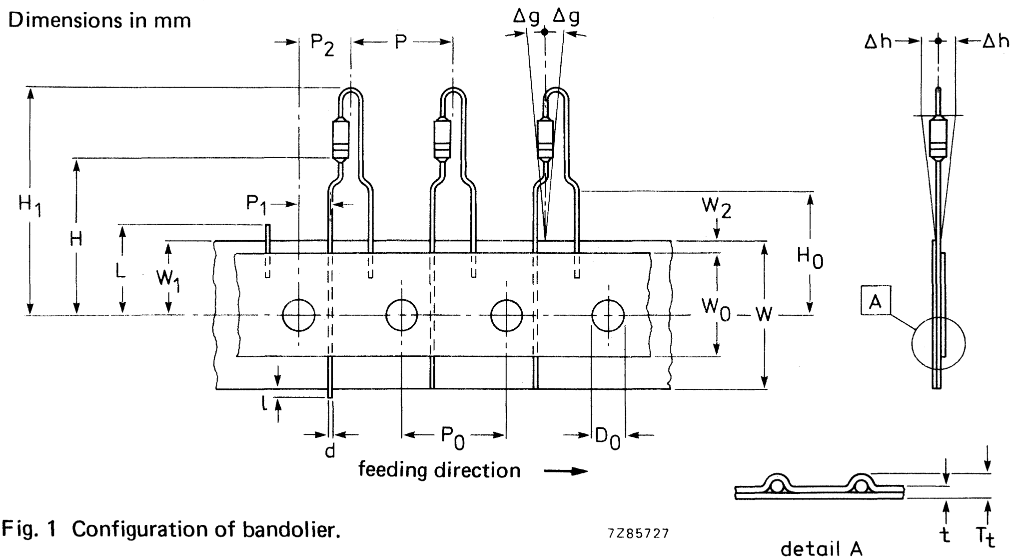


Fig. 1 Configuration of bandolier.

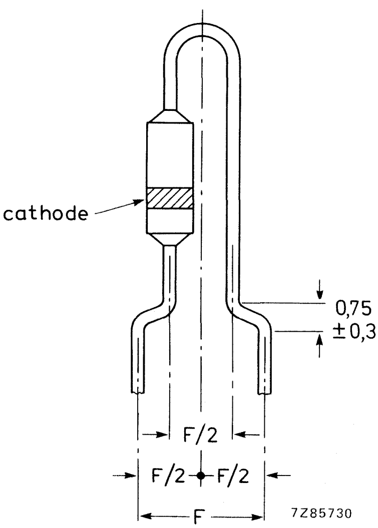


Fig. 2 Detail configuration of component shape.

break force of carrier tape > 15 N
extraction force > 5 N

$\Sigma\Delta P_0$	= deviation of 20 spacings	± 1
F	= lead-to-lead distance	$5{,}08\ ^{+0{,}6}_{-0{,}1}$
H_1	= top of component to tape centre	< 27,5
H	= bottom of component to tape centre	19 ± 1
H_0	= lead-wire clinch height	16 ± 0,5
L	= length of cropped lead	< 11
ℓ	= lead-wire protrusion	< 1
P	= pitch of components	12,7 ± 1
P_2	= feed hole centre to the middle of the leads	6,35 ± 1
P_1	= feed hole centre to lead	3,81 ± 0,7
P_0	= feed hole pitch	12,7 ± 0,3
T_t	= total tape thickness	< 1,5
t	= thickness tape + hold down tape	0,7 ± 0,2
D_0	= feed hole diameter	4 ± 0,2
W_2	= hold down tape position	0 to 1,5
W_0	= hold down tape width	> 12,5
W_1	= feed hole position	9 ± 0,5
W	= tape width	$18\ ^{+1{,}0}_{-0{,}5}$
Δ_g	= component alignment	$0 + 5^{o}$
Δ_h	= component alignment	± 2

This specification concerns radial-taped diodes in DO-34 and DO-35 envelopes. The taped and reeled products fulfil the requirements of IEC 286-2: Tape packaging of components with unidirectional leads.

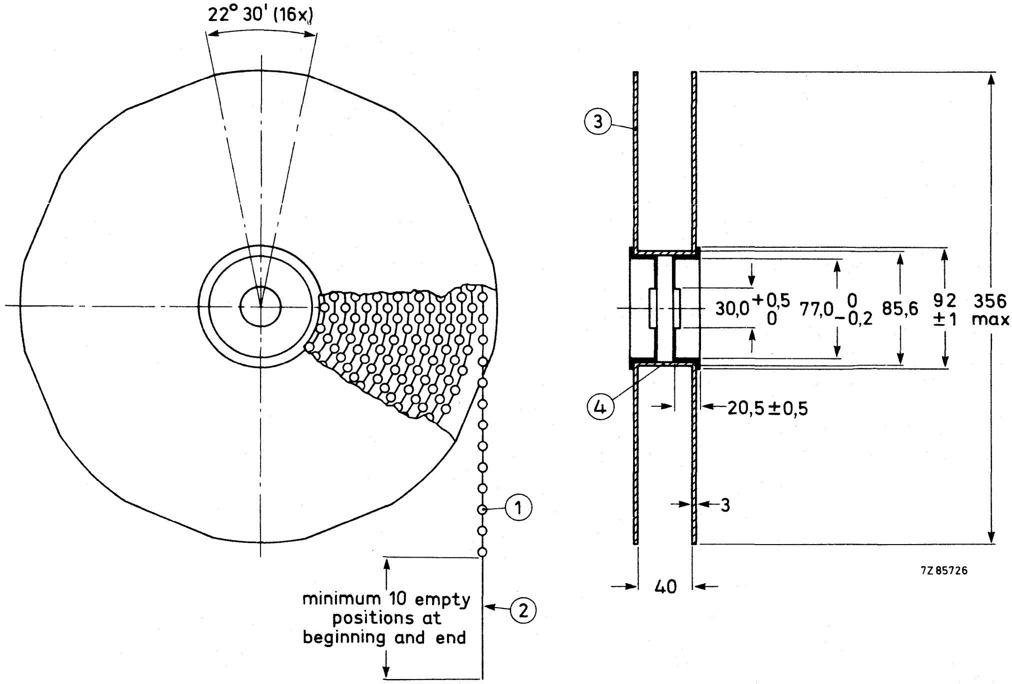
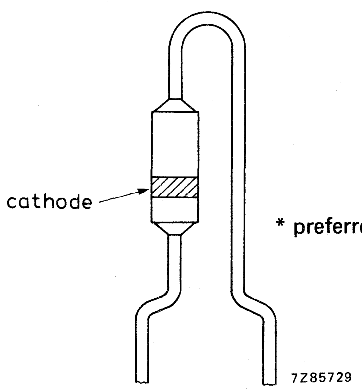


Fig. 3 Reel dimensions (mm) for radial-taped diodes.

(1) Diode
(2) Bandolier
(3) Flange
(4) Cylinder

Quantity per reel for DO-34 and DO-35 encapsulations 5000 diodes.

The diodes can be delivered on request with anode-leading* (+ leading) or with cathode-leading (— leading) configuration. The 11th and 12th digits of the 12 NC code are 16 and 36 for respectively anode-leading and cathode-leading.



* preferred

Fig. 4 + leading*.

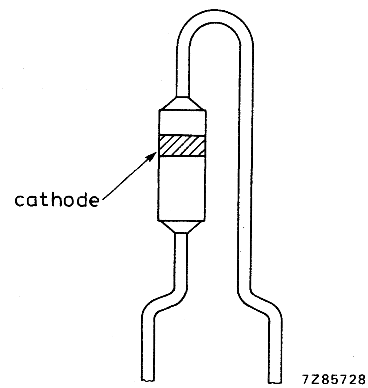


Fig. 5 — leading.

RULES FOR MOUNTING AND SOLDERING OF AXIAL-LEADED DEVICES*

Introduction

Excessive forces or temperatures applied to a diode may cause serious damage to the diode. To avoid damage when soldering and mounting the following rules should be followed.

General

Perpendicular forces on the body of the diode must be avoided.

Avoid sudden forces on the leads or body. These forces often are much higher than allowed.

High acceleration forces as a result of any shock (dropping on a hard surface for instance) must be prevented.

Bending

During bending the leads must be supported between body or stud and bending point.

Axial forces on the body during the bending process must not exceed 20 N.

Bending the leads through 90° is allowed at any distance from the body when it is possible to support the leads during bending without contacting the envelope or weldings.

Bending close to the body or stud without supporting the leads only is allowed if the bend radius is greater than 0,5 mm.

Twisting

Twisting the leads is allowed at any distance from the body or stud if the lead is properly clamped between body or stud and twisting point.

Without clamping, twisting the leads is only allowed at a distance of greater than 3 mm from the body; the torque angle must not exceed 30°.

Straightening

Straightening the leads is allowed if the applied pulling force in the axial direction does not exceed 20 N and the total duration is not longer than 5 seconds.

Soldering

Avoid any force on the body or leads during or just after soldering.

Do not correct the position of an already soldered device by pushing, pulling or twisting the body.

Prevent fast cooling after soldering.

* For Surface Mounted Devices (SMD's) please refer to Handbook "Surface Mounted Semiconductors".

Maximum allowable soldering time and minimum distance soldering point to seal for several envelopes

↓		→	Hand iron soldering mounted *otherwise than on printed-ciruit board* (max. solder temp.: 300 °C)		Hand iron soldering, dip, wave or other bath soldering, *mounted on printed-circuit board* (max. solder temp.: 300 °C)	
			time s	distance mm	time s	distance mm
SOD-7	DO-7	glass	3	5,0	5	5,0
SOD-27	DO-35	glass	3	0,5	5	0,5
SOD-57	–	glass	3	0,5	5	0,5
SOD-61	–	glass	3	2,0	5	2,0
SOD-64	–	glass	3	0,5	5	0,5
SOD-66	DO-41	glass	3	3,0	5	3,0
SOD-68	DO-34	glass	3	0,5	5	0,5
SOD-81	–	glass	3	0,5	5	0,5
SOD-84	–	glass	3	0,5	5	0,5
SOD-91	–	glass	3	0,5	5	0,5
TO-18	–	metal	3	0,5	5	0,5
TO-92 (SOD-69)	–	plastic	3	2,5	5	2,5

MOUNTING

If the rules for mounting and soldering are observed properly, the following mounting or process methods are allowed:

- Preheating of the printed-circuit board before soldering, up to a maximum of 100 °C.
- Flat mounting with the diode body in direct contact with the printed-circuit board with or without metal tracks on both sides and/or plated-through holes.
- Flat mounting with the diode body in direct contact with hot spots or hot tracks during soldering.
- Upright mounting with the diode body in direct contact with the printed-circuit board if the body is not in contact with metal tracks or plated-through holes.

General

Parts of the general mounting and soldering rules can be overruled by individual type mounting and soldering rules, mentioned with the type description.

SOD-64 ENVELOPES WITH PREFORMED LEADS

Some types of automatic insertion machines have problems bending the (relatively thick) leads of SOD-64 glass bead diodes. Therefore we have available the most popular SOD-64 types with preformed leads. They are supplied in bulk, in quantities of 1000 pieces.

The following types are available; (/20 indicates preformed leads):

Type	12NC
BYW95C/20	9336 215 90112
BYW96E/20	9336 765 50112
BY228/20	9336 215 80112
BYV28-150/20	9336 300 90112
BYV28-200/20	9336 104 40112

MECHANICAL DATA

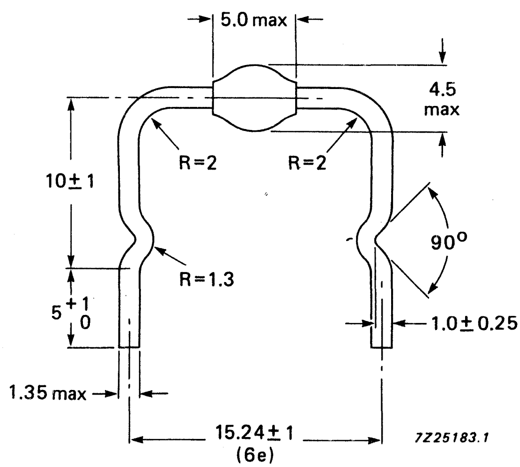


Fig. 9 SOD-64/20 with preformed leads.

SOLDERING RECOMMENDATIONS
SOT-23, SOT-143 AND SOT-89 ENVELOPES

SOT-23, SOT-143 and SOT-89 devices are ideally suited for placement onto thick and thin film substrates and printed circuit boards.

To assure reliable and consistent connections particular attention should be paid to:

1. **Flux**

   A non-active flux is recommended. Where active fluxes are employed, great care in subsequent substrate cleaning must be exercised.

2. **Metal-alloy solder or solder paste**

   Correct choice of solder alloy or solder paste to be employed e.g. 62% Sn, 36% Pb, 2% Ag or 60% Sn/40% Pb. Any paste used should contain at least 85% metal dry weight.

3. **Soldering temperature**

   This will vary according to the actual method employed.

REFLOW SOLDERING

The preferred technique for mounting microminiature components on hybrid thick and thin-film is the method of reflow soldering.

The tags of SOT-23, SOT-143 and SOT-89 envelopes are pre-tinned and the best results are obtained if a similar solder is applied to the corresponding soldering areas on the substrate. This can be done by either dipping the substrate in a solder bath or by screen printing a solder paste.
The maximum temperature of the leads or tab during the soldering cycle should not exceed 285 ^{o}C.
The most economic method of soldering is a process in which all different components are soldered simultaneously for example SOT-23, SOT-143 or SOT-89 devices, capacitors and resistors.

Having first been fluxed, all components are positioned on the substrate. The slight adhesive force of the flux is sufficient to keep the components in place. Solder paste contains a flux and has therefore good inherent adhesive properties which eases positioning of the components.

With the components in position the substrate is heated to a point where the solder begins to flow. This can be done on a heating plate or on a conveyor belt running through an infrared tunnel. The maximum allowed temperature of the plastic body of a device must be kept below 280 ^{o}C during the soldering cycle. For further temperature behaviour during the soldering process see Figs 2 and 3.

The surface tension of the liquid solder tends to draw the tags of the device towards the centre of the soldering area and has thus a correcting effect on slight mispositionings. However, if the layout leaves something to be desired the same effect can result in undesirable shifts; particularly if the soldering areas on the substrate and the components are not concentrally arranged. This problem can be solved using a standard contact pattern, which leaves sufficient scope for the self-positioning effect (see Figs 4 and 5).

After cooling the connections may be visually inspected and, where necessary, repaired with a light soldering iron. Finally any remaining flux must be removed carefully.

WAVE SOLDERING

The normal (dual) wave soldering process can also be aplied to SOT-23 and SOT-143 envelopes
We do not recommend SOT-89 for wave soldering.

IMMERSION SOLDERING

Where a complete substrate or printed circuit board is immersed in solder:
a. The temperature of the soldering bath should not exceed 280 °C.
b. The duration of the soldering cycle should not exceed 10 seconds.
c. Forced cooling may be applied (see Fig. 1).

HAND SOLDERING

It is possible to solder microminiature devices with a light hand-held soldering iron, but this method has obvious drawbacks and should therefore be restricted to laboratory use and/or incidental repairs on production circuits.

1. It is time-consuming and expensive.
2. The device cannot be positioned accurately and therefore the connecting tags may come into contact with the substrate and damage it.
3. There is a great risk of breaking either substrate or even internal connections inside the encapsulation.
4. The envelope may be damaged by the iron.

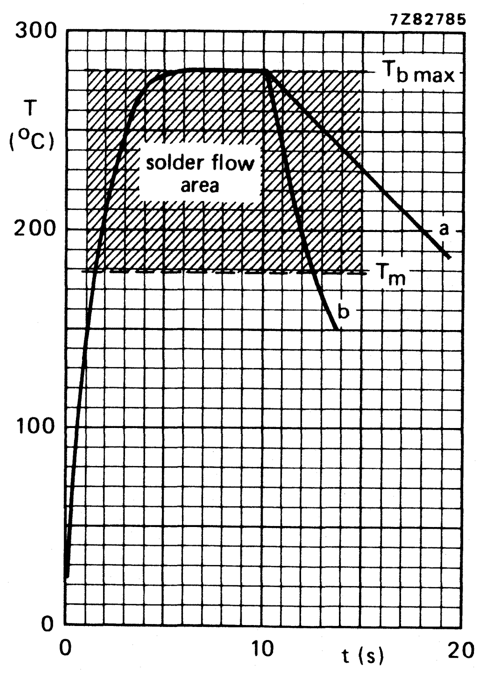
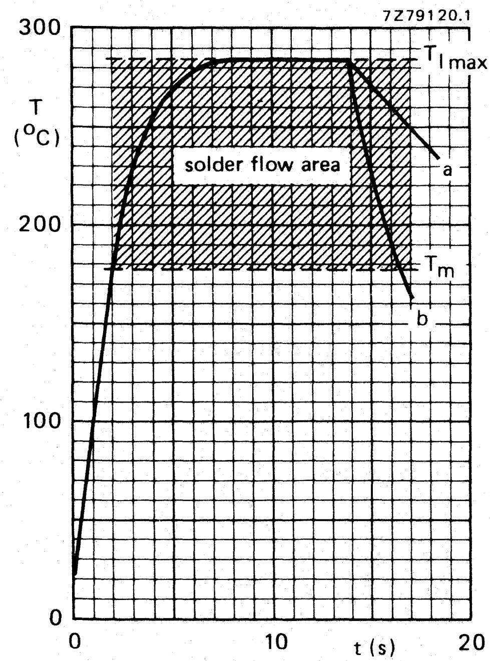


Fig. 1 Device temperature during *immersion* soldering.

Maximum time of immersion in soldering bath is 10 seconds at an ambient temperature of 25 °C.
a = free convection cooling; b = forced cooling.
$T_{b\,max}$ = maximum bath temperature (280 °C).
T_m = melting temperature of solder (179 °C).



a = free convection cooling.

b = permissible forced cooling.

$T_{l\,max}$ = Maximum lead or tab temperature = 285 °C.

T_m = Melting point of the solder is 179 °C.

T_{amb} = 25 °C.

Time of heat supply:
without preheating max. 14 s
with preheating max. 10 s

Maximum time of preheating 45 s

Fig. 2 Reflow soldering without preheating.

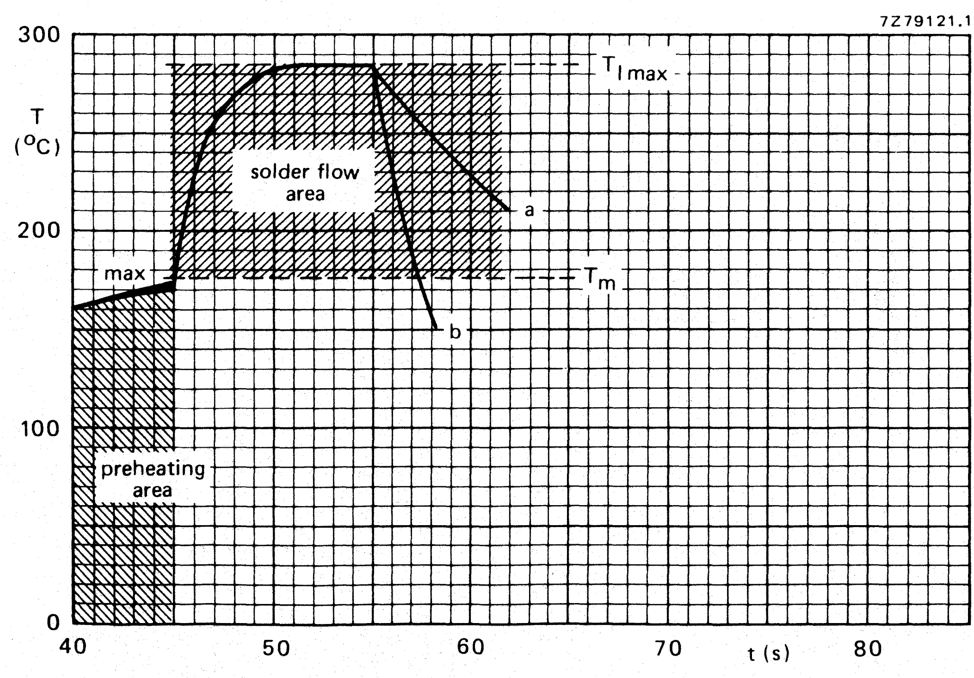


Fig. 3 Reflow soldering with preheating.

Minimum required dimensions of metal connection pads on hybrid thick and thin-film substrates.

Dimensions in mm

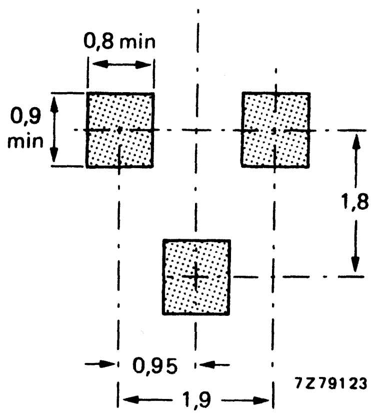


Fig. 4 SOT-23 pattern.

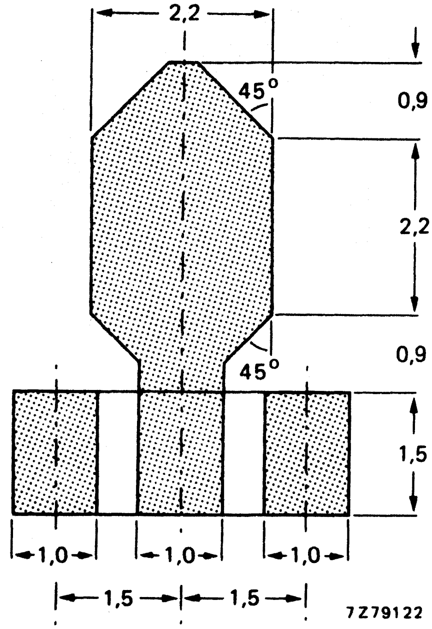


Fig. 5 SOT-89 pattern.

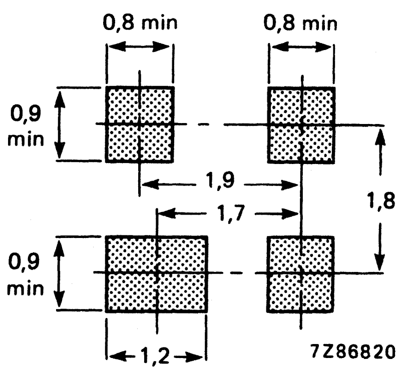


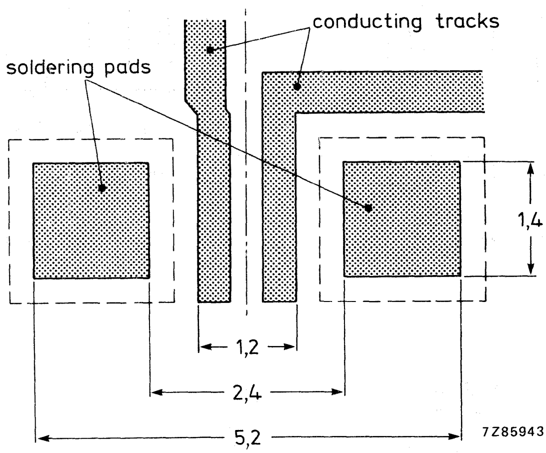
Fig. 6 SOT-143 pattern.

SOLDERING RECOMMENDATIONS
SOD-80 ENVELOPE

The layout shown below is intended for use with mounting of diodes having a SOD-80 envelope onto a printed circuit board in those cases where the diode is glued to the p.c. board first and soldered afterwards.

The dimensions given may be smaller if the diode in question is not fixed to the substrate prior to soldering. The position of the SOD-80 device is then self-adjusted during the soldering process.

Dimensions in mm



SOLDERING RECOMMENDATIONS
SOD-87 ENVELOPE

The layout shown below is intended for use with mounting of diodes having a SOD-87 envelope onto a printed-circuit board in those cases where the diode is glued to the printed-circuit board first and soldered afterwards.

The dimensions given may be smaller if the diode in question is not fixed to the substrate prior to soldering.

Dimensions in mm

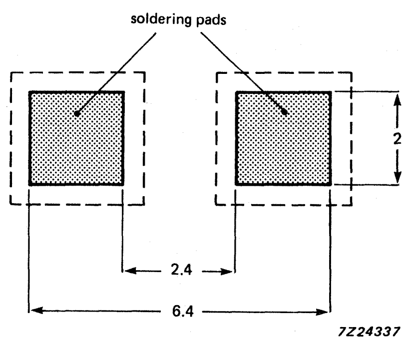


Fig. 2.

For more details refer to Handbook S7 "Soldering recommendations".

THERMAL CHARACTERISTICS FOR SOT-23 AND SOT-143 ENVELOPES

The heat generated in a semiconductor chip normally flows by various paths to the surroundings (ambient).

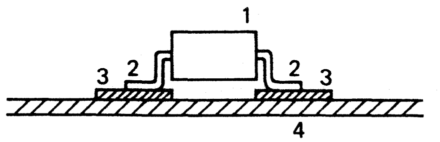


Fig. 1.

1. Heat radiation from the envelope to ambient (1).
   This heat transfer can be neglected when the envelope is mounted on a substrate or printed circuit board.
2. Heat transmission via leads (2) soldering points (3) and substrate (4).

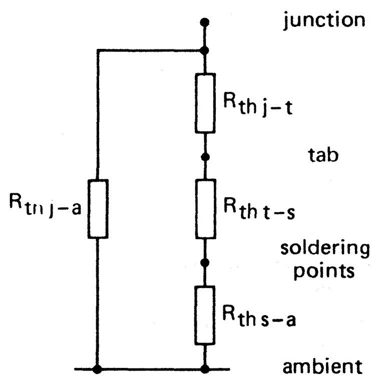


Fig. 2 Thermal behaviour of heat flow when the device is mounted on a substrate or printed circuit board.

$R_{th\ j\text{-}t}$ = Thermal resistance from junction to tab.

$R_{th\ t\text{-}s}$ = Thermal resistance from tab to soldering points.

$R_{th\ s\text{-}a}$ = Thermal resistance from soldering points to ambient.

$R_{th\ j\text{-}a}$ = Thermal resistance from junction to ambient.

Heat transfer directly from envelope to ambient

This depends on the difference between the temperatures of envelope and the surroundings. When the device is mounted on a substrate or printed circuit board direct heat flow can usually be neglected in relation to the heat flow via leads and substrate.
Thus the thermal model can be as in Fig. 3.

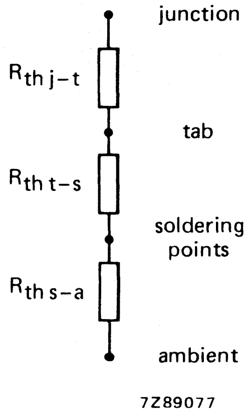


Fig. 3 Basic thermal model.

Heat transfer from junction to tab

This is an internal heat transfer and has been measured. In general it is:

for high-frequency transistors, low-power diodes and (MOS) FETs	60 K/W
for low-frequency and switching transistors	50 K/W
for low-frequency medium-power transistors	30 K/W

Heat transfer from tab to soldering points

This value has also been measured for SOT-23 with $P_{tot} < 350$ mW	280 K/W
for types of semiconductors in this envelope with $P_{tot} < 425$ mW	260 K/W
for types of semiconductors in a SOT-143 envelope this value is	310 K/W

Heat transfer from soldering points to ambient

This depends on the shape and material of tracks and substrate. In figures 4 and 5 standard mounting conditions are given to set up the maximum power ratings for SOT-23 and SOT-143 encapsulations.

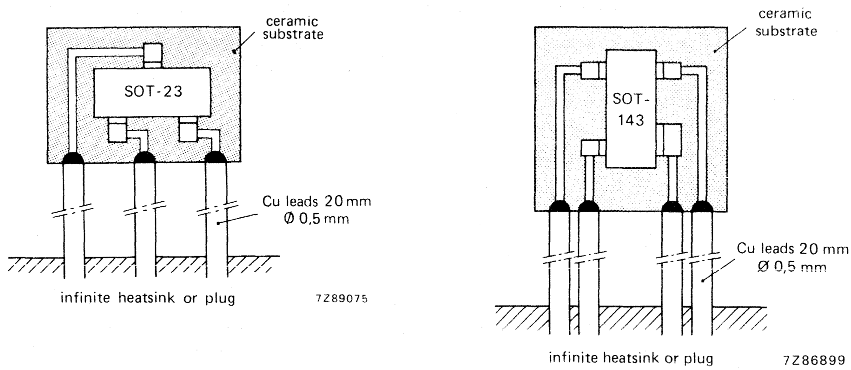


Fig. 4 Test circuits SOT-23 and SOT-143 mounting conditions on a ceramic substrate.

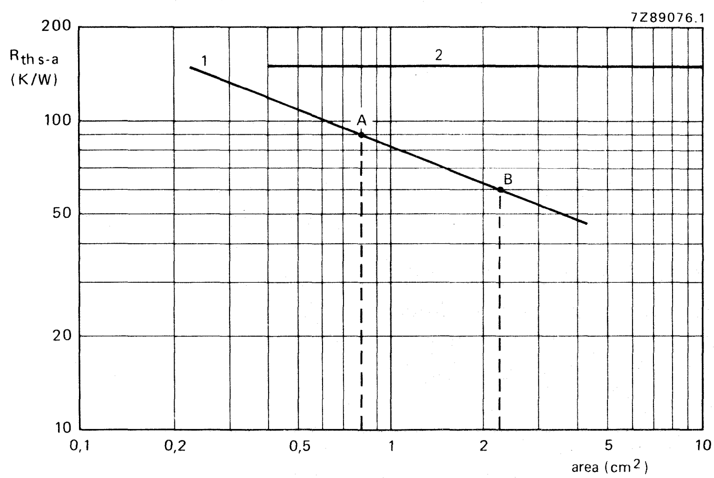


Fig. 5 Heat transfer from soldering points to ambient.

1. Ceramic substrate

Point A on the curve in Fig. 5 is for an area of the ceramic substrate of 8 mm x 10 mm x 0,7 mm for the maximum rating of all high-frequency, low-frequency and switching transistors and also for all diodes.
Point B on the curve in Fig. 5 is for an area of the ceramic substrate of 15 mm x 15 mm x 0,7 mm for the maximum rating of low-frequency medium-power semiconductors.

2. Printed circuit board

$R_{th\ s\text{-}a}$ = 150 K/W for SOT-23 and SOT-143 envelopes mounted on a printed circuit board.

The values for the thermal resistance from junction to tab, and tab to soldering points, are given earlier and in Fig. 5.
The formula for devices in SOT-23 with one crystal can be generalized:

$$T_j = P\,(R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$$

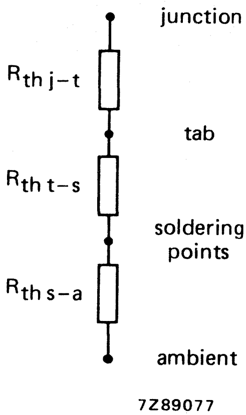


Fig. 6 Thermal model of SOT-23 envelopes with one crystal.

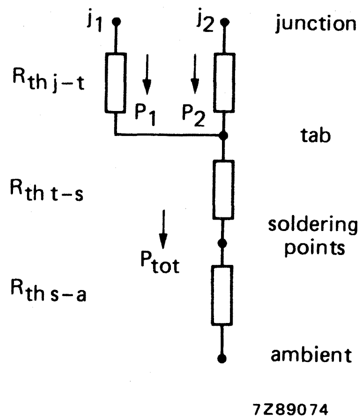


Fig. 7 Thermal model of SOT-23 envelopes with two crystals (double diode).

The formulae for devices with two crystals (double diodes) are:

$$T_{tab} = P_{tot} \cdot (R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb} = P_{tot}\,(280 + 90) + T_{amb}$$

$$T_{j1} = (P_1 \times R_{th\ j\text{-}t}) + T_{tab} = P_1 \cdot 60 + T_{tab}$$

$$T_{j2} = (P_2 \times R_{th\ j\text{-}t}) + T_{tab} = P_2 \cdot 60 + T_{tab}$$

As mentioned with Fig. 3:

$R_{th\ j\text{-}t}$ for diodes is 60 K/W.

$R_{th\ s\text{-}a}$ (area 8 mm x 10 mm x 0,7 mm) = 90 K/W.

$R_{th\ t\text{-}s}$ for all semiconductors in SOT-23 = 280 K/W.

Thus:

$$T_{j1} = 60\,P_1 + 370\,P_{tot} + T_{amb}.$$

$$T_{j2} = 60\,P_2 + 370\,P_{tot} + T_{amb}.$$

THERMAL MODEL

Figure 1 illustrates the various components of thermal resistance for a diode mounted with symmetrical lead length.

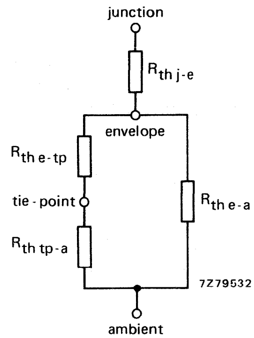


Fig. 1 Thermal resistance model.

The values for these various parameters depend on the outline of the diode, the leadlength and the method used to mount the device on the printed circuit board. Some useful values are shown in Table 1.

Table 1 Thermal resistance values (K/W)

thermal resistance	mounting condition	SOD-81	SOD-84	SOD-57	SOD-64	note
$R_{th\ j\text{-}e}$ junction-envelope		32	22	18	12	
$R_{th\ e\text{-}tp}$ envelope-tie-point	lead length (mm)					
	5	15	15	15	7	
	10	30	30	30	14	
	15	45	45	45	21	
	20	60	60	60	28	
	25	75	75	75	35	
$R_{th\ e\text{-}a}$ envelope-ambient	length length (mm)					
	5	600	440	580	410	
	10	450	350	445	300	
	15	370	300	350	230	
	20	310	265	290	185	
	25	265	240	245	155	
$R_{th\ tp\text{-}a}$ tie-point-ambient	mounted on a 1,5 mm thick epoxy-glass printed circuit board with a copper thickness $\geqslant$ 40 μm (Fig. 2)	70	70	70	70	1. mounted as in Fig. 2
		55	55	55	55	2. mounted with Cu laminate per lead of 1 cm^2
		45	45	45	45	3. mounted with Cu laminate per lead of 2,25 cm^2

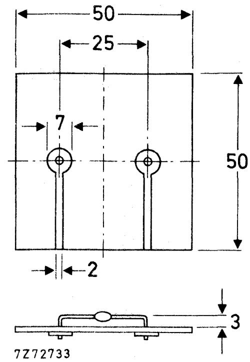


Fig. 2 Mounted on a printed-circuit board.

Using this model, values for the thermal resistance from junction to ambient can be calculated using the formula:

$$R_{th\ j\text{-}a} = R_{th\ j\text{-}e} + \frac{R_{th\ e\text{-}a}\,(R_{th\ e\text{-}tp} + R_{th\ tp\text{-}a})}{R_{th\ e\text{-}a} + R_{th\ e\text{-}tp} + R_{th\ tp\text{-}a}}$$

	SOD-81	SOD-84	SOD-57	SOD-64	Note
$R_{th\ j\text{-}a}$	120 K/W	105 K/W	100 K/W	75 K/W	Mounted on 1,5 mm thick epoxy-glass p.c. board with copper thickness ⩾ 40 μm; Fig. 2.
$R_{th\ j\text{-}tp}$	60 K/W	50 K/W	46 K/W	25 K/W	Lead length = 10 mm.

Note:

The junction temperature can then be calculated by using dissipation graphs and the above thermal model.

CUSTOM MADE EHT STACKS

Based on our experience gained with high voltage stacks in the professional market we are offering a wide range of custom-made EHT stacks for industrial, military and aerospace applications;
e.g.

- X-ray equipment
- E-beam microscopes
- Automobile ignition systems
- Conventional (50 Hz) microwave ovens
- SMPS-microwave ovens
- Ion implanters
- Radar equipment
- Bar-code readers

All stacks are in a glass-bead envelope offering the following features;

- Hermetic sealing
- Glass passivation for excellent stability
- High-temperature metallurgical bonds
- Low leakage currents enabling junction temperatures up to 175 °C
- Well-matched coefficients of expansion of component materials
- Possibility of guaranteed controlled avalanche properties

Encapsulation of the glass-bead stack in plastic, to increase the isolation distance, is also possible.

Some examples of custom made stacks:

OF746: V_{RWM}max. 5 kV; $t_{rr} < 30$ ns; $I_{F(AV)}$max. 0.18 A at T_{oil} = 70 °C (SOD-83A)

OF824: V_{RWM}max. 2.5 kV; $t_{rr} < 350$ ns; $I_{F(AV)}$max. 1.1 A at T_{oil} = 45 °C (SOD-83A)

OF867: V_{RWM}max. 12 kV; $t_{rr} < 350$ ns; $I_{F(AV)}$max. 0.225 A at T_{oil} = 45 °C (SOD-83B)

QUICK REFERENCE DATA (type dependent)

Crest working reverse voltage	V_{RWM}	max.	2 to 20	kV
Average forward current	$I_{F(AV)}$	max.	up to 1.5	A
Reverse recovery time	t_{rr}	max.	30, 75, 150	ns
			350 and 5000	ns
Junction temperature	T_j	max.	175	°C

MECHANICAL DATA (see next page)

MECHANICAL DATA

Dimensions in mm

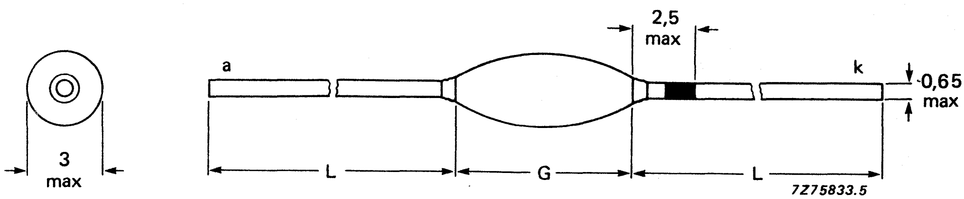


Fig. 1 **SOD-61** G = 11,5 max.; L = 29,5 min.

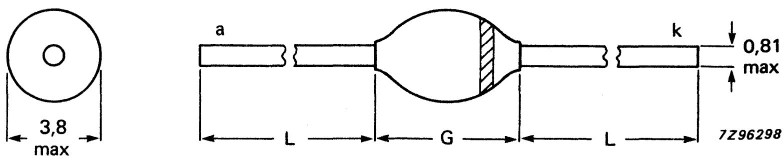


Fig. 2 **SOD-88** G = 8 max.; L = 26 min. (A-version).
G = 11 max.; L = 24,5 min. (B-version).

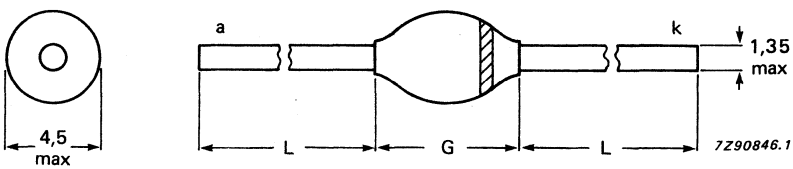


Fig. 3 **SOD-83** G = 7,5 max.; L = 26,5 min. (A-version).
G = 11 max.; L = 24,5 min. (B-version).

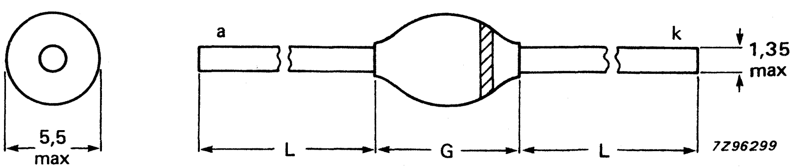


Fig. 4 **SOD-89** G = 7 max.; L = 26,5 min. (A-version).
G = 10 max.; L = 25 min. (B-version).

AVERAGE CURRENT VERSUS WORKING REVERSE VOLTAGE AT VARIOUS REVERSE RECOVERY TIME PARAMETERS

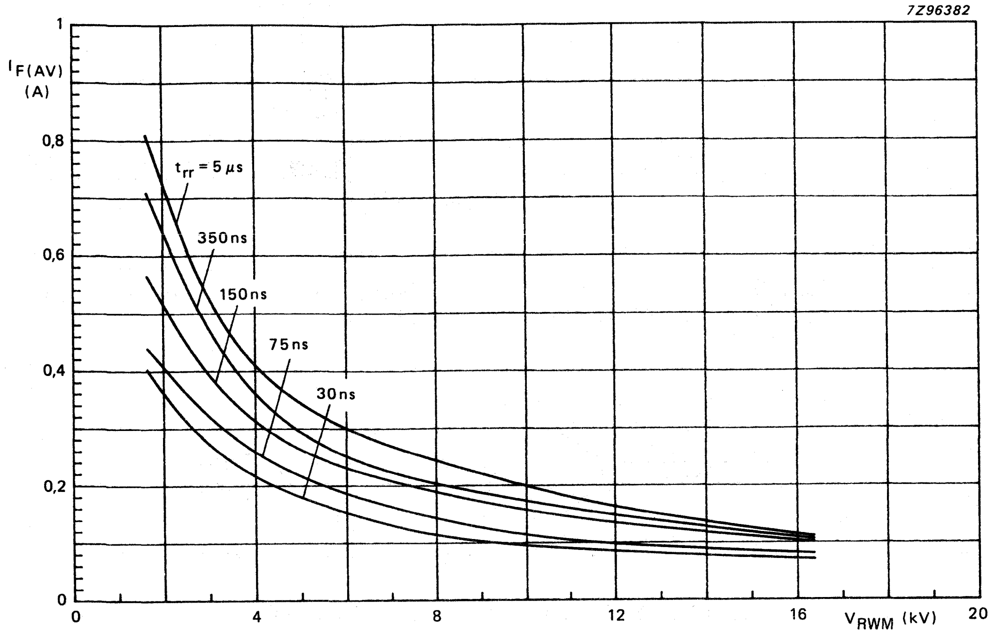


Fig. 5 **SOD-61** $R_{th\ j\text{-}oil}$ = 35 K/W; P_{RSM} = 200 W/kV at 10 μs; T_{oil} = 45 °C; duty cycle for V_{RWM} = 0,5; leakage dissipation included.

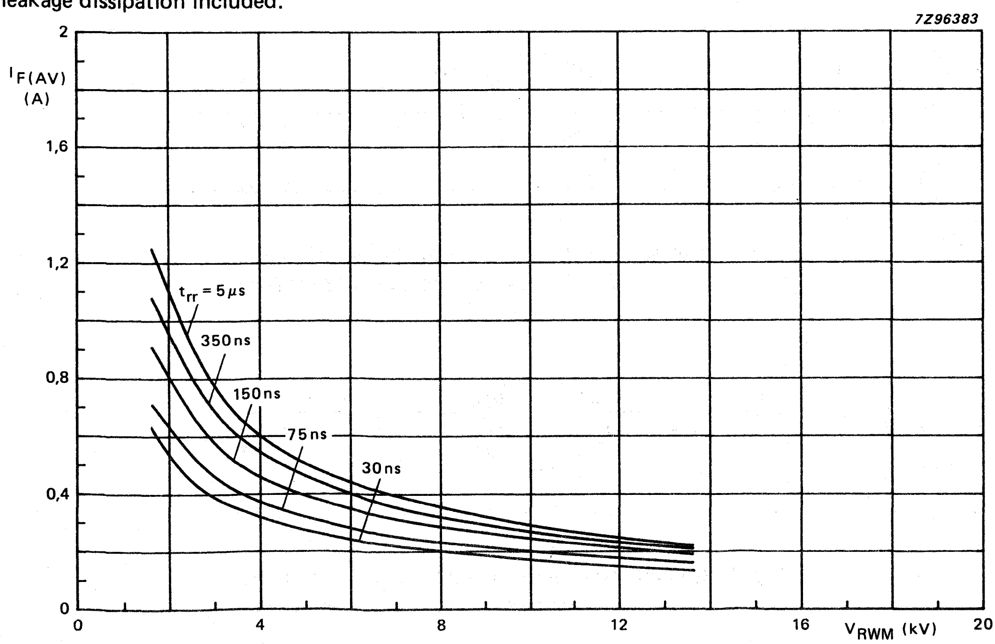


Fig. 6 **SOD-88** $R_{th\ j\text{-}oil}$ = 25 K/W; P_{RSM} = 400 W/kV at 10 μs; T_{oil} = 45 °C; duty cycle for V_{RWM} = 0,5; leakage dissipation included.

AVERAGE CURRENT VERSUS WORKING REVERSE VOLTAGE AT VARIOUS REVERSE RECOVERY TIME PARAMETERS

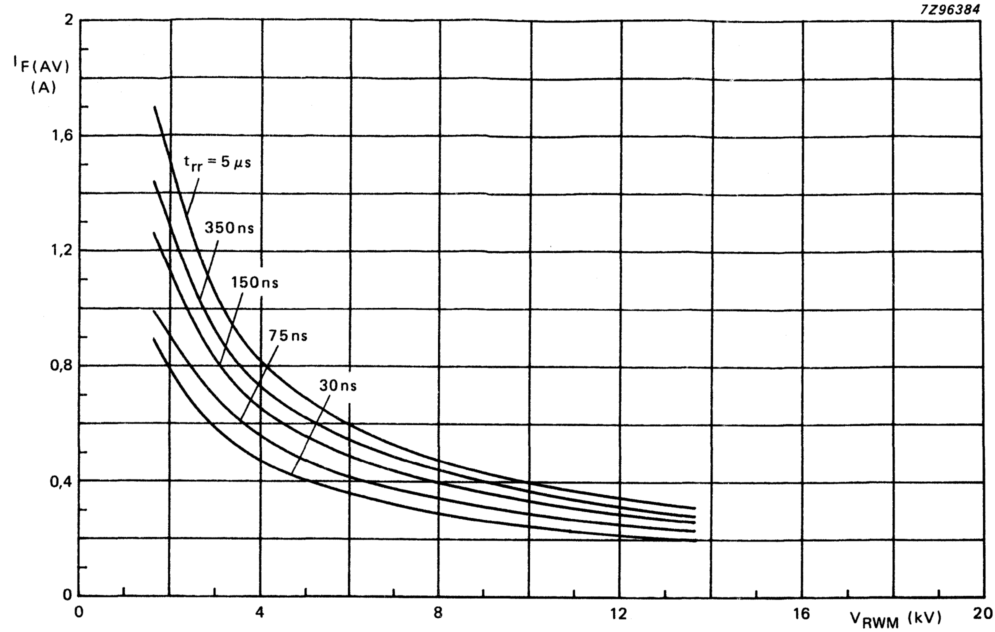


Fig. 7 **SOD-83** $R_{th\ j\text{-}oil}$ = 20 K/W; P_{RSM} = 800 W/kV at 10 μs; T_{oil} = 45 °C; duty cycle for V_{RWM} = 0,5; leakage dissipation included.

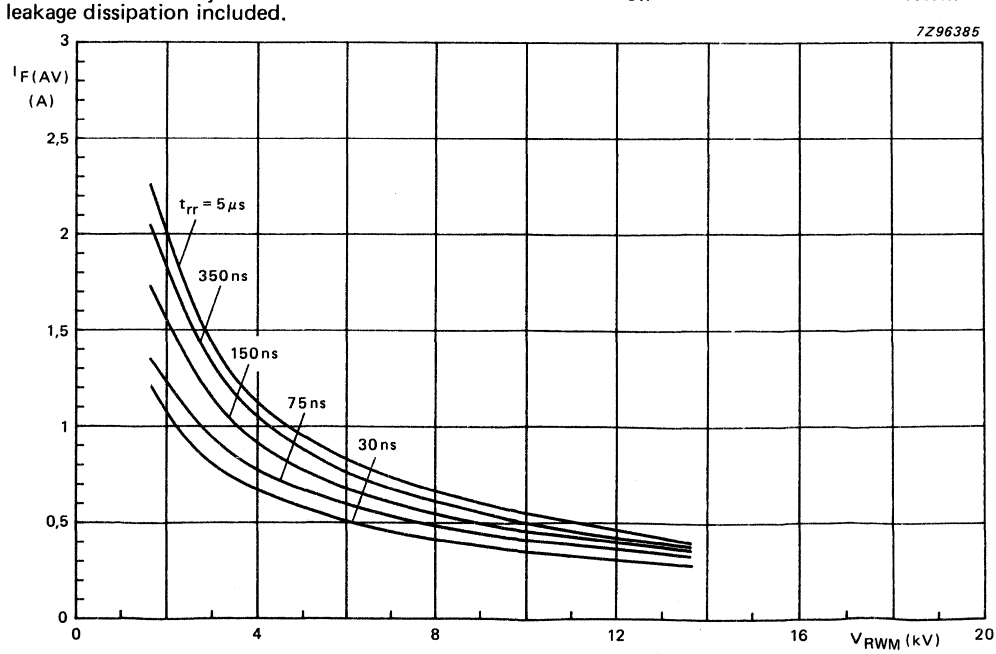


Fig. 8 **SOD-89** $R_{th\ j\text{-}oil}$ = 16 K/W; P_{RSM} = 1500 W/kV at 10 μs; T_{oil} = 45 °C; duty cycle for V_{RWM} = 0,5; leakage dissipation included.

DEVICE DATA

GENERAL PURPOSE DIODE

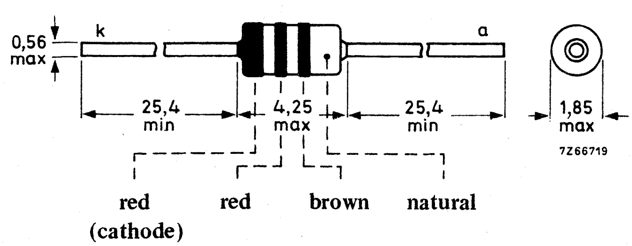
Silicon planar epitaxial diode in a DO-35 envelope; intended for general purpose and can also be used as regulator.

QUICK REFERENCE DATA				
Repetitive peak reverse voltage	V_{RRM}	max.	10	V
Repetitive peak forward current	I_{FRM}	max.	400	mA
Storage temperature	T_{stg}		−65 to +200	°C
Junction temperature	T_j	max.	200	°C
Thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$	=	**500**	K/W
Forward voltage at I_F = 0,1 mA	V_F		460 to 520	mV
I_F = 1,0 mA	V_F		560 to 620	mV
I_F = 10 mA	V_F		680 to 750	mV
I_F = 100 mA	V_F		825 to 950	mV
Diode capacitance at V_R = 0; f = 1 MHz	C_d	<	2,5	pF
Reverse recovery time when switched from I_F = 10 mA to I_R = 60 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	4	ns

MECHANICAL DATA

Dimensions in mm

DO-35



RATINGS Limiting values in accordance with the Absolute Maximum System (IEC 134)

Repetitive peak reverse voltage	V_{RRM}	max.	10	V
Average rectified forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	200	mA [1]
Forward current (d. c.)	I_F	max.	200	mA
Repetitive peak forward current	I_{FRM}	max.	400	mA
Non-repetitive peak forward current t = 1 µs	I_{FSM}	max.	4000	mA
t = 1 s	I_{FSM}	max.	1000	mA
Storage temperature	T_{stg}		−65 to +200	°C
Junction temperature	T_j	max.	200	°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	**500**	K/W

CHARACTERISTICS $T_j = 25\ ^oC$

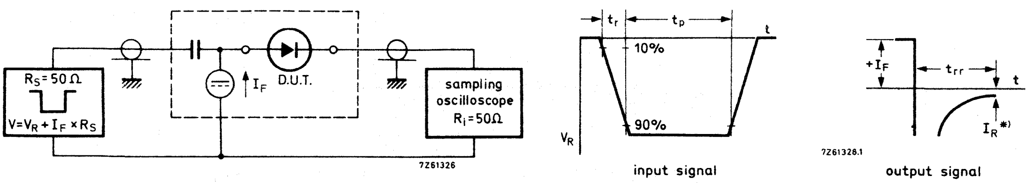
Forward voltage				
I_F = 0, 1 mA	V_F		460 to 520	mV
I_F = 1, 0 mA	V_F		560 to 620	mV
I_F = 5, 0 mA	V_F		640 to 700	mV
I_F = 10 mA	V_F		680 to 750	mV
I_F = 100 mA	V_F		825 to 950	mV
Reverse current				
V_R = 10 V	I_R	<	1500	nA
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	2, 5	pF

[1]) For sinusoidal operation $I_{F(AV)}$ = 130 mA.

CHARACTERISTICS (continued) $T_j = 25\ ^oC$

Reverse recovery time when switched from
$I_F = 10$ mA to $I_R = 60$ mA; $R_L = 100\ \Omega$;
measured at $I_R = 1$ mA t_{rr} < 4 ns

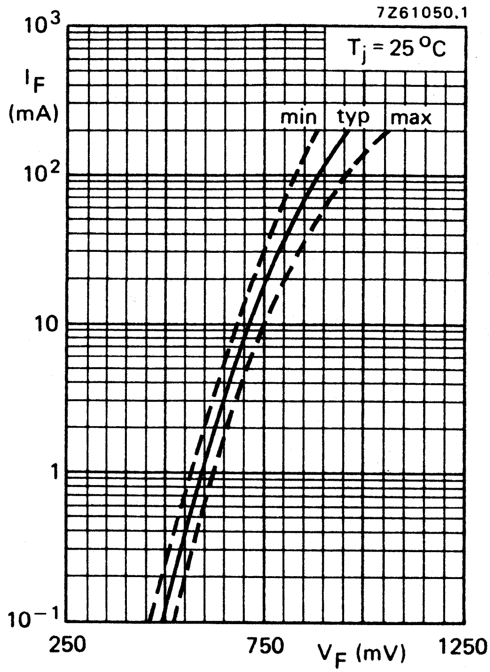
Test circuit and waveforms :



Input signal : Rise time of the reverse pulse	t_r = 0,6 ns	*) I_R = 1 mA
Reverse pulse duration	t_p = 100 ns	
Duty factor	δ = 0,05	

Oscilloscope : Rise time t_r = 0,35 ns

Circuit capacitance C ≤ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)


7Z61050.1
$T_j = 25\ ^oC$
I_F
(mA)
10^3
10^2
10
1
10^{-1}
min
typ
max
250
750
V_F (mV)
1250

GENERAL PURPOSE DIODE

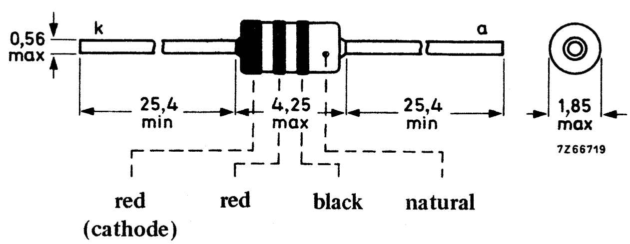
Silicon planar epitaxial diode in a DO-35 envelope; intended for general purposes.

QUICK REFERENCE DATA				
Continuous reverse voltage	V_R	max.	30	V
Repetitive peak forward current	I_{FRM}	max.	400	mA
Storage temperature	T_{stg}	−65 to +200		^oC
Junction temperature	T_j	max.	200	^oC
Thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$	=	500	K/W
Forward voltage at I_F = 1 mA	V_F	<	625	mV
I_F = 100 mA	V_F	<	950	mV
I_F = 200 mA	V_F	<	1050	mV
Diode capacitance at V_R = 0; f = 1 MHz	C_d	<	2,5	pF
Reverse recovery time when switched from I_F = 10 mA to I_R = 60 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	4	ns

MECHANICAL DATA

Dimensions in mm

DO-35



RATINGS Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	30	V
Repetitive peak reverse voltage	V_{RRM}	max.	30	V
Average rectified forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	200	mA [1]
Forward current (d.c.)	I_F	max.	200	mA
Repetitive peak forward current	I_{FRM}	max.	400	mA
Non-repetitive peak forward current t = 1 μs	I_{FSM}	max.	4000	mA
t = 1 s	I_{FSM}	max.	1000	mA
Storage temperature	T_{stg}	−65 to +200		°C
Junction temperature	T_j	max.	200	°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	500	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage				
I_F = 1 mA	V_F	<	625	mV
I_F = 100 mA	V_F	<	950	mV
I_F = 200 mA	V_F	<	1050	mV
Reverse current				
V_R = 10 V	I_R	<	25	nA
V_R = 30 V	I_R	<	200	nA
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	2,5	pF

1) For sinusoidal operation $I_{F(AV)}$ = 130 mA.

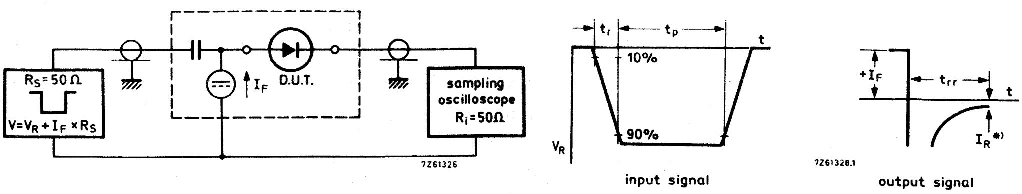
CHARACTERISTICS (continued) $T_j = 25\ ^oC$

Reverse recovery time when switched from

I_F = 10 mA to I_R = 60 mA; R_L = 100 Ω;

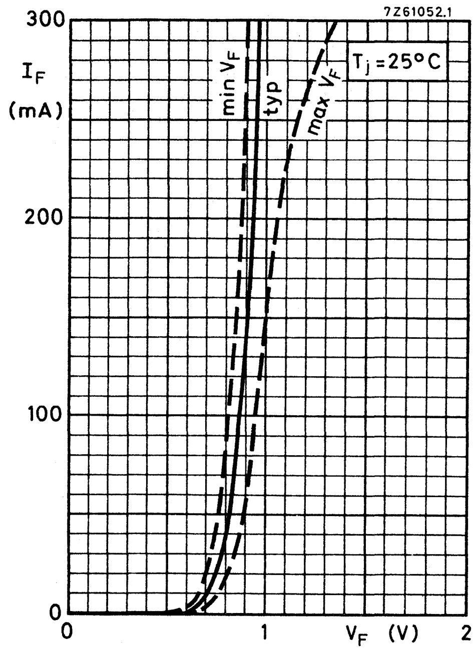
measured at I_R = 1 mA t_{rr} < 4 ns

Test circuit and waveforms:



Input signal	: Rise time of the reverse pulse	t_r = 0,6 ns	*) I_R = 1 mA
	Reverse pulse duration	t_p = 100 ns	
	Duty factor	δ = 0,05	
Oscilloscope	: Rise time	t_r = 0,35 ns	

Circuit capacitance C ≤ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)


7Z61052.1
300
200
100
0
I_F
(mA)
min V_F
typ
max V_F
$T_j = 25\,°C$
0
1
V_F (V)
2

SILICON A.M. BAND SWITCHING DIODE

The BA223 is a switching diode in whiskerless glass encapsulation. It is intended for band switching in a.m. radio receivers.

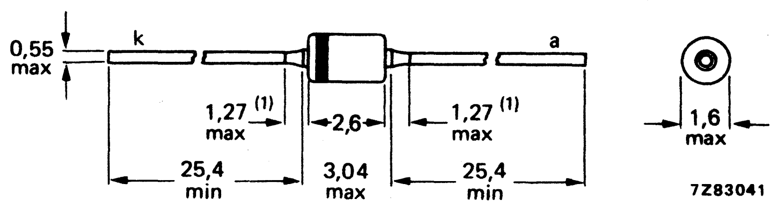
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	20 V
Forward current (d.c.)	I_F	max.	50 mA
Junction temperature	T_j	max.	150 °C
Diode capacitance at f = 1 MHz V_R = 6 V	C_d	<	3,5 pF
Series resistance at f = 1 MHz I_F = 10 mA	r_D	<	1,5 Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 DO-34 (SOD-68).



(1) Lead diameter in this zone uncontrolled.

Cathode indicated by coloured band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	20	V
Forward current (d.c.)	I_F	max.	50	mA
Storage temperature	T_{stg}		−55 to +150	°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0,5	K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage				
I_F = 50 mA	V_F	$<$	1,0	V
Reverse current				
V_R = 20 V	I_R	$<$	100	nA
V_R = 20 V; T_j = 125 °C	I_R	$<$	20	μA
Diode capacitance at f = 1 MHz				
V_R = 6 V	C_d	$<$	3,5	pF
Series resistance at f = 1 MHz				
I_F = 10 mA	r_D	$<$	1,5	Ω

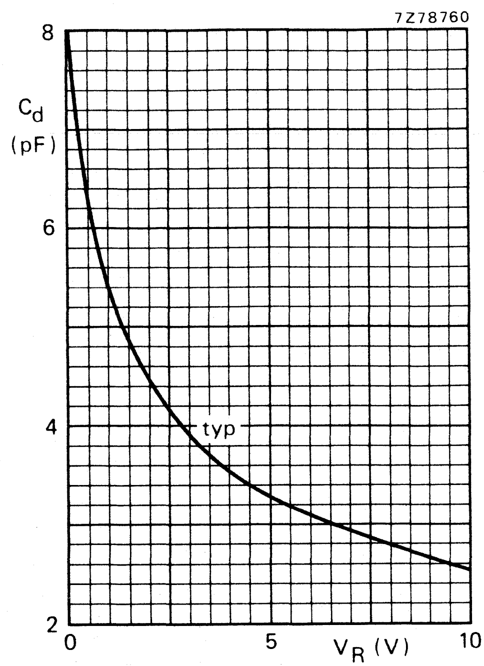


Fig. 2 f = 1 MHz; T_j = 25 °C.

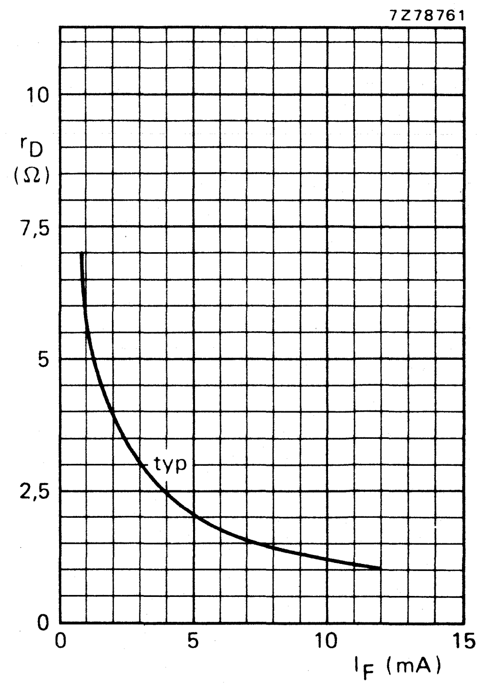


Fig. 3 f = 1 MHz; T_j = 25 °C.

SILICON RATIO DETECTOR DIODE

Silicon planar epitaxial diode in DO-35 envelope, intended for use in ratio detector circuits. Due to small spreads of forward voltage at low currents and of junction capacitance, the diodes can be used as matched pairs.

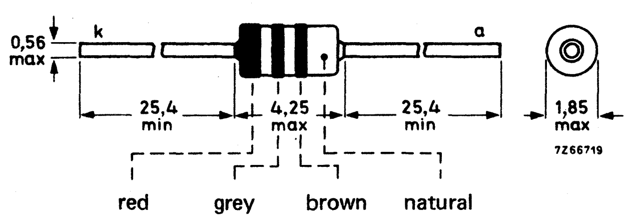
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	50	V
Forward current (d.c.)	I_F	max.	200	mA
Repetitive peak forward current	I_{FRM}	max.	450	mA
Forward voltage	V_F	360 to	420	mV
Diode capacitance	C_d	<	1,2	pF
Junction temperature	T_j	max.	200	°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 DO-35 (SOD-27).



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	50 V
Forward current (d.c.)	I_F	max.	200 mA
Repetitive peak forward current	I_{FRM}	max.	450 mA
Storage temperature	T_{stg}	−65 to +200	°C
Junction temperature	T_j	max.	+200 °C

THERMAL RESISTANCE

from junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0,6 K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage			
I_F = 10 μA	V_F	360 to 420	mV
I_F = 100 mA	V_F	< 1000	mV
Reverse current			
V_R = 50 V	I_R	< 50	nA
Diode capacitance			
V_R = 0, f = 1 MHz	C_d	< 1,2	pF

Dynamic characteristics

Input peak voltage	V_{im}	3	V
Frequency	f_i	10,7	MHz
Load capacitor	C_L	330	pF
Load resistor	R_L	0,033	MΩ
Efficiency	η	85	%
Diode resistance	r_D	12	kΩ

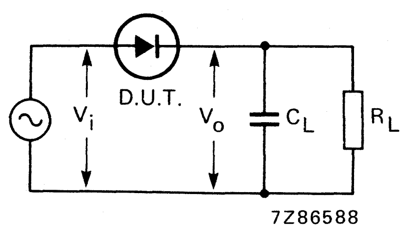


Fig. 2 Test circuit.

LOW VOLTAGE STABISTOR

Silicon planar epitaxial diode in DO-35 envelope. This diode is intended for low voltage stabilizing e.g. bias stabilizer in class-B output stages, clipping, clamping and meter protection.

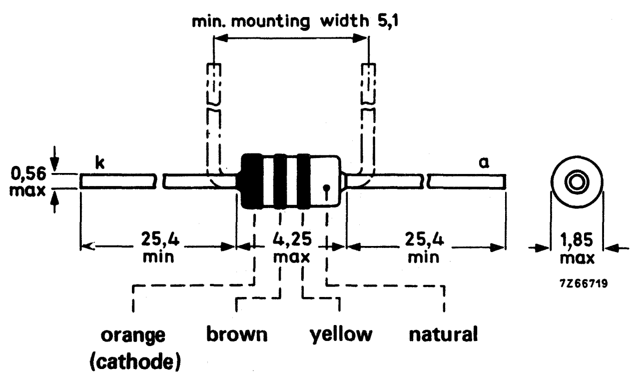
QUICK REFERENCE DATA

Repetitive peak forward current	I_{FRM}	max.	250	mA
Storage temperature	T_{stg}	−65 to +	200	°C
Junction temperature	T_j	max.	200	°C
Thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$	=	0,38	K/mW
Forward voltage				
I_F = 0,1 mA	V_F		610 to 690	mV
I_F = 1,0 mA	V_F		680 to 760	mV
I_F = 10 mA	V_F		750 to 830	mV
I_F = 100 mA	V_F		850 to 940	mV
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	140	pF

MECHANICAL DATA

Dimensions in mm

Fig. 1 DO-35 (SOD-27).



Products approved to CECC 50 001-026 available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Repetitive peak forward current	I_{FRM}	max.	250	mA
Storage temperature	T_{stg}	−65 to +	200	°C
Junction temperature	T_j	max.	200	°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0,38	K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage				
I_F = 0,1 mA	V_F		610 to 690	mV
I_F = 1,0 mA	V_F		680 to 760	mV
I_F = 5,0 mA	V_F		730 to 810	mV
I_F = 10 mA	V_F		750 to 830	mV
I_F = 100 mA	V_F		850 to 940	mV
Reverse current				
V_R = 4 V	I_R	<	5	μA
Temperature coefficient				
I_F = 1 mA	S_F	typ.	−1,8	mV/K
Differential resistance at f = 1 kHz				
I_F = 1 mA	r_{diff}	typ.	30	Ω
I_F = 10 mA	r_{diff}	typ.	3,5	Ω
		<	6,0	Ω
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	140	pF

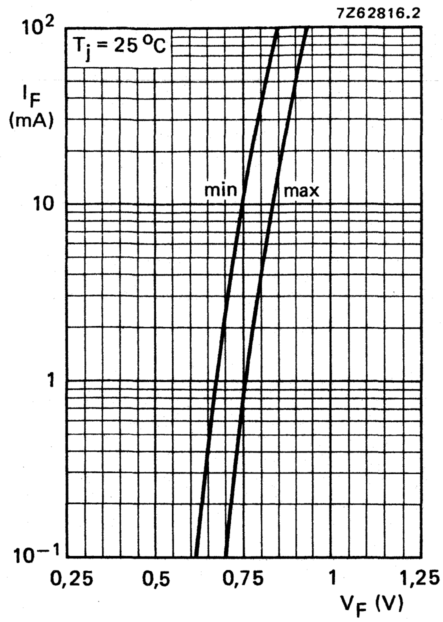


Fig. 2.

LOW VOLTAGE STABISTOR

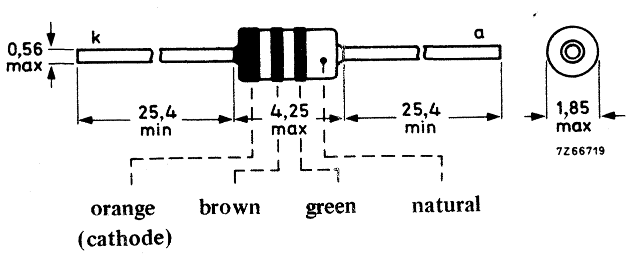
Silicon planar epitaxial diode in a DO-35 envelope primarily intended for low voltage stabilizing.

QUICK REFERENCE DATA				
Repetitive peak reverse voltage	V_{RRM}	max.	5	V
Repetitive peak forward current	I_{FRM}	max.	225	mA
Storage temperature	T_{stg}		−65 to +200	°C
Junction temperature	T_j	max.	200	°C
Thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$	=	0,60	K/mW
Forward voltage at I_F = 0,1 mA	V_F		480 to 540	mV
I_F = 1,0 mA	V_F		590 to 660	mV
I_F = 10 mA	V_F		710 to 790	mV
I_F = 100 mA	V_F		875 to 1050	mV
Diode capacitance at V_R = 0; f = 1 MHz	C_d	<	3,0	pF

MECHANICAL DATA

Dimensions in mm

DO-35



RATINGS Limiting values in accordance with the Absolute Maximum System (IEC134)

Repetitive peak reverse voltage	V_{RRM}	max.	5	V	
Average rectified forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	100	mA	1)
Forward current (d.c.)	I_F	max.	100	mA	
Repetitive peak forward current	I_{FRM}	max.	225	mA	
Non-repetitive peak forward current; t = 1 μs	I_{FSM}	max.	2000	mA	
t = 1 s	I_{FSM}	max.	500	mA	
Storage temperature	T_{stg}	−65 to +200		°C	
Junction temperature	T_j	max.	200	°C	

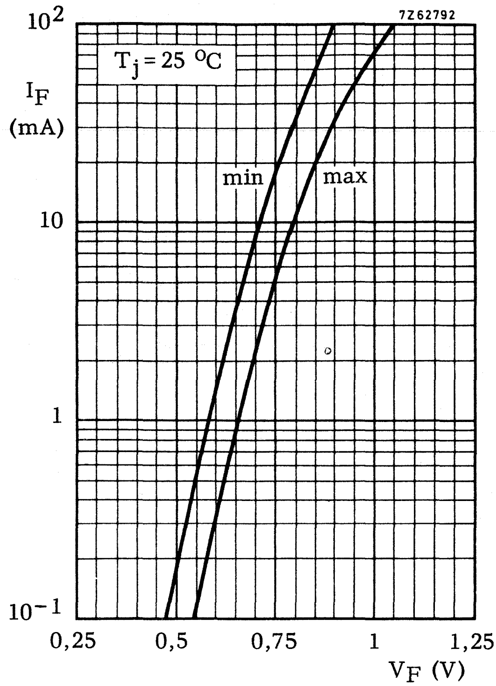
THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j-a}$	=	0,60	K/mW

CHARACTERISTICS T_j = 25 °C

Forward voltage				
I_F = 0,1 mA	V_F	480 to	540	mV
I_F = 1,0 mA	V_F	590 to	660	mV
I_F = 5,0 mA	V_F	670 to	740	mV
I_F = 10 mA	V_F	710 to	790	mV
I_F = 100 mA	V_F	875 to	1050	mV
Reverse current				
V_R = 5 V	I_R	<	1500	nA
Temperature coefficient at I_F = 1 mA	S_F	typ.	−2,1	K/mW
Differential resistance at f = 1 kHz				
I_F = 1 mA	r_{diff}	typ.	50	Ω
I_F = 10 mA	r_{diff}	typ.	6	Ω
		<	7	Ω
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	3,0	pF

1) For sinusoidal operation $I_{F(AV)}$ = 75 mA.


7Z62792
T_j = 25 °C
I_F
(mA)
10^2
10
1
10^{-1}
min
max
0,25
0,5
0,75
1
1,25
V_F (V)

10 V, 30 V and 50 V GENERAL PURPOSE DIODES

Silicon planar epitaxial diodes in DO-35 envelopes intended for general purpose applications.
They have reverse voltages up to 10 V for BA316, 30 V for BA317 and 50 V for BA318.

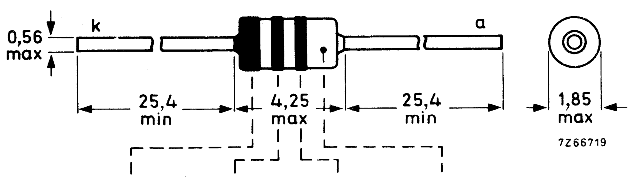
QUICK REFERENCE DATA

			BA316	BA317	BA318	
Continuous reverse voltage	V_R	max.	10	30	50	V
Repetitive peak forward current	I_{FRM}	max.		225		mA
Storage temperature	T_{stg}			−65 to +200		°C
Junction temperature	T_j	max.		200		°C
Thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$	=		0,60		K/mW
Forward voltage at I_F = 1,0 mA	V_F	<		700		mV
I_F = 10 mA	V_F	<		850		mV
I_F = 100 mA	V_F	<		1100		mV
Diode capacitance at V_R = 0; f = 1 MHz	C_d	<		2		pF
Reverse recovery time when switched from I_F = 10 mA to I_R = 60 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<		4		ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 DO-35.



BA316:	orange	brown	blue	natural
BA317:	orange	brown	violet	natural
BA318:	orange	brown	grey	natural
	(cathode)			

RATINGS Limiting values in accordance with the Absolute Maximum System (IEC134)

			BA316	BA317	BA318		
Continuous reverse voltage	V_R	max.	10	30	50	V	

Average rectified forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	100	mA	1)
Forward current (d.c.)	I_F	max.	100	mA	
Repetitive peak forward current	I_{FRM}	max.	225	mA	
Non-repetitive peak forward current					
t = 1 μs	I_{FSM}	max.	2000	mA	
t = 1 s	I_{FSM}	max.	500	mA	
Storage temperature	T_{stg}		−65 to +200	°C	
Junction temperature	T_j	max.	200	°C	

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0, 60	K/mW

CHARACTERISTICS $T_j = 25\ ^oC$

Forward voltage

I_F = 1, 0 mA	V_F	<	700	mV
I_F = 10 mA	V_F	<	850	mV
I_F = 100 mA	V_F	<	1100	mV

Reverse current

			BA316	BA317	BA318	
V_R = 10 V	I_R	<	200	50	–	nA
V_R = 30 V	I_R	<	–	200	50	nA
V_R = 50 V	I_R	<	–	–	200	nA

Diode capacitance

V_R = 0; f = 1 MHz	C_d	<	2	pF

1) For pulse operation see Figs 3 to 6. For sinusoidal operation see Figs 7 to 10.

CHARACTERISTICS (continued) $T_j = 25\ ^oC$

Reverse recovery time when switched from

$I_F = 10$ mA to $I_R = 60$ mA; $R_L = 100\ \Omega$;

Measured at $I_R = 1$ mA t_{rr} < 4 ns

Test circuit and waveforms :

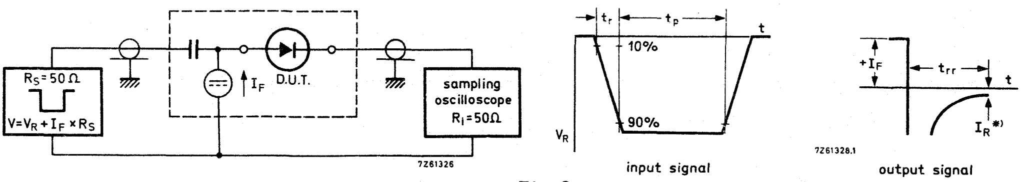


Fig. 2.

Input signal : Rise time of the reverse pulse $t_r = 0,6$ ns *) $I_R = 1$ mA

Reverse pulse duration $t_p = 100$ ns

Duty factor $\delta = 0,05$

Oscilloscope: Rise time $t_r = 0,35$ ns

Circuit capacitance C ≤ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

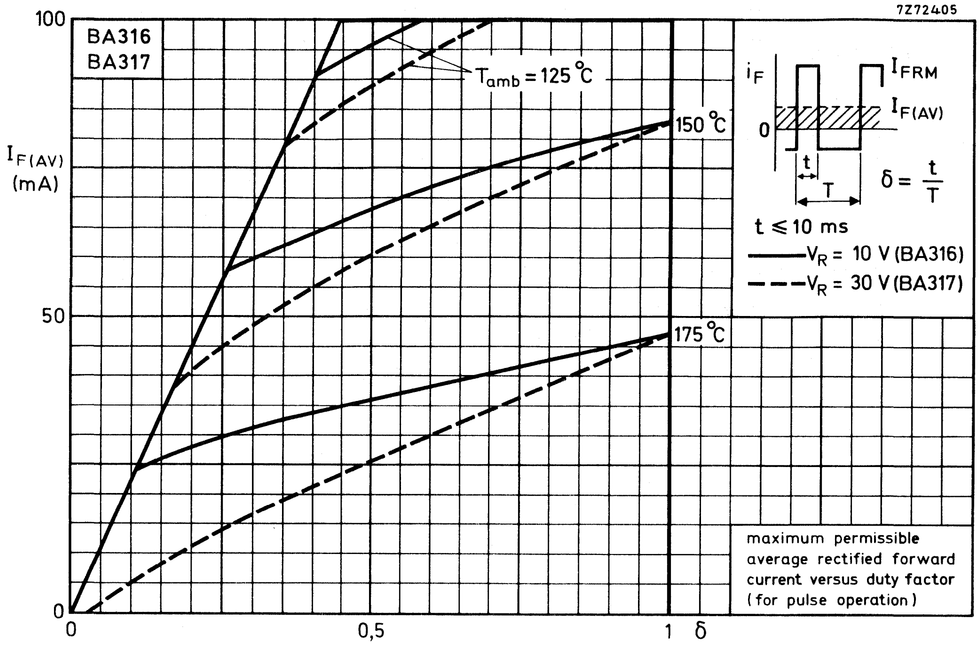

7Z72405
BA316
BA317
100
50
0
$I_{F(AV)}$
(mA)
T_{amb} = 125 °C
150 °C
175 °C
0
0,5
1
δ
i_F
I_{FRM}
$I_{F(AV)}$
0
t
T
δ = t/T
t ≤ 10 ms
V_R = 10 V (BA316)
V_R = 30 V (BA317)
maximum permissible average rectified forward current versus duty factor (for pulse operation)

Fig. 3.

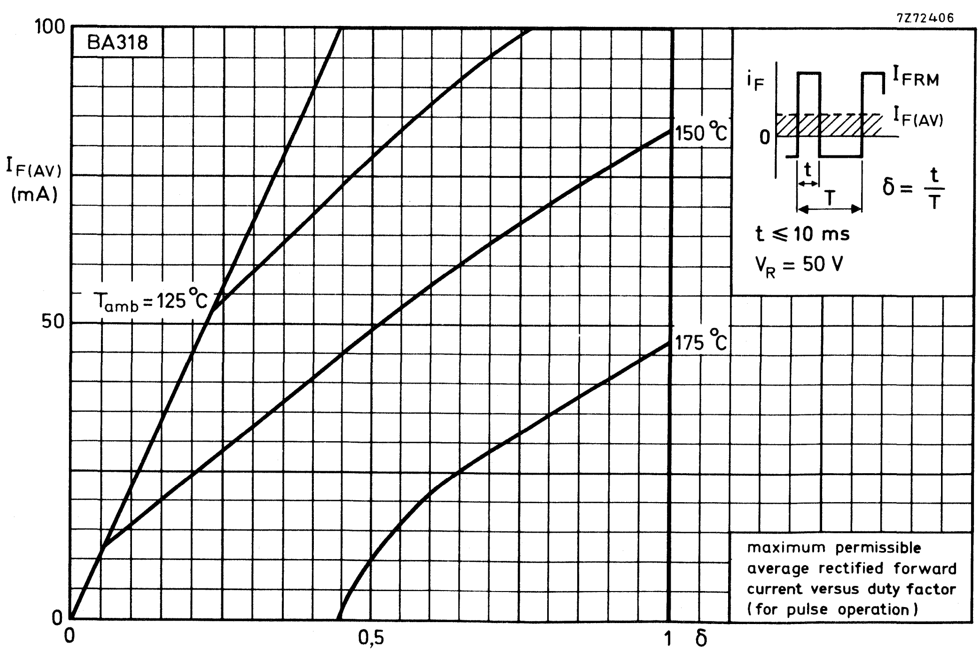

7Z72406
BA318
100
50
0
$I_{F(AV)}$
(mA)
T_{amb} = 125 °C
150 °C
175 °C
0
0,5
1
δ
i_F
I_{FRM}
$I_{F(AV)}$
0
t
T
δ = t/T
t ≤ 10 ms
V_R = 50 V
maximum permissible average rectified forward current versus duty factor (for pulse operation)

Fig. 4.

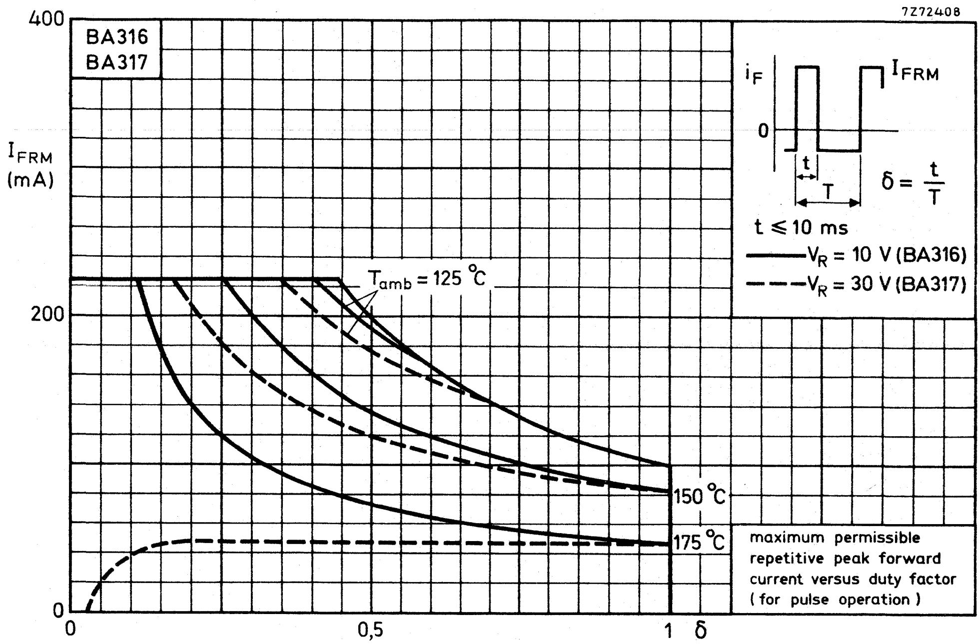

7Z72408
400
200
0
BA316
BA317
I_{FRM}
(mA)
i_F
I_{FRM}
0
t
T
δ = t/T
t ≤ 10 ms
V_R = 10 V (BA316)
V_R = 30 V (BA317)
T_{amb} = 125 °C
150 °C
175 °C
maximum permissible
repetitive peak forward
current versus duty factor
(for pulse operation)
0
0,5
1
δ

Fig. 5.

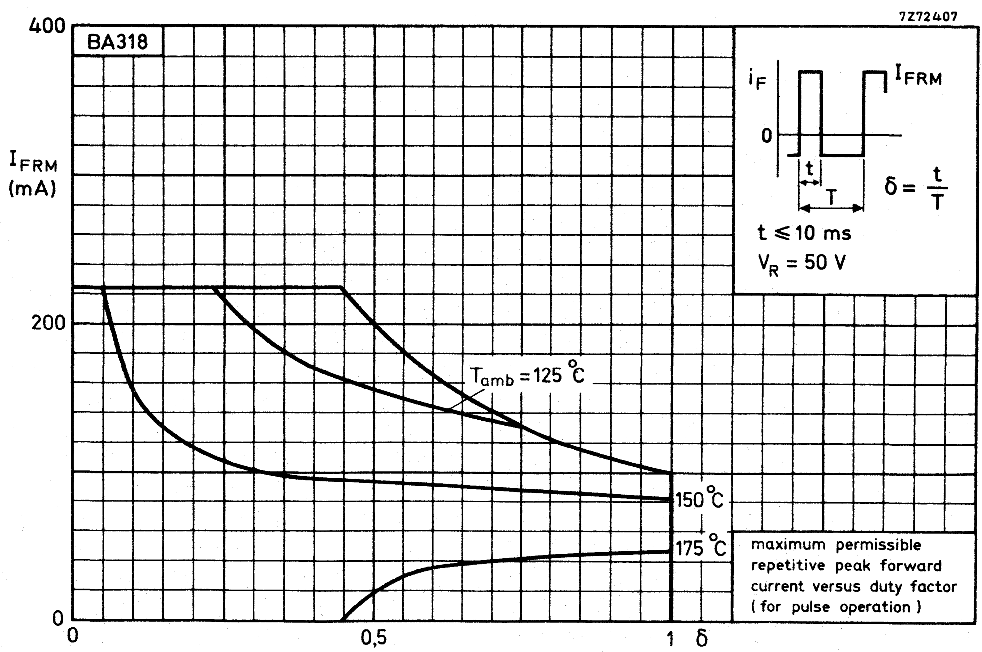

7Z72407
400
200
0
BA318
I_{FRM}
(mA)
i_F
I_{FRM}
0
t
T
δ = t/T
t ≤ 10 ms
V_R = 50 V
T_{amb} = 125 °C
150 °C
175 °C
maximum permissible
repetitive peak forward
current versus duty factor
(for pulse operation)
0
0,5
1
δ

Fig. 6.

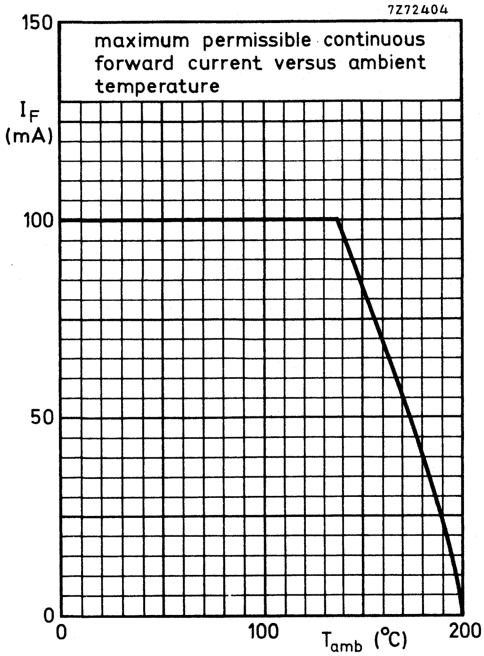


Fig. 7.

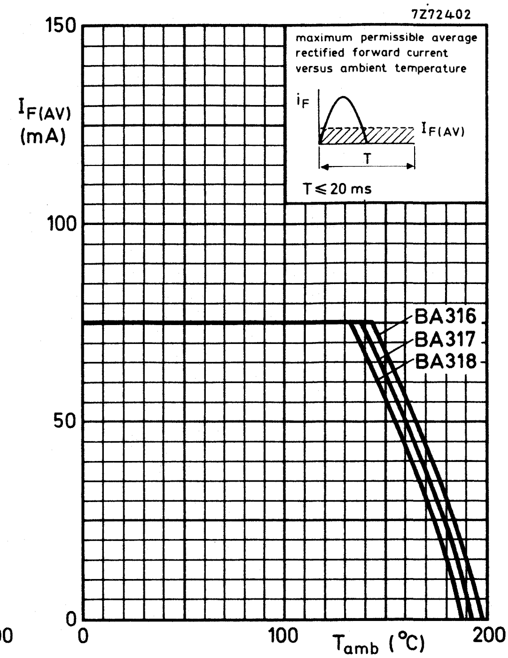


Fig. 8.

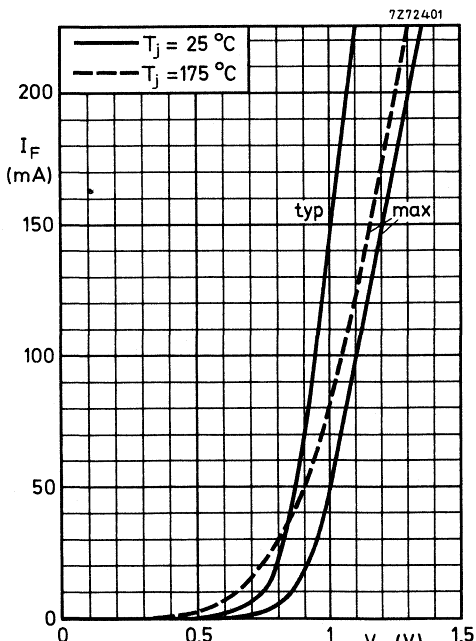


Fig. 9.

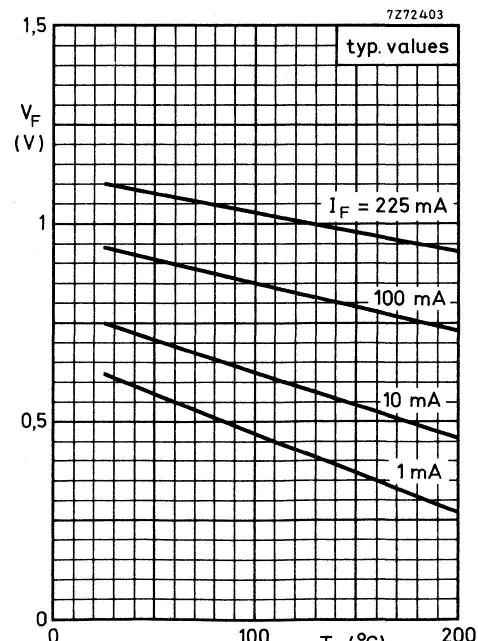


Fig. 10.

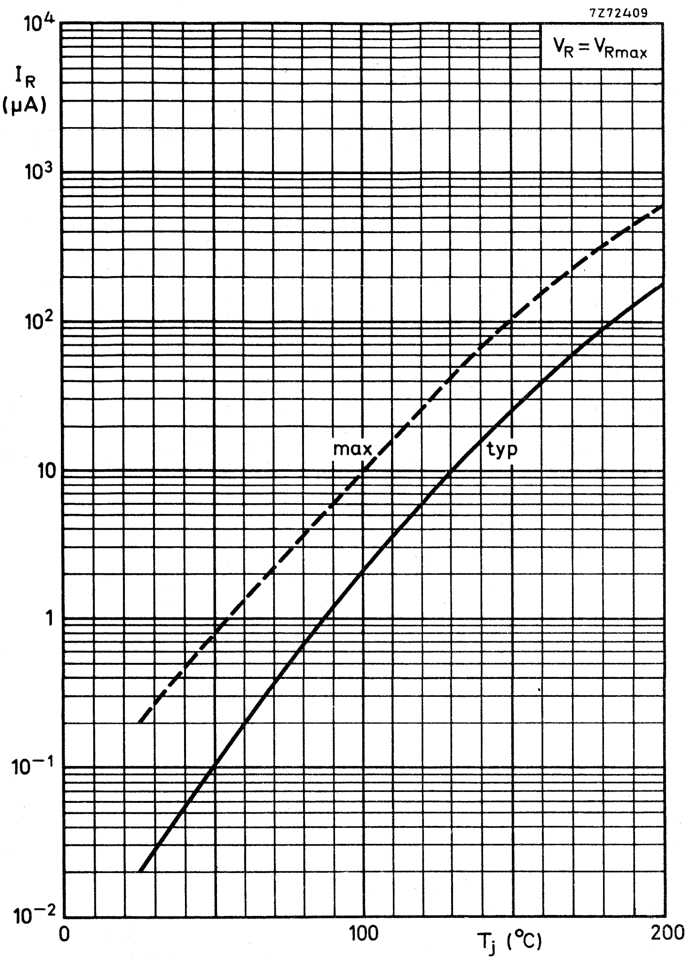

7Z72409
I_R (μA)
10^4
10^3
10^2
10
1
10^{-1}
10^{-2}
0
100
200
T_j (°C)
$V_R = V_{Rmax}$
max
typ

Fig. 11.

SILICON A.M. BAND SWITCHING DIODE

The BA423 is a switching diode in **hermetically sealed glass DO-34 envelope.** Intended for band switching in a.m. radio receivers.

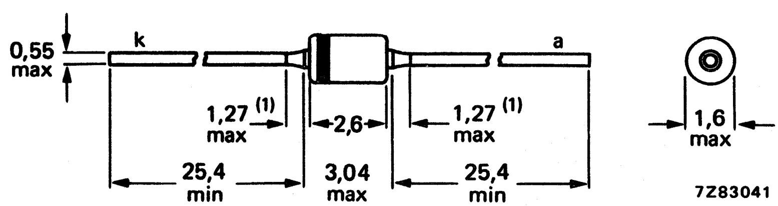
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	20 V
Forward current (d.c.)	I_F	max.	50 mA
Junction temperature	T_j	max.	150 °C
Diode capacitance at f = 1 MHz V_R = 3 V	C_d	<	2,5 pF
Series resistance at f = 1 MHz I_F = 10 mA	r_s	<	1,2 Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-68 (DO-34).



(1) Lead diameter in this zone uncontrolled.
The marking band indicates the cathode.
The diodes are type branded.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	20 V
Forward current (d.c.)	I_F	max.	50 mA
Storage temperature	T_{stg}	−65 to + 150 °C	
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient in free air mounted on a printed-circuit board at a lead-length of 10 mm	$R_{th\ j\text{-}a}$	=	0,4 K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage I_F = 50 mA	V_F	<	0,9 V
Reverse current V_R = 20 V	I_R	<	100 nA
V_R = 20 V; T_j = 125 °C	I_R	<	5 μA
Diode capacitance at f = 1 MHz V_R = 3 V	C_d	<	2,5 pF
Series resistance I_F = 10 mA; f = 1 MHz	r_s	<	1,2 Ω

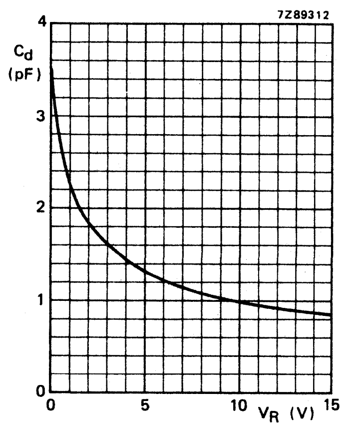


Fig. 2 Typical values
f = 1 MHz; T_j = 25 °C.

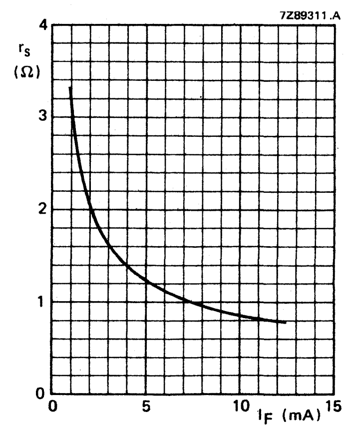


Fig. 3 Typical values
f = 1 MHz; T_j = 25 °C.

SILICON AM BAND SWITCHING DIODE FOR SURFACE MOUNTING

The BA423L is a switching diode intended for band switching in AM radio receivers.

This SM diode is a leadless diode in a hermetically sealed SOD-80 envelope with lead/tin plated metal discs at each end. It is suitable for "automatic placement" and as such it can withstand immersion soldering.

The diodes are delivered in "super 8" tape.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	20	V
Forward current (DC)	I_F	max.	50	mA
Junction temperature	T_j	max.	100	°C
Diode capacitance at f = 1 MHz V_R = 3 V	C_d	<	2.5	pF
Series resistance at f = 1 MHz I_F = 10 mA	r_s	<	1.2	Ω

MECHANICAL DATA

Dimensions in mm

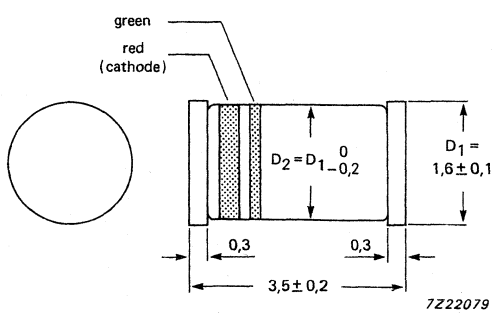


Fig. 1 SOD-80.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	20 V
Forward current (DC)	I_F	max.	50 mA
Storage temperature range	T_{stg}	−65 to + 150 °C	
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient on a ceramic substrate of 8 mm x 10 mm x 0.7 mm (see soldering recommendations SOD-80)	$R_{th\ j\text{-}a}$	max.	400 K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Forward voltage I_F = 50 mA	V_F	<	0.9 V
Reverse current V_R = 20 V	I_R	<	100 nA
V_R = 20 V; T_j = 125 °C	I_R	<	5.0 μA
Diode capacitance at f = 1 MHz V_R = 3 V	C_d	<	2.5 pF
Series resistance at f = 1 MHz I_F = 10 mA	r_s	<	1.2 Ω

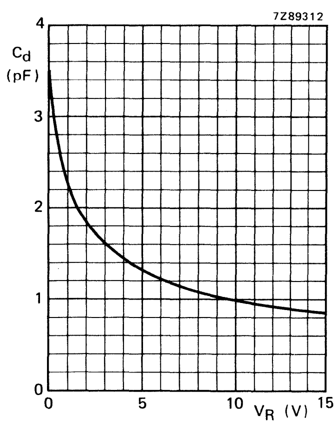


Fig. 2 Diode capacitance as a function of continuous reverse voltage; f = 1 MHz; T_j = 25 °C; typical values.

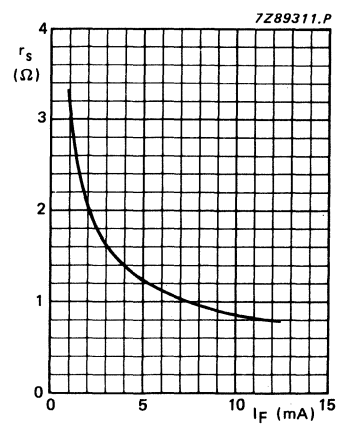


Fig. 3 Series resistance as a function of forward current; f = 1 MHz; T_j = 25 °C; typical values.

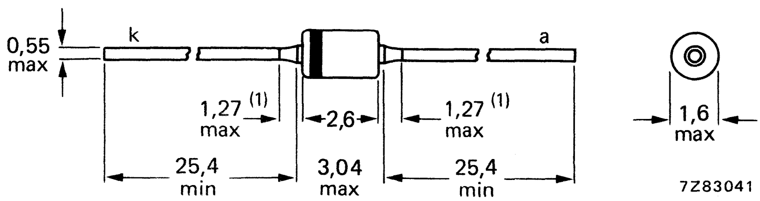
U.H.F. MIXER DIODE

Silicon epitaxial Schottky-barrier diode in a DO-34 envelope and intended for mixer applications in u.h.f. tuners, t.v. modulators and r.f. detectors.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	4	V
Forward current (d.c.)	I_F	max.	30	mA
Noise figure at f = 900 MHz	F	<	8	dB
Junction temperature	T_j	max.	100	°C

Fig. 1 SOD-68 (DO-34).



(1) Lead diameter in this zone uncontrolled.
The BA481 is indicated by a grey band on the cathode side.

The diodes are suitable for mounting on a 2 E (5,08 mm) pitch.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134).

Continuous reverse voltage $I_R = 10\ \mu A$	V_R	max.	4	V
Reverse voltage (peak value)	V_{RM}	max.	5	V
Forward current (d.c.)	I_F	max.	30	mA
Storage temperature	T_{stg}	−65 to + 125		°C
Junction temperature	T_j	max.	100	°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	max.	0,32	K/W

CHARACTERISTICS

$T_{amb} = 25\ ^oC$ unless otherwise specified

Forward voltage $I_F = 1$ mA	V_F	<	450	mV
$I_F = 10$ mA	V_F	<	600	mV
Reverse current $V_R = 4$ V;	I_R	<	10	μA
$V_R = 4$ V; $T_{amb} = 60\ ^oC$	I_R	<	100	μA
Series resistance $I_F = 5$ mA; f = 1 kHz	r_s	<	13	Ω
Noise figure at f = 900 MHz*	F	<	8	dB
Diode capacitance $V_R = 0$; f = 1 MHz	C_d	<	1,1	pF

* The local oscillator is adjusted for a diode current of 2 mA.
I.F. amplifier noise $F_{if} = 1,5$ dB; f = 35 MHz.

SILICON PLANAR DIODES

Switching diodes in the subminiature DO-34 glass envelope, intended for band switching in v.h.f. television tuners. Special feature of the diodes is their low capacitance.

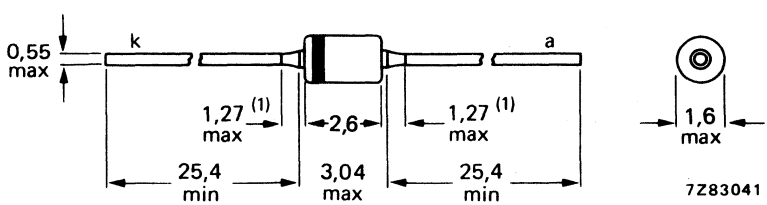
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	35 V			
Forward current (d.c.)	I_F	max.	100 mA			
Junction temperature	T_j	max.	150 °C			
			BA482	BA483	BA484	
Diode capacitance						
V_R = 3 V; f = 1 to 100 MHz	C_d	<	1,2	1,0	1,6	pF
Series resistance at f = 200 MHz						
I_F = 3 mA	r_D	<	0,7	1,2	1,2	Ω
I_F = 10 mA	r_D	typ.	0,4	0,5	0,5	Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-68 (DO-34).



(1) Lead diameter in this zone uncontrolled.

Cathode indicated by coloured band.

BA482: red on a natural background.
BA483: orange on a natural background.
BA484: yellow on a natural background.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	35 V
Forward current (d.c.)	I_F	max.	100 mA
Storage temperature	T_{stg}		−65 to + 150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient mounted on printed board lead length = 5,0 mm	$R_{th\ j\text{-}a}$	=	0,6 K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage I_F = 100 mA	V_F	<	1,2 V
Reverse current V_R = 20 V	I_R	<	100 nA
V_R = 20 V; T_{amb} = 75 °C	I_R	<	1 μA

			BA482	BA483	BA484	
Diode capacitance V_R = 3 V; f = 1 to 100 MHz	C_d	typ.	0,8	0,7	1,0	pF
		<	1,2	1,0	1,6	pF
Series resistance at f = 200 MHz I_F = 3 mA	r_D	typ.	0,6	0,8	0,8	Ω
		<	0,7	1,2	1,2	Ω

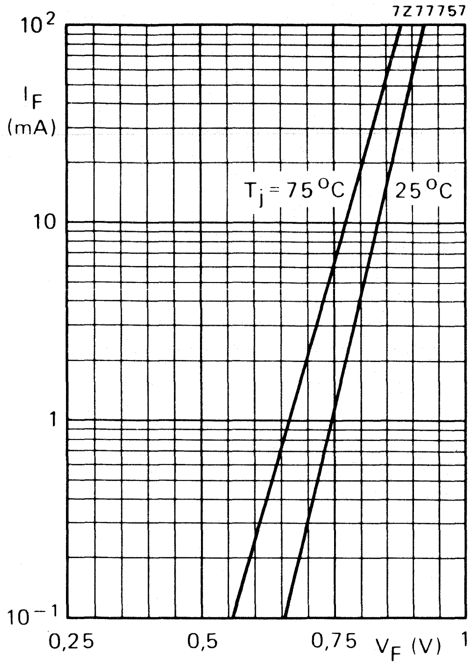


Fig. 2 Typical values.

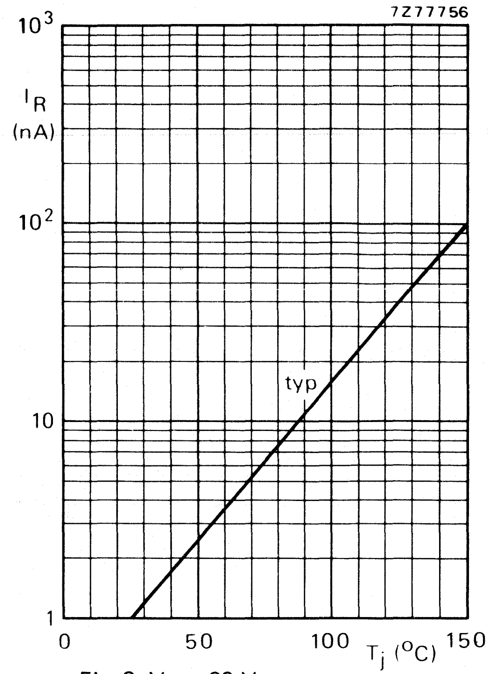


Fig. 3 V_R = 20 V.

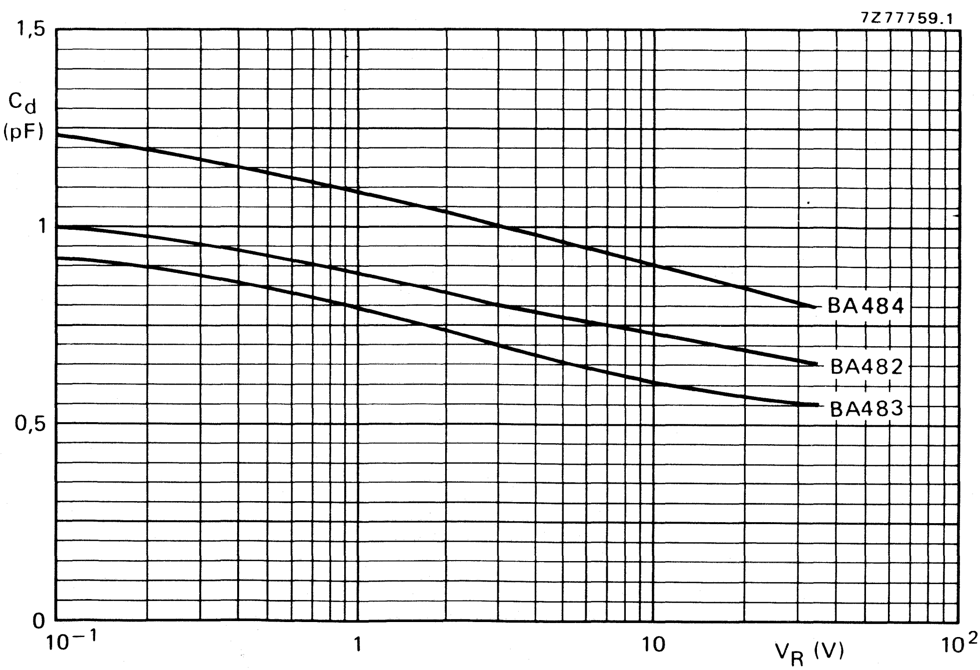


Fig. 4 Typical values; f = 1 to 100 MHz; T_j = 25 ^oC.

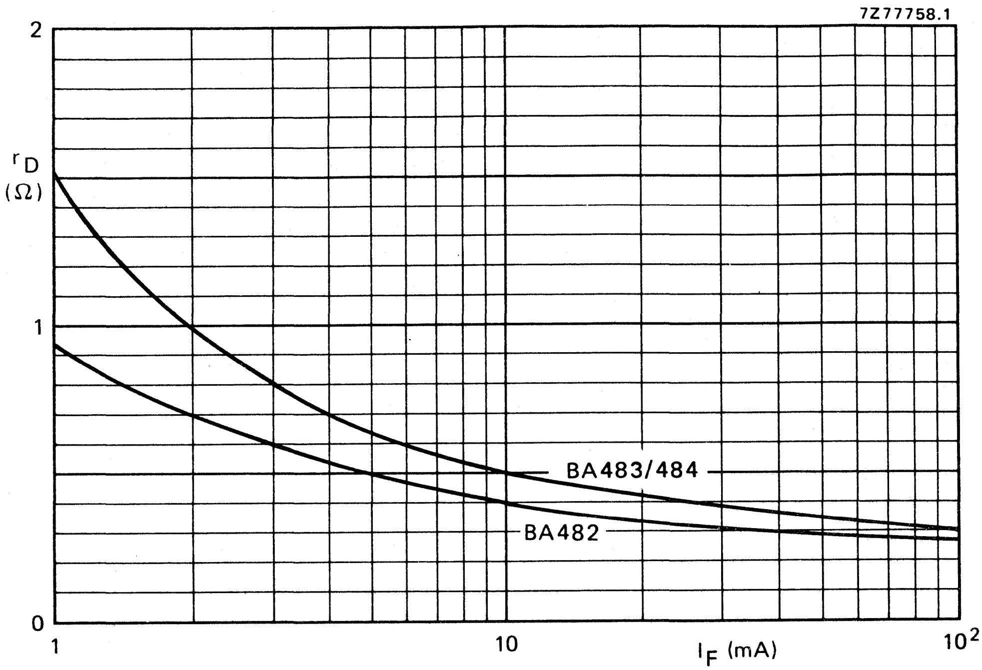


Fig. 5 Typical values; f = 200 MHz; T_j = 25 °C.

BAND-SWITCHING DIODES FOR SURFACE MOUNTING

Switching diodes in a SOD-80 envelope, intended for band switching in v.h.f. television tuners. A special feature of these diodes is their low capacitance.

These SM diodes are leadless diodes in an hermetically sealed micro-miniature glass envelope with tin-plated metal discs at each end. They are suitable for Automatic Placement and as such they can withstand immersion soldering.

The diodes are delivered in "super 8" tape.

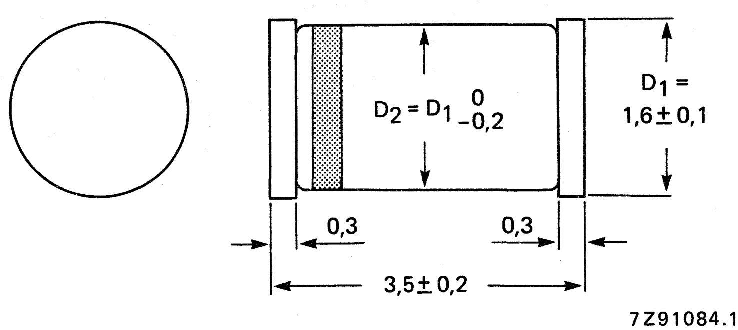
QUICK REFERENCE DATA

			BA682	BA683	
Continuous reverse voltage	V_R	max.	35	35	V
Forward current (d.c.)	I_F	max.	100	100	mA
Junction temperature	T_j	max.	150	150	°C
Diode capacitance $V_R = 3$ V; f = 1 MHz	C_d	<	1,25	1,2	pF
Series resistance at f = 200 MHz					
$I_F = 3$ mA	r_D	<	0,7	1,2	Ω
$I_F = 10$ mA	r_D	<	0,5	0,9	Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



The cathode is indicated by a red band.
The BA683 cathode has an additional orange band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	35	V
Forward current (d.c.)	I_F	max.	100	mA
Storage temperature	T_{stg}		−65 to +150	°C
Junction temperature	T_j		150	°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$ =	0,6	K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

Forward voltage I_F = 100 mA	V_F	<	1,0		V
Reverse current V_R = 20 V	I_R	<	50		nA
V_R = 20 V; T_{amb} = 75 °C	I_R	<	1		μA
			BA682	**BA683**	
Diode capacitance at f = 1 MHz V_R = 1 V	C_d	<	1,5	1,5	pF
V_R = 3 V	C_d	<	1,25	1,2	pF
Series resistance at f = 200 MHz I_F = 3 mA	r_D	<	0,7	1,2	Ω
I_F = 10 mA	r_D	<	0,5	0,9	Ω

SILICON GLASS PASSIVATED AVALANCHE DIODE

Diode in a DO-35 envelope. It is primarily intended for general purpose applications, e.g. scan and flyback rectifiers, protection diodes etc. in television circuits. An advantage of this diode is its capability of absorbing reverse transient energy.

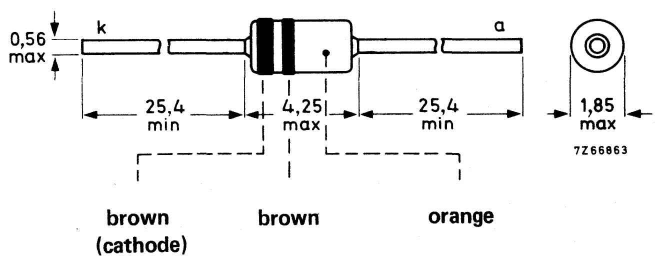
QUICK REFERENCE DATA

Working reverse voltage	V_{RW}	max.	300	V
Average rectified forward current	$I_{F(AV)}$	max.	300	mA
Non-repetitive peak forward current	I_{FSM}	max.	4	A
Repetitive peak reverse power dissipation	P_{RRM}	max.	75	W
Reverse recovery time	t_{rr}	<	1	μs

MECHANICAL DATA

Dimensions in mm

Fig. 1 DO-35 (SOD-27).



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Working reverse voltage	V_{RW}	max.	300	V
Continuous reverse voltage (see Fig. 8)	V_R	max.	300	V
Forward current (d.c.)	I_F	max.	350	mA
Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	300	mA
Repetitive peak forward current				
$t = 10$ ms; $f = 50$ Hz	I_{FRM}	max.	900	mA
$\delta = 0{,}1$; $f = 15$ kHz	I_{FRM}	max.	2	A
Non-repetitive peak forward current				
($t = 10$ ms; half sine-wave) $T_j = 150$ °C prior to surge	I_{FSM}	max.	4	A
($t = 10$ µs; square wave) $T_j = 150$ °C prior to surge	I_{FSM}	max.	30	A
Repetitive peak reverse current				
$t = 10$ µs (square wave; $f = 50$ Hz) $T_{amb} = 25$ °C	I_{RRM}	max.	150	mA
Repetitive peak reverse power dissipation				
$t = 10$ µs (square wave; $f = 50$ Hz) $T_{amb} = 25$ °C	P_{RRM}	max.	75	W
Storage temperature	T_{stg}	−65 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient in free air mounted on printed board at 8 mm lead length	$R_{th\ j\text{-}a}$	=	0,34	K/mW

CHARACTERISTICS

$T_j = 25$ °C unless otherwise specified

Forward voltage				
$I_F = 300$ mA	V_F	<	1,1	V
$I_F = 900$ mA	V_F	<	1,3	V
Reverse avalanche breakdown voltage				
$I_R = 100$ µA	$V_{(BR)R}$	>	300	V
Reverse current				
$V_R = 300$ V	I_R	<	100	nA
$V_R = 300$ V; $T_j = 125$ °C	I_R	<	20	µA
Diode capacitance at $f = 1$ MHz				
$V_R = 0$	C_d	typ.	10	pF
$V_R = 50$ V	C_d	typ.	1,5	pF
Reverse recovery when switched from $I_{FM} = 400$ mA to $V_R = 30$ V; with $-dI_F/dt = 400$ mA/µs				
Recovery charge	Q_s	typ.	70	nC
Recovery time	t_{rr}	<	1	µs
Maximum slope of reverse recovery current when switched from $I_{FM} = 400$ mA to $V_R = 30$ V; with $-dI_F/dt = 400$ mA/µs	$\lvert dI_R/dt \rvert$	typ.	2,0	A/µs

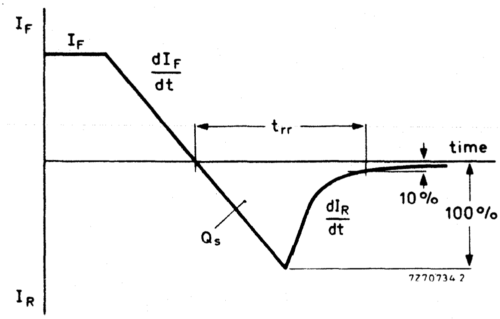


Fig. 2 Definitions of Q_s, t_{rr} and dI_R/dt.

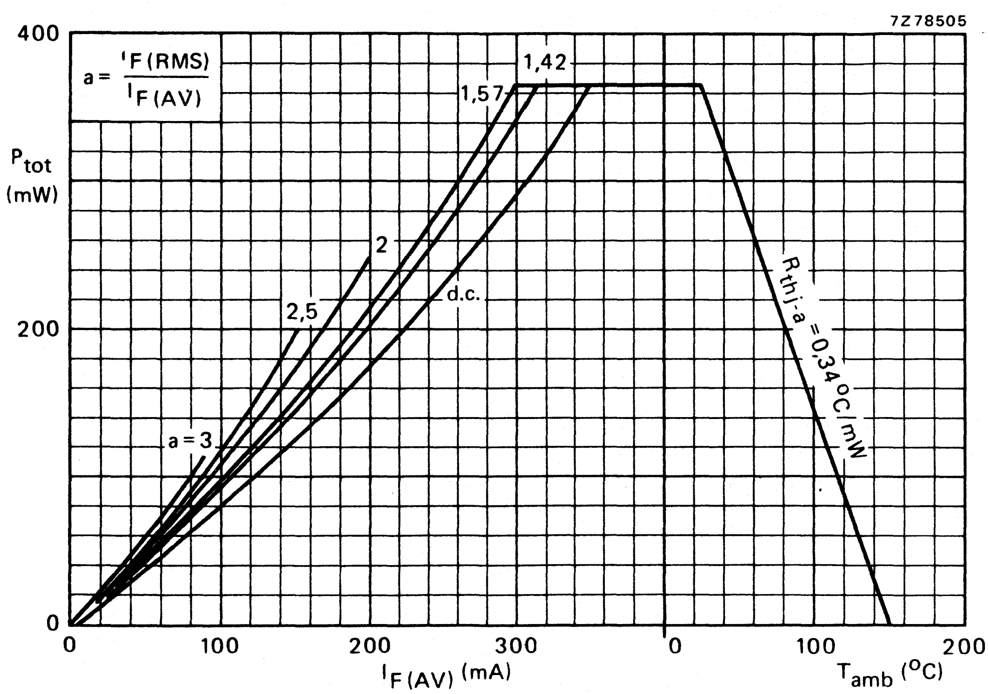


Fig. 3.

From the left-hand graph the total power dissipation can be found as a function of the average output current.

The parameter $a = \frac{I_{F(RMS)}}{I_{F(AV)}}$ depends on $n\omega R_L C_L$ and $\frac{R_t + r_{diff}}{nR_L}$ and can be found from existing graphs.

Once the power dissipation is known, the maximum permissible ambient temperature follows from the right-hand graph.

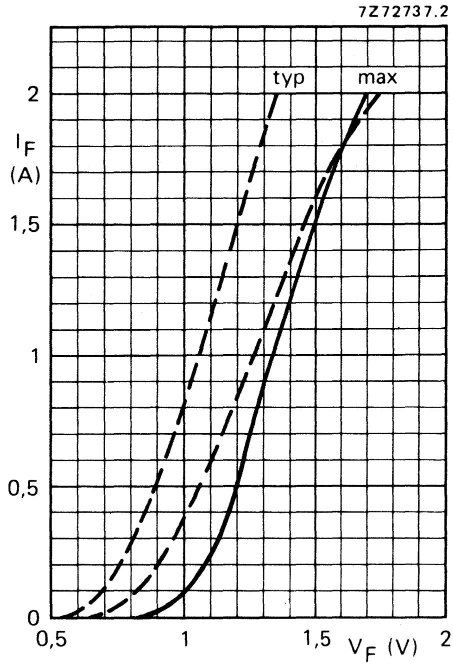


Fig. 4 ——— T_j = 25 °C; – – – T_j = 150 °C.

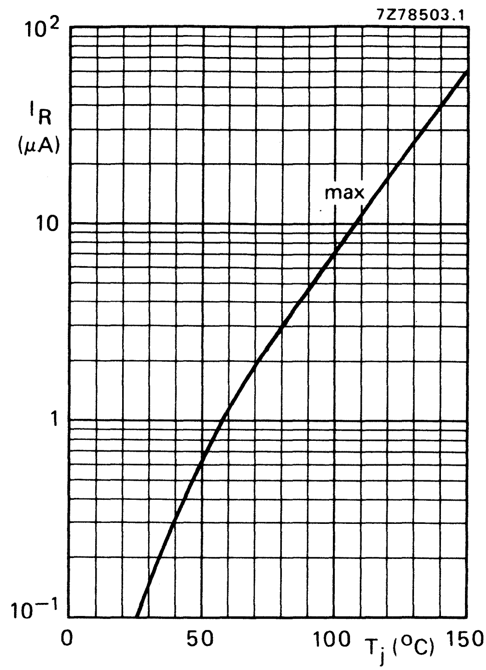


Fig. 5 V_R = 300 V.

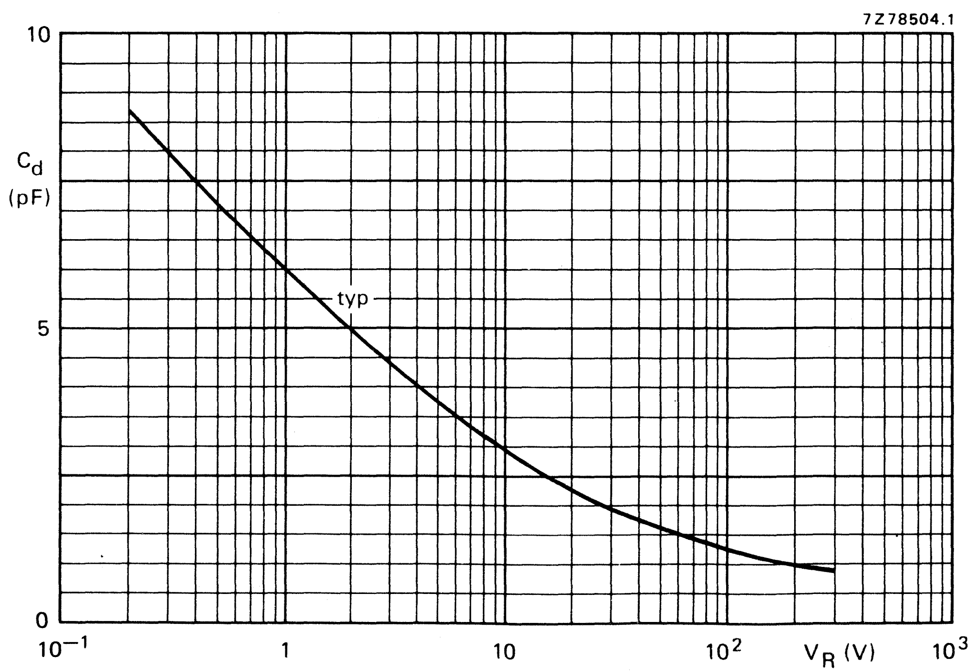


Fig. 6 f = 1 MHz; T_j = 25 °C.

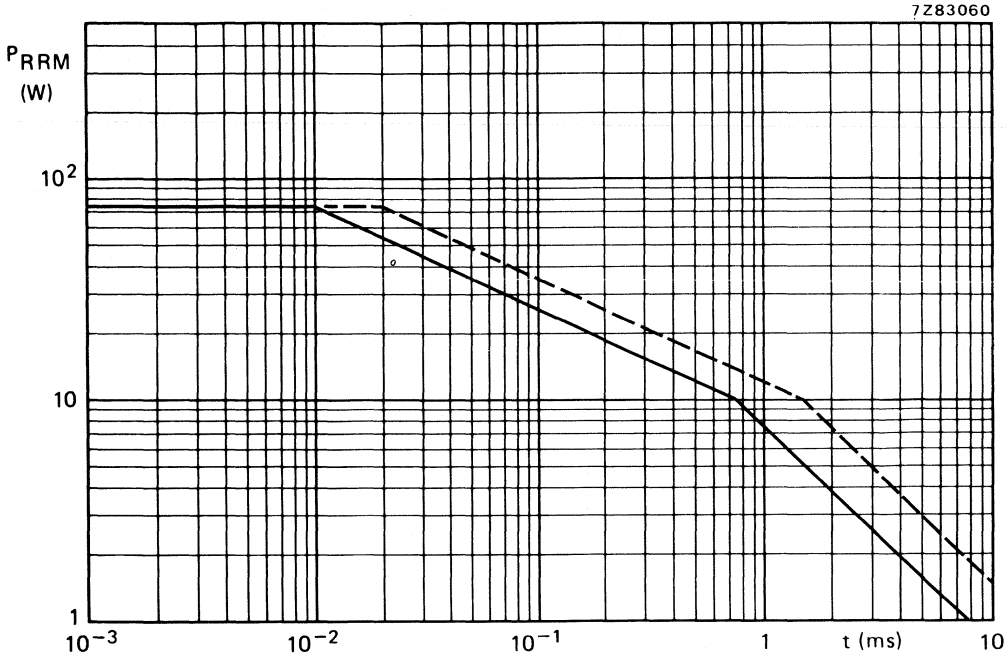


Fig. 7 Maximum permissible repetitive peak reverse power as a function of pulse duration. T ⩾ 20 ms; T_j = 25 °C. ——— rectangular waveform, δ ⩽ 0,01; – – – triangular waveform, δ ⩽ 0,02.

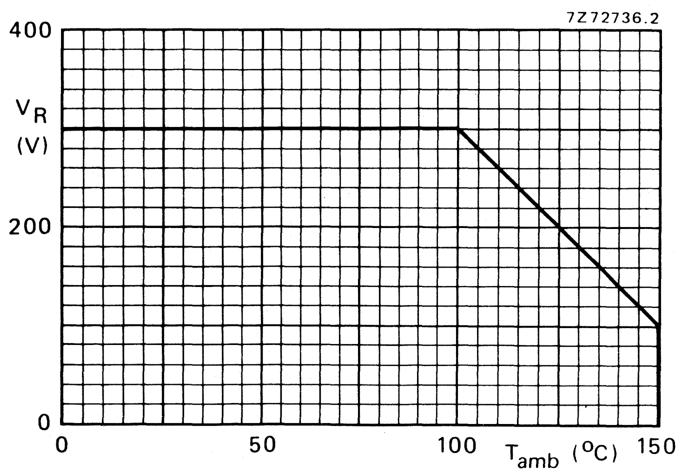


Fig. 8 Maximum permissible continuous reverse voltage versus ambient temperature.

SILICON DIODE

Diode in a DO-34 envelope intended for general purpose applications. Because of its smallness the BAS15 is specially suitable for hybrid mounting, as protection diode in reed relays, etc.

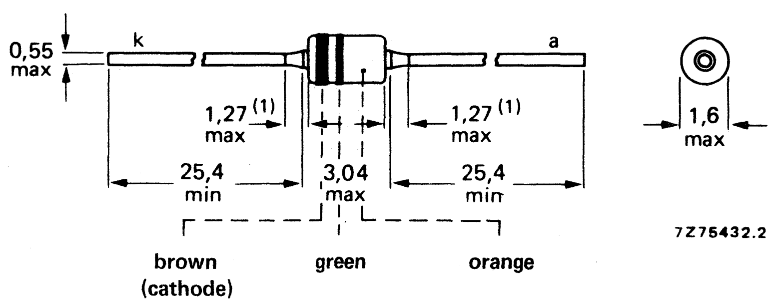
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max	50	V
Repetitive peak forward current	I_{FRM}	max	225	mA
Storage temperature	T_{stg}	−65 to + 200		°C
Junction temperature	T_j	max	200	°C
Thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$	=	0,60	K/mW
Forward voltage at				
I_F = 1 mA	V_F	<	0,7	V
I_F = 10 mA	V_F	<	0,85	V
I_F = 100 mA	V_F	<	1,1	V
Reverse recovery time when switched from I_F = 10 mA to I_R = 60 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	4	ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 DO-34 (SOD-68).



(1) Lead diameter in this zone uncontrolled.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max	50	V
Repetitive peak reverse voltage	V_{RRM}	max	50	V
Average rectified forward current * (averaged over any 20 ms period)	$I_{F(AV)}$	max	100	mA
Forward current (d.c.)	I_F	max	100	mA
Repetitive peak forward current	I_{FRM}	max	225	mA
Non-repetitive peak forward current				
t = 1 μs	I_{FSM}	max	2000	mA
t = 1 s	I_{FSM}	max	500	mA
Storage temperature	T_{stg}	−65 to + 200		°C
Junction temperature	T_j	max	200	°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0,60	K/mW

CHARACTERISTICS

T_j = 25 °C

Forward voltage				
I_F = 1 mA	V_F	<	0,7	V
I_F = 10 mA	V_F	<	0,85	V
I_F = 100 mA	V_F	<	1,1	V
Reverse current				
V_R = 30 V	I_R	<	50	nA
V_R = 50 V	I_R	<	200	nA
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	2	pF

* For sinusoidal operation $I_{F(AV)}$ = 75 mA.

CHARACTERISTICS (continued)

Reverse recovery time when switched from
I_F = 10 mA to I_R = 60 mA; R_L = 100 Ω; T_j = 25 °C;
Measured at I_R = 1 mA — t_{rr} < 4 ns

Test circuit and waveforms:

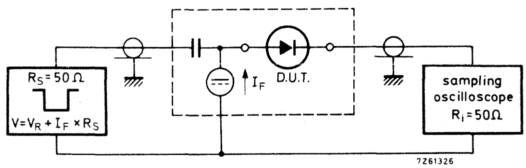
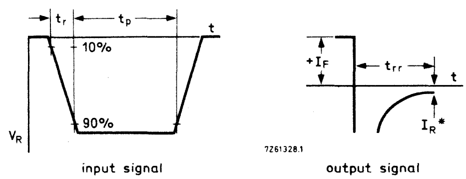


Fig. 2 Test circuit.



* I_R = 1 mA

Fig. 3 Waveforms.

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODE

Silicon epitaxial high-speed diode in a microminiature plastic envelope. It is intended for high-speed switching in hybrid thick and thin-film circuits.

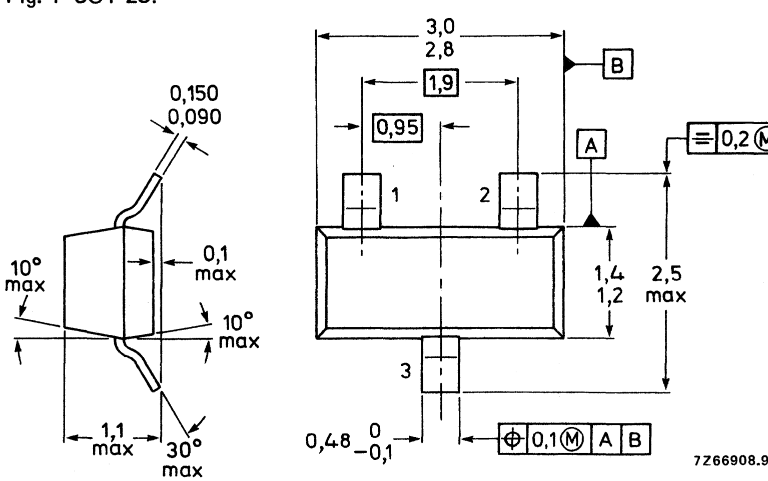
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	75	V
Repetitive peak reverse voltage	V_{RRM}	max.	85	V
Repetitive peak forward current	I_{FRM}	max.	250	mA
Junction temperature	T_j	max.	150	°C
Forward voltage at I_F = 50 mA	V_F	<	1,0	V
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	6	ns
Recovery charge when switched from I_F = 10 mA to V_R = 5 V; R_L = 500 Ω	Q_s	<	45	pC

MECHANICAL DATA

Dimensions in mm

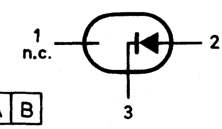
Fig. 1 SOT-23.



TOP VIEW

Marking code

BAS16 = A6



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	75	V
Repetitive peak reverse voltage	V_{RRM}	max.	85	V
Average rectified forward current* (averaged over any 20 ms period) up to T_{amb} = 25 °C	$I_{F(AV)}$	max.	250	mA
Forward current (DC)	I_F	max.	250	mA
Repetitive peak froward current	I_{FRM}	max.	250	mA
Non-repetitive peak forward current (per crystal)				
t = 1 μs	I_{FSM}	max.	2	A
t = 1 ms	I_{FSM}	max.	1	A
t = 1 s	I_{FSM}	max.	0,5	A
→ Storage temperature range	T_{stg}		−65 to + 150	°C
→ Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE**

From junction to ambient▲	$R_{th\,j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

Forward voltage				
I_F = 1 mA	V_F	<	715	mV
I_F = 10 mA	V_F	<	855	mV
I_F = 50 mA	V_F	<	1000	mV
I_F = 150 mA	V_F	<	1250	mV
Reverse current				
V_R = 25 V; T_j = 150 °C	I_R	<	30	μA
V_R = 75 V	I_R	<	1	μA
V_R = 75 V; T_j = 150 °C	I_R	<	50	μA
Diode capacitance V_R = 0; f = 1 MHz	C_d	<	2	pF
Forward recovery voltage (see also Fig. 2) when switched to I_F = 10 mA; t_p = 20 ns	V_{fr}	<	1,75	V
Reverse recovery time (see also Fig. 3) when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	6	ns
Recovery charge (see also Fig. 4) when switched from I_F = 10 mA to V_R = 5 V; R_L = 500 Ω	Q_s	<	45	pC

* Measured under pulse conditions. $t_p \leqslant$ 0,5 ms. $I_{F(AV)}$ = 150 mA, $t_{(AV)} \leqslant$ 1 ms, for sinusoidal operation.

** See *Thermal characteristics.*

▲ Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

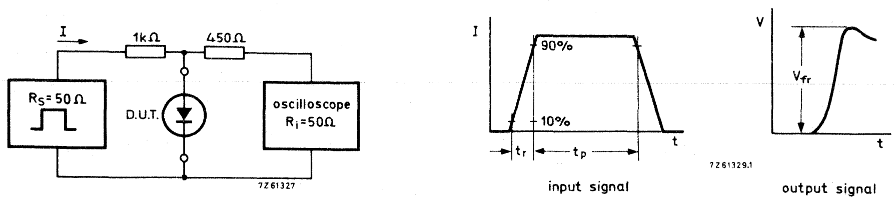


Fig. 2 Forward recovery voltage test circuit and waveforms.

Input signal: forward pulse rise time = t_r = 20 ns; forward current pulse duration t_p = 120 ns; duty factor = δ = 0,01.
Oscilloscope: rise time = t_r = 0,35 ns.
Circuit capacitance C ⩽ 1 pF (C = oscilloscope input capacitance + parasitic capacitance).

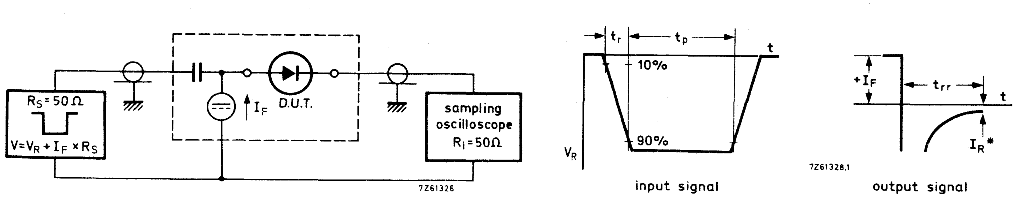


Fig. 3 Reverse recovery time test circuit and waveforms.

Input signal: reverse pulse rise time = t_r = 0,6 ns; reverse pulse duration = t_p = 100 ns; duty factor = δ = 0,05. * t_{rr} up to I_R = 1 mA.
Oscilloscope: rise time = t_r = 0,35 ns.
Circuit capacitance C ⩽ 1 pF (C = oscilloscope input capacitance + parasitic capacitance).

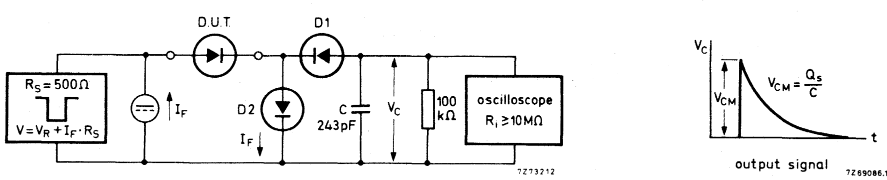


Fig. 4 Recovery charge test circuit and waveform.

D1 = BAW62; D2 = diode with minority carrier life time at 10 mA: < 200 ps
Input signal

Rise time of the reverse pulse	t_r	=	2	ns
Reverse pulse duration	t_p	=	400	ns
Duty factor	δ	=	0,02	

Circuit capacitance C ⩽ 7 pF (C = oscilloscope input capacitance + parasitic capacitance).

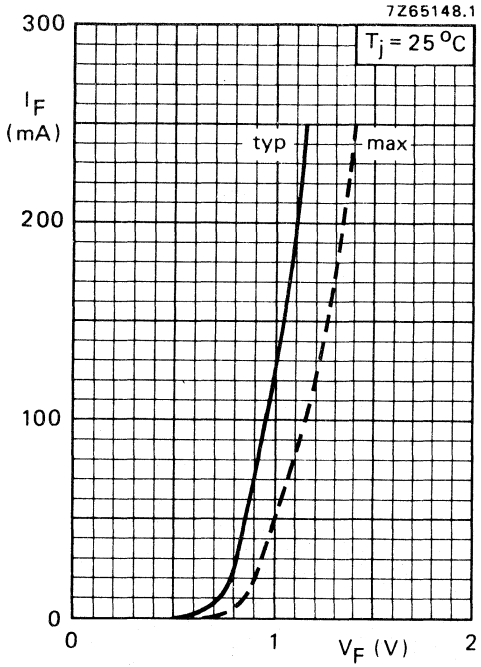


Fig. 5.

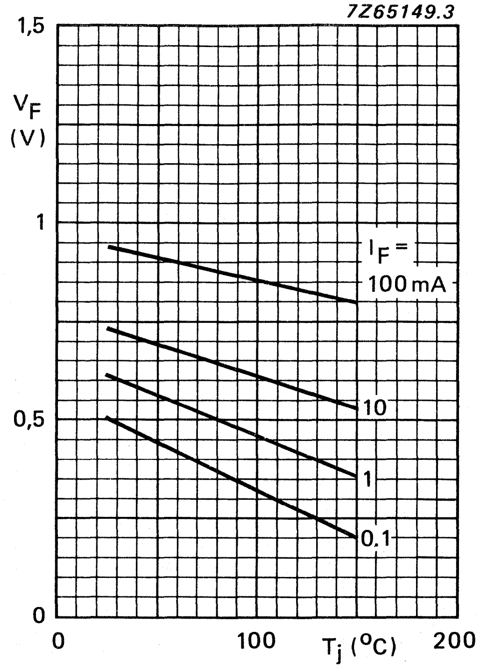


Fig. 6 Typical values.

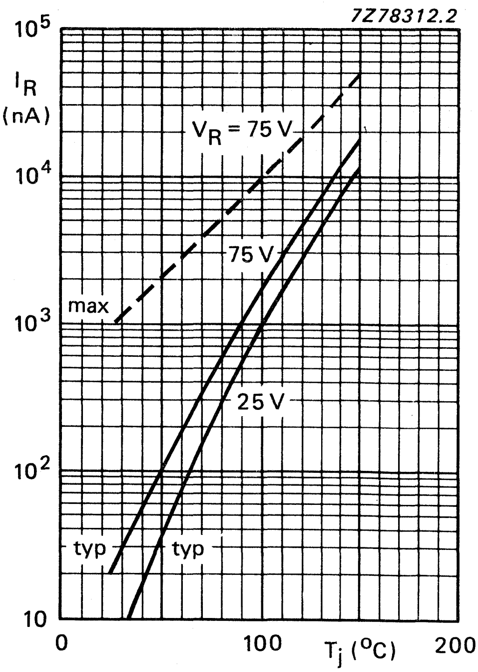


Fig. 7.

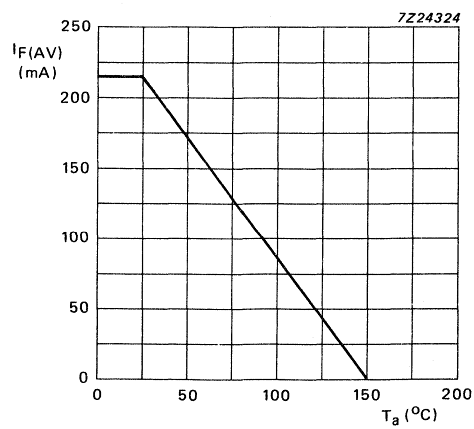


Fig. 8 Current derating curve.

LOW VOLTAGE STABISTOR

Silicon planar epitaxial diode in SOT-23 envelope. This diode is intended for low voltage stabilizing e.g. bias stabilizer in class-B output stages, clipping, clamping and meter protection.

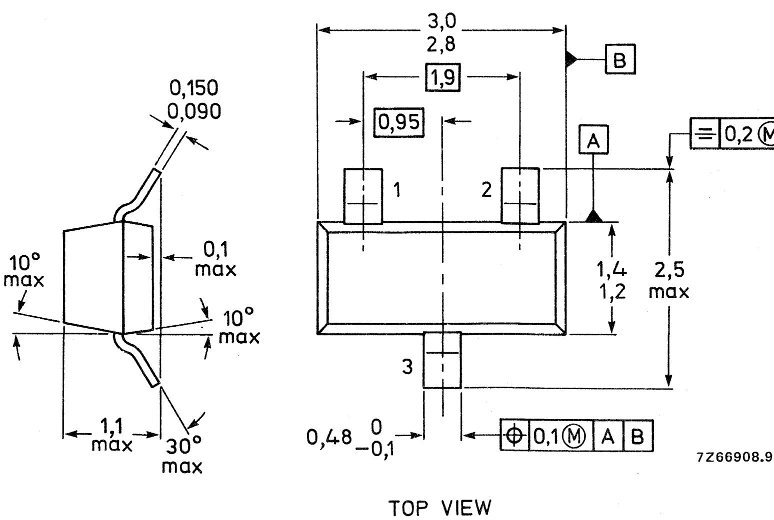
QUICK REFERENCE DATA

Repetitive peak forward current	I_{FRM}	max.	250	mA
Storage temperature	T_{stg}	−65 to + 150		°C
Junction temperature	T_j	max.	150	°C
Forward voltage				
I_F = 0,1 mA	V_F		580 to 660	mV
I_F = 1,0 mA	V_F		665 to 745	mV
I_F = 10 mA	V_F		750 to 830	mV
I_F = 100 mA	V_F		870 to 960	mV
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	140	pF

MECHANICAL DATA

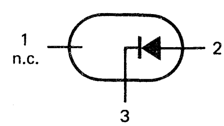
Dimensions in mm

Fig. 1 SOT-23.



Marking code

BAS17 = A91



See also chapter *Soldering Recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Repetitive peak forward current *	I_{FRM}	max.	250	mA
Storage temperature	T_{stg}	−65 to + 150		°C
→ Junction temperature	T_j	max.	150	°C

THERMAL CHARACTERISTICS **

→ From junction to ambient *	$R_{th\ j\text{-}t}$	=	420	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage				
I_F = 0,1 mA	V_F		580 to 660	mV
I_F = 1,0 mA	V_F		665 to 745	mV
I_F = 5,0 mA	V_F		725 to 805	mV
I_F = 10 mA	V_F		750 to 830	mV
I_F = 100 mA	V_F		870 to 960	mV
Reverse current				
V_R = 4 V	I_R	<	5	μA
Temperature coefficient				
I_F = 1 mA	S_F	typ.	−1,8	mV/K
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	140	pF

* Mounted on a ceramic substrate of 7 mm x 5 mm x 0,5 mm.
** See *Thermal characteristics.*

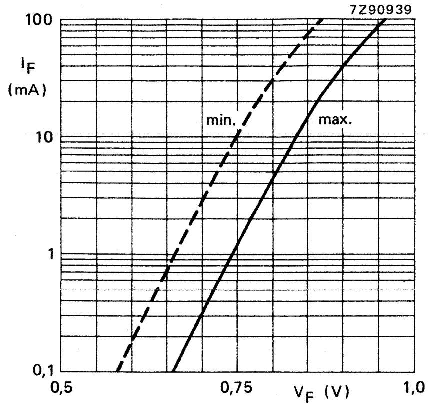


Fig. 2 Forward current as a function of forward voltage.

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODES

Silicon epitaxial high-speed diodes in a microminiature plastic envelope. They are intended for switching and general purposes.

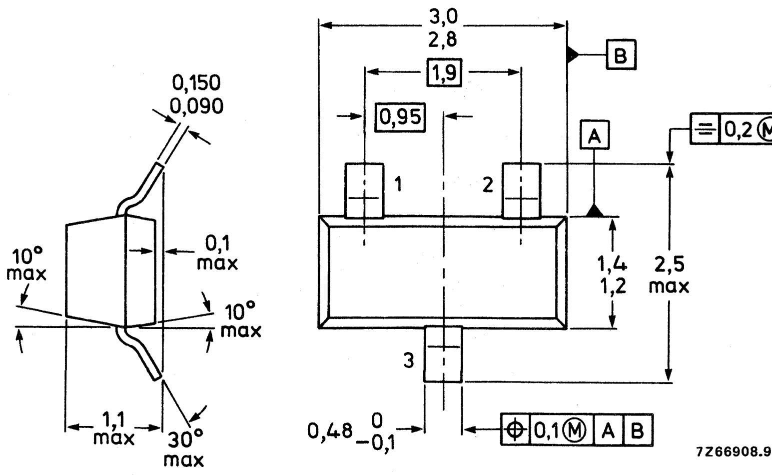
QUICK REFERENCE DATA

			BAS19	BAS20	BAS21	
Continuous reverse voltage	V_R	max.	100	150	200	V
Repetitive peak reverse voltage	V_{RRM}	max.	120	200	250	V
Repetitive peak forward current	I_{FRM}	max.		625		mA
Junction temperature	T_j	max.		150		°C
Forward voltage at I_F = 100 mA	V_F	<		1		V
Reverse recovery time when switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω measured at I_R = 3 mA	t_{rr}	<		50		ns

MECHANICAL DATA

Dimensions in mm

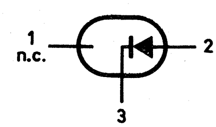
Fig. 1 SOT-23.



TOP VIEW

Marking code

BAS19 = A8
BAS20 = A81
BAS21 = A82



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BAS19	BAS20	BAS21	
Continuous reverse voltage	V_R	max.	100	150	200	V
Repetitive peak reverse voltage	V_{RRM}	max.	120	200	250	V
Non-repetitive peak forward current (per crystal)						
t = 1 μs	I_{FSM}	max.		2,5		A
t = 1 s	I_{FSM}	max.		0,5		A
Average rectified forward current (1) (averaged over any 20 ms period)	$I_{F(AV)}$	max.		200		mA
Forward current (DC) up to T_{amb} = 25 °C*	I_F	max.		200		mA
Repetitive peak forward current	I_{FRM}	max.		625		mA
Storage temperature range	T_{stg}			−65 to + 150		°C
Junction temperature	T_j	max.		150		°C
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.		200		mW

THERMAL RESISTANCE**

From junction to ambient*	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

Forward voltage				
I_F = 100 mA	V_F	<	1,0	V
I_F = 200 mA	V_F	<	1,25	V
Reverse breakdown voltage (1)				
BAS19; I_R = 100 μA	$V_{(BR)R}$	>	120	V
BAS20; I_R = 100 μA	$V_{(BR)R}$	>	200	V
BAS21; I_R = 100 μA (2)	$V_{(BR)R}$	>	250	V
Reverse current				
$V_R = V_{Rmax}$	I_R	<	100	nA
$V_R = V_{Rmax}$; T_j = 150 °C	I_R	<	100	μA
Differential resistance				
I_F = 10 mA	r_{diff}	typ.	5	Ω

(1) Measured under pulse conditions; Pulse time = $t_p \leqslant$ 0,3 ms.
(2) At zero life time, measured under pulse conditions to avoid excessive dissipation and voltage limited to 275 V.
* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.
** See *Thermal characteristics.*

Diode capacitance			
$V_R = 0$; f = 1 MHz	C_d	<	5 pF
Reverse recovery time (see Figs 2 and 3) when switched from $I_F = 30$ mA to $I_R = 30$ mA; $R_L = 100\ \Omega$; measured at $I_R = 3$ mA	t_{rr}	<	50 ns

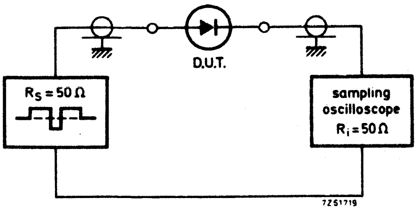


Fig. 2 Test circuit.

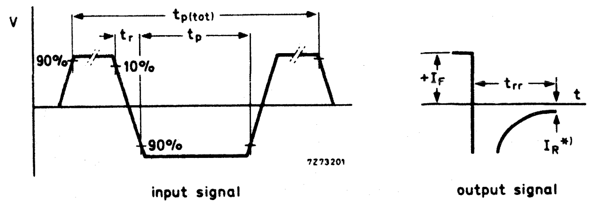


Fig. 3 Waveforms; $I_R = 3$ mA.

Input signal		
total pulse duration	$t_{p(tot)}$	= 2 μs
duty factor	δ	= 0,0025
rise time of reverse pulse	t_r	= 0,6 ns
reverse pulse duration	t_p	= 100 ns
Oscilloscope		
rise time	t_r	= 0,35 ns
circuit capacitance*	C	< 1 pF

*C = oscilloscope input capacitance + parasitic capacitance.

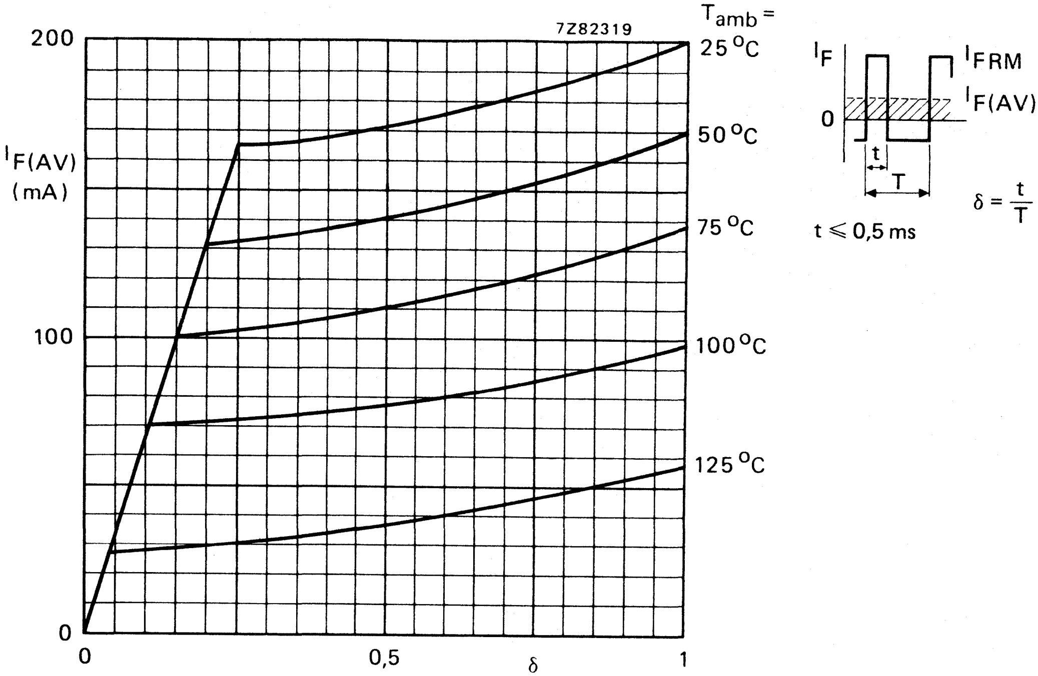


Fig. 4 BAS19; maximum permissible average rectified forward current for pulse operation as a function of the duty factor at V_R = 100 V.

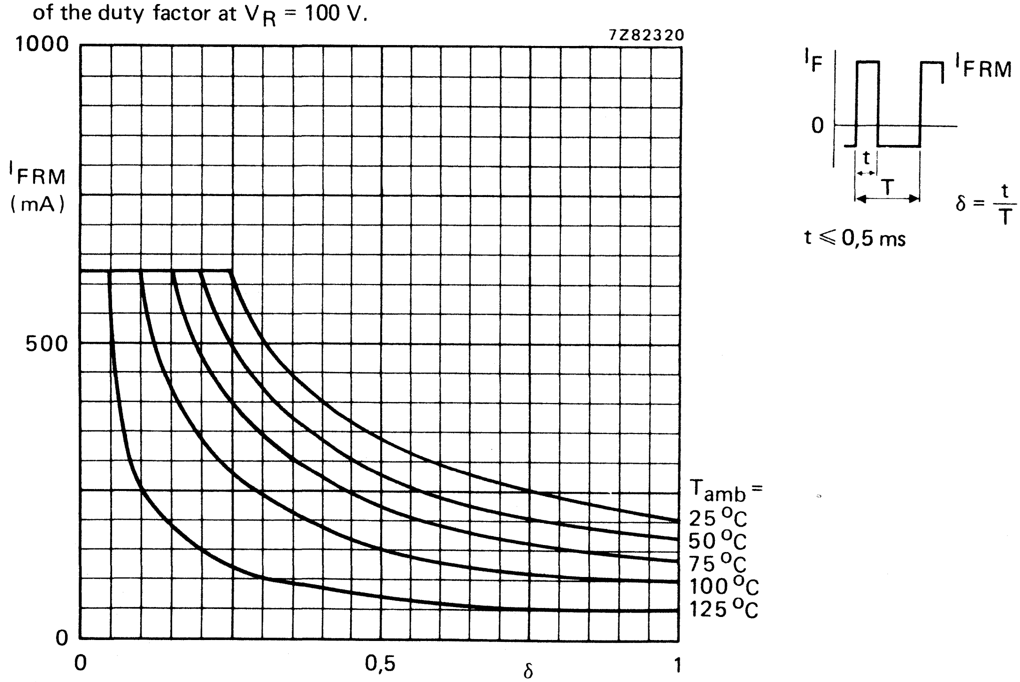


Fig. 5 BAS19; maximum permissible repetitive peak forward current for pulse operation as a function of the duty factor at V_R = 100 V.

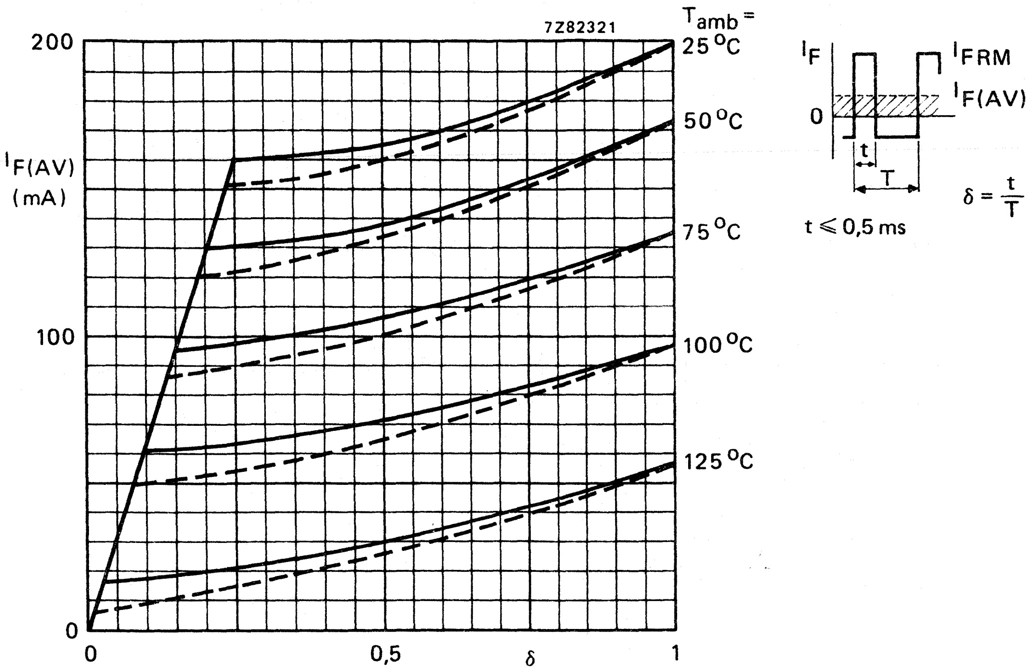


Fig. 6 BAS20/21; maximum permissible average rectified forward current for pulse operation as a function of the duty factor.

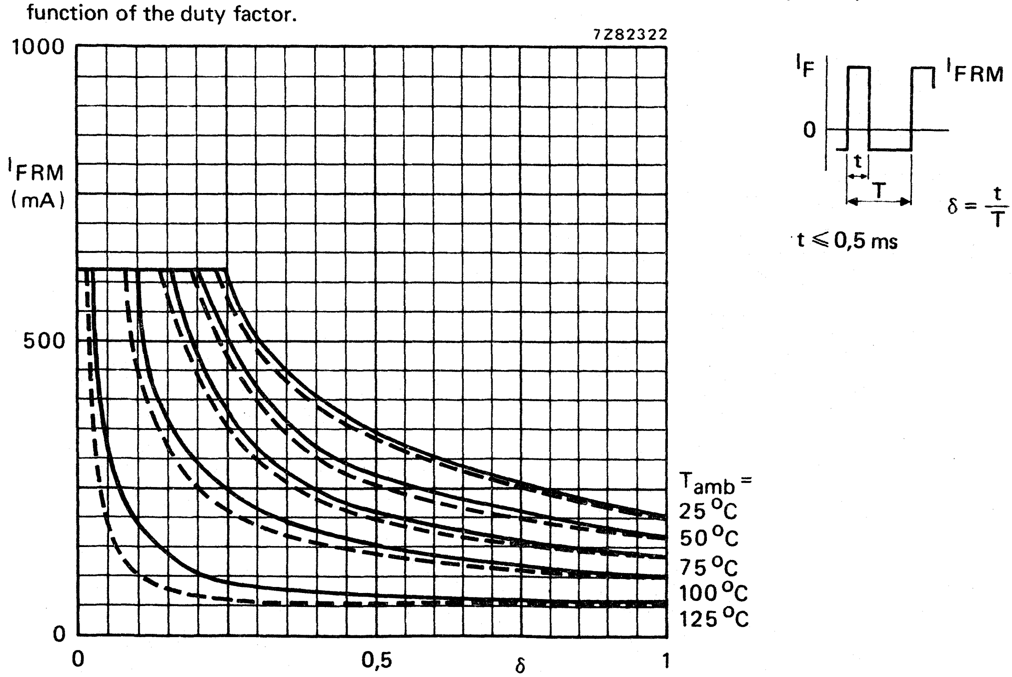


Fig. 7 BAS20/21; maximum permissible repetitive peak forward current for pulse operation as a function of the duty factor.

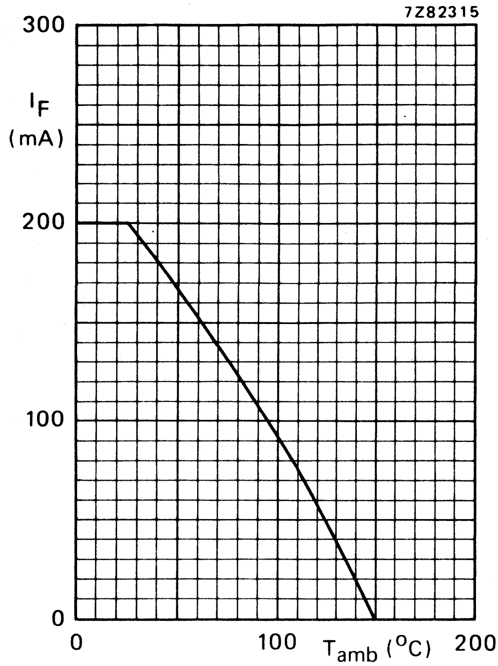


Fig. 8.

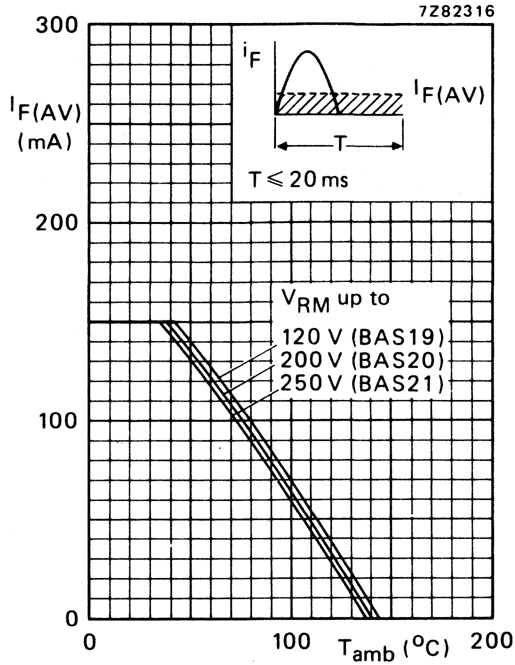


Fig. 9.

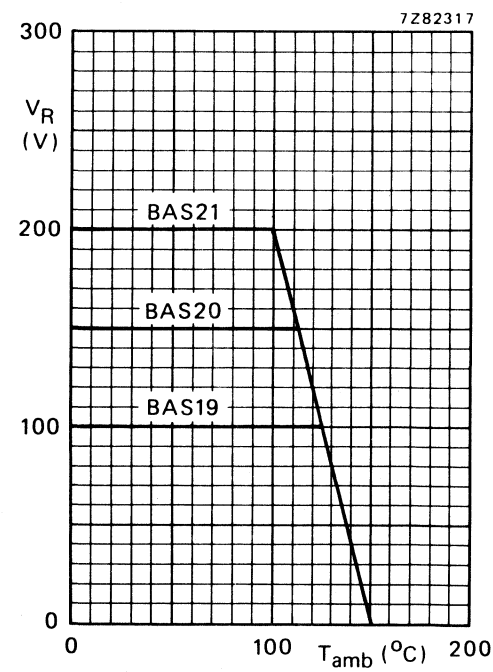


Fig. 10.

Fig. 8 Maximum permissible continuous forward current as a function of the ambient temperature.

Fig. 9 Maximum permissible average rectified forward current as a function of the ambient temperature.

Fig. 10 Maximum permissible continuous reverse voltage as a function of the ambient temperature.

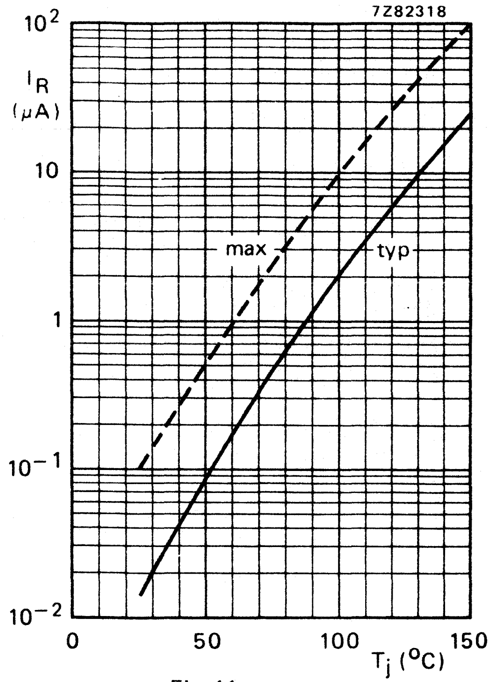


Fig. 11.

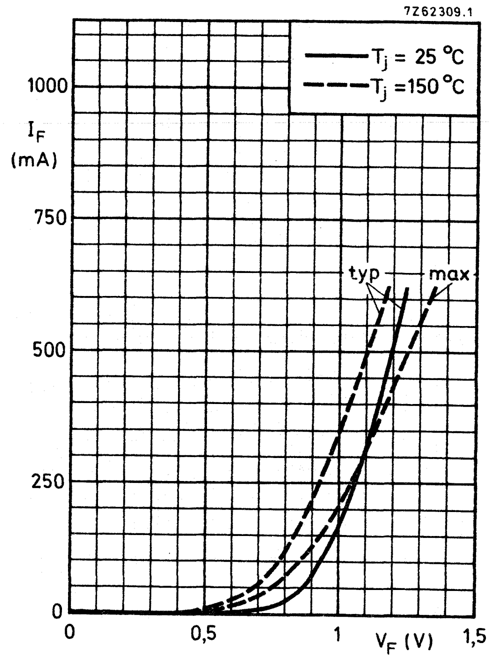


Fig. 12.

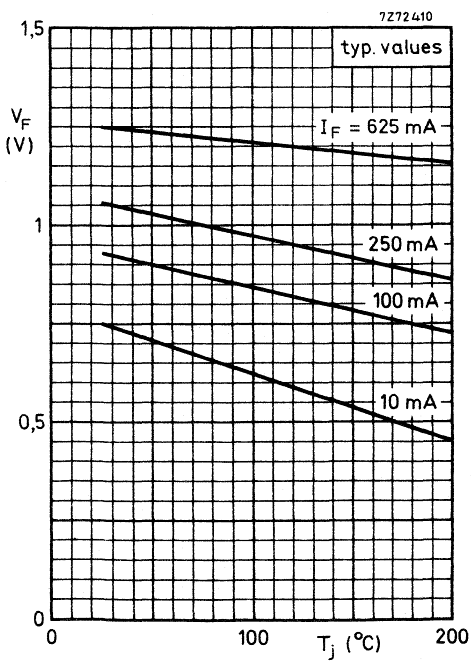


Fig. 13.

Fig. 11 Continuous reverse current as a function of the junction temperature.

Fig. 12 Forward current as a function of forward voltage.

Fig. 13 Forward voltage as a function of the junction temperature.

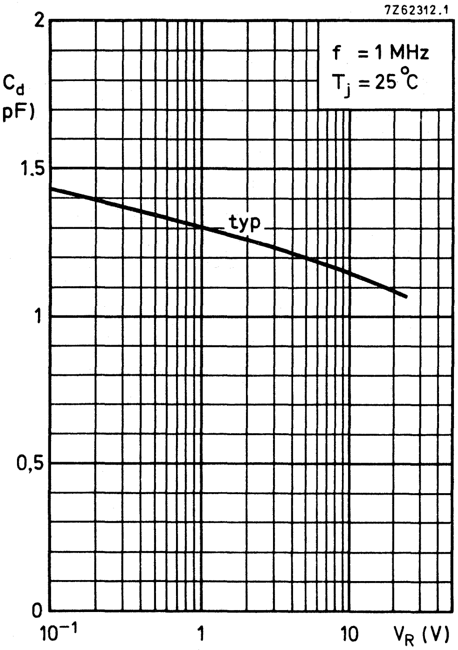

7Z62312.1
f = 1 MHz
T_j = 25 °C
C_d
(pF)
2
1.5
1
0,5
0
typ
10^{-1}
1
10
V_R (V)

Fig. 14.

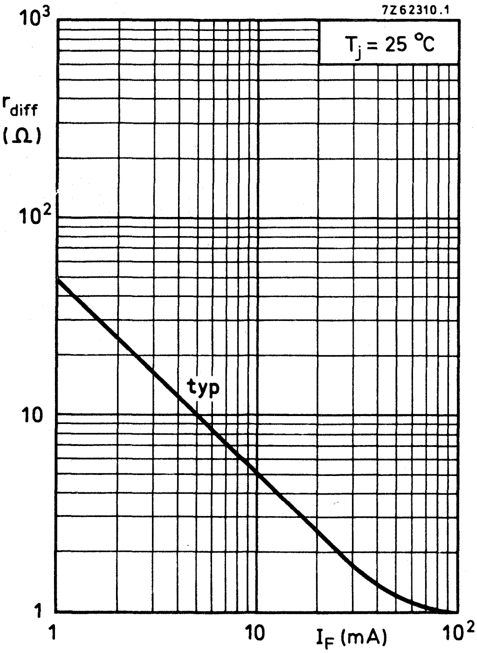

7Z62310.1
T_j = 25 °C
r_{diff}
(Ω)
10^3
10^2
10
1
typ
1
10
I_F (mA)
10^2

Fig. 15.

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODES

The BAS29, BAS31 and the BAS35 are silicon planar epitaxial diodes encapsulated in a SOT-23 envelope.

The BAS29 consists of a single diode. The BAS31 has two diodes in series and the BAS35 has two diodes with a common anode. All diodes are designed for switching inductive loads in semi-electronic telephone exchanges.

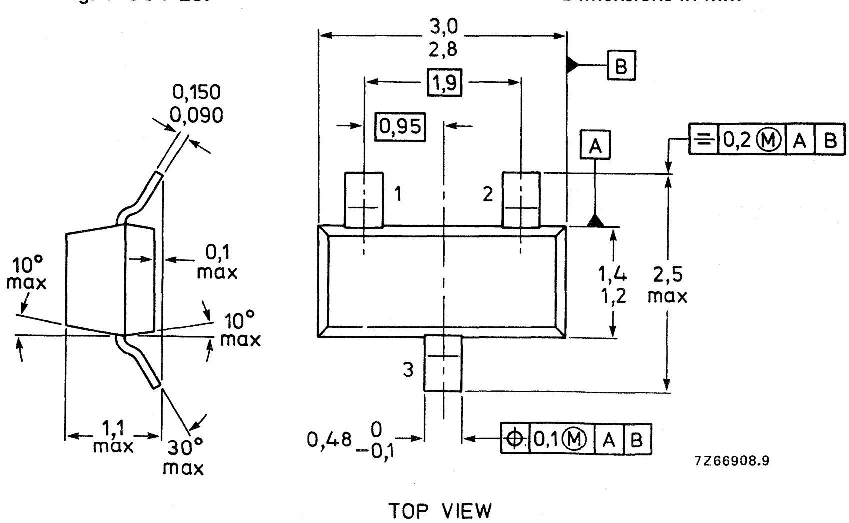
QUICK REFERENCE DATA (per diode)

Continuous reverse voltage	V_R	max.	90	V
Repetitive peak forward current	I_{FRM}	max.	600	mA
Forward current	I_F	max.	250	mA
Junction temperature	T_j	max.	150	°C
Forward voltage at I_F = 50 mA	V_F	<	0,84	V
Reverse recovery time when switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω; measured at I_R = 3 mA	t_{rr}	<	50	ns

MECHANICAL DATA

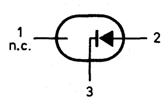
Fig. 1 SOT-23.

Dimensions in mm

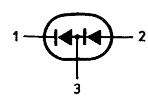


Marking code:

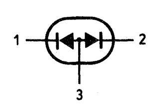
BAS29 = L20
BAS31 = L21
BAS35 = L22



BAS29



BAS31



BAS35

RATINGS (per diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	90	V
Repetitive peak forward current	I_{FRM}	max.	600	mA
Repetitive peak reverse current	I_{RRM}	max.	600	mA
Average rectified forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	250	mA
Non-repetitive peak forward current				
$t = 1\ \mu s$; $T_j = 25\ ^oC$ prior to surge; per crystal	I_{FSM}	max.	3	A
$t = 1\ s$; $T_j = 25\ ^oC$ prior to surge; per crystal	I_{FSM}	max.	0,75	A
Forward current (DC)	I_F	max.	250	mA
Repetitive peak reverse energy				
→ $t_p \geqslant 50\ \mu s$; $f \leqslant 20$ Hz; $T_j = 25\ ^oC$	E_{RRM}	max.	5,0	mJ
Storage temperature	T_{stg}		−65 to + 150	^oC
Junction temperature	T_j	max.	150	^oC

THERMAL RESISTANCE*

From junction to ambient**	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS (per diode)

$T_j = 25\ ^oC$ unless otherwise specified

Forward voltage				
$I_F = 10$ mA	V_F	<	0,75	V
$I_F = 50$ mA	V_F	<	0,84	V
$I_F = 100$ mA	V_F	<	0,90	V
$I_F = 200$ mA	V_F	<	1,00	V
$I_F = 400$ mA	V_F	<	1,25	V
Reverse current				
$V_R = 90$ V	I_R	<	100	nA
$V_R = 90$ V; $T_j = 150\ ^oC$	I_R	<	100	μA
Reverse avalanche breakdown voltage				
$I_R = 1$ mA	$V_{(BR)R}$		120 to 175	V
Diode capacitance				
$V_R = 0$; $f = 1$ MHz	C_d	<	35	pF
Reverse recovery time when switched from $I_F = 30$ mA to $I_R = 30$ mA; $R_L = 100\ \Omega$; measured at $I_R = 3$ mA	t_{rr}	<	50	ns

* See Thermal Characteristics.
** When mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

HIGH-SPEED SILICON DIODE FOR SURFACE MOUNTING

The BAS32 is a planar epitaxial high-speed diode designed for fast logic applications.

This SM diode is a leadless diode in a hermetically sealed SOD-80 envelope with tin-plated metal discs at each end. It is suitable for "automatic placement" and as such it can withstand immersion soldering.

The diodes are delivered in "super 8" tape.

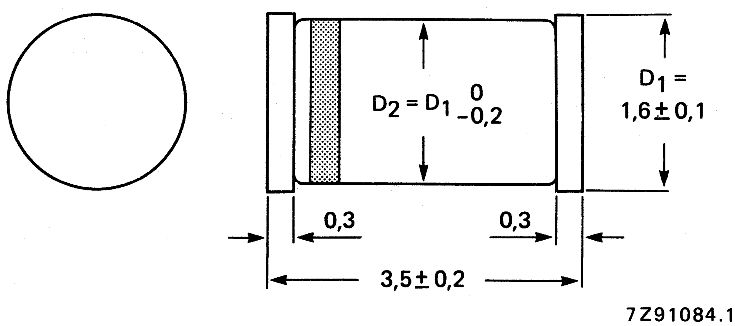
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	75	V
Repetitive peak reverse voltage	V_{RRM}	max.	75	V
Repetitive peak forward current	I_{FRM}	max.	450	mA
Junction temperature	T_j	max.	200	°C
Forward voltage I_F = 100 mA	V_F	<	1	V
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	4	ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



Cathode indicated by black band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	75	V
Repetitive peak reverse voltage	V_{RRM}	max.	75	V*
Average rectified forward current	$I_{F(AV)}$	max.	150	mA**
Forward current (d.c.)	I_F	max.	200	mA
Repetitive peak forward current	I_{FRM}	max.	450	mA
Non-repetitive peak forward current				
t = 1 μs	I_{FSM}	max.	2000	mA
t = 1 s	I_{FSM}	max.	500	mA
Storage temperature	T_{stg}	−65 to + 200		°C
Junction temperature	T_j	max.	200	°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0,6	K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltages				
I_F = 5 mA	V_F	0,62 to	0,75	V
I_F = 100 mA	V_F	<	1,00	V
I_F = 100 mA; T_j = 100 °C	V_F	<	0,93	V
Reverse currents				
V_R = 20 V	I_R	<	25	nA
V_R = 20 V; T_j = 150 °C	I_R	<	50	μA
V_R = 75 V	I_R	<	5	μA
V_R = 75 V; T_j = 150 °C	I_R	<	100	μA
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	2	pF
Forward recovery voltage when switched to				
I_F = 50 mA; t_r = 20 ns	V_{fr}	<	2,5	V

* Measured at zero life time at I_R = 100 μA; V_R > 100 V.

** For sinusoidal operation see Fig. 6. For pulse operation see Figs 4 and 5.

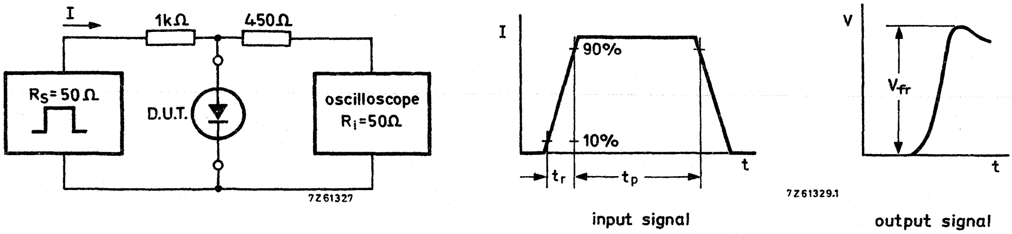


Fig. 2 Forward recovery voltage test circuit and waveforms.

Input signal : Rise time of the forward pulse t_r = 20 ns
Forward current pulse duration t_p = 120 ns
Duty factor δ = 0,01

Oscilloscope: Rise time t_r = 0,35 ns

Circuit capacitance C ⩽ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

Reverse recovery time when switched from
I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω;
measured at I_R = 1 mA t_{rr} < 4 ns

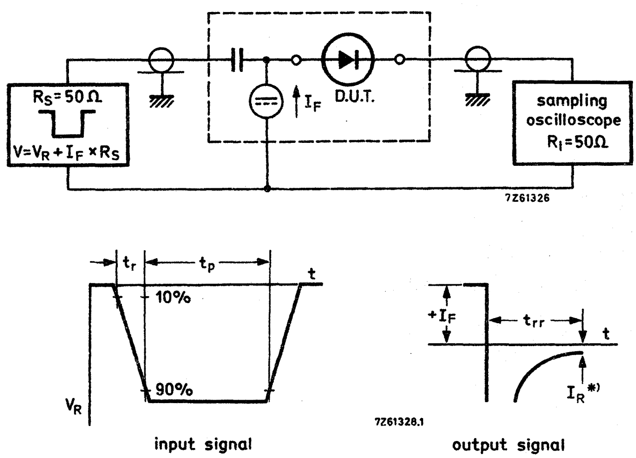


Fig. 3 Reverse recovery time test circuit and waveforms.

Input signal : Rise time of the reverse pulse t_r = 0,6 ns
Reverse pulse duration t_p = 100 ns
Duty factor δ = 0,05

* I_R = 1 mA

Oscilloscope: Rise time t_r = 0,35 ns

Circuit capacitance C ⩽ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

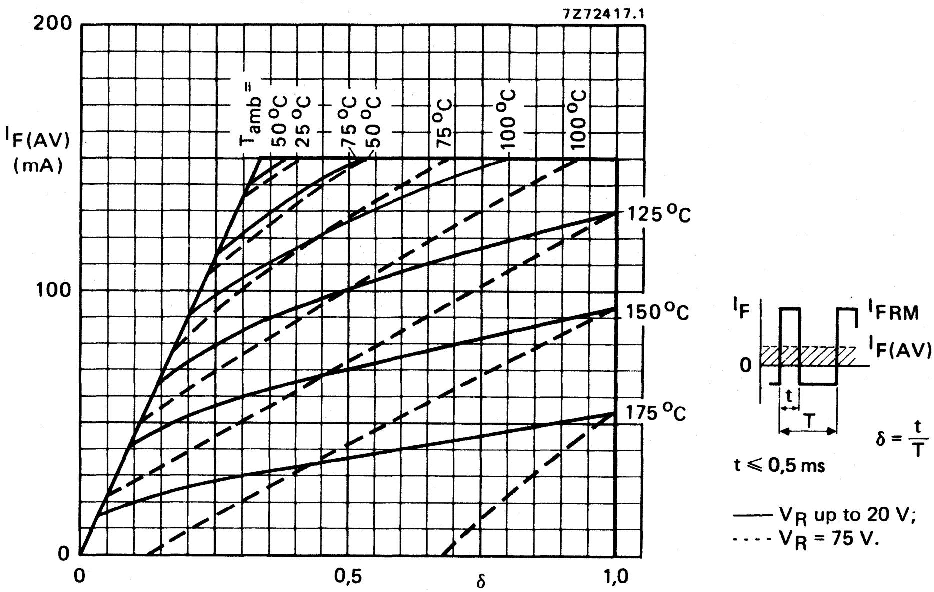


Fig. 4 Maximum permissible average rectified forward current versus duty factor (pulse operated).

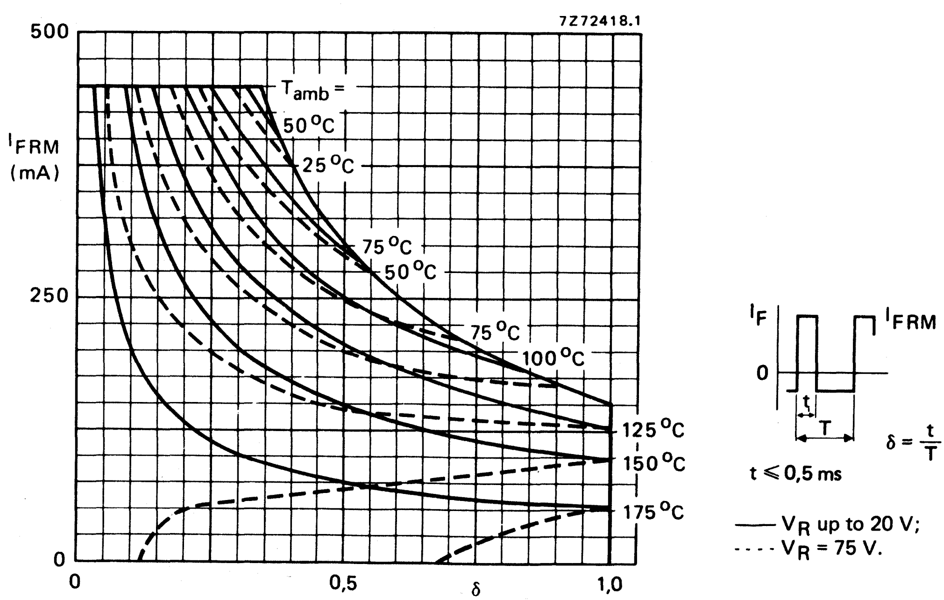


Fig. 5 Maximum permissible repetitive peak forward current versus duty factor (pulse operated).

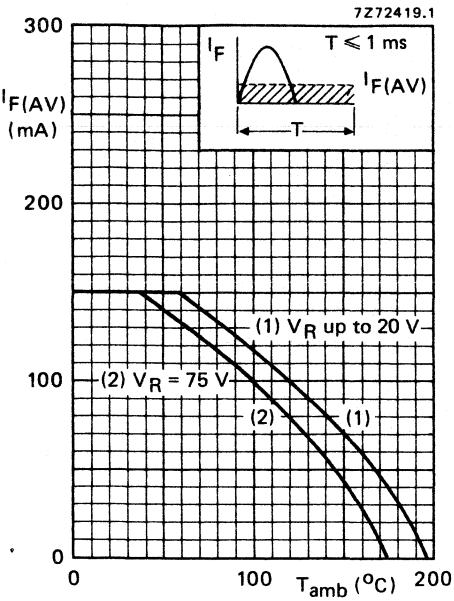


Fig. 6 Maximum permissible average rectified forward current versus ambient temperature.

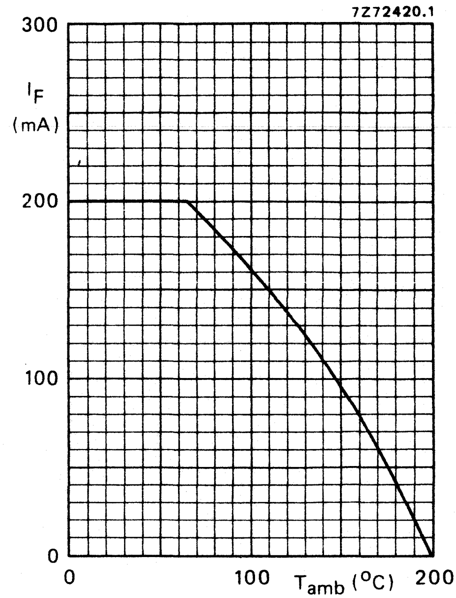


Fig. 7 Maximum permissible continuous forward current versus ambient temperature.

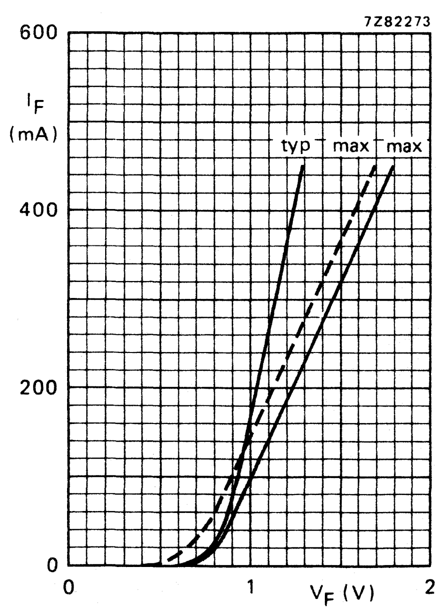


Fig. 8 Forward current versus forward voltage; —— T_j = 25 °C; – – – T_j = 175 °C.

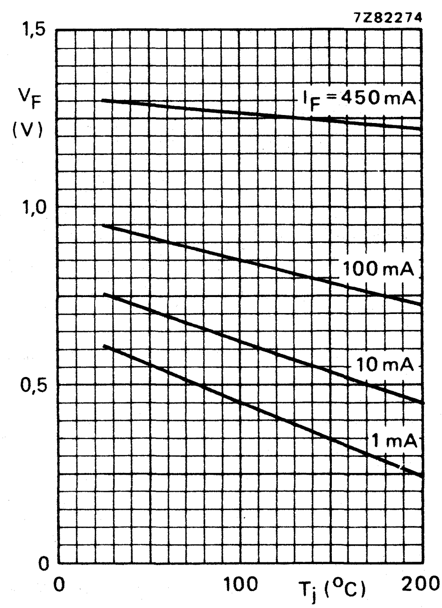


Fig. 9 Forward voltage versus junction temperature; typical values.

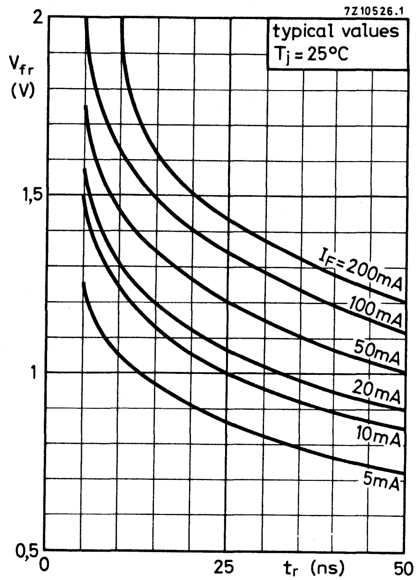


Fig. 10 Forward recovery voltage versus rise time.

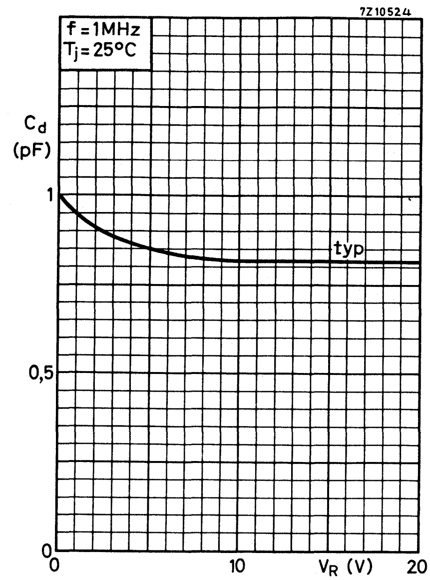


Fig. 11 Diode capacitance versus reverse voltage.

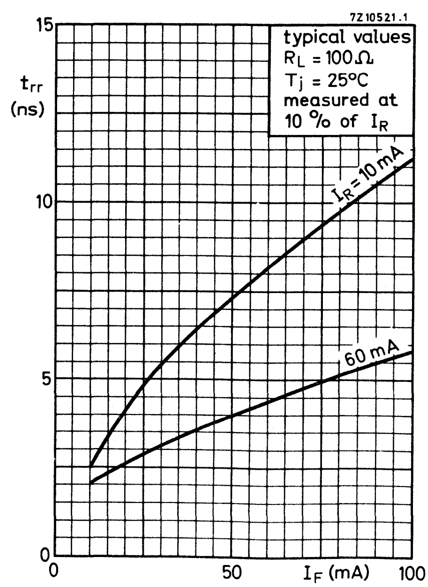


Fig. 12 Reverse recovery time versus forward current.

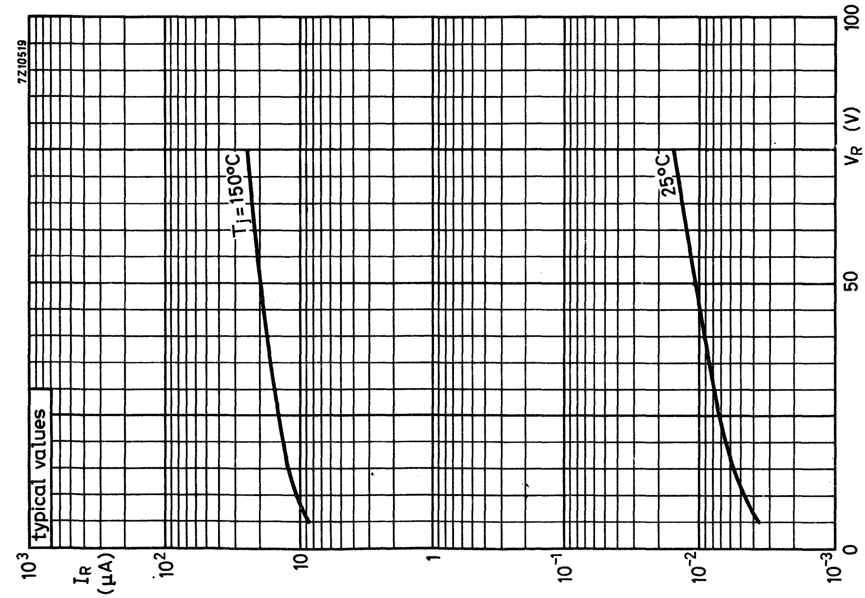


Fig. 13 Reverse current versus reverse voltage.

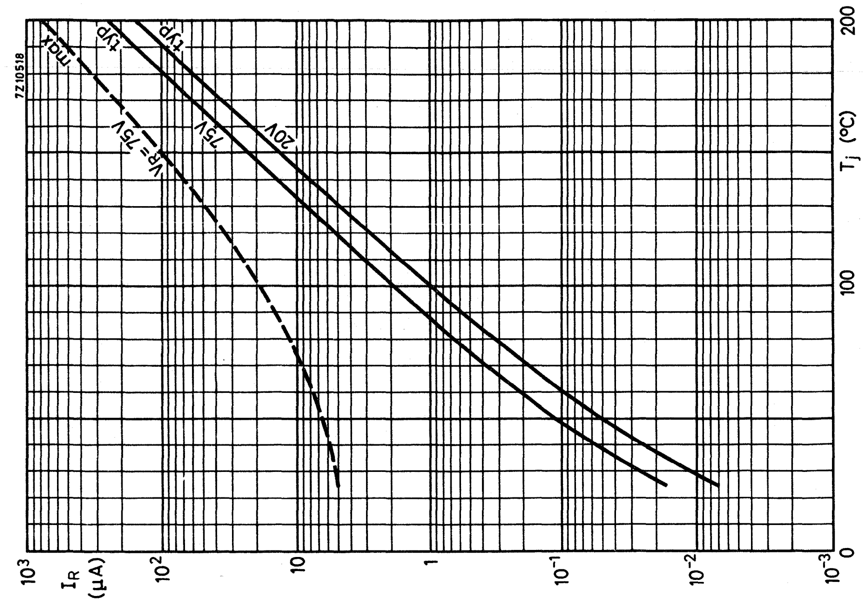


Fig. 14 Reverse current versus junction temperature.

HIGH-SPEED SILICON DIODE FOR SURFACE MOUNTING

The BAS32L is a planar epitaxial high-speed diode designed for fast logic applications.

This SM diode is a leadless diode in a hermetically sealed SOD-80C glass envelope with tin-plated metal discs at each end. It is suitable for "automatic placement" and as such it can withstand immersion soldering.

The diodes are delivered in "super 8" tape.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	75	V
Repetitive peak reverse voltage	V_{RRM}	max.	75	V
Repetitive peak forward current	I_{FRM}	max.	450	mA
Junction temperature	T_j	max.	200	^oC
Forward voltage I_F = 100 mA	V_F	<	1.0	V
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	4.0	ns

MECHANICAL DATA

Dimensions in mm

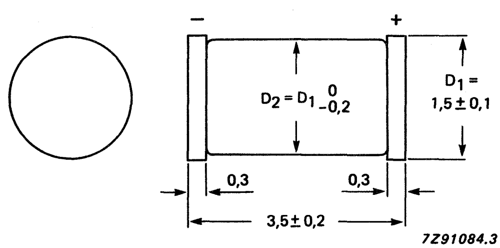


Fig. 1 SOD-80C.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	75	V
Repetitive peak reverse voltage	V_{RRM}	max.	75	V
Average rectified forward current *	$I_{F(AV)}$	max.	150	mA
Forward current (DC)	I_F	max.	200	mA
Repetitive peak forward current	I_{FRM}	max.	450	mA
Non-repetitive peak forward current				
t = 1 μs	I_{FSM}	max.	2000	mA
t = 1 s	I_{FSM}	max.	500	mA
Storage temperature range	T_{stg}	−65 to + 200		°C
Junction temperature	T_j	max.	200	°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\,j\text{-}a}$	=	0.6	K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltages				
I_F = 5 mA	V_F		0.62 to 0.75	V
I_F = 100 mA	V_F	<	1.0	V
I_F = 100 mA; T_j = 100 °C	V_F	<	0.93	V
Reverse breakdown voltage				
I_R = 100 μA	$V_{(BRR)}$	>	100	V
Reverse currents				
V_R = 20 V	I_R	<	25	nA
V_R = 20 V; T_j = 150 °C	I_R	<	50	μA
V_R = 75 V	I_R	<	5.0	μA
V_R = 75 V; T_j = 150 °C	I_R	<	100	μA
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	2.0	pF
Forward recovery voltage when switched to				
I_F = 50 mA; t_r = 20 ns	V_{fr}	<	2.5	V

* For sinusoidal operation see Fig. 6. For pulse operation see Figs 4 and 5.

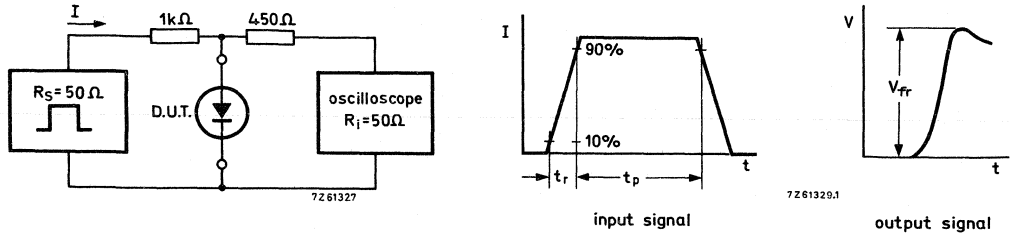


Fig. 2 Forward recovery voltage test circuit and waveforms.

Input signal :	Rise time of the forward pulse	t_r = 20 ns
	Forward current pulse duration	t_p = 120 ns
	Duty factor	δ = 0.01
Oscilloscope:	Rise time	t_r = 0.35 ns

Circuit capacitance C ⩽ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

Reverse recovery time when switched from
I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω;
measured at I_R = 1 mA — t_{rr} < 4 ns

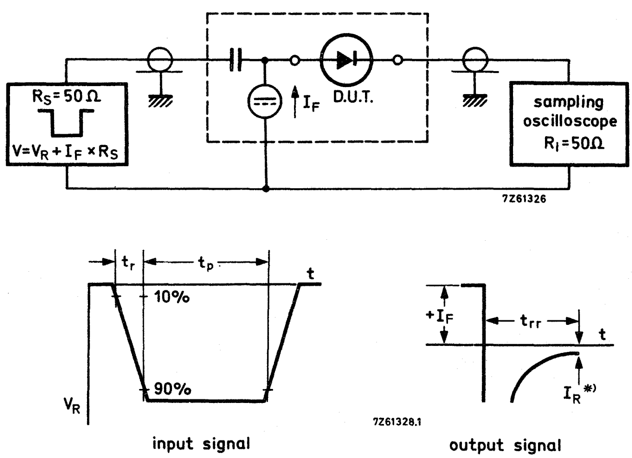


Fig. 3 Reverse recovery time test circuit and waveforms.

Input signal :	Rise time of the reverse pulse	t_r = 0.6 ns	* I_R = 1 mA
	Reverse pulse duration	t_p = 100 ns	
	Duty factor	δ = 0.05	
Oscilloscope:	Rise time	t_r = 0.35 ns	

Circuit capacitance C ⩽ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

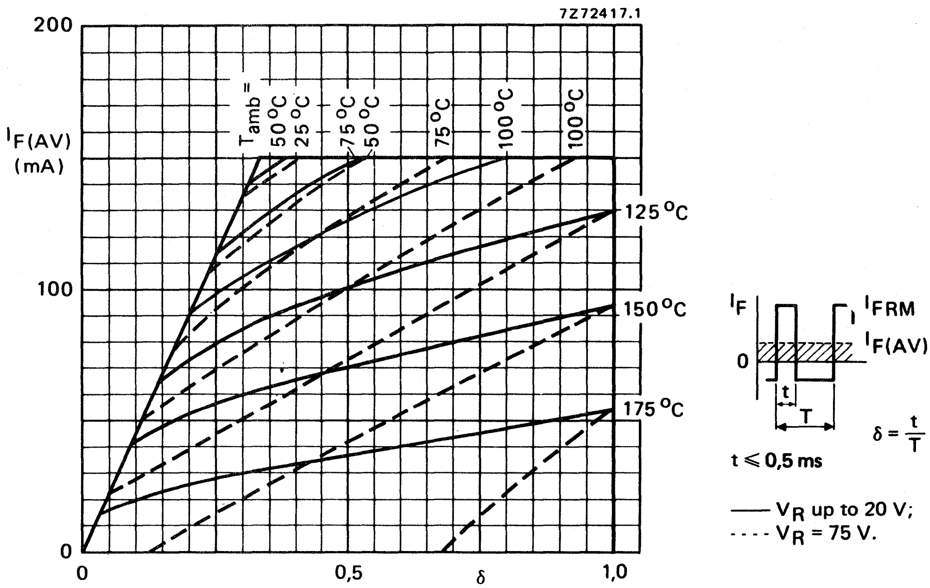


Fig. 4 Maximum permissible average rectified forward current as a function of duty factor (pulse operated).

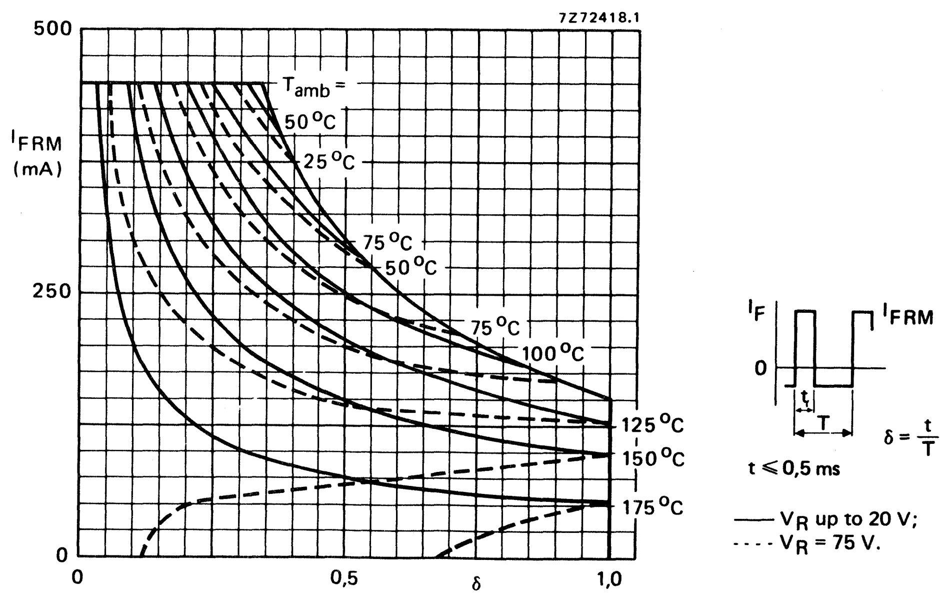


Fig. 5 Maximum permissible repetitive peak forward current as a function of duty factor (pulse operated).

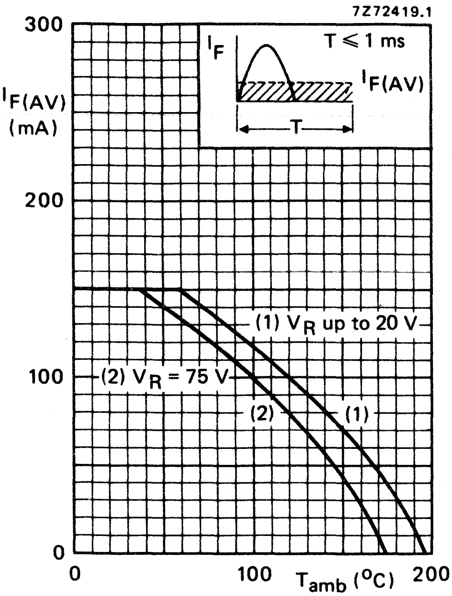


Fig. 6 Maximum permissible average rectified forward current as a function of ambient temperature.

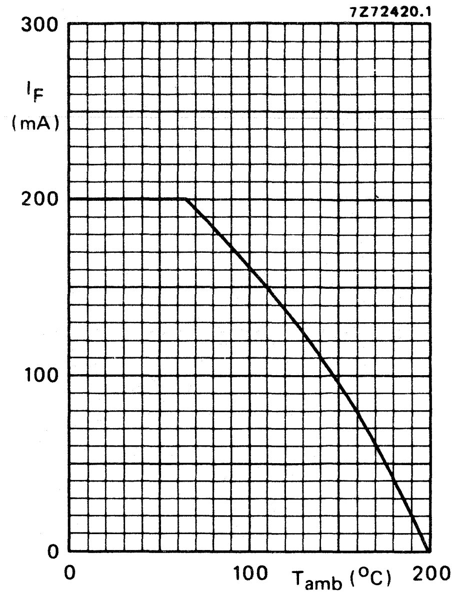


Fig. 7 Maximum permissible continuous forward current as a function of ambient temperature.

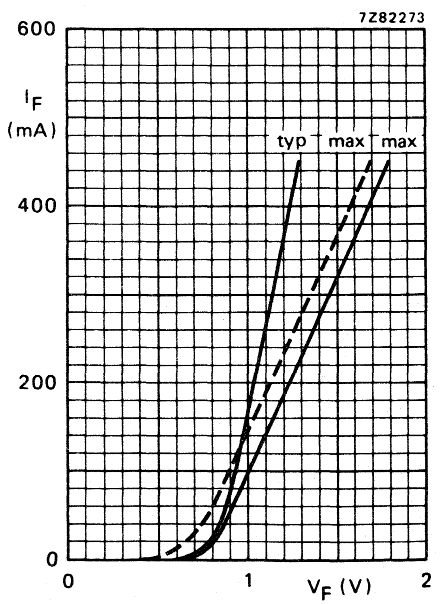


Fig. 8 Forward current as a function of forward voltage; —— T_j = 25 °C; – – – T_j = 175 °C.

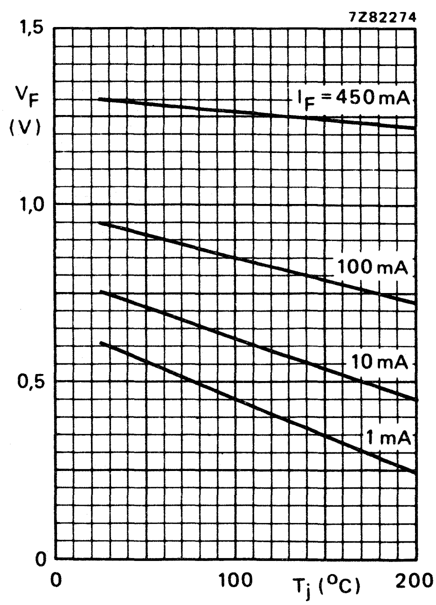


Fig. 9 Forward voltage as a function of junction temperature; typical values.

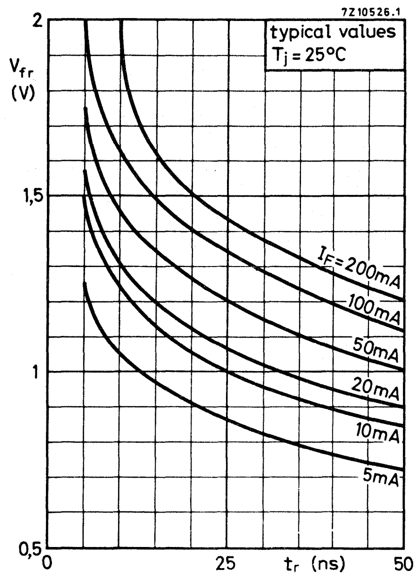


Fig. 10 Forward recovery voltage as a function of rise time.

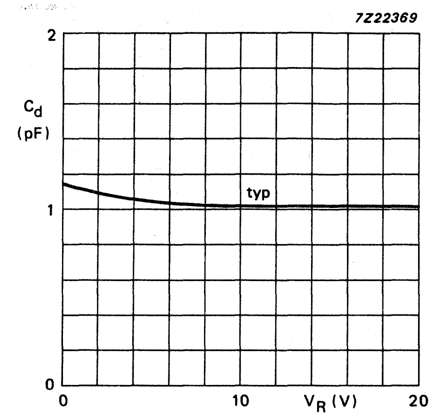


Fig. 11 Diode capacitance as a function of reverse voltage.

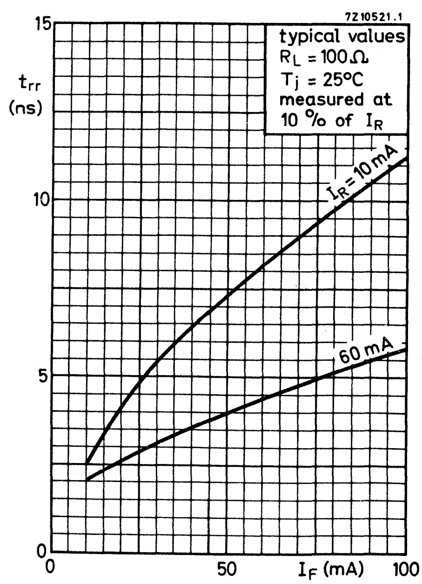


Fig. 12 Reverse recovery time as a function of forward current.

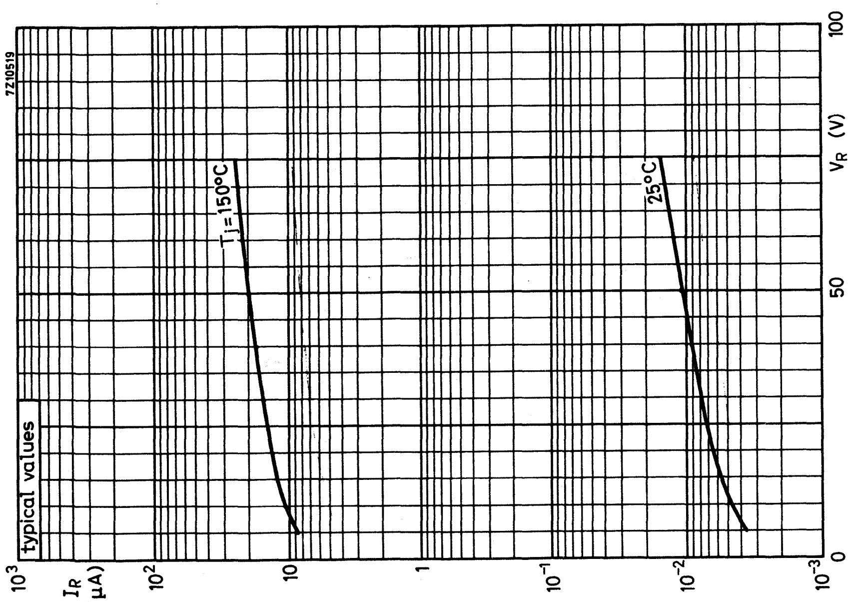


Fig. 13 Reverse current as a function of reverse voltage.

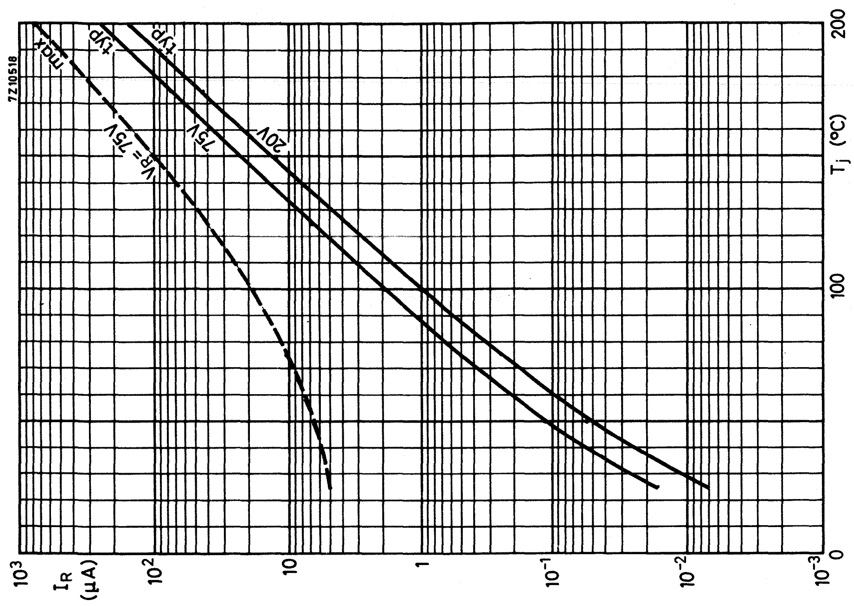


Fig. 14 Reverse current as a function of junction temperature.

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODE

For data of this diode please refer to types BAS29/31.

LOW LEAKAGE DIODE

Switching diode with a very low reverse current, encapsulated in a subminiature glass (DO-34) envelope.

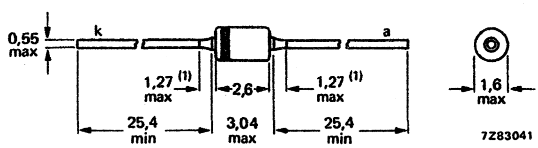
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	125 V
Forward voltage I_F = 200 mA	V_F	max.	1,0 V
Reverse current V_R = 125 V	I_R	max.	1,0 nA
Diode capacitance V_R = 0; f = 1 MHz	C_d	max.	8,0 pF

MECHANICAL DATA

Dimensions in mm

Fig. 1 DO-34 (SOD-68).



(1) Lead diameter in this zone uncontrolled.

The cathode is indicated by a coloured band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	125	V
Forward current (d.c.)	I_F	max.	225	mA
Repetitive peak forward current	I_{FRM}	max.	450	mA
Non-repetitive peak forward current $t_p = 1\ \mu s$	I_{FSM}	max.	4	A
Storage temperature	T_{stg}	−65 to + 175		^oC
Junction temperature	T_j	max.	125	^oC

THERMAL RESISTANCE

From junction to ambient in free air mounted on a p.c. board with a clearance of 10 mm	$R_{th\ j\text{-}a}$	=	400	K/W

CHARACTERISTICS

$T_j = 25\ ^oC$ unless otherwise specified

Reverse current under maximum light conditions (illuminance = 500 lux)				
$V_R = 125$ V	I_R	max.	1	nA
$V_R = 30$ V; $T_j = 125\ ^oC$	I_R	max.	300	nA
$V_R = 125$ V; $T_j = 125\ ^oC$	I_R	max.	500	nA
Forward voltage				
$I_F = 1$ mA	V_F	0,64 to 0,74		V
$I_F = 5$ mA	V_F	0,70 to 0,80		V
$I_F = 50$ mA	V_F	0,74 to 0,88		V
$I_F = 200$ mA	V_F	0,83 to 1,00		V
Diode capacitance				
$V_R = 0$; f = 1 MHz	C_d	max.	8	pF

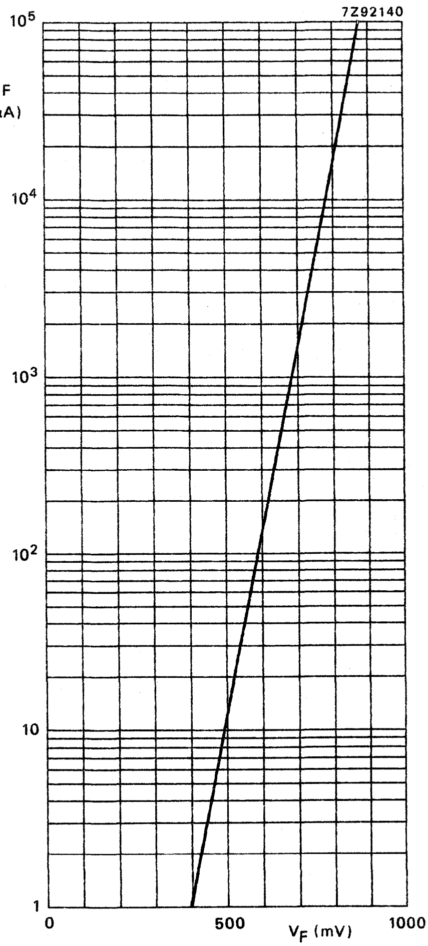


Fig. 2 T_j = 25 °C; typical values.

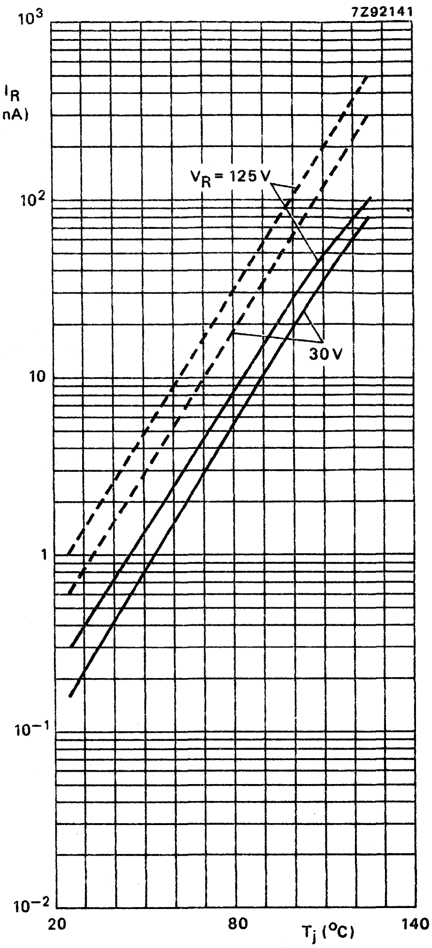


Fig. 3 – – – = max. values;
——— = typ. values.

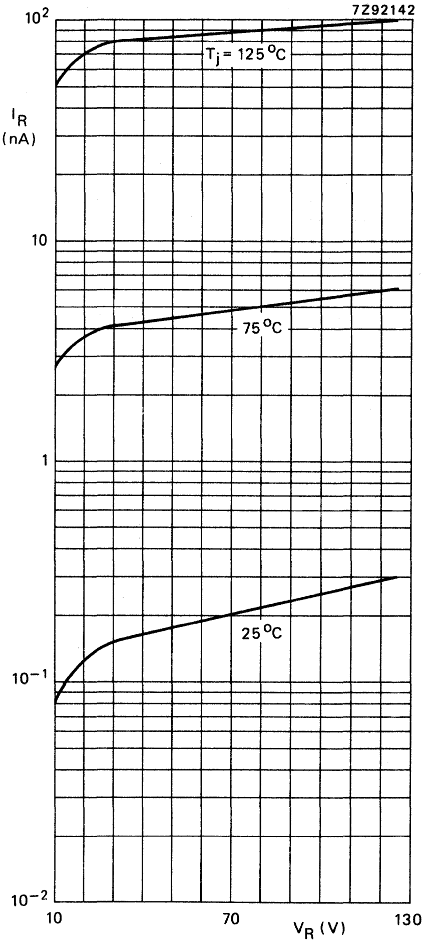


Fig. 4 Typical values.

LOW LEAKAGE DIODE FOR SURFACE MOUNTING

The BAS45L is a switching diode with a very low reverse current.

This SM diode is a leadless diode in a hermetically sealed SOD-80 envelope with lead/tin-plated metal discs at each end. It is suitable for "automatic placement" and as such it can withstand immersion soldering.

The diodes are delivered in "super 8" tape.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	125 V
Forward voltage I_F = 100 mA	V_F	max.	1.0 V
Reverse current V_R = 125 V	I_R	max.	1.0 nA
Diode capacitance V_R = 0; f = 1 MHz	C_d	max.	8.0 pF

MECHANICAL DATA

Dimensions in mm

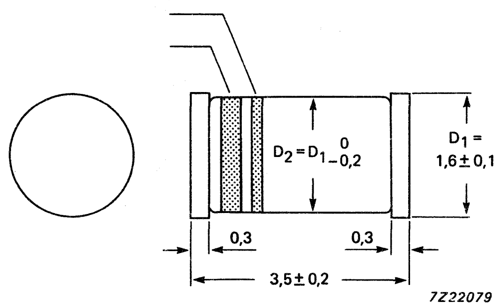


Fig. 1 SOD-80.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	125	V
Forward current (DC)	I_F	max.	225	mA
Repetitive peak forward current	I_{FRM}	max.	450	mA
Non-repetitive peak forward current $t_p = 1\ \mu s$	I_{FSM}	max.	4.0	A
Storage temperature range	T_{stg}	−65 to + 175		^oC
Junction temperature	T_j	max.	125	^oC

THERMAL RESISTANCE

From junction to ambient on a ceramic substrate of 8 mm x 10 mm x 0.7 mm (see soldering recommendations SOD-80)	$R_{th\ j\text{-}a}$	400	K/W

CHARACTERISTICS

$T_j = 25\ ^oC$ unless otherwise specified

Reverse current under maximum light conditions (illuminance ⩽ 100 lux) see Fig. 5				
$V_R = 125$ V	I_R	<	1.0	nA
$V_R = 30$ V; $T_j = 125\ ^oC$	I_R	<	300	nA
$V_R = 125$ V; $T_j = 125\ ^oC$	I_R	<	500	nA
Forward voltage				
$I_F = 1$ mA	V_F	0.64 to 0.74		V
$I_F = 5$ mA	V_F	0.70 to 0.80		V
$I_F = 50$ mA	V_F	0.74 to 0.88		V
$I_F = 200$ mA	V_F	0.83 to 1.00		V
Diode capacitance				
$V_R = 0$; f = 1 MHz	C_d	<	8.0	pF

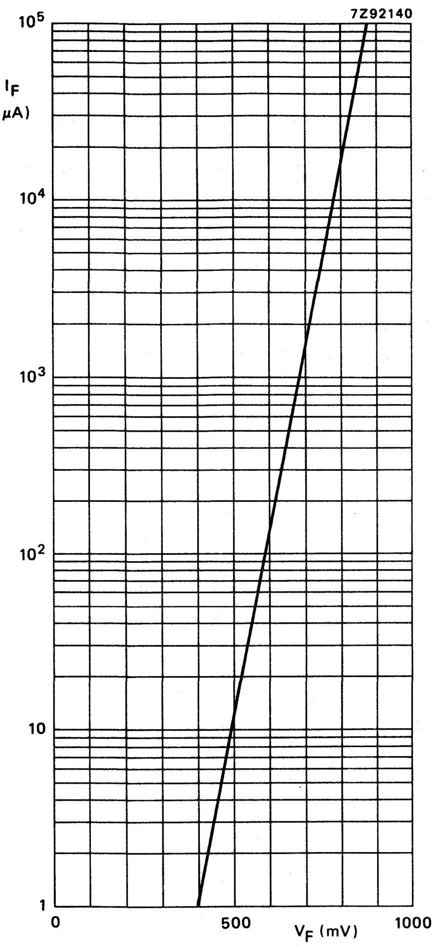


Fig. 2 Forward current as a function of forward voltage; T_j = 25 °C; typical values.

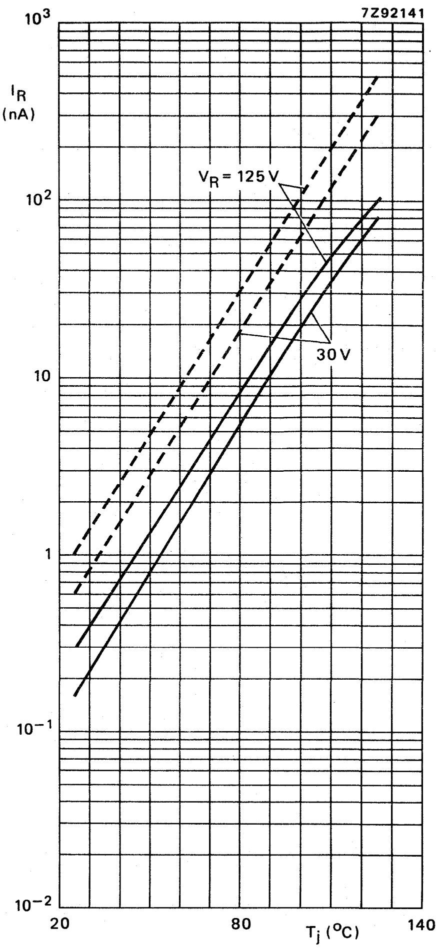


Fig. 3 Reverse current as a function of junction temperature;
– – – = max. values.
——— = typ. values.

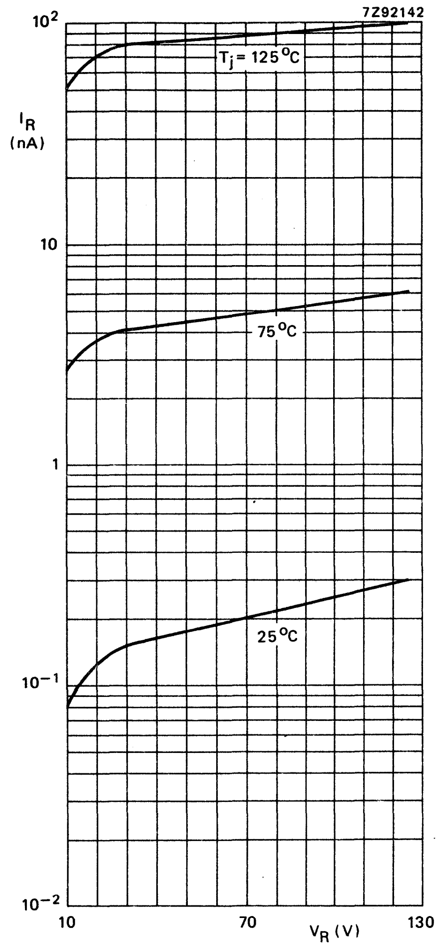


Fig. 4 Reverse current as a function of reverse voltage; typical values.

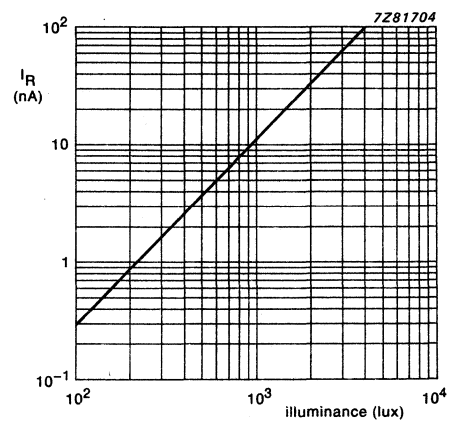


Fig. 5 Reverse current as a function of illuminance; V_R = 125 V; T_{amb} = 25 °C; typical values.

SILICON PLANAR EPITAXIAL ULTRA-HIGH SPEED DIODE

The BAS56 consists of two separate planar epitaxial ultra-high speed, high conductance diodes in one microminiature plastic envelope intended for surface mounting.

The device is primarily intended for core gating in very fast memories using the Surface Mounted Devices (SMD) technology.

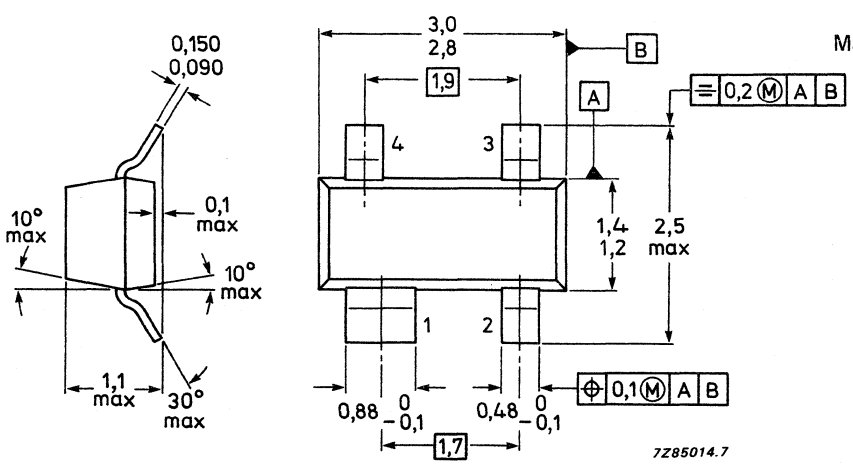
QUICK REFERENCE DATA

			single diode	series connection	
Continuous reverse voltage	V_R	max.	60	120	V
Repetitive peak reverse voltage	V_{RRM}	max.	60	120	V
Forward current	I_F	max.	200	150	mA
Repetitive peak forward current	I_{FRM}	max.	600	430	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300		mW
Reverse recovery time when switched from I_F = 400 mA to I_R = 400 mA; R_L = 100 Ω; measured at I_R = 40 mA	t_{rr}	<	6		ns

MECHANICAL DATA

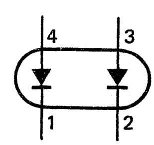
Dimensions in mm

Fig. 1 SOT-143.



TOP VIEW

Marking code: L51



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			single diode	series connection	
Continuous reverse voltage	V_R	max.	60	120	V
Repetitive peak reverse voltage*	V_{RRM}	max.	60	120	V
Forward current	I_F	max.	200	150	mA
Repetitive peak forward current	I_{FRM}	max.	600	430	mA
Non-repetitive peak forward current (per crystal)					
t = 1 µs	I_{FSM}	max.	2000		mA
t = 1 s	I_{FSM}	max.	500		mA
Total power dissipation**					
up to T_{amb} = 25 °C	P_{tot}	max.	300		mW
Storage temperature range	T_{stg}		−65 to +150		°C
Junction temperature	T_j	max.	150		°C

THERMAL RESISTANCE

From junction to ambient**	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS, per diode

T_j = 25 °C unless otherwise specified

Forward voltage				
I_F = 10 mA	V_F	<	0,75	V
I_F = 200 mA	V_F	<	1,00	V
I_F = 200 mA; T_j = 100 °C	V_F	<	0,95	V
I_F = 500 mA	V_F	<	1,25	V
Reverse current				
V_R = 60 V	I_R	<	100	nA
V_R = 60 V; T_j = 150 °C	I_R	<	100	µA
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	2,5	pF

* Measured at zero life time at I_R = 10 µA; V_R = 75 V.
** Mounted on a ceramic substrate of 10 mm x 8 mm x 0,6 mm.

Forward recovery voltage when switched to

I_F = 400 mA; t_r1 = 30 ns	V_{fr}	<	120	V
I_F = 400 mA; t_r2 = 100 ns		<	1,5	V

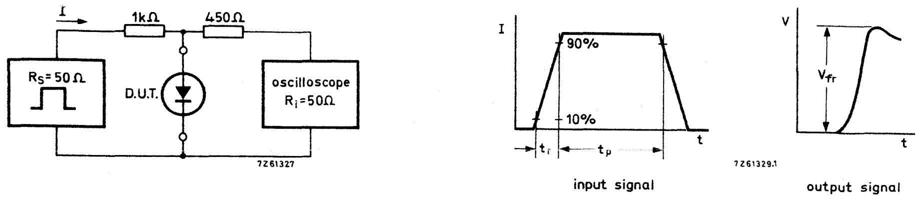


Fig. 2 Test circuit and waveforms; forward recovery voltage.

Input signal:	1st rise time of the forward pulse	t_r1	=	30	ns
	2nd rise time of the forward pulse	t_r2	=	100	ns
	Forward current pulse duration	t_p	=	300	ns
	Duty factor	δ	=	0,01	
Oscilloscope:	Rise time	t_r	=	0,35	ns
	Input capacitance	C_i	$\leqslant$	1	pF

Circuit capacitance C $\leqslant$ 20 pF (C = C_i + parasitic capacitance)

Reverse recovery time when switched
from I_F = 400 mA to I_R = 400 mA;
R_L = 100 Ω; measured at I_R = 40 mA $\quad t_{rr} \quad < \quad 6 \quad$ ns

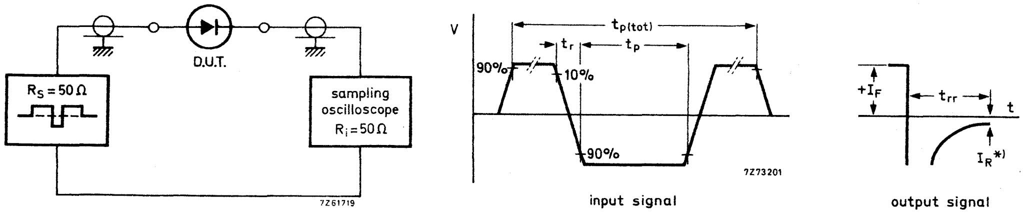


Fig. 3 Test circuits and waveforms; reverse recovery time. *I_R = 40 mA

Input signal:	Total pulse duration	$t_{p(tot)}$	=	0,2	μs
	Duty factor	δ	=	0,0025	
	Rise time of the reverse pulse	t_r	=	0,6	ns
	Reverse pulse duration	t_p	=	30	ns
Oscilloscope:	Rise time	t_r	=	0,35	ns

Circuit capacitance C $\leqslant$ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

Recovery charge when switched from $I_F = 10$ mA to $V_R = 5$ V; $R_L = 500\ \Omega$	Q_s	<	50	pC

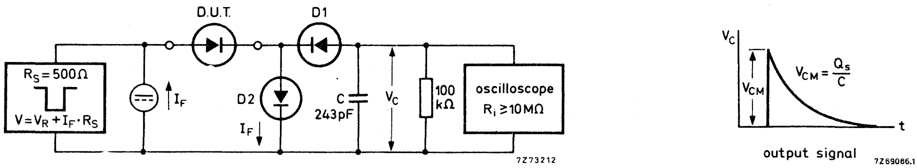


Fig. 4 Test circuit and waveform; recovery charge.

D1 = BAW62

D2 = diode with minority carrier life time at 10 mA		<	200	ps
Input signal: Rise time of the reverse pulse	t_r	=	2	ns
Reverse pulse duration	t_p	=	400	ns
Duty factor	δ	=	0,02	

Circuit capacitance $C \leqslant 7$ pF (C = oscilloscope input capacitance + parasitic capacitance)

SCHOTTKY BARRIER DIODE

Schottky Barrier diode with an integrated protection ring against extremely high static discharges.

This diode, in a SOD-80 envelope, is intended for applications where a very low forward voltage is required.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	30	V
Forward current (d.c.)	I_F	max.	200	mA
Peak forward current	I_{FM}	max.	300	mA
Junction temperature	T_j	max.	125	^oC
Forward voltage I_F = 10 mA	V_F	<	400	mV
Diode capacitance	C_d	<	10	pF

MECHANICAL DATA

Dimensions in mm

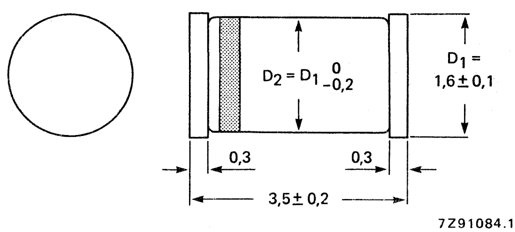


Fig. 1 SOD-80.

The cathode is indicated by a grey band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	30	V
Forward current				
d.c.	I_F	max.	200	mA
peak value	I_{FM}	max.	300	mA
peak value; $t_p < 1$ s		max.	600	mA
Average rectified forward current (see Fig. 2)	$I_{F(AV)}$	max.	200	mA
Storage temperature	T_{stg}	−65 to + 150		°C
Junction temperature	T_j	max.	125	°C

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Forward voltage*				
I_F = 0,1 mA	V_F	<	240	mV
I_F = 1 mA		<	320	mV
I_F = 10 mA	V_F	<	400	mV
I_F = 30 mA		<	500	mV
I_F = 100 mA	V_F	typ.	500	mV
		max.	800	mV
Reverse current				
V_R = 25 V	I_R	<	2,0	μA
Reverse breakdown voltage				
I_R = 10 μA	$V_{(BR)R}$	>	30	V
Diode capacitance				
V_R = 1 V; f = 1 MHz	C_d	<	10	pF
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 measured at I_R = 1 mA	t_{rr}	<	5,0	ns

* Temperature coefficient

I_F = 1 mA	S_F	typ.	−0,2	%/K
I_F = 15 mA		typ.	−0,04	%/K

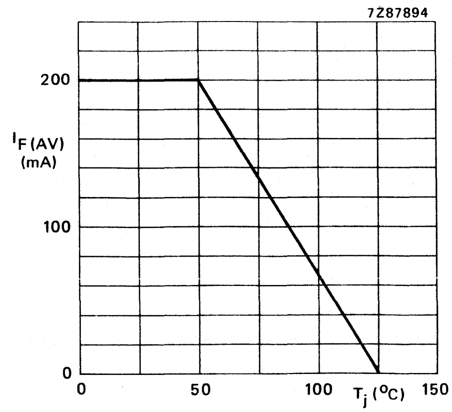


Fig. 2 Power derating curve; typical values.

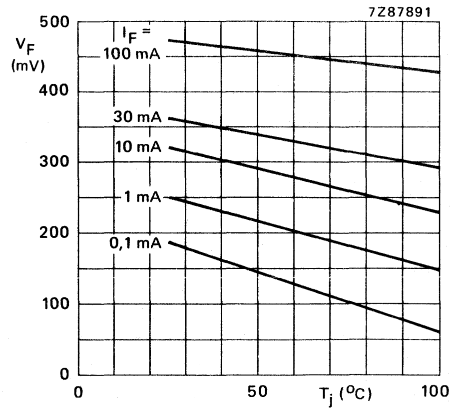


Fig. 3 Forward voltage as a function of temperature; typical values.

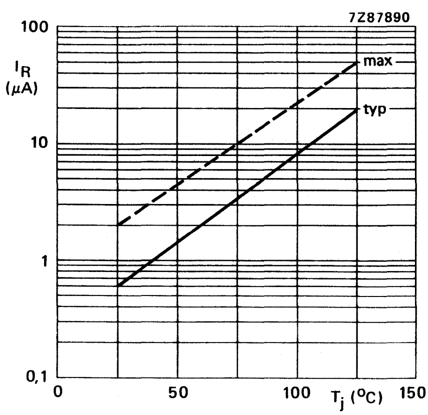


Fig. 4 Reverse current as a function of temperature; V_R = 25 V; typical values.

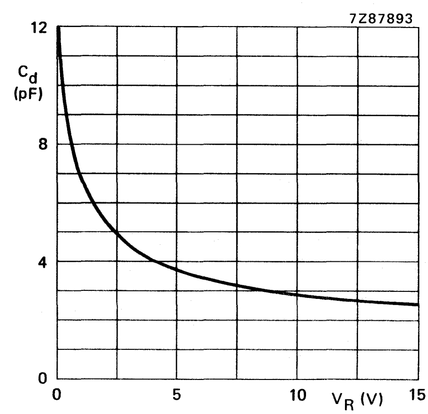


Fig. 5 Diode capacitance as a function of reverse voltage; f = 1 MHz; typical values.

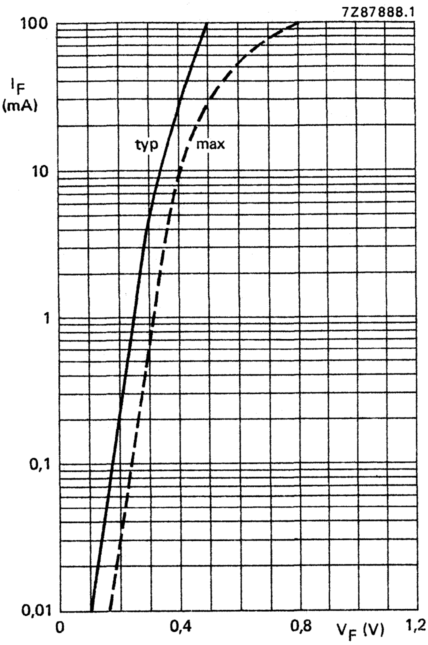


Fig. 6 Forward current as a function of forward voltage.

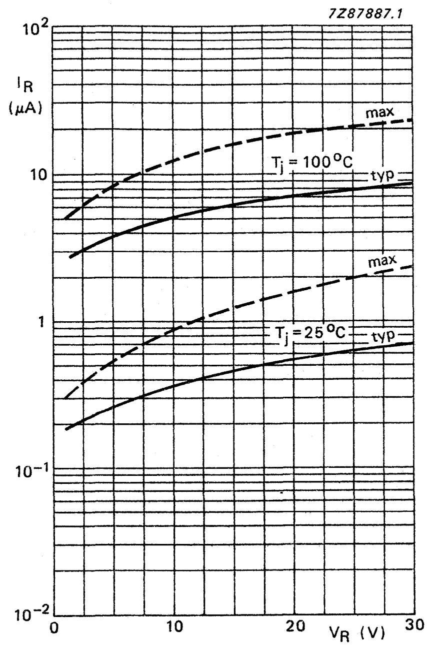


Fig. 7 Reverse current as a function of reverse voltage.

SCHOTTKY BARRIER DIODE

Silicon epitaxial diode in a microminiature plastic envelope. Intended for u.h.f. mixer and fast switching applications in thick and thin-film circuits.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	4	V
Forward current (d.c.)	I_F	max.	30	mA
Junction temperature	T_j	max.	100	°C
Forward voltage at I_F = 10 mA	V_F	<	600	mV
Diode capacitance at V_R = 0; f = 1 MHz	C_d	<	1,0	pF
Noise figure at f = 900 MHz	F	<	8,0	dB

MECHANICAL DATA

Dimensions in mm

Marking code

BAT17 = A3

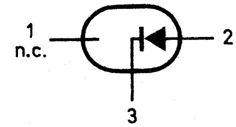
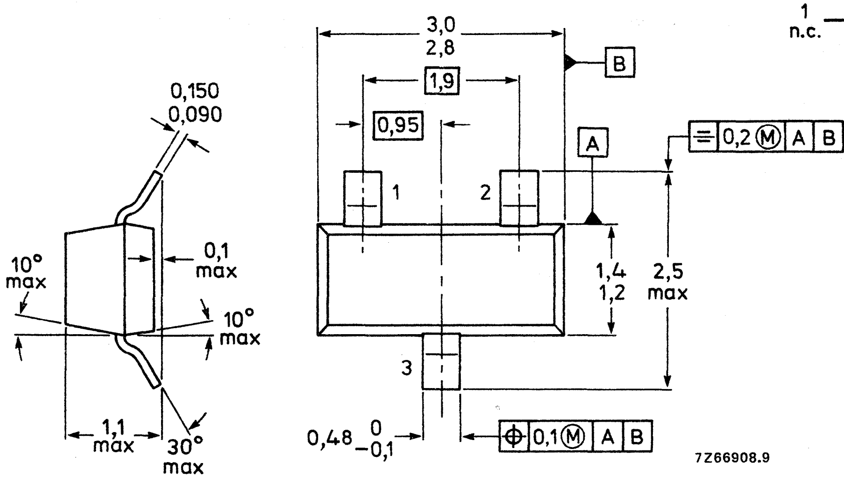


Fig.1 SOT-23.



TOP VIEW

See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	4	V
Forward current (d.c.)**	I_F	max.	30	mA
Storage temperature	T_{stg}	−65 to +100		°C
Junction temperature	T_j	max.	100	°C

THERMAL RESISTANCE*

From junction to ambient**	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Reverse current				
V_R = 3 V	I_R	<	0,25	μA
V_R = 3 V; T_{amb} = 60 °C	I_R	<	1,25	μA
Reverse breakdown voltage				
I_R = 10 μA	$V_{(BR)R}$	>	4	V
Forward voltage				
I_F = 0,1 mA	V_F	<	350	mV
I_F = 1,0 mA	V_F	<	450	mV
I_F = 10 mA	V_F	<	600	mV
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	1,0	pF
Noise figure at f = 900 MHz ▲	F	<	8,0	dB
Series resistance at f = 1 kHz				
I_F = 5 mA	r_D	<	15	Ω

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

▲ The local oscillator is adjusted for a diode current of 2 mA. I.F. amplifier noise F_{if} = 1,5 dB; f = 35 MHz.

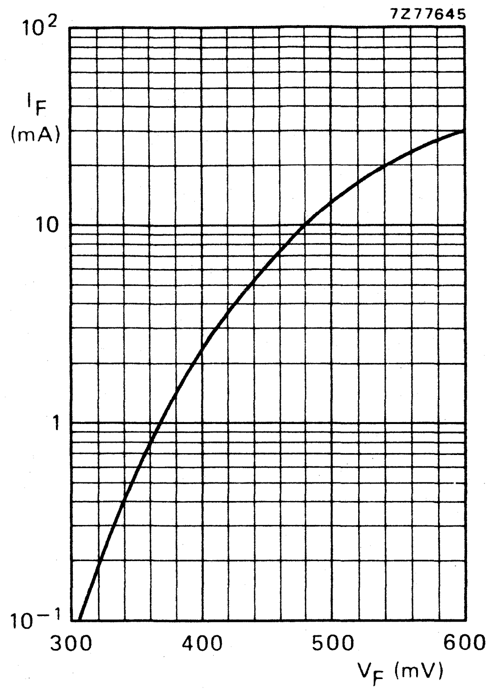


Fig. 2 Typical values.

SILICON PLANAR DIODE

Band switching diode in a microminiature plastic envelope. Intended for thick and thin-film circuits.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	35	V
Forward current (d.c.)	I_F	max.	100	mA
Junction temperature	T_j	max.	100	°C
Diode capacitance at f = 1 MHz V_R = 20 V	C_d	typ. <	0,8 1,0	pF pF
Series resistance at f = 200 MHz I_F = 5 mA	r_D	typ. <	0,5 0,7	Ω Ω

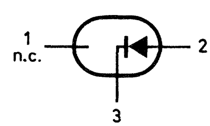
MECHANICAL DATA

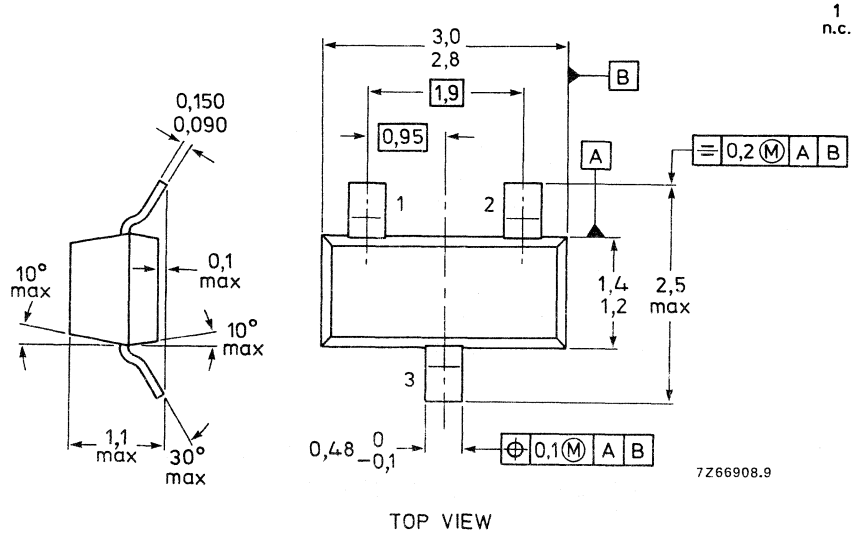
Dimensions in mm

Fig. 1 SOT-23.

Marking code

BAT18 = A2





RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	35	V
Forward current (d.c.)	I_F	max.	100	mA
Storage temperature	T_{stg}	−55 to + 125		°C
Junction temperature	T_j	max.	125	°C

THERMAL RESISTANCE*

From junction to ambient**	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

$T_j = 25\ ^oC$ unless otherwise specified

Forward voltage at $I_F = 100$ mA	V_F	<	1,2	V
Reverse current				
$V_R = 20$ V	I_R	<	100	nA
$V_R = 20$ V; $T_j = 60\ ^oC$	I_R	<	1	μA
Diode capacitance at f = 1 MHz				
$V_R = 20$ V	C_d	typ.	0,8	pF
		<	1,0	pF
Series resistance at f = 200 MHz				
$I_F = 5$ mA	r_D	typ.	0,5	Ω
		<	0,7	Ω

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

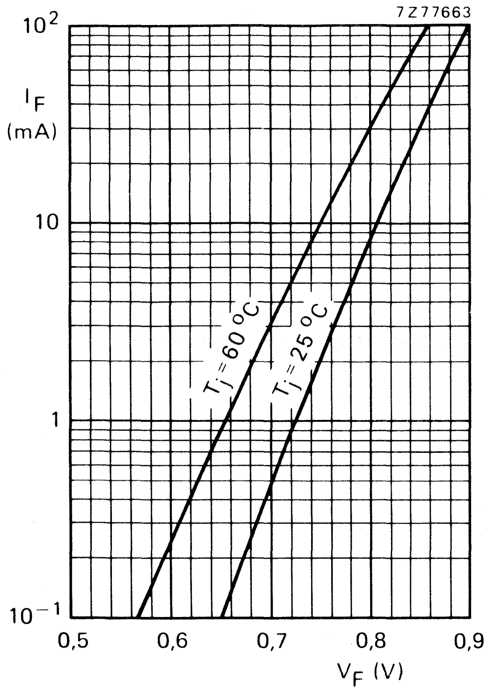


Fig. 2 Typical values.

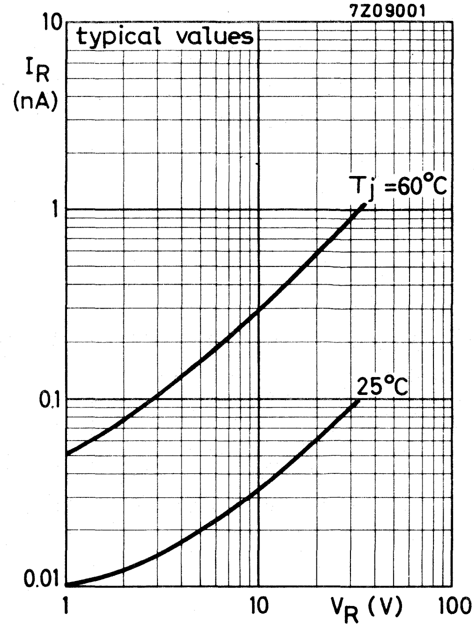


Fig. 3.

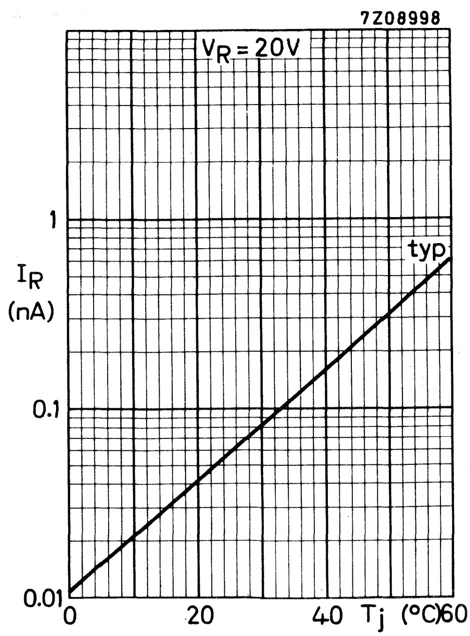


Fig. 4.

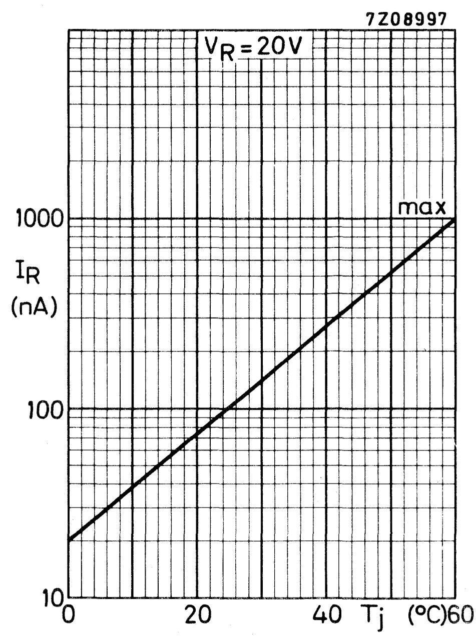


Fig. 5.

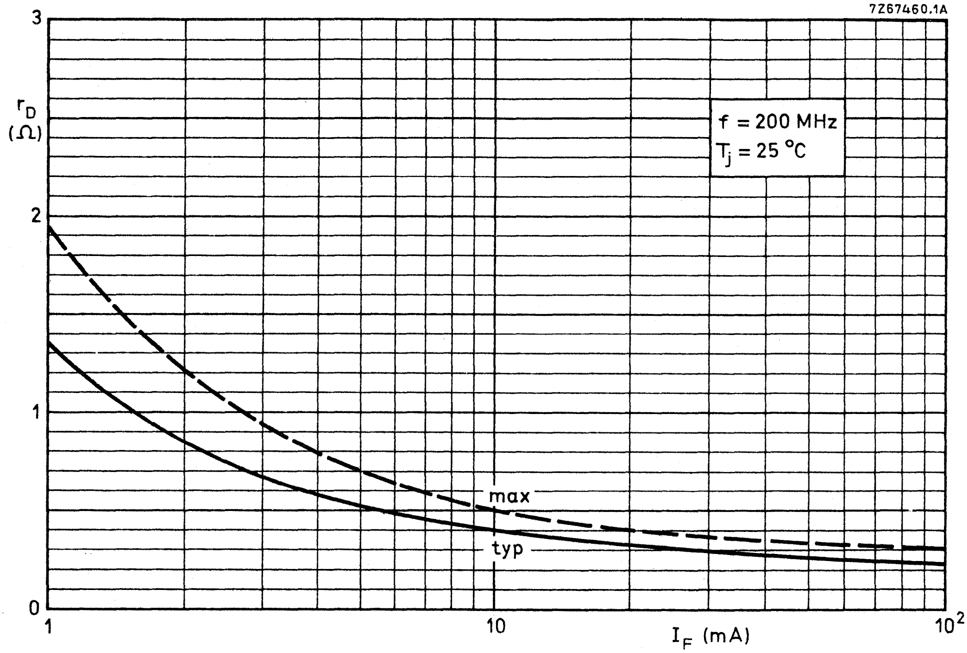


Fig. 6.

SCHOTTKY BARRIER DIODE

Silicon epitaxial Schottky barrier diode with an integrated p-n junction protection ring in a micro-miniature SOT-23 envelope intended for surface mounting.

The diode features especially a low forward voltage.

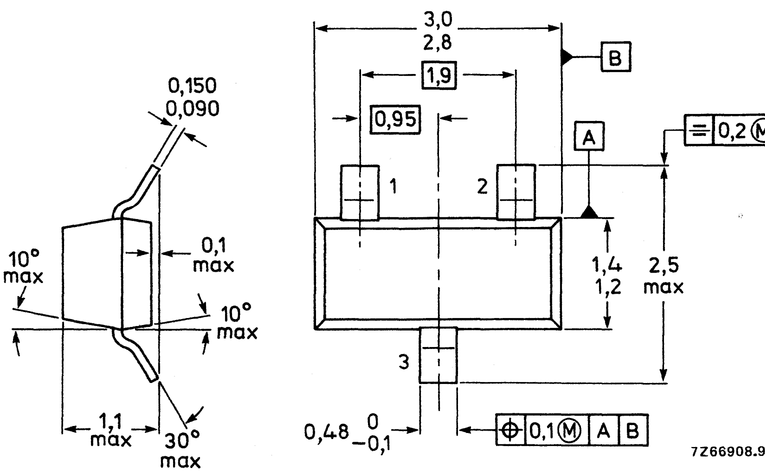
QUICK REFERENCE DATA

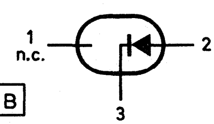
Continuous reverse voltage	V_R	max.	30	V
Forward current (d.c.)	I_F	max.	200	mA
Forward voltage at I_F = 10 mA	V_F	max.	400	mV
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	230	mW
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	⩽	5	ns
Junction temperature	T_j	max.	125	°C

Fig. 1 SOT-23

Dimensions in mm

Marking code: L4





TOP VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	30	V
Forward current (d.c.) see Fig. 2	I_F	max.	200	mA
Repetitive peak forward current	I_{FRM}	max.	300	mA
Non-repetitive peak forward current $t < 1$ s	I_{FSM}	max.	600	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	230	mW
Storage temperature	T_{stg}		−55 to +150	°C
Junction temperature	T_j	max.	125	°C

THERMAL RESISTANCE

From junction to ambient mounted on a ceramic substrate of 10 mm x 8 mm x 0,6 mm	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Forward voltage				
I_F = 0,1 mA	V_F	⩽	240	mV
I_F = 1 mA*	V_F	⩽	320	mV
I_F = 10 mA	V_F	⩽	400	mV
I_F = 30 mA*	V_F	⩽	500	mV
I_F = 100 mA	V_F	=	500	mV
	V_F	<	1000	mV
Reverse current V_R = 25 V	I_R	⩽	2	μA
Reverse breakdown voltage	$V_{(BR)R}$	>	30	V
Diode capacitance V_R = 1 V; f = 1 MHz	C_d	⩽	10	pF
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	⩽	5	ns

* Temperature coefficient of forward voltage:
−0,6 %/K at I_F = 1 mA
−0,3 %/K at I_F = 30 mA

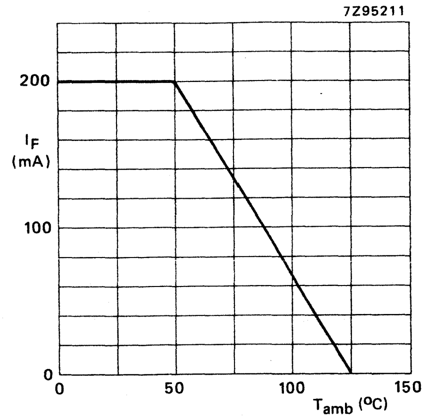


Fig. 2 Derating curve maximum ambient temperature.

DEVELOPMENT DATA

SCOTTKY BARRIER DIODE

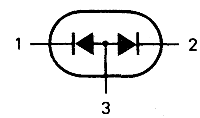
Silicon epitaxial Schottky Barrier double diodes with an integrated p-n junction protection ring in a microminiature SOT-23 envelope intended for surface mounting.

The diodes feature an especially low forward voltage.

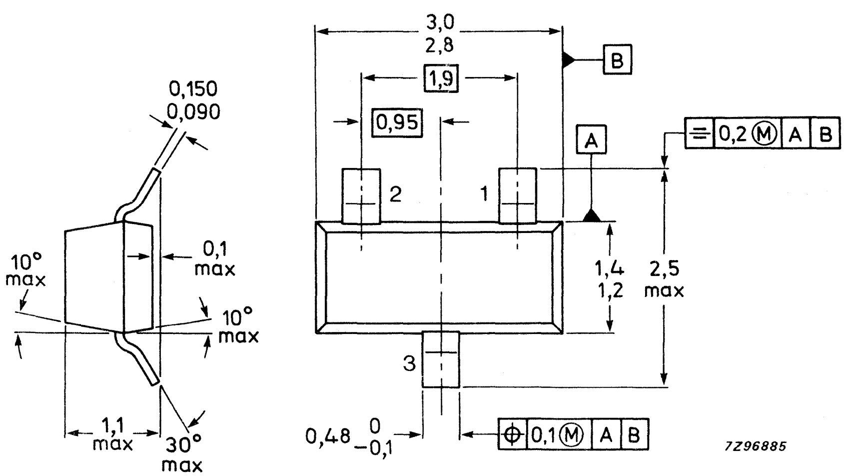
QUICK REFERENCE DATA

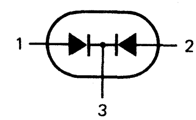
Continuous reverse voltage	V_R	max.	30	V
Forward current (DC)	I_F	max.	200	mA
Forward voltage at I_F = 10 mA	V_F	max.	400	mV
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100; measured at I_R = 1 mA	t_{rr}	<	5	ns
Junction temperature	T_j	max.	125	°C

Dimensions in mm

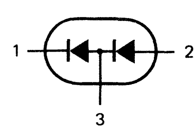


BAT54A





BAT54C



BAT54S

TOP VIEW

Fig. 1 SOT-23.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Repetitive peak reverse voltage	V_{RRM}	max.	30 V
Forward current (DC)	I_F	max.	200 mA
Repetitive peak forward current	I_{FRM}	max.	300 mA
Non-repetitive peak forward current $t < 1$ s	I_{FSM}	max.	600 mA
Storage temperature	T_{stg}	−50 to + 150	°C
Junction temperature	T_j	max.	125 °C

THERMAL RESISTANCE

From junction to ambient; mounted on a ceramic substrate of 10 mm x 8 mm x 0,6 mm	$R_{th\ j\text{-}a}$	=	430 K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Forward voltage			
I_F = 0,1 mA	V_F	max.	240 mV
I_F = 1 mA	V_F	max.	320 mV
I_F = 10 mA	V_F	max.	400 mV
I_F = 30 mA	V_F	max.	500 mV
I_F = 100 mA	V_F	typ.	500 mV
		max.	1000 mV
Reverse current V_R = 25 V	I_R	<	2 μA
Reverse breakdown voltage	$V_{(BR)R}$	>	30 V
Diode capacitance V_R = 1 V; f = 1 MHz	C_d	<	10 pF
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100; measured at I_R = 1 mA	t_{rr}	<	5 ns

SCHOTTKY BARRIER DIODE

Two separate silicon epitaxial Schottky barrier diodes with an integrated p-n junction protection ring in one microminiature SOT-143 envelope, intended for surface mounting (SMD technology).

The device features a low forward voltage drop.

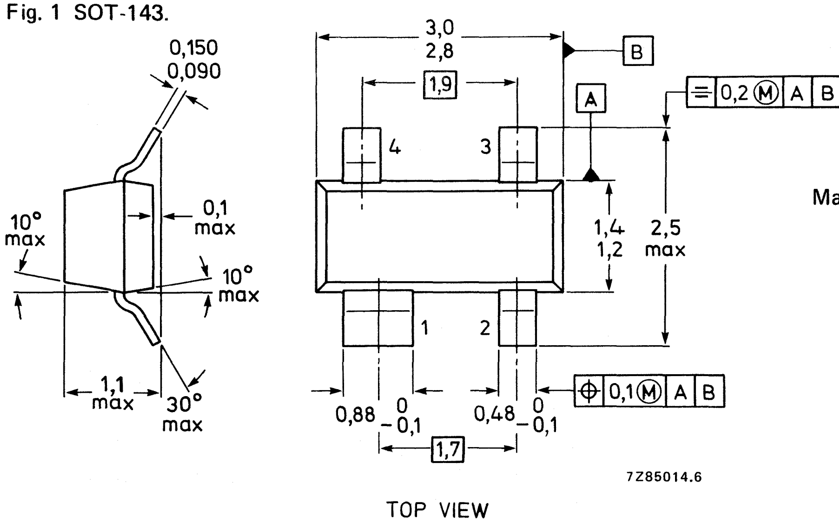
QUICK REFERENCE DATA

			single diode	double-diode operation	
Continuous reverse voltage	V_R	max.	30	30	V
Continuous reverse voltage series connection	V_R	max.	–	60	V
Forward current	I_F	max.	200	110	mA
Repetitive peak forward current	I_{FRM}	max.	300	200	mA
Non-repetitive peak forward current	I_{FSM}	max.	600		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	230		mW
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	≤	5		ns

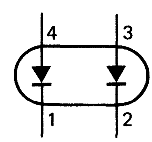
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-143.



Marking code : L41



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			single diode	double-diode operation
Continuous reverse voltage	V_R	max.	30	30 V
Continuous reverse voltage series connection	V_R	max.	–	60 V
Forward current (see Fig. 2)	I_F	max.	200	110* mA
Repetitive peak forward current	I_{FRM}	max.	300	200 mA
Non-repetitive peak forward current $t < 1$ s	I_{FSM}	max.	600	mA
Total power dissipation up to $T_{amb} = 25$ °C	P_{tot}	max.	230	mW
Storage temperature	T_{stg}		−65 to + 150	°C
Junction temperature	T_j	max.	125	°C

THERMAL RESISTANCE

From junction to ambient mounted on a ceramic substrate of 10 mm x 8 mm x 0,6 mm	$R_{th\ j\text{-}a}$	430	K/W

CHARACTERISTICS, per diode

$T_{amb} = 25$ °C unless otherwise specified

Forward voltage				
$I_F = 0{,}1$ mA	V_F	⩽	240	mV
$I_F = 1$ mA**		⩽	320	mV
$I_F = 10$ mA	V_F	⩽	400	mV
$I_F = 30$ mA**		⩽	500	mV
$I_F = 100$ mA	V_F	=	500	mV
		<	1000	mV
Reverse current $V_R = 25$ V	I_R	⩽	2	µA
Reverse breakdown voltage	$V_{(BR)R}$	>	30	V
Diode capacitance $V_R = 1$ V; f = 1 MHz	C_d	⩽	10	pF
Reverse recovery time when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100\ \Omega$; measured at $I_R = 1$ mA	t_{rr}	⩽	5	ns

* If both diodes are in forward operation at the same moment, total device current max. 110 mA. If one diode is in reverse and the other in forward operation at the same moment, total device current max. 200 mA.

** Temperature coefficient of forward voltage: −0,6%/K at $I_F = 1$ mA.

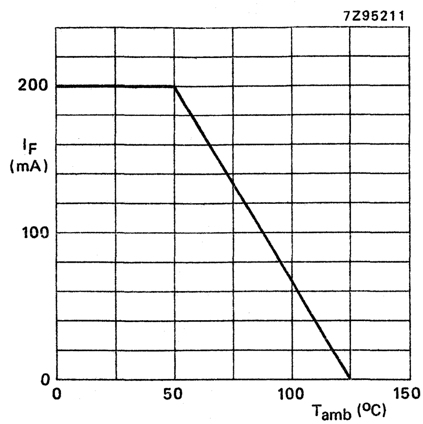


Fig. 2 Derating curve maximum ambient temperature.

DEVELOPMENT DATA

SCHOTTKY BARRIER DIODES

General purpose and switching Schottky barrier diodes in a SOD-68 envelope, with an integrated protection ring against extremely high static discharges. They feature a low forward voltage drop, low leakage current and a low capacitance and as such can be used in very fast switching applications.

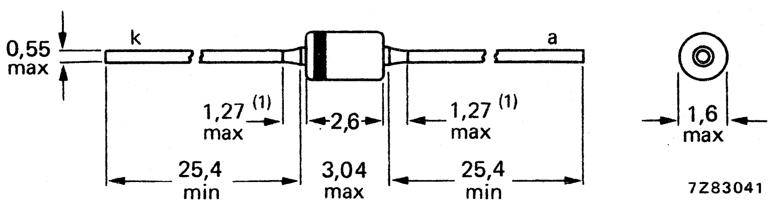
QUICK REFERENCE DATA

			BAT81	82	82	
Continuous reverse voltage	V_R	max.	40	50	60	V
Forward current (d.c.)	I_F	max.		30		mA
Junction temperature	T_j	max.		200		°C
Forward voltage I_F = 1 mA	V_F	<		410		mV
Reverse current at V_R = 30 V	I_R	<		200		nA
Diode capacitance	C_d	<		1,6		pF

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-68 (DO-34).



(1) Lead diameter in this zone uncontrolled band.

The cathode is indicated by a coloured band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BAT81	82	83	
Continuous reverse voltage	V_R	max.	40	50	60	V
Forward current						
d.c.	I_F	max		30		mA
peak value; $t_p < 1$ s	I_{FM}	max.		150		mA
Storage temperature	T_{stg}			−65 to +200		^oC
Junction temperature (see Fig. 2)	T_j	max.		200		^oC

THERMAL RESISTANCE

THERMAL RESISTANCE	$R_{th\ j\text{-}a}$	max.	320	K/W

CHARACTERISTICS

T_{amb} = 25 ^oC unless otherwise specified

			BAT81	82	83	
Reverse breakdown voltage						
$I_R = 10\ \mu A$	$V_{(BR)R}$	>	40	50	60	V
Forward voltage						
I_F = 0,1 mA	V_F	<		330		mV
I_F = 1 mA	V_F	<		410		mV
I_F = 15 mA	V_F	<		1		V
Temperature coefficient						
I_F = 1 mA	S_F	=		0,2		%/K
I_F = 10 mA	S_F	=		0,04		%/K
Reverse current						
V_R = 30 V	I_R	<		200		nA
Diode capacitance						
V_R = 1 V; f = 1 MHz	C_d	<		1,6		pF
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<		1		ns*

* Due to lack of minority carrier injection reverse recovery time only depends on junction capacitance and circuit resistance.

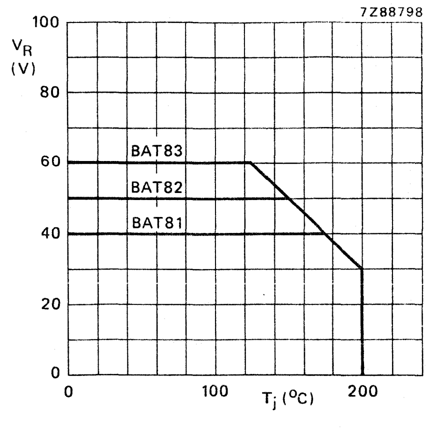


Fig. 2 Derating curve maximum junction temperature.

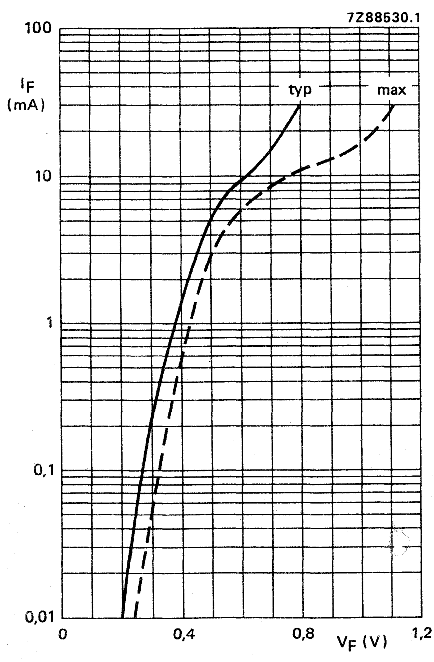


Fig. 3 Forward current versus forward voltage; typ.values.

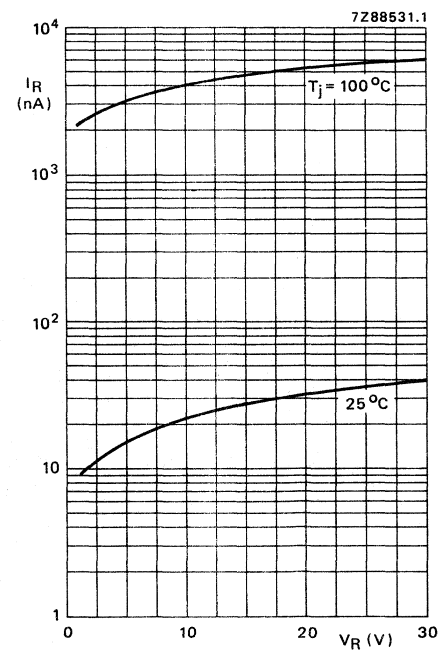


Fig. 4 Reverse current versus reverse voltage; typ. values.

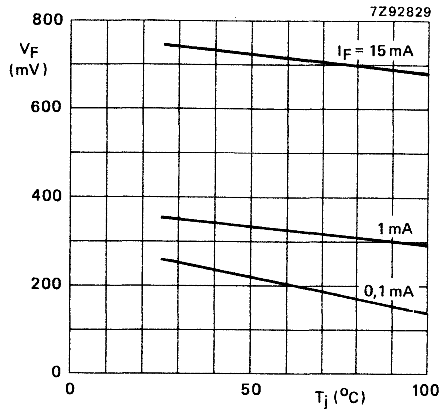


Fig. 5 Forward voltage versus junction temperature; typ. values.

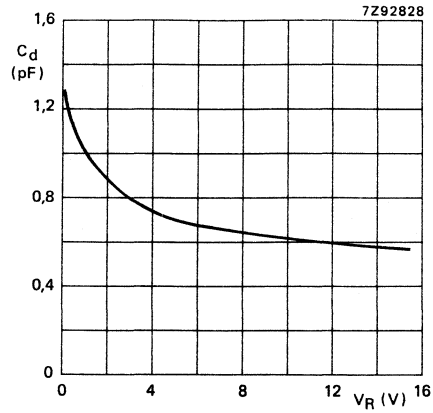


Fig. 6 Diode capacitance versus reverse voltage; f = 1 MHz; typical values.

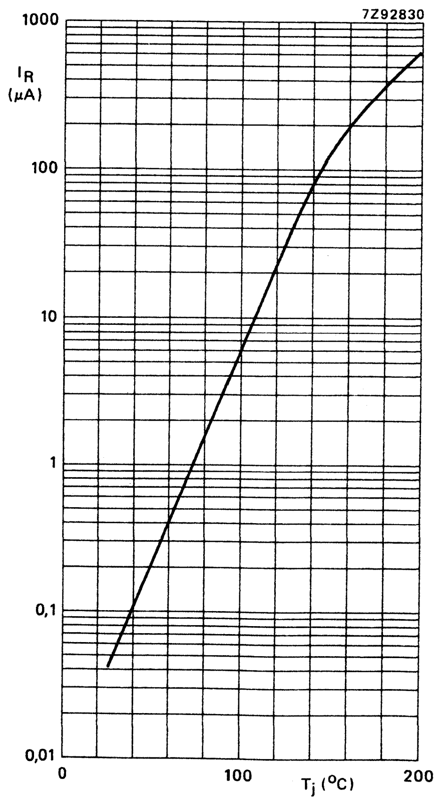


Fig. 7 Reverse current versus junction temperature; V_R = 30 V; typical values.

SCHOTTKY BARRIER DIODE

Schottky barrier diode with an integrated protection ring against extremely high static discharges.
This diode, in a DO-34 envelope, is intended for applications where a very low forward voltage is required.

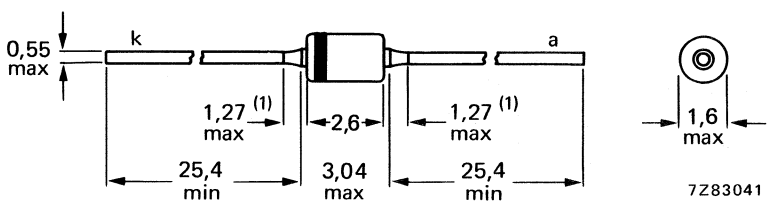
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	30	V
Forward current (d.c.)	I_F	max.	200	mA
Peak forward current	I_{FM}	max.	300	mA
Junction temperature	T_j	max.	125	^oC
Forward voltage I_F = 10 mA	V_F	<	400	mV
Diode capacitance	C_d	<	10	pF

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-68 (DO-34).



(1) Lead diameter in this zone uncontrolled.
The cathode is indicated by a grey and a green band on a beige-coloured body.

Products, approved to CECC 50 001.059, available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	30	V
Forward current				
d.c.	I_F	max.	200	mA
peak value	I_{FM}	max.	300	mA
peak value; $t_p < 1$ s	I_{FM}	max.	600	mA
Average rectified forward current (see Fig. 2)	$I_{F(AV)}$	max.	200	mA
Storage temperature	T_{stg}		−65 to +150	°C
Junction temperature	T_j	max.	125	°C

THERMAL RESISTANCE

From junction to ambient when mounted on a printed circuit board at a lead length of 4 mm	$R_{th\ j\text{-}a}$	max.	320	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Forward voltage*				
I_F = 0,1 mA	V_F	<	240	mV
I_F = 1 mA	V_F	<	320	mV
I_F = 10 mA	V_F	<	400	mV
I_F = 30 mA	V_F	<	500	mV
I_F = 100 mA	V_F	typ.	500	mV
		max.	800	mV
Reverse current V_R = 25 V	I_R	<	2	µA
Reverse breakdown voltage I_R = 10 µA	$V_{(BR)R}$	>	30	V
Diode capacitance V_R = 1 V; f = 1 MHz	C_d	<	10	pF
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	5	ns

* Temperature coefficient

I_F = 1 mA	S_F	typ.	−0,2	%/K
I_F = 15 mA	S_F	typ.	−0,04	%/K

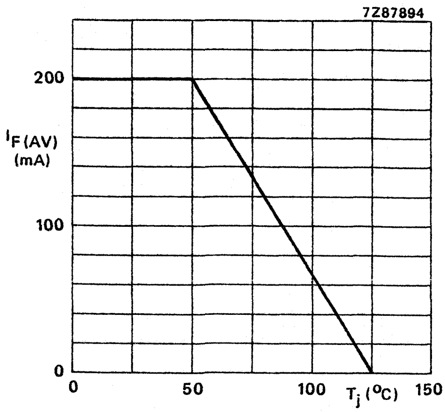


Fig. 2 Derating curve.

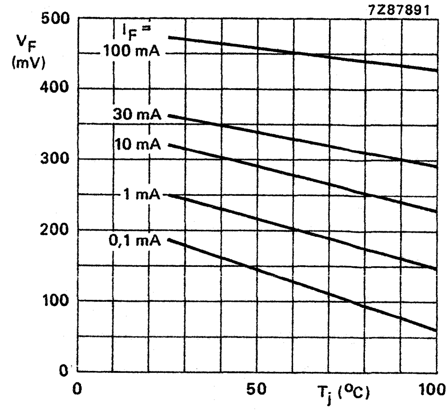


Fig. 3 Typical values.

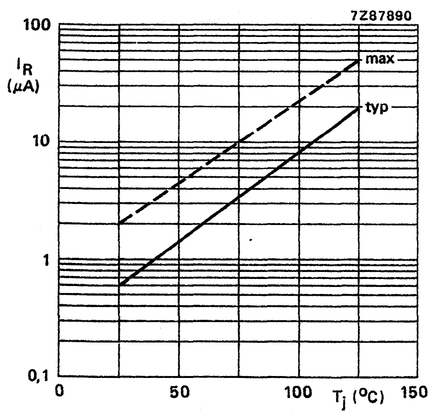


Fig. 4 V_R = 25 V; typ. values.

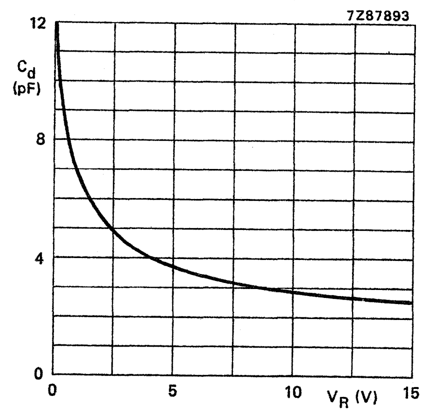


Fig. 5 f = 1 MHz; typ. values.

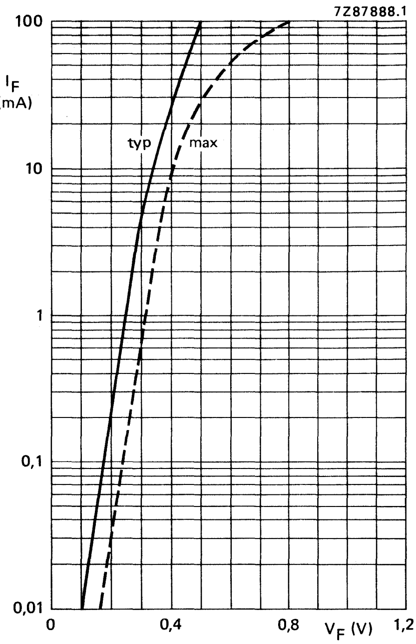


Fig. 6 ——— Typical values
– – – Maximum values.

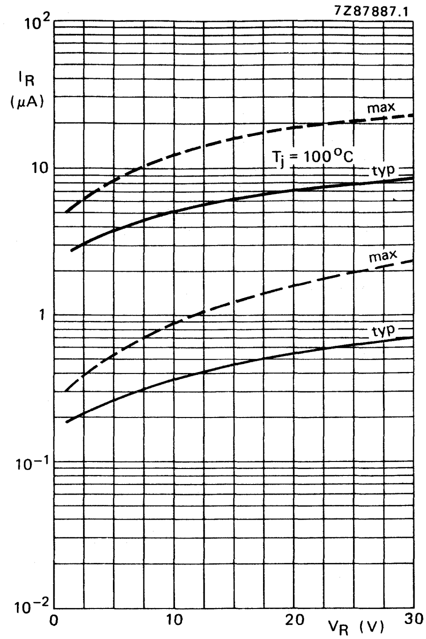


Fig. 7 ——— Typical values
– – – Maximum values.

SCHOTTKY BARRIER DIODE

Schottky barrier diode with an integrated protection ring against extremely high static discharges. The small DO-34 envelope can actually be mounted on a 2E pitch.

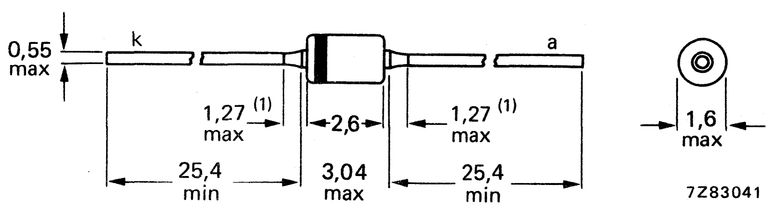
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	50	V
Forward current (d.c.)	I_F	max.	200	mA
Peak forward current	I_{FM}	max.	250	mA
Junction temperature	T_j	max.	125	°C
Forward voltage $I_F = 10$ mA	V_F	<	450	mV
Diode capacitance	C_d	<	8	pF

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-68 (DO-34).



(1) Lead diameter in this zone uncontrolled.
The cathode is indicated by a grey and a blue band on a beige-coloured body.

Products, approved to CECC 50 001-059, available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	50	V
Forward current				
d.c.	I_F	max.	200	mA
peak value	I_{FM}	max.	250	mA
peak value; $t_p < 1$ s	I_{FM}	max.	500	mA
Average rectified forward current (see Fig. 2)	$I_{F(AV)}$	max.	200	mA
Storage temperature	T_{stg}		−65 to +150	°C
Junction temperature	T_j	max.	125	°C

THERMAL RESISTANCE

From junction to ambient when mounted on a printed circuit board at a lead length of 4 mm	$R_{th\ j\text{-}a}$	max.	320	K/W

CHARACTERISTICS

$T_{amb} = 25\ ^{o}C$ unless otherwise specified

Forward voltage*				
$I_F = 0,1$ mA	V_F	<	300	mV
$I_F = 1$ mA	V_F	<	380	mV
$I_F = 10$ mA	V_F	<	450	mV
$I_F = 30$ mA	V_F	<	600	mV
$I_F = 100$ mA	V_F	typ.	600	mV
		max.	900	mV
Reverse current				
$V_R = 40$ V	I_R	<	5	µA
Reverse breakdown voltage				
$I_R = 10\ \mu A$	$V_{(BR)R}$	>	50	V
Diode capacitance				
$V_R = 1$ V; f = 1 MHz	C_d	<	8	pF
Reverse recovery time when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100\ \Omega$; measured at $I_R = 1$ mA	t_{rr}	<	4	ns

* Temperature coefficient

$I_F = 1$ mA	S_F	typ.	−0,2	%/K
$I_F = 15$ mA	S_F	typ.	−0,04	%/K

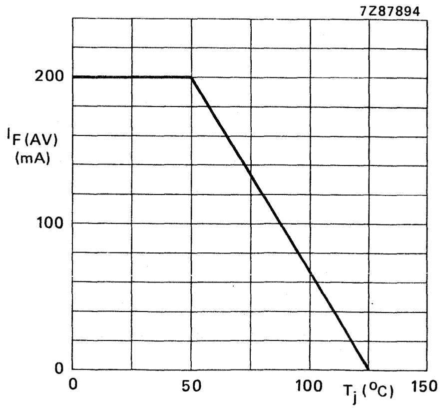


Fig. 2 Derating curve.

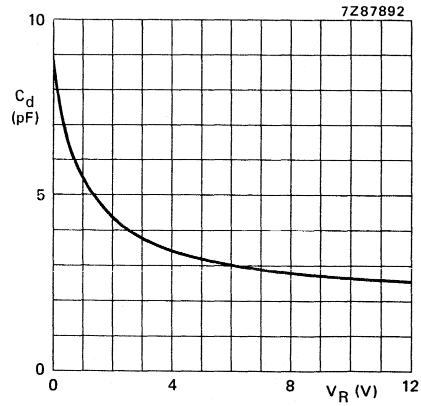


Fig. 3 f = 1 MHz; typ. values.

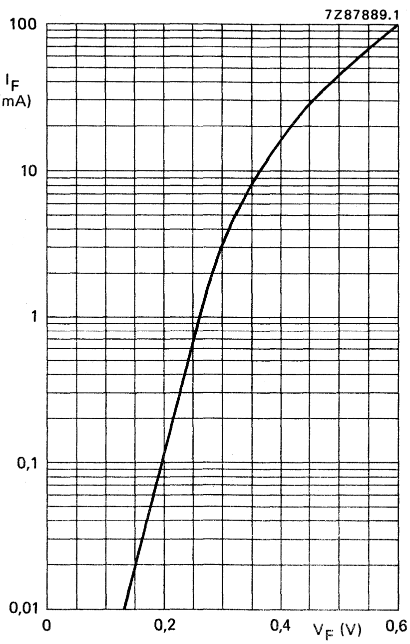


Fig. 4 Typical values.

ULTRA-HIGH-SPEED DIODES

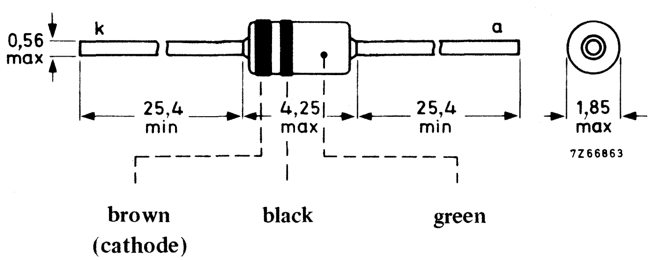
Silicon planar epitaxial, ultra-high-speed, high-conductance diode in a DO-35 envelope.
The BAV10 is primarily intended for core gating in very fast memories.

QUICK REFERENCE DATA				
Continuous reverse voltage	V_R	max.	60	V
Repetitive peak reverse voltage	V_{RRM}	max.	60	V
Repetitive peak forward current	I_{FRM}	max.	600	mA
Junction temperature	T_j	max.	200	^oC
Forward voltage at I_F = 200 mA	V_F	<	1,0	V
Reverse recovery time when switched from I_F = 400 mA to I_R = 400 mA; R_L = 100 Ω; measured at I_R = 40 mA	t_{rr}	<	6	ns
Recovery charge when switched from I_F = 10 mA to V_R = 5 V; R_L = 500 Ω	Q_s	<	50	pC

MECHANICAL DATA

Dimensions in mm

Fig. 1 DO-35.



RATINGS Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	60	V	
Repetitive peak reverse voltage	V_{RRM}	max.	60	V	1)
Average rectified forward current	$I_{F(AV)}$	max.	300	mA	2)
Forward current (d.c.)	I_F	max.	300	mA	
Repetitive peak forward current	I_{FRM}	max.	600	mA	
Non-repetitive peak forward current t = 1 μs	I_{FSM}	max.	4000	mA	
t = 1 s	I_{FSM}	max.	1000	mA	
Storage temperature	T_{stg}		−65 to +200	°C	
Junction temperature	T_j	max.	200	°C	

THERMAL RESISTANCE

From junction to ambient in free air at maximum lead length	$R_{th\ j-a}$	=	0,5	K/mW

CHARACTERISTICS T_j = 25 °C unless otherwise specified

Forward voltage				
I_F = 10 mA	V_F	<	0,75	V
I_F = 200 mA	V_F	<	1,00	V
I_F = 200 mA; T_j = 100 °C	V_F	<	0,95	V
I_F = 500 mA	V_F	<	1,25	V
Reverse current				
V_R = 60 V	I_R	<	100	nA
V_R = 60 V; T_j = 150 °C	I_R	<	100	μA
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	2,5	pF

1) Measured at zero life time at I_R = 10 μA; V_R = 75 V.

2) For pulse operation see Figs 6 and 7. For sinusoidal operation see Figs 8 to 11.

CHARACTERISTICS (continued) $T_j = 25\ ^oC$

Forward recovery voltage when switched to

I_F = 400 mA; t_{r1} = 30 ns	V_{fr}	<	2,0	V
I_F = 400 mA; t_{r2} = 100 ns	V_{fr}	<	1,5	V

Test circuit and waveforms:

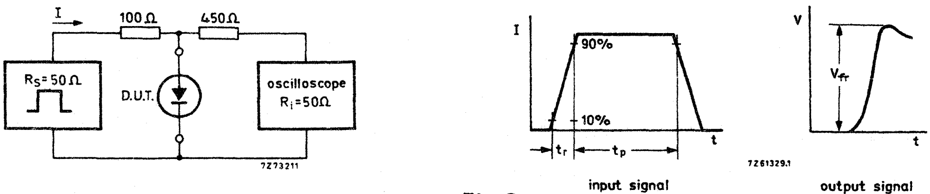


Fig. 2.

Input signal : 1st rise time of the forward pulse t_{r1} = 30 ns

2nd rise time of the forward pulse t_{r2} = 100 ns

Forward current pulse duration t_p = 300 ns

Duty factor δ = 0,01

Oscilloscope: Rise time t_r = 0,35 ns

Input capacitance C_i ≤ 1 pF

Circuit capacitance C ≤ 20 pF (C = C_i + parasitic capacitance)

Reverse recovery time when switched from

I_F = 400 mA to I_R = 400 mA; R_L = 100 Ω;
measured at I_R = 40 mA t_{rr} < 6 ns

Test circuit and waveforms:

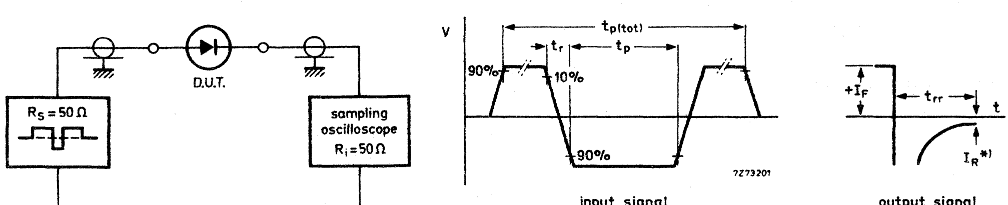


Fig. 3.

Input signal : Total pulse duration $t_{p(tot)}$ = 0,2 μs *) I_R = 40 mA

Duty factor δ = 0,0025

Rise time of the reverse pulse t_r = 0,6 ns

Reverse pulse duration t_p = 30 ns

Oscilloscope: Rise time t_r = 0,35 ns

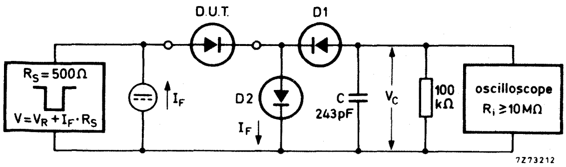
Circuit capacitance C ≤ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

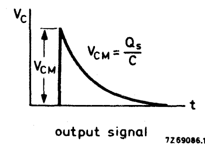
CHARACTERISTICS (continued) T_j = 25 °C

Recovery charge when switched from

I_F = 10 mA to V_R = 5 V; R_L = 500 Ω | Q_s < 50 pC

Test circuit and waveform:





D1 = BAW62 Fig. 4.

D2 = diode with minority carrier life time at 10 mA: < 200 ps

Input signal	: Rise time of the reverse pulse	t_r	=	2 ns
	Reverse pulse duration	t_p	=	400 ns
	Duty factor	δ	=	0,02

Circuit capacitance C ≤ 7 pF (C = oscilloscope input capacitance + parasitic capacitance)

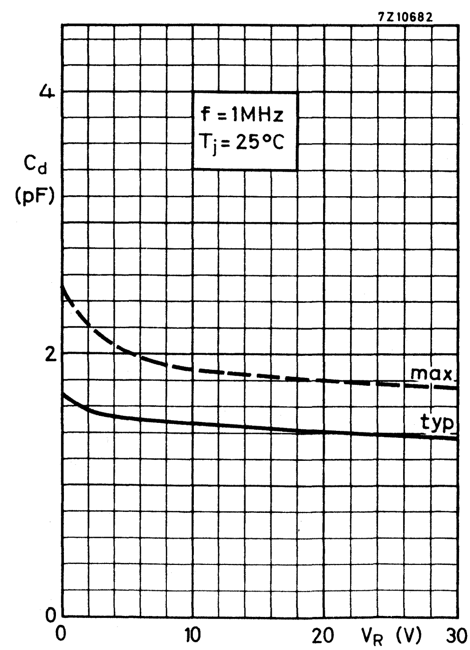


Fig. 5.

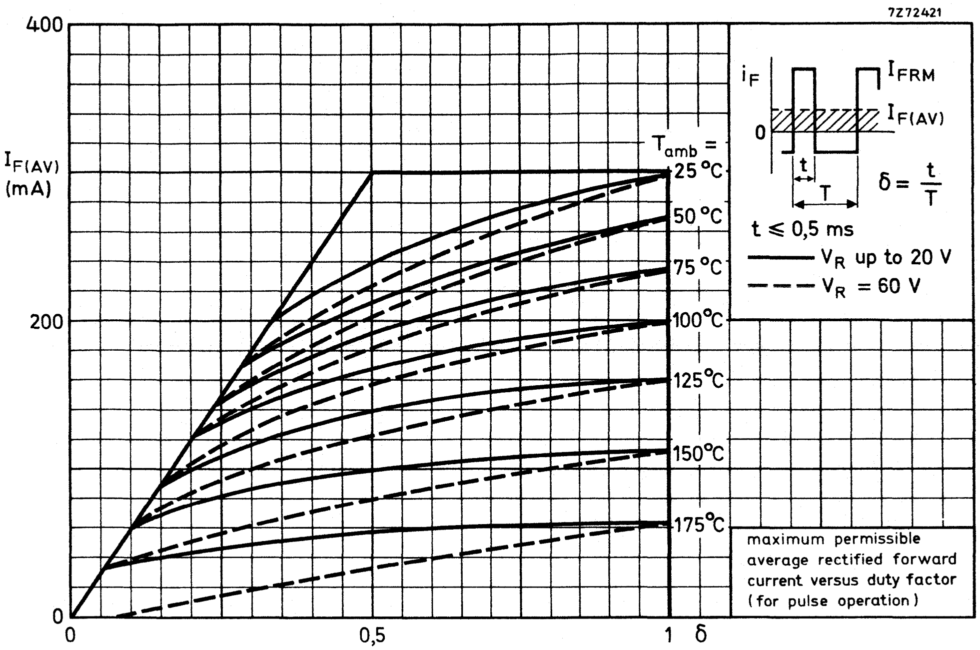

7Z72421
400
200
0
$I_{F(AV)}$ (mA)
0
0,5
1 δ
T_{amb} =
25 °C
50 °C
75 °C
100°C
125°C
150°C
175°C
i_F
I_{FRM}
$I_{F(AV)}$
0
t
T
δ = t/T
t ≤ 0,5 ms
V_R up to 20 V
V_R = 60 V
maximum permissible average rectified forward current versus duty factor (for pulse operation)

Fig. 6.

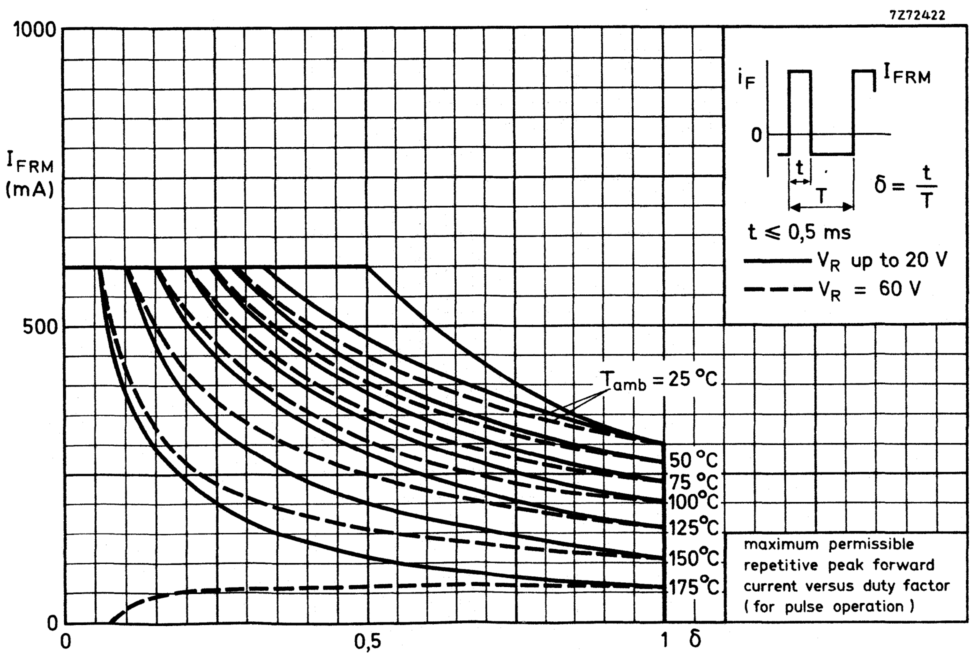

7Z72422
1000
500
0
I_{FRM} (mA)
0
0,5
1 δ
T_{amb} = 25 °C
50 °C
75 °C
100°C
125°C
150°C
175°C
i_F
I_{FRM}
0
t
T
δ = t/T
t ≤ 0,5 ms
V_R up to 20 V
V_R = 60 V
maximum permissible repetitive peak forward current versus duty factor (for pulse operation)

Fig. 7.

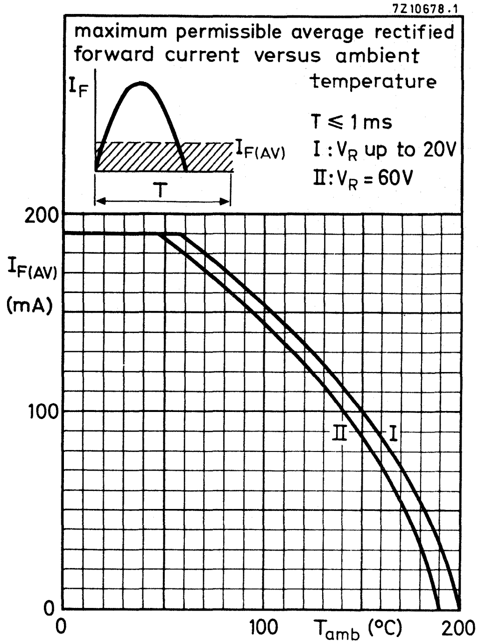


Fig. 8.

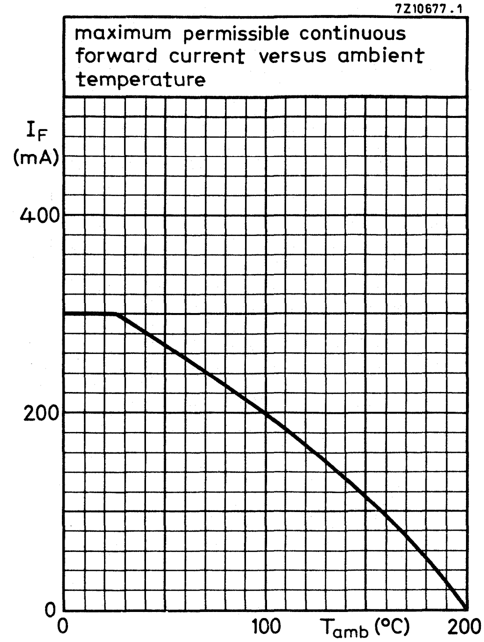


Fig. 9.

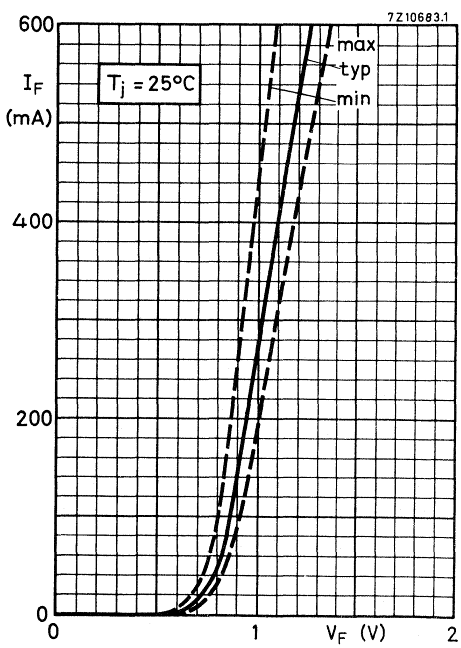


Fig. 10.

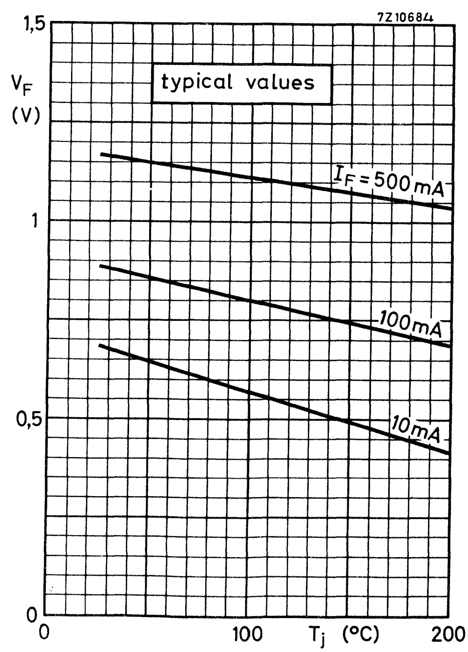


Fig. 11.

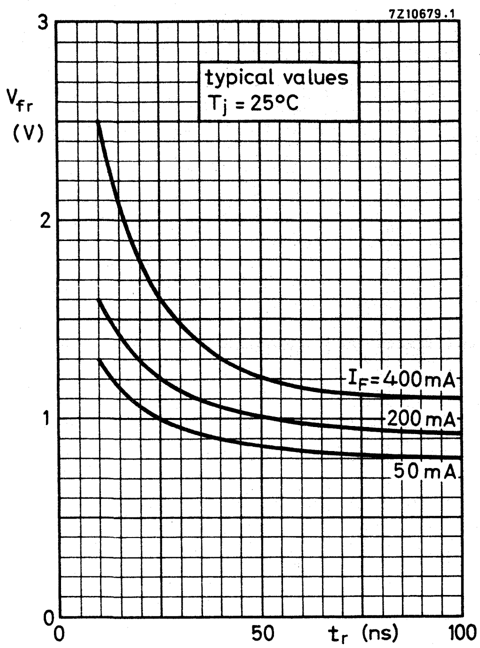


Fig. 12.

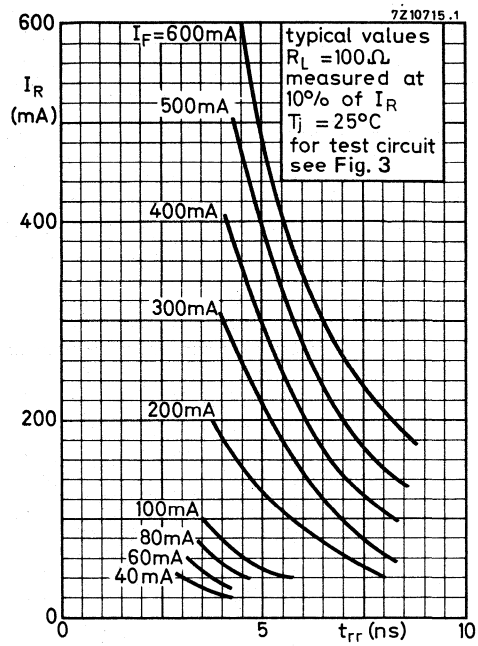


Fig. 13.

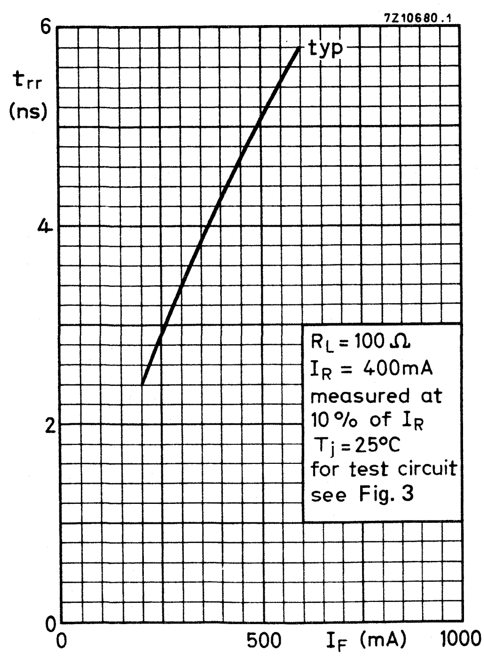


Fig. 14.

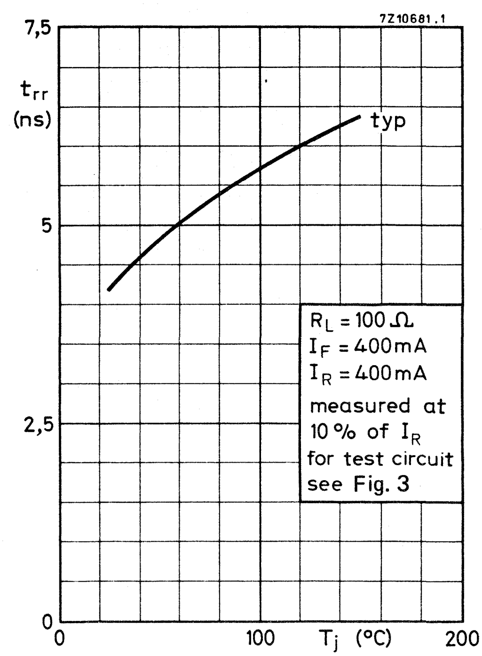
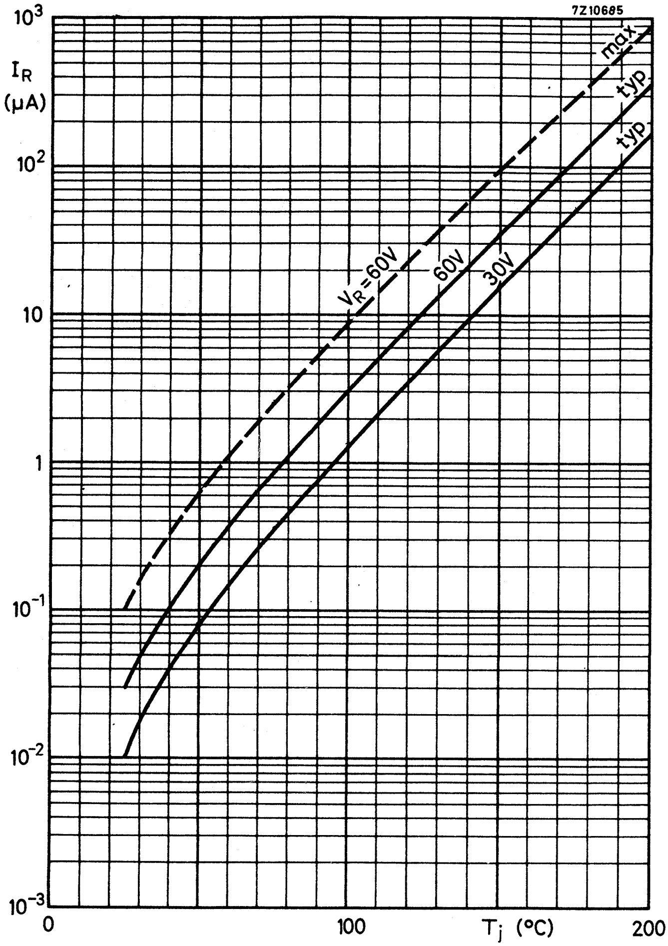


Fig. 15.


7Z10685
10^3
I_R
(μA)
10^2
10
1
10^{-1}
10^{-2}
10^{-3}
0
100
T_j (°C)
200
max
typ
typ
V_R=60V
60V
30V

GENERAL PURPOSE DIODES

Silicon planar epitaxial diodes in DO-35 envelopes; intended for switching and general purposes in industrial equipment e.g. oscilloscopes, digital voltmeters and video output stages in colour television.

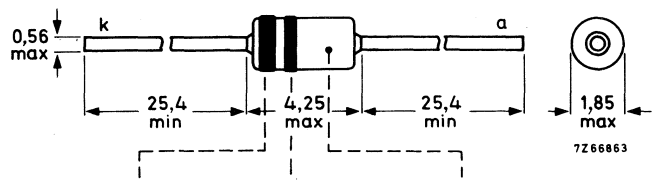
QUICK REFERENCE DATA

			BAV18	BAV19	BAV20	BAV21	
Continuous reverse voltage	V_R	max.	50	100	150	200	V
Forward current (d.c.)	I_F	max.	250				mA
Junction temperature	T_j	max.	175				°C
Thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$	=	0,375				K/mW
Forward voltage at I_F = 100 mA	V_F	<	1,0				V
Reverse current at $V_R = V_{Rmax}$	I_R	<	100				nA
Diode capacitance at V_R = 0; f = 1 MHz	C_d	typ.	1,5				pF
		<	5,0				pF
Reverse recovery time when switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω; measured at I_R = 3 mA	t_{rr}	<	50				ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-27 (DO-35).



BAV18:	**brown**	**grey**	**green**
BAV19:	**brown**	**white**	**green**
BAV20:	**red**	**black**	**green**
BAV21:	**red**	**brown**	**green**
	(cathode)		

Diodes may be either type-branded or colour coded.

Products approved to CECC 50 001-022, available on request.

RATINGS Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BAV18	BAV19	BAV20	BAV21	
Continuous reverse voltage	V_R	max.	50	100	150	200	V
Repetitive peak reverse voltage	V_{RRM}	max.	60	120	200	250	V

Average rectified forward current	$I_{F(AV)}$	max.	250	mA	1)
Forward current (d.c.)	I_F	max.	250	mA	
Repetitive peak forward current	I_{FRM}	max.	625	mA	
Non-repetitive peak forward current					
$t < 1$ s ; $T_j = 25\ ^oC$	I_{FSM}	max.	1	A	
$t = 1\ \mu s$; $T_j = 25\ ^oC$	I_{FSM}	max.	5	A	
Total power dissipation up to $T_{amb} = 25\ ^oC$	P_{tot}	max.	400	mW	
Storage temperature	T_{stg}		-65 to +175	^oC	
Junction temperature	T_j	max.	175	^oC	

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j-a}$	=	0, 375	K/mW

1) For pulse operation see Figs 3 to 6. For sinusoidal operation see Figs 7 to 10.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage

I_F = 100 mA	V_F	<	1,0	V
I_F = 200 mA	V_F	<	1,25	V

Reverse breakdown voltage

			BAV18	BAV19	BAV20	BAV21		
I_R = 100 μA	$V_{(BR)R}$	>	60	120	200	250	V	[1]

Reverse current

$V_R = V_{Rmax}$	I_R	<	100	nA
$V_R = V_{Rmax}$; T_j = 150 °C	I_R	<	100	μA

Differential resistance

I_F = 10 mA	r_{diff}	typ.	5	Ω

Diode capacitance

V_R = 0; f = 1 MHz	C_d	typ.	1,5	pF
		<	5,0	pF

Reverse recovery time when switched from

I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω; measured at I_R = 3 mA	t_{rr}	<	50	ns

Test circuit and waveforms:

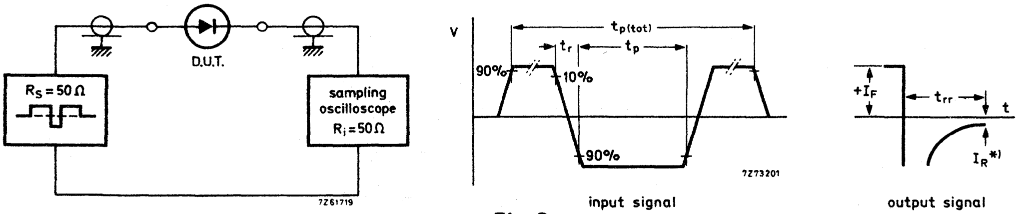


Fig. 2.

Input signal	: Total pulse duration	$t_{p(tot)}$	= 2 μs
	Duty factor	δ	= 0,0025
	Rise time of the reverse pulse	t_r	= 0,6 ns
	Reverse pulse duration	t_p	= 100 ns
Oscilloscope:	Rise time	t_r	= 0,35 ns

*) I_R = 3 mA

Circuit capacitance C ≤ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

[1]) At zero life time, measured under pulse conditions to avoid excessive dissipation and voltage limited at 275 V.

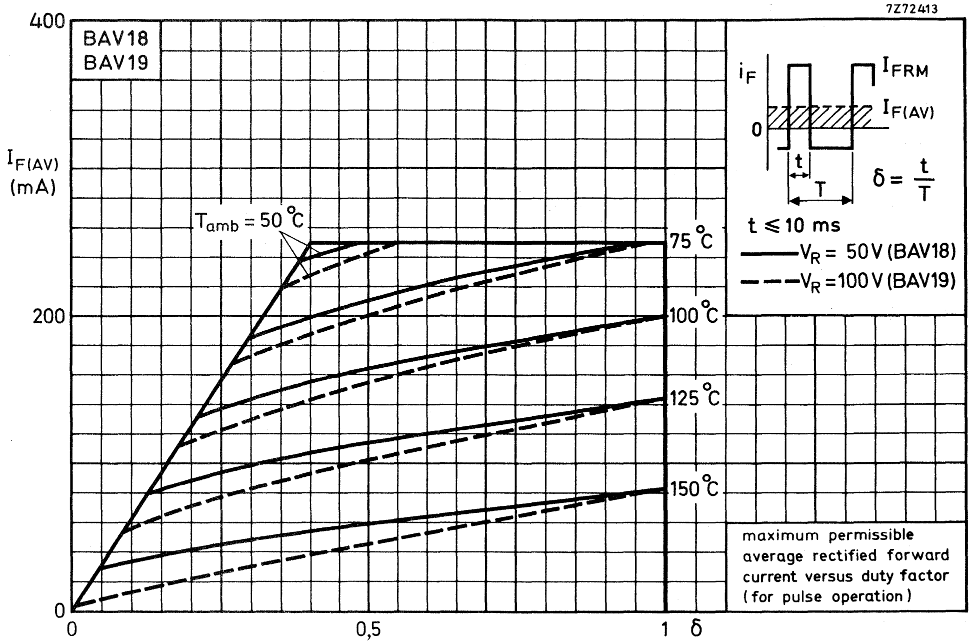

7Z72413
400
200
0
$I_{F(AV)}$
(mA)
BAV18
BAV19
T_{amb} = 50 °C
75 °C
100 °C
125 °C
150 °C
0
0,5
1 δ
i_F
I_{FRM}
$I_{F(AV)}$
0
t
T
δ = t/T
t ⩽ 10 ms
V_R = 50 V (BAV18)
V_R = 100 V (BAV19)
maximum permissible average rectified forward current versus duty factor (for pulse operation)

Fig. 3.

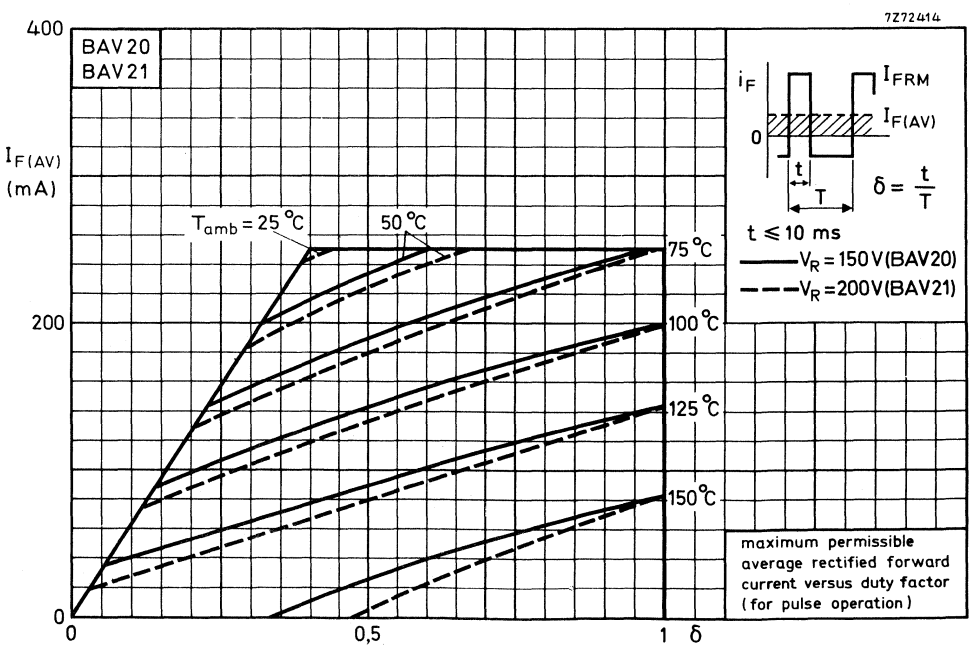

7Z72414
400
200
0
$I_{F(AV)}$
(mA)
BAV20
BAV21
T_{amb} = 25 °C
50 °C
75 °C
100 °C
125 °C
150 °C
0
0,5
1 δ
i_F
I_{FRM}
$I_{F(AV)}$
0
t
T
δ = t/T
t ⩽ 10 ms
V_R = 150 V (BAV20)
V_R = 200 V (BAV21)
maximum permissible average rectified forward current versus duty factor (for pulse operation)

Fig. 4.

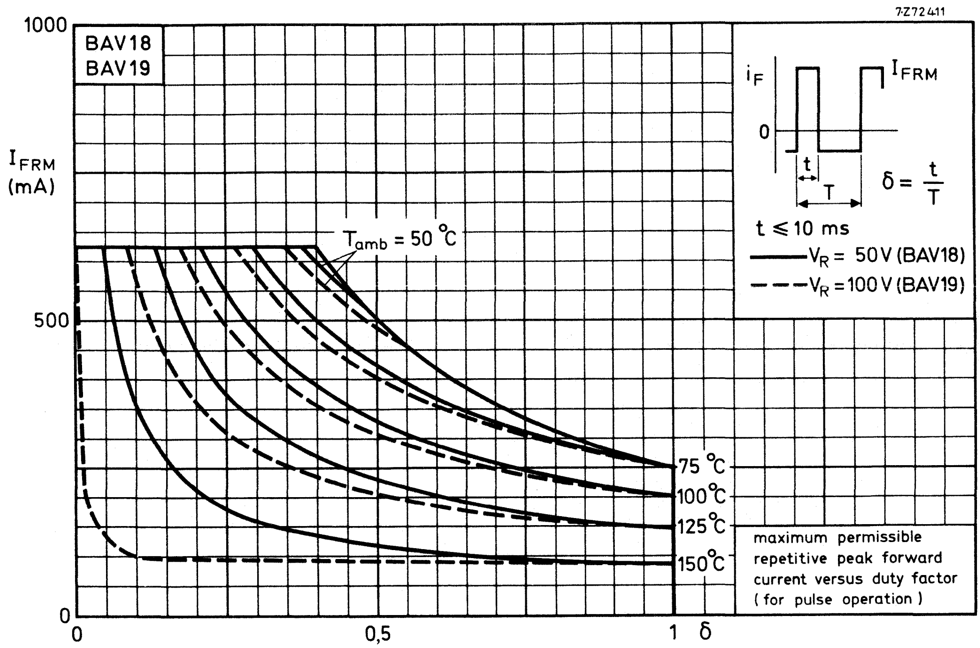

7Z72411
1000
BAV18
BAV19
I_{FRM}
(mA)
500
0
0
0,5
1 δ
T_{amb} = 50 °C
75 °C
100 °C
125 °C
150 °C
i_F
I_{FRM}
0
t
T
δ = t/T
t ≤ 10 ms
V_R = 50 V (BAV18)
V_R = 100 V (BAV19)
maximum permissible
repetitive peak forward
current versus duty factor
(for pulse operation)

Fig. 5.

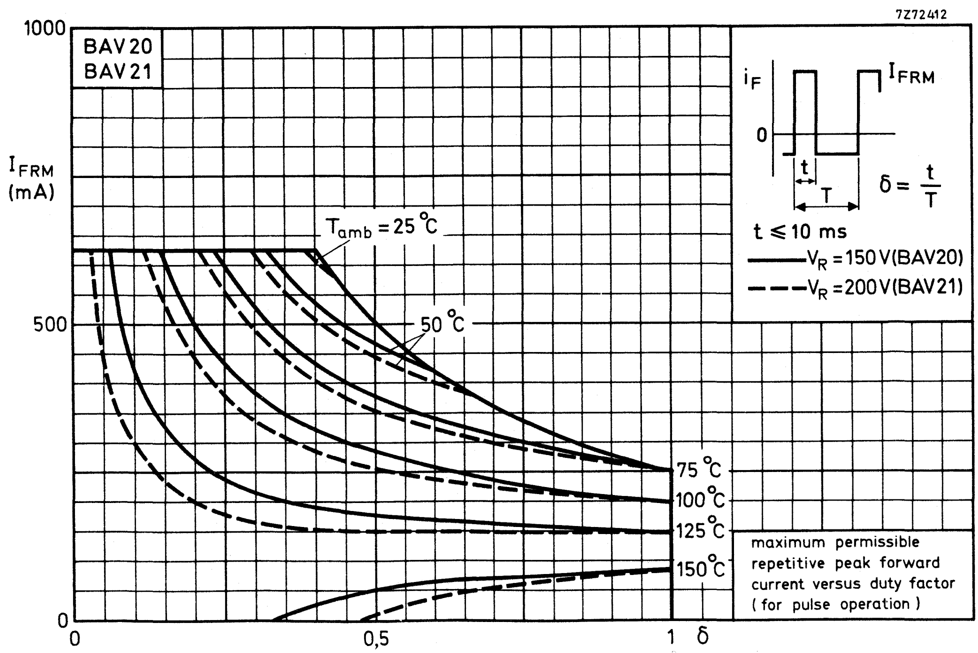

7Z72412
1000
BAV20
BAV21
I_{FRM}
(mA)
500
0
0
0,5
1 δ
T_{amb} = 25 °C
50 °C
75 °C
100 °C
125 °C
150 °C
i_F
I_{FRM}
0
t
T
δ = t/T
t ≤ 10 ms
V_R = 150 V (BAV20)
V_R = 200 V (BAV21)
maximum permissible
repetitive peak forward
current versus duty factor
(for pulse operation)

Fig. 6.

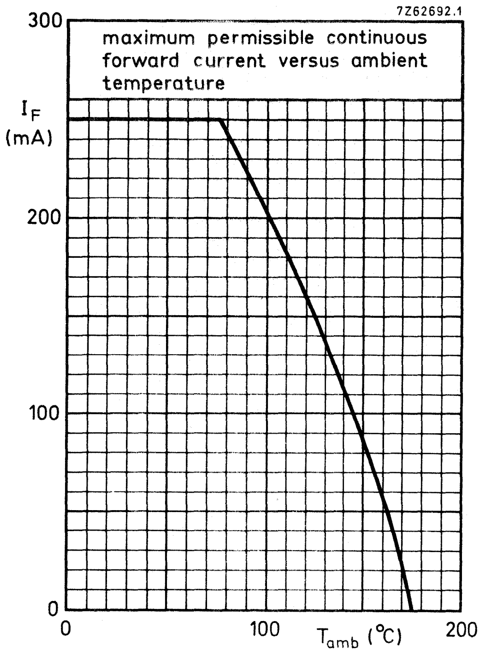


Fig. 7.

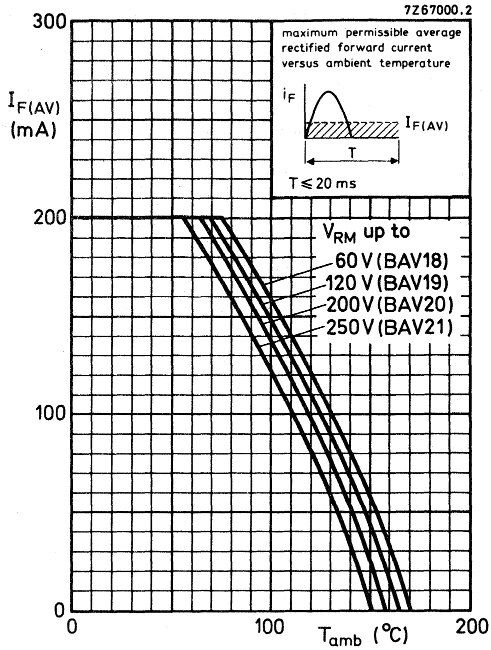


Fig. 8.

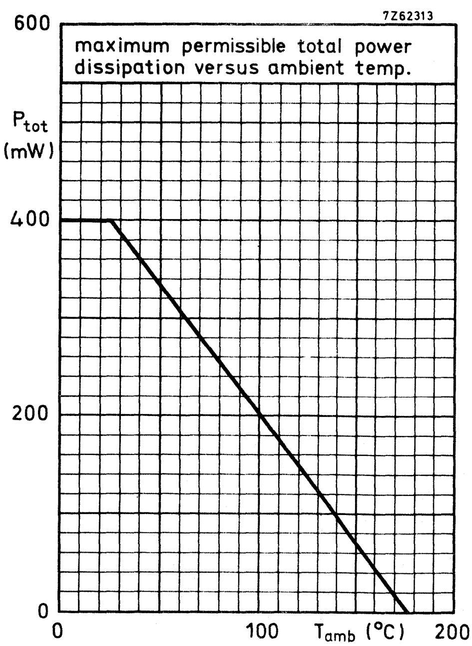


Fig. 9.

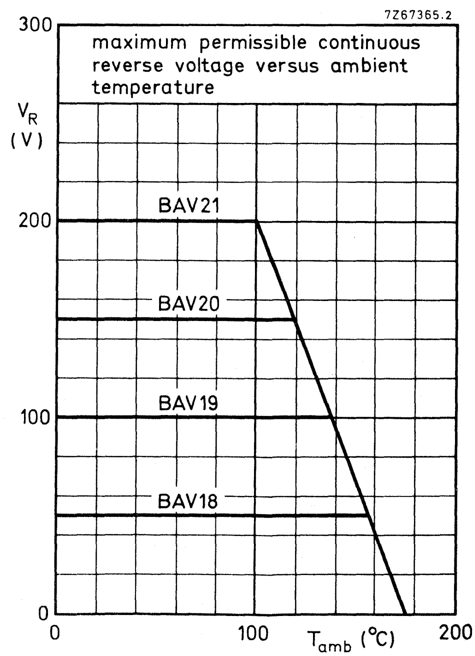


Fig. 10.

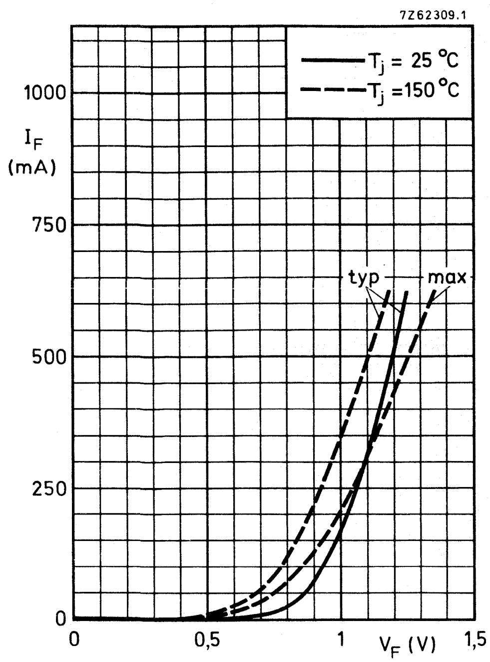


Fig. 11.

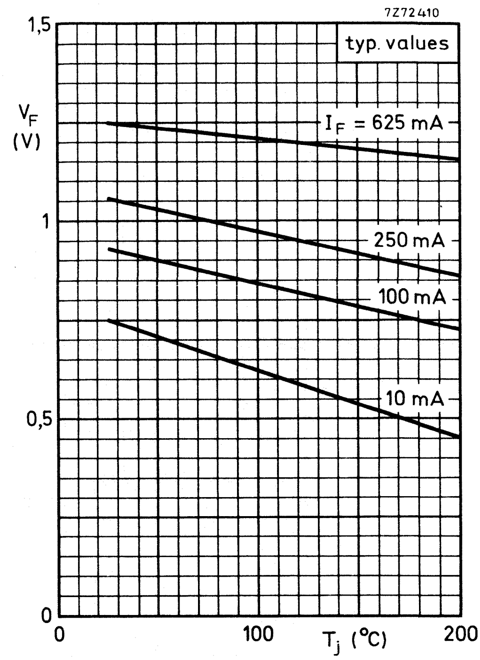


Fig. 12.

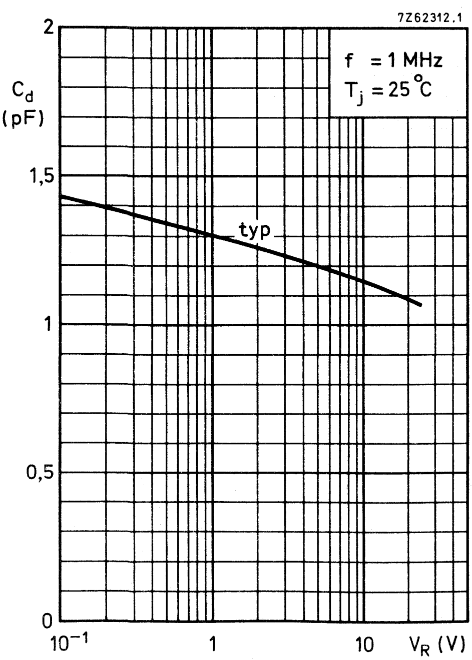


Fig. 13.

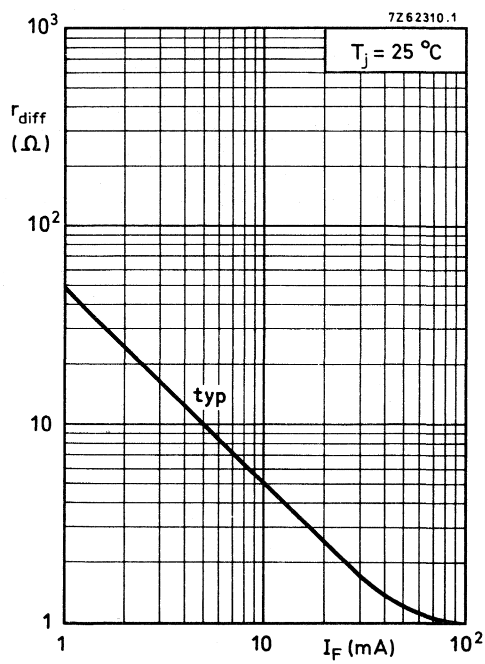


Fig. 14.

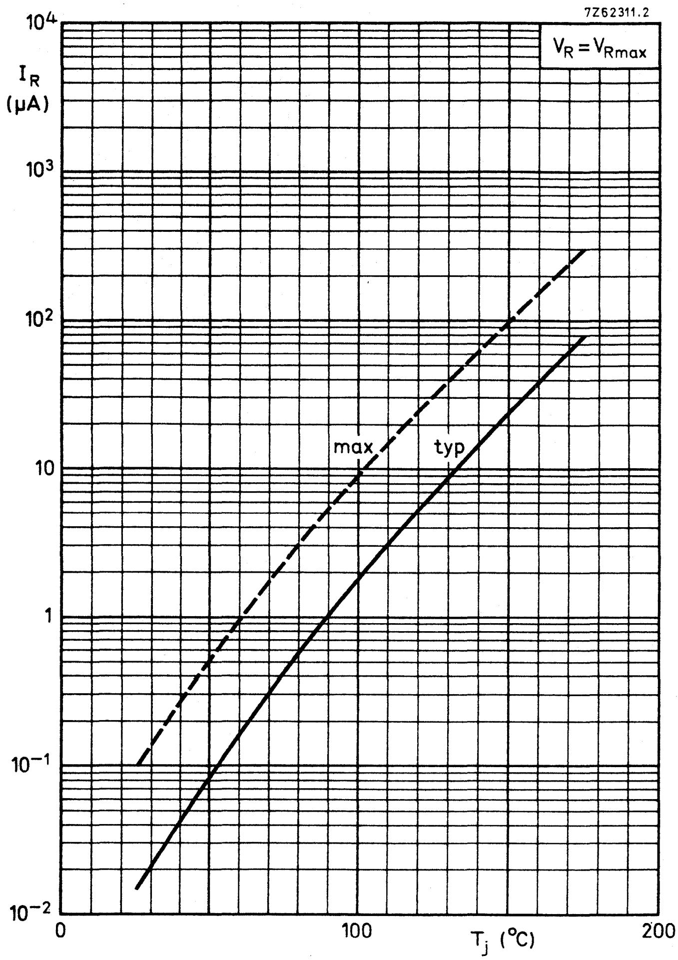

7Z62311.2
$V_R = V_{Rmax}$
I_R (μA)
10^4
10^3
10^2
10
1
10^{-1}
10^{-2}
max
typ
0
100
200
T_j (°C)

Fig. 15.

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODE

The BAV23 consists of two separate planar epitaxial high-speed diodes in one microminiature plastic envelope intended for surface mounting.

The device is designed for switching and general applications where high breakdown voltages are required.

QUICK REFERENCE DATA

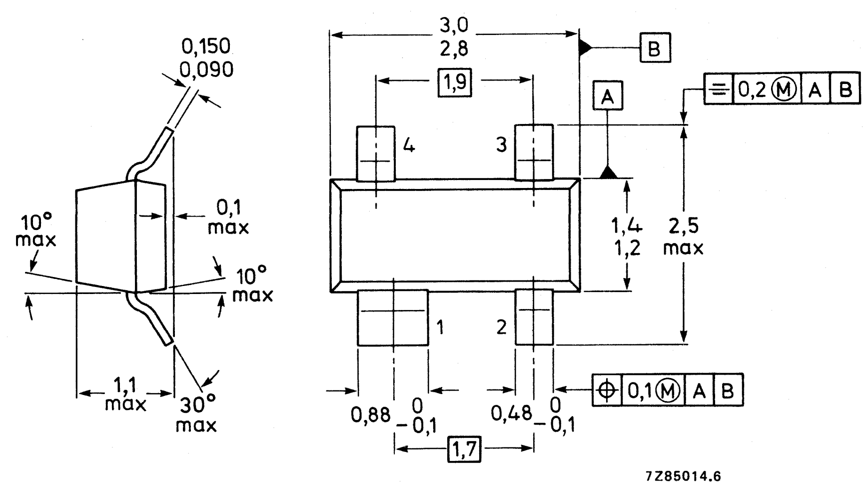
			single diode	series connection	
Continuous reverse voltage	V_R	max.	200	400	V
Repetitive peak rerverse voltage	V_{RRM}	max.	250	500	V
Average forward current	$I_{F(AV)}$	max.	200	120	mA
Repetitive peak forward current	I_{FRM}	max.	625	450	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300		mW
Reverse recovery time when switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω; measured at I_R = 3 mA	t_{rr}	<	50		ns

MECHANICAL DATA

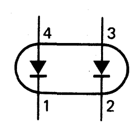
Dimensions in mm

Fig. 1 SOT-143.

Marking code: L30



TOP VIEW



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			single diode	series connection	
Continuous reverse voltage	V_R	max.	200	400	V
Repetitive peak reverse voltage	V_{RRM}	max.	250	500	V
Average forward current	$I_{F(AV)}$	max.	200	120	mA
Repetitive peak forward current	I_{FRM}	max.	625	450	mA
Non-repetitive peak forward current t = 1 μs;	I_{FSM}	max.	2,5	1,5	A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300		mW
Storage temperature	T_{stg}		−65 to +150		°C
Junction temperature	T_j	max.	150		°C

THERMAL RESISTANCE

From junction to ambient on a ceramic substrate of 8 mm x 10 mm x 0,6 mm	$R_{th\ j\text{-}a}$	430	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			single diode	series connection	
Forward voltage I_F = 100 mA	V_F	<	1000	2000	mV
I_F = 200 mA	V_F	<	1250	2500	mV
Reverse current $V_R = V_{Rmax}$	I_R	<	100	100	nA
Reverse breakdown voltage I_R = 100 μA	$V_{(BR)R}$	>	250	500	V
Differential forward resistance I_F = 10 mA	r_f	typ.	5	10	Ω
Diode capacitance V_R = 0; f = 1 MHz	C_d	<	5	2,5	pF
Reverse recovery time when switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω; measured at I_R = 3 mA	t_{rr}	<	50	50	ns

PICOAMPERE DIODE

Silicon diode in a metal envelope. It has an extremely low leakage current over a wide temperature range combined with a low capacitance and is not sensitive to light. It is intended for clamping, holding, peak follower, time delay circuits as well as for logarithmic amplifiers and protection of insulated gate field-effect transistors.

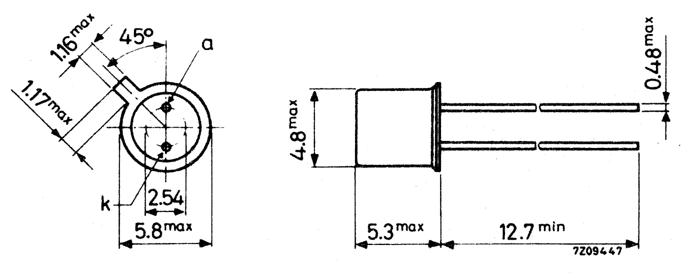
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	20	V
Forward current (d.c.)	I_F	max.	50	mA
Forward voltage at I_F = 10 mA	V_F	<	1,0	V
Reverse current				
V_R = 5 V; T_j = 25 °C	I_R	<	5	pA
V_R = 20 V; T_j = 25 °C	I_R	<	10	pA
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	1,3	pF

MECHANICAL DATA

Dimensions in mm

Fig. 1 TO-18 (except for the two leads)



Handle the device with care whilst soldering into the circuit. The extremely low leakage current can only be guaranteed when the bottom is free from solder flux or other contaminations.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	20	V
Repetitive peak reverse voltage	V_{RRM}	max.	35	V
Forward current (d.c. or average)	I_F	max.	50	mA
Repetitive peak forward current	I_{FRM}	max.	100	mA
Storage temperature	T_{stg}	−65 to + 125		^oC
Junction temperature	T_j	max.	125	^oC

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	500	K/W

CHARACTERISTICS

$T_j = 25\ ^oC$ unless otherwise specified

Forward voltage				
$I_F = 10$ mA	V_F	<	1,0	V
Reverse current				
$V_R = 5$ V	I_R	<	5	pA
$V_R = 5$ V; $T_j = 80\ ^oC$	I_R	<	250	pA
$V_R = 20$ V	I_R	<	10	pA
Diode capacitance				
$V_R = 0$; f = 1 MHz	C_d	<	1,3	pF
Forward recovery voltage when switched to				
$I_F = 10$ mA	V_{fr}	<	1,25	V

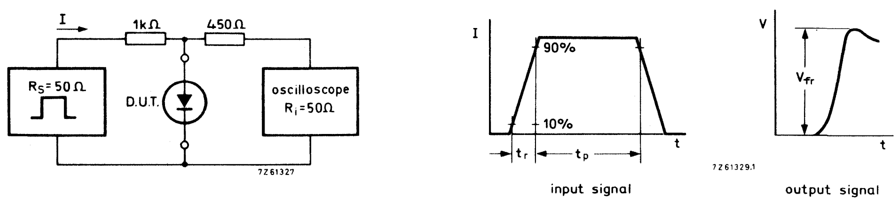


Fig. 2 Test circuit and waveforms.

Input signal				
Rise time of the forward pulse	t_r	⩽	20	ns
Forward current pulse duration	t_p	=	300	ns
Duty factor	δ	=	0,01	
Oscilloscope				
Rise time	t_r	=	0,35	ns
Input capacitance	C_i	⩽	1	pF

Circuit capacitance $C \leqslant 20$ pF ($C = C_i$ + parasitic capacitance)

CHARACTERISTICS (continued)

Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	600	ns

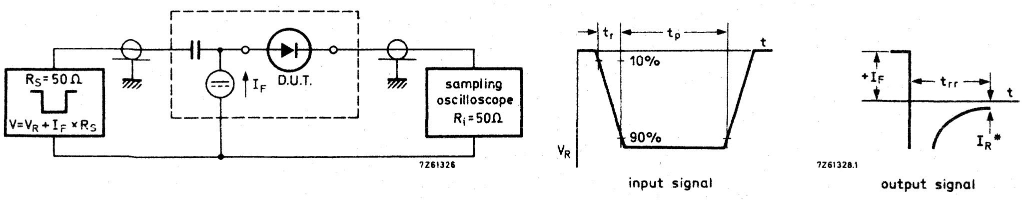


Fig. 3 Test circuit and waveforms. * I_R = 1 mA.

Input signal				
Rise time of the reverse pulse	t_r	=	0,6	ns
Reverse pulse duration	t_p	=	500	ns
Duty factor	δ	=	0,05	
Oscilloscope				
Rise time	t_r	=	0,35	ns

Circuit capacitance C ≤ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

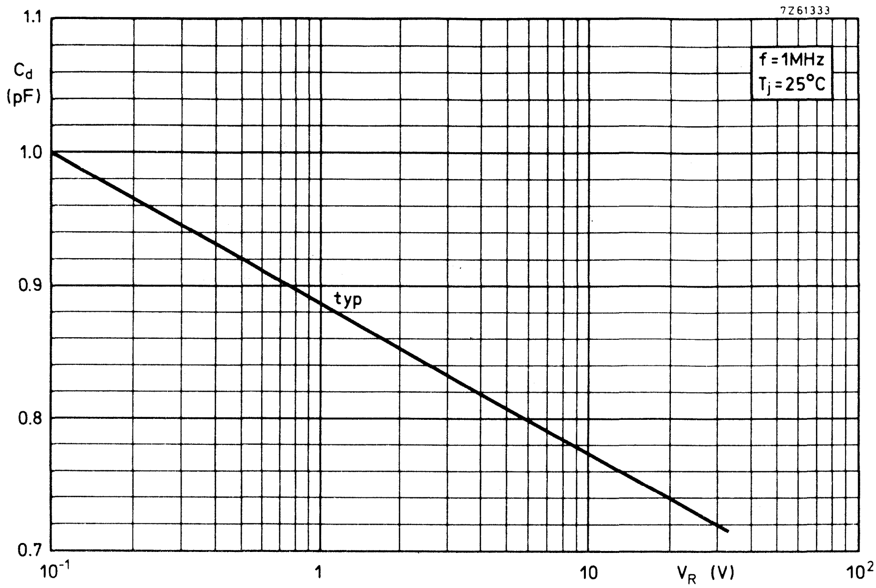

7Z61333
1.1
C_d
(pF)
1.0
0.9
0.8
0.7
f = 1MHz
T_j = 25°C
typ
10^{-1}
1
10
V_R (V)
10^2

Fig. 4.

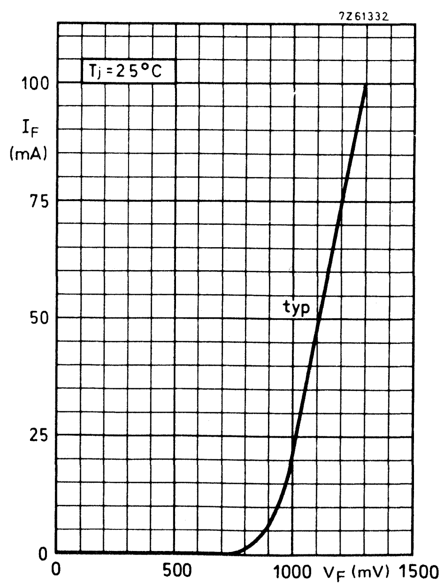

7Z61332
T_j = 25°C
100
I_F
(mA)
75
50
25
0
typ
0
500
1000
V_F (mV)
1500

Fig. 5.

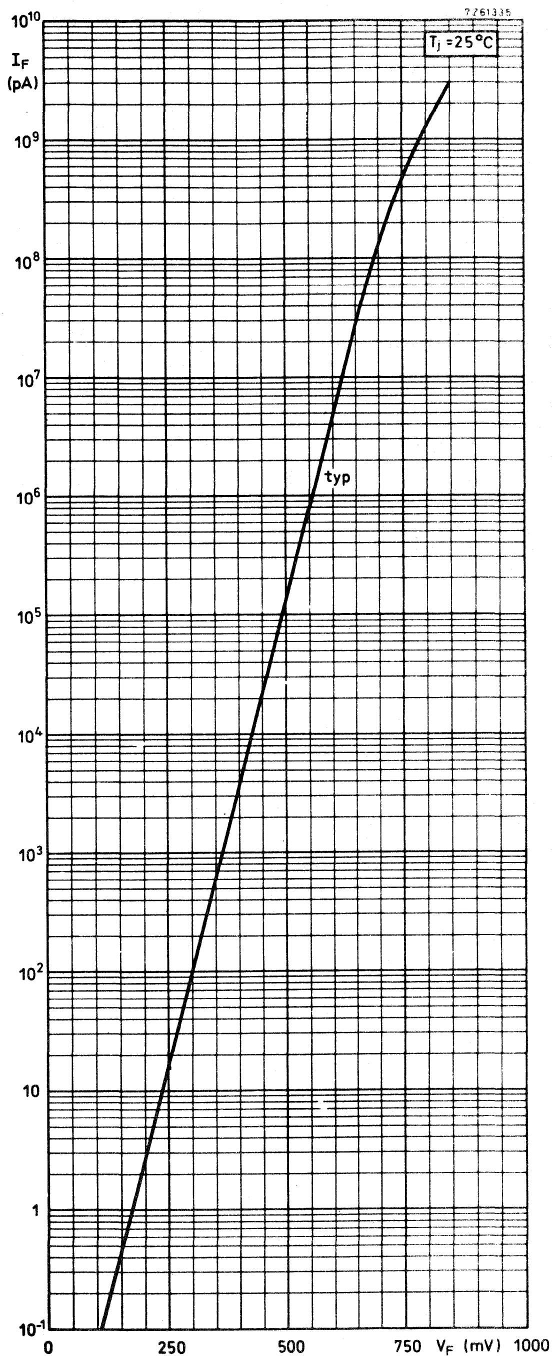

7Z61335
10^{10}
I_F
(pA)
10^9
10^8
10^7
10^6
10^5
10^4
10^3
10^2
10
1
10^{-1}
$T_j = 25\,^{\circ}C$
typ
0
250
500
750
V_F (mV)
1000

Fig. 6.

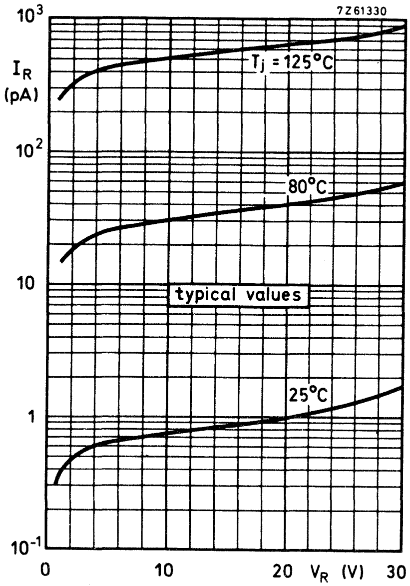

7Z61330
I_R
(pA)
10^3
10^2
10
1
10^{-1}
T_j = 125°C
80°C
typical values
25°C
0
10
20
30
V_R (V)

Fig. 7.

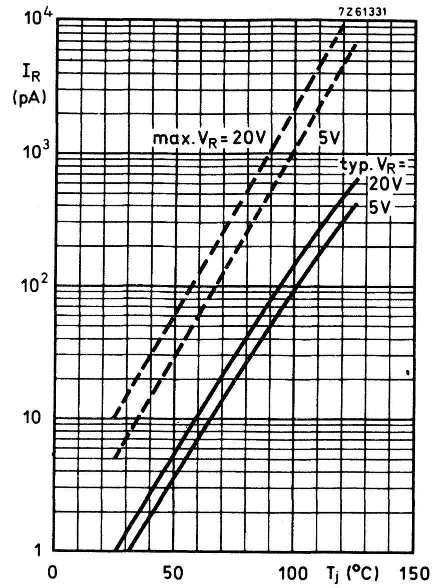

7Z61331
I_R
(pA)
10^4
10^3
10^2
10
1
max. V_R = 20V
5V
typ. V_R =
20V
5V
0
50
100
150
T_j (°C)

Fig. 8.

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODE

The device consists of two diodes in a microminiature plastic envelope. The cathodes are commoned and the device is intended for high-speed switching in thick and thin-film circuits.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	50	V
Repetitive peak reverse voltage	V_{RRM}	max.	50	V
Repetitive peak forward current	I_{FRM}	max.	250	mA
Junction temperature	T_j	max.	150	°C ←
Forward voltage I_F = 100 mA	V_F	≤	1,0	V
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	≤	4	ns

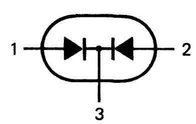
MECHANICAL DATA

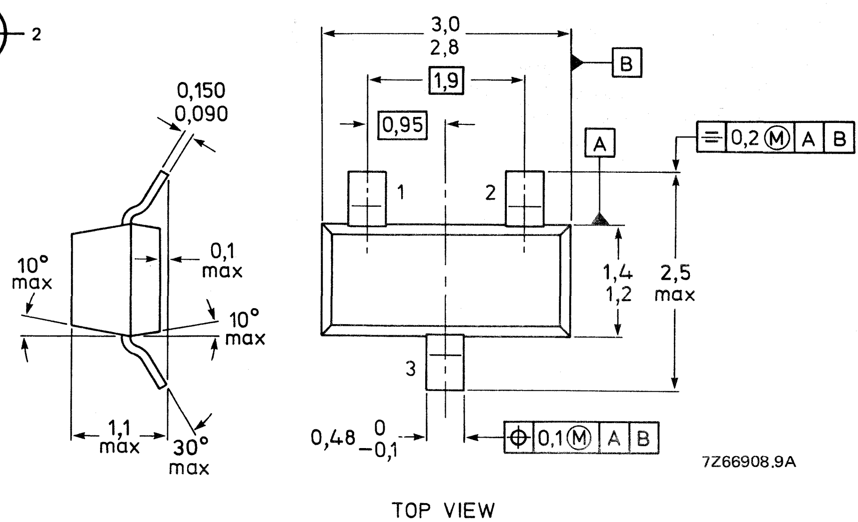
Dimensions in mm

Fig. 1 SOT-23.

Marking code

BAV74 = JA ←





RATINGS (per diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	50 V
Repetitive peak reverse voltage	V_{RRM}	max.	50 V
Average rectified forward current (averaged over any 20 ms period; t_p = 10 ms)	$I_{F(AV)}$	max.	250 mA
Forward current (d.c. or average)	I_F	max.	250 mA
Repetitive peak forward current	I_{FRM}	max.	250 mA
Non-repetitive peak forward current t = 1 µs	I_{FSM}	max.	4,5 A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300 mW
Storage temperature	T_{stg}		−65 to +150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE*

From junction to ambient **	$R_{th\ j\text{-}a}$	max.	430 K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Breakdown voltage at I_R = 100 µA	$V_{(BR)R}$	≥	50 V
Forward voltage I_F = 100 mA	V_F	≤	1,0 V
Reverse currents V_R = 50 V	I_R	≤	0,1 µA
V_R = 50 V; T_{amb} = 150 °C	I_R	≤	100 µA
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA See Fig. 2	t_{rr}	≤	4 ns
Diode capacitance at V_R = 0; f = 1 MHz	C_d	≤	2 pF

* See Thermal Characteristics.
** When mounted on ceramic substrate of 8 mm x 10 mm x 0,7 mm.

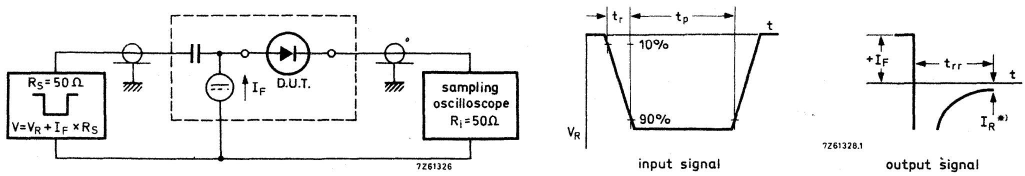


Fig. 2 Reverse recovery time test circuit and waveforms.

* I_R = 1 mA

Input signal :	Rise time of the reverse pulse	t_r	= 0,6 ns
	Reverse pulse duration	t_p	= 100 ns
	Duty factor	δ	= 0,05
Oscilloscope :	Rise time	t_r	= 0,35 ns

Circuit capacitance C ⩽ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

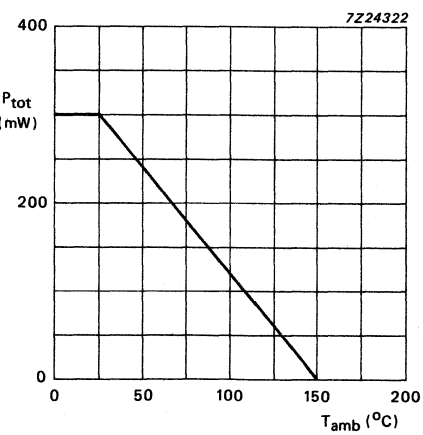


Fig. 3 Power derating curve.

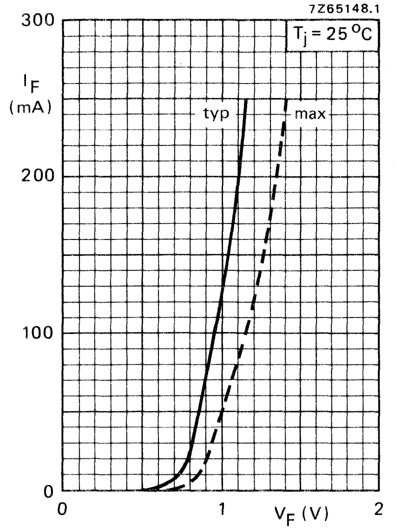


Fig. 4 Forward current as a function of forward voltage.

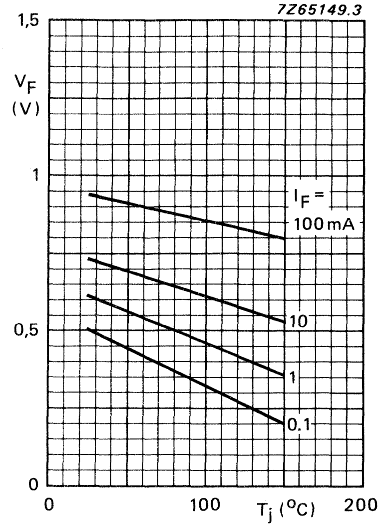


Fig. 5 Forward voltage as a function of junction temperature.

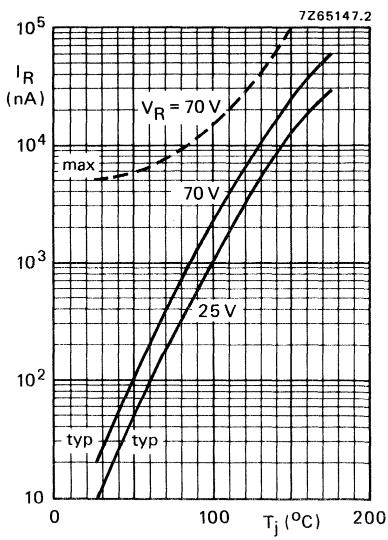


Fig. 6 Reverse current as a function of junction temperature.

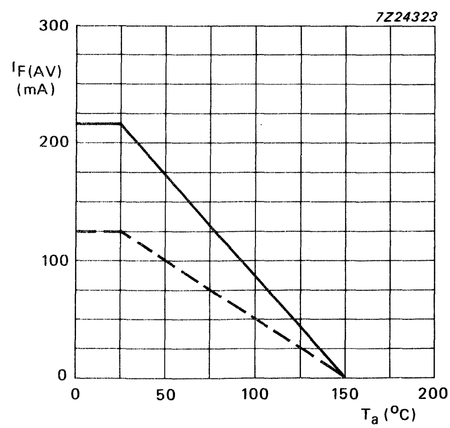


Fig. 7 Average current as a function of ambient temperature: ——— single diode; ----------- double diode, equally loaded.

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODES

The BAV99 consists of two diodes in a microminiature plastic envelope. The diodes are connected in series and the unit is intended for high-speed switching in thick and thin-film circuits.

QUICK REFERENCE DATA (per diode)

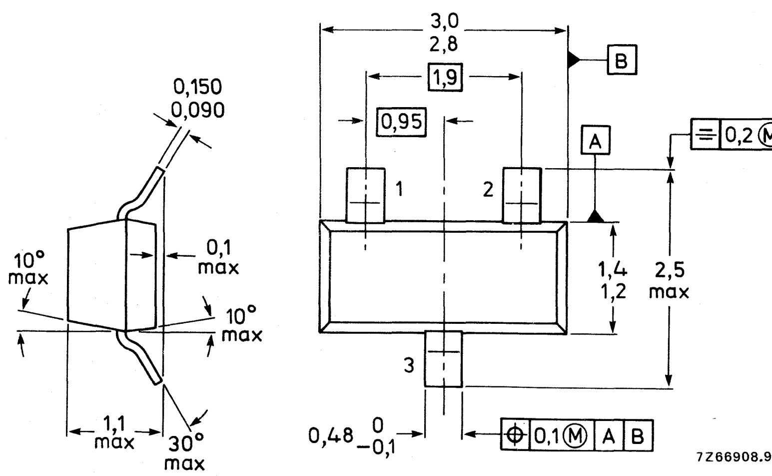
Continuous reverse voltage	V_R	max.	70	V
Repetitive peak reverse voltage	V_{RRM}	max.	70	V
Repetitive peak forward current	I_{FRM}	max.	215	mA
Junction temperature	T_j	max.	150	°C
Forward voltage at I_F = 50 mA	V_F	<	1,0	V
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	6	ns
Recovery charge when switched from I_F = 10 mA to V_R = 5 V; R_L = 500 Ω	Q_s	<	45	pC

MECHANICAL DATA Dimensions in mm

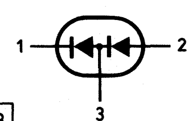
Fig. 1 SOT-23.

Marking code

BAV99 = A7



TOP VIEW



See also *Soldering recommendations.*

RATINGS (per diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	70 V
Repetitive peak reverse voltage	V_{RRM}	max.	70 V
Average rectified forward current* (averaged over any 20 ms period)	$I_{F(AV)}$	max.	215 mA
Forward current (d.c.)	I_F	max.	215 mA
Repetitive peak forward current	I_{FRM}	max.	215 mA
Non-repetitive peak forward current (per crystal)			
t = 1 μs	I_{FRM}	max.	2 A
t = 1 ms	I_{FRM}	max.	1 A
t = 1 s	I_{FRM}	max.	0,5 A
Storage temperature range	T_{stg}		−65 to + 150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE**

From junction to ambient▲	$R_{th\,j\text{-}a}$	=	430 K/W

CHARACTERISTICS (per diode)

T_j = 25 °C unless otherwise specified

Forward voltage			
I_F = 1 mA	V_F	<	715 mV
I_F = 10 mA	V_F	<	855 mV
I_F = 50 mA	V_F	<	1000 mV
I_F = 150 mA	V_F	<	1250 mV
Reverse current			
V_R = 25 V; T_j = 150 °C	I_R	<	30 μA
V_R = 70 V	I_R	<	2,5 μA
V_R = 70 V; T_j = 150 °C	I_R	<	50 μA
Diode capacitance			
V_R = 0; f = 1 MHz	C_d	<	1,5 pF
Forward recovery voltage when switched to I_F = 10 mA; t_r = 20 ns	V_{fr}	<	1,75 V

* Measured under pulse conditions: pulse time $t_p \leq 0{,}5$ ms.
For sinusoidal operation $I_{F(AV)}$ = 150 mA; averaging time $t_{(av)} \leq 1$ ms.

** See *Thermal characteristics.*

▲ Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

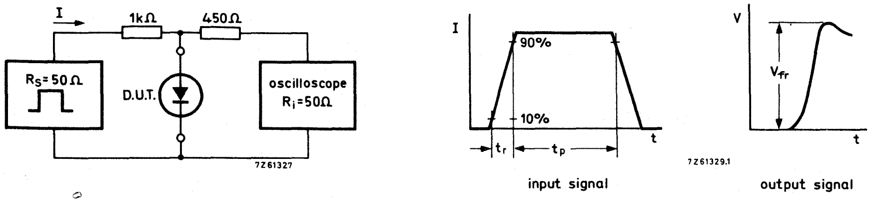


Fig. 2 Test circuit and waveforms; forward recovery voltage.

Input signal: Rise time of the forward pulse $t_r = 20$ ns;
Forward current pulse duration = t_p = 120 ns. Duty factor = δ = 0,01.
Oscilloscope: Rise time t_r = 0,35 ns.

Circuit capacitance $C \leqslant 1$ pF (C = oscilloscope input capacitance + parasitic capacitance).

Reverse recovery time when switched from
I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω;
measured at I_R = 1 mA t_{rr} < 6 ns

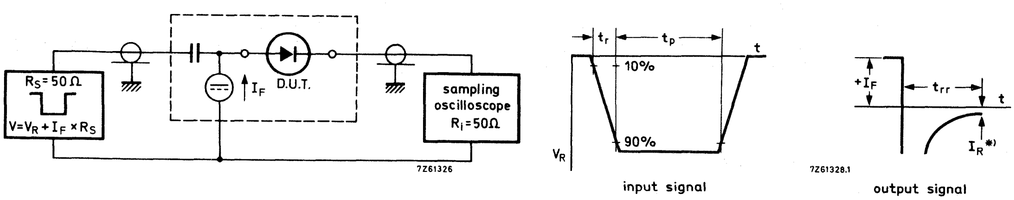


Fig. 3 Test circuit and waveforms; reverse recovery time.

Input signal: Rise time of the reverse pulse t_r = 0,6 ns *) I_R = 1 mA
Reverse pulse duration t_p = 100 ns. Duty factor δ = 0,05.
Oscilloscope: Rise time t_r = 0,35 ns.

Circuit capacitance $C \leqslant 1$ pF (C = oscilloscope input capacitance + parasitic capacitance).

Recovery charge when switched from
I_F = 10 mA to V_R = 5 V; R_L = 500 Ω Q_s < 45 pC

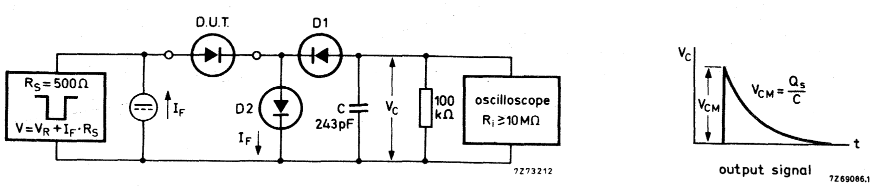


Fig. 4 Test and waveform; recovery charge.

D2 = diode with minority carrier life time at 10 mA: < 200 ps; D1 = BAW62.

Input signal: Rise time of the reverse pulse t_r = 2 ns
Reverse pulse duration t_p = 400 ns. Duty factor δ = 0,02.

Circuit capacitance $C \leqslant 7$ pF (C = oscilloscope input capacitance + parasitic capacitance).

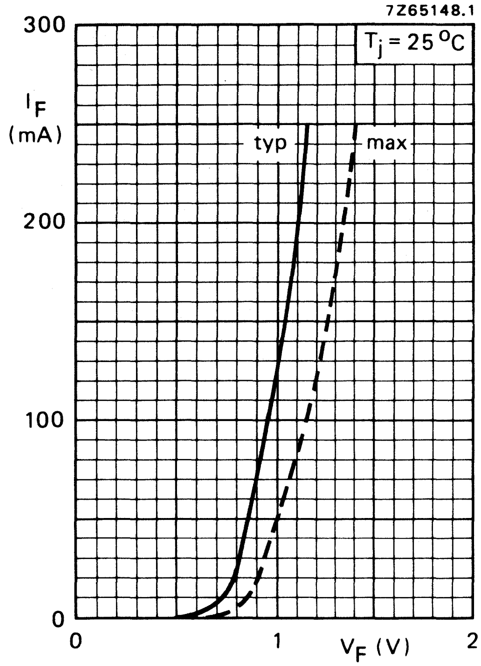


Fig. 5.

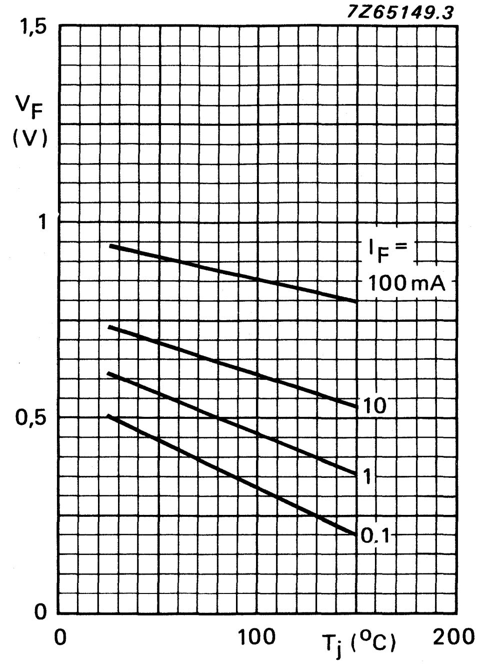


Fig. 6 Typical values.

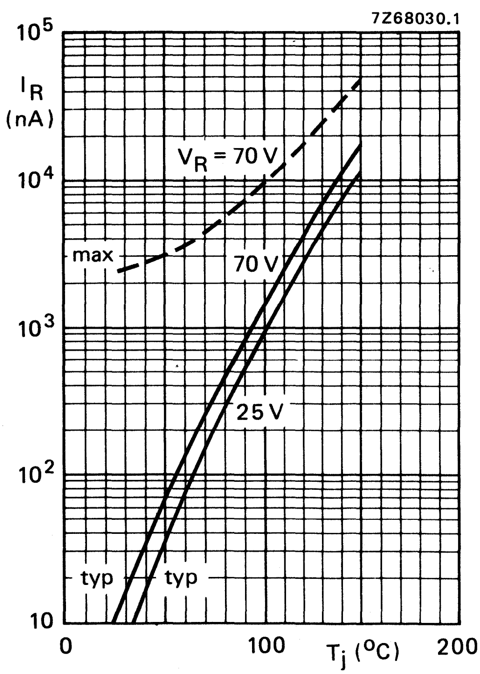


Fig. 7.

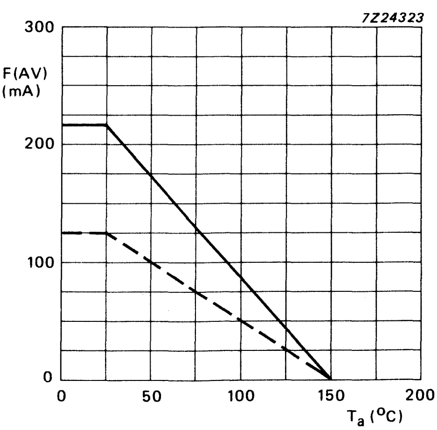


Fig. 8 ——— single diode
– – – – double diode; equally loaded.

GENERAL PURPOSE DIODES FOR SURFACE MOUNTING

Silicon planar epitaxial diodes; intended for switching and general purposes in industrial equipment e.g. oscilloscopes, digital voltmeters and video output stages in colour television.

The SM DIODE is a leadless diode in an hermetically sealed glass envelope with tin plated metal discs at each end. It is suitable for Automatic Placement and as such it can withstand immersion soldering.

The diodes are delivered in "super 8" tape.

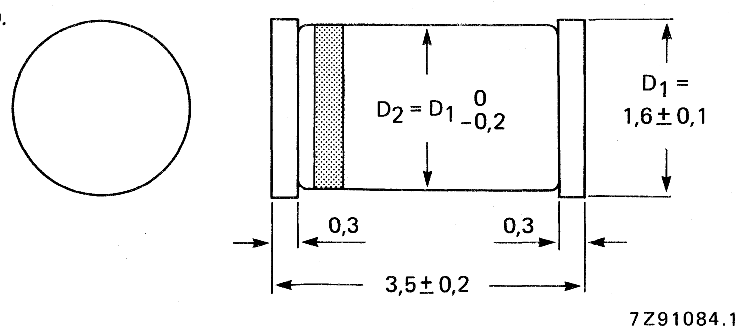
QUICK REFERENCE DATA

			BAV100	BAV101	BAV102	BAV103	
Continuous reverse voltage	V_R	max.	50	100	150	200	V
Forward current (d.c.)	I_F	max.	250				mA
Junction temperature	T_j	max.	175				°C
Thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$	=	0,375				K/mW
Forward voltage at I_F = 100 mA	V_F	<	1,0				V
Reverse current at $V_R = V_{Rmax}$	I_R	<	100				nA
Diode capacitance at V_R = 0; f = 1 MHz	C_d	typ.	1,5				pF
		<	5,0				pF
Reverse recovery time when switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω; measured at I_R = 3 mA	t_{rr}	<	50				ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



The BAV100 cathode is indicated by a green and a black band.
The BAV101 cathode is indicated by a green and a brown band.
The BAV102 cathode is indicated by a green and a red band.
The BAV103 cathode is indicated by a green and an orange band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BAV100	BAV101	BAV102	BAV103	
Continuous reverse voltage	V_R	max.	50	100	150	200	V
Repetitive peak reverse voltage	V_{RRM}	max.	60	120	200	250	V
Average rectified forward current	$I_{F(AV)}$	max.	250				mA[1])
Forward current (d.c.)	I_F	max.	250				mA
Repetitive peak forward current	I_{FRM}	max.	625				mA
Non-repetitive peak forward current							
$t < 1$ s; $T_j = 25\ ^oC$	I_{FSM}	max.	1				A
$t = 1\ \mu s$; $T_j = 25\ ^oC$	I_{FSM}	max.	5				A
Total power dissipation up to $T_{amb} = 25\ ^oC$	P_{tot}	max.	400				mW
Storage temperature	T_{stg}		−65 to + 175				^oC
Junction temperature	T_j	max.	175				^oC

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0,375	K/mW

CHARACTERISTICS

$T_j = 25\ ^oC$ unless otherwise specified

			BAV100	BAV101	BAV102	BAV103	
Forward voltage							
$I_F = 100$ mA	V_F	<	1,0				V
$I_F = 200$ mA	V_F	<	1,25				V
Reverse breakdown voltage $I_R = 100\ \mu A$	$V_{(BR)R}$	>	60	120	200	250	V[2])
Reverse current							
$V_R = V_{Rmax}$	I_R	<	100				nA
$V_R = V_{Rmax}$; $T_j = 150\ ^oC$	I_R	<	100				μA
Differential resistance $I_F = 10$ mA	r_{diff}	typ.	5				Ω
Diode capacitance $V_R = 0$; f = 1 MHz	C_d	typ.	1,5				pF
		<	5,0				pF
Reverse recovery time when switched from $I_F = 30$ mA to $I_R = 30$ mA; $R_L = 100\ \Omega$; measured at $I_R = 3$ mA	t_{rr}	<	50				ns

[1]) For sinusoidal operation see Figs 7 to 10. For pulse operation see Figs 3 to 6.

[2]) At zero life time, measured under pulse conditions to avoid excessive dissipation and voltage limited at 275 V.

Test circuit and waveforms:

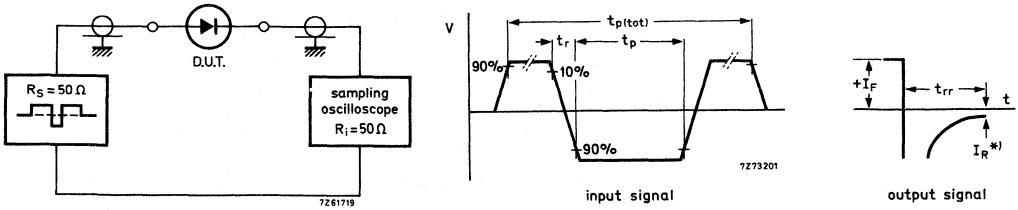


Fig. 2.

*) I_R = 3 mA

Input signal:	Total pulse duration	$t_{p(tot)}$	=	2	μs
	Duty factor	δ	=	0,0025	
	Rise time of the reverse pulse	t_r	=	0,6	ns
	Reverse pulse duration	t_p	=	100	ns
Oscilloscope:	Rise time	t_r	=	0,35	ns

Circuit capacitance C ⩽ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

DEVELOPMENT DATA

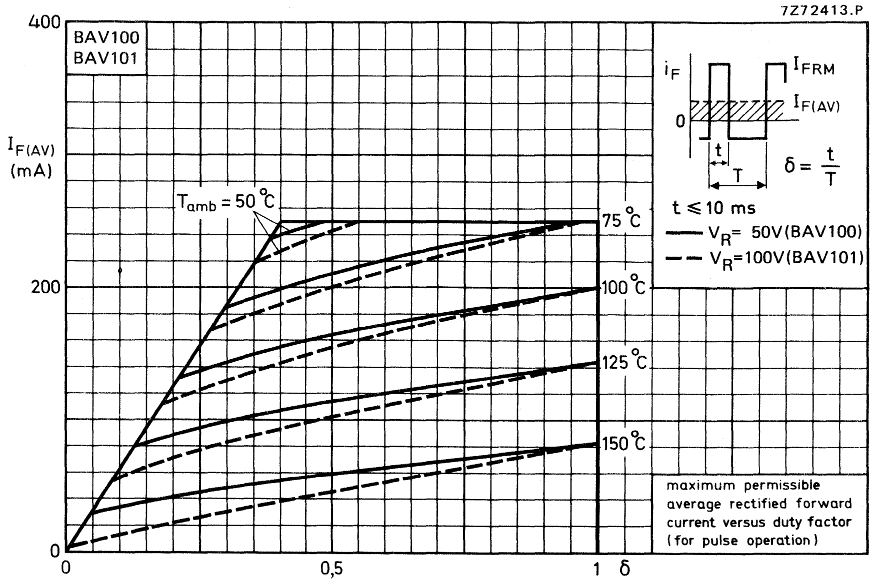

7Z72413.P
400
200
0
BAV100
BAV101
$I_{F(AV)}$
(mA)
T_{amb} = 50 °C
75 °C
100 °C
125 °C
150 °C
0
0,5
1 δ
i_F
I_{FRM}
$I_{F(AV)}$
0
t
T
δ = t/T
t ≤ 10 ms
— V_R = 50V(BAV100)
- - V_R=100V(BAV101)
maximum permissible average rectified forward current versus duty factor (for pulse operation)

Fig. 3.

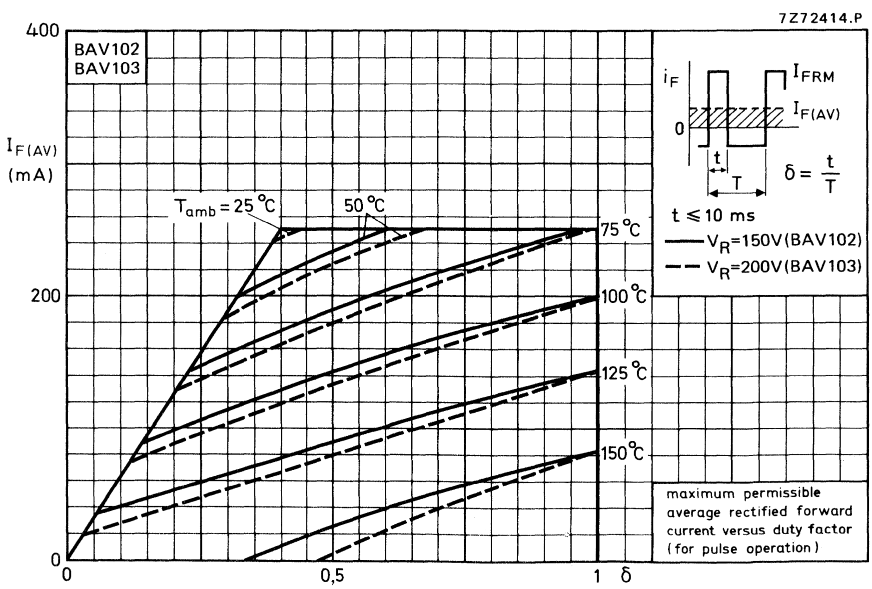

7Z72414.P
400
200
0
BAV102
BAV103
$I_{F(AV)}$
(mA)
T_{amb} = 25 °C
50 °C
75 °C
100 °C
125 °C
150 °C
0
0,5
1 δ
i_F
I_{FRM}
$I_{F(AV)}$
0
t
T
δ = t/T
t ≤ 10 ms
— V_R=150V(BAV102)
- - V_R=200V(BAV103)
maximum permissible average rectified forward current versus duty factor (for pulse operation)

Fig. 4.

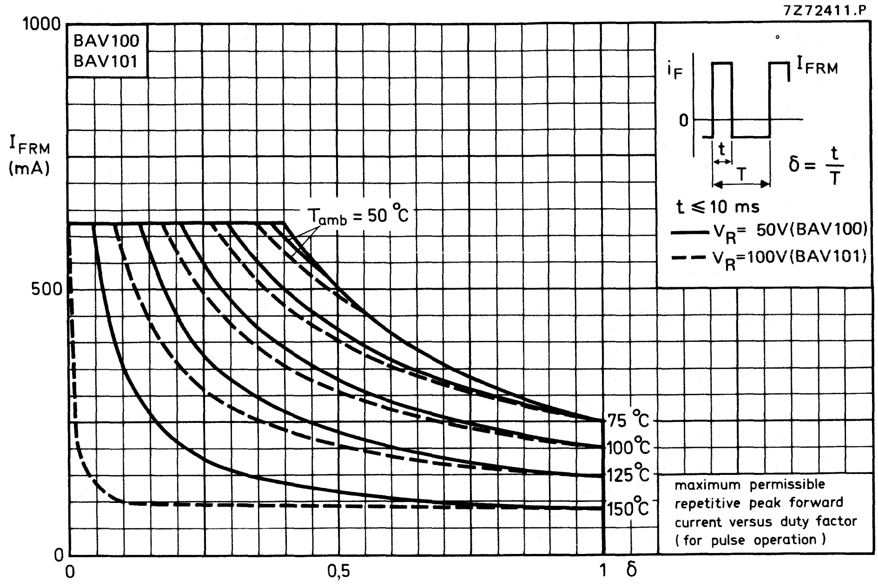


Fig. 5.

DEVELOPMENT DATA

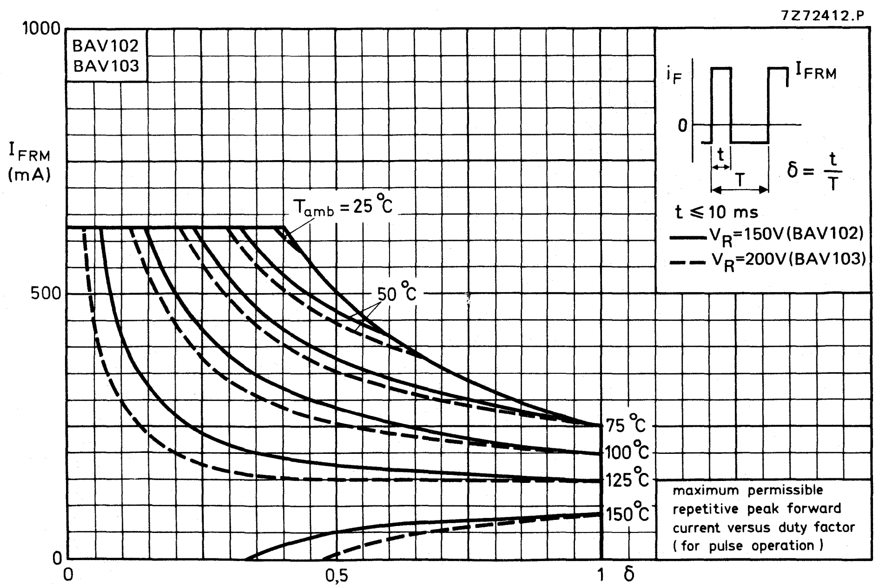


Fig. 6.

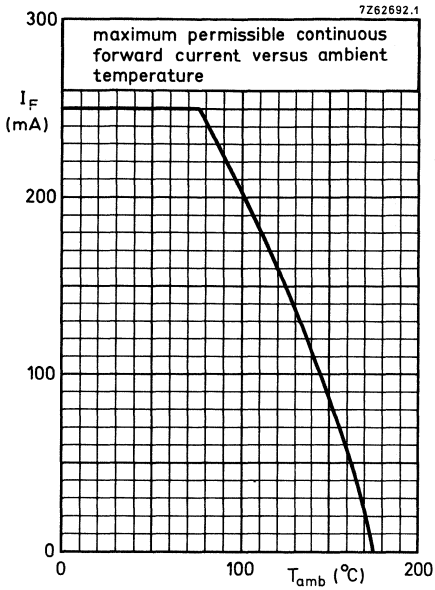


Fig. 7.

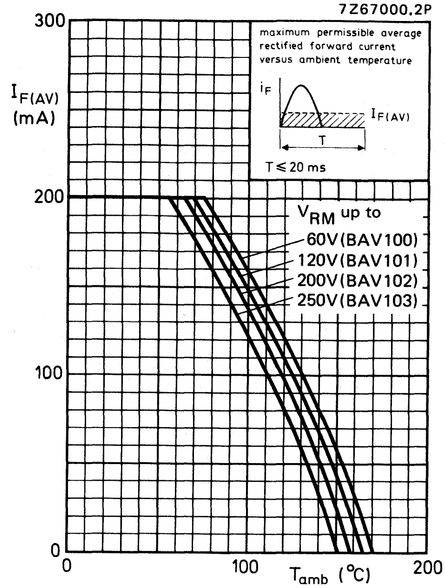


Fig. 8.

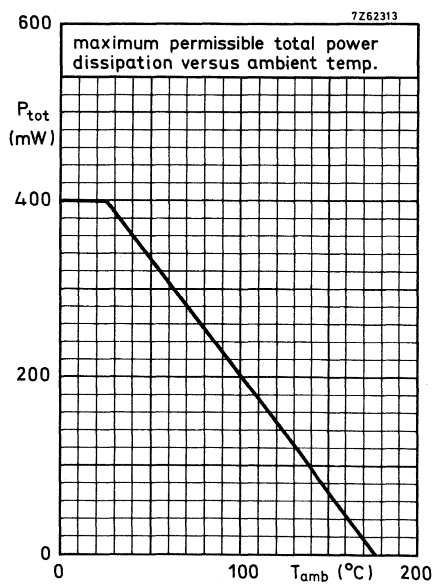


Fig. 9.

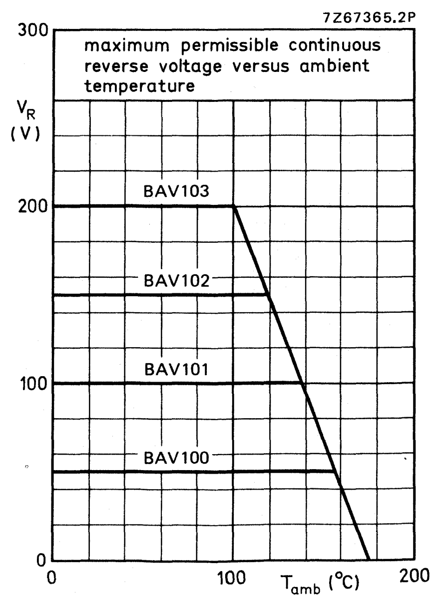


Fig. 10.

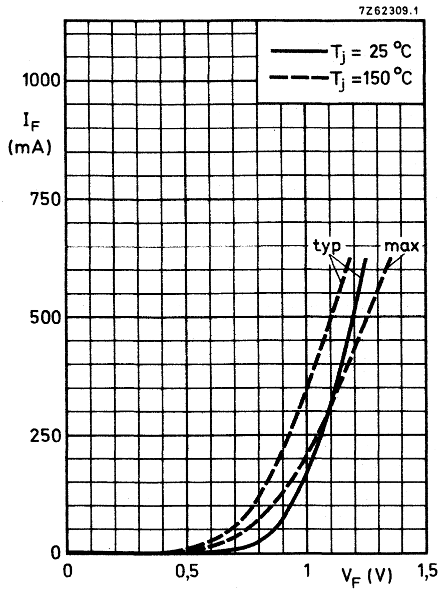


Fig. 11.

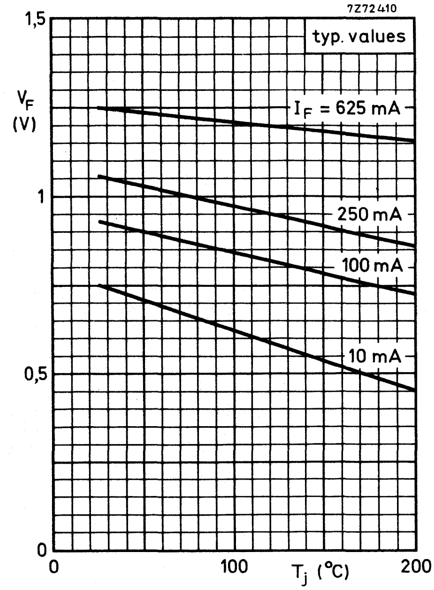


Fig. 12.

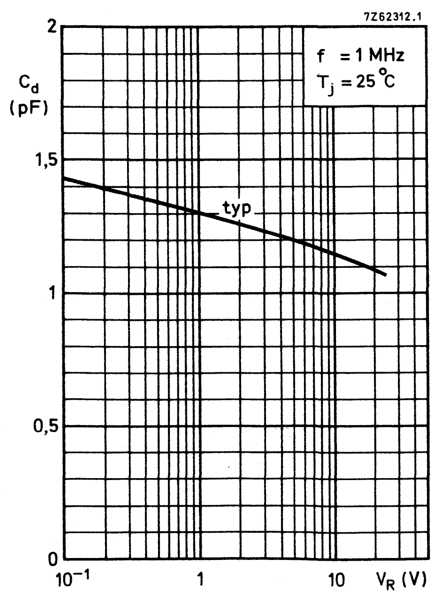


Fig. 13.

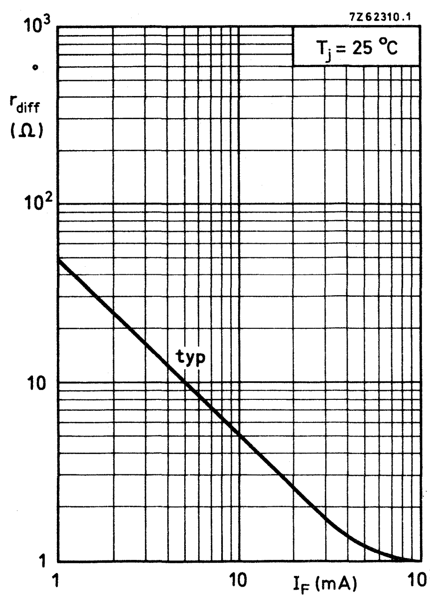


Fig. 14.

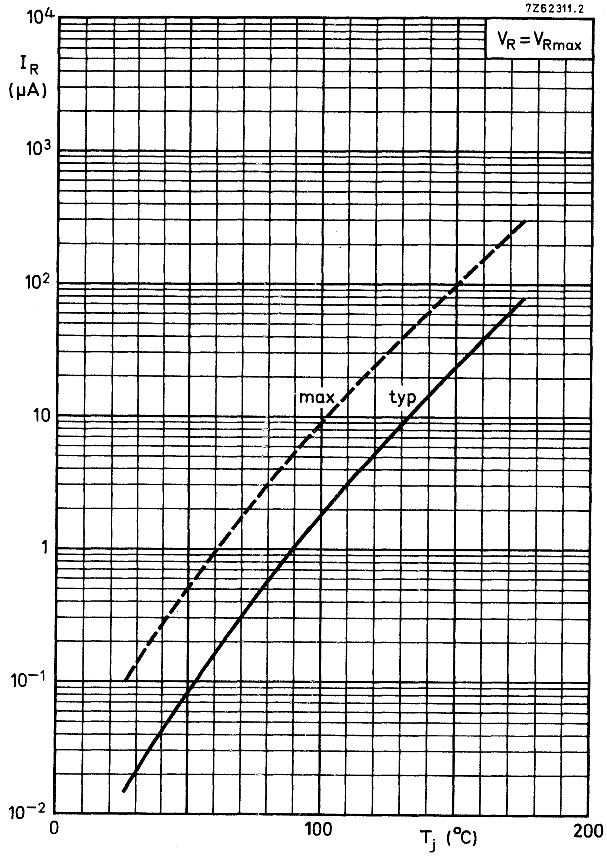

7Z62311.2
$V_R = V_{Rmax}$
I_R (μA)
10^4
10^3
10^2
10
1
10^{-1}
10^{-2}
max
typ
0
100
200
T_j (°C)

Fig. 15.

ULTRA HIGH-SPEED DIODE

Silicon planar epitaxial, ultra-high speed, high conductance diode in a SOD-80 envelope.

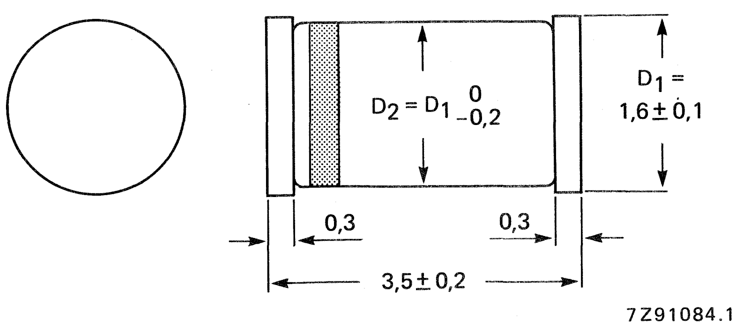
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	60	V
Repetitive peak reverse voltage	V_{RRM}	max.	60	V
Repetitive peak forward current	I_{FRM}	max.	600	mA
Junction temperature	T_j	max.	200	°C
Forward voltage at I_F = 200 mA	V_F	<	1,0	V
Reverse recovery time when switched from I_F = 400 mA to I_R = 400 mA; R_L = 100 Ω; measured at I_R = 40 mA	t_{rr}	<	6	ns
Recovery charge when switched from I_F = 10 mA to V_R = 5 V; R_L = 500 Ω	Q_s	<	50	pC

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



A green band indicates the cathode side and identifies the type BAV105.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	60	V
Repetitive peak reverse voltage	V_{RRM}	max.	60	V
Average rectified forward current	$I_{F(AV)}$	max.	300	mA
Forward current	I_F	max.	300	mA
Repetitive peak forward current	I_{FRM}	max.	600	mA
Non-repetitive peak forward current				
t = 1 μs	I_{FSM}	max.	4000	mA
t = 1 s		max.	1000	mA
Storage temperature	T_{stg}	−65 to + 175		^{o}C
Junction temperature	T_j	max.	175	^{o}C

THERMAL RESISTANCE

From junction to ambient	$R_{th\ j\text{-}a}$	375	K/W

CHARACTERISTICS

T_j = 25 ^{o}C unless otherwise specified

Forward voltage				
I_F = 10 mA	V_F	<	0,75	V
I_F = 200 mA		<	1,00	V
I_F = 200 mA; T_j = 100 ^{o}C	V_F	<	0,95	V
I_F = 500 mA		<	1,25	V
Reverse current				
V_R = 60 V	I_R	<	100	nA
V_R = 60 V; T_j = 100 ^{o}C		<	100	μA
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	2,5	pF
Forward recovery voltage when switched to				
I_F = 400 mA; t_r1 = 30 ns	V_{fr}	<	2,0	V
I_F = 400 mA; t_r2 = 100 ns		<	1,5	V
(see Fig. 2)				

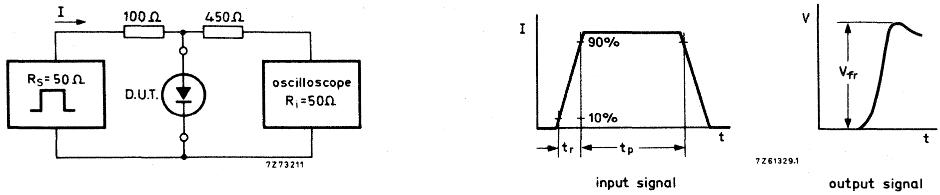
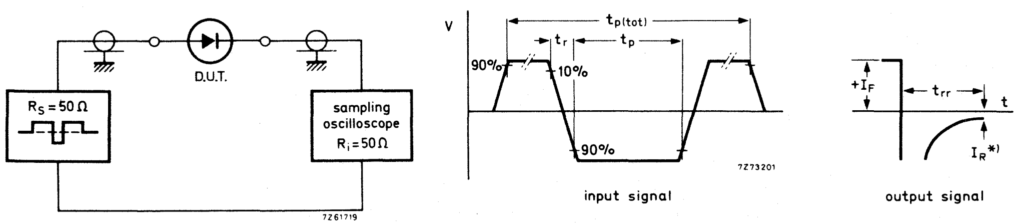


Fig. 2 Test circuit and waveforms; forward recovery voltage.

Input signal:	1st rise time of the forward pulse	t_r1	= 30 ns
	2nd rise time of the forward pulse	t_r2	= 100 ns
	Forward current pulse duration	t_p	= 300 ns
	Duty factor	δ	= 0,01
Oscilloscope:	Rise time	t_r	= 0,35 ns
	Input capacitance	C_i	= 1 pF

Circuit capacitance C ⩽ 20 pF (C = C_i + parasitic capacitance)

Reverse recovery time when switched
from I_F = 400 mA to I_R = 400 mA;
R_L = 100 Ω; measured at I_R = 40 mA — t_{rr} < 6 ns
(see Fig. 3)



*) I_R = 40 mA

Fig. 3 Test circuit and waveforms; reverse recovery time.

Input signal:	Total pulse duration	$t_{p(tot)}$	= 0,2 μs
	Duty factor	δ	= 0,0025
	Rise time of the reverse pulse	t_r	= 0,6 ns
	Reverse pulse duration	t_p	= 30 ns
Oscilloscope:	Rise time	t_r	= 0,35 ns

Circuit capacitance C ⩽ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

Recovery charge when switched from
I_F = 10 mA to V_R = 5 V; R_L = 500 Ω (see Fig. 4) Q_s < 50 pC

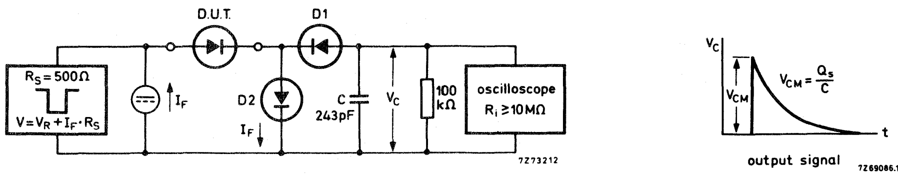


Fig. 4 Test circuit and waveform; recovery charge.

D1 = BAW62
D2 = diode with minority carrier life time at 10 mA: < 200 ps

Input signal:	Rise time of the reverse pulse	t_r	= 2 ns
	Reverse pulse duration	t_p	= 400 ns
	Duty factor	δ	= 0,02

Circuit capacitance C ≤ 7 pF (C = oscilloscope input capacitance + parasitic capacitance)

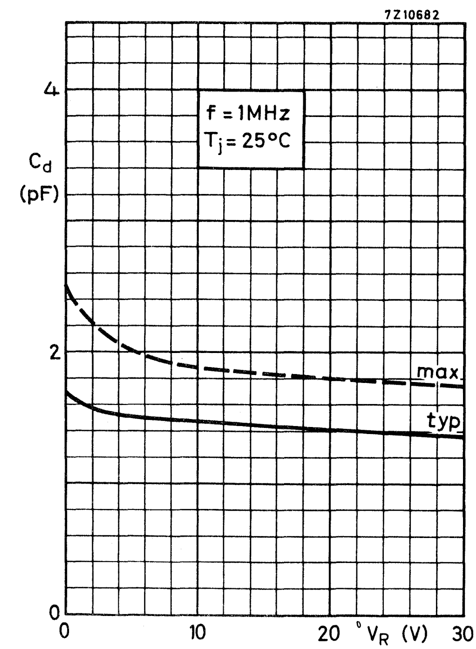


Fig. 5.

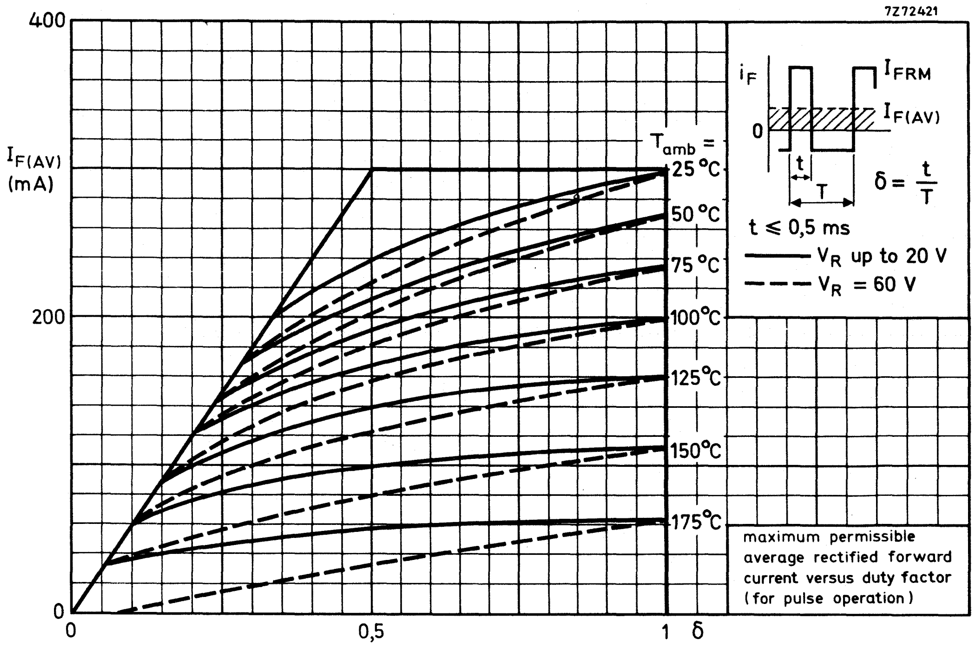

7Z72421
400
200
0
$I_{F(AV)}$
(mA)
0
0,5
1 δ
T_{amb} =
25 °C
50 °C
75 °C
100 °C
125 °C
150 °C
175 °C
i_F
I_{FRM}
$I_{F(AV)}$
0
t
T
δ = t/T
t ≤ 0,5 ms
V_R up to 20 V
V_R = 60 V
maximum permissible average rectified forward current versus duty factor (for pulse operation)

Fig. 6.

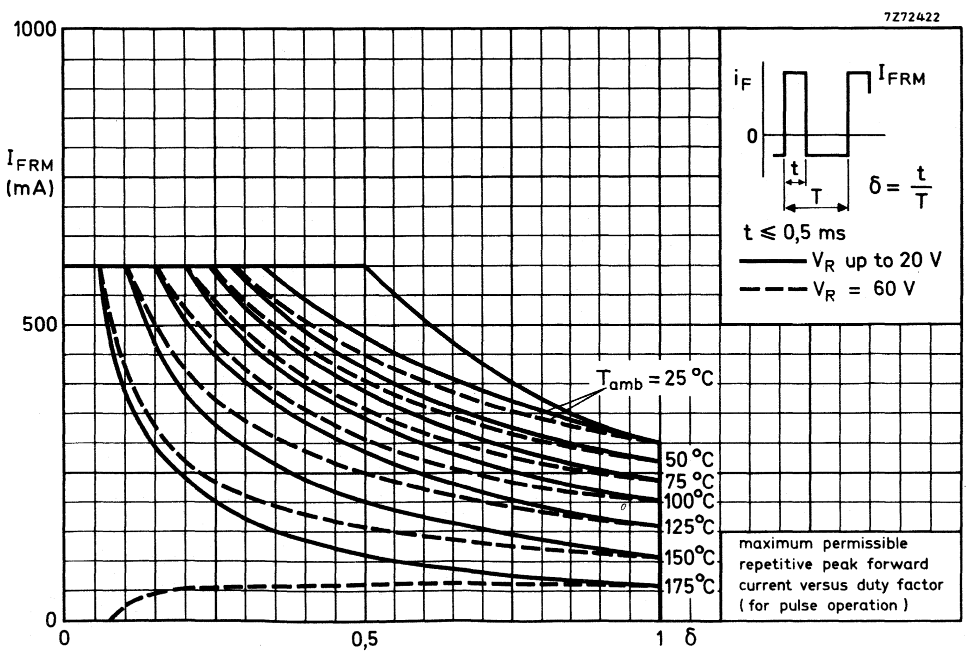

7Z72422
1000
500
0
I_{FRM}
(mA)
0
0,5
1 δ
T_{amb} = 25 °C
50 °C
75 °C
100 °C
125 °C
150 °C
175 °C
i_F
I_{FRM}
0
t
T
δ = t/T
t ≤ 0,5 ms
V_R up to 20 V
V_R = 60 V
maximum permissible repetitive peak forward current versus duty factor (for pulse operation)

Fig. 7.

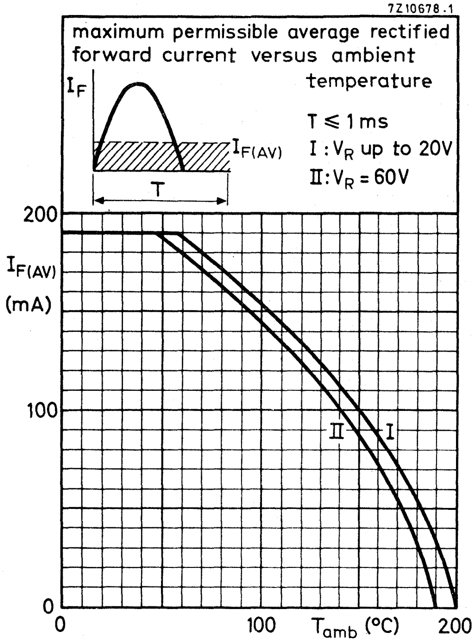


Fig. 8.

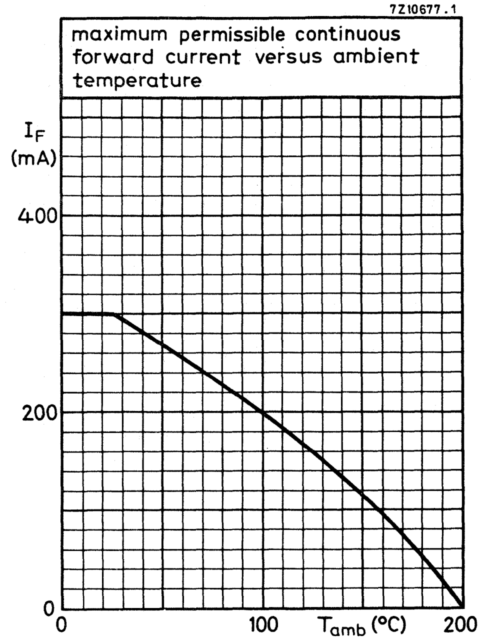


Fig. 9.

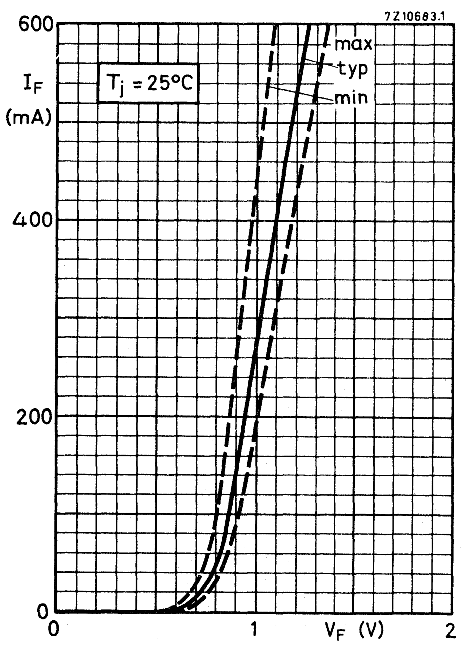


Fig. 10.

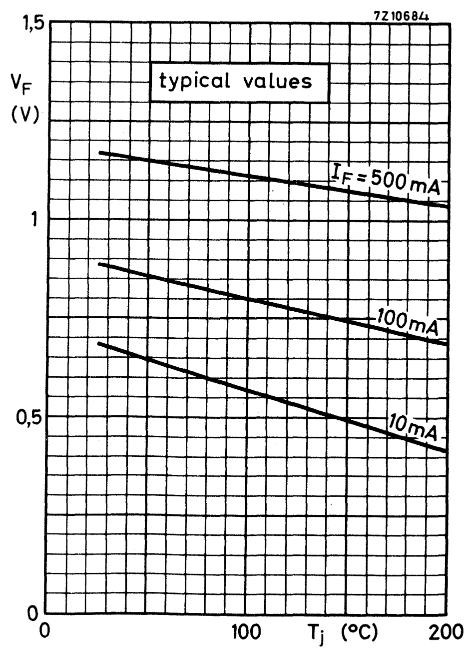


Fig. 11.

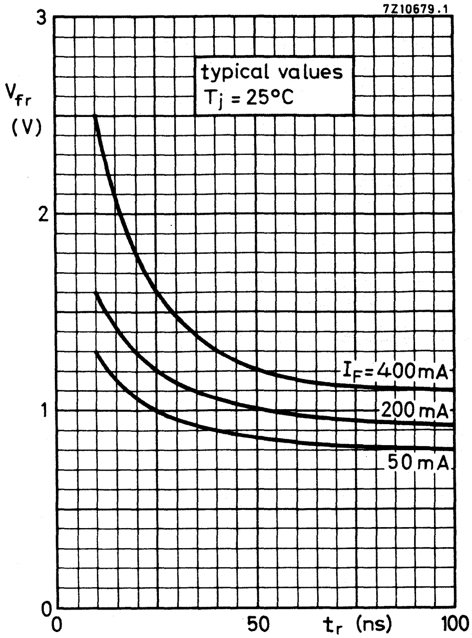


Fig. 12.

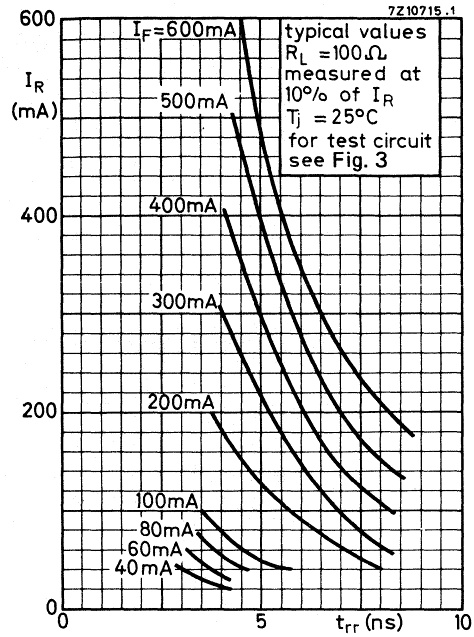


Fig. 13.

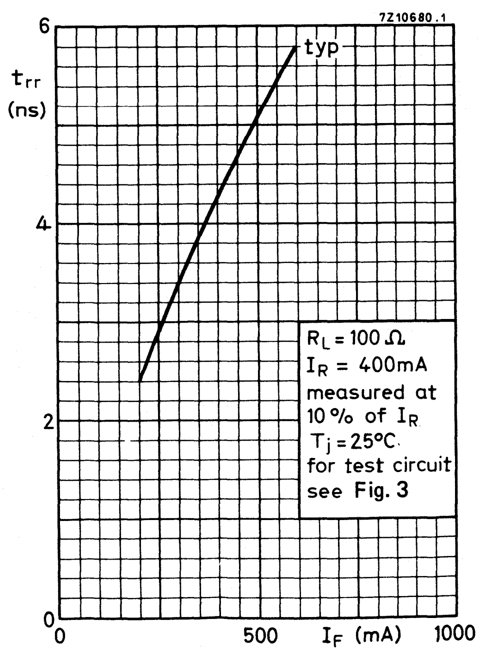


Fig. 14.

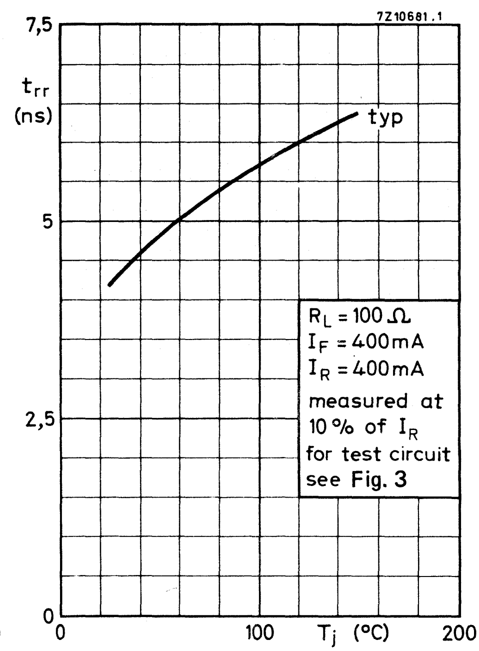


Fig. 15.

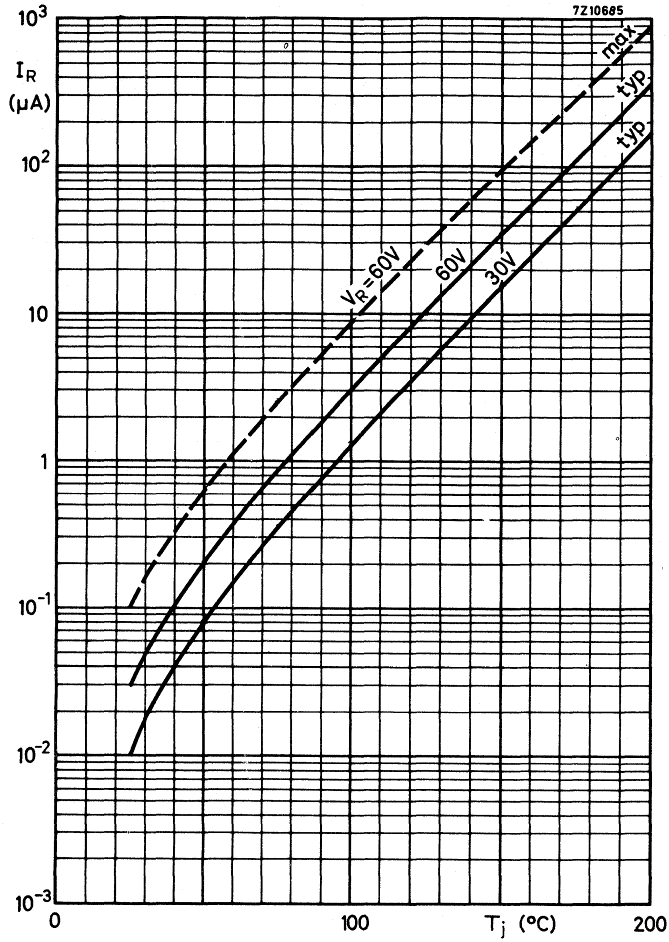

7Z10685
I_R
(μA)
10^3
10^2
10
1
10^{-1}
10^{-2}
10^{-3}
0
100
T_j (°C)
200
V_R=60V
60V
30V
max
typ
typ

Fig. 16.

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODES

The BAW56 consists of two diodes in a microminiature plastic envelope. The anodes are commoned and the unit is intended for high-speed switching in thick and thin-film circuits.

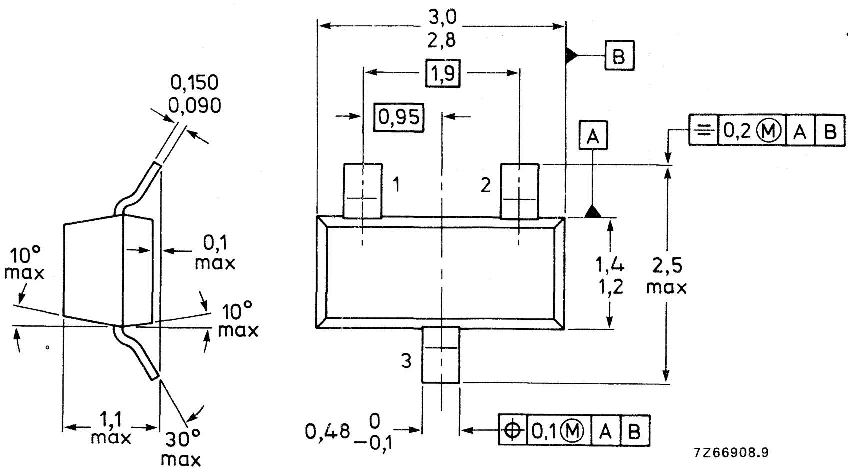
QUICK REFERENCE DATA (per diode)

Continuous reverse voltage	V_R	max.	70	V
Repetitive peak reverse voltage	V_{RRM}	max.	70	V
Repetitive peak forward current	I_{FRM}	max.	215	mA ←
Junction temperature	T_j	max.	150	°C ←
Forward voltage at I_F = 50 mA	V_F	<	1,0	V
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	6	ns
Recovery charge when switched from I_F = 10 mA to V_R = 5 V; R_L = 500 Ω	Q_s	<	45	pC

MECHANICAL DATA

Dimensions in mm

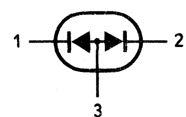
Fig. 1 SOT-23.



TOP VIEW

Marking code

BAW56 = A1



See also *Soldering recommendations.*

RATINGS (per diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	70 V
Repetitive peak reverse voltage	V_{RRM}	max.	70 V
Average rectified forward current* (averaged over any 20 ms period)	$I_{F(AV)}$	max.	215 mA
Forward current (DC)	I_F	max.	215 mA
→ Repetitive peak forward current	I_{FRM}	max.	215 mA
Non-repetitive peak forward current (per crystal)			
t = 1 μs	I_{FSM}	max.	2 A
t = 1 ms	I_{FSM}	max.	1 A
t = 1 s	I_{FSM}	max.	0,5 A
→ Storage temperature range	T_{stg}		−65 to + 150 °C
→ Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE**

From junction to ambient**	$R_{th\ j\text{-}t}$	=	430 K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	2 x 280 K/W
From soldering points to ambient ▲	$R_{th\ s\text{-}a}$	=	2 x 90 K/W

CHARACTERISTICS (per diode)

T_j = 25 °C unless otherwise specified

Forward voltage			
I_F = 1 mA	V_F	<	715 mV
I_F = 10 mA	V_F	<	855 mV
I_F = 50 mA	V_F	<	1000 mV
I_F = 150 mA	V_F	<	1250 mV
Reverse current			
V_R = 25 V; T_j = 150 °C	I_R	<	30 μA
V_R = 70 V	I_R	<	2,5 μA
V_R = 70 V; T_j = 150 °C	I_R	<	50 μA
Diode capacitance			
V_R = 0; f = 1 MHz	C_d	<	2 pF
Forward recovery voltage when switched to I_F = 10 mA; t_r = 20 ns see Fig. 2	V_{fr}	<	1,75 V

* Measured under pulse conditions: pulse time $t_p \leq$ 0,5 ms.
For sinusoidal operation $I_{F(AV)}$ = 150 mA; averaging time $t_{(AV)} \leq$ 1 ms.

** See *Thermal characteristics.*

▲ Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

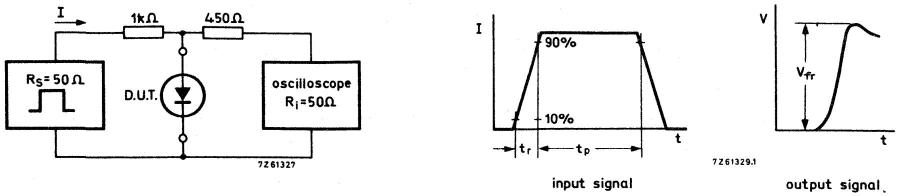


Fig. 2 Test circuit and waveforms; forward recovery voltage.

Input signal: Rise time of the forward pulse t_r = 20 ns
Forward current pulse duration t_p = 120 ns. Duty factor δ = 0,01
Oscilloscope: Rise time t_r = 0,35 ns.

Circuit capacitance $C \leqslant 1$ pF (C = oscilloscope input capacitance + parasitic capacitance)

Reverse recovery time when switched from
I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω;
measured at I_R = 1 mA see Fig. 3 t_{rr} < 6 ns

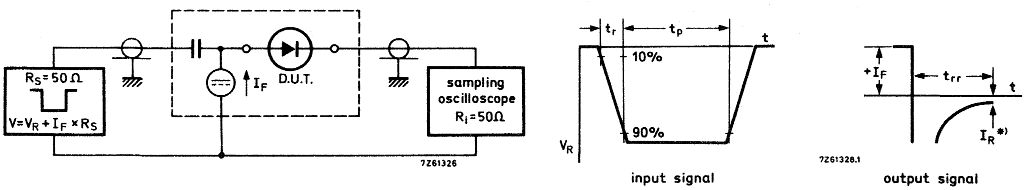


Fig. 3 Test circuit and waveforms; reverse recovery time.

*) I_R = 1 mA

Input signal: Rise time of the reverse pulse t_r = 0,6 ns
Reverse pulse duration t_p = 100 ns. Duty factor δ = 0,05.
Oscilloscope: Rise time t_r = 0,35 ns

Circuit capacitance $C \leqslant 1$ pF (C = oscilloscope input capacitance + parasitic capacitance)

Recovery charge when switched from
I_F = 10 mA to V_R = 5 V; R_L = 500 Ω see Fig. 4 Q_s < 45 pC

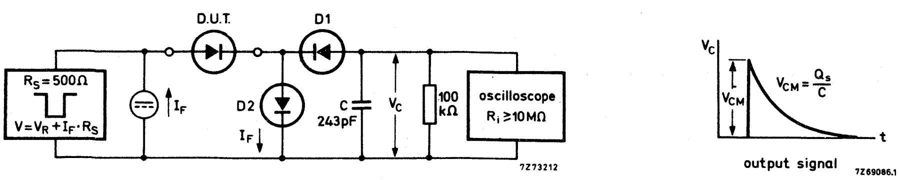


Fig. 4 Test circuit and waveform; recovery charge.

D2 = diode with minority carrier life time at 10 mA: < 200 ps. D1 = BAW62.

Input signal: Rise time of the reverse pulse t_r = 2 ns
Reverse pulse duration t_p = 400 ns. Duty factor δ = 0,02

Circuit capacitance $C \leqslant 7$ pF (C = oscilloscope input capacitance + parasitic capacitance).

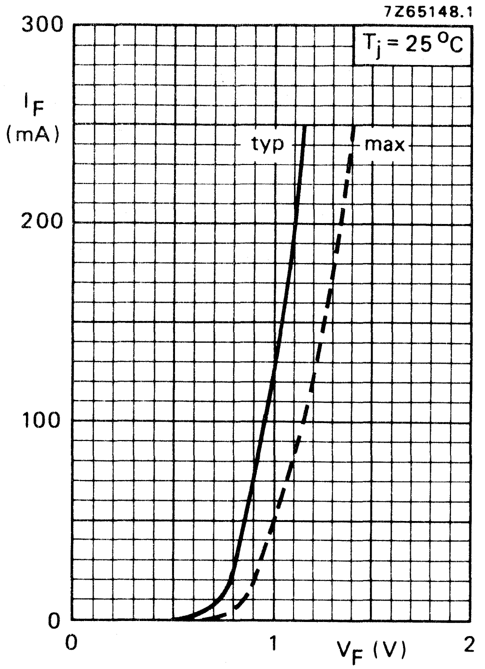


Fig. 5.

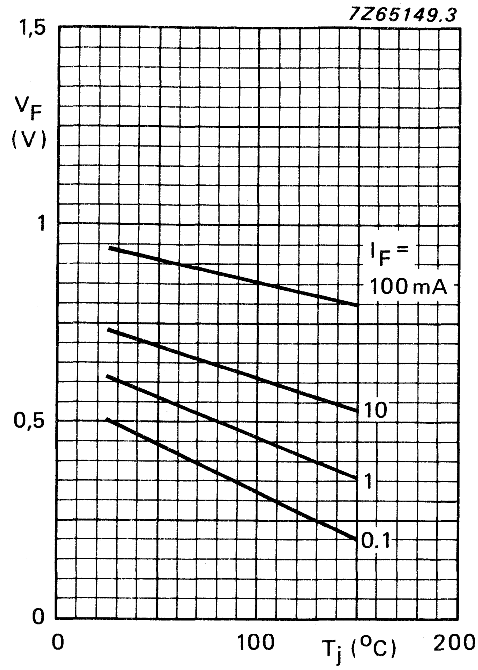


Fig. 6 Typical values.

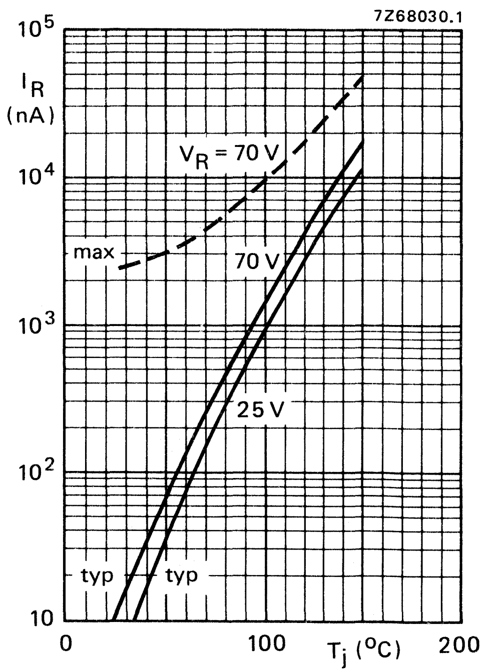


Fig. 7.

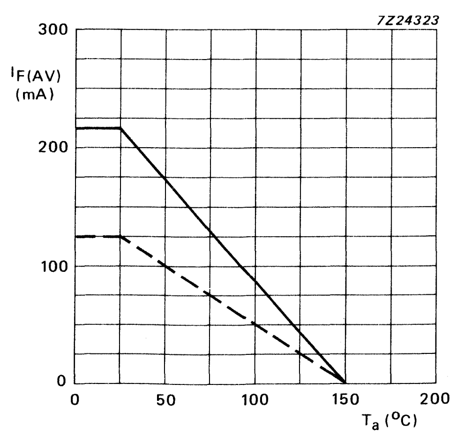


Fig. 8 ——— single diode;
– – – – double diode, equally loaded.

HIGH-SPEED SILICON DIODE

Planar epitaxial high-speed diode in a DO-35 envelope. The BAW62 is primarily intended for fast logic applications.

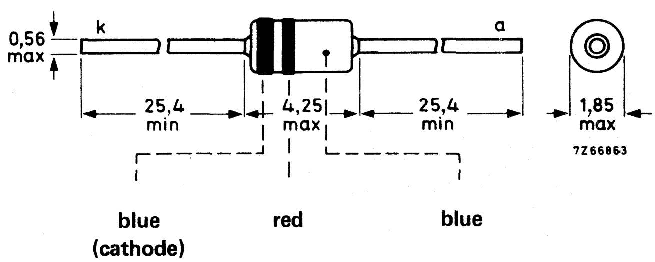
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	75	V
Repetitive peak reverse voltage	V_{RRM}	max.	75	V
Repetitive peak forward current	I_{FRM}	max.	450	mA
Junction temperature	T_j	max.	200	°C
Forward voltage at I_F = 100 mA	V_F	<	1	V
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	4	ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-27 (DO-35).



Diodes may be either type-branded or colour-coded.

Products, approved to CECC 50 001-021, available on request.

RATINGS Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	75	V	
Repetitive peak reverse voltage	V_{RRM}	max.	75	V	1)
Average rectified forward current	$I_{F(AV)}$	max.	150	mA	2)
Forward current (d.c.)	I_F	max.	200	mA	
Repetitive peak forward current	I_{FRM}	max.	450	mA	
Non-repetitive peak forward current; t = 1 µs	I_{FSM}	max.	2000	mA	
t = 1 s	I_{FSM}	max.	500	mA	
Storage temperature	T_{stg}		−65 to +200	°C	
Junction temperature	T_j	max.	200	°C	

THERMAL RESISTANCE

From junction to ambient in free air at maximum lead length	$R_{th\ j\text{-}a}$	=	0,6	K/mW

CHARACTERISTICS $T_j = 25\ ^oC$ unless otherwise specified

Forward voltages				
$I_F = 5$ mA	V_F		0,62 to 0,75	V
$I_F = 100$ mA	V_F	<	1,00	V
$I_F = 100$ mA; $T_j = 100\ ^oC$	V_F	<	0,93	V
Reverse currents				
$V_R = 20$ V	I_R	<	25	nA
$V_R = 20$ V; $T_j = 150\ ^oC$	I_R	<	50	µA
$V_R = 50$ V	I_R	<	200	nA
$V_R = 75$ V	I_R	<	5	µA
$V_R = 75$ V; $T_j = 150\ ^oC$	I_R	<	100	µA
Diode capacitance				
$V_R = 0$; f = 1 MHz	C_d	<	2	pF

1) Measured at zero life time at $I_R = 100$ µA; $V_R > 100$ V.

2) For pulse operation see Figs 5 and 6. For sinusoidal operation see Figs7 to 10.

CHARACTERISTICS (continued) $T_j = 25\ ^oC$

Forward recovery voltage when switched to $I_F = 50$ mA; $t_r = 20$ ns	V_{fr}	<	2,5	V

Test circuit and waveforms:

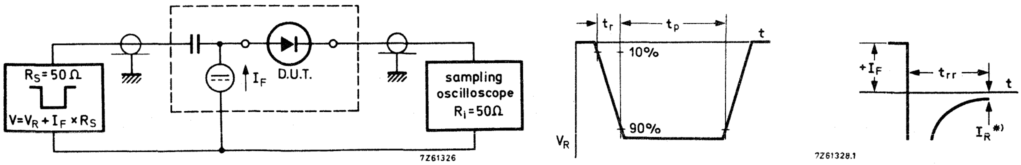


Fig. 3.

Input signal :	Rise time of the forward pulse	t_r	=	20 ns
	Forward current pulse duration	t_p	=	120 ns
	Duty factor	δ	=	0,01
Oscilloscope :	Rise time	t_r	=	0,35 ns

Circuit capacitance $C \leq 1$ pF (C = oscilloscope input capacitance + parasitic capacitance)

Reverse recovery time when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100\ \Omega$; measured at $I_R = 1$ mA	t_{rr}	<	4	ns

Test circuit and waveforms:

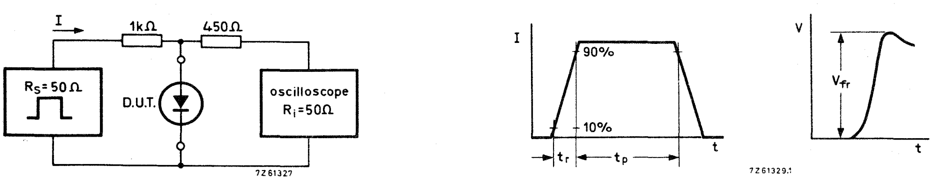


Fig. 2.

Input signal :	Rise time of the reverse pulse	t_r	=	0,6 ns	*) $I_R = 1$ mA
	Reverse pulse duration	t_p	=	100 ns	
	Duty factor	δ	=	0,05	
Oscilloscope:	Rise time	t_r	=	0,35 ns	

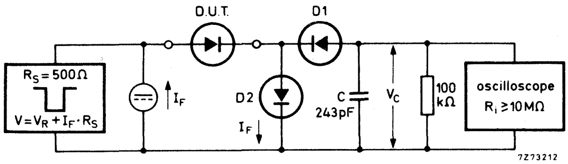
Circuit capacitance $C \leq 1$ pF (C = oscilloscope input capacitance + parasitic capacitance)

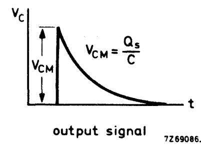
CHARACTERISTICS (continued) $T_j = 25\ ^oC$

Recovery charge when switched from

$I_F = 10$ mA to $V_R = 5$ V; $R_L = 500\ \Omega$ Q_s typ. 50 pC

Test circuit and waveform:





D1 = D2 = BAW62

Fig. 4.

Input signal :	Rise time of the reverse pulse	t_r	=	2 ns
	Reverse pulse duration	t_p	=	400 ns
	Duty factor	δ	=	0, 02

Circuit capacitance C ≤ 7 pF (C = oscilloscope input capacitance + parasitic capacitance)

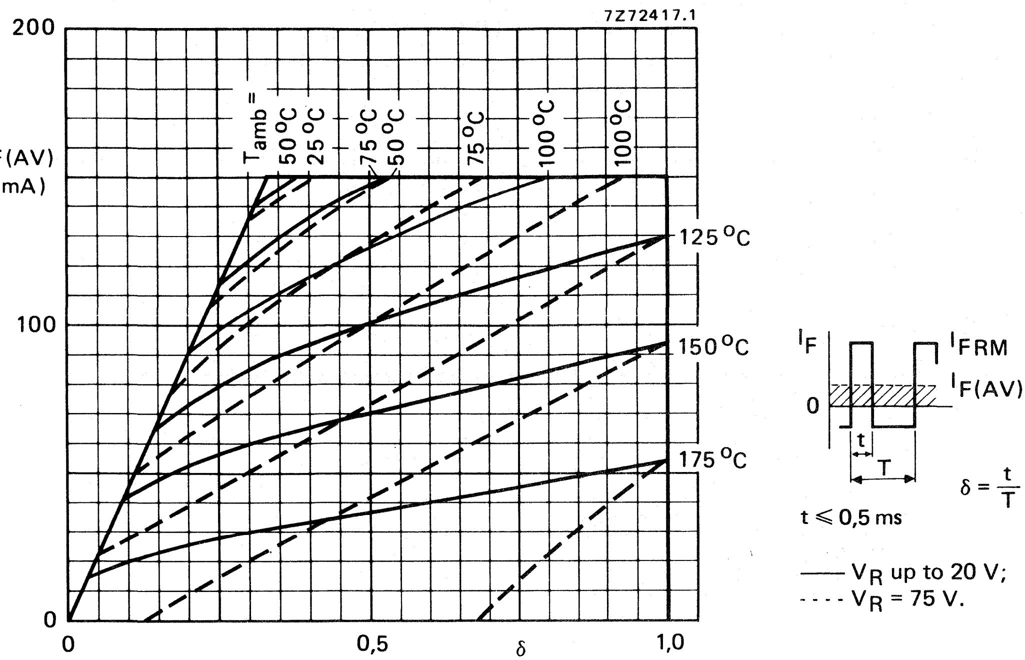


Fig. 5 Maximum permissible average rectified forward current as a function of the duty factor (pulse operated).

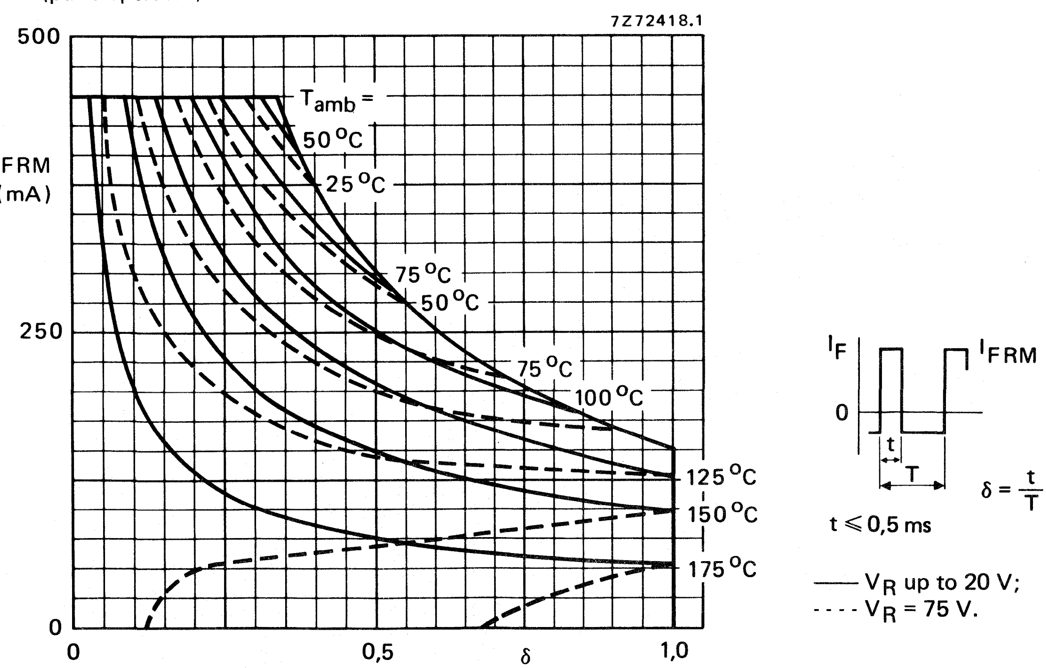


Fig. 6 Maximum permissible repetitive peak forward current as a function of the duty factor (pulse operated).

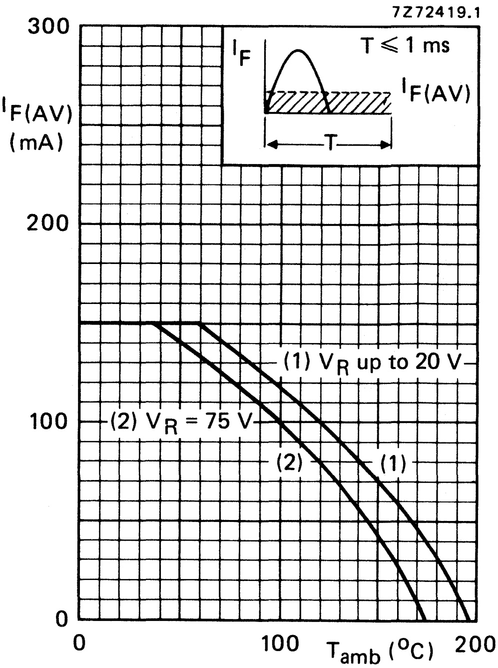


Fig. 7 Maximum permissible average rectified forward current.

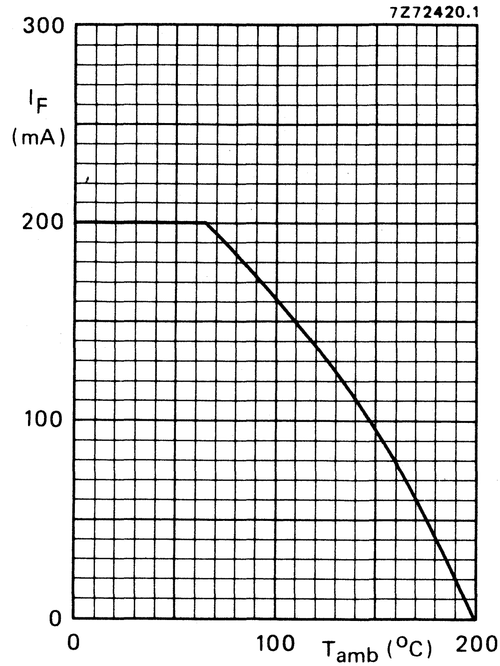


Fig. 8 Maximum permissible continuous forward current.

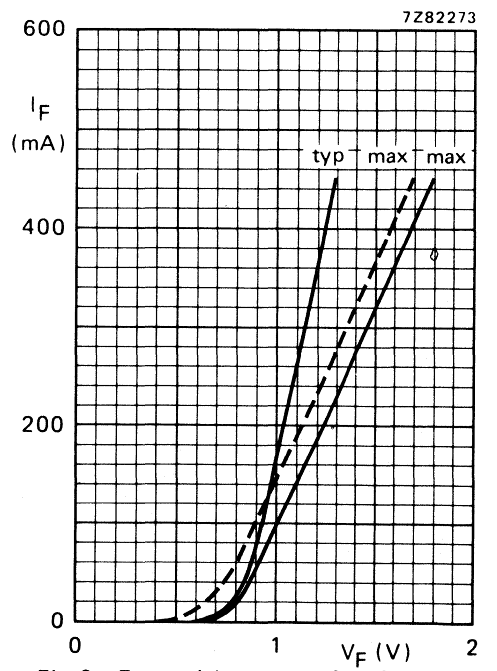


Fig. 9 Forward current as a function forward voltage. —— T_j = 25 °C; – – – T_j = 175 °C.

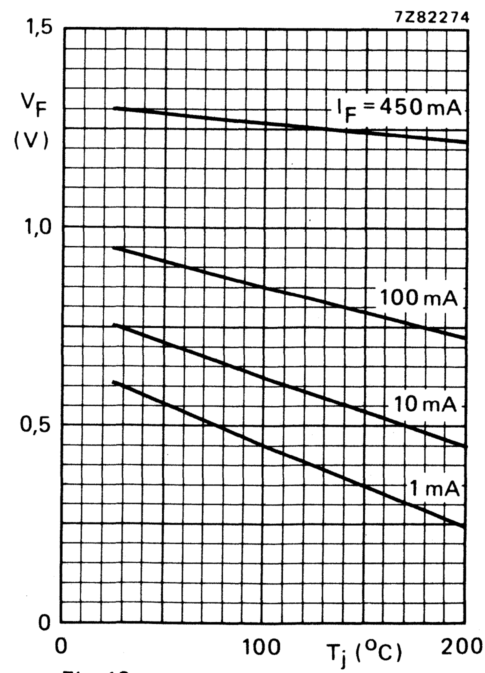
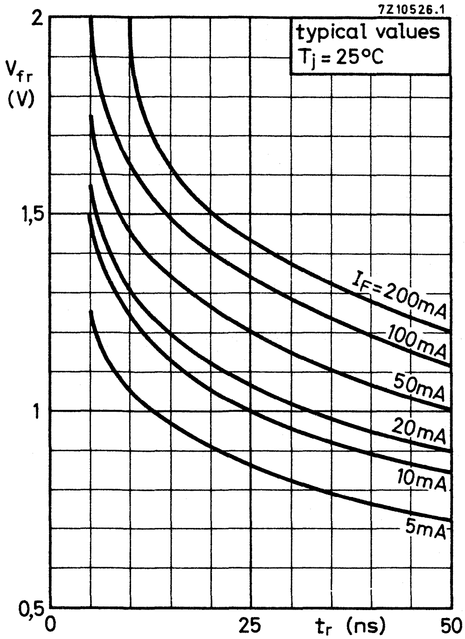
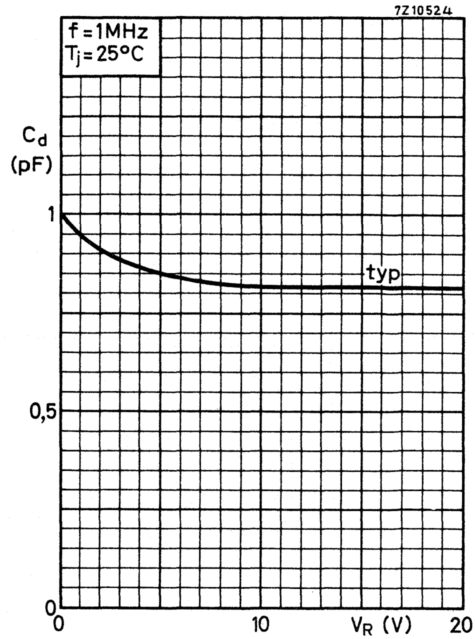
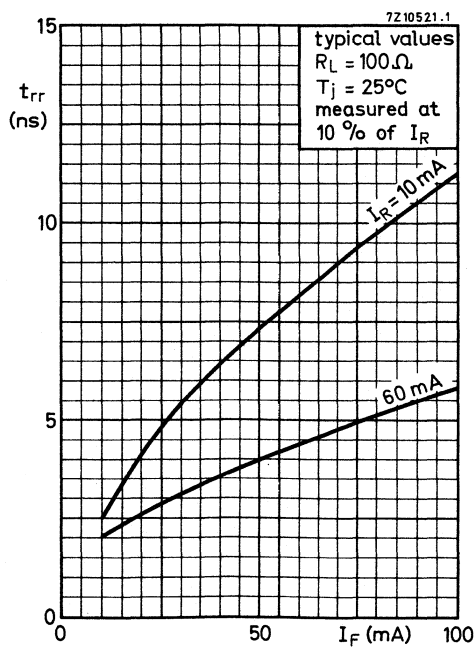
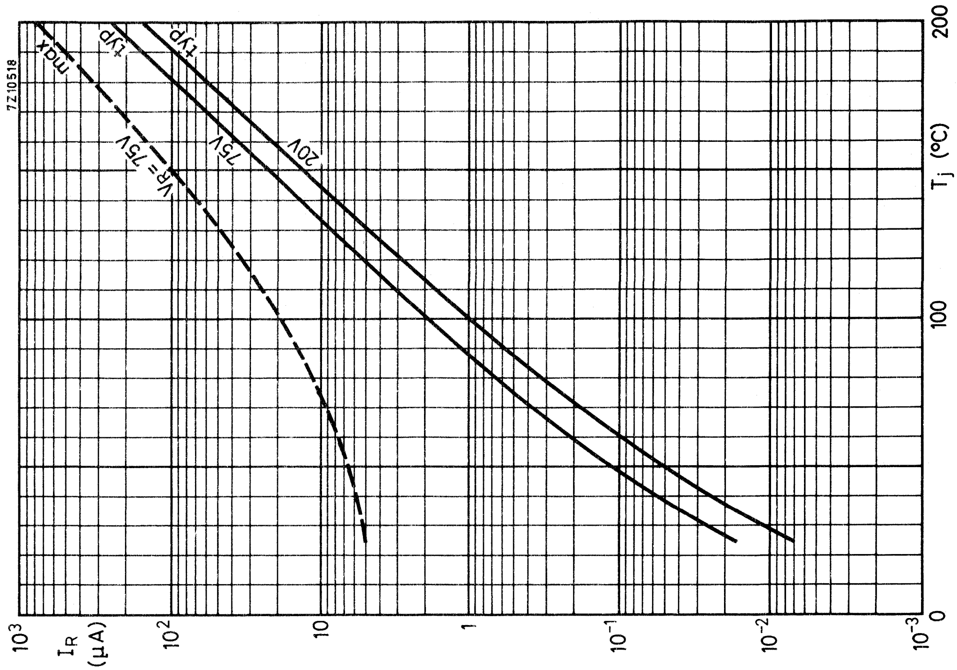


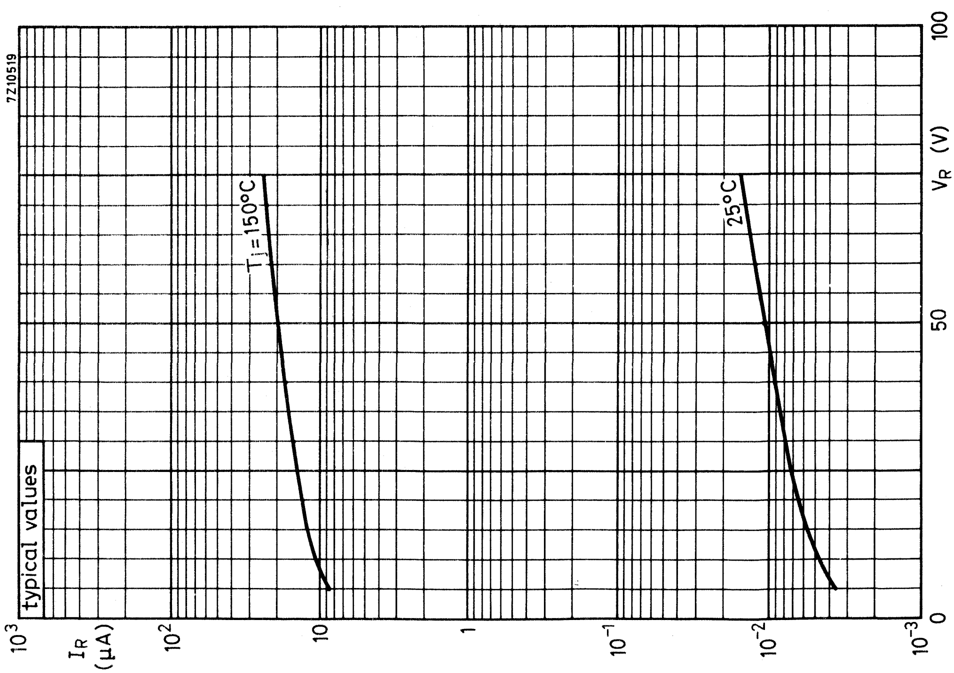
Fig. 10 Typical values forward voltage as a function of junction temperature.


7Z10526.1
typical values
T_j = 25°C
V_{fr} (V)
2
1,5
1
0,5
0
25
t_r (ns)
50
I_F=200mA
100mA
50mA
20mA
10mA
5mA


7Z10524
f = 1MHz
T_j = 25°C
C_d (pF)
1
0,5
0
10
V_R (V)
20
typ


7Z10521.1
typical values
R_L = 100 Ω
T_j = 25°C
measured at
10 % of I_R
t_{rr} (ns)
15
10
5
0
50
I_F (mA)
100
I_R=10 mA
60 mA


7Z10518
max
typ
typ
V_R = 75V
75V
20V
T_j (°C)
I_R (μA)


7Z10519
typical values
T_j = 150°C
25°C
V_R (V)
I_R (μA)

SILICON PLANAR EPITAXIAL CONTROLLED-AVALANCHE DIODE

A planar epitaxial diode in a DO-35 envelope, capable of absorbing transients repetitively. It is a fast, controlled avalanche diode, intended for switching inductive loads e.g. in semi-electronic telephone exchanges.

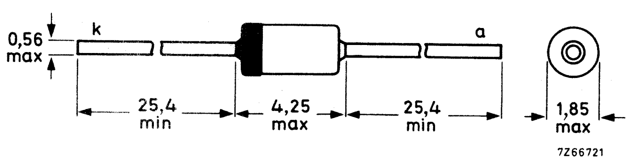
QUICK REFERENCE DATA

Repetitive peak forward current	I_{FRM}	max.	0,8	A
Repetitive peak reverse energy $t_p \geq 50\ \mu s$; $f \leq 20$ Hz; $T_j = 25\ ^oC$	E_{RRM}	max.	5,0	mJ
Thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$	=	0,38	K/mW
Forward voltage at $I_F = 200$ mA	V_F	<	1,00	V
Reverse avalanche breakdown voltage $I_R = 1$ mA	$V_{(BR)R}$		120 to 175	V
Reverse recovery time when switched from $I_F = 30$ mA to $I_R = 30$ mA; $R_L = 100\ \Omega$; measured at $I_R = 3$ mA	t_{rr}	<	50	ns

MECHANICAL DATA

Fig. 1 SOD-27 (DO-35).

Dimensions in mm
Mark: BAX12



The cathode is indicated by a coloured band

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage*	V_R	max.	90	V
Average rectified forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	0,4	A
Forward current (d.c.)	I_F	max.	0,4	A
Repetitive peak forward current	I_{FRM}	max.	0,8	A
Non-repetitive peak forward current				
t = 1 μs; T_j = 25 °C prior to surge	I_{FSM}	max.	6,0	A
t = 1 s; T_j = 25 °C prior to surge	I_{FSM}	max.	1,5	A
Repetitive peak reverse current	I_{RRM}	max.	0,6	A
Repetitive peak reverse energy $t_p \geq 50$ μs; f ≤ 20 Hz; T_j = 25 °C	E_{RRM}	max.	5,0	mJ
Storage temperature	T_{stg}		−65 to +200	°C
Junction temperature	T_j	max.	200	°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0,38	K/mW
From junction to ambient in free air T_{lead} = 25 °C at 8 mm from the body	$R_{th\ j\text{-}a}$	=	0,30	K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage				
I_F = 10 mA	V_F	<	0,75	V
I_F = 50 mA	V_F	<	0,84	V
I_F = 100 mA	V_F	<	0,90	V
I_F = 200 mA	V_F	<	1,00	V
I_F = 400 mA	V_F	<	1,25	V
Reverse avalanche breakdown voltage I_R = 1 mA	$V_{(BR)R}$		120 to 175	V
Reverse current				
V_R = 90 V	I_R	<	100	nA
V_R = 90 V; T_j = 150 °C	I_R	<	100	μA
Diode capacitance V_R = 0; f = 1 MHz	C_d	typ.	15	pF
		<	35	pF

* It is allowed to exceed this value as described with fig. 4. Care should be taken not to exceed the I_{RRM} rating.

Reverse recovery time when switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω; measured at I_R = 3 mA	t_{rr}	$<$	50	ns

Test circuit and waveforms:

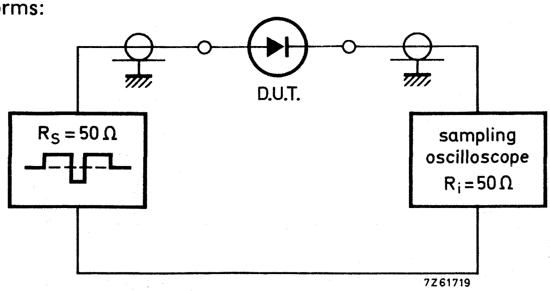


Fig. 2 Test circuit for t_{rr} measurement.

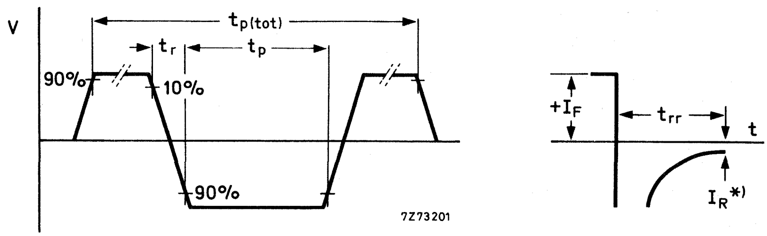


Fig. 3 Waveforms t_{rr} measurement.

*I_R = 3 mA.

Input signal:				
Total pulse duration	$t_{p(tot)}$	=	2	μs
Duty factor	δ	=	0,0025	
Rise time of the reverse pulse	t_r	=	0,6	ns
Reverse pulse duration	t_p	=	100	ns
Oscilloscope: Rise time	t_r	=	0,35	ns

Circuit capacitance C $\leqslant$ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

Reverse voltages higher than the V_R ratings are allowed, provided:

a. the transient energy ⩽ 7,5 mJ at P_{RRM} ⩽ 30 W; T_j = 25 °C
   the transient energy ⩽ 5 mJ at P_{RRM} = 120 W; T_j = 25 °C (see Fig. 8).

b. T ⩾ 50 ms; δ ⩽ 0,01 (rectangular waveform)
   δ ⩽ 0,02 (triangular waveform).

With increasing temperature, the maximum permissible transient energy must be decreased by 0,03 mJ/K.

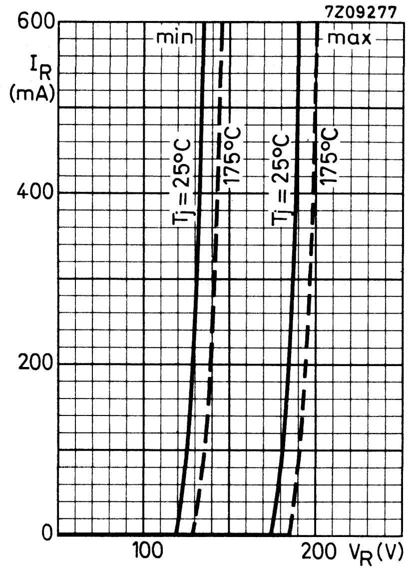


Fig. 4.

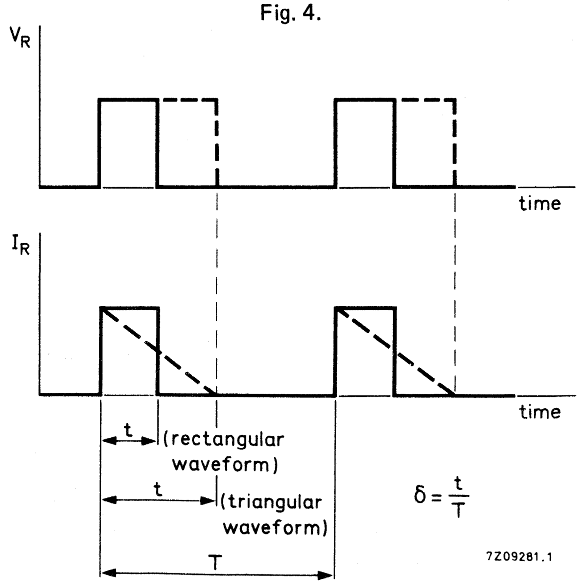


Fig. 5.

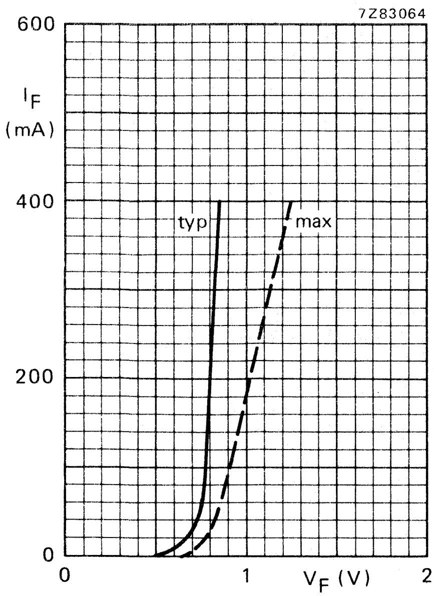


Fig. 6 I_F as a function of V_F at T_j = 25 °C.

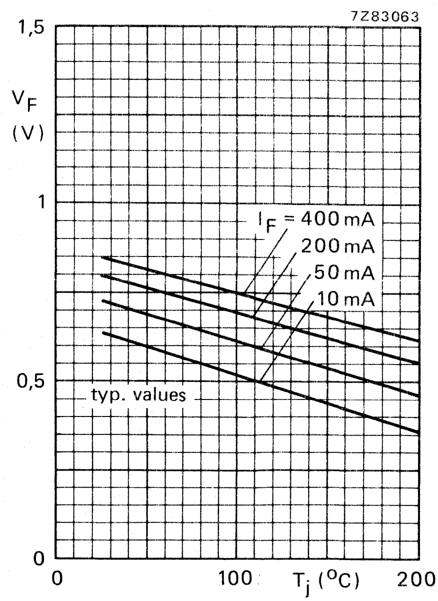


Fig. 7 V_F as a function of T_j.

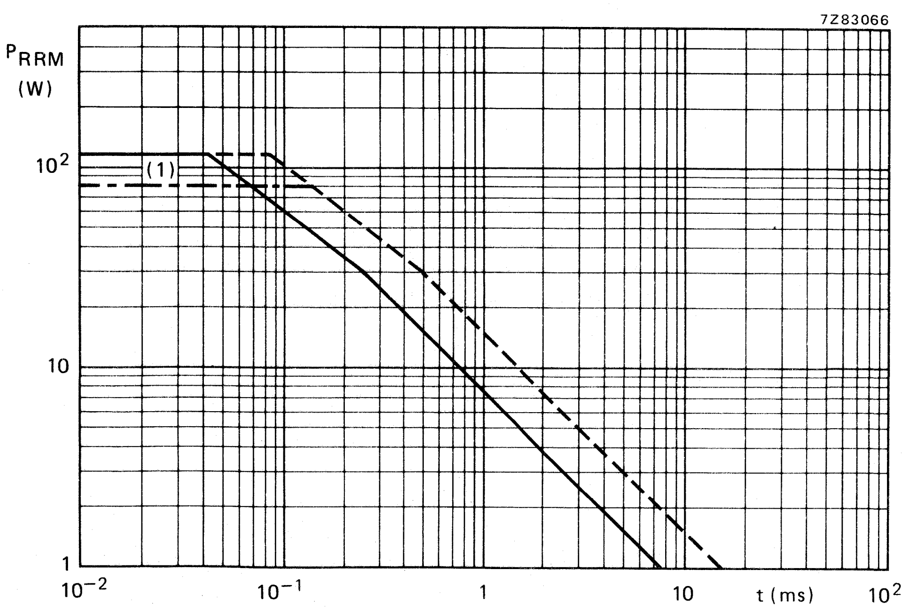


Fig. 8 Maximum permissible repetitive peak reverse power as a function of the pulse duration
T ⩾ 50 ms; T_j = 25 °C. ——— rectangular waveform; $\delta \leqslant 0{,}01$; – – – triangular waveform; $\delta \leqslant 0{,}02$.

(1) Limited by I_{RRM} = 600 mA.

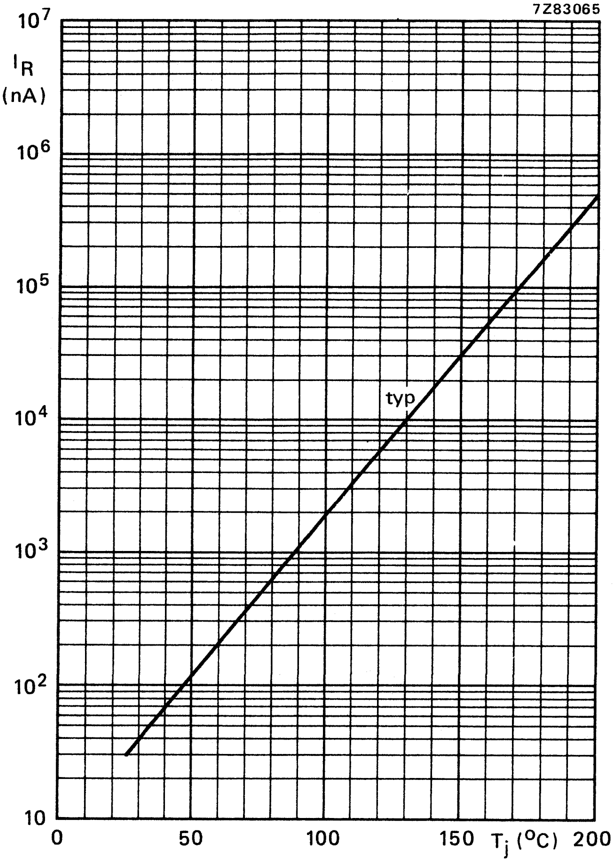


Fig. 9 Typical values reverse current as a function of junction temperature at $V_R = 90$ V.

GENERAL PURPOSE DIODE

General purpose diode in a DO-35 envelope intended for low-voltage switching and rectifier applications, but owing to its steep forward voltage curve also suitable for low-voltage stabilizing.

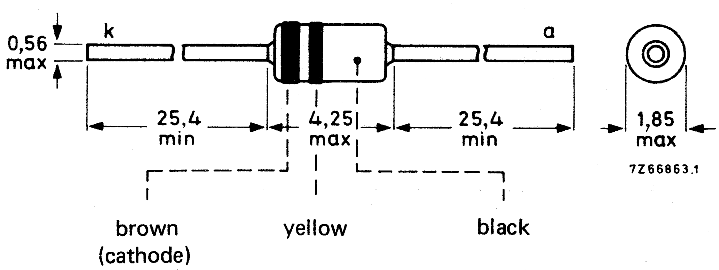
QUICK REFERENCE DATA

Repetitive peak reverse voltage	V_{RRM}	max.	40	V
Average forward current	$I_{F(AV)}$	max.	400	mA
Non-repetitive peak forward current	I_{FSM}	max.	6,0	A
Reverse recovery time when switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω; measured at I_R = 3 mA	t_{rr}	<	50	ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-27 (DO-35).



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Repetitive peak reverse voltage	V_{RRM}	max.	40 V
Continuous reverse voltage	V_R	max.	20 V
Forward current (d.c.)	I_F	max.	500 mA
Average forward current (averaged over any 20 ms period) see Fig. 6	$I_{F(AV)}$	max.	400 mA
Repetitive peak forward current	I_{FRM}	max.	2,0 A
Non-repetitive peak forward current (t = 10 ms; half sine-wave) T_j = 25 °C prior to surge	I_{FSM}	max.	6,0 A
Storage temperature	T_{stg}	−65 to +200	°C
Junction temperature	T_j	max.	200 °C

THERMAL RESISTANCE

From junction to ambient in free air			
at maximum lead length	$R_{th\ j\text{-}a}$	=	0,38 K/mW
at T_{lead} = 25 °C at 8 mm from the body	$R_{th\ j\text{-}a}$	=	0,30 K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage			
I_F = 1 mA	V_F	520 to	600 mV
I_F = 300 mA	V_F	750 to	1000 mV
I_F = 2000 mA; T_j = 150 °C	V_F	<	1500 mV
Reverse current			
V_R = 20 V	I_R	<	100 nA
V_R = 20 V; T_j = 150 °C	I_R	<	100 μA
Diode capacitance			
V_R = 0; f = 1 MHz	C_d	typ.	20 pF
		<	35 pF

Reverse recovery time when switched from
I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω;
measured at I_R = 3 mA — t_{rr} < 50 ns

Test circuit and waveforms:

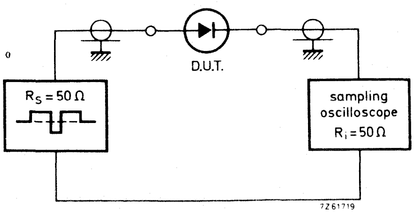


Fig. 2.

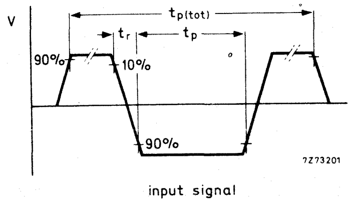


Fig. 3.

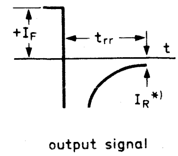


Fig. 4.

Input signal:	Total pulse duration	$t_{p(tot)}$	= 2	μs
	Duty factor	δ	= 0,0025	
	Rise time of the reverse pulse	t_r	= 0,6	ns
	Reverse pulse duration	t_p	= 100	ns
Oscilloscope:	Rise time	t_r	= 0,35	ns

* I_R = 3 mA.

Circuit capacitance C ⩽ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

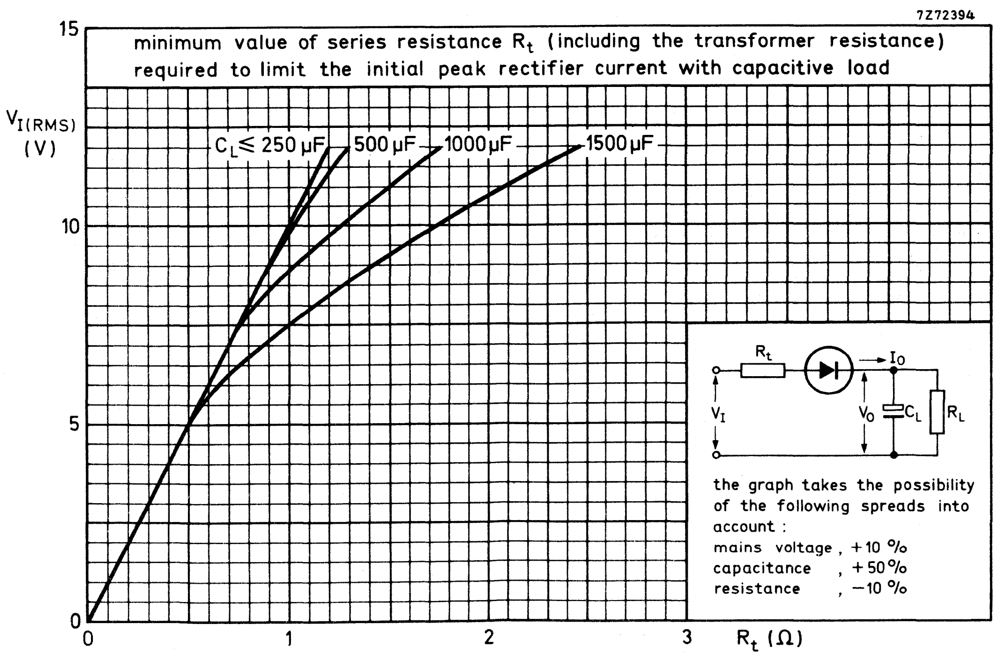


Fig. 5.

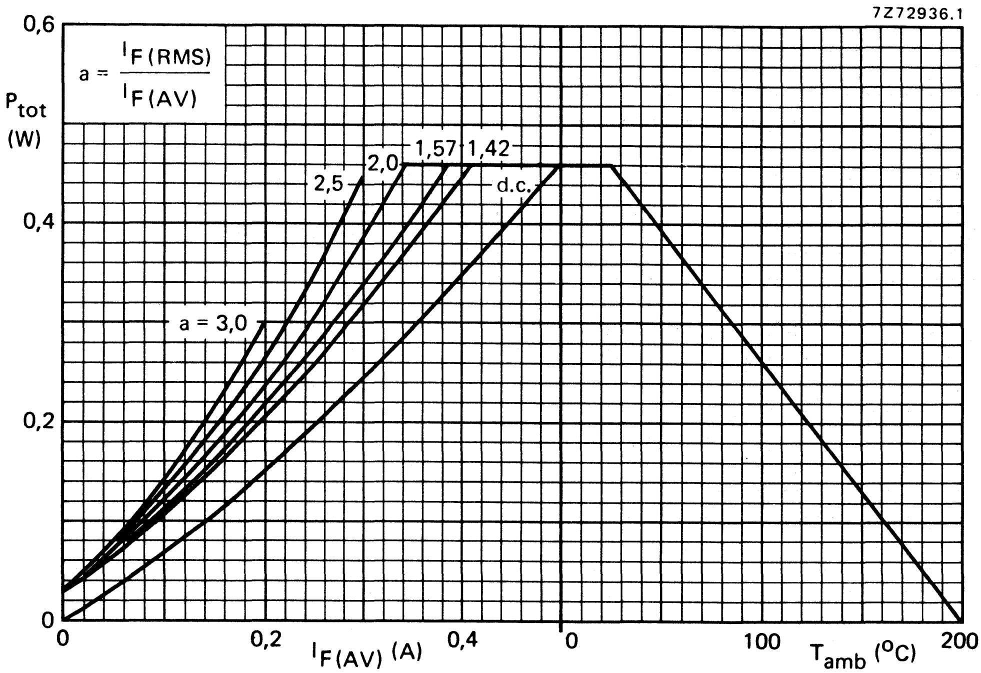


Fig. 6.

From the left-hand graph the total power dissipation can be found as a function of the average output current

The parameter $a = \frac{I_{F(RMS)} \text{ per diode}}{I_{F(AV)} \text{ per diode}}$ depends on $n\omega R_L C_L$ and $\frac{R_t + r_{diff}}{nR_L}$ and can be found from existing graphs.

For detailed explanation see Application Book: RECTIFIER DIODES.

Once the power dissipation is known, the maximum permissible ambient temperature follows from the right-hand graph.

For the series resistance, added to limit the initial peak rectifier current, the required minimum value can be found from Fig. 5.

The value of r_{diff} can be found from Fig. 9.

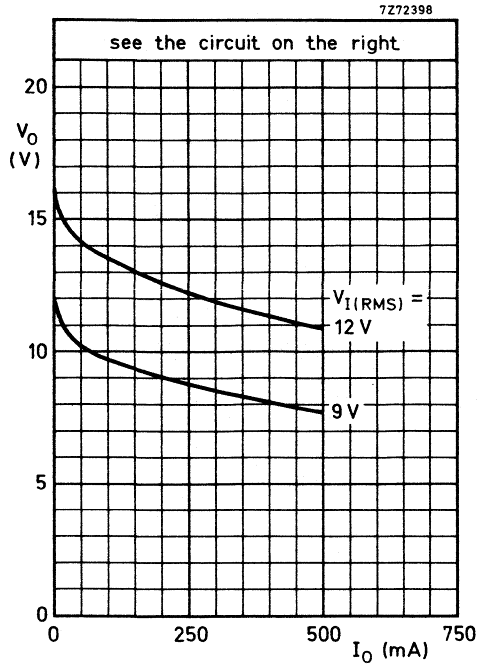


Fig. 7.

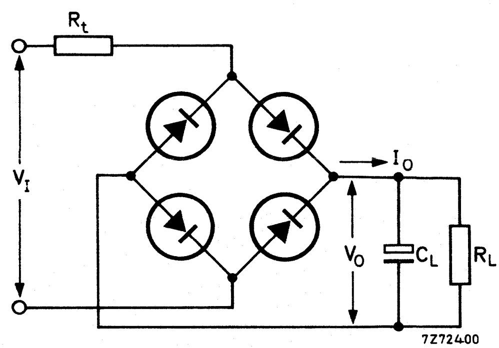


Fig. 8 Test circuit.

V_I (V)	R_t (Ω)	C_L (μF)
12	1,7	1000
9	1,1	1000

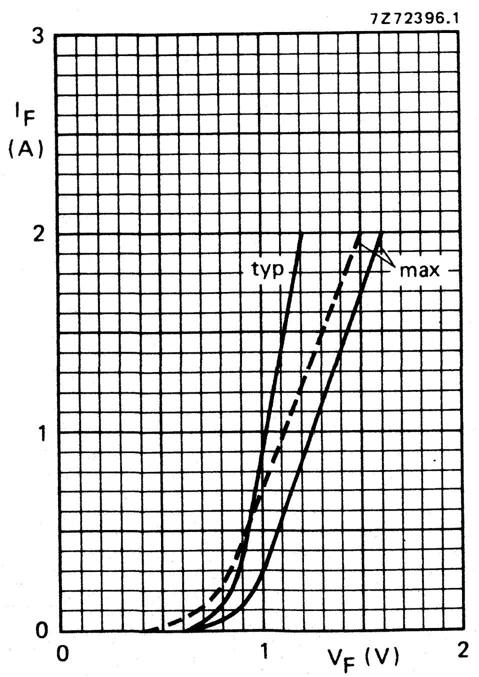


Fig. 9 Forward voltage as a function of the forward current.
—— T_j = 25 °C; – – – T_j = 150 °C.

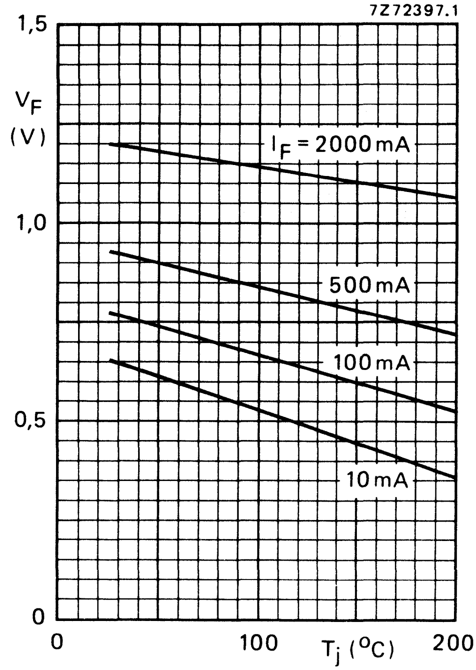


Fig. 10 Typical values forward voltage as a function of junction temperature.

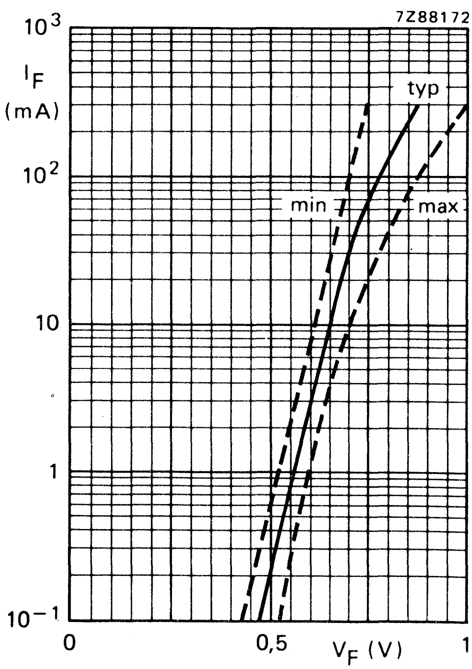


Fig. 11 Forward voltage as a function of the forward current. T_j = 25 °C.

GENERAL PURPOSE DIODE

General purpose diode in a DO-35 in envelope primarily intended for rectifier applications

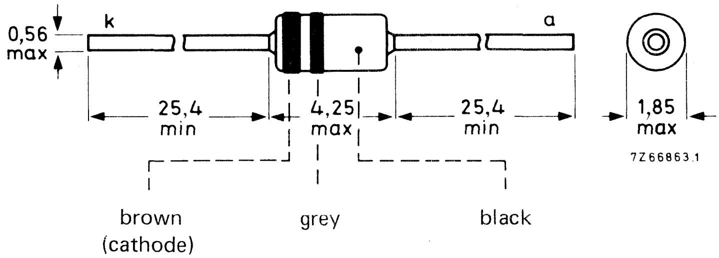
QUICK REFERENCE DATA

Repetitive peak reverse voltage	V_{RRM}	max.	75 V
Average forward current	$I_{F(AV)}$	max.	400 mA
Non-repetitive peak forward current	I_{FSM}	max.	6,0 A

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-27 (DO-35).



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Repetitive peak reverse voltage	V_{RRM}	max.	75	V
Continuous reverse voltage	V_R	max.	75	V
Forward current (d.c.)	I_F	max.	500	mA
Average forward current (averaged over any 20 ms period) see Fig. 2	$I_{F(AV)}$	max.	400	mA
Repetitive peak forward current	I_{FRM}	max.	2,0	A
Non-repetitive peak forward current (t = 10 ms; half sine-wave) T_j = 25 °C prior to surge	I_{FSM}	max.	6,0	A
Storage temperature	T_{stg}	−65 to +	200	°C
Junction temperature	T_j	max.	200	°C

THERMAL RESISTANCE

From junction to ambient in free air at maximum lead strength	$R_{th\ j\text{-}a}$	=	0,38	K/mW
at T_{lead} = 25 °C at 8 mm from the body	$R_{th\ j\text{-}a}$	=	0,30	K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage I_F = 2 A; T_j = 150 °C	V_F	<	1500	mV
Reverse current V_R = 75 V; T_j = 150 °C	I_R	<	100	μA
Diode capacitance V_R = 0; f = 1 MHz	C_d	typ.	20	pF
		<	35	pF

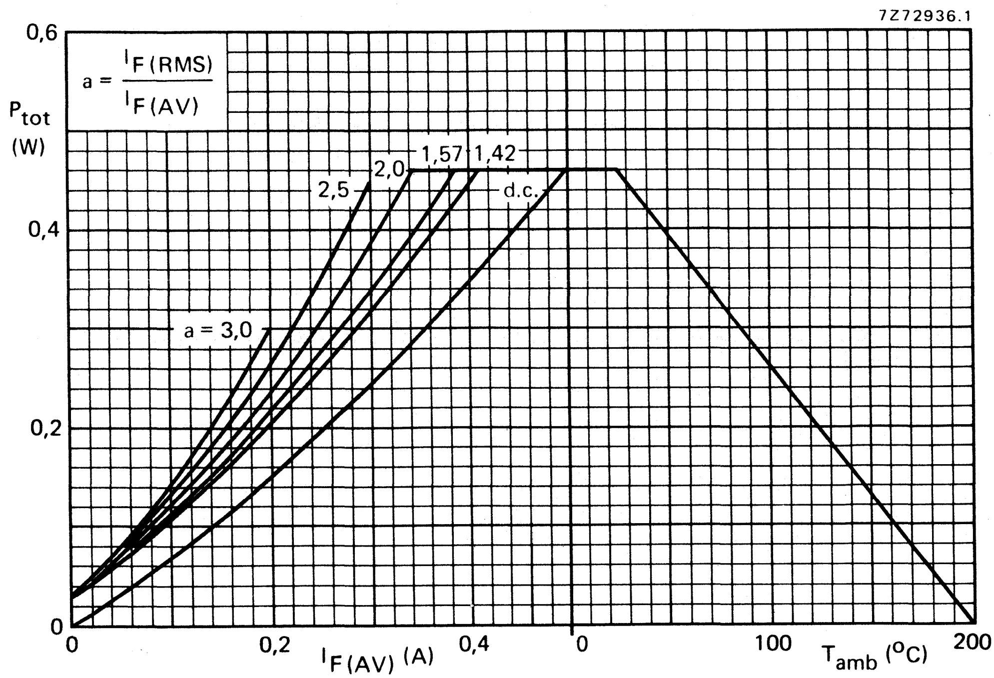


Fig. 2.

From the left-hand graph the total power dissipation can be found as a function of the average output current

The parameter $a = \frac{I_{F(RMS)} \text{ per diode}}{I_{F(AV)} \text{ per diode}}$ depends on $n\omega R_L C_L$ and $\frac{R_t + r_{diff}}{nR_L}$ and can be found from existing graphs.

For detailed explanation see Application Book: RECTIFIER DIODES.

Once the power dissipation is known, the maximum permissible ambient temperature follows from the right-hand graph.
For the series resistance, added to limit the initial peak rectifier current, the required minimum value can be found from Fig. 3.
The value of r_{diff} can be found from Fig. 6.

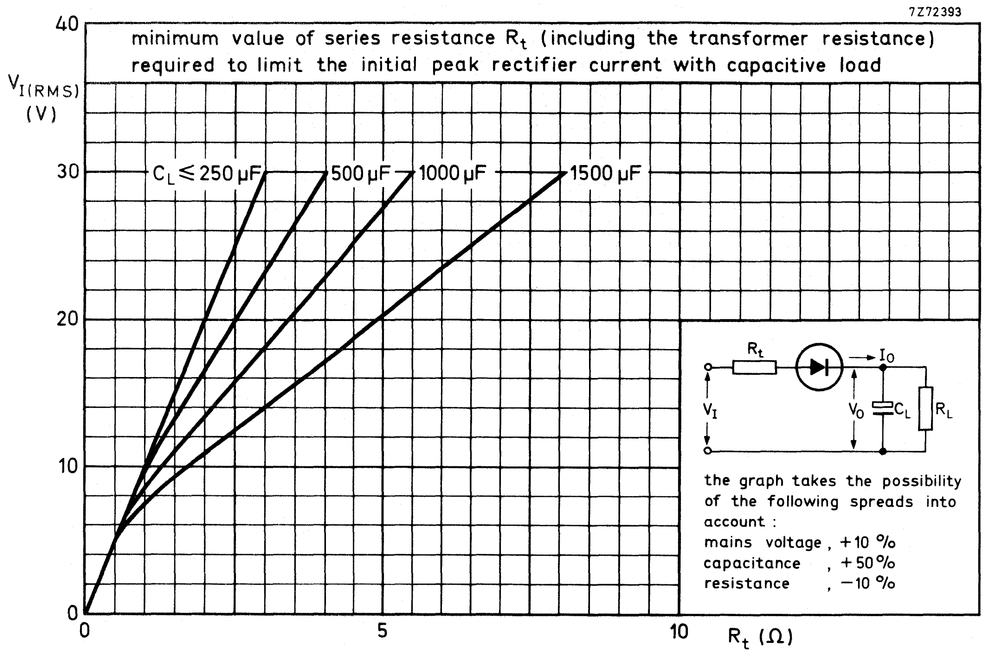


Fig. 3.

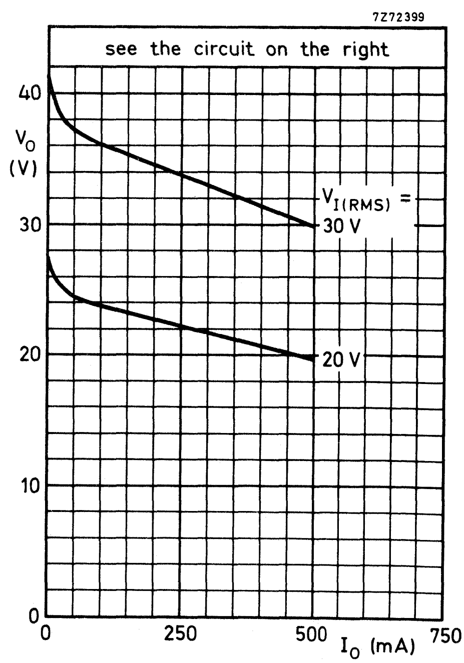


Fig. 4 Output voltages.

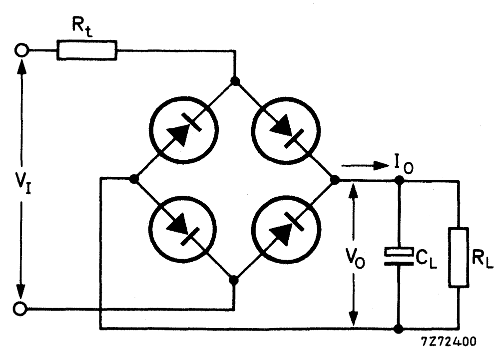


Fig. 5 Test circuit.

V_I (V)	R_t (Ω)	C_L (μF)
30	5,6	1000
20	3,4	1000

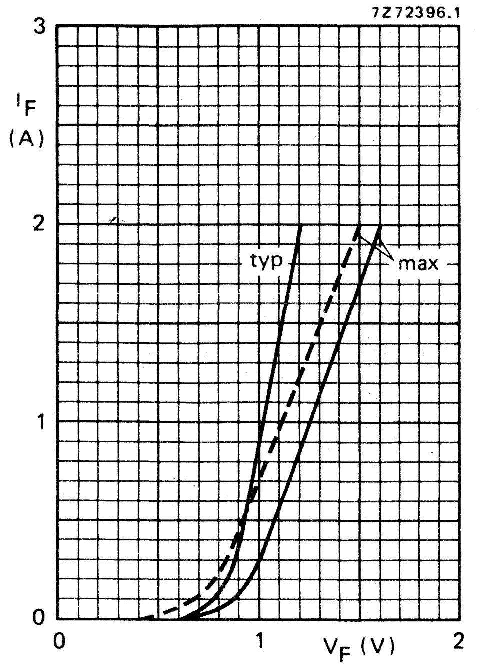


Fig. 6 Typical and maximum values forward current as a function of the forward voltage.
—— T_j = 25 °C; – – – – T_j = 150 °C.

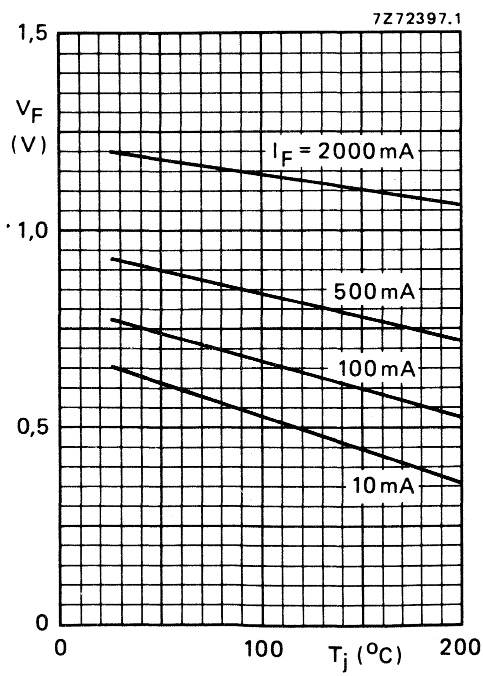


Fig. 7 Typical values forward voltage as a function of junction temperature.

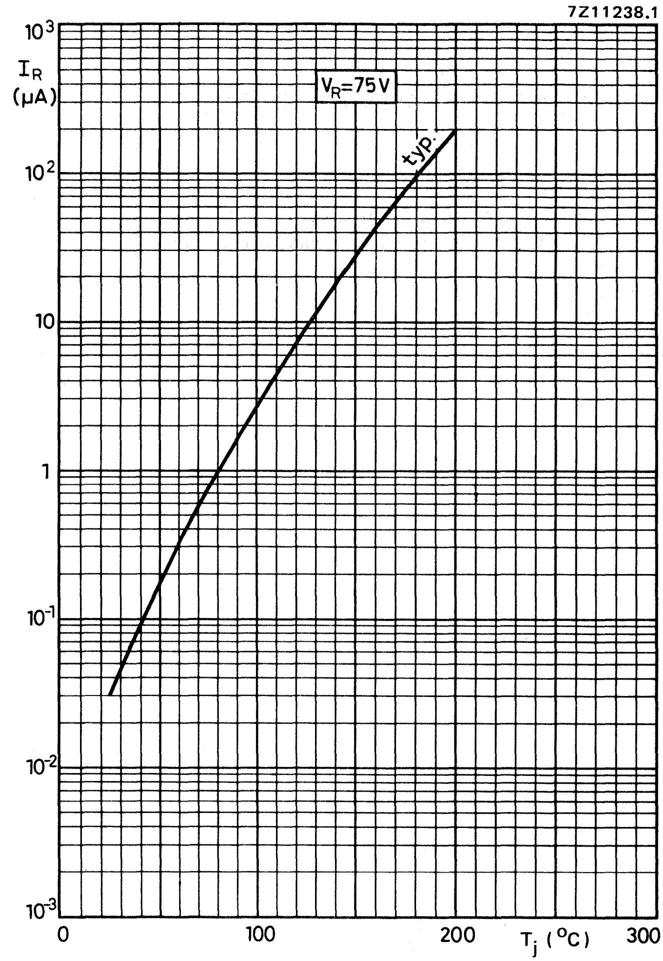


Fig. 8 Typical value reverse current as a function of junction temperature.

GENERAL PURPOSE DIODE

Silicon planar epitaxial diode in DO-35 envelope; intended for switching and general purposes in industrial equipment e.g. oscilloscopes, digital voltmeters and video output stages in colour television.

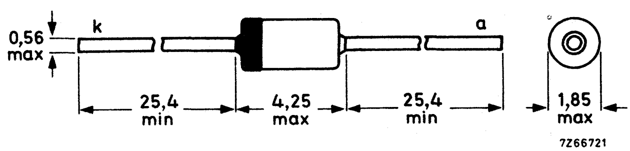
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	120 V
Forward current (d.c.)	I_F	max.	250 mA
Junction temperature	T_j	max.	175 °C
Forward voltage I_F = 100 mA	V_F	<	1,0 V
Reverse current V_R = 120 V	I_R	<	100 nA
Diode capacitance V_R = 0; f = 1 MHz	C_d	<	6 pF
Reverse recovery time when switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω; measured at I_R = 3 mA	t_{rr}	<	50 ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 DO-35



The cathode is indicated by a coloured band.

RATINGS

Limting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	120	V
Repetitive peak reverse voltage	V_{RRM}	max.	150	V
Forward current (d.c.)	I_F	max.	250	mA
Average rectified forward current	$I_{F(AV)}$	max.	200	mA
Repetitive peak forward current	I_{FRM}	max.	625	mA
Non-repetitive peak forward current $t < 1$ s; $T_j = 25$ °C	I_{FSM}	max.	1	A
Total power dissipation up to $T_{amb} = 25$ °C	P_{tot}	max.	400	mW
Storage temperature	T_{stg}	−65	to + 175	°C
Junction temperature	T_j	max.	175	°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0,375	K/mW

CHARACTERISTICS

$T_j = 25$ °C unless otherwise specified

Forward voltage					
$I_F = 0{,}1$ mA	V_F	0,45	to	0,55	V
$I_F = 10$ mA	V_F	0,65	to	0,80	V
$I_F = 50$ mA	V_F	0,73	to	0,92	V
$I_F = 100$ mA	V_F	0,78	to	1,0	V
$I_F = 150$ mA	V_F	$<$		1,07	V
Reverse breakdown voltage* $I_R = 100\ \mu A$	$V_{(BR)R}$	$>$		150	V
Reverse current					
$V_R = 120$ V	I_R	$<$		100	nA
$V_R = 120$ V, $T_j = 150$ °C	I_R	$<$		100	μA
Reverse recovery time when switched from $I_F = 30$ mA to $I_R = 30$ mA; $R_L = 100\ \Omega$; measured at $I_R = 3$ mA	t_{rr}	$<$		50	ns
Diode capacitance $V_R = 0$; $f = 1$ MHz	C_d	$<$		6	pF

* At zero lifetime, measured under pulse conditions to avoid excessive dissipation and voltage limited at 275 V.

SILICON PLANAR VARIABLE CAPACITANCE DIODE

The BB112 is a single 9 V variable capacitance diode in a plastic encapsulation for application in tuning circuits in a.m. receivers. The diodes are supplied in matched sets of three items.

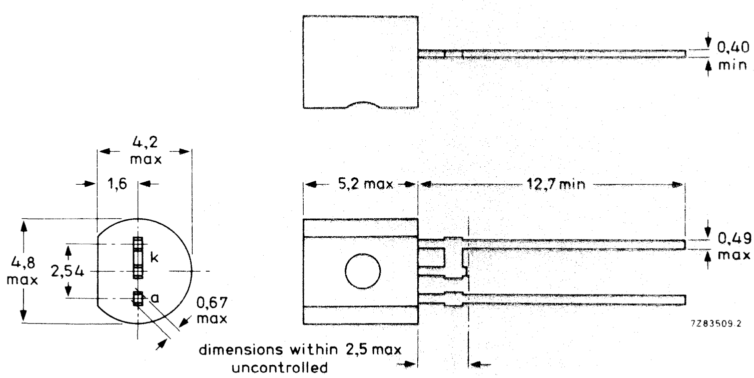
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	12	V
Operating junction temperature	T_j	max.	85	°C
Forward current	I_F	max.	50	mA
Reverse current at T_{amb} = 25 °C				
V_R = 12 V	I_R	<	50	nA
Diode capacitance at f = 1 MHz				
V_R = 1 V	C_d		440 to 540	pF
V_R = 8,5 V	C_d		17 to 29	pF
Series resistance at f = 500 kHz				
V_R = 1 V	r_s	<	1,5	Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-69



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	12 V
Forward current (d.c.)	I_F	max.	50 mA
Operating junction temperature	T_j	max.	85 °C
Storage temperature	T_{stg}		−55 to + 125 °C

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Reverse current			
V_R = 12 V	I_R	<	50 nA
V_R = 12 V; T_{amb} = 85 °C	I_R	<	300 nA
Diode capacitance at f = 1 MHz			
V_R = 1 V	C_d		440 to 540 pF
V_R = 8,5 V	C_d		17 to 29 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 1\ V)}{C_d\ (V_R = 8{,}5\ V)}$	>	18
Series resistance at f = 500 kHz			
V_R = 1 V	r_s	<	1,5 Ω
Temperature coefficient of the diode capacitance at f = 1 MHz; T_{amb} = −40 to + 85 °C; V_R = 1 V	η	typ.	0,05 %/K

Matching properties

D.C. capacitance ratio for a set of 3 diodes; V_P = 1 to 9 V	ΔC	⩽	3 %

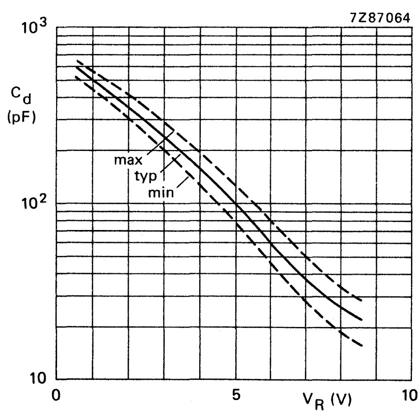


Fig. 2 Diode capacitance at f = 1 MHz as a function of the reverse voltage.

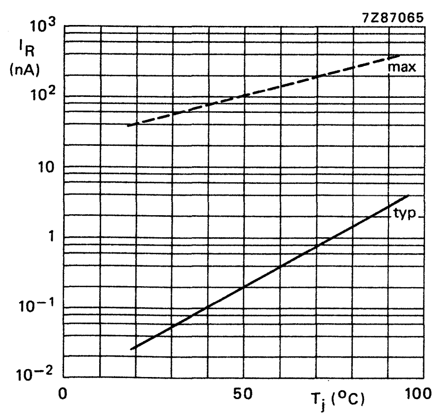


Fig. 3 Reverse current as a function of junction temperature at V_R = 12 V.

SILICON VARIABLE CAPACITANCE DIODE

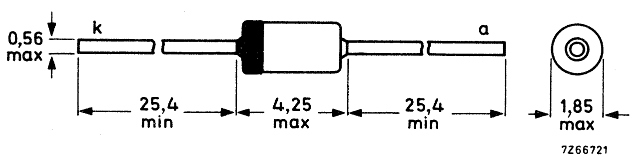
Planar-diffused diode in a DO-35 envelope intended for automatic frequency control in radio and television receivers.

QUICK REFERENCE DATA				
Continuous reverse voltage	V_R	max.	15	V
Junction temperature	T_j	max.	200	^oC
Reverse current at V_R = 15 V; T_j = 150 ^oC	I_R	<	2,0	μA
Diode capacitance at f = 1 MHz V_R = 4 V	C_d		20 to 25	pF
Capacitance ratio at f < 300 MHz	$\frac{C_d\ (V_R = 4\ V)}{C_d\ (V_R = 10\ V)}$	≥	1,3	
Series resistance at V_R = 4 V; f = 200 MHz	r_D	<	1,5	Ω

MECHANICAL DATA

Dimensions in mm

DO-35



The coloured band indicates the cathode

RATINGS Limiting values in accordance with the Absolute Maximum System (IEC 134)

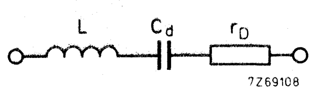
Continuous reverse voltage	V_R	max.	15	V
Forward current (d.c.)	I_F	max.	200	mA
Storage temperature	T_{stg}		−65 to +200	^oC
Junction temperature	T_j	max.	200	^oC

CHARACTERISTICS

T_j = 25 ^oC unless otherwise specified

Reverse current				
V_R = 15 V; T_j = 150 ^oC	I_R	<	2,0	μA
Forward voltage				
I_F = 100 mA	V_F	<	950	mV
Diode capacitance at f = 1 MHz				
V_R = 4 V	C_d		20 to 25	pF
Capacitance ratio at f < 300 MHz	$\frac{C_d\ (V_R = 4\ V)}{C_d\ (V_R = 10\ V)}$	≥	1,3	
Series resistance at f = 200 MHz				
V_R = 4 V	r_D	typ.	0,9	Ω
		<	1,5	Ω

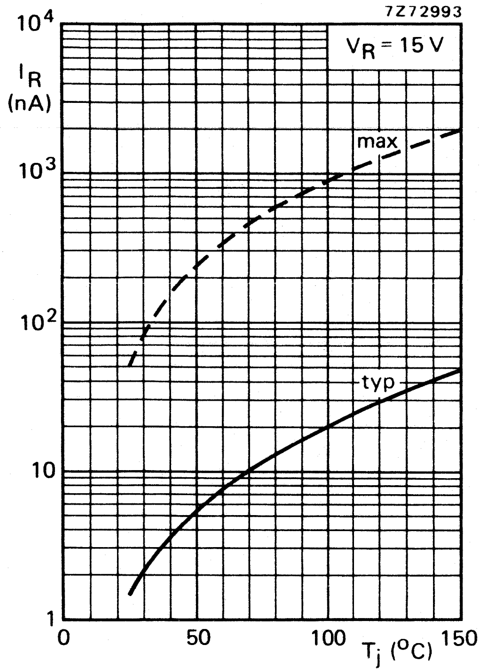
Simplified equivalent circuit:

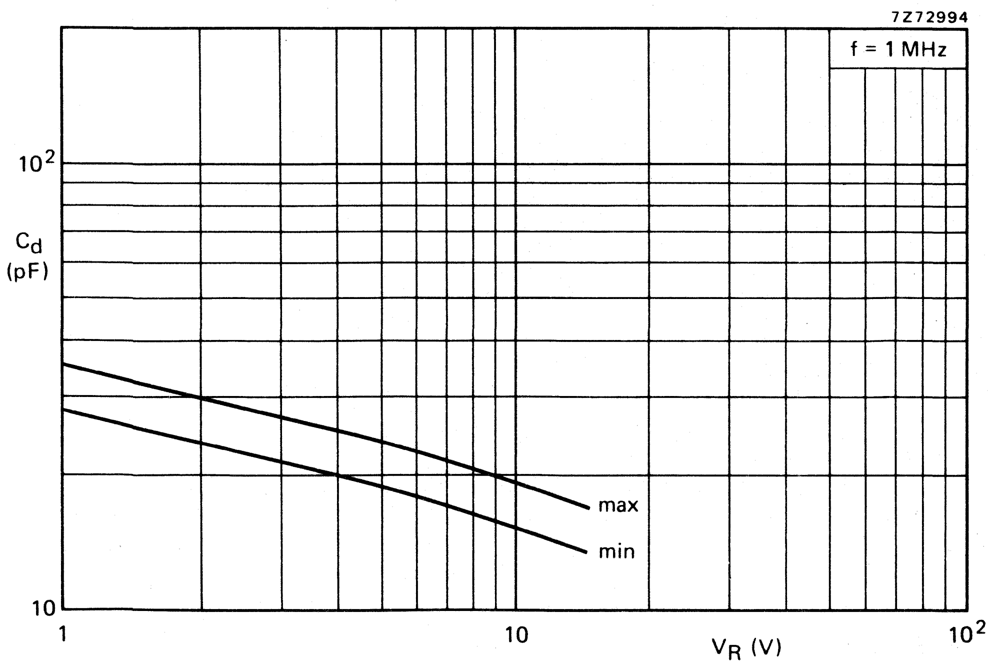


L = lead inductance ≈ 6 nH
r_D = series resistance
C_d = diode capacitance (see next page)

frequency independent up to f = 300 MHz

These data apply for a distance of 10 mm between the two measuring points.


7Z72993
10^4
I_R
(nA)
10^3
10^2
10
1
0
50
100
150
T_j (°C)
V_R = 15 V
max
typ


7Z72994
f = 1 MHz
10^2
C_d
(pF)
10
1
10
10^2
V_R (V)
max
min

VARIABLE CAPACITANCE DIODE

A single variable capacitance diode, in a plastic envelope. The diode is for tuning of long, medium and short wavebands. Also suitable for frequency synthesizer applications.

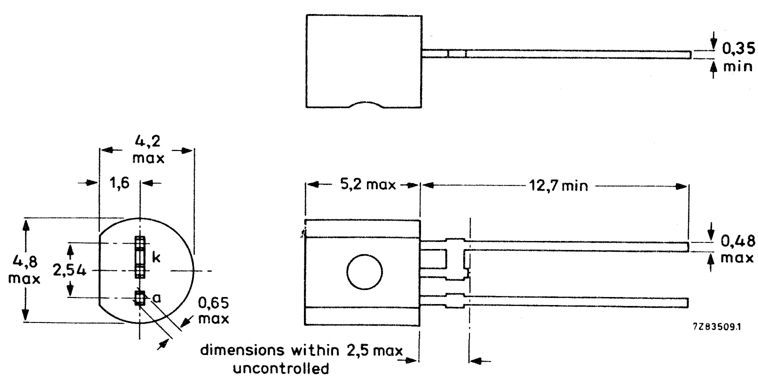
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	30 V
Reverse current at V_R = 30 V	I_R	<	50 nA
Diode capacitance at f = 1 MHz; V_R = 28 V	C_d		12 to 21 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 1\ V)}{C_d\ (V_R = 28\ V)}$	>	23
Series resistance f = 1 MHz; V_R = 1 V	r_s	<	2 Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-69 (TO-92 variant).



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	30 V
Reverse voltage (peak value)	V_{RM}	max.	32 V
Forward current (d.c.)	I_F	max.	50 mA
Storage temperature	T_{stg}		−55 to + 125 °C
Operation junction temperature	T_j	max.	85 °C

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Reverse current			
V_R = 30 V	I_R	<	50 nA
V_R = 30 V; T_{amb} = 85 °C	I_R	<	300 nA
Diode capacitance at f = 1 MHz			
V_R = 1 V	C_d		450 to 550 pF
V_R = 28 V	C_d		12 to 21 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 1\ V)}{C_d\ (V_R = 28\ V)}$	>	23
Series resistance at f = 1 MHz and V_R = 1 V	r_s	<	2 Ω
Temperature coefficient of the diode capacitance at f = 1 MHz; T_{amb} = −20 °C to + 85 °C, V_R = 1 V	η	typ.	0,05 %/°C
Capacitance matching			
Relative capacitance difference between two diodes at V_R = 1 to 28 V	$\frac{\Delta C}{C}$	<	3 %

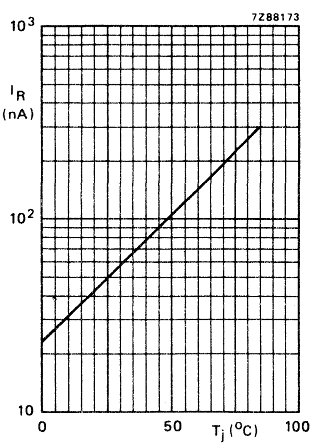


Fig. 2 Maximum values. Reverse current as a function of the junction temperature. V_R = 30 V.

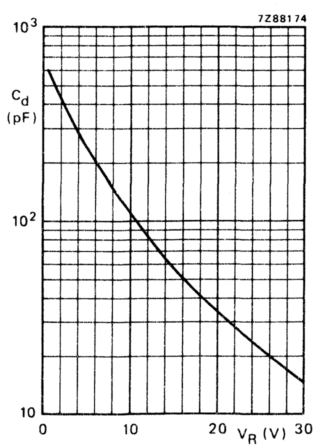


Fig. 3 Typical diode capacitance as a function of reverse voltage; f = 1 MHz.

SILICON PLANAR VARIABLE CAPACITANCE DOUBLE DIODES

The BB204B and BB204G are double diodes with common cathode in a plastic TO-92 variant, primarily intended for electronic tuning in band II (f.m.). They are recommended for stages where large signals occur (e.g. oscillator circuits).

QUICK REFERENCE DATA

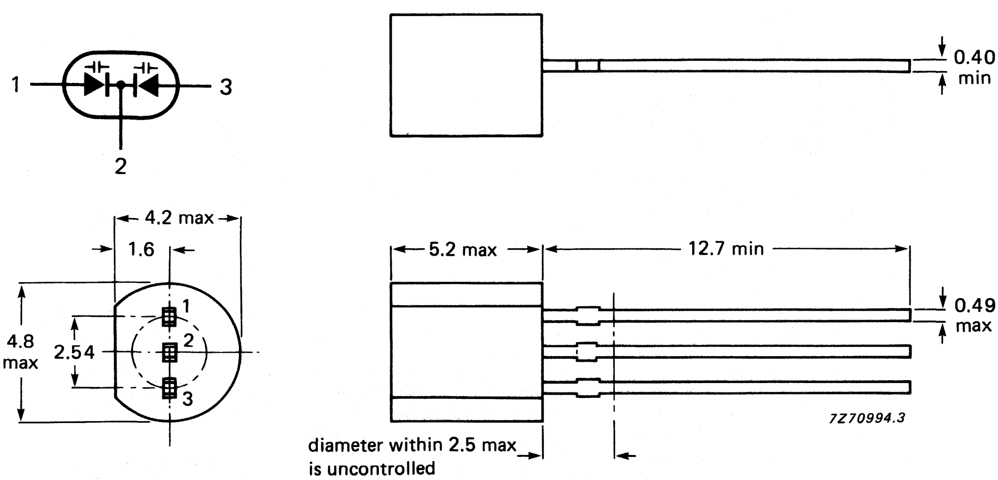
For each diode:

Continuous reverse voltage	V_R	max.		30 V
Junction temperature	T_j	max.		100 °C
Reverse current at V_R = 30 V	I_R	<		50 nA
			BB204G	BB204B
Diode capacitance at f = 1 MHz				
V_R = 3 V	C_d		34 – 39	37 – 42 pF
V_R = 8 V	C_d		22 – 27	24 – 29 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 3\ V)}{C_d\ (V_R = 30\ V)}$		2,5 to 2,8	
Series resistance at f = 100 MHz, V_R is that value at which C_d = 38 pF	r_D	typ.	0,2	Ω
		<	0,4	Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 TO-92 variant.



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

For each diode:

Continuous reverse voltage	V_R	max.	30 V
Forward current (d.c.)	I_F	max.	100 mA
Storage temperature	T_{stg}		−55 to +100 °C
Junction temperature	T_j	max.	100 °C

CHARACTERISTICS

For each diode:

$T_j = 25$ °C

			BB204G	BB204B	
Reverse current at $V_R = 30$ V	I_R	<	50		nA
Diode capacitance at f = 1 MHz			BB204G	BB204B	
$V_R = 3$ V	C_d		34 – 39	37 – 42	pF
$V_R = 8$ V	C_d		22 – 27	24 – 29	pF
$V_R = 30$ V	C_d	typ.	14		pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 3\ V)}{C_d\ (V_R = 30\ V)}$		2,5 to 2,8		
Series resistance at f = 100 MHz; V_R is that value at which $C_d = 38$ pF	r_D	typ.	0,2		Ω
		<	0,4		Ω

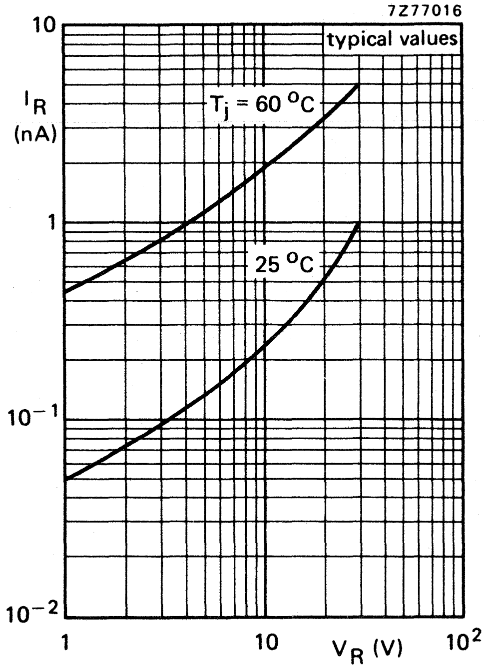

7Z77016
typical values
I_R
(nA)
10
1
10^{-1}
10^{-2}
T_j = 60 °C
25 °C
1
10
V_R (V)
10^2

Fig. 2.

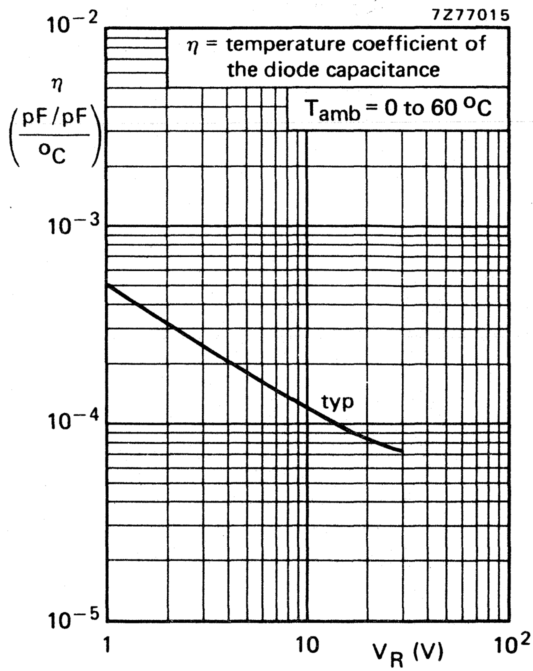

7Z77015
η = temperature coefficient of
the diode capacitance
T_{amb} = 0 to 60 °C
η
(pF/pF / °C)
10^{-2}
10^{-3}
10^{-4}
10^{-5}
typ
1
10
V_R (V)
10^2

Fig. 3.

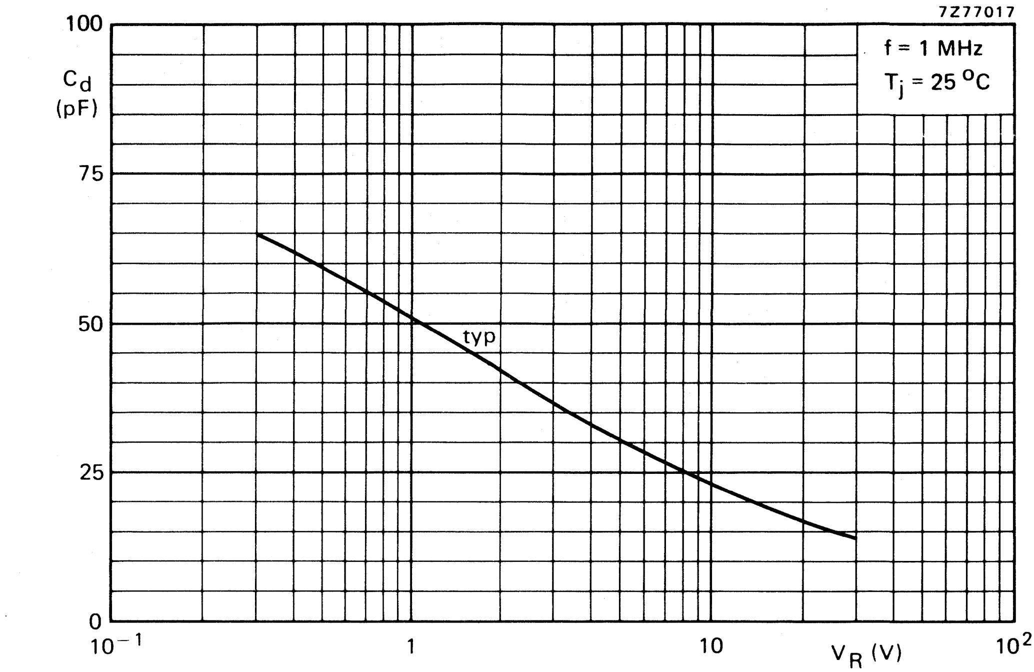

7Z77017
f = 1 MHz
T_j = 25 °C
100
C_d (pF)
75
50
25
0
typ
10^{-1}
1
10
V_R (V)
10^2

Fig. 4.

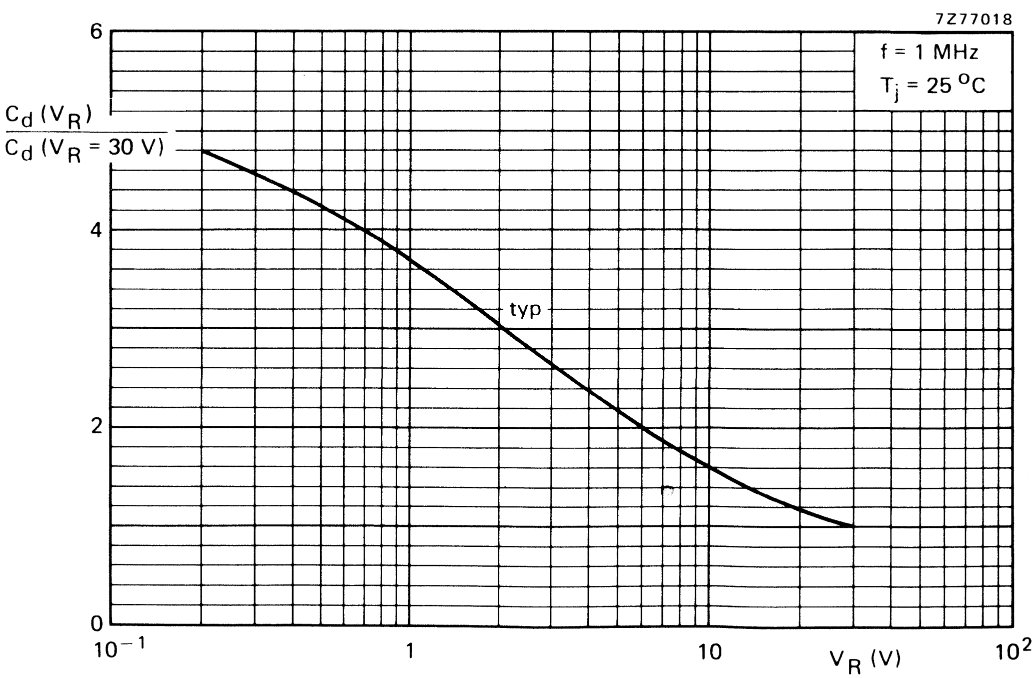

7Z77018
f = 1 MHz
T_j = 25 °C
6
$\frac{C_d(V_R)}{C_d(V_R = 30\ V)}$
4
2
0
typ
10^{-1}
1
10
V_R (V)
10^2

Fig. 5.

A.M. VARIABLE CAPACITANCE DOUBLE DIODES

The BB212 is a silicon mesa profiled epitaxial double tuning diode with common cathode in a plastic TO-92 variant.

A special feature is the low tuning voltage which makes the device particularly suited to car and domestic receivers in the L.W., M.W. and S.W. bands.

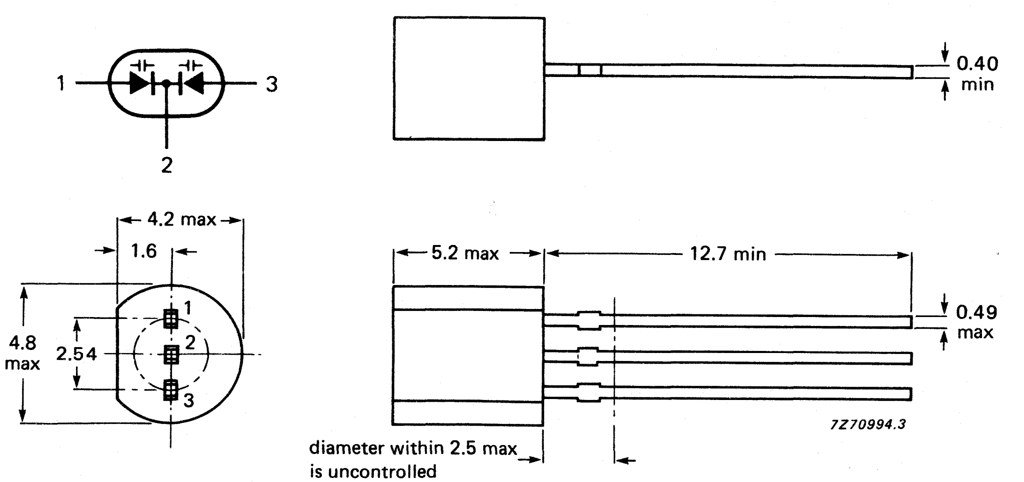
QUICK REFERENCE DATA

For each diode:				
Continuous reverse voltage	V_R	max.	12	V
Operating junction temperature	T_j	max.	85	°C
Reverse current at T_j = 25 °C; V_R = 10 V	I_R	<	50	nA
Diode capacitance at f = 1 MHz; V_R = 0,5 V	C_d		500 to 620	pF
V_R = 8,0 V	C_d	<	22	pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 0,5\ V)}{C_d\ (V_R = 8,0\ V)}$	>	22,5	
Series resistance at f = 500 kHz; V_R is that value at which C_d = 500 pF	r_s	<	2,5	Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 TO-92 variant.



The anode of the diode with the higher capacitance C_1 at V_R = 3 V, i.e. a more positive mismatch, is identified by a white dot.

RATINGS (for each diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	12	V
Forward current (d.c.)	I_F	max.	100	mA
Storage temperature	T_{stg}		−55 to + 100	°C
Operating junction temperature	T_j	max.	85	°C

CHARACTERISTICS (for each diode)

T_j = 25 °C unless otherwise specified

Reverse current				
V_R = 10 V	I_R	<	50	nA
V_R = 10 V; T_{amb} = 60 °C	I_R	<	200	nA
Diode capacitance at f = 1 MHz				
V_R = 0,5 V	C_d		500 to 620	pF
V_R = 3,0 V	C_d		140 to 280	pF
V_R = 5,5 V	C_d		40 to 90	pF
V_R = 8,0 V	C_d	<	22	pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 0{,}5\ V)}{C_d\ (V_R = 8{,}0\ V)}$	>	22,5	
Series resistance at f = 500 MHz				
V_R is that value at which C_d = 500 pF	r_s	<	2,5	Ω
Temperature coefficient of the diode capacitance at f = 1 MHz; T_{amb} = 25 °C to 60 °C				
V_R = 0,5 V	η	typ.	0,054	%/K
V_R = 8,0 V	η	typ.	0,050	%/K

MATCHING PROPERTIES

The capacitance of the two diodes in their common envelope may differ within certain limits. The total, relative capacitance difference between the two diodes in one envelope may be found in Fig. 2. The anode a1 or a2 with the higher capacitance at V_R = 3 V, is identified by a white dot.

BASIC TOLERANCE

The relative deviation of the capacitance value at V_R = 0,5 V is maximum 3,5%.

$$k = \left| \frac{C_1\ (0{,}5\ V) - C_2\ (0{,}5\ V)}{C_2\ (0{,}5\ V)} \right| = < 3{,}5\%.$$

ADDITIONAL TOLERANCE

In the range of V_R = 0,5 to 8 V the following additional tolerances are valid.

$$S = \left| \left(\frac{C_1}{C_2}\right)_{V_R} - \left(\frac{C_1}{C_2}\right)_{0{,}5\ V} \right|$$

S < 2% for V_R = 0,5 to 3 V
S < 4% for V_R = 3 to 5,5 V
S < 6% for V_R = 5,5 to 8 V
} see Fig. 2

C_1 is the capacitance of a_1 when $a_1 > a_2$
C_1 is the capacitance of a_2 when $a_2 > a_1$

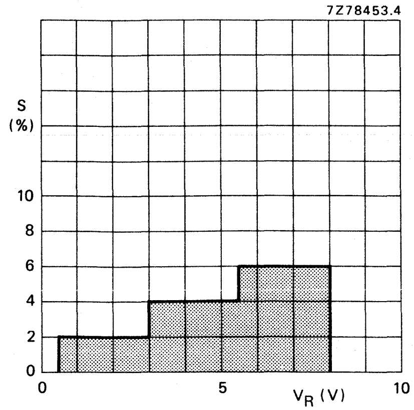


Fig. 2 The shaded area represents the maximum tolerance of the two diodes in one envelope as a function of the reverse voltage.

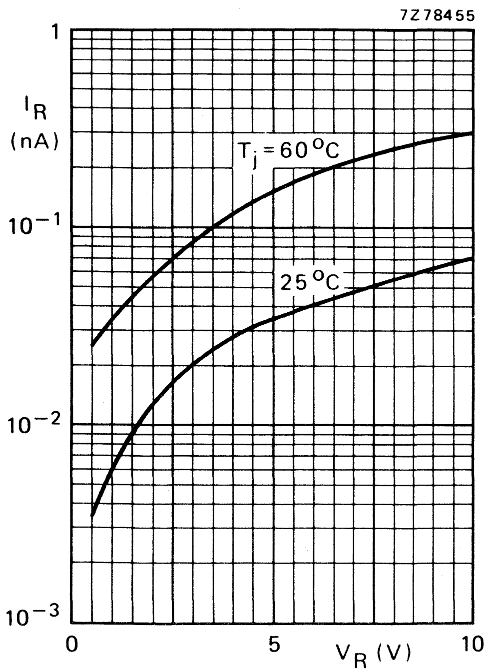


Fig. 3 Typical values.

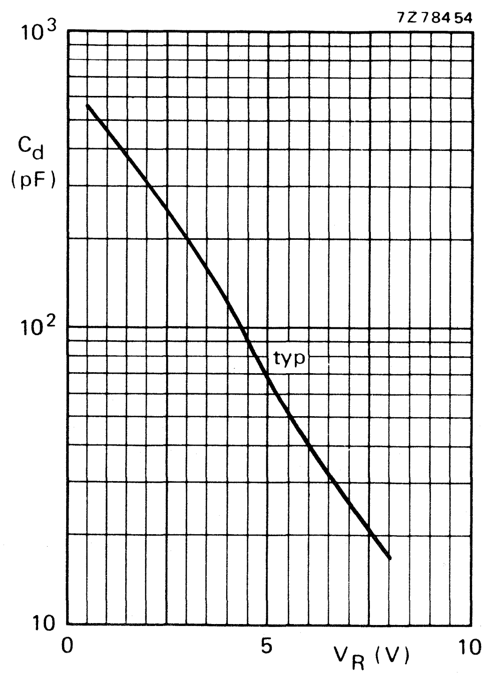


Fig. 4 f = 1 MHz.

UHF VARIABLE CAPACITANCE DIODE

The BB215 is a silicon variable capacitance diode in a hermetically sealed glass envelope (SOD-80) and intended for application in UHF tuners. The leadless SOD-80 encapsulation is intended for surface mounting.
The diode features a capacitance characteristic with a good linearity.

Diodes are supplied in matched sets and the capacitance difference between any two diodes in one set is less than 3% over the voltage range from 0,5 V to 28 V.

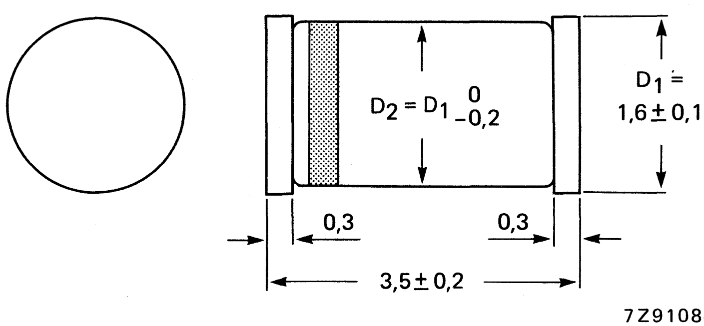
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	30 V
Reverse current V_R = 28 V	I_R	<	10 nA
Diode capacitance at f = 500 kHz V_R = 28 V	C_d		1,8 to 2,2 pF
Capacitance ratio at f = 500 kHz	$\frac{C_d(V_R = 1\ V)}{C_d(V_R = 28\ V)}$	>	7,6
Series resistance at f = 470 MHz V_R is that value at which C_d = 9 pF	r_s	<	0,75 Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



The cathode is indicated by a white band on the body and a second green band indicates the BB215 type.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	30 V
Forward current (DC)	I_F	max.	20 mA
Storage temperature	T_{stg}		−55 to +150 °C
Operating junction temperature	T_j	max.	100 °C

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Reverse current			
V_R = 28 V	I_R	<	10 nA
V_R = 28 V; T_{amb} = 85 °C	I_R	<	200 nA
Diode capacitance at f = 500 kHz			
V_R = 1 V	C_d	typ.	17 pF
		<	18 pF
V_R = 28 V	C_d		1,8 to 2,2 pF
Capacitance ratio at f = 500 kHz	$\frac{C_d(V_R = 1\ V)}{C_d(V_R = 28\ V)}$	>	7,6
		typ.	8,3
Series resistance at f = 470 MHz and at that value of V_R at which C_d = 9 pF	r_s	typ.	0,63 Ω

VHF VARIABLE CAPACITANCE DIODE

The BB219 is a silicon variable capacitance diode in a hermetically sealed glass envelope (SOD-80) and intended for electronic tuning in VHF television tuners for C.A.T.V. applications.
The SOD-80 envelope is suitable for surface mounting.

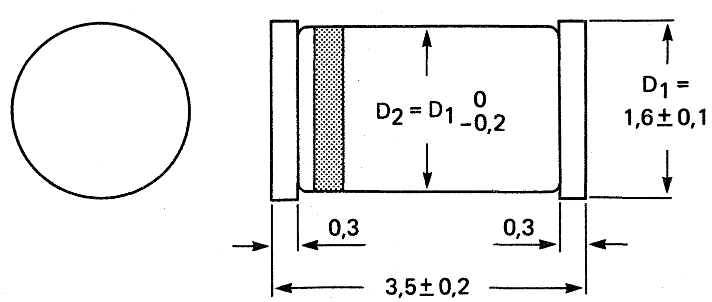
QUICK REFERENCE DATA

Reverse voltage, peak value	V_{RM}	max.	30 V
Reverse current V_R = 28 V	I_R	<	10 nA
Diode capacitance at f = 1 MHz V_R = 1 V	C_d	>	31 pF
V_R = 28 V	C_d		2,6 to 3,2 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d(V_R = 1\ V)}{C_d(V_R = 28\ V)}$		12 to 15
Series resistance at f = 100 MHz V_R is that value at which C_d = 30 pF	r_s	typ.	0,7 Ω
		<	0,9 Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



The cathode is indicated by a white band on the body.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Reverse voltage, peak value	V_{RM}	max.	30 V
Forward current (DC)	I_F	max.	20 mA
Storage temperature	T_{stg}		−55 to +150 °C
Operating junction temperature	T_j	max.	100 °C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0,6 K/mW

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Reverse current			
V_R = 28 V	I_R	<	10 nA
V_R = 28 V; T_{amb} = 85 °C	I_R	<	200 nA
Diode capacitance at f = 0,5 MHz			
→ V_R = 1 V	C_d	>	31 pF
V_R = 28 V	C_d		2,6 to 3,2 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d(V_R = 1\ V)}{C_d(V_R = 28\ V)}$		12 to 15
Series resistance at f = 100 MHz and at that value of V_R at which C_d = 30 pF	r_s	typ.	0,7 Ω
		<	0,9 Ω
Tolerance of capacitance difference between two diodes at V_R = 1 to 28 V	$\frac{\Delta C}{C}$	<	2,5 %

VHF VARIABLE CAPACITANCE DIODE

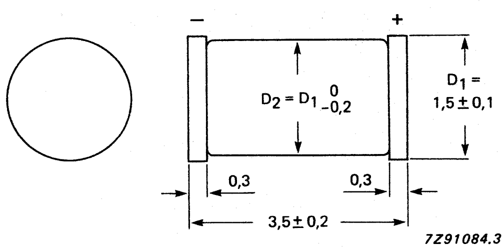
The BB240 is a VHF variable capacitance diode in planar technology with a very high capacitance ratio intended for VHF-band B up to 460 MHz in all-band tuners.
The diode is encapsulated in the hermetically sealed glass envelope SOD-80 suitable for surface mounting.

QUICK REFERENCE DATA

Reverse voltage, peak value	V_{RM}	max.	32	V
Reverse current V_R = 28 V	I_R	<	10	nA
Diode capacitance at f = 1 MHz V_R = 0.5 V	C_d	>	38	pF
V_R = 28 V			2.4 to 2.7	pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 0.5\ V)}{C_d\ (V_R = 28\ V)}$	>	14	
Series resistance at f = 100 MHz V_R is that value at which C_d = 40 pF	r_s	<	1.0	Ω

MECHANICAL DATA

Dimensions in mm



The cathode is indicated by a green band on the body.

Fig. 1 SOD-80.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Reverse voltage, peak value	V_{RM}	max.	32 V
Forward current (DC)	I_F	max.	20 mA
Storage temperature range	T_{stg}		−55 to + 150 °C
Operating junction temperature	T_j	max.	100 °C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\,j\text{-}a}$	=	0.6 K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Reverse current			
V_R = 28 V	I_R	<	10 nA
V_R = 28 V; T_{amb} = 85 °C	I_R	<	200 nA
Diode capacitance at f = 1 MHz			
V_R = 0.5 V	C_d	>	38 pF
V_R = 28 V	C_d		2.4 to 2.7 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 0.5\ V)}{C_d\ (V_R = 28\ V)}$	>	14
Series resistance at f = 100 MHz and at that value of V_R at which C_d = 40 pF	r_s	<	1.0 Ω
Tolerance of capacitance difference between two diodes at V_R = 1 to 28 V	$\frac{\Delta C}{C}$	<	2.5 %

VHF VARIABLE CAPACITANCE DIODE

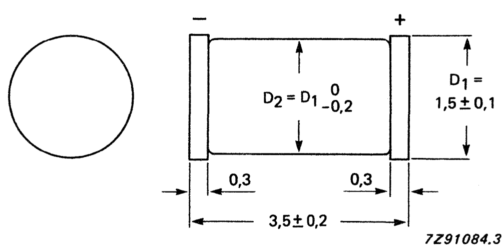
The BB241 is a VHF variable capacitance diode in planar technology with a very high capacitance ratio intended for VHF-band A up to 160 MHz in all-band tuners.
The diode is encapsulated in the hermetically sealed glass envelope SOD-80 suitable for surface mounting.

QUICK REFERENCE DATA

Reverse voltage, peak value	V_{RM}	max.	32 V
Reverse current V_R = 28 V	I_R	<	10 nA
Diode capacitance at f = 1 MHz V_R = 0.5 V	C_d	>	63 pF
V_R = 28 V	C_d		2.5 to 3.0 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 0.5\ V)}{C_d\ (V_R = 28\ V)}$	>	21
Series resistance at f = 100 MHz V_R is that value at which C_d = 40 pF	r_s	<	2.0 Ω

MECHANICAL DATA

Dimensions in mm



The cathode is indicated by a black band on the body.

Fig. 1 SOD-80.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Reverse voltage, peak value	V_{RM}	max.	32 V
Forward current (DC)	I_F	max.	20 mA
Storage temperature range	T_{stg}		−55 to + 150 °C
Operating junction temperature	T_j	max.	100 °C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0.6 K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Reverse current			
V_R = 28 V	I_R	<	10 nA
V_R = 28 V; T_{amb} = 85 °C	I_R	<	200 nA
Diode capacitance at f = 1 MHz			
V_R = 0.5 V	C_d	>	63 pF
V_R = 28 V	C_d		2.5 to 3.0 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 0.5\ V)}{C_d\ (V_R = 28\ V)}$	>	21
Series resistance at f = 100 MHz and at that value of V_R at which C_d = 40 pF	r_s	<	2.0 Ω
Tolerance of capacitance difference between two diodes at V_R = 1 to 28 V	$\frac{\Delta C}{C}$	<	2.5 %

UHF VARIABLE CAPACITANCE DIODE

The BB405B is a silicon variable capacitance diode in a hermetically sealed glass envelope and intended for application in UHF tuners.

This miniature diode can be mounted on a 2 E (5,08 mm) pitch.
Diodes are supplied in matched sets and the capacitance difference between any two diodes in one set is less than 3% over the voltage range from 0,5 V to 28 V.

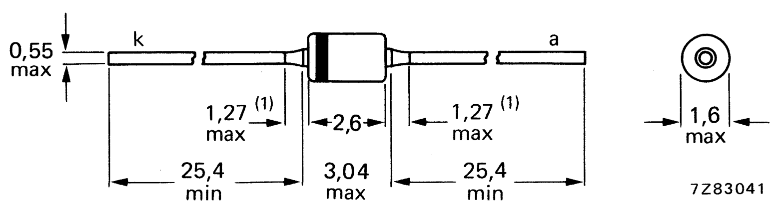
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	30	V
Reverse current V_R = 28 V	I_R	<	10	nA
Diode capacitance at f = 500 kHz V_R = 28 V	C_d		1,8 to 2,2	pF
Capacitance ratio at f = 500 kHz	$\frac{C_d(V_R = 1\ V)}{C_d(V_R = 28\ V)}$	>	7,6	
Series resistance at f = 470 MHz V_R is that value at which C_d = 9 pF	r_s	<	0,75	Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-68 (DO-34).



(1) Lead diameter in this zone uncontrolled.
The cathode is indicated by a white band on a black body.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134).

Continuous reverse voltage	V_R	max.	30 V
Reverse voltage (peak value)	V_{RM}	max.	30 V
Forward current (DC)	I_F	max.	20 mA
Storage temperature	T_{stg}		−55 to +150 °C
Operating junction temperature	T_j	max.	100 °C

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Reverse current			
V_R = 28 V	I_R	<	10 nA
V_R = 28 V; T_{amb} = 85 °C	I_R	<	100 nA
Diode capacitance at f = 500 kHz*			
V_R = 1 V	C_d	<	18 pF
V_R = 3 V	C_d	typ.	11 pF
V_R = 28 V	C_d		1,8 to 2,2 pF
Capacitance ratio at f = 500 kHz	$\frac{C_d(V_R = 1\ V)}{C_d(V_R = 28\ V)}$	>	7,6
Relative capacitance difference	$\frac{\Delta C}{C}$	⩽	3 %
Series resistance at f = 470 MHz and at that value of V_R at which C_d = 9 pF	r_s	<	0,75 Ω

* Matching: Devices are supplied on a bandolier with a space between matched sets (minimum quantity is 120 pieces per set).

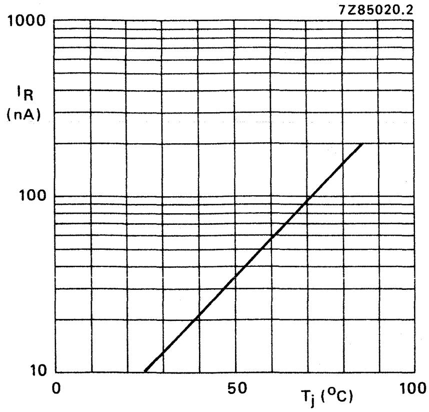


Fig. 2 Maximum values reverse current versus junction temperature; V_R = 28 V.

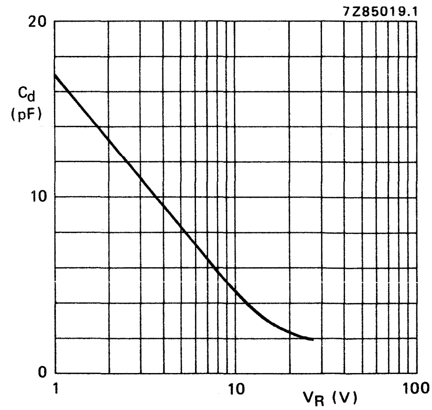


Fig. 3 Maximum values diode capacitance at f = 500 kHz.

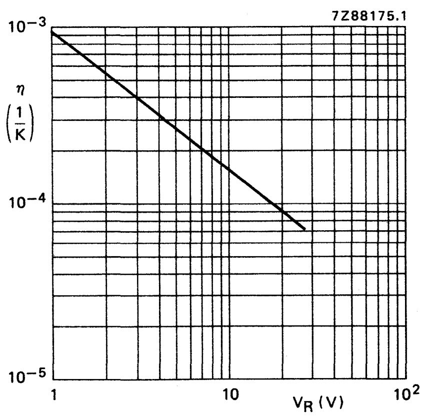


Fig. 4 Maximum values temperature coefficient versus reverse voltage; T_j = 0 to 85 °C.

VARIABLE CAPACITANCE DIODE

The BB417 is a silicon variable capacitance diode in a hermetically sealed glass DO-34 envelope. The diode is primarily intended for automatic frequency control in television receivers.

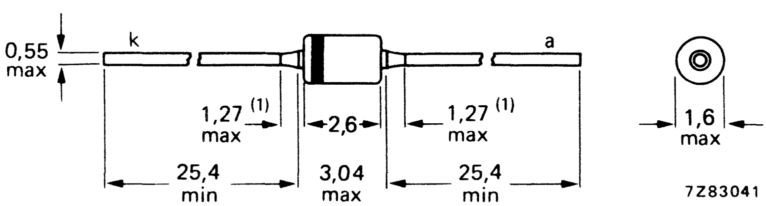
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	20	V
Reverse current at V_R = 20 V	I_R	<	100	nA
Diode capacitance at f = 500 kHz V_R = 15 V	C_d		2,2 to 4,0	pF
Capacitance ratio	$\frac{C_d(V_R = 4\ V)}{C_d(V_R = 15\ V)}$		2,0 to 5,0	
Series resistance at f = 470 MHz V_R is that value at which C_d = 9 pF	r_D	<	1,2	Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-68 (DO-34).



(1) Lead diameter in this zone uncontrolled.

Cathode indicated by a white band.

Maximum soldering iron or solder bath temperature 300 °C; maximum soldering time 3 s. Distance from soldering point to seal must be at least 1,5 mm.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	20 V
Forward current (d.c.)	I_F	max.	20 mA
Storage temperature	T_{stg}	−55 to + 100	°C
Junction temperature	T_j	max.	100 °C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0,6 K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Reverse current			
V_R = 20 V	I_R	<	100 nA
V_R = 20 V; T_j = 100 °C	I_R	<	2 mA
Diode capacitance at f = 500 kHz			
V_R = 4 V	C_d		8 to 11 pF
V_R = 15 V	C_d		2,2 to 4,0 pF
Capacitance ratio at f = 500 kHz	$\frac{C_d(V_R = 4\ V)}{C_d(V_R = 15\ V)}$		2,0 to 5,0
Series resistance at f = 470 MHz			
V_R is that value at which C_d = 9 pF	r_D	<	1,2 Ω

VHF VARIABLE CAPACITANCE DOUBLE DIODE

The BB804 is a variable capacitance double diode in planar technology with common cathode in a plastic SOT23 envelope. It is intended for FM tuning especially for car radios.

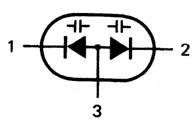
QUICK REFERENCE DATA

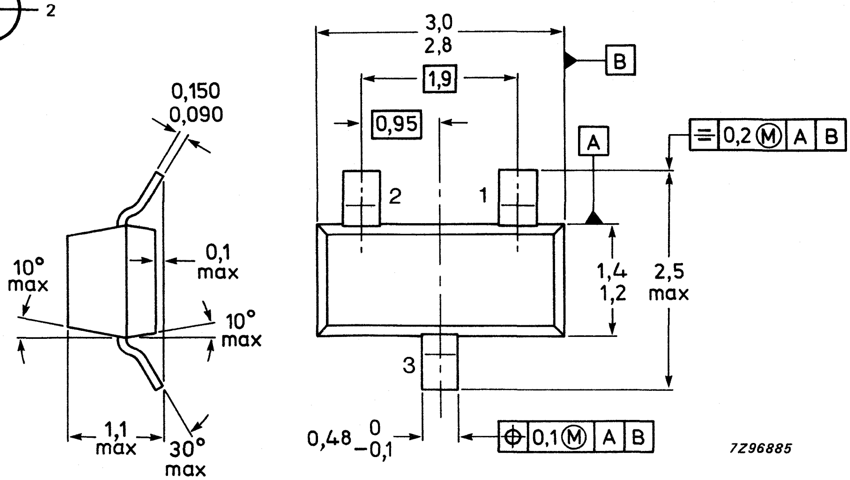
Continuous reverse voltage	V_R	max.	18 V
Repetitive peak reverse voltage	V_{RRM}	max.	20 V
Forward current (DC)	I_F	max.	50 mA
Operating junction temperature	T_j	max.	100 °C
Reverse current	I_R	max.	20 nA
Diode capacitance at f = 1 MHz V_R = 2 V	C_d		42 to 47.5 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 2\ V)}{C_d\ (V_R = 8\ V)}$		1.65 to 1.75
Series resistance at f = 100 MHz V_R is that value at which C_d = 38 pF	r_s	typ.	0.20 Ω

MECHANICAL DATA

Dimensions in mm

Marking S3 x (x = 0 - 4)





TOP VIEW

Fig.1 SOT23.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	18 V
Forward current (DC)	I_F	max.	50 mA
Repetitive peak reverse voltage	V_{RRM}	max.	20 V
Storage temperature range	T_{stg}	−55 to + 100	°C
Operating junction temperature	T_j	max.	100 °C

THERMAL RESISTANCE

From junction to ambient mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm	$R_{th\ j\text{-}a}$	=	430 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Reverse current			
V_R = 16 V	I_R	<	20 nA
V_R = 16 V; T_{amb} = 60 °C	I_R	<	200 nA
Diode capacitance at f = 1.0 MHz			
V_R = 2 V			
red 0	C_d		42 to 43.5 pF
yellow 1	C_d		43 to 44.5 pF
white 2	C_d		44 to 45.5 pF
green 3	C_d		45 to 46.5 pF
blue 4	C_d		46 to 47.5 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 2\ V)}{C_d\ (V_R = 8\ V)}$		1.65 to 1.75
Series resistance at f = 100 MHz, V_R is that value at which C_d = 38 pF	r_s	typ.	0.20 Ω

SILICON PLANAR VARIABLE CAPACITANCE DIODE

The BB809 is a variable capacitance diode in a miniature glass envelope intended for electronic tuning in v.h.f. television tuners with extended band I (FCC and OIRT-norm).

Diodes are supplied in matched sets (minimum 120 pieces and divisible by 12) and the capacitance difference between any two diodes in one set is less than 3% over the voltage range from 0,5 V to 28 V.

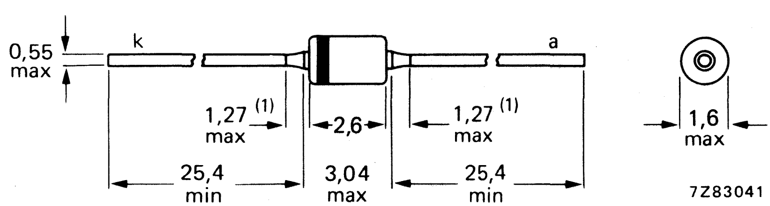
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	28	V
Reverse current at V_R = 28 V	I_R	max.	10	nA
Diode capacitance at f = 500 kHz				
V_R = 1 V	C_d		39 to 46	pF
V_R = 28 V	C_d		4,0 to 5,0	pF
Capacitance ratio at f = 500 kHz	$\frac{C_d\ (V_R = 1\ V)}{C_d\ (V_R = 28\ V)}$		8 to 10	
Series resistance at f = 200 MHz				
V_R is that value at which C_d = 25 pF	r_s	max.	0,6	Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-68 (DO-34).



(1) Lead diameter in this zone uncontrolled.

Cathode indicated by yellow band.

Maximum soldering iron or solder bath temperature 300 °C; maximum soldering time 3 s. Distance from case is not critical, but the glass envelope must not come into contact with soldering iron.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	28 V
Reverse voltage (peak value)	V_{RM}	max.	30 V
Forward current (d.c.)	I_F	max.	20 mA
Storage temperature	T_{stg}		−55 to + 150 °C
Operating junction temperature	T_j	max.	100 °C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0,6 K/mW

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Reverse current			
V_R = 28 V	I_R	⩽	10 nA
V_R = 28 V; T_{amb} = 85 °C	I_R	⩽	200 nA
Diode capacitance at f = 500 kHz			
V_R = 1 V	C_d		39 to 46 pF
V_R = 28 V	C_d		4,0 to 5,0 pF
Capacitance ratio at f = 500 kHz	$\frac{C_d\ (V_R = 1\ V)}{C_d\ (V_R = 28\ V)}$		8 to 10
Series resistance at f = 200 MHz; V_R is that value at which C_d = 25 pF	r_s	⩽	0,6 Ω
Relative capacitance difference between two diodes; V_R = 0,5 to 28 V	$\frac{\Delta C}{C}$	⩽	3 %

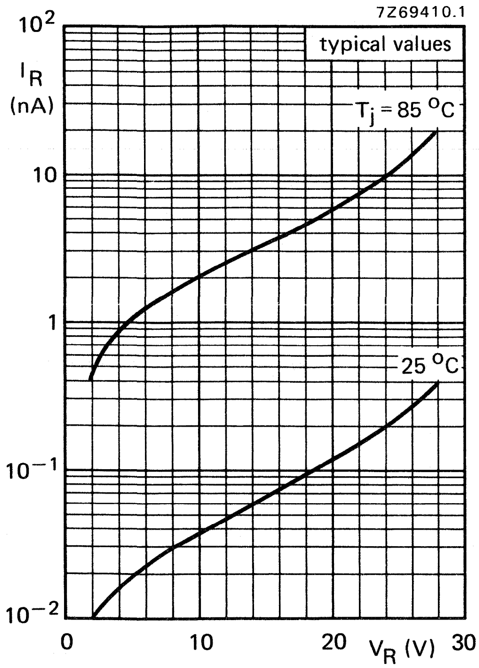


Fig. 2 Typical values.

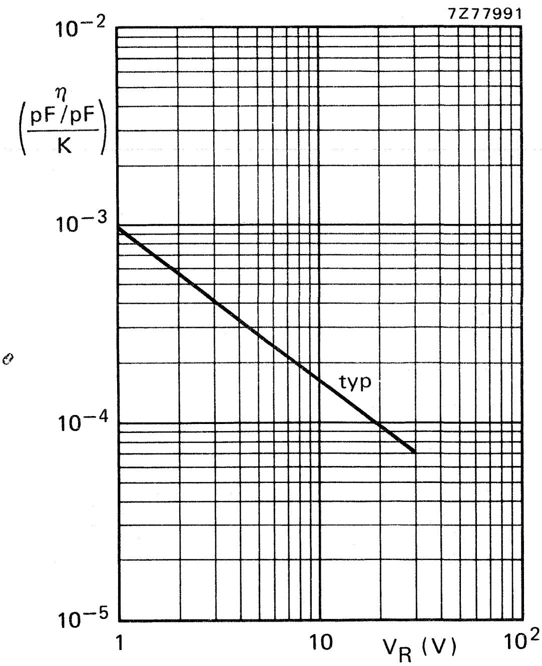


Fig. 3 Temperature coefficient of the diode capacitance; T_{amb} = 0 to 85 °C.

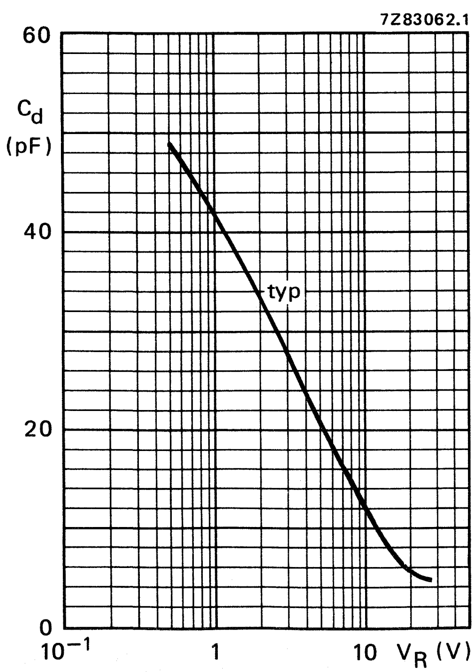


Fig. 4 f = 500 kHz; T_{amb} = 25 °C.

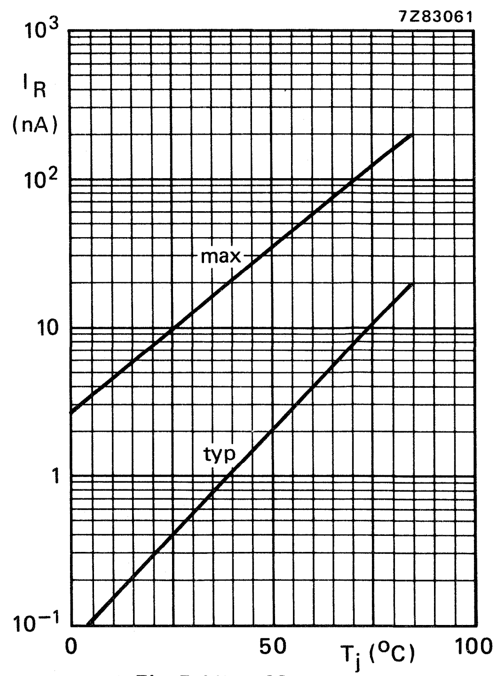


Fig. 5 V_R = 28 V.

SILICON PLANAR VARIABLE CAPACITANCE DIODE

The BB909 is a variable capacitance diode in a glass envelope intended for electronic tuning in v.h.f. television tuners for C.A.T.V. applications.

Diodes are supplied in matched sets (minimum 120 pieces and divisible by 12) and the capacitance difference between any two diodes in one set is less than 2,5% over the voltage range from 1 V to 28 V.

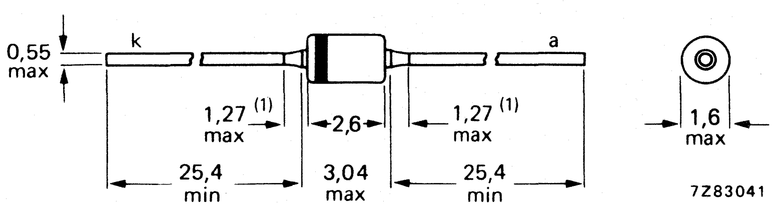
QUICK REFERENCE DATA

			BB909A	BB909B	
Reverse voltage (peak value)	V_{RM}	max.		32	V
Reverse current at V_R = 28 V	I_R	<		10	nA
Diode capacitance at f = 0,5 MHz			BB909A	BB909B	
V_R = 1 V	C_d	>	31	33,5	pF
V_R = 28 V	C_d		2,6–3,0	2,8–3,2	pF
Capacitance ratio at f = 0,5 MHz	$\frac{C_d (V_R = 1\ V)}{C_d (V_R = 28\ V)}$		12–15		
Series resistance at f = 100 MHz V_R is that value at which C_d = 30 pF	r_s	typ. <		0,7 0,9	Ω Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 DO-34 (SOD-68).



(1) Lead diameter in this zone uncontrolled.

BB909B : green cathode ring; body black coloured.
BB909A : additional red band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Reverse voltage (peak value)	V_{RM}	max.	32 V
Forward current (d.c.)	I_F	max.	20 mA
Storage temperature	T_{stg}		−55 to + 150 °C
Operating junction temperature	T_j	max.	100 °C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\,j\text{-}a}$	=	0,6 K/mW

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Reverse current			
V_R = 28 V	I_R	<	10 nA
V_R = 28 V; T_{amb} = 85 °C	I_R	<	200 nA

		BB909A	BB909B
Diode capacitance at f = 0,5 MHz			
V_R = 1 V	C_d	> 31	> 33,5 pF
V_R = 3 V	C_d	typ. 23	25 pF
V_R = 28 V	C_d	2,6–3,0	2,8–3,2 pF

Capacitance ratio at f = 0,5 MHz	$\frac{C_d\ (V_R = 1\ V)}{C_d\ (V_R = 28\ V)}$		12–15
Series resistance at f = 100 MHz; V_R is that value at which C_d = 30 pF	r_s	typ.	0,7 Ω
		<	0,9 Ω
Tolerance of the capacitance difference between two diodes at V_R = 1 to 28 V	$\frac{\Delta C}{C}$	<	2,5 %

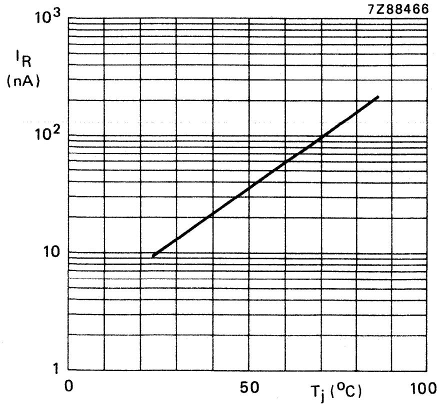


Fig. 2 Reverse current as a function of junction temperature at $V_R = 28$ V.

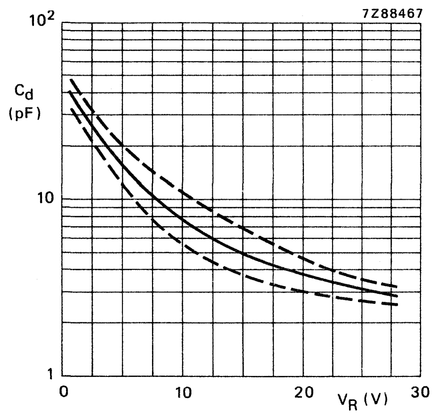


Fig. 3 Diode capacitance as a function of reverse voltage.

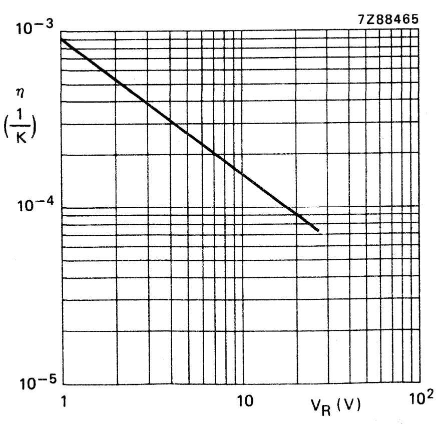


Fig. 4 Temperature coefficient of the diode capacitance as a function of reverse voltage at $T_j = 0$ to 85 °C.

VHF VARIABLE CAPACITANCE DIODE

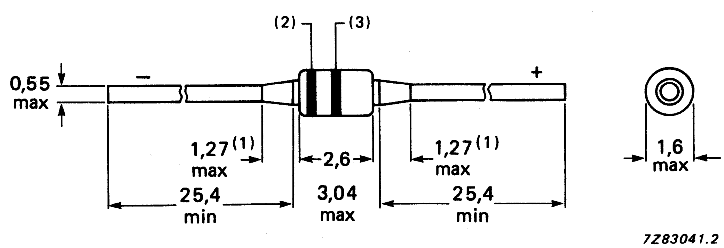
The BB910 is a VHF variable capacitance diode in planar technology with a very high capacitance ratio intended for VHF-band B up to 460 MHz in all-band tuners.
The diode is encapsulated in the whiskerless glass envelope SOD-68.

QUICK REFERENCE DATA

Reverse voltage, peak value	V_{RM}	max.	32 V
Reverse current V_R = 28 V	I_R	<	10 nA
Diode capacitance at f = 1 MHz V_R = 0.5 V	C_d	>	38 pF
V_R = 28 V	C_d		2.4 to 2.7 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d (V_R = 0.5 V)}{C_d (V_R = 28 V)}$	>	14
Series resistance at f = 100 MHz V_R is that value at which C_d = 40 pF	r_s	<	1.0 Ω

MECHANICAL DATA

Dimensions in mm



(1) Lead diameter in this zone uncontrolled
(2) Cathode type taping (on black body)
(3) Additional ring for type taping.

Fig. 1 SOD-68.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Reverse voltage, peak value	V_{RM}	max.	32	V
Forward current (DC)	I_F	max.	20	mA
Storage temperature range	T_{stg}		−55 to + 150	°C
Operating junction temperature	T_j	max.	100	°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0.6	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Reverse current				
V_R = 28 V	I_R	<	10	nA
V_R = 28 V; T_{amb} = 85 °C	I_R	<	200	nA
Diode capacitance at f = 1 MHz				
V_R = 0.5 V	C_d	>	38	pF
V_R = 28 V	C_d		2.4 to 2.7	pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 0.5\ V)}{C_d\ (V_R = 28\ V)}$	>	14	
Series resistance at f = 100 MHz and at that value of V_R at which C_d = 40 pF	r_s	<	1.0	Ω
Tolerance of capacitance difference between two diodes at V_R = 0.5 to 28 V	$\frac{\Delta C}{C}$	<	2.5	%

VHF VARIABLE CAPACITANCE DIODE

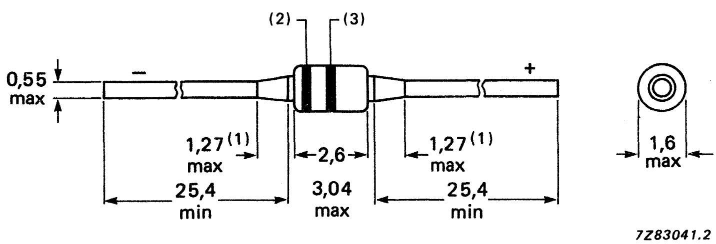
The BB911 is a VHF variable capacitance diode in planar technology with a very high capacitance ratio intended for VHF-band A up to 160 MHz in all-band tuners.
The diode is encapsulated in the whiskerless glass envelope SOD-68.

QUICK REFERENCE DATA

Reverse voltage, peak value	V_{RM}	max.	32 V
Reverse current			
V_R = 28 V	I_R	<	10 nA
Diode capacitance at f = 1 MHz			
V_R = 0.5 V	C_d	>	63 pF
V_R = 28 V	C_d		2.5 to 3.0 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 0.5\ V)}{C_d\ (V_R = 28\ V)}$	>	21
Series resistance at f = 100 MHz			
V_R is that value at which C_d = 40 pF	r_s	<	2.0 Ω

MECHANICAL DATA

Dimensions in mm



(1) Lead diameter in this zone uncontrolled
(2) Cathode type taping (on black body)
(3) Additional ring for type taping.

Fig. 1 SOD-68.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Reverse voltage, peak value	V_{RM}	max.	32 V
Forward current (DC)	I_F	max.	20 mA
Storage temperature range	T_{stg}		−55 to +150 °C
Operating junction temperature	T_j	max.	100 °C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0.6 K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Reverse current			
V_R = 28 V	I_R	<	10 nA
V_R = 28 V; T_{amb} = 85 °C	I_R	<	200 nA
Diode capacitance at f = 1 MHz			
V_R = 0.5 V	C_d	>	63 pF
V_R = 28 V	C_d		2.5 to 3.0 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 0.5\ V)}{C_d\ (V_R = 28\ V)}$	>	21
Series resistance at f = 100 MHz and at that value of V_R at which C_d = 40 pF	r_s	<	2.0 Ω
Tolerance of capacitance difference between two diodes at V_R = 1 to 28 V	$\frac{\Delta C}{C}$	<	2.5 %

VARIABLE CAPACITANCE DIODE

Silicon planar variable capacitance diode in a microminiature envelope. It is intended for electronic tuning applications in thick and thin-film circuits.

QUICK REFERENCE DATA

Reverse voltage	V_R	max.	28 V
Reverse current at V_R = 28 V	I_R	<	50 nA
Diode capacitance at f = 1 MHz V_R = 28 V	C_d		1,6 to 2,0 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 1\ V)}{C_d\ (V_R = 28\ V)}$	typ.	9,7
Series resistance at f = 470 MHz V_R = that value at which C_d = 9 pF	r_D	<	1,2 Ω

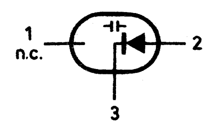
MECHANICAL DATA

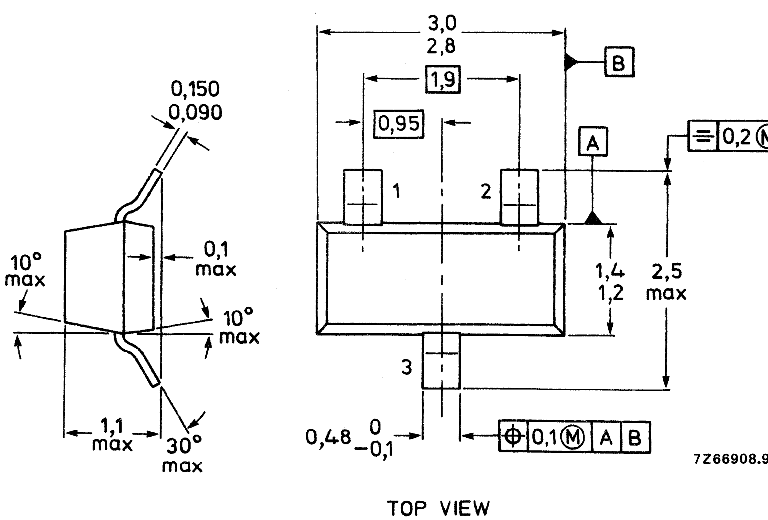
Dimensions in mm

Fig. 1 SOT-23.

Marking code

BBY31 = S1





See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	28 V
Reverse voltage (peak value)	V_{RM}	max.	30 V
Forward current (d.c.)**	I_F	max.	20 mA
Storage temperature	T_{stg}	−65 to + 100 °C	
Operating junction temperature	T_j	max.	85 °C

THERMAL RESISTANCE

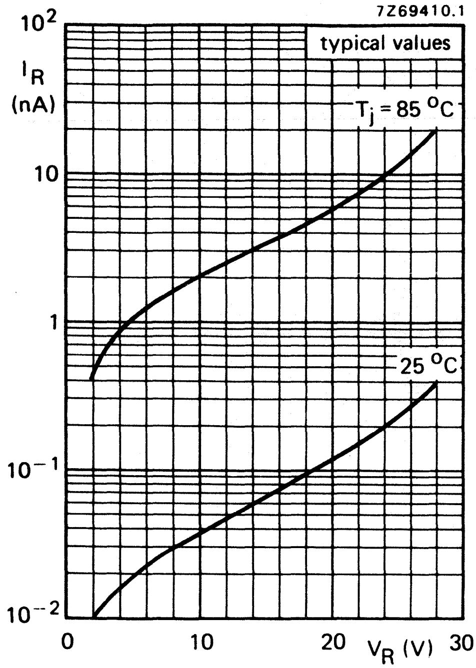
From junction to ambient*	$R_{th\ j\text{-}a}$	=	430 K/W

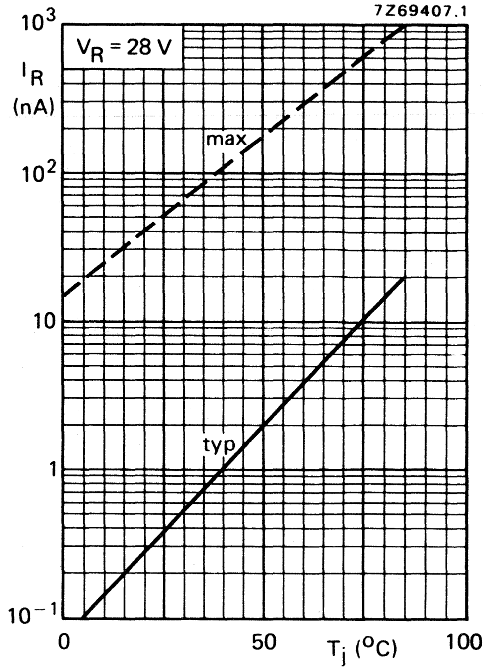
CHARACTERISTICS

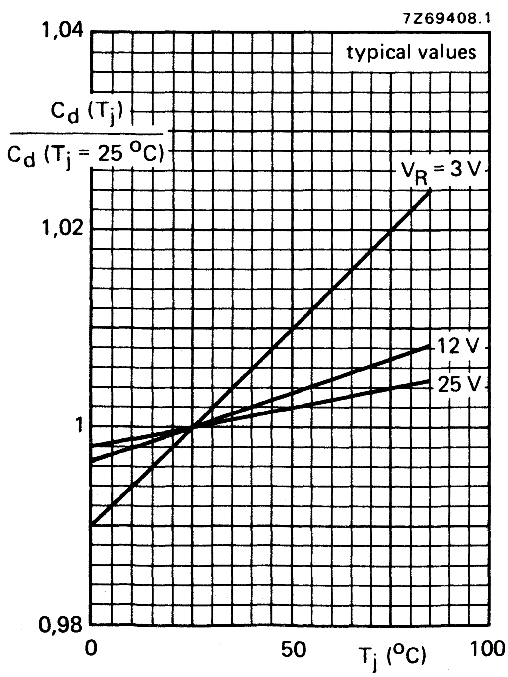
T_j = 25 °C unless otherwise specified

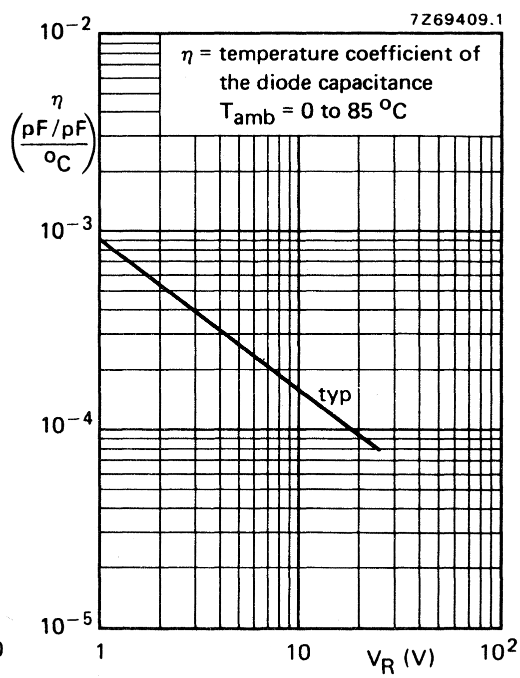
Reverse current			
V_R = 28 V	I_R	<	50 nA
V_R = 28 V; T_j = 85 °C	I_R	<	1000 nA
Diode capacitance at f = 1 MHz			
V_R = 1 V	C_d	typ.	17,5 pF
V_R = 28 V	C_d		1,6 to 2,0 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 1\ V)}{C_d\ (V_R = 28\ V)}$	typ.	9,7
Series resistance at f = 470 MHz and at that value of V_R at which C_d = 9 pF	r_D	<	1,2 Ω

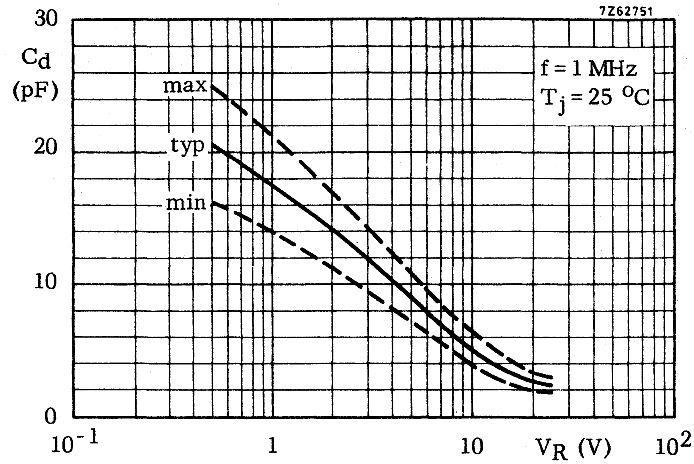
* Mounted on a ceramic substrate of 7 mm x 5 mm x 0,5 mm.


7Z69410.1
typical values
I_R (nA)
10^2
10
1
10^{-1}
10^{-2}
T_j = 85 °C
25 °C
0
10
20
V_R (V)
30


7Z69407.1
V_R = 28 V
I_R (nA)
10^3
10^2
10
1
10^{-1}
max
typ
0
50
T_j (°C)
100


7Z69408.1
typical values
$\frac{C_d(T_j)}{C_d(T_j = 25\ °C)}$
1,04
1,02
1
0,98
V_R = 3 V
12 V
25 V
0
50
T_j (°C)
100


7Z69409.1
η = temperature coefficient of
the diode capacitance
T_{amb} = 0 to 85 °C
η $\left(\frac{pF/pF}{°C}\right)$
10^{-2}
10^{-3}
10^{-4}
10^{-5}
typ
1
10
V_R (V)
10^2


7Z62751
30
Cd
(pF)
20
10
0
max
typ
min
f = 1 MHz
Tj = 25 °C
10^-1
1
10
VR (V)
10^2

DOUBLE VARIABLE CAPACITANCE DIODE

The BBY39 is a double variable capacitance diode with a common cathode and mounted in a micro-miniature envelope (SOT-23), suitable for surface mounting. The two diodes in one envelope are matched.

The device is intended for application in electronic tuners in satellite TV systems.

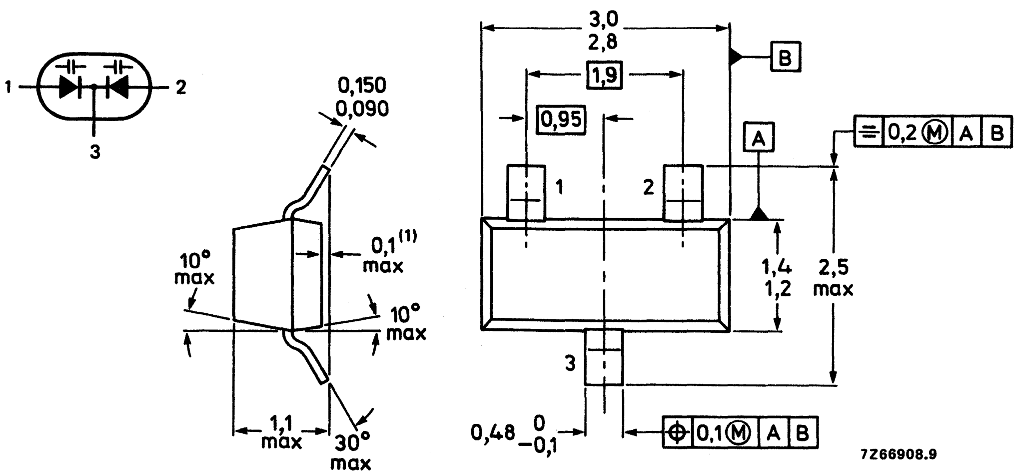
QUICK REFERENCE DATA

For each diode:			
Continuous reverse voltage	V_R	max.	30 V
Operating junction temperature	T_j	max.	85 °C
Reverse current V_R = 28 V	I_R	<	10 nA
Diode capacitance at f = 1 MHz V_R = 28 V	C_d		1,6 to 2,0 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 1\ V)}{C_d\ (V_R = 28\ V)}$	>	8,0
Series resistance at f = 470 MHz V_R is that value at which C_d = 9 pF	r_s	<	1,2 Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.



TOP VIEW

(1) Also available in 0,1 – 0,2 mm version.

RATINGS (for each diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	30	V
Reverse voltage (peak value)	V_{RM}	max.	30	V
Forward current (d.c.)	I_F	max.	20	mA
Storage temperature	T_{stg}		−65 to +100	°C
Operating junction temperature	T_j	max.	85	°C

THERMAL RESISTANCE

From junction to ambient *	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS (for each diode)

T_j = 25 °C unless otherwise specified

Reverse current				
V_R = 28 V	I_R	<	10	nA
V_R = 28 V; T_j = 85 °C	I_R	<	100	nA
Diode capacitance at f = 1 MHz				
V_R = 1 V	C_d	typ.	17,5	pF
V_R = 28 V	C_d		1,8 to 2,0	pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 1\ V)}{C_d\ (V_R = 28\ V)}$	>	7,6	
Series resistance at f = 470 MHz and that value of V_R at which C_d = 9 pF	r_s	<	0,75	Ω

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

SILICON PLANAR VARIABLE CAPACITANCE DIODE

The BBY40 is a variable capacitance diode in a plastic envelope intended for electronic tuning in VHF television tuners with extended band I (FCC and OIRT-norm).

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	28 V
Reverse current at V_R = 28 V	I_R	<	10 nA
Diode capacitance at f = 1 MHz			
V_R = 1 V	C_d		39 to 46 pF
V_R = 28 V	C_d		3.8 to 4.8 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 1\ V)}{C_d\ (V_R = 28\ V)}$		8 to 12
Series resistance at f = 200 MHz			
V_R is that value at which C_d = 25 pF	r_S	<	0.7 Ω

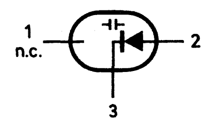
MECHANICAL DATA

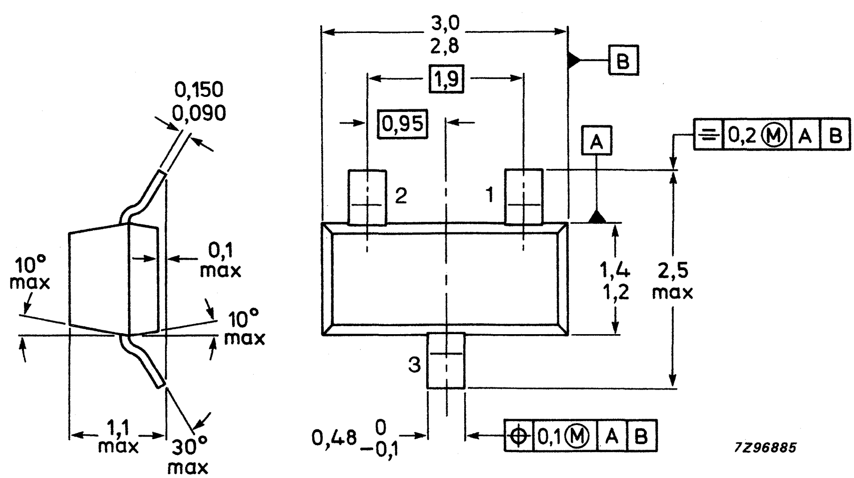
Dimensions in mm

Fig. 1 SOT-23.

Marking code

BBY40 = S2





TOP VIEW

See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	28 V
Reverse voltage (repetitive peak value)	V_{RRM}	max.	30 V
Forward current (DC)	I_F	max.	20 mA
Storage temperature	T_{stg}		−55 to +100 °C
Operating junction temperature	T_j	max.	85 °C

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j\text{-}a}$	=	430 K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Reverse current			
→ V_R = 28 V	I_R	typ.	0.1 nA
		<	10 nA
→ V_R = 28 V; T_{amb} = 60 °C	I_R	<	100 nA
Diode capacitance at f = 1 MHz			
V_R = 1 V	C_d		39 to 46 pF
→ V_R = 3 V	C_d	typ.	29.0 pF
V_R = 28 V	C_d		3.8 to 4.8 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 1\ V)}{C_d\ (V_R = 28\ V)}$		8 to 12
Series resistance at f = 200 MHz			
→ V_R is that value at which C_d = 25 pF	r_s	<	0.7 Ω

* Mounted on a ceramic substrate of 7 mm x 5 mm x 0.5 mm.

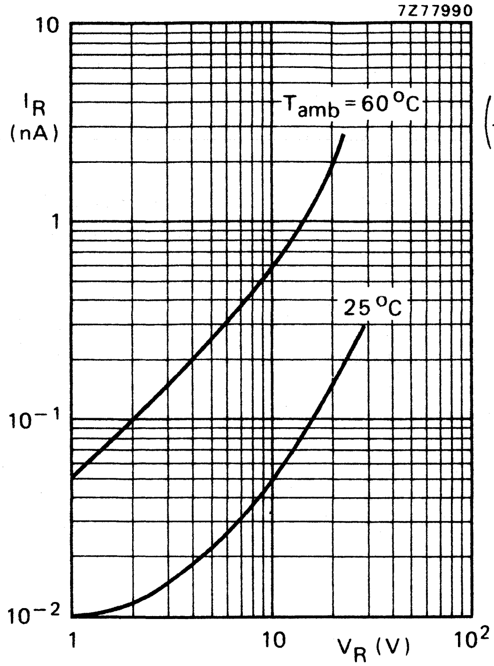


Fig. 2 Typical values

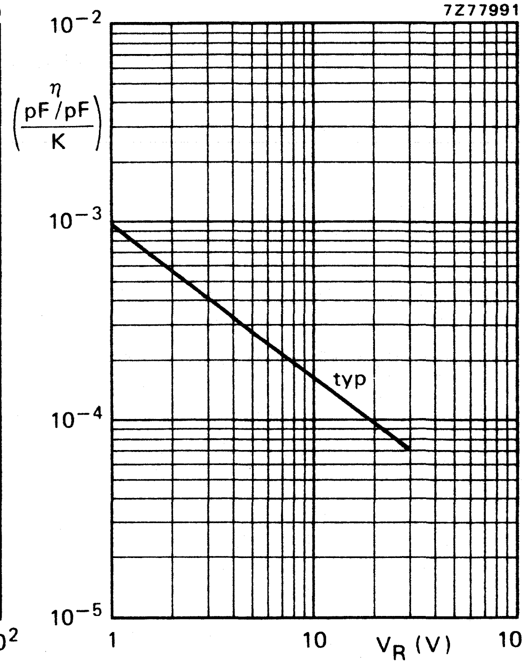


Fig. 3 Temperature coefficient of the diode capacitance; T_{amb} = 0 to 85 °C.

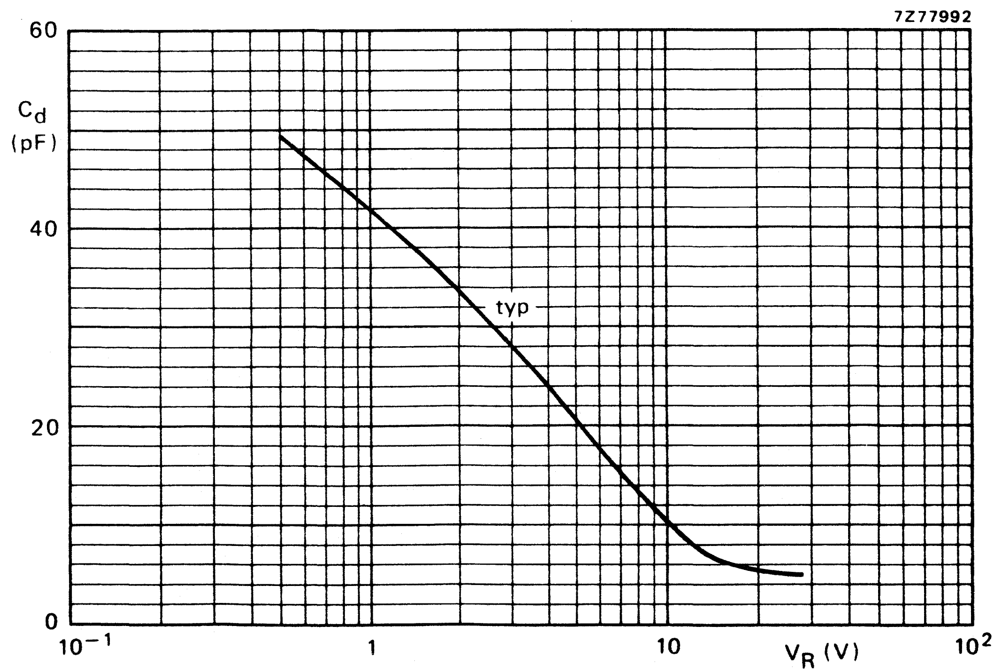


Fig. 4 f = 1 MHz; T_{amb} = 25 °C.

V.H.F. VARIABLE CAPACITANCE DIODE

The BBY42 is a variable capacitance diode in a microminiature plastic envelope SOT-23. It is intended for use in v.h.f. TV tuners and CATV applications using SMD technology.

QUICK REFERENCE DATA

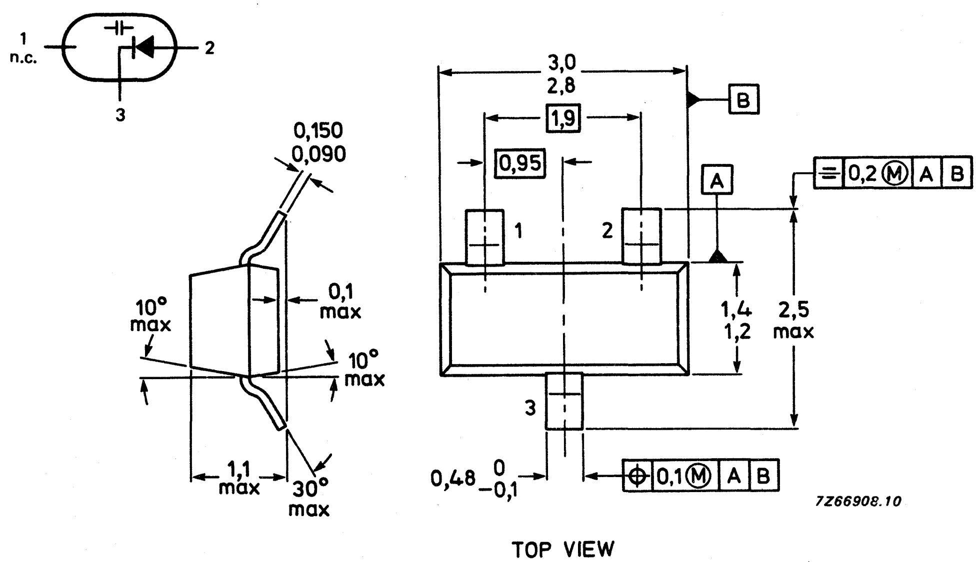
Reverse voltage, peak value	V_{RM}	max. 32 V
Reverse current V_R = 28 V	I_R	max. 10 nA
Diode capacitance at f = 1 MHz V_R = 28 V	C_d	2,4 to 3,0 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d (V_R = 1\ V)}{C_d (V_R = 28\ V)}$	12 to 16
Series resistance at f = 100 MHz V_R is that value at which C_d = 30 pF	r_s	typ. 0,9 Ω max. 1,0 Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.

Marking code: S13



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Reverse voltage (peak value)	V_{RM}	max.	32 V
Forward current (d.c.)	I_F	max.	20 mA
Storage temperature	T_{stg}	−65 to + 100	°C
Operating junction temperature	T_j	max.	85 °C

THERMAL RESISTANCE

From junction to ambient and mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm	$R_{th\ j\text{-}a}$	=	430 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Reverse current			
V_R = 28 V	I_R	<	10 nA
V_R = 28 V; T_j = 85 °C	I_R	<	200 nA
Diode capacitance at f = 1 MHz			
V_R = 1 V	C_d	>	31 pF
V_R = 3 V	C_d	typ.	24 pF
V_R = 28 V	C_d		2,4 to 3,0 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d (V_R = 1\ V)}{C_d (V_R = 28\ V)}$		12 to 16
Series resistance at f = 100 MHz and at that value of V_R at which C_d = 30 pF	r_s	typ.	0,9 Ω
		<	1,0 Ω

DOUBLE VARIABLE CAPACITANCE DIODE

The BBY62 is a double variable capacitance diode and mounted in a microminiature envelope (SOT-143).

The device is intended for application in electronic tuners using SMD technology.

QUICK REFERENCE DATA

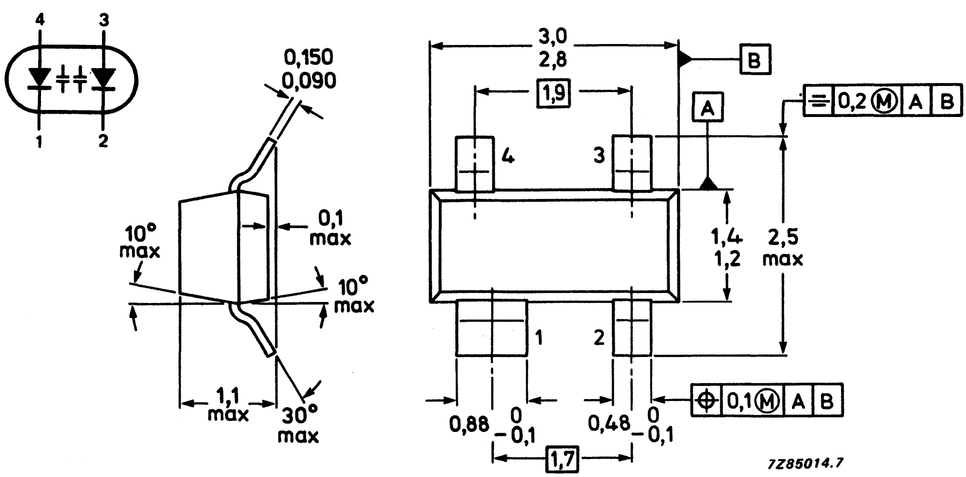
For each diode:			
Continuous reverse voltage	V_R	max.	28 V
Reverse current $V_R = 28$ V	I_R	<	50 nA
Diode capacitance at f = 1 MHz $V_R = 28$ V	C_d		1,6 to 2,0 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d(V_R = 1\ V)}{C_d(V_R = 28\ V)}$	typ.	9,7
Series resistance at f = 470 MHz V_R is that value at which $C_d = 9$ pF	r_s	<	1,2 Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-143.

Marking code: S4



TOP VIEW

RATINGS (for each diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	28	V
Reverse voltage (peak value)	V_{RM}	max.	30	V
Forward current (d.c.)	I_F	max.	20	mA
Storage temperature	T_{stg}		−65 to + 100	°C
Operating junction temperature	T_j	max.	85	°C

THERMAL RESISTANCE

From junction to ambient and mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS (for each diode)

T_j = 25 °C unless otherwise specified

Reverse current				
V_R = 28 V	I_R	<	50	nA
V_R = 28 V; T_j = 85 °C	I_R	<	1	μA
Diode capacitance at f = 1 MHz				
V_R = 1 V	C_d	typ.	17,5	pF
V_R = 28 V	C_d		1,6 to 2,0	pF
Capacitance ratio at f = 1 MHz	$\frac{C_d(V_R = 1\ V)}{C_d(V_R = 28\ V)}$	typ.	9,7	
Series resistance at f = 470 MHz and at that value of V_R at which C_d = 9 pF	r_s	<	1,2	Ω

HIGH-VOLTAGE TRIPLER UNITS

Extra-high-tension supply unit in a small housing intended for use in colour television receivers. A protection resistor for the diodes is incorporated in the unit. A sixth diode is to be used as a clamping diode.
The device has a non-flammable encapsulation and is also available with different lead lengths. To enable mounting on a BG 1895 mounting base a mechanical adapter, type number 56397, is available (see 'Accessories').

QUICK REFERENCE DATA

Input voltage (peak-to-peak value)	$V_{i(p-p)}$	max.	10	kV
Output voltage (d.c.) for e.h.t. supply	$V_{O(EHT)}$	max.	27,5	kV
Output current (d.c.) for e.h.t. supply	$I_{O(EHT)}$	max.	1,7	mA
Output current for focus supply	$I_{O(FOC)}$	max.	400	μA
Main mechanical dimensions		24 mm x 52 mm x 51 mm		

MECHANICAL DATA see next page

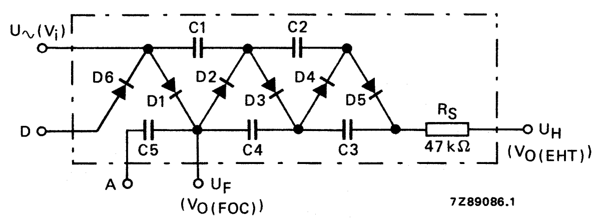
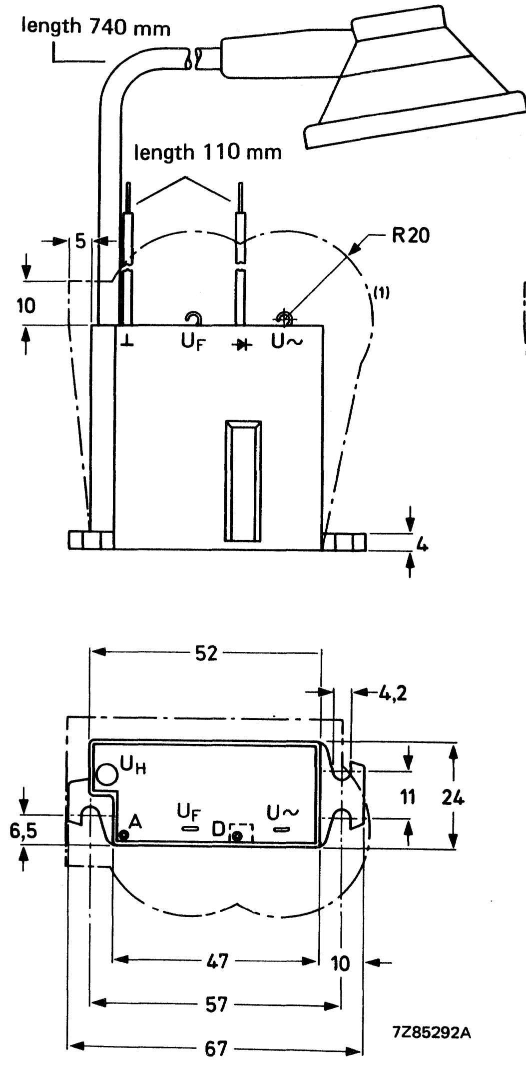


Fig. 1 Circuit diagram.

Dimensions in mm



* Clearance between encapsulation and any other component

Fig. 2 Mechanical data.

The encapsulation is of non-flammable material fulfilling IEC recommendation 65-14.4. Mounting on a metal chassis is permissible.

Weight: approx. 126 g. Mounting instructions: M4 screw; torque 1,5 Nm (15 kg cm).

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Input voltage (peak-to-peak value)	$V_{i(p-p)}$	max.	10,0	kV
Output voltage (d.c.)	$V_{OM(EHT)}$	max.	27,5	kV
Output current (d.c.) for e.h.t. supply	$I_{O(EHT)}$	max.	1,7	mA
Output current for focus supply	$I_{O(FOC)}$	max.	400	μA
Input current of diode D6	$I_{I(D6)}$	max.	4,0	mA
Storage temperature	T_{stg}	−25 to + 70		°C
Operating ambient temperature	T_{amb}	max.	65	°C

CHARACTERISTICS

T_{amb} = 25 °C

Input voltage (peak-to-peak value) for $V_{O(EHT)}$ = 27,5 V at $I_{(O(EHT)}$ = 1,7 mA; $I_{O(FOC)}$ = 400 μA; $I_{I(D6)}$ = 4 mA	$V_{i(p-p)}$	≤	9,5	kV
Internal resistance $I_{O(EHT)}$ = 0,1 to 1,5 mA; $V_{i(p-p)}$ is constant	R_i	typ.	500	kΩ
Input capacitance	C_i	typ.	10	pF

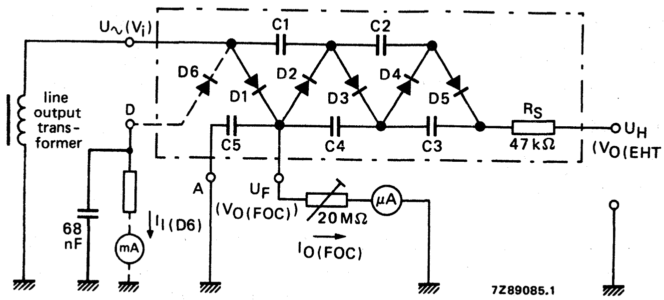


Fig. 3 Test circuit

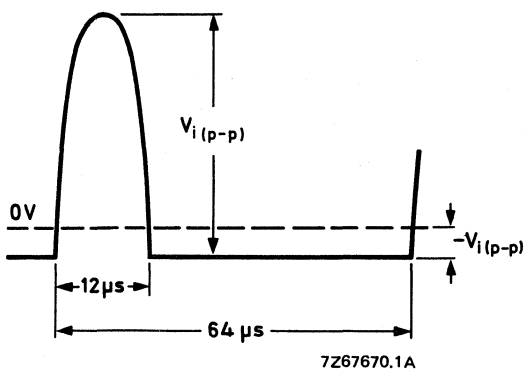


Fig. 4 Input voltage pulse.

EXAMPLE OF OPERATION

$T_{amb} \leq 65$ °C; see also Fig. 5

Input voltage (peak-to-peak value)	$V_{i(p\text{-}p)}$	8,6 kV
Output voltage (d.c.) for e.h.t. supply	$V_{O(EHT)}$	25 kV
Output current (d.c.) for e.h.t. supply	$I_{O(EHT)}$	1,5 mA
Output current for focus supply	$I_{O(FOC)}$	300 μA
Input current of diode D6	$I_{I(D6)}$	3,7 mA
Resistor (R) current for V_{G2} voltage divider (see Fig. 5)	$I_{resistor}$	2,0 mA

The resistor (R_s) of 47 kΩ in the tripler is essential for protection of the silicon diodes in the tripler and the output power transistor in the horizontal deflection circuit, it also acts to suppress radiation. Its contribution to the e.h.t. source impedance is negligible.

The diode D6 can be used in conjunction with an RC circuit to clamp negative voltage pulses, and reduce the e.h.t. source impedance during periods of low beam current.

Separate connections for D6 and the capacitor C5 are provided in the interest of flexibility in circuit layout.

APPLICATION INFORMATION

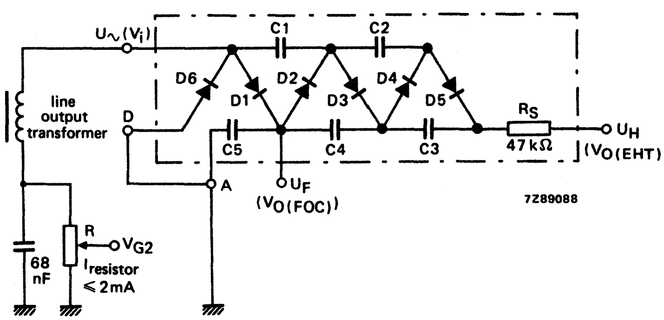


Fig. 5.

HIGH-VOLTAGE TRIPLER UNITS

Extra-high-tension supply unit in a small housing intended for use in colour television receivers. A protection resistor for the diodes is incorporated in the unit. Two versions are available:

BG2097-641 integrated focus resistor in series with the bleeder resistor;
BG2097-642 same as 641 with focus potentiometer.

The devices have non-flammable encapsulations. To enable mounting on a BG1895 mounting base a mechanical adapter, type number 56397, is available (see "Accessories").

QUICK REFERENCE DATA

Input voltage (peak-to-peak value)	$V_{i(p-p)}$	max.	10	kV
Output voltage (d.c.) for e.h.t. supply	$V_{O(EHT)}$	max.	27,5	kV
Focus output voltage range; $V_O(EHT) = 25$ kV;				
20AX television	$V_{O(FOC)}$		4 to 5,3	kV
30AX television	$V_{O(FOC)}$		6,5 to 7,45	kV
Output current (d.c.) for e.h.t. supply	$I_{O(EHT)}$	max.	1,7	mA
Current through bleeder resistor	I_{BL}	>	70	µA
Input current of diode D6	$I_{I(D6)}$	<	4	mA
Main dimensions (without focus potentiometer)		24 mm x 80 mm x 51		mm

MECHANICAL DATA see next page

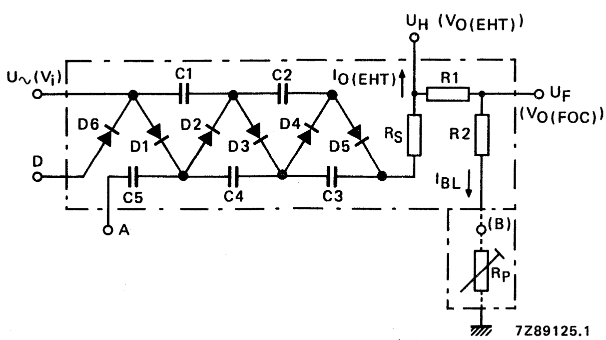
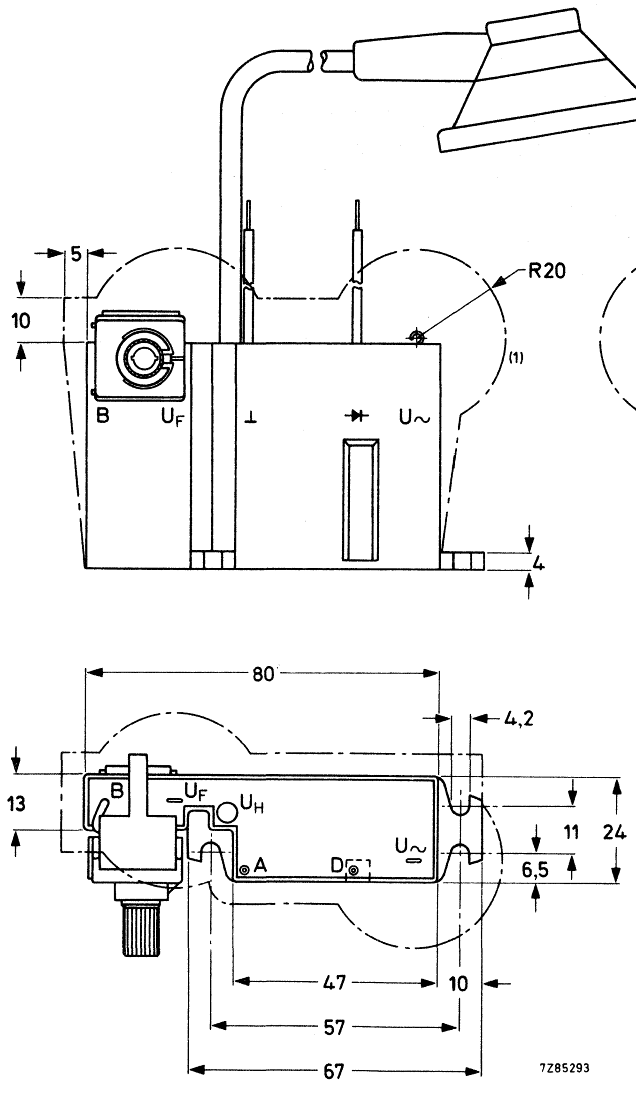


Fig. 1 Circuit diagram.

Dimensions in mm



* Clearance between encapsulation and any other component

Fig. 2 Mechanical data.

The encapsulation is of non-flammable material fulfilling IEC recommendation 65-14.4. Mounting on a metal chassis is permissible.

Weight: approx. 165 g. Mounting instructions: M4 screw; torque 1,5 Nm (15 kg cm).

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Input voltage (peak-to-peak value) without load	$V_{i(p-p)}$	max.	10,0	kV
Output voltage (d.c.)	$V_{OM(EHT)}$	max.	27,5	kV
Output current (d.c.) for e.h.t. supply	$I_{O(EHT)}$	max.	1,7	mA
Input current of diode D6	$I_{I(D6)}$	max.	4,0	mA
Storage temperature	T_{stg}		−25 to + 70	°C
Operating ambient temperature	T_{amb}	max.	65	°C

CHARACTERISTICS

T_{amb} = 25 °C

Input voltage (peak-to-peak value) for $V_{O(EHT)}$ = 27,5 V at $I_{O(EHT)}$ = 1,7 mA; $I_{I(D6)}$ = 4 mA	$V_{i(p-p)}$	$\leqslant$	9,5	kV
Internal resistance $I_{O(EHT)}$ = 0,1 to 1,5 mA; $V_{i(p-p)}$ is constant	R_i	typ.	500	kΩ
Input capacitance	C_i	typ.	10	pF
Value of focus adjusting potentiometer▲	R_P	typ.	30	MΩ
Adjustable focus output voltage range; $V_{O(EHT)}$ = 25 kV				
20AX television	$V_{O(FOC)}$		4 to 5,3	kV
30AX television	$V_{O(FOC)}$		6,5 to 7,45	kV
Bleeder resistance				
20AX television	R1	typ.	256	MΩ
30AX television*	R1	typ.	221	MΩ
R2 will be accommodated to the adjustment range of $V_{O(FOC)}$				
Current through bleeder resistor; $V_{O(EHT)}$ = 25 kV	I_{BL}	>	70	μA

* Tripler for 30AX television is identified by the first digit of the third group of numbers of the type number e.g. BG2097-641-3.

▲ For BG2097-641 an external potentiometer of 30 MΩ ± 15% is necessary to realize the given adjustment range of $V_{O(FOC)}$.

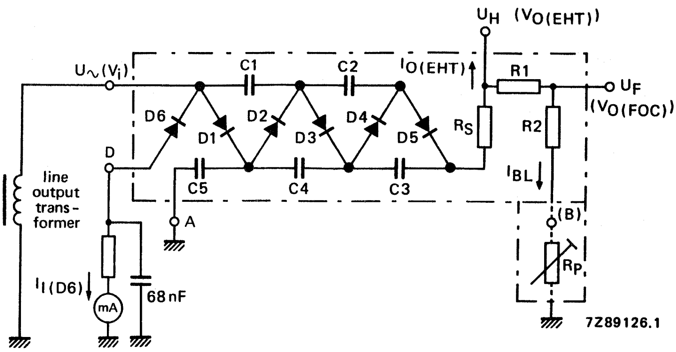


Fig. 3 Test circuit.

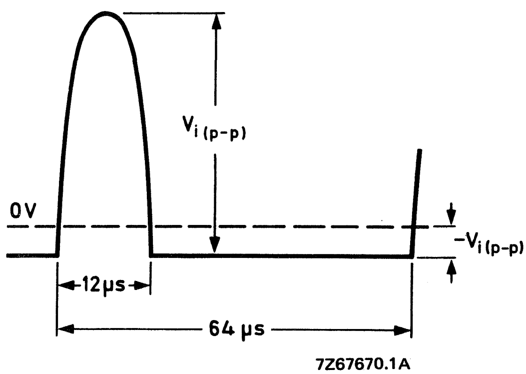


Fig. 4 Input voltage pulse.

EXAMPLE OF OPERATION

$T_{amb} \leq 65\ ^oC$

Input voltage (peak-to-peak value)	$V_{i(p-p)}$	typ.	8,6 kV
Output voltage (d.c.) for e.h.t. supply	$V_{O(EHT)}$	typ.	25 kV
Output current (d.c.) for e.h.t. supply	$I_{O(EHT)}$	typ.	1,5 mA
Adjustable focus output voltage range			
20AX	$V_{O(FOC)}$		4,0 to 5,3 kV
30AX	$V_{O(FOC)}$		6,5 to 7,45 kV
Current through bleeder resistance	I_{BL}	typ.	85 μA
Input current of diode D6	$I_{I(D6)}$	typ.	3,7 mA
Resistor (R) current for V_{G2} voltage divider (see Fig. 5)	$I_{resistor}$	typ.	2,0 mA

The resistor (R_S) of 47 kΩ in the tripler is essential for protection of the silicon diodes in the tripler and the output power transistor in the horizontal deflection circuit, it also acts to suppress radiation. Its contribution to the e.h.t. source impedance is negligible.

The diode D6 can be used in conjunction with an RC circuit to clamp negative voltage pulses, and reduce the e.h.t. source impedance during periods of low beam current.

Separate connections for D6 and the capacitor C5 are provided in the interest of flexibility in circuit layout.

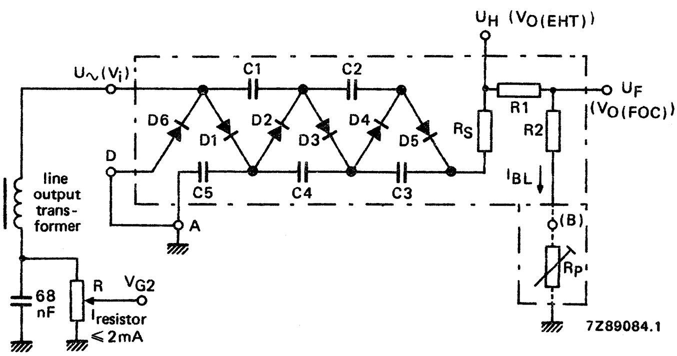


Fig. 5 Example of operation.

PARALLEL EFFICIENCY DIODE

Double-diffused passivated rectifier diode in an hermetically sealed axial-leaded glass envelope, intended for use as efficiency diode in transistorized horizontal deflection circuits of television receivers. The device features high reverse voltage capability with controlled recovery time.

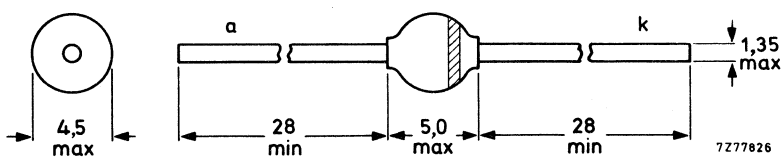
QUICK REFERENCE DATA

Repetitive peak reverse voltage	V_{RRM}	max.	1500	V
Working peak forward current	I_{FWM}	max.	5	A
Repetitive peak forward current	I_{FRM}	max.	10	A
Total reverse recovery time	t_{tot}	<	20	μs

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-64.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Non-repetitive peak reverse voltage during flashover of picture tube	V_{RSM}	max.	1650 V
Repetitive peak reverse voltage	V_{RRM}	max.	1500 V
Working reverse voltage	V_{RW}	max.	1500 V
Working peak forward current	I_{FWM}	max.	5 A
Repetitive peak forward current	I_{FRM}	max.	10 A
Non-repetitive peak forward current t = 10 ms; half sine-wave; T_j = 140 °C prior to surge; with reapplied V_{RWmax}	I_{FSM}	max.	50 A
Storage temperature	T_{stg}		−65 to +175 °C
Junction temperature	T_j	max.	140 °C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\ j\text{-}tp}$	=	25 K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ⩾ 40 μm; Fig. 2 (see "Thermal model")	$R_{th\ j\text{-}a}$	=	75 K/W

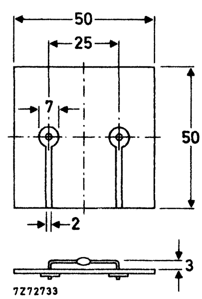


Fig. 2.

CHARACTERISTICS

Forward voltage * I_F = 5 A; T_j = 25 °C	V_F	<	1,5 V*
Reverse current $V_R = V_{RWmax}$; T_j = 140 °C	I_R	<	200 μA
Total reverse recovery time when switched from I_F = 1 A; $-dI_F/dt$ = 0,05 A/μs; T_j = 140 °C	t_{tot}	<	20 μs
Forward recovery time when switched to I_F = 5 A with t_r = 0,1 μs; T_j = 140 °C	t_{fr}	<	1 μs

* Measured under pulse conditions to avoid excessive dissipation.

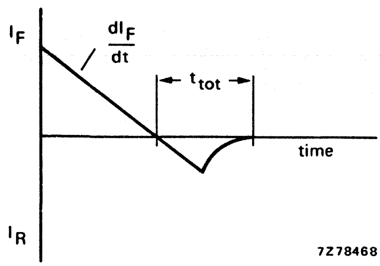


Fig. 3 Definition of t_{tot}.

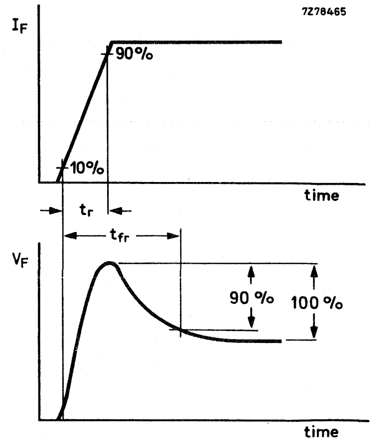


Fig. 4 Definition of t_{fr}.

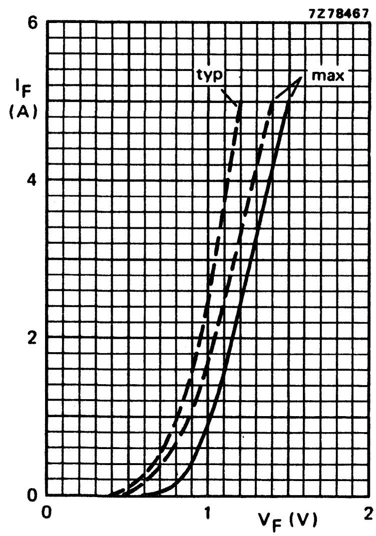


Fig. 5 —— T_j = 25 °C;
– – – T_j = 140 °C.

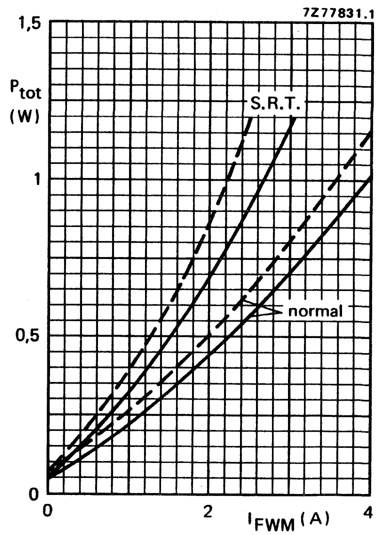


Fig. 6 P_{tot} = power dissipation including switching losses:
– – – – 819 lines; ——— 625 lines;
S.R.T. = self regulating time-base circuit;
normal = conventional deflection circuit or high-voltage E—W modulator circuit;
I_{FWM} is the **nominal** diode current, for tolerances and spreads 25% safety margin is taken into account.

APPLICATION INFORMATION

In designing horizontal deflection circuits, allowance has to be made for component and operating spreads, in order not to exceed any Absolute Maximum Rating.
Extensive analysis have shown that for the working peak forward current and reverse voltage the total allowance need not to be higher than 25%. For that reason the dissipation graph (Fig. 6) is based on the **nominal** I_{FWM}; 25% safety margin for tolerance and spreads is taken into account.

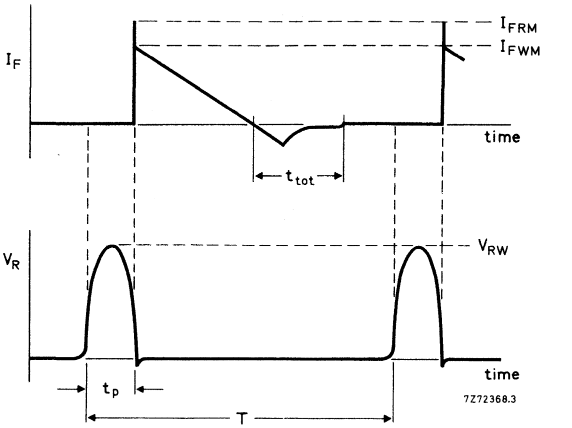


Fig. 7 Basic waveforms.

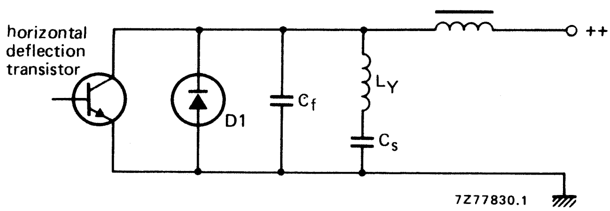


Fig. 8 Basic conventional horizontal deflection circuit. D_1 = BY228.

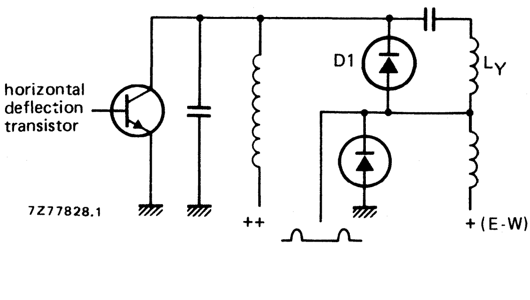


Fig. 9 Basic high-voltage E–W modulator circuit. D_1 = BY228.

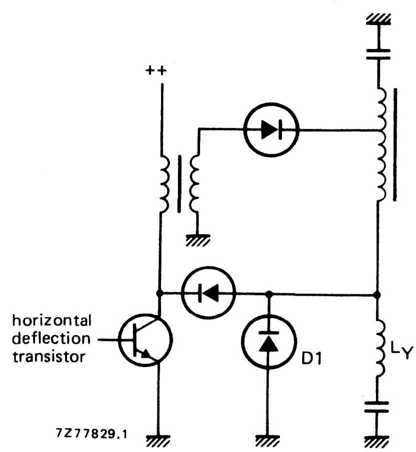


Fig. 10 Basic self-regulating time base circuit (S.R.T.). D_1 = BY228.

32 kHz PARALLEL EFFICIENCY DIODE

Double-diffused glass passivated rectifier diode in an hermetically sealed axial-leaded glass envelope, intended for use as an efficiency diode in transistorized horizontal deflection circuits of television receivers with line frequency up to 32 kHz. The device features high reverse voltage capability with controlled recovery time and fast turn-on.

QUICK REFERENCE DATA

Repetitive peak reverse voltage	V_{RRM}	max.	1400	V
Working peak forward current	I_{FWM}	max.	6	A
Repetitive peak forward current	I_{FRM}	max.	10	A
Total reverse recovery time	t_{tot}	max.	13	μs

MECHANICAL DATA

Dimensions in mm

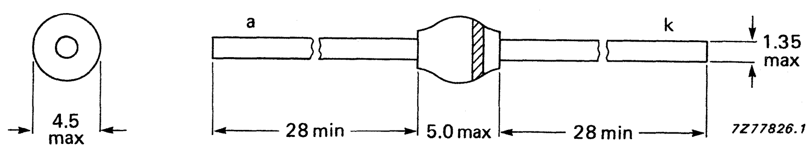


Fig. 1 SOD-64.

The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Non-repetitive peak reverse voltage during flash-over of picture tube	V_{RSM}	max.	1500	V
Repetitive peak reverse voltage	V_{RRM}	max.	1400	V
Working reverse voltage	V_{RW}	max.	1300	V*
Working peak forward current				
T_{tp} = 55 °C; leadlength 10 mm	I_{FWM}	max.	6	A
T_{amb} = 55 °C; Fig. 3	I_{FWM}	max.	4.7	A
T_{amb} = 55 °C; Fig. 2	I_{FWM}	max.	3	A
Repetitive peak forward current	I_{FRM}	max.	10	A
Non-repetitive peak forward current t = 10 ms; half sinewave; T_j = 150 °C prior to surge; with reapplied V_{RWmax}.	I_{FSM}	max.	60	A
Storage temperature range	T_{stg}		−65 to + 175	°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\ j\text{-}tp}$	25	K/W
2. Thermal resistance from junction to ambient when mounted on a 1.5 mm thick epoxyglass printed-circuit board; Cu-thickness ⩾ 40 μm; Fig. 2 (see "Thermal Model")	$R_{th\ j\text{-}a}$	75	K/W
3. Thermal resistance from junction to ambient when mounted as shown in Fig. 3	$R_{th\ j\text{-}a}$	40	K/W

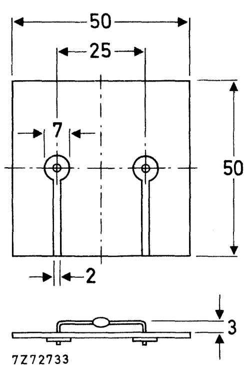


Fig. 2 Mounted on a printed-circuit board.

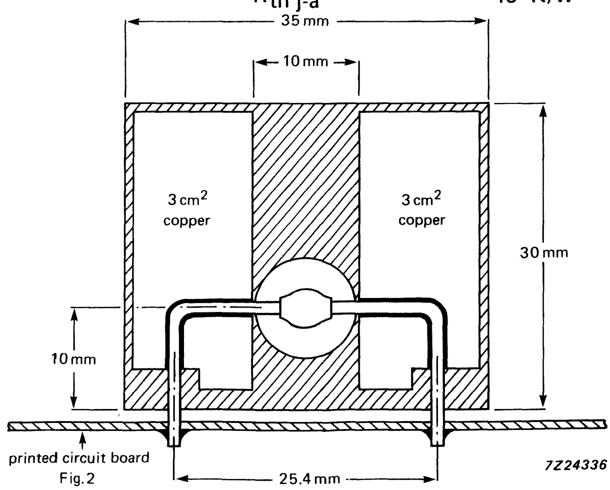


Fig. 3 Mounting

* V_{RW} 1400 V allowed only for a short period, e.g. during adjusting.

CHARACTERISTICS

Forward voltage *			
I_F = 5 A; T_j = 25 °C	V_F	max.	1.45 V
Reverse current			
$V_R = V_{RWmax}$; T_j = 150 °C	I_R	max.	150 μA
Total reverse recovery time when switched from I_F = 1 A; $-dI_F/dt$ = 0.05 A/μs; T_j = 150 °C	t_{tot}	max.	13 μs
Forward recovery time when switched to I_F = 5 A with t_r = 50 ns; T_j = 150 °C	t_{fr}	max.	0.5 μs

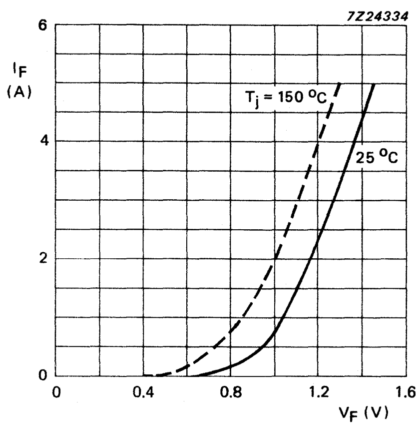


Fig. 4 Maximum forward voltage drop.

DEVELOPMENT DATA

* Measured under pulse conditions to avoid excessive dissipation.

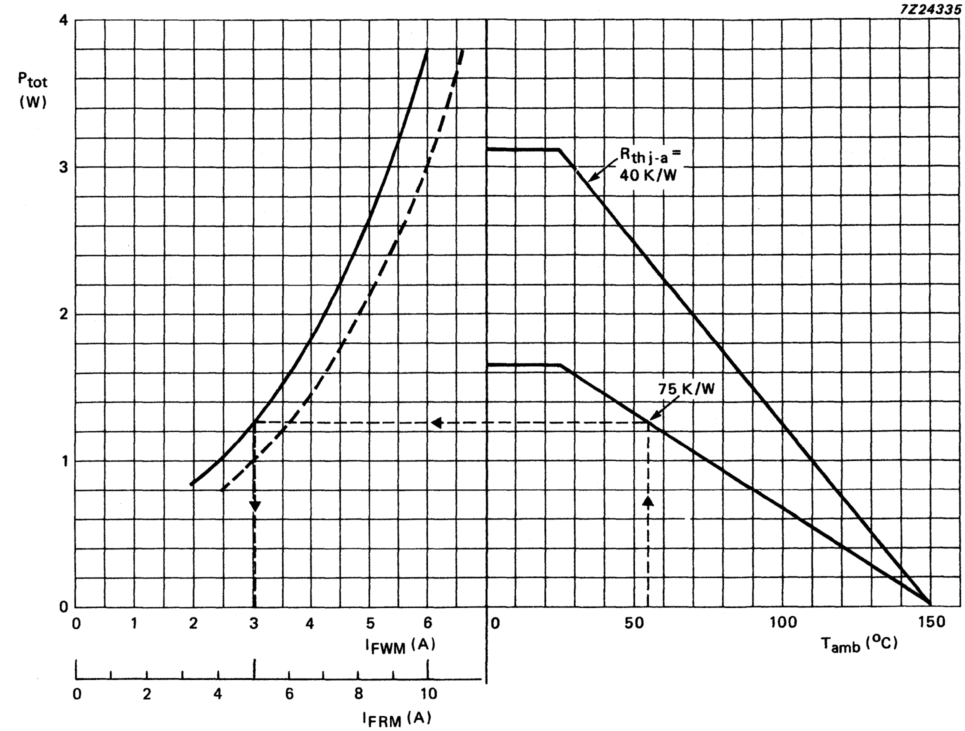


Fig. 5 Total power dissipation, including switching losses, as a function of I_{FWM}; I_{FRM}; and T_{amb}.

——— Basic high-voltage E-W modulator circuit, see Fig. 10.

– – – – Basic conventional horizontal deflection circuit, see Fig. 9.

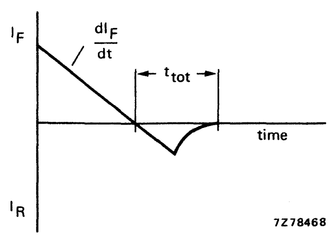


Fig. 6 Definition of t_{tot}.

DEVELOPMENT DATA

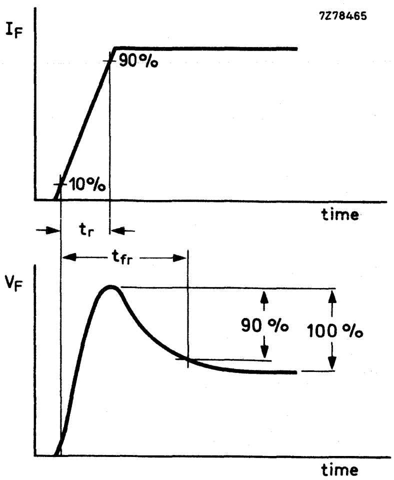


Fig. 7 Definition of t_{fr}.

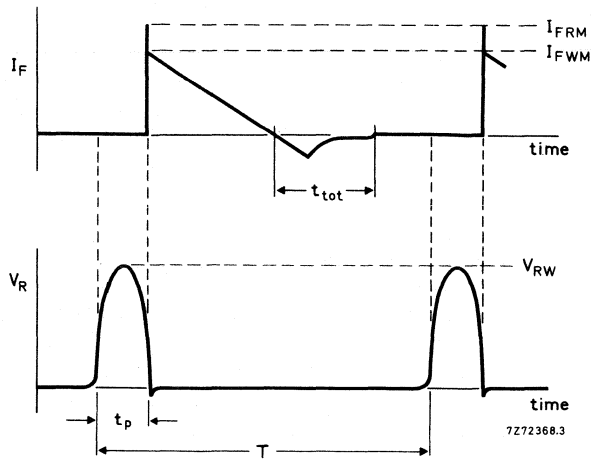


Fig. 8 Basic waveforms.

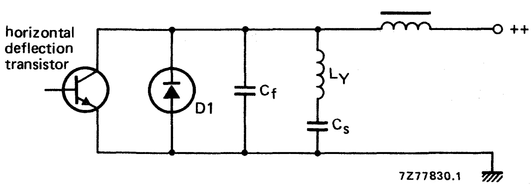


Fig. 9 Basic conventional horizontal deflection circuit. D1 = BY328.

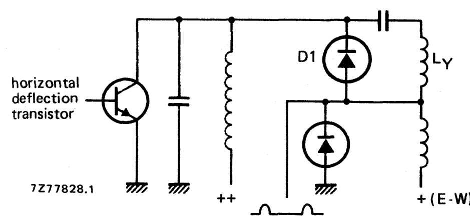


Fig. 10 Basic high-voltage E-W modulator circuit. D1 = BY328.

PARALLEL EFFICIENCY DIODE

Double-diffused passivated rectifier diode in an hermetically sealed axial-leaded glass envelope, intended for use as efficiency diode in transistorized horizontal deflection circuits of television receivers. The device features high reverse voltage capability with controlled recovery time.

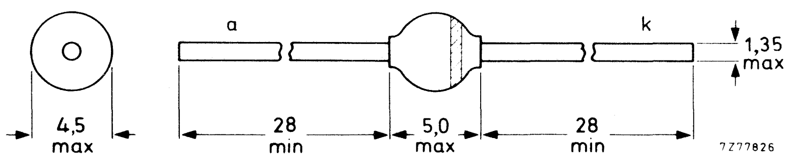
QUICK REFERENCE DATA

Repetitive peak reverse voltage	V_{RRM}	max.	1200	V
Working peak forward current	I_{FWM}	max.	5	A
Repetitive peak forward current	I_{FRM}	max.	10	A
Total reverse recovery time	t_{tot}	<	20	μs

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-64.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Non-repetitive peak reverse voltage during flashover of picture tube	V_{RSM}	max.	1300 V
Repetitive peak reverse voltage	V_{RRM}	max.	1200 V
Working peak forward current	I_{FWM}	max.	5 A
Repetitive peak forward current	I_{FRM}	max.	10 A
Non-repetitive peak forward current $t = 10$ ms; half sine-wave; $T_j = 140$ °C prior to surge; with reapplied V_{RWmax}	I_{FSM}	max.	50 A
Storage temperature	T_{stg}		−65 to +175 °C
Junction temperature	T_j	max.	140 °C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\ j\text{-}tp}$	=	25 K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ⩾ 40 μm; Fig. 2 (see "Thermal model")	$R_{th\ j\text{-}a}$	=	75 K/W

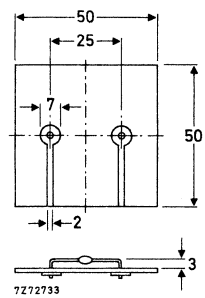


Fig. 2.

CHARACTERISTICS

Forward voltage $I_F = 5$ A; $T_j = 25$ °C	V_F	<	1,5 V*
Reverse current $V_R = V_{RWmax}$; $T_j = 140$ °C	I_R	<	200 μA
Total reverse recovery time when switched from $I_F = 1$ A; $-dI_F/dt = 0{,}05$ A/μs; $T_j = 140$ °C	t_{tot}	<	20 μs
Forward recovery time when switched to $I_F = 5$ A with $t_r = 0{,}1$ μs; $T_j = 140$ °C	t_{fr}	<	1 μs

* Measured under pulse conditions to avoid excessive dissipation.

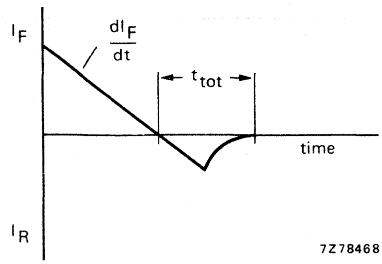


Fig. 3 Definition of t_{tot}.

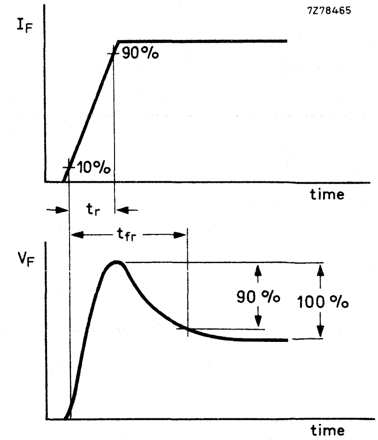


Fig. 4 Definition of t_{fr}.

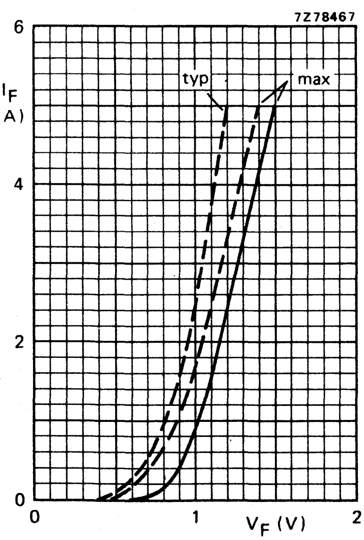


Fig. 5 —— $T_j = 25\ ^oC$; – – – $T_j = 140\ ^oC$.

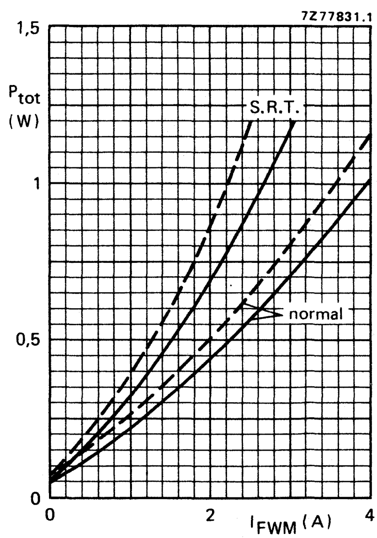


Fig. 6 P_{tot} = power dissipation including switching losses; – – – 819 lines; —— 625 lines; S.R.T. = self regulating time-base circuit; normal = conventional deflection circuit or high-voltage E–W modulator circuit; I_{FWM} is the **nominal** diode current, for tolerances and spreads 25% safety margin is taken into account.

APPLICATION INFORMATION

In designing horizontal deflection circuits, allowance has to be made for component and operating spreads, in order not to exceed any Absolute Maximum Rating.
Extensive analysis have shown that for the working peak forward current and reverse voltage the total allowance need not to be higher than 25%. For that reason the dissipation graph (Fig. 6) is based on the **nominal** I_{FWM}; 25% safety margin for tolerance and spreads is taken into account.

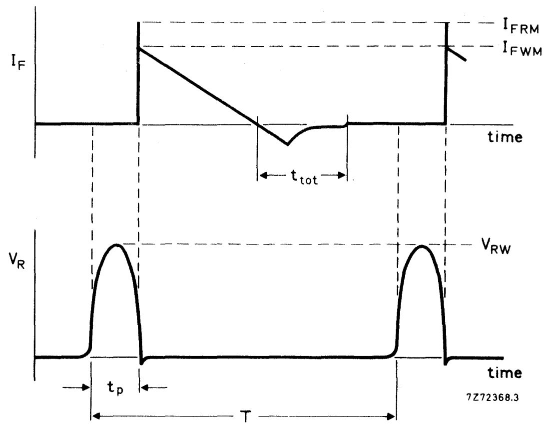


Fig. 7 Basic waveforms.

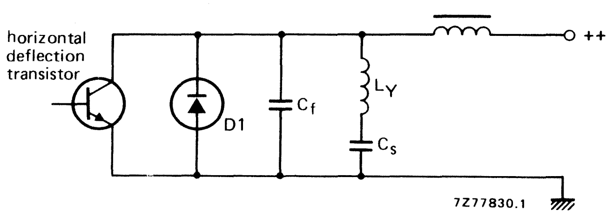


Fig. 8 Basic conventional horizontal deflection circuit. D1 = BY438.

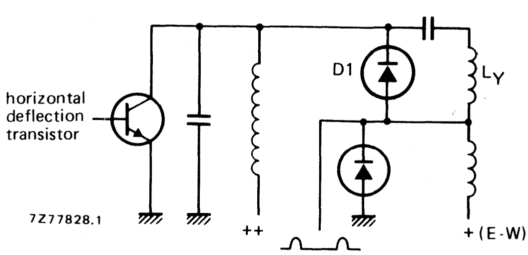


Fig. 9 Basic high-voltage E—W modulator circuit. D1 = BY438.

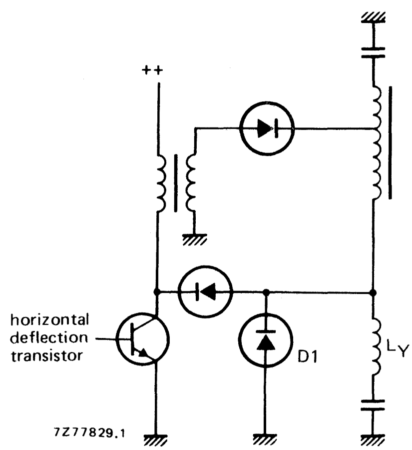


Fig. 10 Basic self-regulating time base circuit (S.R.T.). D1 = BY438.

PARALLEL EFFICIENCY DIODES

Double-diffused passivated rectifier diodes in hermetically sealed axial-leaded glass envelopes, intended for use as efficiency diodes in transistorized horizontal deflection circuits and PPS (power-pack system) circuits of television receivers. The devices feature high reverse voltage capability with controlled recovery time.

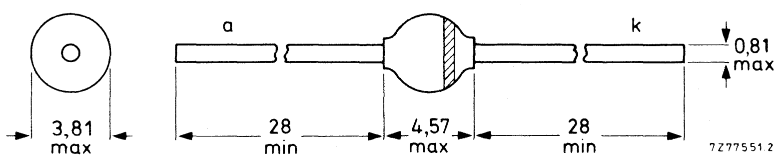
QUICK REFERENCE DATA

			BY458	BY448	
Repetitive peak reverse voltage	V_{RRM}	max.	1200	1500	V
Working peak forward current	I_{FWM}	max.		4	A
Repetitive peak forward current	I_{FRM}	max.		8	A
Total reverse recovery time	t_{tot}	<		20	μs

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-57.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BY458	BY448	
Non-repetitive peak reverse voltage during flashover of picture tube	V_{RSM}	max.	1300	1650	V
Repetitive peak reverse voltage	V_{RRM}	max.	1200	1500	V
Working peak forward current	I_{FWM}	max.	4		A
Repetitive peak forward current	I_{FRM}	max.	8		A
Non-repetitive peak forward current t = 10 ms; half sine-wave; T_j = 140 °C prior to surge; with reapplied V_{RRMmax}	I_{FSM}	max.	30		A
Storage temperature	T_{stg}		−65 to +175		°C
Operating junction temperature	T_j	max.	140		°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm — $R_{th\ j\text{-}tp}$ = 46 K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ⩾ 40 μm; Fig. 2 (see "Thermal model") — $R_{th\ j\text{-}a}$ = 100 K/W

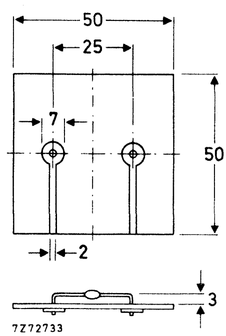


Fig. 2.

MOUNTING AND SOLDERING NOTES

Introduction

Excessive forces or temperatures applied to a diode may cause serious damage to the diode. To avoid damage when soldering and mounting, the following rules have to be followed.

Bending

During bending, the leads must be supported between body and bending point. Axial forces on the body during the bending process must not exceed 50 N. Perpendicular force on the body must be avoided as much as possible, however, if present, it shall not exceed 10 N. Bending the leads through 90° is allowed at any distance from the studs when it is possible to support the leads during the bending without contacting envelope or solder joints.

Twisting

Twisting the leads is allowed at any distance from the body if the lead is properly clamped between stud and twisting point. Without clamping, twisting is allowed only at a distance > 5 mm from the studs, the torque-angle must not exceed 30°.

Soldering

The minimum distance of soldering point to stud is 2 mm, the maximum allowed solder temperature is 300 °C, and the soldering time must not be longer than 10 seconds.

Prevent fast cooling after soldering.

When the device has to be mounted with straight or short-cropped leads, the leads should be soldered individually; bent leads may be soldered simultaneously. Do not correct the position of an already soldered device by pushing, pulling or twisting the body.

CHARACTERISTICS

Forward voltage			
$I_F = 3$ A; $T_j = 25$ °C	V_F	<	1,6 V*
Reverse current			
$V_R = V_{RRMmax}$; $T_j = 140$ °C	I_R	<	200 μA
Total reverse recovery time when switched from			
$I_F = 1$ A; $-dI_F/dt = 0{,}05$ A/μs; $T_j = 140$ °C	t_{tot}	<	20 μs

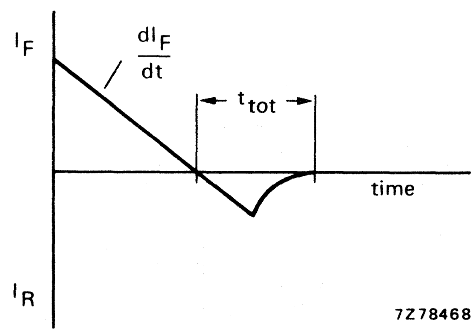


Fig. 3 Definition of t_{tot}.

* Measured under pulse conditions to avoid excessive dissipation.

CHARACTERISTICS (continued)

Forward recovery time when switched to I_F = 4 A with t_r = 0,1 μs; T_j = 140 °C	t_{fr}	<	1 μs

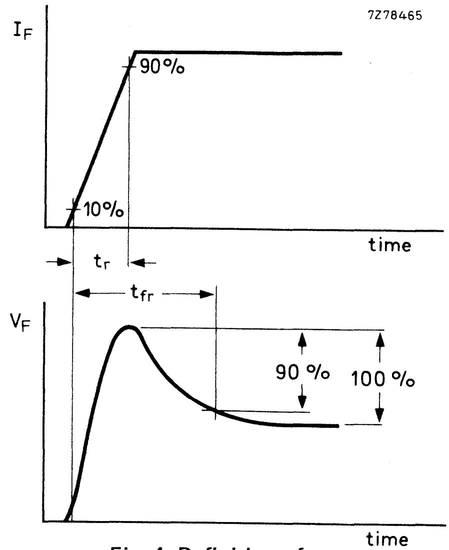


Fig. 4 Definition of t_{fr}.

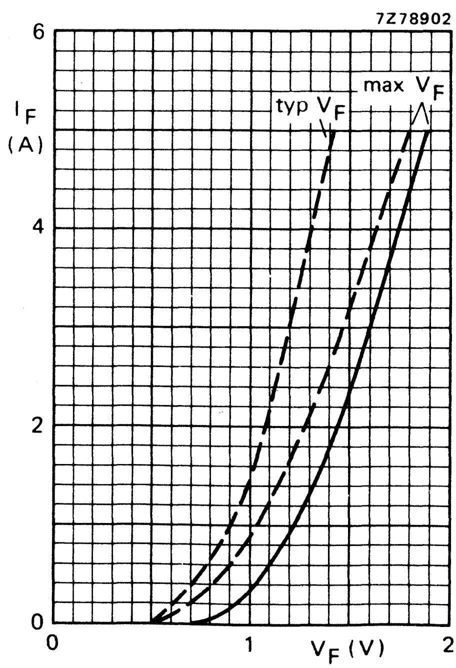


Fig. 5 —— T_j = 25 °C; – – – T_j = 140 °C.

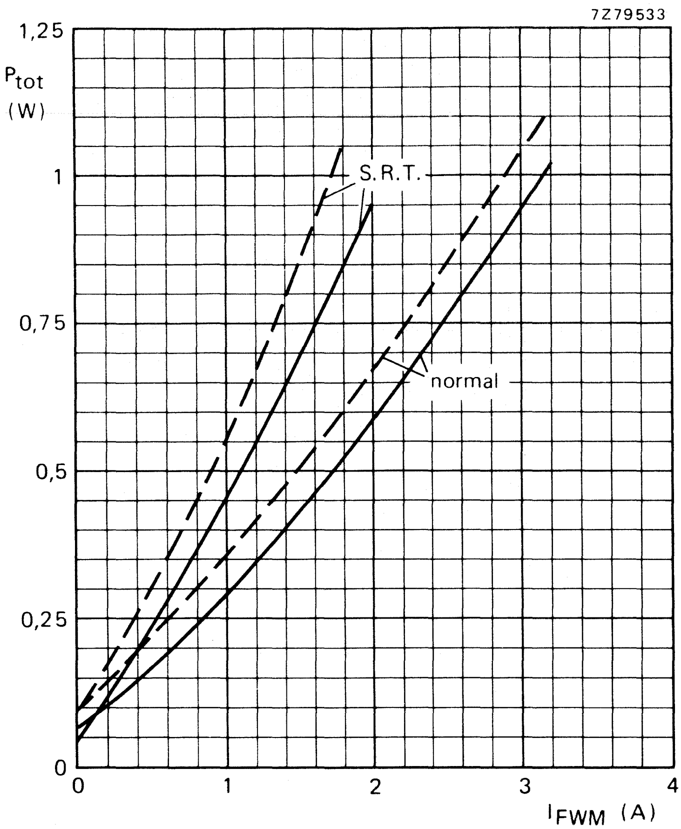


Fig. 6 P_{tot} = maximum power dissipation including switching losses; – – – 819 lines; —— 625 lines; S.R.T. = self regulating time-base circuit; normal = conventional deflection circuit or high-voltage E-W modulator circuit; I_{FWM} = the **nominal** peak diode current, for tolerances and spreads 25% safety margin is taken into account.

APPLICATION INFORMATION

In designing horizontal deflection circuits, allowance has to be made for component and operating spreads, in order not to exceed any Absolute Maximum Rating.
Extensive analysis have shown that for the working peak forward current and reverse voltage the total allowance need not to be higher than 25%. For that reason the dissipation graph (Fig. 6) is based on the **nominal** I_{FWM}; 25% safety margin for tolerance and spreads is taken into account.

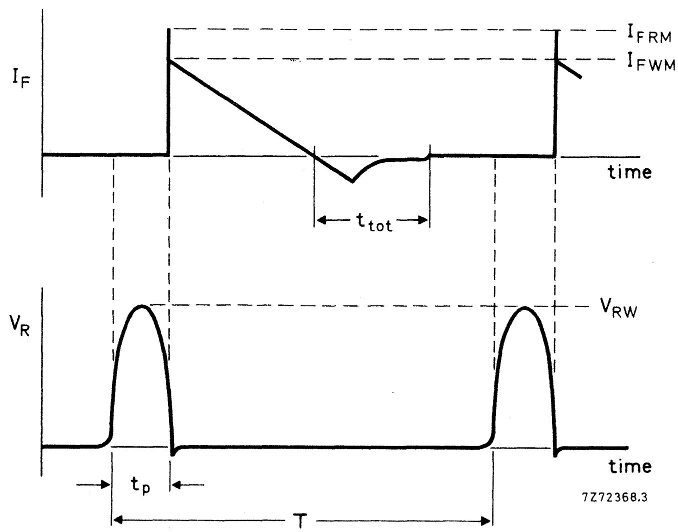


Fig. 7 Basic waveforms.

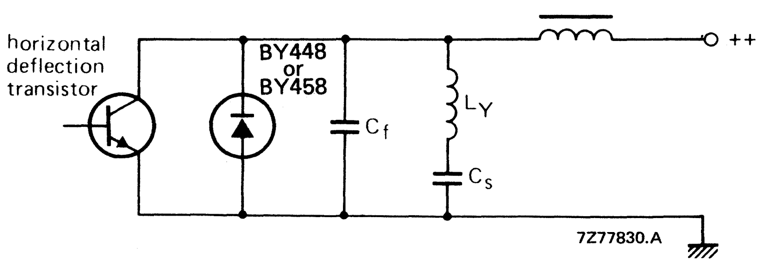


Fig. 8 Basic conventional horizontal deflection circuit.

APPLICATION INFORMATION (continued)

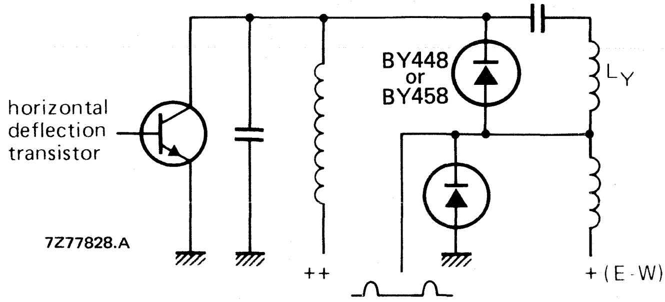


Fig. 9 Basic high-voltage E—W modulator circuit.

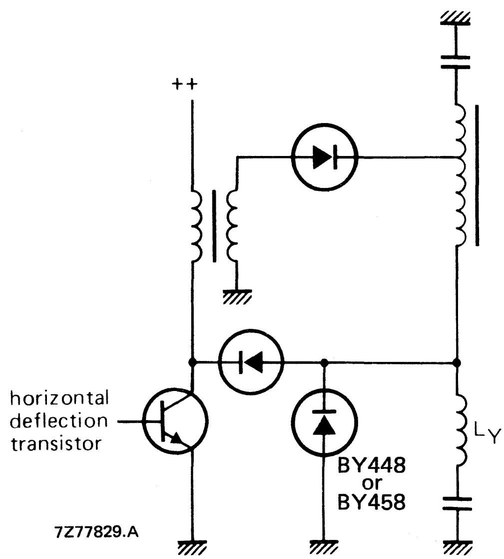


Fig. 10 Basic self-regulating time base circuit (S.R.T.).

HIGH-VOLTAGE SOFT-RECOVERY RECTIFIER DIODE

Glass-passivated rectifier diode in hermetically sealed axial-leaded glass envelope. It is intended as general purpose rectifier for high frequencies and features non-snap-off (soft recovery) switching characteristics.

QUICK REFERENCE DATA

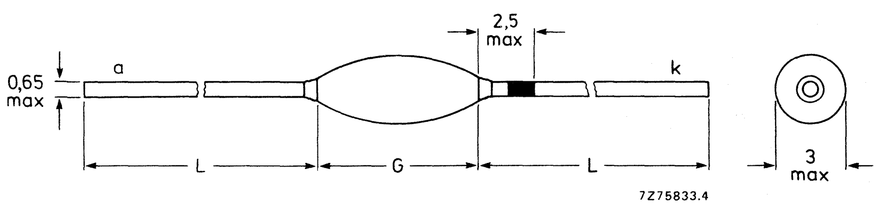
Working reverse voltage	V_{RW}	max.	2000	V
Repetitive peak reverse voltage	V_{RRM}	max.	2200	V
Average forward current	$I_{F(AV)}$	max.	85	mA
Repetitive peak forward current	I_{FRM}	max.	800	mA
Junction temperature	T_j	max.	120	^oC
Reverse recovery charge	Q_s	$<$	1,0	nC

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-61.

G = max. 4,9; L = min. 32,5.



The cathode is indicated by a black band on the lead.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134).

Working reverse voltage	V_{RW}	max.	2000 V
Repetitive peak reverse voltage	V_{RRM}	max.	2200 V
Non-repetitive peak reverse voltage; $t \leqslant 10$ ms	V_{RSM}	max.	2200 V
Average forward current averaged over any 20 ms period;			
$T_{tp} = 25\ ^oC$; lead length = 10 mm	$I_{F(AV)}$	max.	85 mA
$T_{amb} = 60\ ^oC$; Fig. 2	$I_{F(AV)}$	max.	50 mA
Repetitive peak forward current	I_{FRM}	max.	800 mA
Non-repetitive peak forward current $t \leqslant 10$ ms	I_{FSM}	max.	5 A
Storage temperature	T_{stg}	−65 to + 120	^oC
Junction temperature	T_j	max.	120 ^oC

THERMAL RESISTANCE

From junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-wiring board; Cu-thickness $\geqslant 40\ \mu m$; see Fig. 2	$R_{th\ j\text{-}a}$	=	155 K/W

CHARACTERISTICS

Forward voltage $I_F = 100$ mA; $T_j = 120\ ^oC$	V_F	<	8,5 V
Reverse current $V_R = V_{RW}$; $T_j = 120\ ^oC$	I_R	<	3 μA
Reverse recovery when switched from $I_F = 100$ mA to $V_R \geqslant 100$ V with $-dI_F/dt = 200$ mA/μs; $T_j = 25\ ^oC$			
recovery charge	Q_s	<	1 nC
recovery time	t_{rr}	typ.	0,2 μs
fall time	t_f	>	0,1 μs

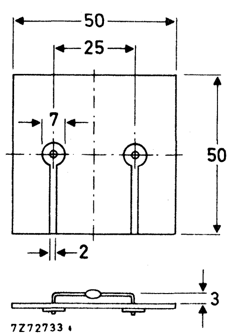


Fig. 2 Mounted on a printed-circuit board.

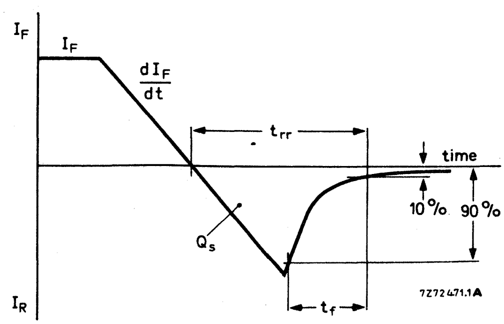


Fig. 3 Definitions of Q_s, t_{rr} and t_f.

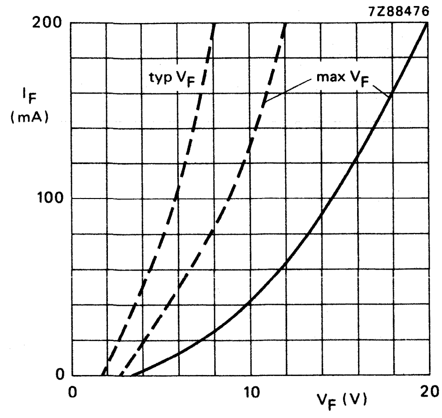


Fig. 4 —— T_j = 25 °C; – – – T_j = 120 °C.

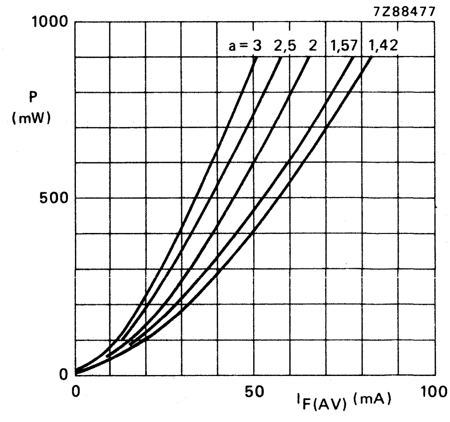


Fig. 5 Steady state power dissipation (forward plus leakage current) excluding switching losses as a function of the average forward current.

The graph is for switched-mode application.

a = $I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RWmax}$; δ = 0,5.

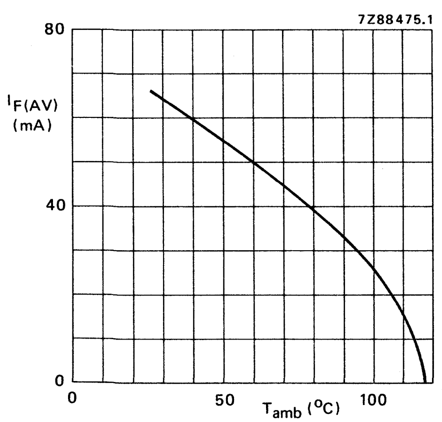


Fig. 6 Maximum permissible average forward current as a function of the ambient temperature; The graph is for switched-mode application. $V_R = V_{RWmax}$, δ = 0,5, a = 1,42, Mounting method see Fig. 2.

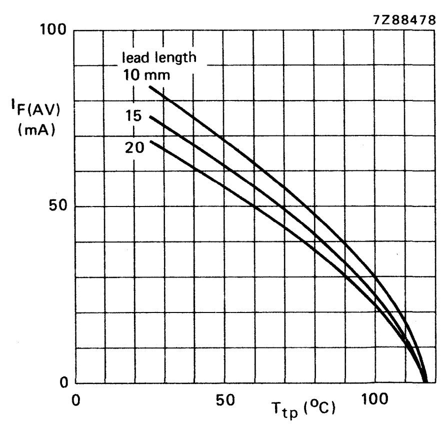


Fig. 7 Maximum average forward current as a function of the tie-point temperature; the curves include losses due to reverse leakage.

The graph is for switched-mode application; $V_R = V_{RWmax}$; δ = 0,5; a = 1,42.

SILICON E.H.T. SOFT-RECOVERY RECTIFIER DIODE*

E.H.T. rectifier diode in a glass envelope intended for use in high-voltage applications such as multipliers, e.g. tripler circuits. The device features non-snap-off characteristics. Because of the smallness of the envelope, the diodes should be used in a suitable insulating medium (resin, oil or special arrangements in test-cases).

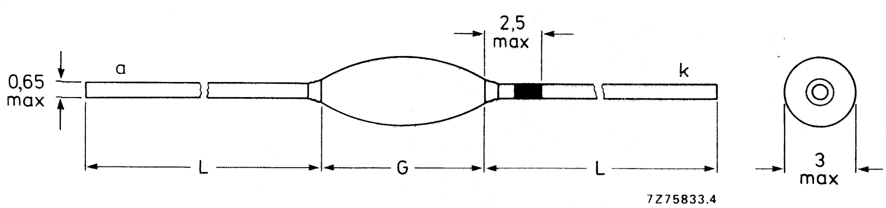
QUICK REFERENCE DATA

Working reverse voltage	V_{RW}	max.	11,5 kV
Repetitive peak reverse voltage	V_{RRM}	max.	15 kV
Average forward current	$I_{F(AV)}$	max.	4 mA
Junction temperature	T_j	max.	120 °C
Reverse recovery charge	Q_s	<	1 nC
Reverse recovery time	t_{rr}	typ.	0,2 μs

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-61.
L = min. 29; G = max. 8,2.



The cathode is indicated by a purple band on the lead.

*See also "Custom made e.h.t. stacks" in section "General".

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134).

Working reverse voltage	V_{RW}	max.	11,5 kV
Repetitive peak reverse voltage	V_{RRM}	max.	12,5 kV
Repetitive peak reverse voltage; $t = 1$ min; $T_{amb} = 25\ ^oC$	V_{RRM}	max.	15 kV
Non-repetitive peak reverse voltage; $t \leqslant 10$ ms	V_{RSM}	max.	15 kV
Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	4 mA
Repetitive peak forward current	I_{FRM}	max.	500 mA*
Storage temperature	T_{stg}		−65 to +120 ^oC
Junction temperature	T_j	max.	120 ^oC

CHARACTERISTICS

Forward voltage $I_F = 100$ mA; $T_j = 120\ ^oC$	V_F	<	43 V**
Reverse current $V_R = 11,5$ kV; $T_j = 120\ ^oC$	I_R	<	3 µA
Reverse recovery when switched from $I_F = 100$ mA to $V_R \geqslant 100$ V with $-dI_F/dt = 200$ mA/µs; $T_j = 25\ ^oC$			
recovery charge	Q_s	<	1 nC
recovery time	t_{rr}	typ.	0,2 µs
fall time	t_f	>	0,1 µs

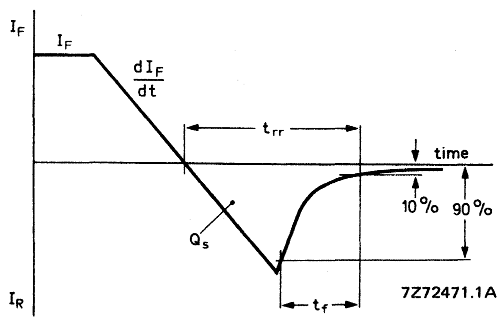


Fig. 2 Definitions of Q_s, t_{rr} and t_f.

* The device can withstand peak currents occurring at flashover in the picture tube.
** Measured under pulse conditions to avoid excessive dissipation.

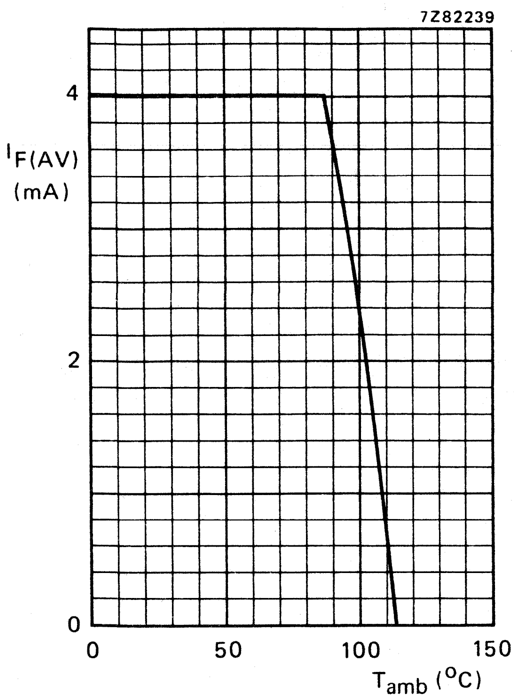


Fig. 3 Maximum permissible average forward current as a function of ambient temperature. $V_R = V_{RWmax}$. The device should be mounted in such a way that $R_{th\ j\text{-}a} \leqslant 120$ K/W .

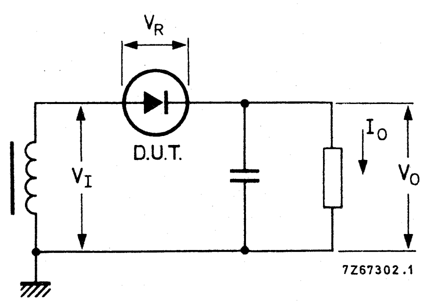


Fig. 4 Typical operation circuit.

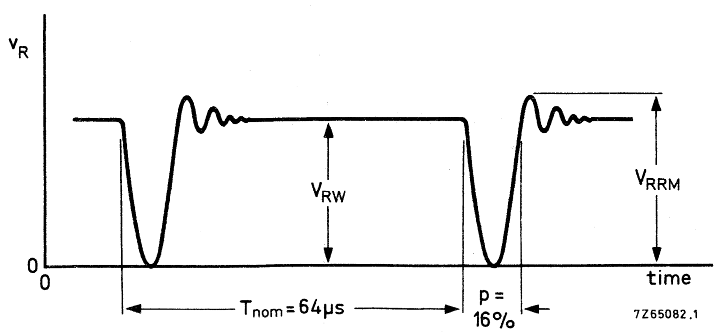


Fig. 5 Typical applied voltage.

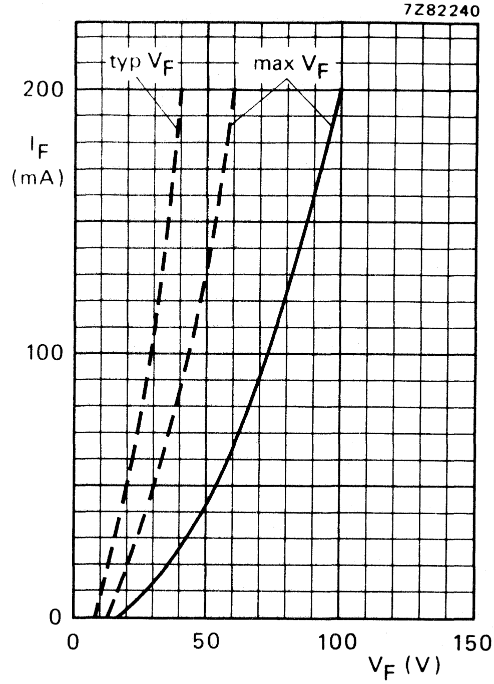


Fig. 6 —— T_j = 25 °C; ---- T_j = 120 °C.

CONTROLLED AVALANCHE RECTIFIER DIODE

Double-diffused glass passivated rectifier diode in hermetically sealed axial-leaded glass envelope capable of absorbing reverse transients, intended for rectifier applications in colour television circuits as well as general purpose applications in telephony equipment.

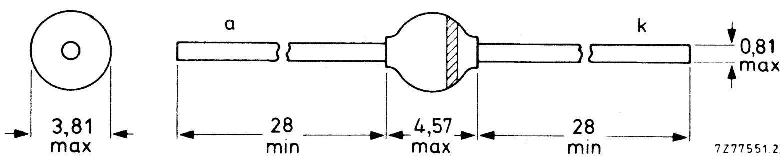
QUICK REFERENCE DATA

Crest working reverse voltage	V_{RWM}	max.	800	V
Repetitive peak reverse voltage	V_{RRM}	max.	1250	V
Average forward current	$I_{F(AV)}$	max.	2	A
Non-repetitive peak forward current	I_{FSM}	max.	50	A
Non-repetitive peak reverse power dissipation	P_{RSM}	max.	1	kW
Junction temperature	T_j	max.	165	°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-57.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Repetitive peak reverse voltage ($\delta \leqslant 1\%$)	V_{RRM}	max.	1250	V
Crest working reverse voltage	V_{RWM}	max.	800	V
Continuous reverse voltage (Fig. 9)	V_R	max.	800	V
Average forward current (averaged over any 20 ms period);				
T_{tp} = 35 °C; lead length 10 mm	$I_{F(AV)}$	max.	2	A
T_{amb} = 75 °C; Fig. 2	$I_{F(AV)}$	max.	0,8	A
Repetitive peak forward current	I_{FRM}	max.	12	A
Non-repetitive peak forward current (see Figs 7 and 12) (t = 10 ms; half sine-wave)	I_{FSM}	max.	50	A
Non-repetitive peak reverse power dissipation (t = 20 μs; half sine-wave); $T_j = T_{j\,max}$ prior to surge	P_{RSM}	max.	1	kW
Non-repetitive peak reverse avalanche mode pulse energy; I_R = 1 A; $T_j = T_{j\,max}$ prior to surge; with inductive load switched off	E_{RSM}	max.	20	mJ
Storage temperature	T_{stg}	−65 to +175		°C
Junction temperature (see Fig. 9)	T_j	max.	165	°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\,j\text{-}tp}$	=	46	K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness $\geqslant$ 40 μm; Fig. 2 (see "Thermal model")	$R_{th\,j\text{-}a}$	=	100	K/W

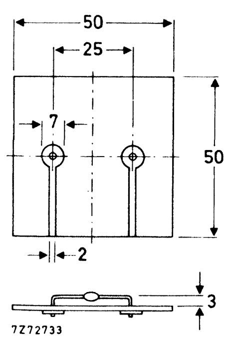


Fig. 2 Device mounted on a printed circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage*			
I_F = 1 A	V_F	<	1 V
I_F = 10 A	V_F	<	1,65 V
Reverse avalanche breakdown voltage			
I_R = 0,1 mA	$V_{(BR)R}$	>	1250 V
Reverse current			
$V_R = V_{RWM\,max}$ **	I_R	<	1,0 μA
$V_R = V_{RWM\,max}$; T_j = 100 °C	I_R	<	10 μA
Reverse recovery charge when switched from I_F = 1 A to $V_R \geq$ 50 V with $-dI_F/dt$ = 5 A/μs	Q_s	typ.	3 μC
Reverse recovery time when switched from I_F = 1 A to $V_R \geq$ 50 V at i_{rr} = 10% of I_R with $-dI_F/dt$ = 5 A/μs	t_{rr}	typ.	2,5 μs

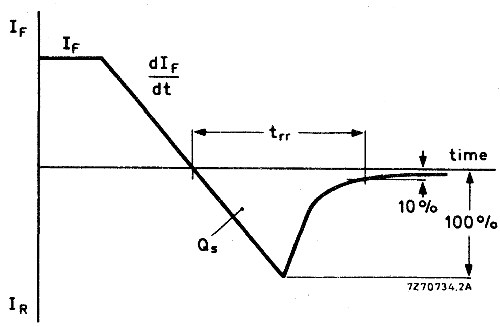


Fig. 3 Definitions of t_{rr} and Q_s.

Diode capacitance			
V_R = 0 V; f = 1 MHz	C_d	typ.	50 pF

* Measured under pulse conditions to avoid excessive dissipation.

** Illuminance ≤ 500 lux (daylight); relative humidity < 65%.

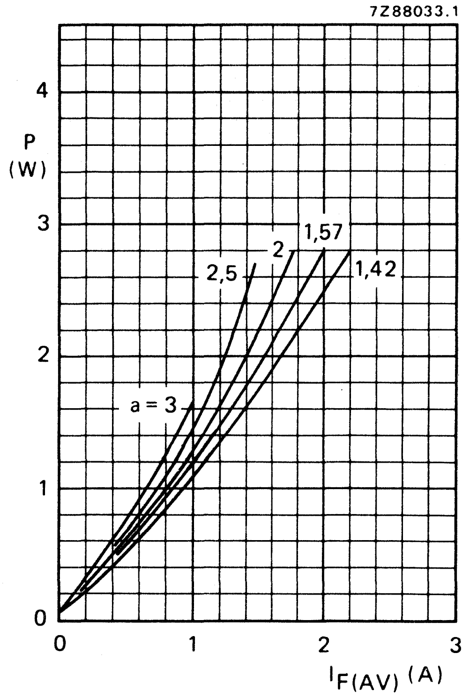


Fig. 4 Steady state power dissipation (forward plus leakage current excluding switching losses) as a function of the average forward current.

$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RWMmax}$.

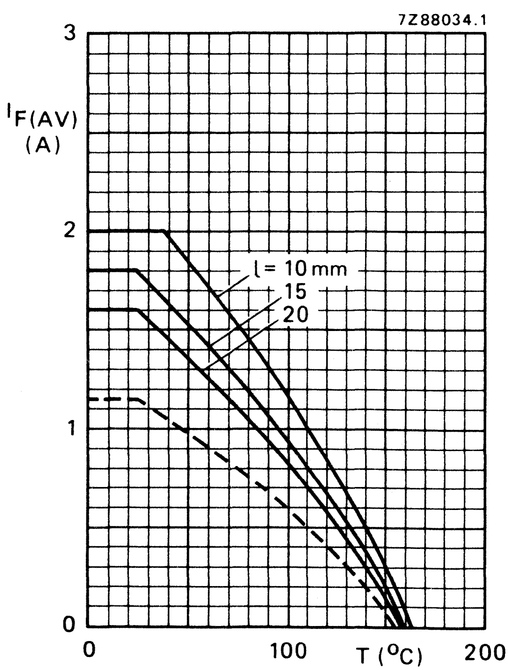


Fig. 5 Maximum average forward current as a function of the temperature.
The curves include losses due to reverse current.
a = 1,57; $V_R = V_{RWMmax}$; l = lead length
——— T = tie-point temperature
– – – – T = ambient temperature and device mounted as shown in Fig. 2.

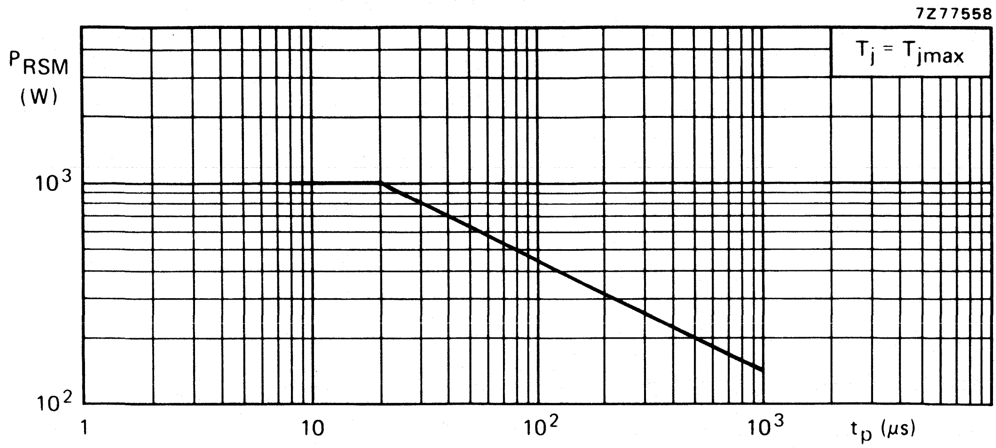
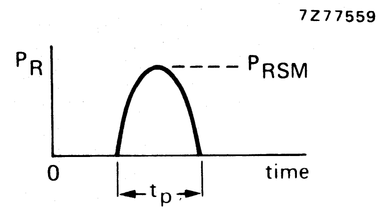


Fig. 6 Maximum permissible non-repetitive peak reverse power dissipation in the avalanche region.



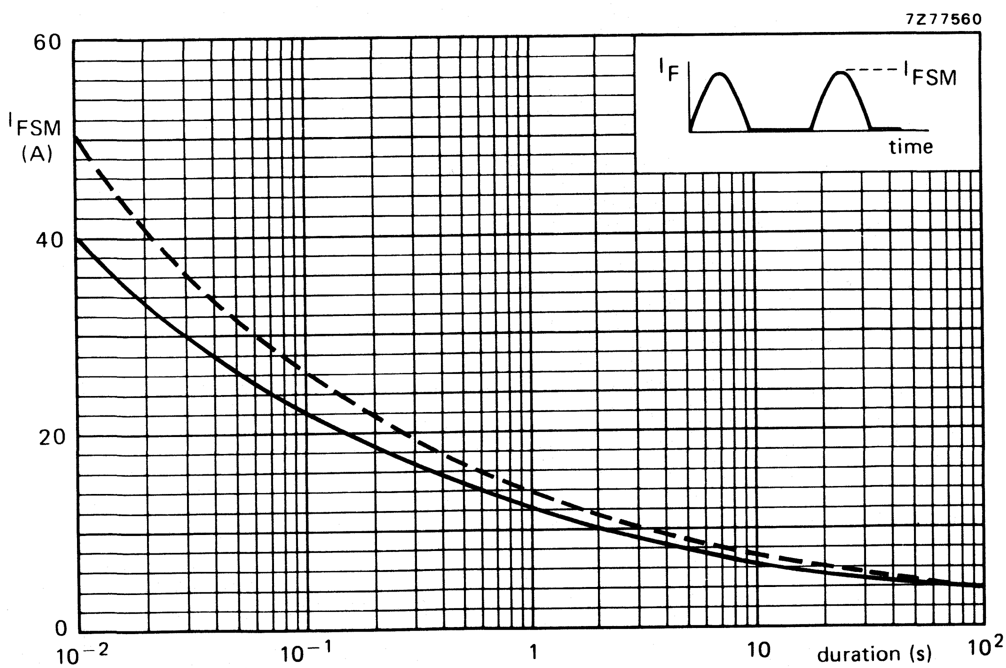


Fig. 7 Maximum permissible non-repetitive peak forward current based on sinusoidal currents (f = 50 Hz)
- - - - T_j = 25 °C; V_R = 0.
——— $T_j = T_{j\,max}$ prior to surge; $V_R = V_{RWMmax}$.

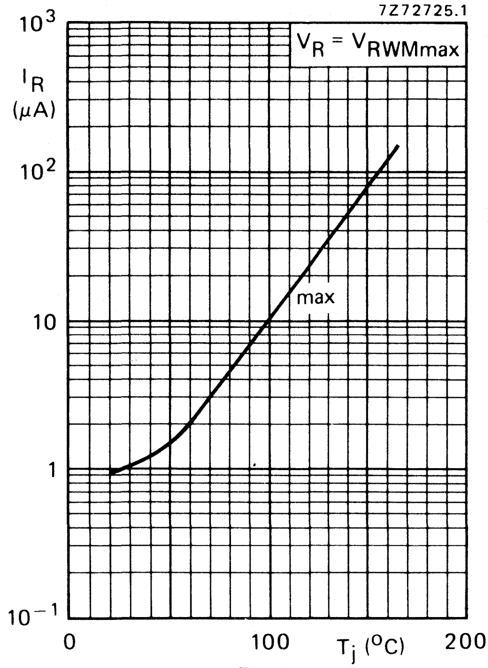


Fig. 8.

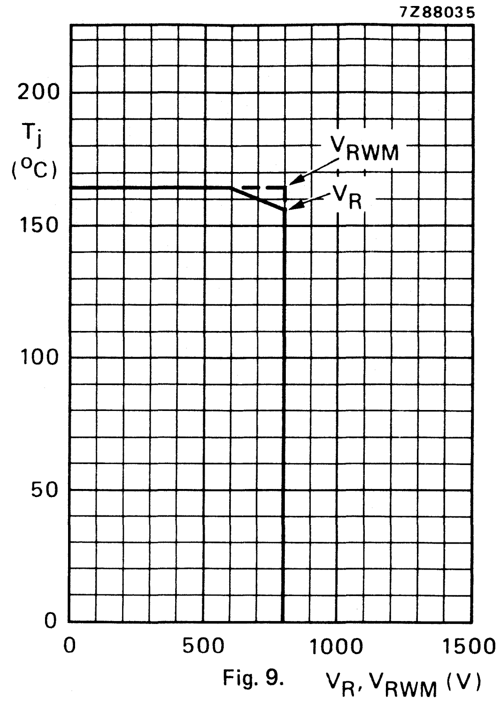


Fig. 9.

f = 50 Hz; sine-wave; $R_{th\ j\text{-}a}$ = 100 K/W.

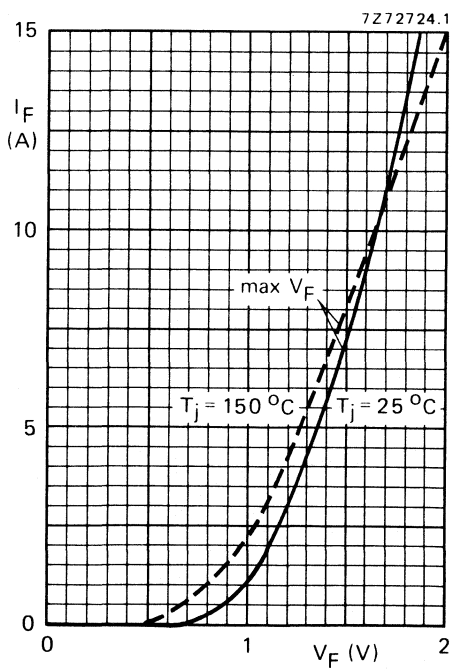


Fig. 10.

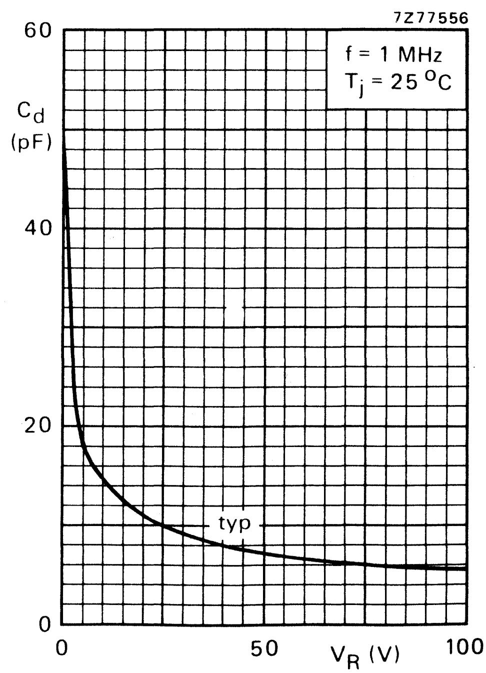


Fig. 11.

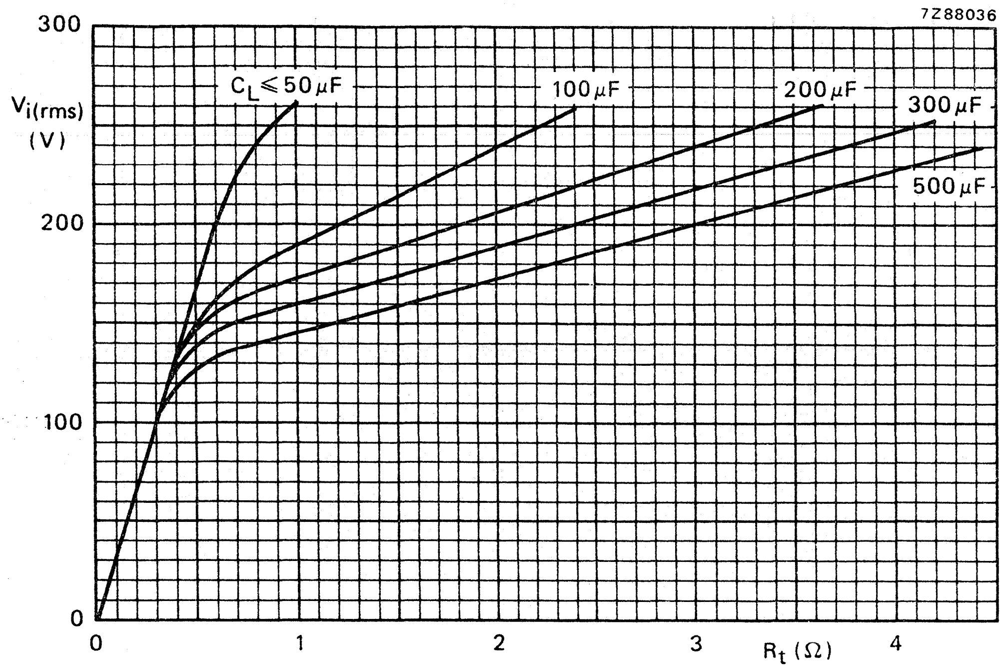


Fig. 12 Minimum values of series resistance (R_t), including the transformer resistance, required to limit the initial peak rectifier current with capacitive load. The possibility of the following spreads are taken into account: mains voltage +10%; capacitance +50%, resistance −10%.

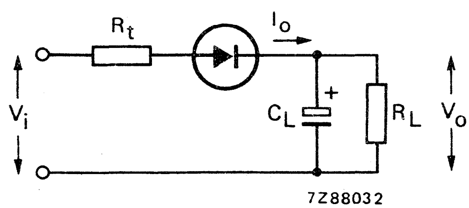


Fig. 13 Test circuit series resistance (R_t).

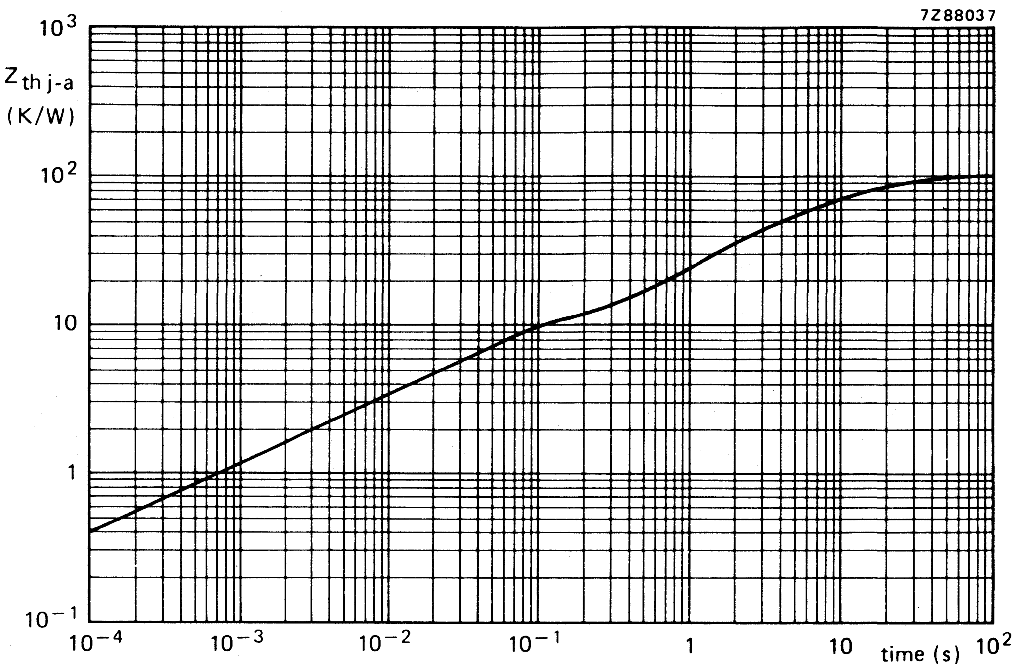


Fig. 14.

Device mounted on a printed circuit board (see Fig. 2).

HIGH VOLTAGE SOFT RECOVERY RECTIFIER DIODE

Glass-passivated rectifier diode in hermetically sealed axial-lead glass envelope. For high voltage applications such as grid 2 supply in colour television picture tubes and as general purpose rectifiers for high frequencies. The diode has non-snap-off characteristics.

QUICK REFERENCE DATA

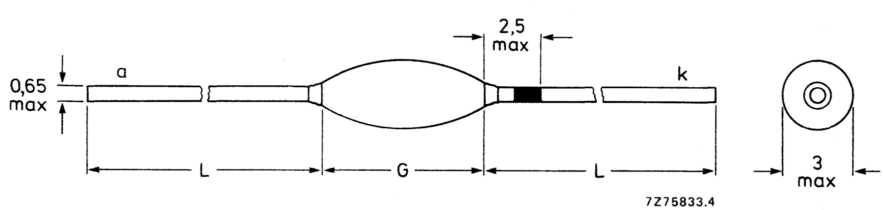
Working reverse voltage	V_{RW}	max.	1500 V
Repetitive peak reverse voltage	V_{RRM}	max.	1800 V
Average forward current	$I_{F(AV)}$	max.	85 mA
Repetitive peak forward current	I_{FRM}	max.	800 mA
Junction temperature	T_j	max.	120 °C
Reverse recovery charge	Q_s	<	1,0 nC

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-61A.

G = max. 4,9; L = min. 32,5.



The cathode is indicated by a black band on the lead.
Diodes are type branded.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134).

Working reverse voltage	V_{RW}	max.	1500 V
Repetitive peak reverse voltage	V_{RRM}	max.	1800 V
Non-repetitive peak reverse voltage	V_{RSM}	max.	1800 V
Average forward current (averaged over any 20 ms)			
T_{tp} = 25 °C; lead length = 10 mm	$I_{F(AV)}$	max.	85 mA
T_{amb} = 60 °C; p.c.b. mounting see Fig. 2	$I_{F(AV)}$	max.	50 mA
Repetitive peak forward current	I_{FRM}	max.	800 mA
Non-repetitive peak forward current t < 10 ms, half sinewave, $T_j = T_{j\,max}$ prior to surge	I_{FSM}	max.	5 A
Storage temperature	T_{stg}	−65 to +120 °C	
Junction temperature	T_j	max.	120 °C

THERMAL RESISTANCE

From junction to ambient when mounted on a 1,5 mm thick epoxy-glass p.c.b.; Cu-thickness > 40 μm; see Fig. 9 and 11	$R_{th\,j\text{-}a}$	=	155 K/W

CHARACTERISTICS

Forward voltage * I_F = 100 mA; T_j = 120 °C	V_F	<	8,5 V
Reverse current $V_R = V_{RW}$; T_j = 120 °C	I_R	<	3 μA
Reverse recovery when switched from I_F = 100 mA to V_R > 100 V with $-dI_F/dt$ = 200 mA/μs; T_j = 25 °C			
recovery charge	Q_s	<	1 nC
recovery time	t_{rr}	typ.	0,2 μs
fall time	t_f	>	0,1 μs

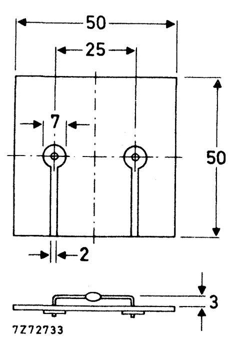


Fig. 2 Device mounted on a printed circuit board.

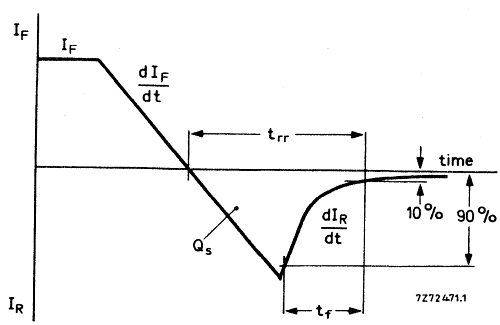


Fig. 3 Definitions of Q_s, t_{rr} and t_f.

* Measured under pulse conditions to avoid excessive dissipation.

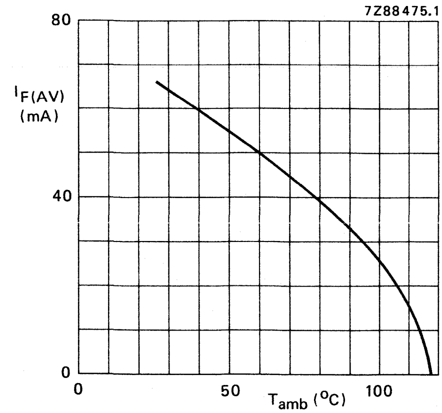


Fig. 4 Maximum permissible average forward current as a function of the ambient temperature; $V_R = V_{RWmax}$; a = 1,42, mounting Fig. 2.

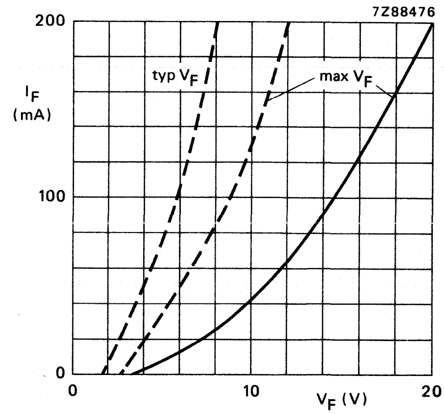


Fig. 5 —— T_j = 25 °C; – – – T_j = 120 °C.

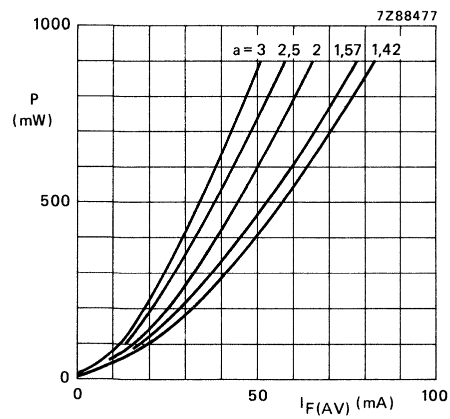


Fig. 6 Steady state power dissipation (forward plus leakage current but excluding switching losses) as a function of average forward current.

a = $I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RWmax}$; δ = 0,5.

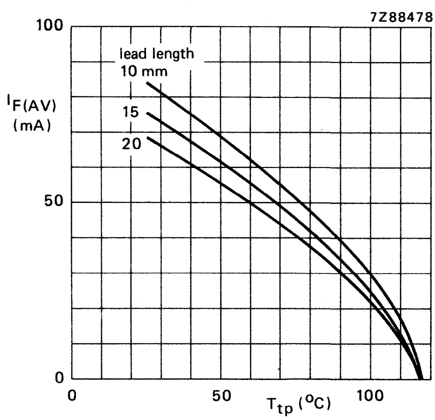


Fig. 7 Maximum average forward current as a function of the tie-point temperature; the curves include losses due to reverse leakage.

a = 1,42; $V_R = V_{RWmax}$; δ = 0,5*.

* Figs 4 and 7 apply to switched mode application.

APPLICATION INFORMATION

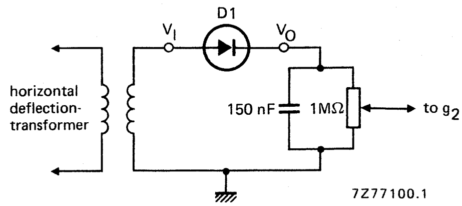


Fig. 8 Basic circuit for voltage supply of grid 2 incolour television picture tubes. D_1 = BY584. Stable continuous operation is ensured at an ambient temperature up to 70 °C.

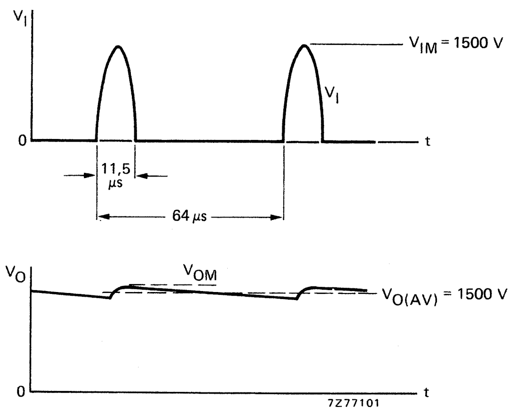


Fig. 9 Waveform.

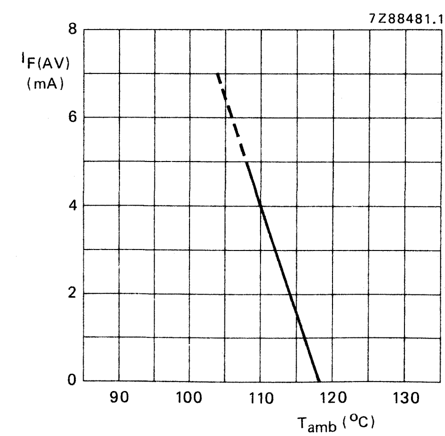


Fig. 10 Maximum permissible average forward current as a function of ambient temperature. V_R = 1500 V; diode used in circuit Fig. 8 mounted as in Fig. 2.

OPERATING NOTES

The various components of junction temperature rise above ambient, for mounting with symmetrical lead length, are illustrated below.

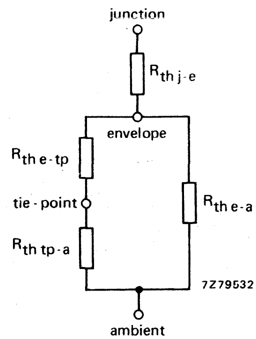


Fig. 11 Thermal model. $R_{th\ j-e}$ = 35 K/W.

The thermal resistances between envelope and tie-point, and between envelope and ambient depend on lead length.

lead length	5	10	15	20	25	mm
$R_{th\ e-tp}$	38	76	114	152	190	K/W
$R_{th\ e-a}$	750	560	410	330	280	K/W

The thermal resistance between tie-point and ambient depends on the mounting method; for mounting on a 1,5 mm thick epoxy-glass printed-circuit board with a copper-thickness ⩾ 40 μm, the following values apply:

1. Mounted as given in Fig. 2 the thermal resistance $R_{th\ tp-a}$ is 70 K/W.
2. Mounted with copper laminate of 1 cm^2 per lead $R_{th\ tp-a}$ is 55 K/W.
3. Mounted with copper laminate of 2,25 cm^2 per lead $R_{th\ tp-a}$ is 45 K/W.

Note
Any temperature can be calculated by using the dissipation graph (Fig. 6) and the above thermal model.

BASE-EMITTER EFFICIENCY DIODE

Solid-glass passivated rectifier diode in a hermetically sealed axial-leaded glass envelope. The device is intended for use as efficiency diode in horizontal deflection circuits between base and emitter terminals of the output transistor.

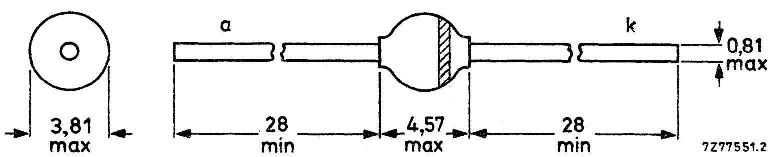
QUICK REFERENCE DATA

Repetitive peak reverse voltage	V_{RRM}	max.	50	V
Continuous reverse voltage	V_R	max.	25	V
Average forward current	$I_{F(AV)}$	max.	1,5	A
Non-repetitive peak forward current	I_{FSM}	max.	25	A
Repetitive peak forward current	I_{FRM}	max.	10	A
Forward conduction delay	t_d	>	0,7	µs

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-57.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Repetitive peak reverse voltage	V_{RRM}	max.	50 V
Continuous reverse voltage	V_R	max.	25 V
Average forward current (averaged over any 20 ms period)			
T_{tp} = 65 °C; lead length 10 mm (a = 1,42)*	$I_{F(AV)}$	max.	1,5 A
T_{amb} = 65 °C; Fig. 2	$I_{F(AV)}$	max.	0,87 A
Repetitive peak forward current	I_{FRM}	max.	10 A
Non-repetitive peak forward current (t = 10 ms; half-sinewave) $T_j = T_{j\,max}$ prior to surge; $V_R = V_{RRMmax}$	I_{FSM}	max.	25 A
Storage temperature	T_{stg}	−65 to +175	°C
Operating junction temperature	T_j	max.	175 °C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\ j\text{-}tp}$	=	46 K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ≥ 40 μm; Fig. 2 (see "Thermal model")	$R_{th\ j\text{-}a}$	=	100 K/W

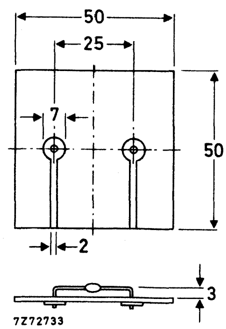


Fig. 2 Mounted on a printed-circuit board.

* a = $I_{F(RMS)}/I_{F(AV)}$.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage*			
I_F = 3 A	V_F	<	1,6 V
I_F = 3 A; T_j = 175 °C	V_F	<	1,54 V
Reverse current			
$V_R = V_{RRMmax}$	I_R	<	5 μA
Forward conduction delay			
V_F = 6 V; T_j = 175 °C	t_d	>	0,7 μs

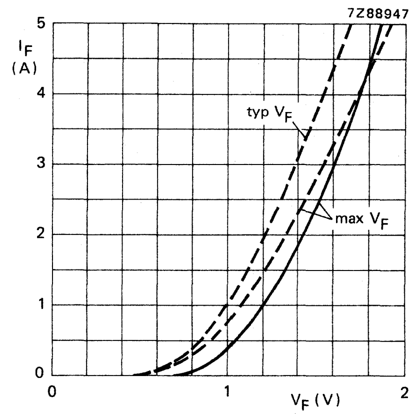


Fig. 3 —— T_j = 25 °C; ---- T_j = 175 °C.

* Measured under pulse conditions to avoid excessive dissipation.

SILICON E.H.T. AVALANCHE RECTIFIER DIODES *

E.H.T. rectifier diodes in glass envelopes. For use in high-voltage applications such as multipliers, especially in diode-split transformers. The devices feature non-snap-off characteristics and are capable of absorbing avalanche energy e.g. during flashover in a picture tube. Because of the small envelope, the diode should be used in a suitable insulating medium (resin, oil or special arrangements in test-cases).

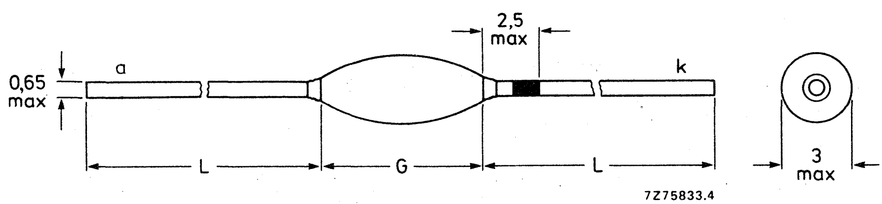
QUICK REFERENCE DATA

			BY609	BY610	
Working reverse voltage	V_{RW}	max.	12	12	kV
Repetitive peak reverse voltage	V_{RRM}	max.	15	17	kV
Average forward current	$I_{F(AV)}$	max.	4		mA
Junction temperature	T_j	max.	120		°C
Reverse recovery charge	Q_s	<	1		nC
Reverse recovery time	t_{rr}	typ.	0,2		μs

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-61.
L = 29,5 min.
G = 8,9 max.



The cathode of the BY609 is indicated by a yellow band on the lead.
The cathode of the BY610 is indicated by an orange band on the lead.

*See also "Custom made E.H.T. stacks" in section "General".

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BY609	BY610	
Working reverse voltage	V_{RW}	max.	12	12	kV
Repetitive peak reverse voltage	V_{RRM}	max.	12	12	kV
Repetitive peak reverse voltage ▲ t = 1 min.; T_{amb} = 25 °C	V_{RRM}	max.	15	17	kV
Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	4		mA
Repetitive peak forward current *	I_{FRM}	max.	500		mA
Storage temperature	T_{stg}		−65 to +120		°C
Junction temperature	T_j	max.	120		°C

CHARACTERISTICS

Forward voltage ** I_F = 100 mA; T_j = 120 °C	V_F	<	50	V
Reverse current V_R = 12 kV; T_j = 120 °C	I_R	<	3	μA
Reverse recovery when switched from I_F = 100 mA to V_R > 100 V with $-dI_F/dt$ = 200 mA/μs; T_j = 25 °C				
recovery charge	Q_s	<	1	nC
recovery time	t_{rr}	typ.	0,2	μs
fall time	t_f	>	0,08	μs

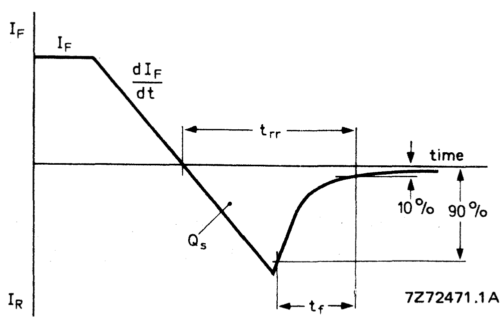


Fig. 2 Definitions of Q_s, t_{rr} and t_f.

▲ The device can withstand the avalanche energy e.g. during flashover in a picture tube.
* The device can withstand peak currents occurring during flashover in a picture tube.
** Measured under pulse conditions to avoid excessive dissipation.

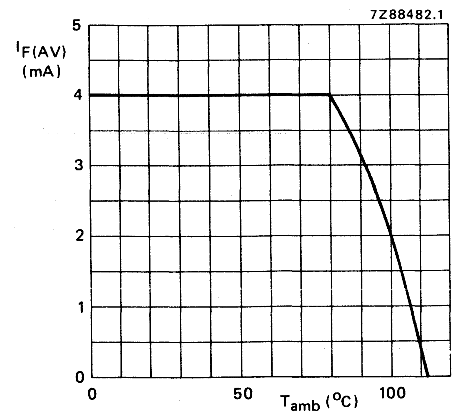


Fig. 3 Maximum permissible average forward current as a function of ambient temperature. $V_R = V_{RWmax}$. The diode should be mounted in such a way that $R_{th\ j\text{-}a} \leq 120$ K/W.

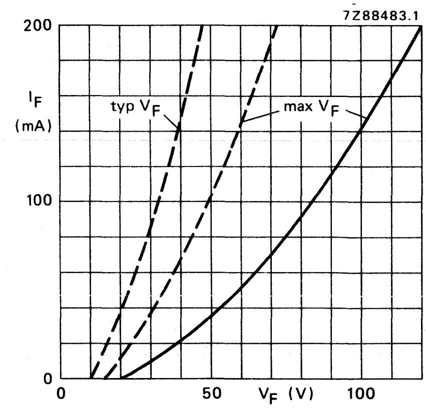


Fig. 4 ——— T_j = 25 °C; – – – – T_j = 120 °C.

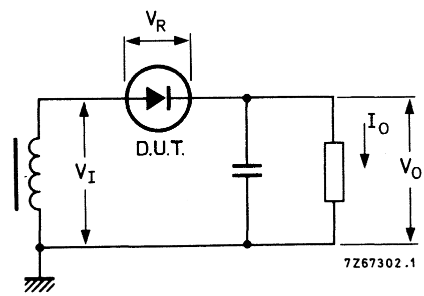


Fig. 5 Typical operation circuit.

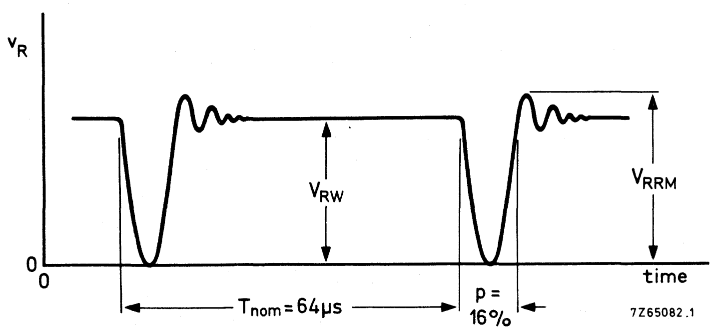


Fig. 6 Typical applied voltage.

MINIATURE HIGH-VOLTAGE SOFT-RECOVERY RECTIFIER DIODE

Glass-passivated rectifier diode in a miniature hermetically sealed axial-leaded glass envelope. It is intended as a general purpose rectifier for high frequencies and high voltages and owing to its small size this diode is extremely suitable for mounting in miniature assemblies, such as voltage multipliers.

Because of the small envelope, the diode should be well insulated (insulating material: resin, oil or with special arrangements in test cases-SF6 gas).

QUICK REFERENCE DATA

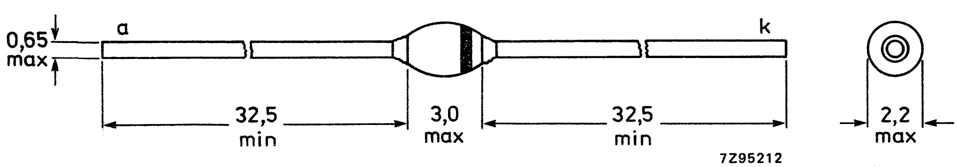
Working reverse voltage	V_{RW}	max.	2000 V
Repetitive peak reverse voltage	V_{RRM}	max.	2200 V
Average forward current	$I_{F(AV)}$	max.	50 mA
Repetitive peak forward current	I_{FRM}	max.	500 mA
Junction temperature	T_j	max.	150 °C
Reverse recovery time	t_{rr}	<	300 ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-61H2.

L = 32,5 min.
G = 3,0 max.



The cathode is indicated by a coloured band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	2000 V
Working reverse voltage	V_{RW}	max.	2000 V
Repetitive peak reverse voltage	V_{RRM}	max.	2200 V
Non-repetitive peak reverse voltage $t \leqslant 10$ ms	V_{RSM}	max.	2200 V
Average forward current (averaged over any 20 ms period); $T_{amb} = 65$ °C	$I_{F(AV)}$	max.	50 mA
Repetitive peak forward current	I_{FRM}	max.	500 mA
Non-repetitive peak forward current; t = 10 ms; half sine-wave; $T_j = T_{j\,max}$ prior to surge; re-applied V_{RW}	I_{FSM}	max.	1 A
Storage temperature	T_{stg}	−65 to + 150 °C	
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient	$R_{th\,j\text{-}a}$	=	155 K/W

CHARACTERISTICS

$T_j = 25$ °C unless otherwise specified

Forward voltage*			
$I_F =$ 50 mA; $T_j = 150$ °C	V_F	<	6 V
$I_F = 200$ mA	V_F	<	20 V
$I_F = 200$ mA; $T_j = 150$ °C	V_F	<	12 V
Reverse current**			
$V_R = 2000$ V	I_R	typ.	5 nA
		<	10 nA
$V_R = 2000$ V; $T_j = 120$ °C	I_R	<	3 μA
Reverse recovery time when switched from $I_F = 100$ mA to $V_R \geqslant 100$ V with $-dI_F/dt = 200$ mA/μs	t_{rr}	<	300 ns
Diode capacitance at f = 1 MHz $V_R = 100$V	C_d	<	0,8 pF

* Measured under pulsed conditions to avoid excessive dissipation.
** Illumination ⩽ 300 lux; relative humidity ⩽ 65%.

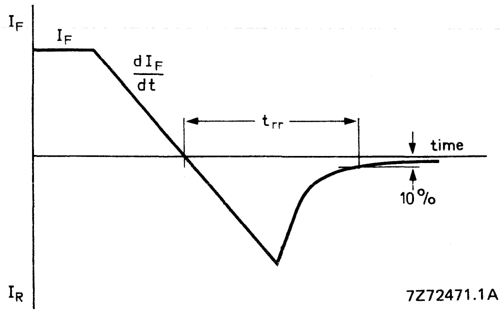


Fig. 2 Definition of t_{rr}.

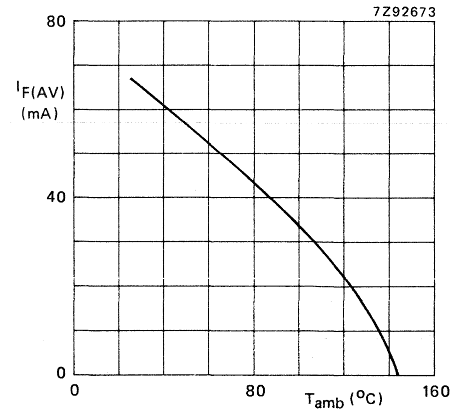


Fig. 3 Maximum permissible average forward current vs. ambient temperature; a = 1,57.

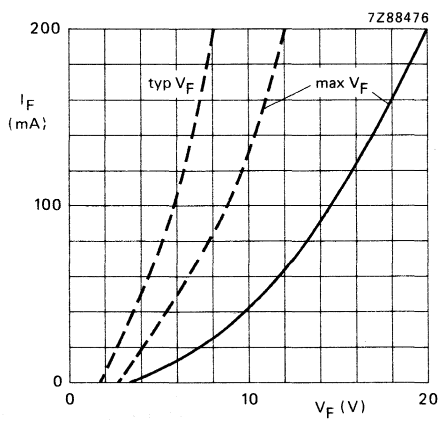


Fig. 4 Forward current vs. forward voltage ——— T_j = 25 °C; – – – – T_j = 150 °C.

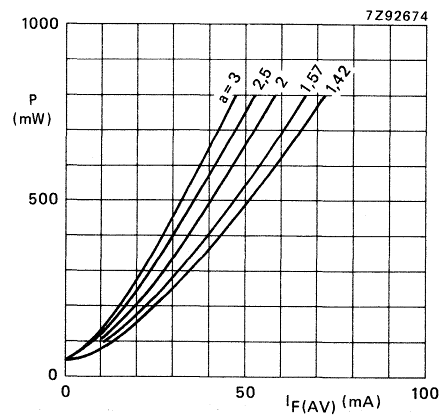


Fig. 5 Steady state power dissipation (forward plus leakage current) excluding switching losses vs. average forward current; a = $I_{F(RMS)}/I_{F(AV)}$.

Conditions for Figs 3 and 5:
switched-mode application; $V_R = V_{RWmax}$; δ = 0,5.

E.H.T. AVALANCHE VERY FAST SOFT-RECOVERY DIODES *

E.H.T. rectifier diodes in hermetically-sealed, axially-leaded glass envelope and designed for c.t.v. and monitor applications with frequencies up to 128 kHz. They are suitable for use in high-voltage application such as multipliers and especially in diode-split transformers.

Because of the small envelope, the diode should be used in a suitable insulating medium (resin, oil or SF6 gas).

Features:

- Non-snap-off characteristics;
- Capable of absorbing avalanche energy e.g. during flash-over in picture tubes.

QUICK REFERENCE DATA

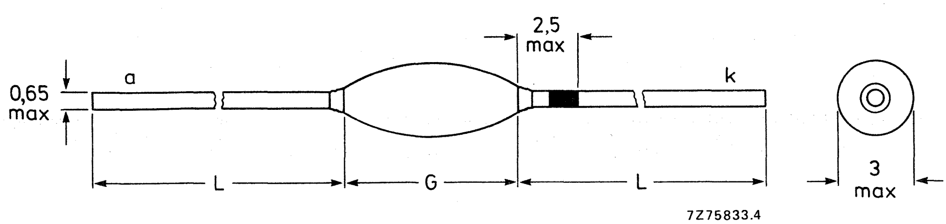
			BY619	BY620	
Working reverse voltage	V_{RW}	max.	12	12	kV
Repetitive peak reverse voltage	V_{RRM}	max.	15	17	kV
Average forward current	$I_{F(AV)}$	max.	4		mA
Junction temperature	T_j	max.	120		°C
Reverse recovery charge	Q_s	$<$	0,4		nC
Reverse recovery time	t_{rr}	typ.	100		ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-61.

L = 28 min.
G = 11 max.



The BY619 cathode is indicated by a curry yellow band on the lead.
The BY620 cathode is indicated by a lilac band on the lead.

*See also "Custom made E.H.T. stacks" in section "General".

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BY619	BY620	
Working reverse voltage	V_{RW}	max.	12	12	kV
Repetitive peak reverse voltage	V_{RRM}	max.	12	12	kV
Repetitive peak reverse voltage* $t = 1$ min.; $T_{amb} = 25$ °C	V_{RRM}	max.	15	17	kV
Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	4		mA
Repetitive peak forward current**	I_{FRM}	max.	500		mA
Storage temperature	T_{stg}		−65 to + 120		°C
Junction temperature	T_j	max.	120		°C

CHARACTERISTICS

$T_j = 25$ °C unless otherwise specified

Forward voltage ▲ $I_F = 100$ mA; $T_j = 120$ °C	V_F	<	75	V
Reverse current $V_R = V_{RW}$; $T_j = 120$ °C	I_R	<	3	μA
Reverse recovery when switched from $I_F = 100$ mA to $V_R \geqslant 100$ V with $-dI_F/dt = 200$ mA/μs				
recovery charge	Q_s	<	0,4	nC
recovery time at $I_R = 1$ mA	t_{rr}	typ.	100	ns
fall time at $I_R = 1$ mA	t_f	>	40	ns

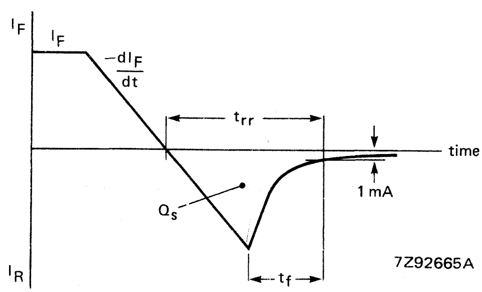


Fig. 2 Definitions of Q_s, t_{rr} and t_f.

* Capable of withstanding the avalanche energy e.g. during flash-over in a picture tube.
** Capable of withstanding peak currents during flash-over in a picture tube.
▲ Measured under pulse conditions to avoid excessive dissipation.

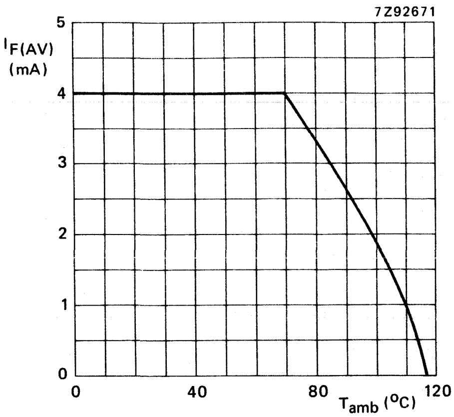


Fig. 3 Maximum permissible average forward current versus ambient temperature; the current includes losses due to reverse leakage. Diode to be mounted such that $R_{th\ j\text{-}a} < 120$ K/W.

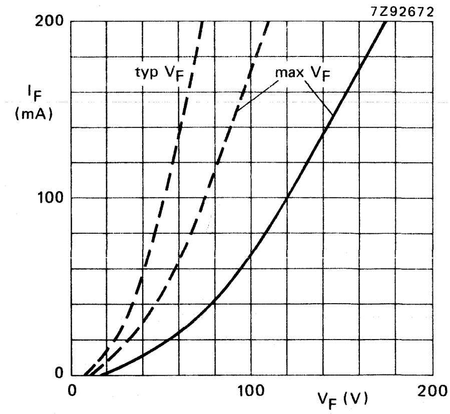


Fig. 4 —— $T_j = 25$ °C; – – – $T_j = 120$ °C.

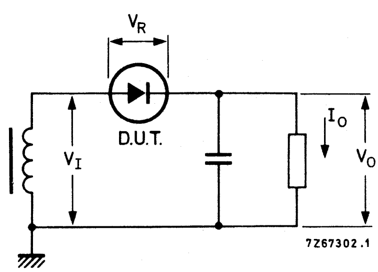


Fig. 5 Typical operation circuit.

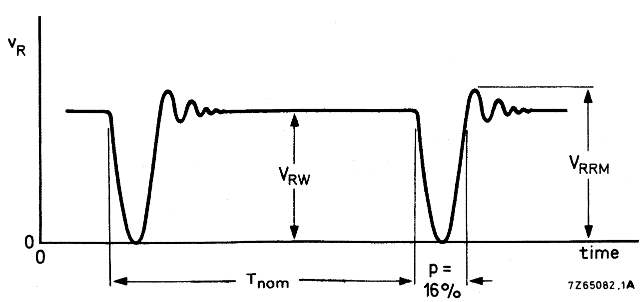


Fig. 6 Typical applied voltage.

CONTROLLED AVALANCHE RECTIFIER DIODES

Glass passivated rectifier diode in hermetically sealed axial-leaded ID* envelope capable of absorbing reverse transients, intended for rectifier applications in colour television circuits as well as general purpose applications in telephony equipment.

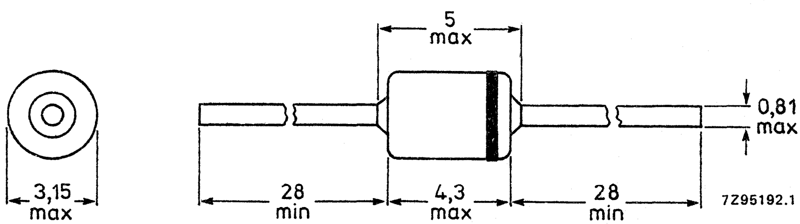
QUICK REFERENCE DATA

Crest working voltage	V_{RWM}	max.	800	V
Repetitive peak reverse voltage	V_{RRM}	max.	1250	V
Average forward current	$I_{F(AV)}$	max.	2	A
Non-repetitive peak forward current	I_{FSM}	max.	50	A
Non-repetitive peak reverse avalanche energy	E_{RSM}	max.	40	mJ
Junction temperature	T_j	max.	175	°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-84.



The marking band indicates the cathode.

* Implosion Diode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Crest working voltage	V_{RWM}	max.	800	V
Repetitive peak reverse voltage ($\delta \leqslant 1\%$)	V_{RRM}	max.	1250	V
Continuous reverse voltage	V_R	max.	800	V
Average forward current (averaged over any 20 ms period)				
T_{tp} = 45 °C; lead length 10 mm	$I_{F(AV)}$	max.	2	A
T_{amb} = 60 °C; see Fig. 2	$I_{F(AV)}$	max.	1	A
Repetitive peak forward current T_{tp} = 45 °C; f = 50 Hz; a = 4,5 (inclusive derating for $T_{j\,max}$ at V_{RRM} = 1250 V)	I_{FRM}	max.	20	A
Non-repetitive peak forward current t = 10 ms, half-sine wave (see Fig. 10)	I_{FSM}	max.	50	A
Non-repetitive peak reverse avalanche pulse energy; I_R = 0,8 A; T_j = 25 °C prior to surge; with inductive load switched off	E_{RSM}	max.	40	mJ
Storage temperature	T_{stg}	−65 to + 175		°C
Junction temperature	T_j	max.	175	°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\,j\text{-}tp}$	=	50	K/W
2. Thermal resistance from junction to ambient; device mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness $\geqslant$ 40 μm; Fig. 2 (See "Thermal model")	$R_{th\,j\text{-}a}$	=	105	K/W

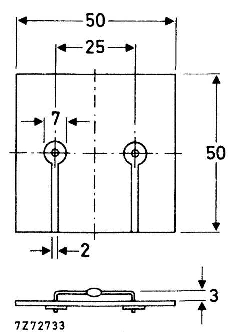


Fig. 2 Mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage*			
I_F = 3 A	V_F	<	1,15 V
I_F = 3 A; $T_j = T_{j\,max}$	V_F	<	1,05 V
Reverse avalanche breakdown voltage			
I_R = 0,1 mA	$V_{(BR)R}$	>	1250 V
Reverse current			
$V_R = V_{RWM\,max}$**	I_R	<	1,0 μA
$V_R = V_{RWM\,max}$; T_j = 100 °C	I_R	<	10 μA
Reverse recovery when switched from I_F = 1 A to $V_R \geq 30$ V with $-dI_F/dt$ = 5 A/μs			
recovery charge	Q_s	typ.	3 μC
recovery time	t_{rr}	typ.	2,5 μs
Diode cpacitance at f = 1 MHz			
V_R = 0	C_d	typ.	50 pF

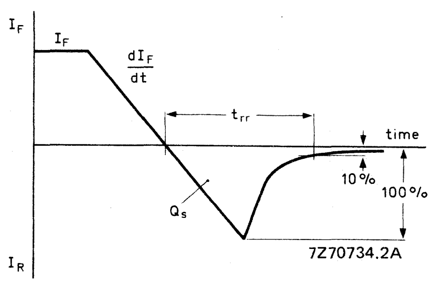


Fig. 3 Definitions of t_{rr}, Q_s and dI_F/dt.

* Measured under pulse conditions to avoid excessive dissipation.

** Illuminance ≤ 500 lux (daylight); relative humidity < 65%.

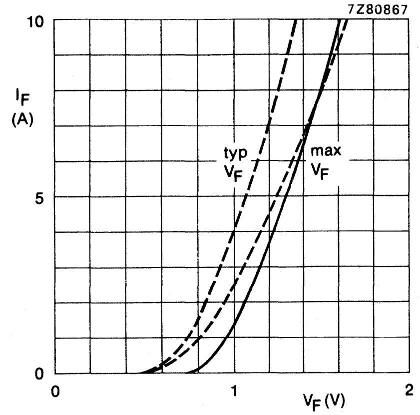


Fig. 4 Forward voltage;
—— T_j = 25 °C;
– – – T_j = 175 °C.

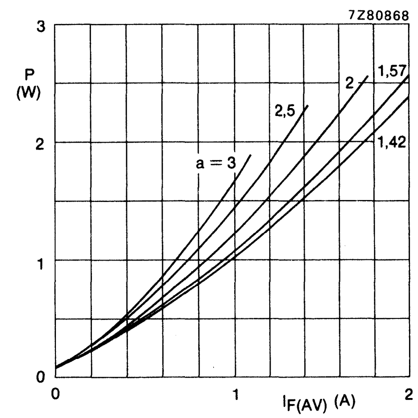


Fig. 5 Maximum values steady state power dissipation (forward plus leakage current) as a function of the average forward current.

$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RWM\,max}$.

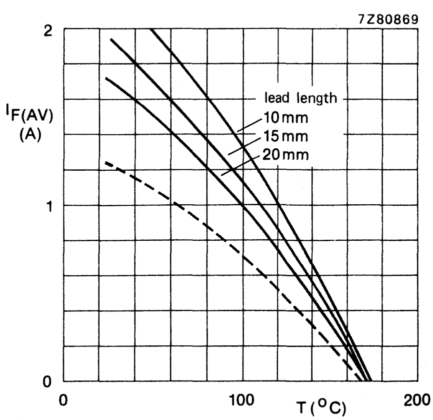


Fig. 6 Maximum average forward current as a function of temperature; the curves include losses due to reverse leakage.

$V_R = V_{RWM\,max}$, δ = 0,5; a = 1,57.

– – – = ambient temperature and device mounted as shown in Fig. 2.

—— = tie-point temperature.

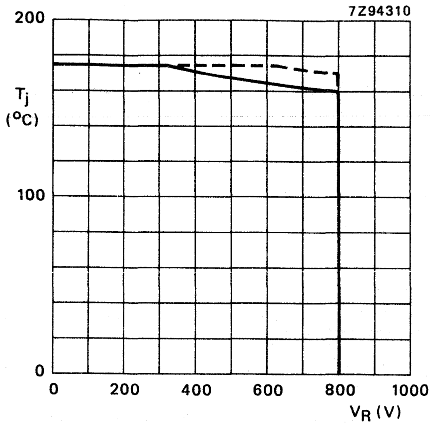


Fig. 7 Maximum permissible junction temperature as a function of reverse voltage;
—— = V_R; – – – = V_{RWM}; δ = 0,5.
Device mounted as shown in Fig. 2.

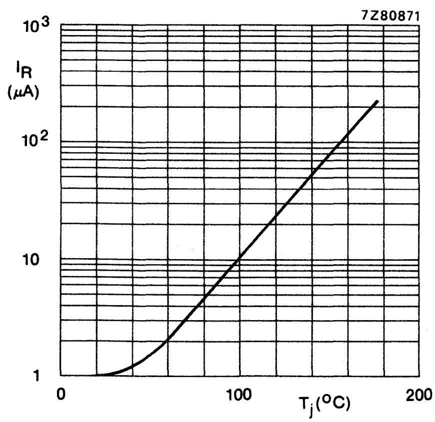


Fig. 8 Maximum values reverse current as a function of junction temperature;
$V_R = V_{RWM\,max}$.

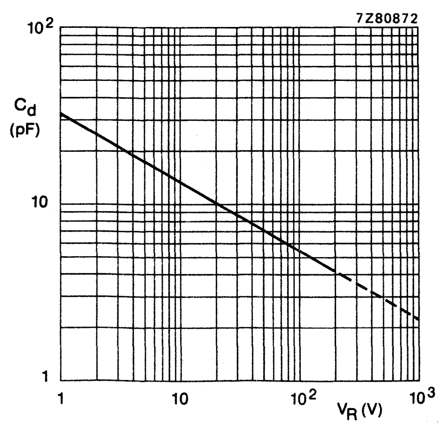


Fig. 9 Capacitance as a function of reverse voltage; f = 1 MHz; T_j = 25 °C; typical values.

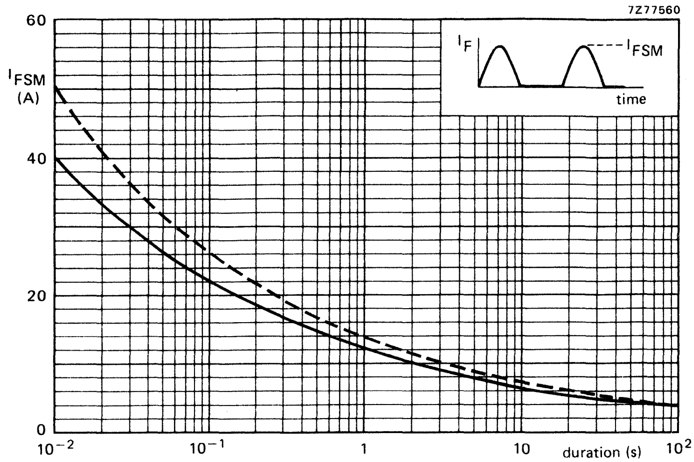
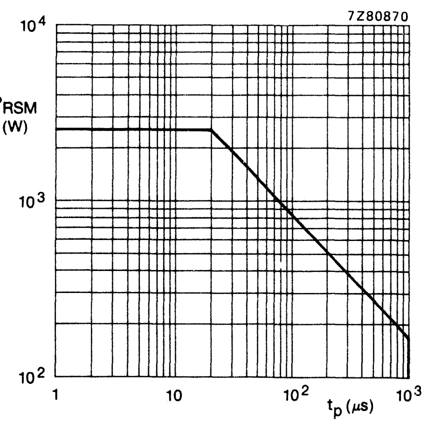


Fig. 10 Maximum permissible non-repetitive peak forward current based on sinusoidal currents; f = 50 Hz.

– – – T_j = 25 °C prior to surge; V_R = 0.

——— $T_j = T_{j\,max}$ prior to surge; $V_R = V_{RWM\,max}$.



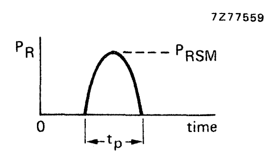


Fig. 11 Non-repetitive peak reverse power in the avalanche region; T_j = 25 °C prior to surge; typical values.

SILICON EHT SOFT-RECOVERY RECTIFIER DIODES

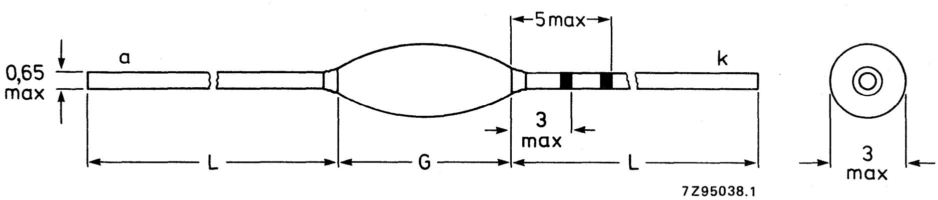
EHT rectifier diodes in glass envelopes intended for use in general purpose high-voltage applications. The devices feature non-snap-off characteristics. Because of the small envelope, the diodes should be used in a suitable insulating medium (resin, oil or special arrangements in test cases).

QUICK REFERENCE DATA

			BY705	BY706	
Working reverse voltage	V_{RW}	max.	4.0	5.0	kV
Repetitive peak reverse voltage	V_{RRM}	max.	5.0	6.0	kV
Average forward current	$I_{F(AV)}$	max.	20		mA
Junction temperature	T_j	max.	120		^oC
Reverse recovery charge	Q_s	$<$	1.0		nC
Reverse recovery time	t_{rr}	typ.	0.2		μs

MECHANICAL DATA

Dimensions in mm



L = 28 min.
G = 5.5 max.

The BY705 cathode is indicated by two brown bands on the lead.
The BY706 cathode is indicated by a brown band on the lead.

Fig. 1 SOD-61.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BY705	BY706	
Working reverse voltage	V_{RW}	max.	4.0	5.0	kV
Repetitive peak reverse voltage	V_{RRM}	max.	5.0	6.0	kV
Non-repetitive peak reverse voltage $t < 10$ ms	V_{RSM}	max.	5.0	6.0	kV
Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	20		mA
Repetitive peak forward current	I_{FRM}	max.	500		mA
Storage temperature	T_{stg}		−65 to + 120		°C
Junction temperature	T_j	max.	120		°C

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage* I_F = 100 mA; T_j = 120 °C	V_F	<	21	V
Reverse current $V_R = V_{RW}$; T_j = 120 °C	I_R	<	3.0	µA
Reverse recovery when switched from I_F = 100 mA to $V_R \geq$ 100 V; $-dI_F/dt$ = 200 mA/µs; T_j = 25 °C				
recovery charge	Q_s	<	1.0	nC
recovery time at I_R = 1 mA	t_{rr}	typ.	0.2	µs
fall time at I_R = 1 mA	t_f	>	0.1	µs

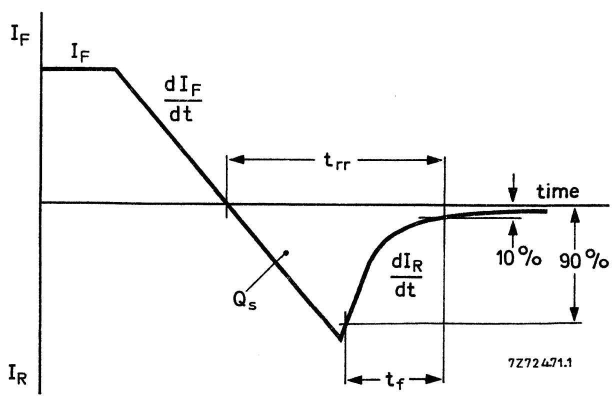


Fig. 2 Definitions of Q_s, t_{rr} and t_f.

* Measured under pulse conditions to avoid excessive dissipation.

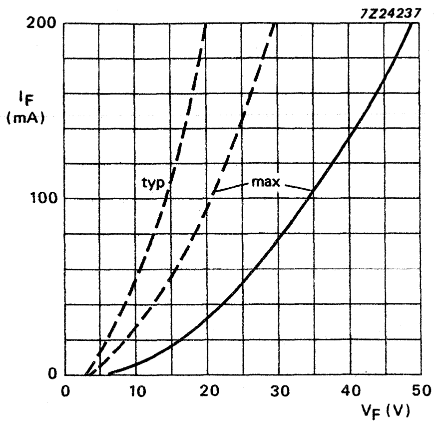


Fig. 3 Max. forward voltage;
—— = T_j = 25 °C
- - - = T_j = 120 °C

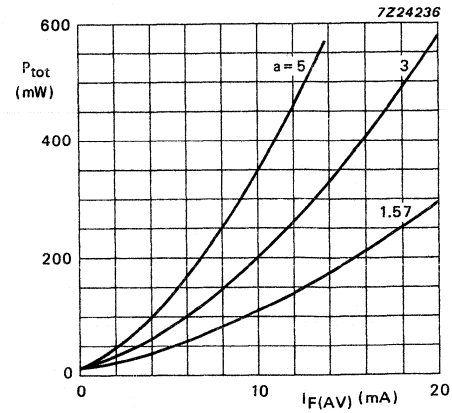


Fig. 4 Total power dissipation (forward leakage current) as a function of average forward current; a = $I_F(rms)/_F(av)$; $V_R = V_{RWmax}$.

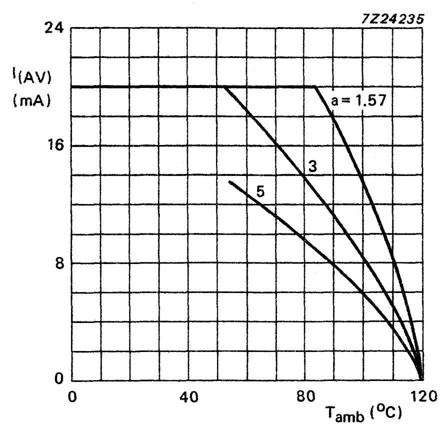


Fig. 5 Maximum average forward current as a function of ambient temperature; a = $I_F(rms)/I_F(av)$.
(The diode should be mounted in such a way that $R_{th\,j\text{-}a} \leqslant 120$ K/W)

SILICON E.H.T. SOFT-RECOVERY RECTIFIER DIODES*

E.H.T. rectifier diodes in glass envelopes intended for use in high-voltage applications such as the high-voltage supply of television receivers and monitors. The devices feature non-snap-off characteristics. Because of the small envelope, the diodes should be used in a suitable insulating medium (resin, oil or special arrangements in test-cases).

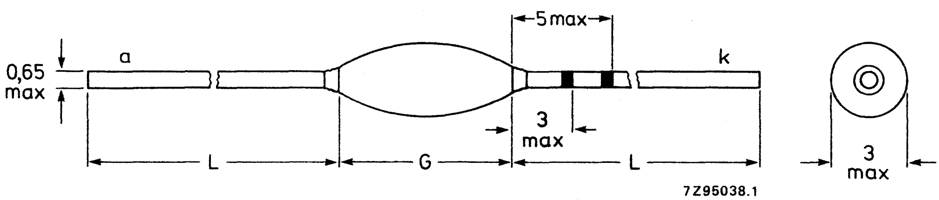
QUICK REFERENCE DATA

			BY707	708	709	
Working reverse voltage	V_{RW}	max.	9	10	12	kV
Repetitive peak reverse voltage	V_{RRM}	max.	10	12	14	kV
Average forward current	$I_{F(AV)}$	max.		4		mA
Junction temperature	T_j	max.		120		°C
Reverse recovery charge	Q_s	<		1		nC
Reverse recovery time	t_{rr}	typ.		0,2		µs

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-61.
L = 29 min.
G = 9,5 max.



The cathode of the BY707 is indicated by two red bands on the lead.
The cathode of the BY708 is indicated by a red band on the lead.
The cathode of the BY709 is indicated by a red band (inner) and a violet band (outer) on the lead.

*See also "Custom made E.H.T. stacks" in section "General".

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BY707	708	709	
Working reverse voltage	V_{RW}	max.	9	10	12	kV
Repetitive peak reverse voltage	V_{RRM}	max.	10	12	14	kV
Non-repetitive peak reverse voltage $t < 10$ ms	V_{RSM}	max.	10	12	14	kV
Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.		4		mA
Repetitive peak forward current*	I_{FRM}	max.		500		mA*
Storage temperature	T_{stg}			−65 to + 120		°C
Junction temperature	T_j	max.		120		°C

CHARACTERISTICS

Forward voltage** $I_F = 100$ mA; $T_j = 120$ °C	V_F	<	52	V**
Reverse current $V_R = V_{RW}$; $T_j = 120$ °C	I_R	<	3	µA
Reverse recovery when switched from $I_F = 100$ mA to $V_R \geqslant 100$ V with $-dI_F/dt = 200$ mA/µs; $T_j = 25$ °C				
recovery charge	Q_s	<	1	nC
recovery time	t_{rr}	typ.	0,2	µs
fall time	t_f	>	0,1	µs

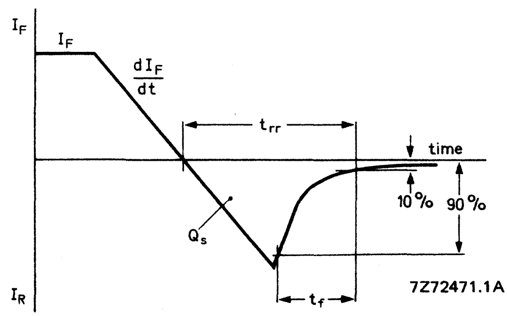


Fig. 2 Definitions of Q_s, t_{rr} and t_f.

* The device can withstand peak currents occuring during flashover in a picture tube.
** Measured under pulse conditions to avoid excessive dissipation.

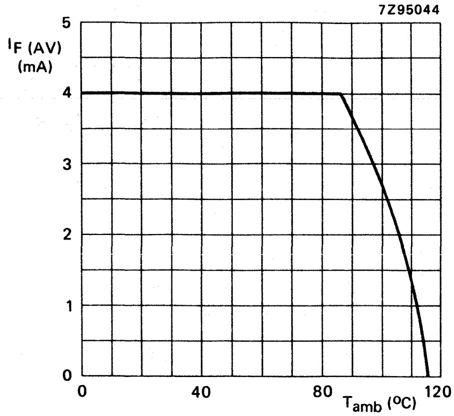


Fig. 3 Maximum permissible average forward current as a function of ambient temperature. $V_R = V_{RWmax}$. The diode should be mounted in such a way that $R_{th\ j\text{-}a} \leq 120$ K/W.

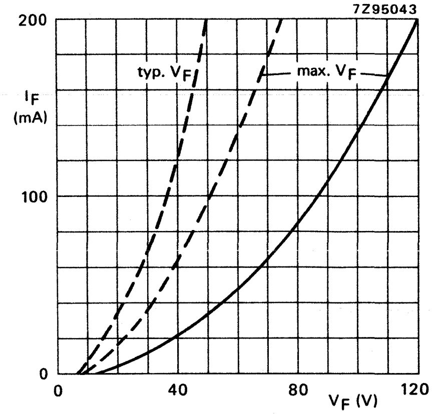


Fig. 4 ——— $T_j = 25$ °C; – – – – $T_j = 120$ °C.

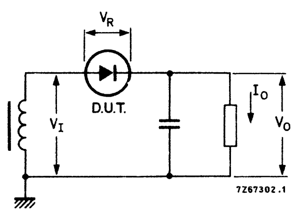


Fig. 5 Typical operation circuit.

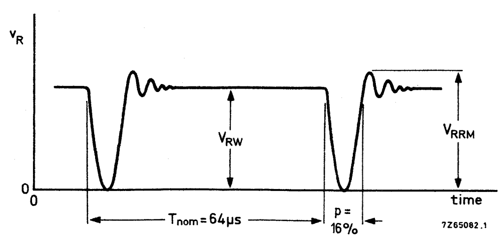


Fig. 6 Typical applied voltage.

SILICON E.H.T. SOFT-RECOVERY RECTIFIER DIODES*

E.H.T. rectifier diodes in glass envelopes intended for use in high-voltage applications such as the high-voltage supply of television receivers and monitors. The devices feature non-snap-off characteristics. Because of the small envelope, the diodes should be used in a suitable insulating medium (resin, oil or special arrangements in test cases).

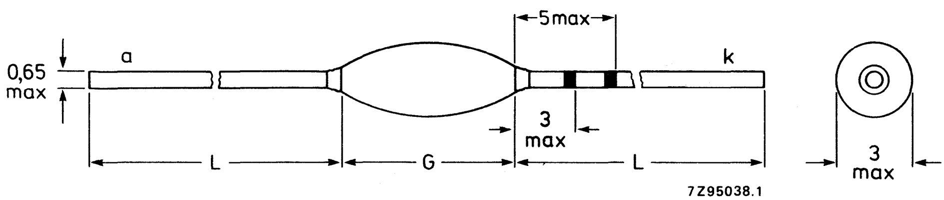
QUICK REFERENCE DATA

			BY710	711	
Working reverse voltage	V_{RW}	max.	14	16	kV
Repetitive peak reverse voltage	V_{RRM}	max.	17	19	kV
Average forward current	$I_{F(AV)}$	max.	3		mA
Junction temperature	T_j	max.	120		°C
Reverse recovery charge	Q_s	<	1		nC
Reverse recovery time	t_{rr}	typ.	0,2		μs

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-61.
L = 28 min.
G = 11 max.



The cathode of the BY710 is indicated by two green bands on the lead.
The cathode of the BY711 is indicated by a green band on the lead.

*See also "Custom made E.H.T. stacks" in section "General".

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BY710	711	
Working reverse voltage	V_{RW}	max.	14	16	kV
Repetitive peak reverse voltage	V_{RRM}	max.	17	19	kV
Non-repetitive peak reverse voltage $t < 10$ ms	V_{RSM}	max.	17	19	kV
Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	3		mA
Repetitive peak forward current*	I_{FRM}	max.	500		mA
Storage temperature	T_{stg}		−65 to + 120		°C
Junction temperature	T_j	max.	120		°C

CHARACTERISTICS

Forward voltage ** $I_F = 100$ mA; $T_j = 120$ °C	V_F	<	70	V
Reverse current $V_R = V_{RW}$; $T_j = 120$ °C	I_R	<	3	µA
Reverse recovery when switched from $I_F = 100$ mA to $V_R \geqslant 100$ V; $-dI_F/dt = 200$ mA/µs; $T_j = 25$ °C				
recovery charge	Q_s	<	1	nC
recovery time	t_{rr}	typ.	0,2	µs
fall time	t_f	>	0,1	µs

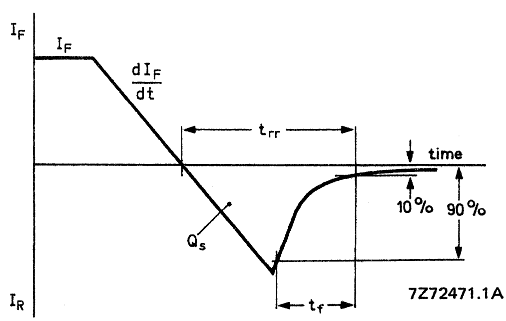


Fig. 2 Definitions of Q_s, t_{rr} and t_f.

* The device can withstand peak currents occurring during flashover in a picture tube.
** Measured under pulse conditions to avoid excessive dissipation.

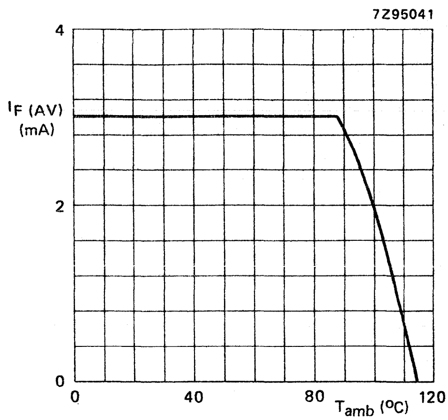


Fig. 3 Maximum permissible average forward current as a function of ambient temperature. $V_R = V_{RWmax}$. The diode should be mounted in such a way that $R_{th\ j\text{-}a} \leqslant 120$ K/W.

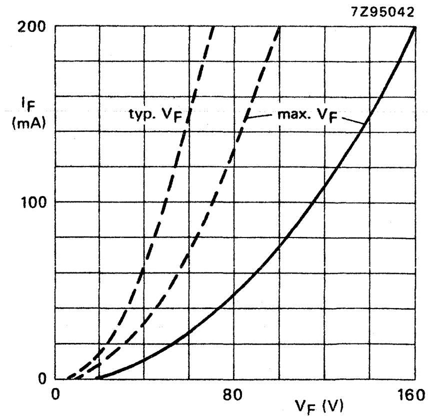


Fig. 4 ——— T_j = 25 °C; – – – – T_j = 120 °C.

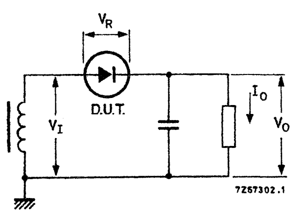


Fig. 5 Typical operation circuit.

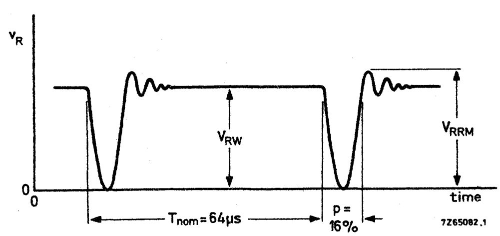


Fig. 6 Typical applied voltage.

SILICON E.H.T. SOFT-RECOVERY RECTIFIER DIODES*

E.H.T. rectifier diodes in glass envelopes intended for use in high-voltage applications such as the high-voltage supply of television receivers and monitors. The devices feature non-snap-off characteristics. Because of the small envelope, the diodes should be used in a suitable insulating medium (resin, oil or special arrangements in test-cases).

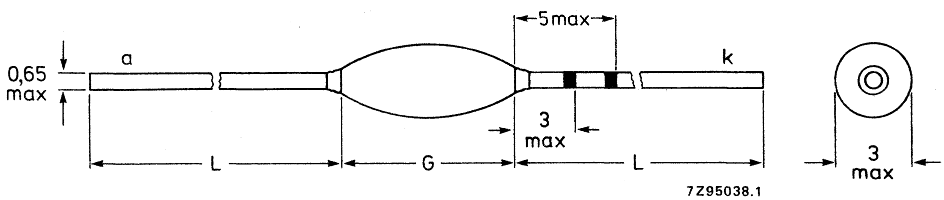
QUICK REFERENCE DATA

			BY712	713	714	
Working reverse voltage	V_{RW}	max.	18	20	24	kV
Repetitive peak reverse voltage	V_{RRM}	max.	22	24	30	kV
Average forward current	$I_{F(AV)}$	max.		3		mA
Junction temperature	T_j	max.		120		°C
Reverse recovery charge	Q_s	<		1		nC
Reverse recovery time	t_{rr}	typ.		0,2		µs

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-61.
L = 27 min.
G = 12,5 max.



The cathode of the BY712 is indicated by two blue bands on the lead.
The cathode of the BY713 is indicated by a blue band on the lead.
The cathode of the BY714 is indicated by a light blue band on the lead.

*See also "Custom made E.H.T. stacks" in section "General".

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BY712	713	714	
Working reverse voltage	V_{RW}	max.	18	20	24	kV
Repetitive peak reverse voltage	V_{RRM}	max.	22	24	30	kV
Non-repetitive peak reverse voltage $t < 10$ ms	V_{RSM}	max.	22	24	30	kV
Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.		3		mA
Repetitive peak forward current*	I_{FRM}	max.		500		mA
Storage temperature	T_{stg}			−65 to + 120		°C
Junction temperature	T_j	max.		120		°C

CHARACTERISTICS

Forward voltage** $I_F = 50$ mA; $T_j = 120$ °C	V_F	<	76	V
Reverse current $V_R = V_{RW}$; $T_j = 120$ °C	I_R	<	3	µA
Reverse recovery when switched from $I_F = 100$ mA to $V_R \geq 100$ V with $-dI_F/dt = 200$ mA/µs; $T_j = 25$ °C				
recovery charge	Q_s	<	1	nC
recovery time	t_{rr}	typ.	0,2	µs
fall time	t_f	>	0,1	µs

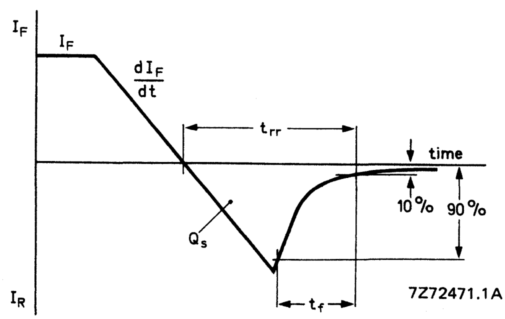


Fig. 2 Definitions of Q_s, t_{rr} and t_f.

* The device can withstand peak currents occurring during flashover in a picture tube.
** Measured under pulse conditions to avoid excessive dissipation.

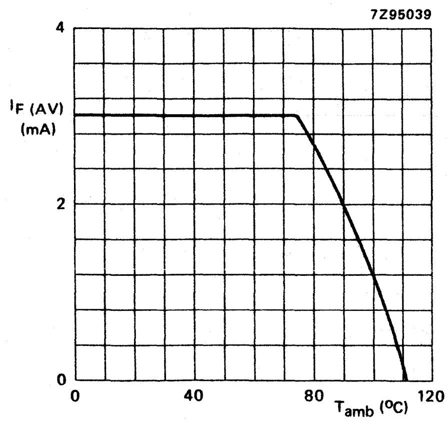


Fig. 3 Maximum permissible average forward current as a function of ambient temperature. $V_R = V_{RWmax}$. The diode should be mounted in such a way that $R_{th\,j\text{-}a} \leq 120$ K/W.

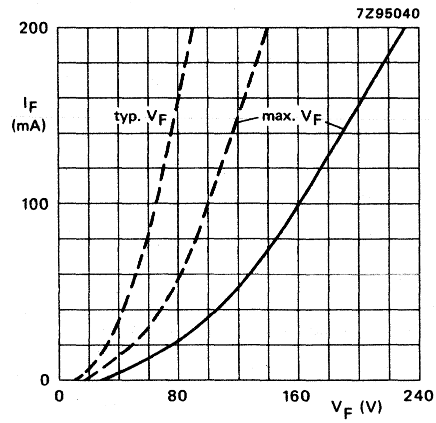


Fig. 4 ——— T_j = 25 °C; – – – – T_j = 120 °C.

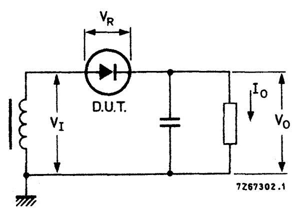


Fig. 5 Typical operation circuit.

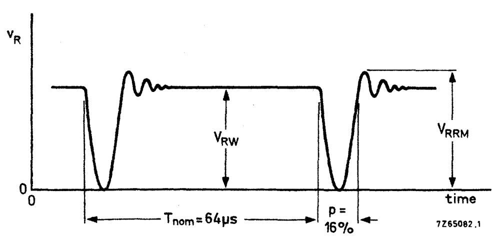


Fig. 6 Typical applied voltage.

SILICON VERY FAST EHT SOFT-RECOVERY RECTIFIER DIODES

EHT rectifier diodes in glass envelopes intended for use in general purpose high-speed high-voltage applications. The devices feature non-snap-off characteristics. Because of the small envelope, the diodes should be used in a suitable insulating medium (resin, oil or special arrangements in test cases).

QUICK REFERENCE DATA

			BY715	BY716	
Working reverse voltage	V_{RW}	max.	4.0	5.0	kV
Repetitive peak reverse voltage	V_{RRM}	max.	5.0	6.0	kV
Average forward current	$I_{F(AV)}$	max.	20		mA
Junction temperature	T_j	max.	120		°C
Reverse recovery charge	Q_s	$<$	0.4		nC
Reverse recovery time	t_{rr}	typ.	100		ns

MECHANICAL DATA

Dimensions in mm

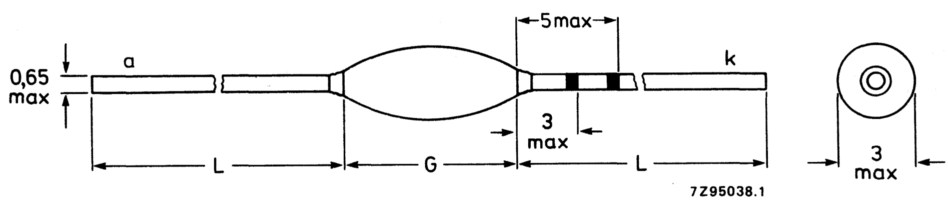


Fig. 1 SOD-61.

L = 28 min.
G = 5.5 max.

The BY715 cathode is indicated by a brown band (inner) and a green band (outer) on the lead.
The BY716 cathode is indicated by a brown band (inner) and a red band (outer) on the lead.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BY715	BY716	
Working reverse voltage	V_{RW}	max.	4.0	5.0	kV
Repetitive peak reverse voltage	V_{RRM}	max.	5.0	6.0	kV
Non-repetitive peak reverse voltage $t < 10$ ms	V_{RSM}	max.	5.0	6.0	kV
Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	20		mA
Repetitive peak forward current	I_{FRM}	max.	500		mA
Storage temperature range	T_{stg}		−65 to +120		°C
Junction temperature	T_j	max.	120		°C

CHARACTERISTICS

$T_j = 25$ °C unless otherwise specified

Forward voltage* $I_F = 100$ mA; $T_j = 120$ °C	V_F	<	28	V
Reverse current $V_R = V_{RW}$; $T_j = 120$ °C	I_R	<	3.0	µA
Reverse recovery when switched from $I_F = 100$ mA to $V_R \geqslant 100$ V; $-dI_F/dt = 200$ mA/µs; $T_j = 25$ °C				
recovery charge	Q_s	<	0.4	nC
recovery time	t_{rr}	typ.	100	ns
fall time	t_f	>	0.04	µs

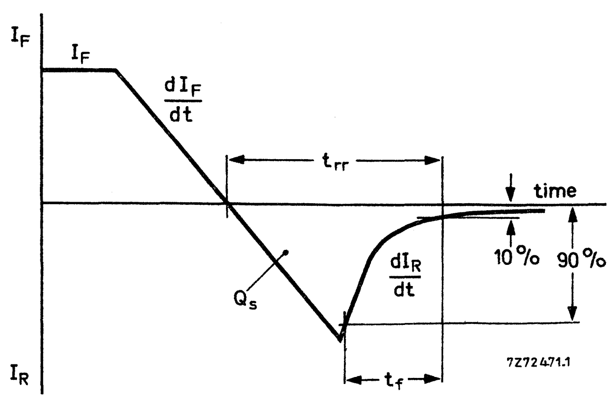


Fig. 2 Definitions of Q_s, t_{rr} and t_f.

* Measured under pulse conditions to avoid excessive dissipation.

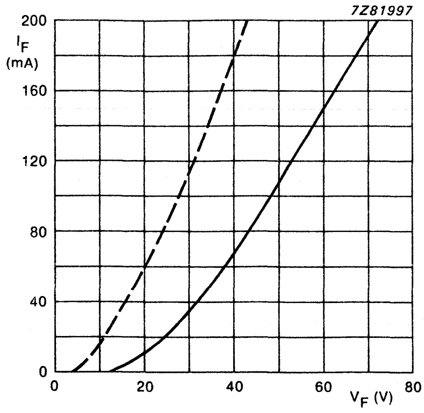


Fig. 3 Maximum forward voltage drop.
———— = T_j 25 °C;
– – – – = T_j max.

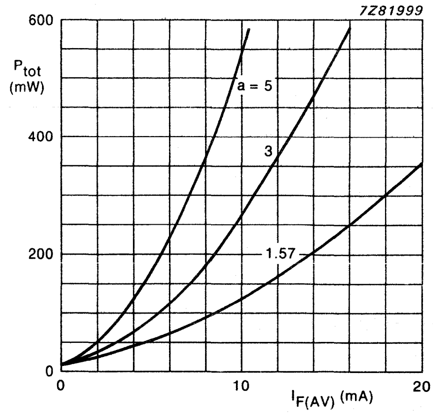


Fig. 4 Maximum steady state power dissipation (forward plus leakage current) $a = I_{F(RMS)}/I_{F(AV)}$; $V_R = R_{RWmax}$.

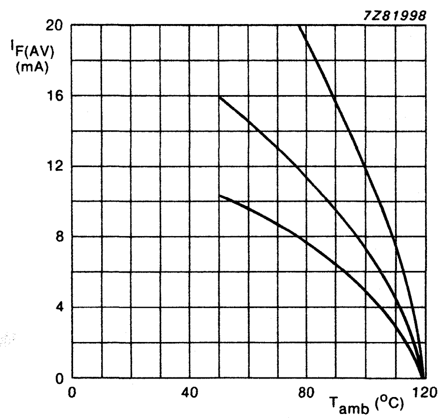


Fig. 5 Maximum average forward current as a function of ambient temperature; the curves include losses due to reverse leakage current.
Devices should be mounted in such a way that $R_{th\ j\text{-}a} \leqslant 120$ K/W.

SILICON VERY FAST EHT SOFT-RECOVERY RECTIFIER DIODES

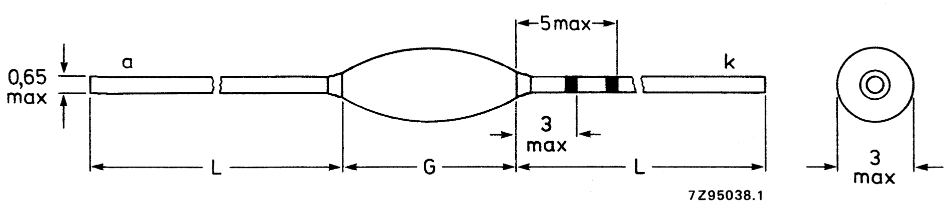
EHT rectifier diodes in glass envelopes intended for use in high-voltage applications e.g. the high-voltage supply of television receivers and monitors, at frequencies in excess of 30 kHz. The devices feature non-snap-off characteristics. Because of the small envelope, the diodes should be used in a suitable insulating medium (resin, oil or special arrangements in test cases).

QUICK REFERENCE DATA

			BY717	718	719	
Working reverse voltage	V_{RW}	max.	9.0	10	12	kV
Repetitive peak reverse voltage	V_{RRM}	max.	10	12	14	kV
Average forward current	$I_{F(AV)}$	max.		4.0		mA
Junction temperature	T_j	max.		120		°C
Reverse recovery charge	Q_s	$<$		0.4		nC
Reverse recovery time	t_{rr}	typ.		0.1		μs

MECHANICAL DATA

Dimensions in mm



L = 29 min.
G = 9.5 max.

The BY717 cathode is indicated by a red band (inner) and a green band (outer) on the lead.
The BY718 cathode is indicated by a red band (inner) and a blue band (outer) on the lead.
The BY719 cathode is indicated by a red band (inner) and a curry yellow band (outer) on the lead.

* See also "Custom made EHT stacks" in section "General".

Fig. 1 SOD-61.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BY717	718	719	
Working reverse voltage	V_{RW}	max.	9.0	10	12	kV
Repetitive peak reverse voltage	V_{RRM}	max.	10	12	14	kV
Non-repetitive peak reverse voltage $t < 10$ ms	V_{RSM}	max.	10	12	14	kV
Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	4.0			mA
Repetitive peak forward current	I_{FRM}	max.	500			mA
Storage temperature range	T_{stg}		−65 to + 120			°C
Junction temperature	T_j	max.	120			°C

CHARACTERISTICS

$T_j = 25$ °C unless otherwise specified

Forward voltage * $I_F = 100$ mA; $T_j = 120$ °C	V_F	<	69	V
Reverse current $V_R = V_{RW}$; $T_j = 120$ °C	I_R	<	3.0	μA
Reverse recovery when switched from $I_F = 100$ mA to $V_R \geqslant 100$ V; $-dI_F/dt = 200$ mA/μs; $T_j = 25$ °C				
recovery charge	Q_s	<	0.4	nC
recovery time	t_{rr}	typ.	0.1	μs
fall time	t_f	>	0.04	μs

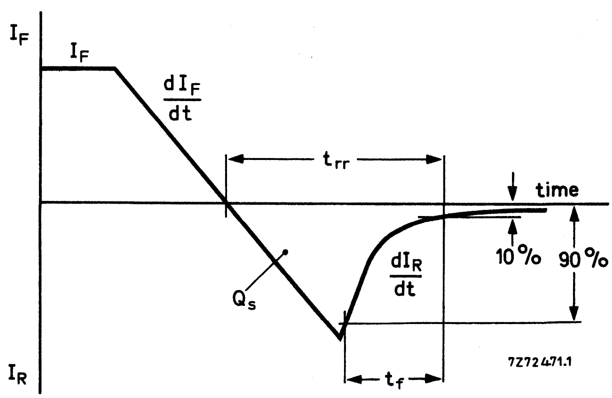


Fig. 2 Definitions of Q_s, t_{rr} and t_f.

* Measured under pulse conditions to avoid excessive dissipation.

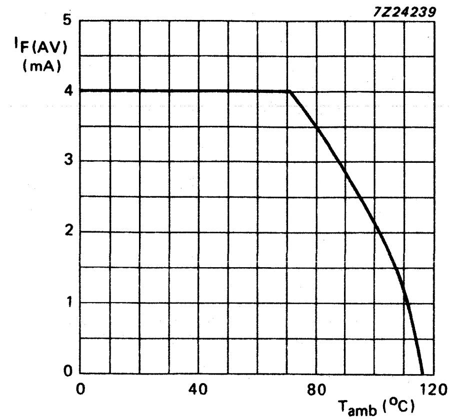


Fig. 3 Maximum permissible average forward current as a function of ambient temperature. $V_R = V_{RWmax}$. The diode should be mounted in such a way that $R_{th\ j\text{-}a} \leq 120$ K/W.

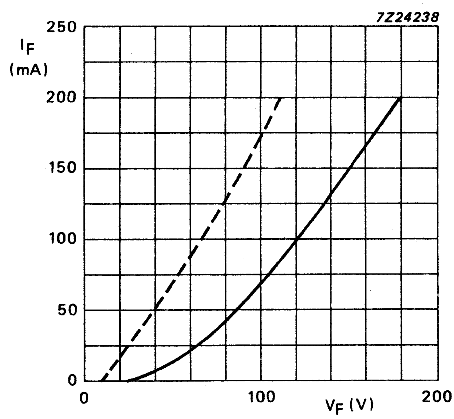


Fig. 4 Max. forward voltage drop; —— = T_j = 25 °C; - - - = T_j = 120 °C.

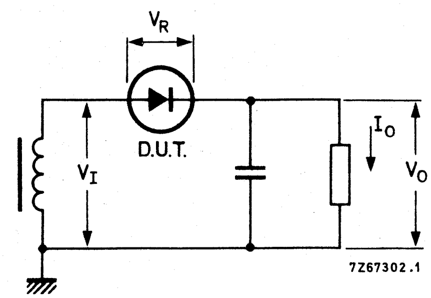


Fig. 5 Typical operation circuit.

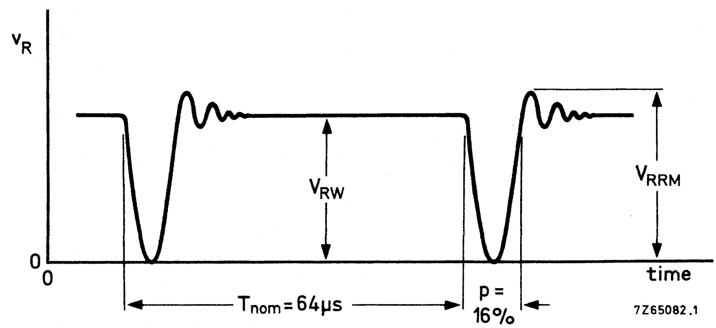


Fig. 6 Typical applied voltage waveform.

SILICON VERY FAST EHT SOFT-RECOVERY RECTIFIER DIODES*

EHT rectifier diodes in glass envelopes intended for use in high voltage applications such as the high voltage supply of television receivers and monitors at frequencies in excess of 30 kHz. The devices feature non-snap-off characteristics.
Because of the small envelope, the diodes should be used in a suitable insulating medium (resin, oil or special arrangements in test cases).

QUICK REFERENCE DATA

			BY720	BY721	
Working reverse voltage	V_{RW}	max.	14.0	16.0	kV
Repetitive peak reverse voltage	V_{RRM}	max.	17.0	19.0	kV
Average forward current	$I_{F(AV)}$	max.	3		mA
Junction temperature	T_j	max.	120		°C
Reverse recovery charge	Q_s	<	0.4		nC
Reverse recovery time	t_{rr}	typ.	100		ns

MECHANICAL DATA

Dimensions in mm

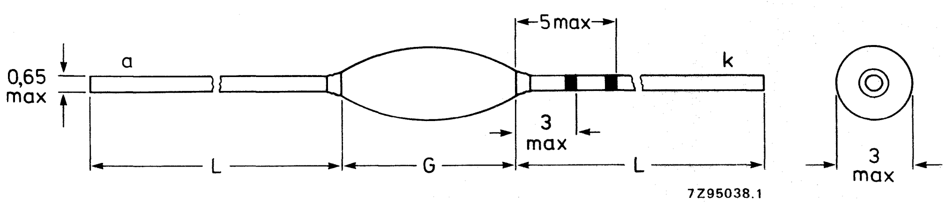


Fig. 1 SOD-61.

L = 28 min.
G = 11 max.

The BY720 cathode is indicated by a green band (inner) and a red band (outer) on the lead.
The BY721 cathode is indicated by a green band (inner) and a blue band (outer) on the lead.

* See also "Custom made EHT stacks" in section "General".

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BY720	BY721	
Working reverse voltage	V_{RW}	max.	14.0	16.0	kV
Repetitive peak reverse voltage	V_{RRM}	max.	17.0	19.0	kV
Non-repetitive peak reverse voltage $t < 10$ ms	V_{RSM}	max.	17.0	19.0	kV
Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	3		mA
Repetitive peak forward current	I_{FRM}	max.	400		mA
Storage temperature range	T_{stg}		−65 to + 120		°C
Junction temperature	T_j	max.	120		°C

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage* I_F = 100 mA; T_j = 120 °C	V_F	<	92	V
Reverse current $V_R = V_{RW}$; T_j = 120 °C	I_R	<	3.0	μA
Reverse recovery when switched from I_F = 100 mA to $V_R \geqslant 100$ V $-dI_F/dt$ = 200 mA/μs; T_j = 25 °C				
recovery charge	Q_s	<	0.4	nC
recovery time	t_{rr}	typ.	100	ns
fall time	t_f	>	0.04	μs

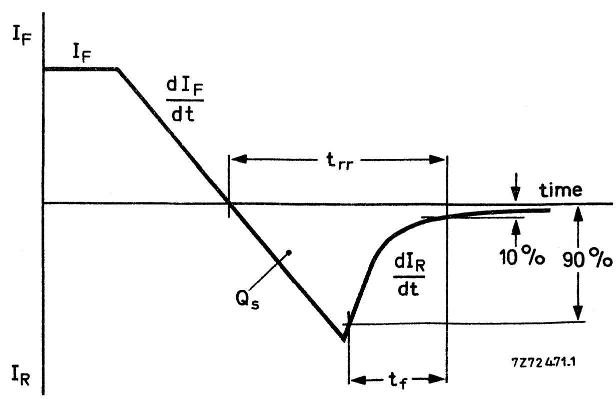


Fig. 2 Definitions of Q_s, t_{rr} and t_f.

* Measured under pulse conditions to avoid excessive dissipation.

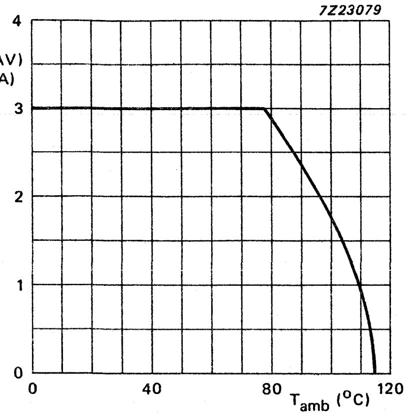


Fig. 3 Maximum permissible average forward current as a function of ambient temperature. $V_R = V_{RWmax}$. The diode should be mounted in such a way that $R_{th\ j\text{-}a} \leqslant 120$ K/W.

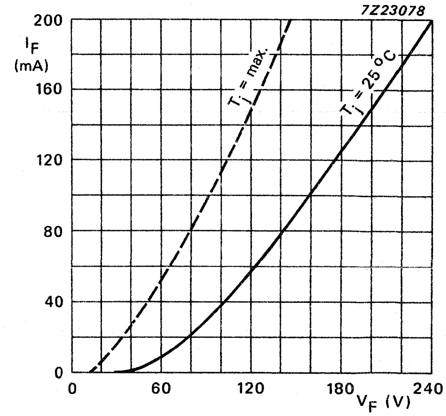


Fig. 4 Forward voltage drop.
——— T_j = 25 °C
– – – T_j = 120 °C.

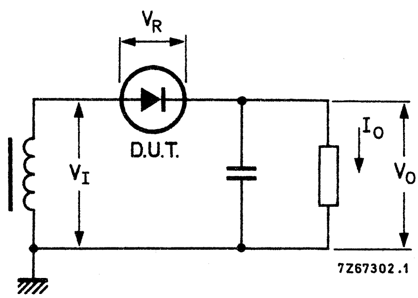


Fig. 5 Typical operation circuit.

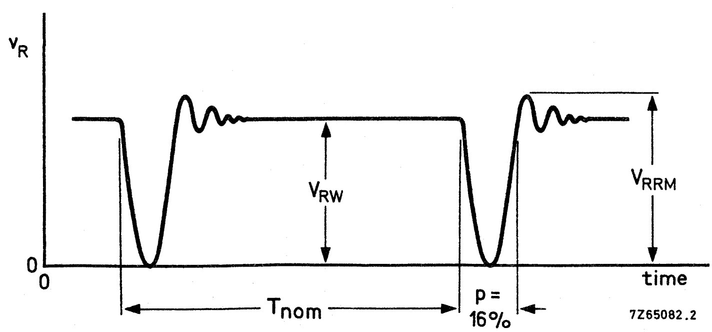


Fig. 6 Typical applied voltage.

SILICON VERY FAST EHT SOFT-RECOVERY RECTIFIER DIODES*

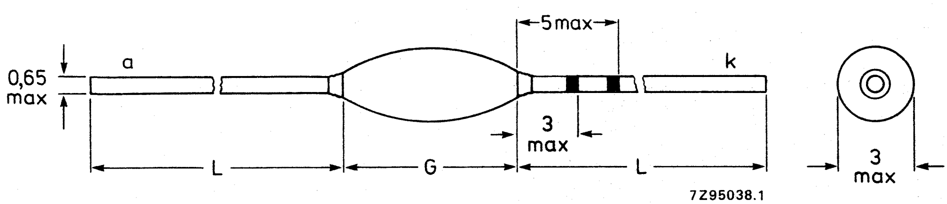
EHT rectifier diodes in glass envelopes intended for use in high-voltage applications e.g. the high-voltage supply of television receivers and monitors, at frequencies in excess of 30 kHz. The devices feature non-snap-off characteristics. Because of the small envelope, the diodes should be used in a suitable insulating medium (resin, oil or special arrangements in test cases).

QUICK REFERENCE DATA

			BY722	723	724	
Working reverse voltage	V_{RW}	max.	18	20	24	kV
Repetitive peak reverse voltage	V_{RRM}	max.	22	24	30	kV
Average forward current	$I_{F(AV)}$	max.		3.0		mA
Junction temperature	T_j	max.		120		°C
Reverse recovery charge	Q_s	max.		0.4		nC
Reverse recovery time	t_{rr}	typ.		0.1		µs

MECHANICAL DATA

Dimensions in mm



L = 27 min.
G = 12.5 max.

Fig. 1 SOD-61.

The BY722 cathode is indicated by a blue band (inner) and a red band (outer) on the lead.
The BY723 cathode is indicated by a blue band (inner) and a green band (outer) on the lead.
The BY724 cathode is indicated by a blue band (inner) and a curry yellow band (outer) on the lead.

* See also "Custom made EHT stacks" in section "General".

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BY722	723	724	
Working reverse voltage	V_{RW}	max.	18	20	24	kV
Repetitive peak reverse voltage	V_{RRM}	max.	22	24	30	kV
Non-repetitive peak reverse voltage $t < 10$ ms	V_{RSM}	max.	22	24	30	kV
Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.		3.0		mA
Repetitive peak forward current	I_{FRM}	max.		300		mA
Storage temperature range	T_{stg}			−65 to + 120		°C
Junction temperature	T_j	max.		120		°C

CHARACTERISTICS

$T_j = 25$ °C unless otherwise specified

Forward voltage* $I_F = 50$ mA; $T_j = 120$ °C	V_F	max.	88	V
Reverse current $V_R = V_{RW}$; $T_j = 120$ °C	I_R	max.	3.0	μA
Reverse recovery when switched from $I_F = 100$ mA to $V_R \geqslant 100$ V; $-dI_F/dt = 200$ mA/μs; $T_j = 25$ °C				
recovery charge	Q_s	max.	0.4	nC
recovery time	t_{rr}	typ.	0.1	μs
fall time	t_f	min.	0.04	μs

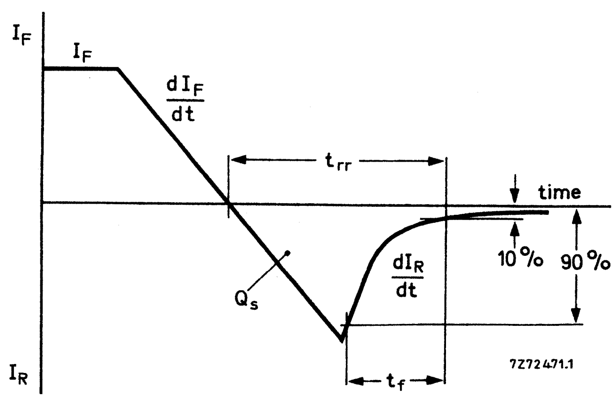


Fig. 2 Definitions of Q_s, t_{rr} and t_f.

* Measured under pulse conditions to avoid excessive dissipation.

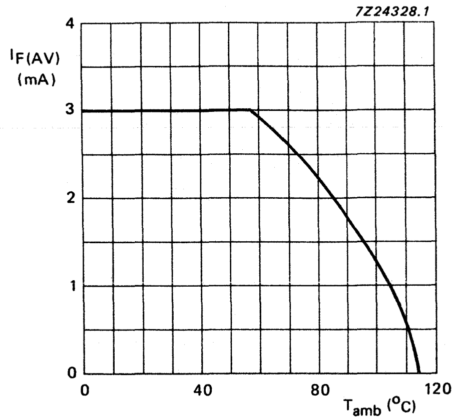
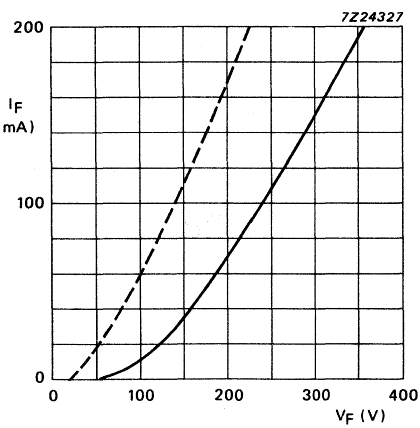


Fig. 3 Maximum permissible average forward current as a function of ambient temperature. $V_R = V_{RWmax}$. The diode should be mounted in such a way that $R_{th\,j\text{-}a} \leqslant 120$ K/W.



——— = T_j = 25 °C;
– – – = T_j = 120 °C.

Fig. 4 Forward voltage drop.

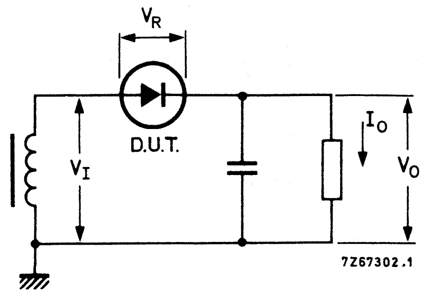


Fig. 5 Typical operation circuit.

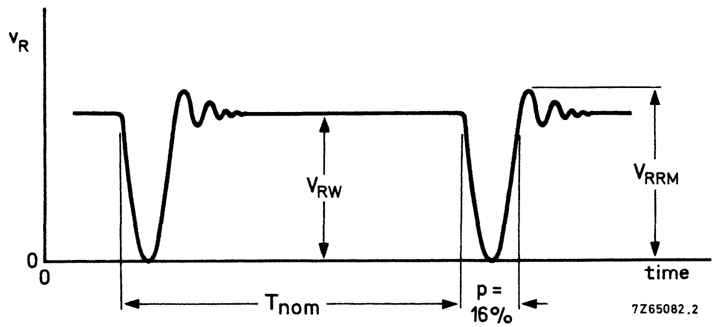


Fig. 6 Typical applied voltage waveform.

CONTROLLED AVALANCHE RECTIFIER DIODES

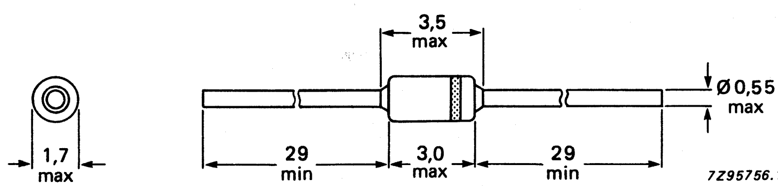
Glass passivated rectifier diodes in hermetically sealed axial-leaded SOD-91 ID* envelope, intended for general purpose rectifier applications.
The devices are capable of absorbing reverse transient energy.

QUICK REFERENCE DATA

			BYD11D	G	J	K	M	
Crest working voltage	V_{RWM}	max.	200	400	600	800	1000	V
Reverse avalanche breakdown breakdown voltage	$V_{(BR)R}$	>	225	450	650	900	1100	V
		<	1600	1600	1600	1600	1600	V
Average forward current	$I_{F(AV)}$	max.	0.58	0.58	0.58	0.58	0.58	A
Non-repetitive peak forward current	I_{FSM}	max.	10	10	10	10	10	A
Junction temperature	T_j	max.			175			°C

MECHANICAL DATA

Dimensions in mm



The marking band indicates the cathode.

Fig. 1 SOD-91.

* Implosion Diode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYD11D	G	J	K	M	
Crest working reverse voltage	V_{RWM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	800	1000	V
Average forward current (a = 1.57) T_{tp} = 55 °C; leadlength 10 mm;	$I_{F(AV)}$		0.58	0.58	0.58	0.58	0.58	A
T_{amb} = 65 °C; (see Fig. 2)	$I_{F(AV)}$		0.4	0.4	0.4	0.4	0.4	A
Non-repetitive peak forward current	I_{FSM}	max.	10	10	10	10	10	A
Non-repetitive peak reverse avalanche energy;	E_{RSM}				*			mJ
Storage temperature range	T_{stg}				−65 to + 175			°C
Junction temperature range	T_j	max.			175			°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm — $R_{thj\text{-}tp}$ = 155 K/W
2. Thermal resistance from junction to ambient; device mounted on a 1.5 mm thick epoxy-glass pc board; Cu-thickness ⩾ 40 μm; Fig. 2 (see "Thermal Model") — $R_{thj\text{-}a}$ = 225 K/W

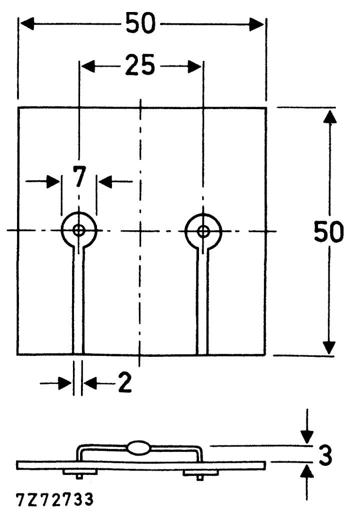


Fig. 2 Device mounted on a printed circuit board.

* Value to be fixed.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYD11D	G	J	K	M	
Forward voltage*								
I_F = 1 A; $T_j = T_{jmax.}$	V_f	<	1.1	1.1	1.1	1.1	1.1	V
I_F = 1 A	V_f	<	1.2	1.2	1.2	1.2	1.2	V
Reverse avalanche breakdown voltage								
I_R = 0.1 mA	$V_{(BR)R}$	>	225	450	650	900	1100	V
		<	1600	1600	1600	1600	1600	V
Reverse current**								
$V_R = V_{RWMmax.}$	I_R	<	1	1	1	1	1	μA
$V_R = V_{RWMmax}$; T_j = 165 °C	I_R	<	75	75	75	75	75	μA
Diode capacitance								
V_R = 0; f = 1 MHz	C_d	typ.	14	14	14	14	14	pF

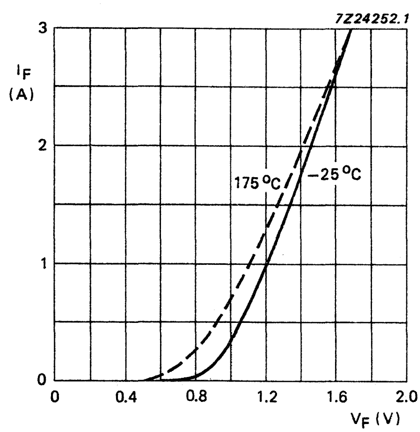


Fig. 3 Maximum forward voltage.

* Measured under pulse conditions to avoid excessive dissipation.

** Illuminance ⩽ 500 lux (daylight); relative humidity < 65%.

CONTROLLED AVALANCHE RECTIFIER DIODES

Glass passivated rectifier diodes in hermetically sealed axial-leaded ID* envelopes and intended for general purpose rectifier applications.

The device is capable of absorbing reverse transient energy.

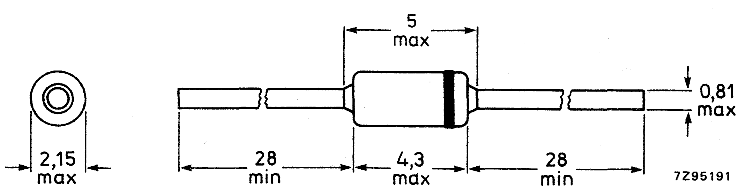
QUICK REFERENCE DATA

			BYD13D	G	J	K	M	
Crest working voltage	V_{RWM}	max.	200	400	600	800	1000	V
Reverse avalanche breakdown voltage	$V_{(BR)R}$	>	225	450	650	900	1100	V
		<	1600	1600	1600	1600	1600	V
Average forward current	$I_{F(AV)}$	max.			1,4			A
Non-repetitive peak forward current	I_{FSM}	max.			20			A
Non-repetitive peak reverse power dissipation	P_{RSM}	max.			0,4			kW
Junction temperature	T_j	max.			175			^oC

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-81.



The marking band indicates the cathode.

* Implosion Diode

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC134).

			BYD13D	G	J	K	M	
Crest working reverse voltage	V_{RWM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	800	1000	V

Average forward current (averaged over any 20 ms period)				
T_{tp} = 55 °C; lead length 10 mm	$I_{F(AV)}$	max.	1,4	A
T_{amb} = 65 °C; see Fig. 2	$I_{F(AV)}$	max.	0,75	A
Repetitive peak forward current T_{tp} = 55 °C; f = 50 Hz; a = 3; (inclusive derating for T_{jmax} at V_{RRM} = 1000 V)	I_{FRM}	max.	5,5	A
Non-repetitive peak forward current t = 10 ms, half-sine wave; T_j = $T_j$max prior to surge; $V_R = V_{RWMmax}$	I_{FSM}	max.	20	A
Non-repetitive peak reverse power dissipation; t = 20 μs (half-sine wave); $T_j = T_{j\,max}$ prior to surge	P_{RSM}	max.	0,4	kW
Non-repetitive peak reverse avalanche energy; I_R = 0,34 A; $T_j = T_{jmax}$ prior to surge; with inductive load switched off	E_{RSM}	max.	7	mJ
Storage temperature	T_{stg}		–65 to +175	°C
Junction temperature	T_j	max.	175	°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\ j\text{-}tp}$	=	60	K/W
2. Thermal resistance from junction to ambient; device mounted on an 1,5 mm thick epoxy-glass printed circuit board; Cu-thickness ⩾ 40 μm; Fig. 2 (see "Thermal model")	$R_{th\ j\text{-}a}$	=	120	K/W

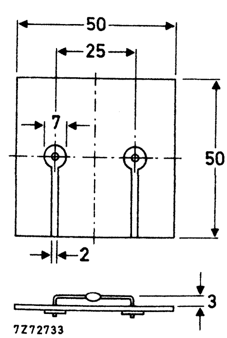


Fig. 2 Device mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYD13D	G	J	K	M	
Forward voltage *								
I_F = 1 A	V_F	<	1,05	1,05	1,05	1,05	1,05	V
I_F = 1 A; $T_j = T_{jmax}$	V_F	<	0,93	0,93	0,93	0,93	0,93	V
Reverse avalanche breakdown voltage								
I_R = 0,1 mA	$V_{(BR)R}$	>	225	450	650	900	1100	V
		<	1600	1600	1600	1600	1600	V
Reverse current								
$V_R = V_{RWMmax}$ **	I_R	<			1			μA
$V_R = V_{RWMmax}$; T_j = 165 °C	I_R	<			100			μA
Diode capacitance								
V_R = 0; f = 1 MHz	C_d	typ.			21			pF

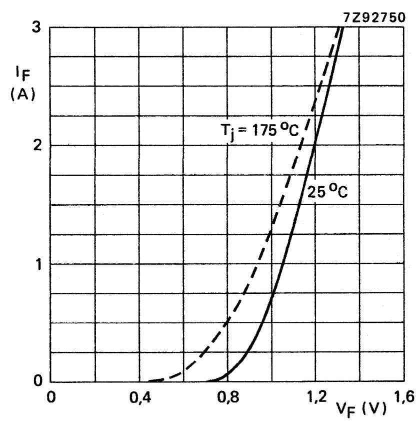


Fig. 3 Maximum forward voltage.

* Measured under pulse conditions to avoid excessive dissipation.
** Illuminance ⩽ 500 lux (daylight); relative humidity < 65%.

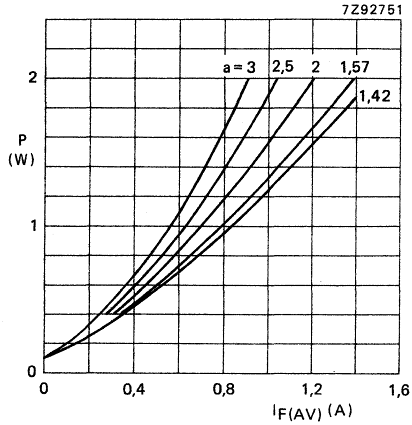


Fig. 4 Maximum values steady state power dissipation (forward plus leakage current) as a function of the average forward current.

$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RWMmax}$.

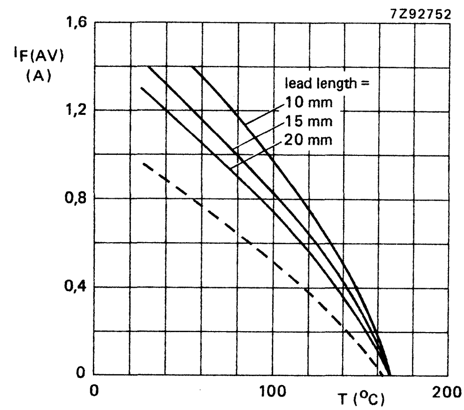


Fig. 5 Maximum average forward current as a function of temperature; the curves include losses due to reverse leakage.

$V_R = V_{RWMmax}$, $\delta = 0,5$; a = 1,57.

---------- = ambient temperature and device mounted as shown in Fig. 2

——— = tie-point temperature

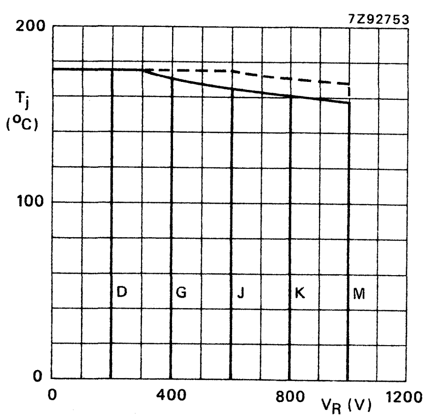


Fig. 6 Maximum permissible junction temperature as a function of reverse voltage;

——— = V_R; -------- = V_{RWM}, $\delta = 0,5$.

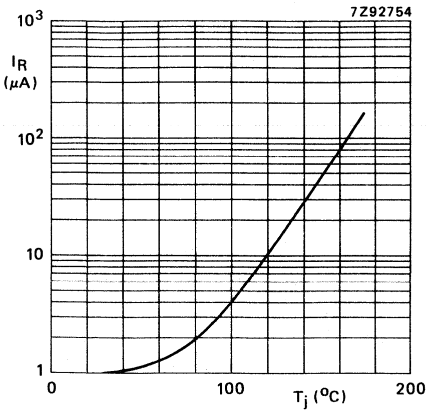


Fig. 7 Maximum values reverse current as a function of junction temperature; $V_R = V_{RWMmax}$.

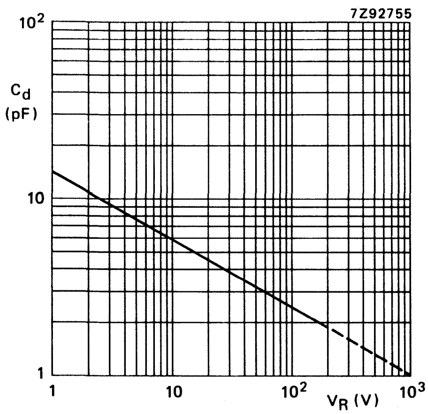
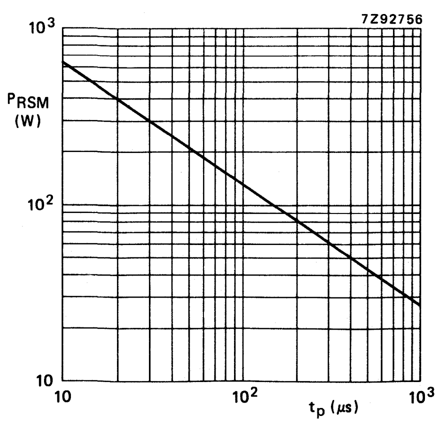


Fig. 8 Capacitance as a function of reverse voltage; f = 1 MHz; T_j = 25 °C; typical values.



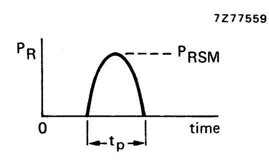


Fig. 9 Maximum permissible non-repetitive peak reverse power dissipation in the avalanche region; $T_j = T_{j\ max}$.

CONTROLLED AVALANCHE RECTIFIER DIODES

Glass passivated rectifier diodes in hermetically sealed axial-leaded ID* envelopes and intended for general purpose rectifier applications.

The device is capable of absorbing reverse transient energy.

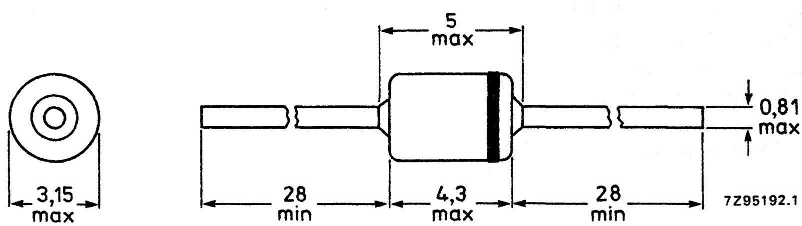
QUICK REFERENCE DATA

			BYD14D	G	J	K	M	
Crest working voltage	V_{RWM}	max.	200	400	600	800	1000	V
Reverse avalanche breakdown voltage	$V_{(BR)R}$	>	225	450	650	900	1100	V
		<	1600	1600	1600	1600	1600	
Average forward current	$I_{F(AV)}$	max.			2			A
Non-repetitive peak forward current	I_{FSM}	max.			50			A
Non-repetitive peak reverse avalanche energy	E_{RSM}	max.			40			mJ
Junction temperature	T_j	max.			175			°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-84.



The marking band indicates the cathode.

* Implosion Diode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134).

			BYD14D	G	J	K	M	
Crest working voltage	V_{RWM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	800	1000	V
Average forward current (averaged over any 20 ms period)								
T_{tp} = 45 °C; lead length 10 mm	$I_{F(AV)}$	max.			2			A
T_{amb} = 60 °C; see Fig. 2	$I_{F(AV)}$	max.			1			A
Repetitive peak forward current T_{tp} = 45 °C; f = 50 Hz; a = 4,5 (inclusive derating for T_{jmax} at V_{RRM} = 1000 V)	I_{FRM}	max.			20			A
Non-repetitive peak forward current t = 10 ms, half-sinewave (see Fig. 10)	I_{FSM}	max.			50			A
Non-repetitive peak reverse avalanche energy; I_R = 0,8 A; T_j = 25 °C prior to surge; with inductive load switched off	E_{RSM}	max.			40			mJ
Storage temperature	T_{stg}				−65 to +175			°C
Junction temperature	T_j	max.			175			°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\ j\text{-}tp}$	=	50	K/W
2. Thermal resistance from junction to ambient; device mounted on an 1,5 mm thick epoxy-glass printed circuit board; Cu-thickness ⩾ 40 μm; Fig. 2 (see "Thermal model")	$R_{th\ j\text{-}a}$	=	105	K/W

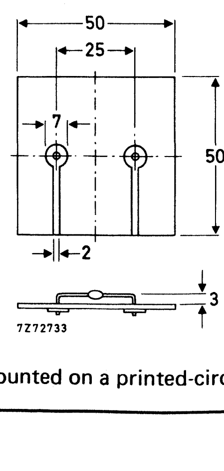


Fig. 2 Mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYD14D	G	J	K	M	
Forward voltage*								
I_F = 3 A	V_F	<	1,15	1,15	1,15	1,15	1,15	V
I_F = 3 A; T_j = T_{jmax}	V_F	<	1,05	1,05	1,05	1,05	1,05	V
Reverse avalanche breakdown voltage								
I_R = 0,1 mA	$V_{(BR)R}$	>	225	450	650	900	1100	V
		<	1600	1600	1600	1600	1600	V
Reverse current								
V_R = V_{RWMmax}**	I_R	<			1			μA
V_R = V_{RWMmax}; T_j = 165 °C	I_R	<			150			μA
Reverse recovery when switched from I_F = 1 A to $V_R \geqslant$ 30 V with $-dI_F/dt$ = 5 A/μs								
recovery charge	Q_s	typ.			3			μC
recovery time	t_{rr}	typ.			2,5			μs
Diode capacitance at f = 1 MHz								
V_R = 0	C_d	typ.			50			pF

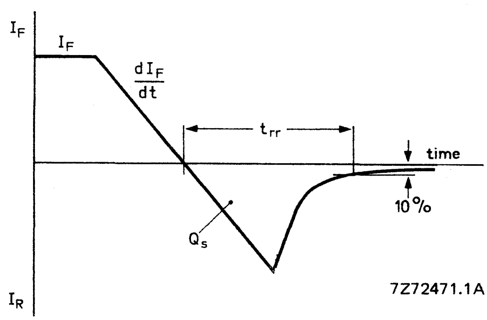


Fig. 3 Definitions of t_{rr}, Q_s and dI_F/dt.

* Measured under pulse conditions to avoid excessive dissipation.

** Illuminance ⩽ 500 lux (daylight); relative humidity < 65%.

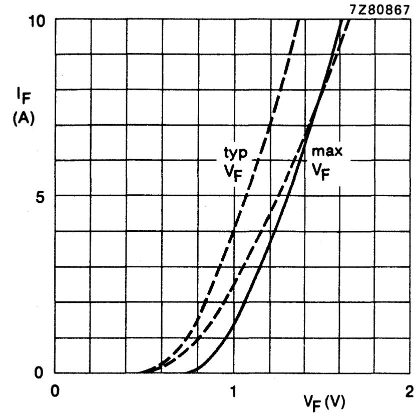


Fig. 4 Forward voltage;
——— T_j = 25 °C; -------------T_j = 175 °C.

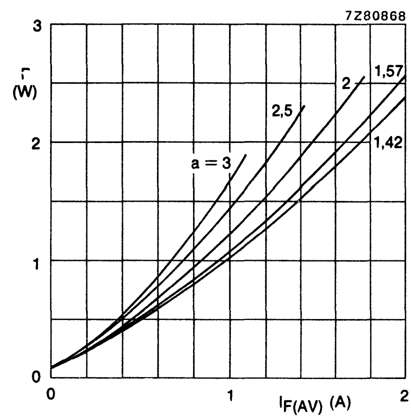


Fig. 5 Maximum values steady state power dissipation (forward plus leakage current) as a function of the average a forward current.

$A = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RWMmax}$.

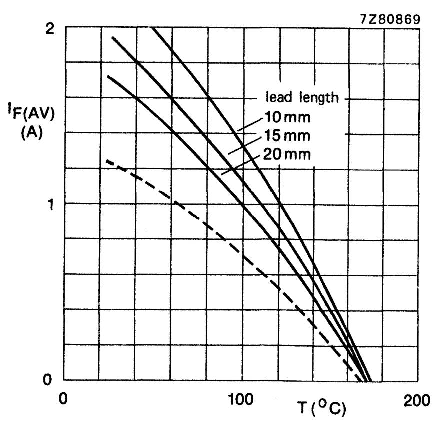


Fig. 6 Maximum average forward current as a function of temperature; the curves include losses due to reverse leakage.

$V_R = V_{RWMmax}$, δ = 0,5; a = 1,57.

------- = ambient temperature and device mounted as shown in Fig. 2

—— = tie-point temperature

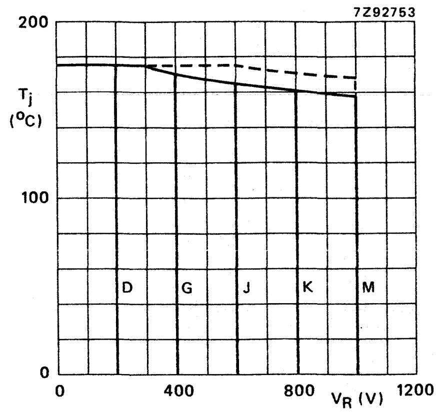


Fig. 7 Maximum permissible junction temperature as a function of reverse voltage; ———— = V_R; ------------ = V_{RWM}, $\delta = 0,5$; device mounted as shown in Fig. 2.

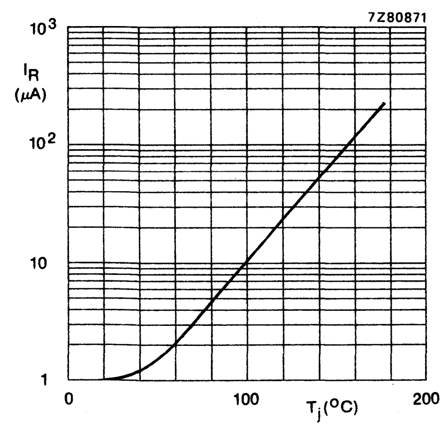


Fig. 8 Maximum values reverse current as a function of junction temperature; $V_R = V_{RWMmax}$.

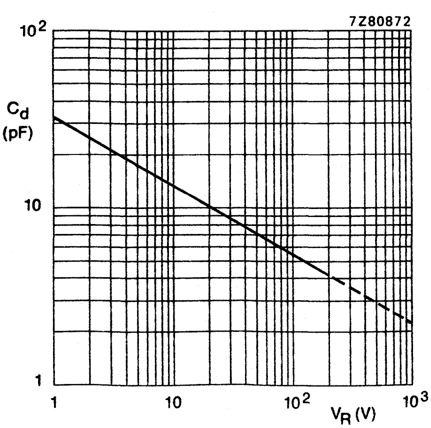


Fig. 9 Capacitance as a function of reverse voltage; f = 1 MHz; T_j = 25 °C; typical values.

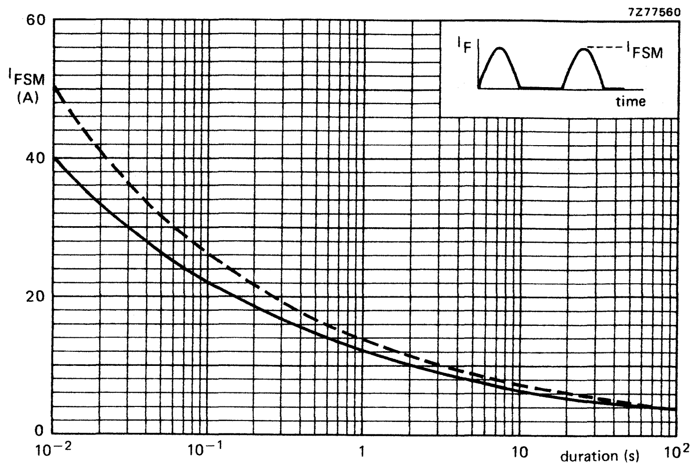
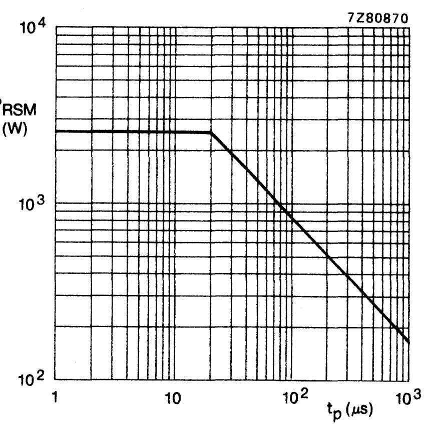


Fig. 10 Maximum permissible non-repetitive peak forward current based on sinusoidal currents; f = 50 Hz.

---------------- T_j = 25 °C prior to surge; $V_R = 0$

———————— $T_j = T_{j\,max}$ prior to surge; $V_R = V_{RWM\,max}$.



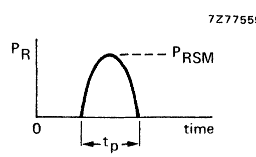


Fig. 11 Non-repetitive peak reverse power in the avalanche region; T_j = 25 °C prior to surge; typical values.

CONTROLLED AVALANCHE RECTIFIER DIODES

Glass passivated rectifier diodes in hermetically sealed leadless SMID* envelopes and intended for general purpose rectifier applications.

The device is capable of absorbing reverse transient energy.

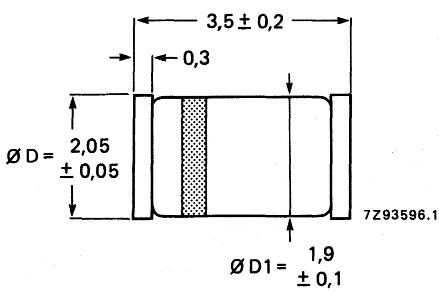
QUICK REFERENCE DATA

			BYD17D	G	J	K	M	
Crest working voltage	V_{RWM}	max.	200	400	600	800	1000	V
Reverse avalanche breakdown voltage	$V_{(BR)R}$	>	225	450	650	900	1100	V
		<	1600	1600	1600	1600	1600	V
Average forward current	$I_{F(AV)}$	max.			1,5			A
Non-repetitive peak forward current	I_{FSM}	max.			20			A
Non-repetitive peak reverse power dissipation	P_{RSM}	max.			0,4			kW
Junction temperature	T_j	max.			175			°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-87.



* Surface-mounted implosion diode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYD17D	G	J	K	M	
Crest working reverse voltage	V_{RWM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	800	1000	V

Average forward current (averaged over any 20 ms period)				
T_{tp} = 105 °C;	$I_{F(AV)}$	max.	1,5	A
T_{amb} = 65 °C; p.c. board mounting	$I_{F(AV)}$	max.	0,6	A
Repetitive peak forward current T_{tp} = 55 °C; f = 50 Hz; a = 3; (inclusive derating for $T_{j\,max}$ at V_{RRM} = 1000 V)	I_{FRM}	max.	5,5	A
Non-repetitive peak forward current t = 10 ms, half-sinewave; $T_j = T_{j\,max}$ prior to surge; $V_R = V_{RWMmax}$	I_{FSM}	max.	20	A
Non-repetitive peak reverse power dissipation; t = 20 µs (half-sinewave); $T_j = T_{j\,max}$ prior to surge	P_{RSM}	max.	0,4	kW
Non-repetitive peak reverse avalanche energy; I_R = 0,34 A; $T_j = T_{j\,max}$ prior to surge; with inductive load switched off	E_{RSM}	max.	7	mJ
Storage temperature	T_{stg}		−65 to + 175	°C
Junction temperature	T_j	max.	175	°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point	$R_{th\,j\text{-}tp}$	=	30	K/W
2. Thermal resistance from junction to ambient; device mounted on an 1,5 mm thick epoxy-glass p.c. board; Cu-thickness ⩾ 40 µm (see Fig. 2)	$R_{th\,j\text{-}a}$	=	150	K/W

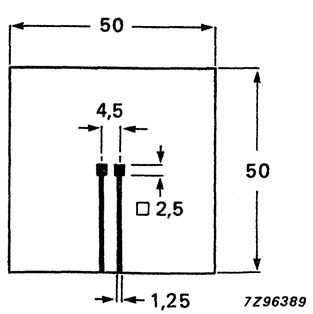


Fig. 2 Mounted on a p.c. board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYD17D	G	J	K	M	
Forward voltage*								
I_F = 1 A; $T_j = T_{j\,max}$	V_F	<	0,93	0,93	0,93	0,93	0,93	V
I_F = 1 A	V_F	<	1,05	1,05	1,05	1,05	1,05	V
Reverse avalanche breakdown voltage		>	225	450	650	900	1100	V
I_R = 0,1 mA	$V_{(BR)R}$	<	1600	1600	1600	1600	1600	V
Reverse current								
$V_R = V_{RWMmax}$	I_R	<			1			μA
$V_R = V_{RWMmax}$; T_j = 165 °C	I_R	<			100			μA
Diode capacitance								
V_R = 0; f = 1 MHz	C_d	typ.			21			pF

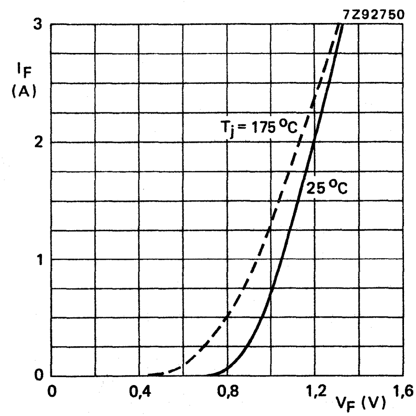


Fig. 3 Maximum forward voltage.

* Measured under pulse conditions to avoid excessive dissipation.

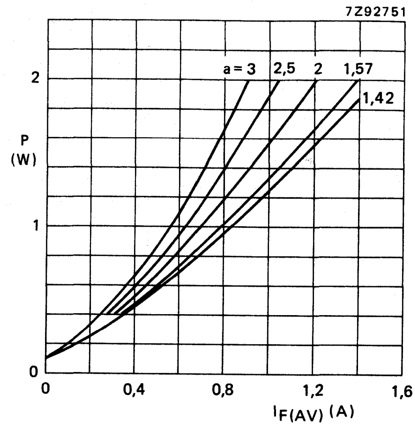


Fig. 4 Maximum values steady power dissipation (forward plus leakage current) as a function of the average (a) forward current.
$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RWMmax}$.

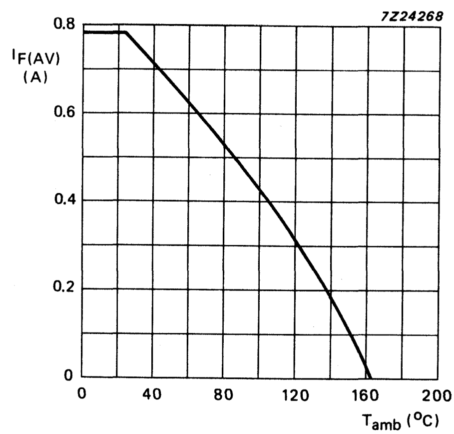


Fig. 5 Maximum average forward current as a function of temperature; the curves include losses due to reverse leakage.
$V_R = V_{RWMmax}$, $\delta = 0.5$; $a = 1.57$.
——— = ambient temperature and device mounted as shown in Fig. 2.

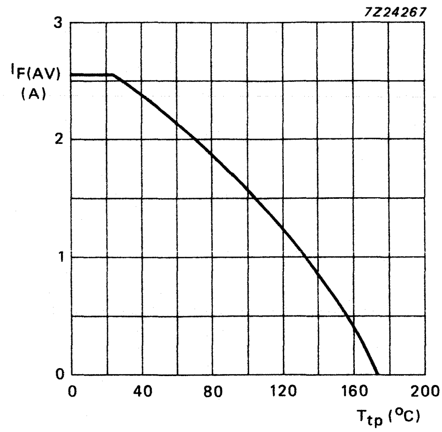


Fig. 6 Maximum average forward current as a function of temperature; the curves include losses due to reverse leakage.
$V_R = V_{RWMmax}$, $\delta = 0.5$; a = 1.57.
——— = tie-point temperature and device mounted as shown in Fig. 2.

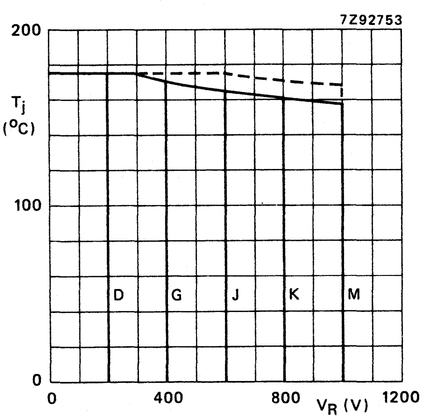


Fig. 7 Maximum permissible junction temperature as a function of reverse voltage;
——— = V_R; – – – – = V_{RWM}, $\delta = 0.5$.

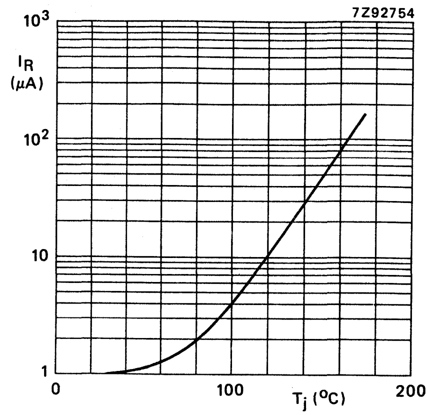


Fig. 8 Maximum values reverse current as a function of junction temperature; $V_R = V_{RWMmax}$.

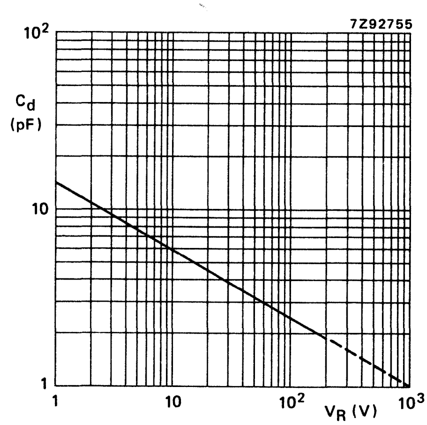


Fig. 9 Capacitance as a function of reverse voltage; f = 1 MHz; T_j = 25 °C; typical values.

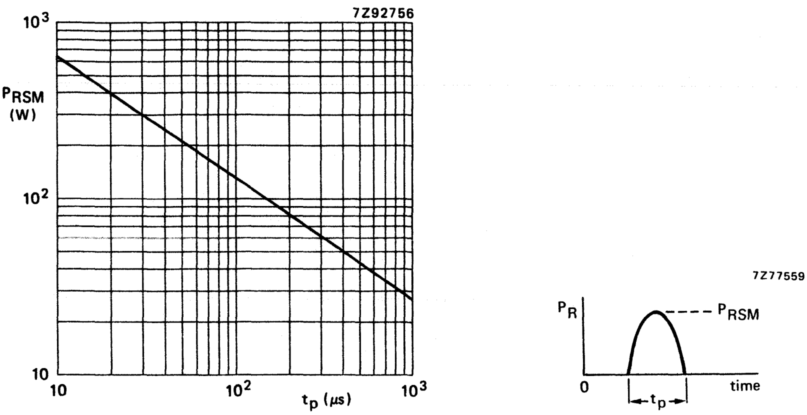


Fig. 10 Maximum permissible non-repetitive peak reverse power dissipation in the avalanche region; $T_j = T_{jmax}$.

AVALANCHE FAST SOFT-RECOVERY RECTIFIER DIODES

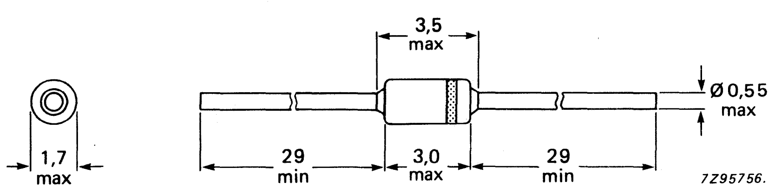
Glass passivated rectifier diodes in hermetically sealed axial leaded SOD-91 envelopes, intended for television and industrial applications.
The devices feature non-snap-off (soft recovery) switching characteristics and are capable of absorbing reverse transient energy.

QUICK REFERENCE DATA

			BYD31D	31G	31J	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	V
Continuous reverse voltage	V_R	max.	200	400	600	V
Average forward current	$I_{F(AV)}$	max.	0.5	0.5	0.5	A
Non-repetitive peak forward current	I_{FSM}	max.	10	10	10	A
Reverse recovery time	t_{rr}	<	250	250	250	ns

MECHANICAL DATA

Dimensions in mm



The marking band indicates the cathode.

Fig. 1 SOD-91.

* Implosion Diode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYD31D	31G	31J	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	V
Continuous reverse voltage	V_R	max.	200	400	600	V
Average forward current (a = 1.42)						
T_{tp} = 55 °C; lead length 10 mm	$I_{F(AV)}$	max.	0.5	0.5	0.5	A
T_{amb} = 60 °C; see Fig. 2	$I_{F(AV)}$	max.	0.35	0.35	0.35	A
Non-repetitive peak forward current	I_{IFSM}	max.	10	10	10	A
Non-repetitive peak reverse avalanche energy.	E_{RSM}			*		mJ
Storage temperature range	T_{stg}			−65 to + 175		°C
Junction temperature range	T_j	max.		−65 to + 175		°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{thj\text{-}tp}$	=	155	K/W
2. Thermal resistance from junction to ambient; device mounted on a 1.5 mm thick epoxy-glass pc board; Cu-thickness ⩾ 40 μm; Fig. 2 (see "Thermal Model")	$R_{thj\text{-}a}$	=	225	K/W

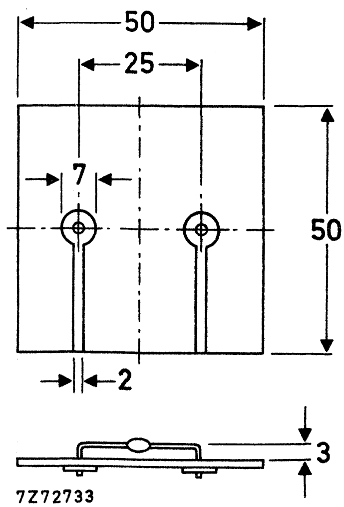


Fig. 2 Mounted on a printed-circuit board.

* Value to be fixed.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYD31D	31G	31J	
Forward voltage*						
I_F = 1 A; $T_j = T_{jmax}$.	V_f	<	1.44	1.44	1.44	V
I_F = 1 A	V_f	<	1.6	1.6	1.6	V
Reverse avalanche breakdown voltage						
I_R = 0.1 mA	$V_{(BR)R}$	>	300	500	700	V
Reverse current**						
$V_R = V_{RRM}$max.	I_R	<	1	1	1	μA
$V_R = V_{RRM}$max; T_j = 165 °C	I_R	<	75	75	75	μA
Reverse recovery when switched from I_F = 1 A to $V_R \geq$ 30 V with $-dI_F/dt$ = 20 A/μs						
recovered charge	Qs	<	250	250	250	nC
recovery time	t_{rr}	<	250	250	250	ns

DEVELOPMENT DATA

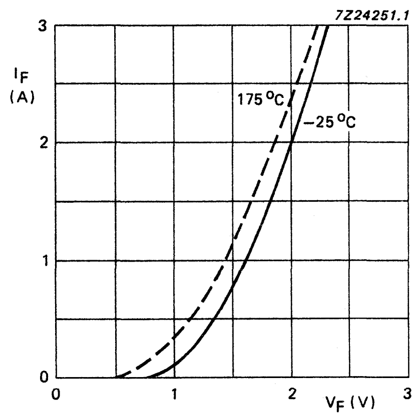


Fig. 3 Maximum forward voltage.

* Measured under pulse conditions to avoid excessive dissipation.
** Illuminance ≤ 500 lux (daylight); relative humidity < 65%.

AVALANCHE FAST SOFT-RECOVERY RECTIFIER DIODES

Rectifier diodes in hermetically sealed axial-leaded ID* envelopes. They are intended for television and industrial applications, such as switched-mode power supplies, scan rectifiers in TV receivers and also for use in inverter and converter applications. The devices feature non-snap-off (soft-recovery) switching characteristics and are capable of absorbing reverse transient energy (e.g. during flashover in a picture tube).

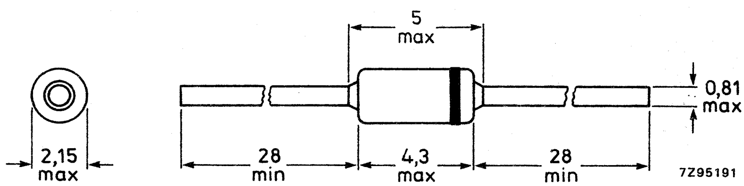
QUICK REFERENCE DATA

			BYD33D	G	J	K	M	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	600	1000	V
Average forward current	$I_{F(AV)}$	max.		1,3		1,3		A
Non-repetitive peak forward current	I_{FSM}	max.		20		20		A
Non-repetitive peak reverse energy	E_{RSM}	max.		10		7		mJ
Reverse recovery time	t_{rr}	<		250		300		ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-81.



The marking band indicates the cathode.

* Implosion Diode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYD33D	G	J	K	M	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	800	1000	V
Average forward current (averaged over any 20 ms period)								
T_{tp} = 55 °C; lead length 10 mm	$I_{F(AV)}$	max.		1,3		1,3		A
T_{amb} = 65 °C; see Fig. 2	$I_{F(AV)}$	max.		0,7		0,7		A
Repetitive peak forward current								
T_{tp} = 55 °C; see Fig. 10	I_{FRM}	max.		12		12		A
T_{amb} = 65 °C; see Fig. 11	I_{FRM}	max.		7		7		A
Non-repetitive peak forward current t = 10 ms, half-sine wave; T_j = $T_{j\,max}$ prior to surge; V_R = V_{RRMmax}	I_{FSM}	max.		20		20		A
Non-repetitive peak reverse avalanche energy; I_R = 400 mA; T_j = $T_{j\,max}$, prior to surge; with inductive load switched off	E_{RSM}	max.		10		7		mJ
Storage temperature	T_{stg}				−65 to +175			°C
Junction temperature	T_j	max.			175			°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm — $R_{th\,j\text{-}tp}$ = 60 K/W
2. Thermal resistance from junction to ambient; device mounted on a 1,5 mm thick epoxy-glass printed circuit board; Cu-thickness ⩾ 40 μm; Fig. 2 (see "Thermal Model") — $R_{th\,j\text{-}a}$ = 120 K/W

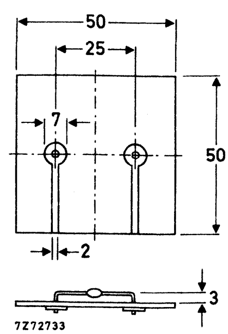


Fig. 2 Mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYD33D	G	J	K	M	
Forward voltage*								
I_F = 1 A	V_F	<	1,3	1,3	1,3	1,3	1,3	V
I_F = 1 A; T_j = $T_{j\,max}$	V_F	<	1,1	1,1	1,1	1,1	1,1	V
Reverse avalanche breakdown voltage								
I_R = 0,1 mA	$V_{(BR)R}$	>	300	500	700	900	1100	V

			BYD33D;G;J	K;M	
Reverse current					
$V_R = V_{RRMmax}$**	I_R	<	1	1	μA
$V_R = V_{RRMmax}$; T_j = 165 °C	I_R	<	100	100	μA
Reverse recovery when switched from I_F = 1 A to $V_R \geqslant$ 30 V with $-dI_F/dt$ = 20 A/μs					
recovery charge	Q_s	<	250	400	nC
recovery time	t_{rr}	<	250	300	ns
Maximum slope of reverse recovery current when switched from I_F = 1 A to $V_R \geqslant$ 30 V with $-dI_F/dt$ = 1 A/μs	$\lvert dI_R/dt \rvert$	<	6	5	A/μs

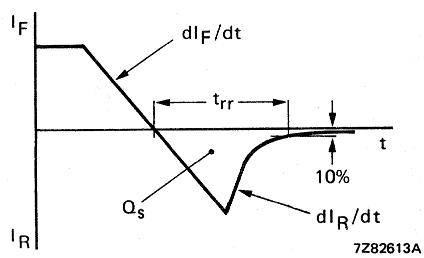


Fig. 3 Definitions of t_{rr}, Q_s, dI_F/dt and dI_R/dt.

* Measured under pulse conditions to avoid excessive dissipation.

** Illuminance ⩽ 500 lux (daylight); relative humidity < 65%.

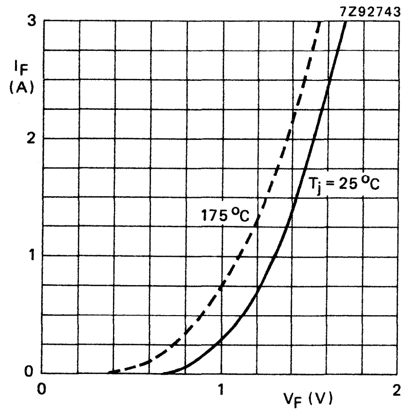


Fig. 4 Maximum forward voltage.

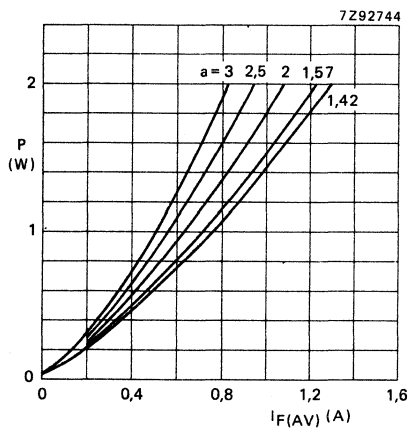
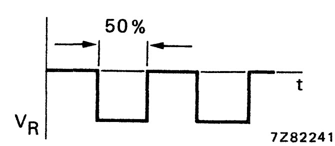


Fig. 5 Maximum values steady state power dissipation (forward plus leakage current) excluding switching losses as a function of the average forward current.

The graph is for switched-mode application.

$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRM\,max}$.



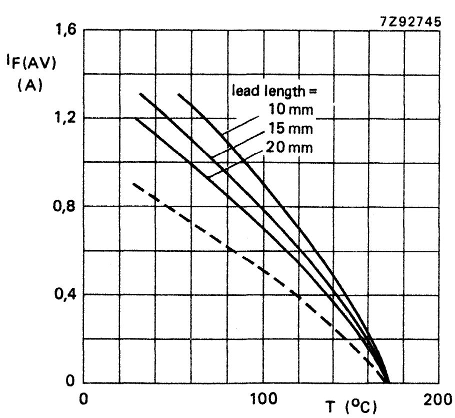


Fig. 6 Maximum average forward current as a function of temperature; the curves include losses due to reverse leakage.

The graph is for switched-mode application.

$V_R = V_{RRM\,max}$, $\delta = 0,5$; a = 1,42.

– – – = ambient temperature and device mounted as shown in Fig. 2

——— = tie-point temperature

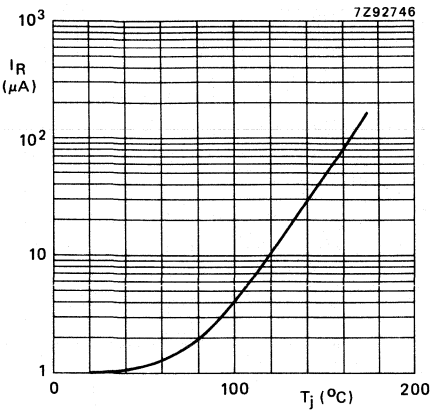


Fig. 7 Maximum values reverse current as a function of junction temperature; $V_R = V_{RRM\,max}$.

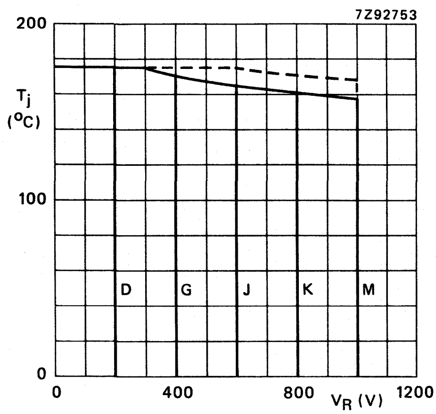


Fig. 8 Maximum permissible junction temperature as a function of reverse voltage;
—— = V_R; – – – = V_{RRM}, δ = 0,5.

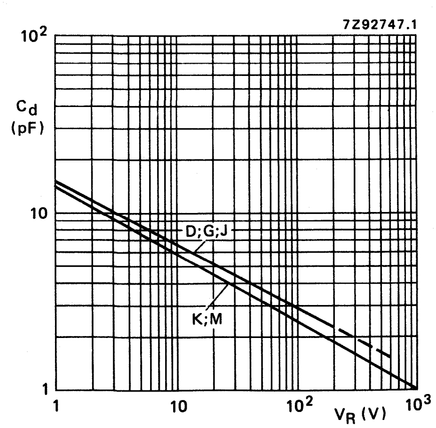


Fig. 9 Capacitance as a function of reverse voltage; f = 1 MHz; T_j = 25 °C; typical values.

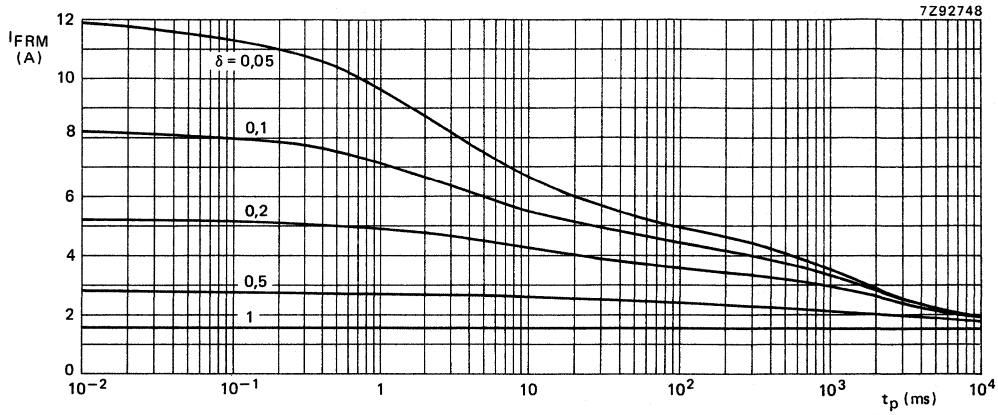


Fig. 10 Maximum repetitive peak forward current as a function of the pulse time (square pulse) and duty-factor δ at $T_{tie\text{-}point}$ = 55 °C; $R_{th\ j\text{-}tp}$ = 60 K/W; V_{RRM} during 1 − δ; the curves include derating for $T_{j\ max}$ at V_{RRM} = 1000 V.

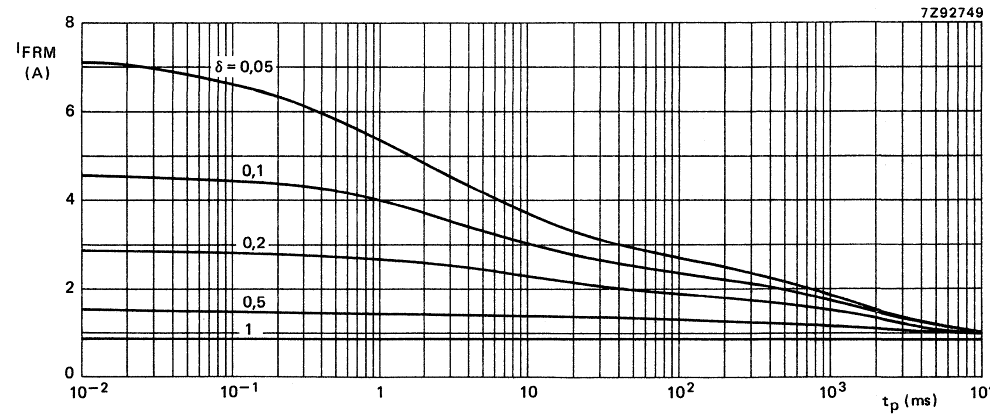


Fig. 11 Maximum repetitive peak forward current as a function of the pulse time (square pulse) and duty-factor δ at T_{amb} = 65 °C; $R_{th\ j\text{-}a}$ = 120 K/W; V_{RRM} during 1 − δ; the curves include derating for $T_{j\ max}$ at V_{RRM} = 1000 V.

AVALANCE FAST SOFT-RECOVERY RECTIFIER DIODES

Glass passivated rectifier diodes in hermetically sealed axial-leaded ID* envelopes. They are intended for television and industrial applications, such as switched-mode power supplies, scan rectifiers in TV receivers and also for use in inverter and converter applications. The devices feature non-snap-off (soft-recovery) switching characteristics and are capable of absorbing reverse transient energy (e.g. during flashover in a picture tube).

QUICK REFERENCE DATA

			BYD34D	G	J	K	M	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	600	1000	V
Average forward current	$I_{F(AV)}$	max.		1.8			1.8	A
Non-repetitive peak forward current	I_{FSM}	max.		45			35	A
Non-repetitive peak reverse energy	E_{RSM}	max.		10			10	mJ
Reverse recovery time	t_{rr}	<		250			300	ns

MECHANICAL DATA

Dimensions in mm

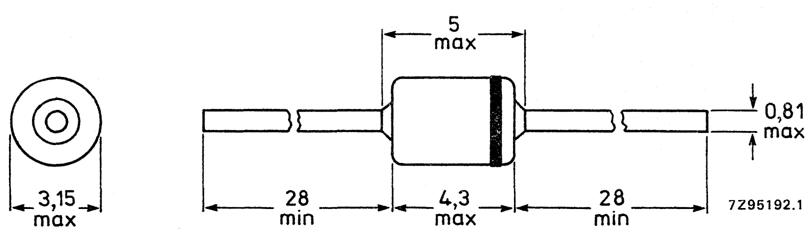


Fig. 1 SOD-84.

The marking band indicates the cathode.

* Implosion diode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYD34D	G	J	K	M	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	800	1000	V

			BYD34D; G; J	K; M	
Average forward current (averaged over any 20 ms period)					
T_{tp} = 55 °C; lead length 10 mm	$I_{F(AV)}$	max.	1.8	1.8	A
T_{amb} = 60 °C; see Fig. 2	$I_{F(AV)}$	max.	1.0	1.0	A
Repetitive peak forward current					
T_{tp} = 55 °C	I_{FRM}	max.	17	17	A
T_{amb} = 60 °C	I_{FRM}	max.	9	9	A
Non-repetitive peak forward current t = 10 ms, halfsine wave; $T_j = T_{j\,max}$ prior to surge; $V_R = V_{RRM\,max}$	I_{FSM}	max.	45	35	A
Non-repetitive peak reverse avalanche energy; I_R = 400 mA; $T_j = T_{j\,max}$, prior to surge; with inductive load switched off	E_{RSM}	max.	10	10	mJ
Storage temperature range	T_{stg}		−65 to + 175		°C
Junction temperature	T_j	max.	175		°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\,j\text{-}tp}$	=	50	K/W
2. Thermal resistance from junction to ambient; device mounted on an 1.5 mm thick epoxy-glass printed-circuit board; Cu-thickness ≥ 40 μm; Fig. 2 (see Thermal Model)	$R_{th\,j\text{-}a}$	=	105	K/W

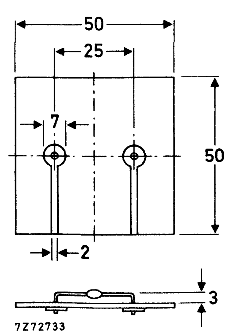


Fig. 2 Mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYD34D	G	J	K	M	
Forward voltage*								
I_F = 3 A	V_F	<	1.4	1.4	1.4	1.4	1.4	V
I_F = 3 A; $T_j = T_{j\,max}$	V_F	<	1.2	1.2	1.2	1.2	1.2	V
Reverse avalanche breakdown voltage								
I_R = 0.1 mA	$V_{(BR)R}$	>	300	500	700	900	1100	V

			BYD34D; G; J	K; M	
Reverse current					
$V_R = V_{RRM\,max}$**	I_R	<	1	1	μA
$V_R = V_{RRM\,max}$; T_j = 165 °C	I_R	<	150	150	μA
Reverse recovery when switched from I_F = 1 A to V_R > 30 V with $-dI_F/dt$ = 20 A/μs					
recovery charge	Q_s	<	250	400	nC
recovery time	t_{rr}	<	250	300	ns
Maximum slope of reverse recovery current when switched from I_F = 1 A to V_R > 30 V with $-dI_F/dt$ = 1 A/μs	$\lvert dI_R/dt \rvert$	<	6	5	A/μs

DEVELOPMENT DATA

* Measured under pulse conditions to avoid excessive dissipation.

** Illuminance < 500 lux (daylight); relative humidity < 65%.

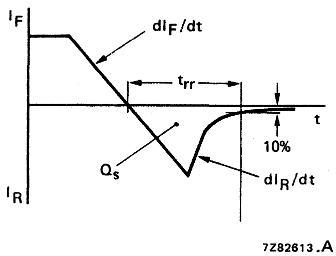


Fig. 3 Definitions of t_{rr}, Q_s, dI_F/dt and dI_R/dt.

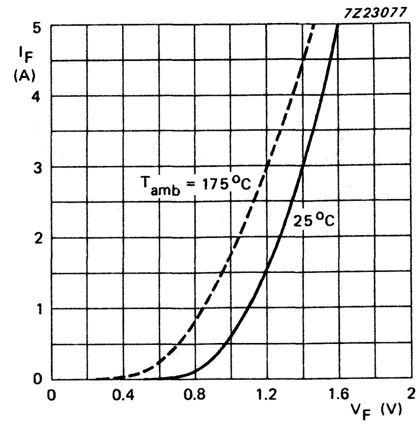


Fig. 4 Maximum forward voltage.

AVALANCHE FAST SOFT-RECOVERY RECTIFIER DIODES

Glass passivated rectifier diodes in hermetically sealed leadless SMID* envelopes. They are intended for television and industrial applications, such as switched-mode power supplies, scan rectifiers in TV receivers and also for use in inverter and converter applications. The devices feature non-snap-off (soft-recovery) switching characteristics and are capable of absorbing reverse transient energy (e.g. during flashover in a picture tube).

QUICK REFERENCE DATA

			BYD37D	G	J	K	M	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	800	1000	V
Average forward current	$I_{F(AV)}$	max.		1.5		1.5		A
Non-repetitive peak forward current	I_{FSM}	max.		20		20		A
Non-repetitive peak reverse energy	E_{RSM}	max.		10		7		mJ
Reverse recovery time	t_{rr}	<		250		300		ns

MECHANICAL DATA

Dimensions in mm

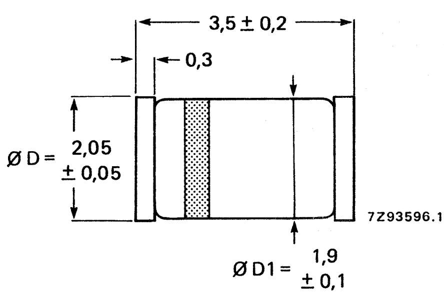


Fig. 1 SOD-87.

* Implosion Diode

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYD37D	G	J	K	M	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	800	1000	V
Average forward current square wave; $\delta = 0.5$								
$T_{tp} = 105\ ^oC$	$I_{F(AV)}$	max.		1.5		1.5		A
$T_{amb} = 65\ ^oC$; PCB mounting	$I_{F(AV)}$	max.		0.6		0.6		A
Repetitive peak forward current				12		12		A
Non-repetitive peak forward current t = 10 ms, half-sinewave; $T_j = T_j$max prior to surge; $V_R = V_{RRMmax}$	I_{FSM}	max.		20		20		A
Non-repetitive peak reverse avalanche energy; I_R = 400 mA; $T_j = T_{jmax}$, prior to surge; with inductive load switched off	E_{RSM}	max.		10		7		mJ
Storage temperature range	T_{stg}			−65 to + 175				^oC
Junction temperature	T_j	max.		175				^oC

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point	$R_{th\ j\text{-}tp}$	=	30	K/W
2. Thermal resistance from junction to ambient; device mounted on an 1.5 mm thick epoxy-glass printed circuit board; Cu-thickness ⩾ 40 µm; Fig. 2	$R_{th\ j\text{-}a}$	=	150	K/W

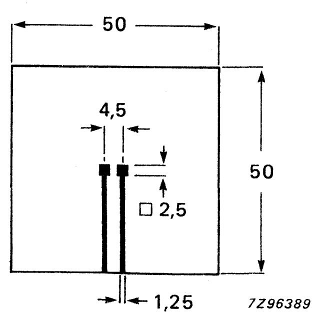


Fig. 2 Mounted on a PCB.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYD37D	G	J	K	M	
Forward voltage *								
I_F = 1 A	V_F	<	1.3	1.3	1.3	1.3	1.3	V
I_F = 1 A; $T_j = T_{jmax}$	V_F	<	1.1	1.1	1.1	1.1	1.1	V
Reverse avalanche breakdown voltage								
I_R = 0.1 mA	$V_{(BR)R}$	>	300	500	700	900	1100	V
Reverse current								
$V_R = V_{RRMmax}$	I_R	<		1		1		μA
$V_R = V_{RRMmax}$; T_j = 165 °C	I_R	<		100		100		μA
Reverse recovery when switched from I_F = 1 A to $V_R \leqslant$ 30 V with $-dI_F/dt$ = 20 A/μs								
recovery charge	Q_s	<		250		400		nC
recovery time	t_{rr}	<		250		300		ns
Maximum slope of reverse recovery current when switched from I_F = 1 A to $V_R \geqslant$ 30 V with $-dI_F/dt$ = 1 A/μs	$\lvert dI_R/dt \rvert$	<		6		5		A/μs

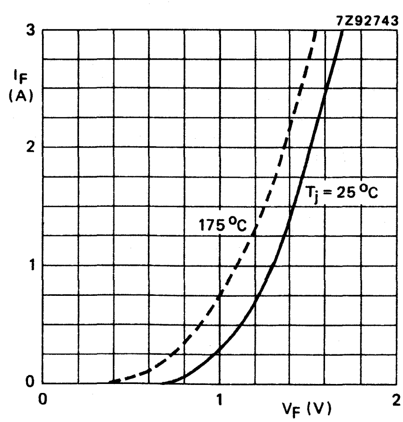


Fig. 3 Maximum forward voltage.

* Measured under pulse conditions to avoid excessive dissipation.

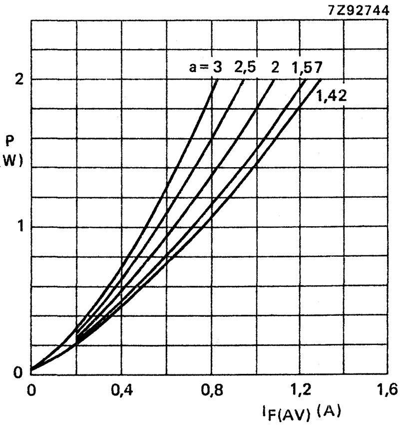


Fig. 4 Maximum values steady state power dissipation (forward plus leakage current) excluding switching losses as a function of the forward current.
The graph is for switched-mode application.
$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$.

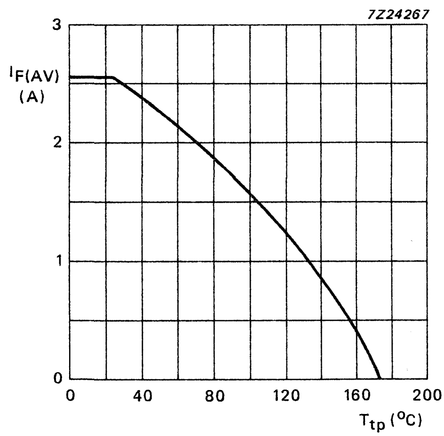


Fig. 5 Maximum average forward current as a function of temperature; the curve includes losses due to reverse leakage.
The graph is for switched-mode application.
$V_R = V_{RRMmax}$, $\delta = 0.5$; a = 1.42.
—— = tie-point temperature.

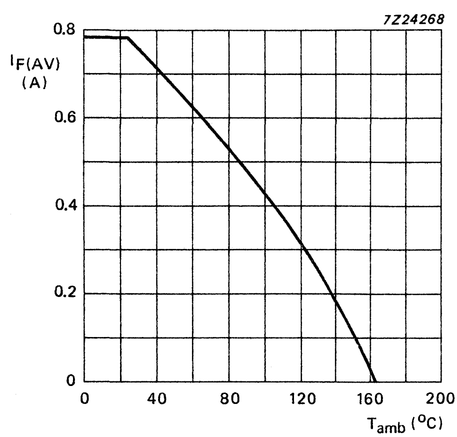


Fig. 6 Maximum average forward current as a function of temperature; the curve includes losses due to reverse leakage.
The graph is for switched-mode application.
$V_R = V_{RRMmax}$, $\delta = 0.5$; a = 1.42.
—— = ambient temperature and device mounted as shown in Fig. 2.

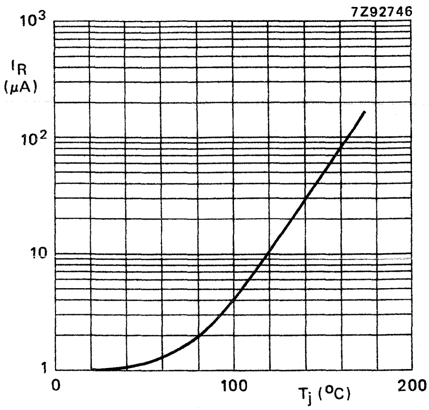


Fig. 7 Maximum values reverse current as a function of junction temperature.
$V_R = V_{RRMmax}$.

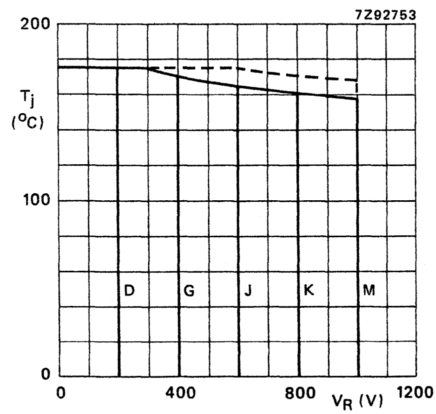


Fig. 8 Maximum permissible junction temperature as a function of reverse voltage.
—— = V_R; – – – = V_{RRM}; δ = 0.5.

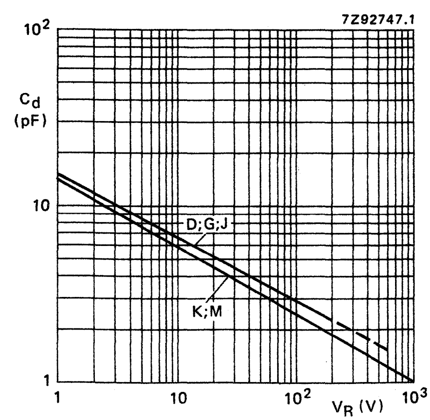


Fig. 9 Capacitance as a function of reverse voltage.
f = 1 MHz; T_j = 25 °C; typical values.

EPITAXIAL AVALANCHE DIODES

Glass passivated rectifier diodes in hermetically sealed axial-leaded ID* envelopes. They feature low forward voltage drop, very fast recovery, very low stored charge, non-snap-off switching characteristics and are capable of absorbing reverse transient energy (e.g. during flashover in a picture tube). These properties make the diodes very suitable for use in switched-mode power supplies and in general high frequency circuits, where low conduction and switching losses are essential.

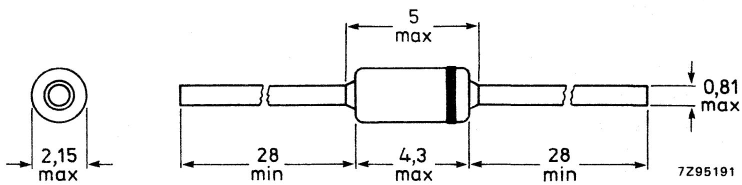
QUICK REFERENCE DATA

		BYD73	A	B	C	D	E	F	G	
Repetitive peak reverse voltage	V_{RRM}	max.	50	100	150	200	250	300	400	V
Continuous reverse voltage	V_R	max.	50	100	150	200	250	300	400	V
Average forward current	$I_{F(AV)}$	max.	1,75	1,75	1,75	1,75	1,7	1,7	1,7	A
Non-repetitive peak forward current	I_{FSM}	max.	25	25	25	25	25	25	25	A
Non-repetitive peak reverse energy	E_{RSM}	max.	20	20	20	20	20	20	20	mJ
Reverse recovery time	t_{rr}	<	25	25	25	25	50	50	50	ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-81



The marking band indicates the cathode.

* Implosion diode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYD73 A	B	C	D	E	F	G	
Repetitive peak reverse voltage	V_{RRM}	max.	50	100	150	200	250	300	400	V
Continuous reverse voltage	V_R	max.	50	100	150	200	250	300	400	V
Average forward current										
square wave; δ = 0,5										
T_{tp} = 55 °C; lead length = 10 mm	$I_{F(AV)}$	max.	1,75	1,75	1,75	1,75	1.7	1,7	1,7	A
T_{amb} = 60 °C; Fig. 2	$I_{F(AV)}$	max.	1	1	1	1	0,95	0,95	0,95	A
Repetitive peak forward current	I_{FRM}	max.	15	15	15	15	13	13	13	A

Non-repetitive peak forward current (t = 10 ms; half sine-wave) $T_j = T_{j\,max}$ prior to surge; with reapplied V_{RRM}	I_{FSM}	max.	25	A
Non-repetitive peak reverse avalanche energy; with inductive load switched off:				
I_R = 600 mA at T_j = 25 °C prior to surge	E_{RSM}	max.	20	mJ
I_R = 400 mA at $T_j = T_{j\,max}$ prior to surge	E_{RSM}	max.	10	mJ
Storage temperature	T_{stg}		−65 to +175	°C
Junction temperature	T_j	max.	175	°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\,j\text{-}tp}$	=	60	K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ⩾ 40 μm; Fig 2. (see "Thermal Model")	$R_{th\,j\text{-}a}$	=	120	K/W

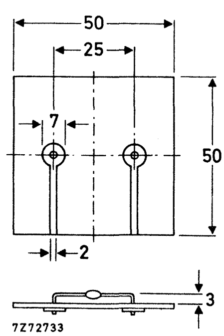


Fig. 2 Mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYD73 A	B	C	D	E	F	G	
Reverse avalanche breakdown voltage I_R = 0,1 mA	$V_{(BR)R}$	>	55	110	165	220	275	330	440	V
Forward voltage* I_F = 1 A; $T_j = T_{j\,max}$	V_F	<	0,74	0,74	0,74	0,74	0.83	0,83	0,83	V
I_F = 1 A	V_F	<	0,95	0,95	0,95	0,95	1,05	1,05	1,05	V
Reverse current $V_R = V_{RRMmax}$; T_j = 25 °C	I_R	<	1	1	1	1	1	1	1	μA
$V_R = V_{RRMmax}$; T_j = 165 °C	I_R	<	100	100	100	100	100	100	100	μA
Reverse recovery time when switched from I_F = 0,5 A to I_R = 1 A; measured at I_R = 0,25 A. For definition see Figs 3 and 4	t_{rr}	<	25	25	25	25	50	50	50	ns

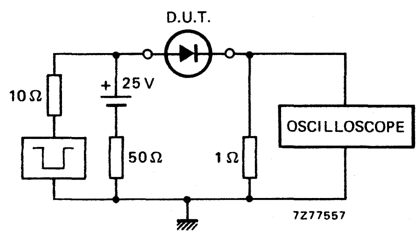


Fig. 3 Test circuit.
Input impedance oscilloscope 1 MΩ; 22 pF. Rise time ⩽ 7 ns.
Source impedance 50 Ω. Rise time ⩽ 15 ns.

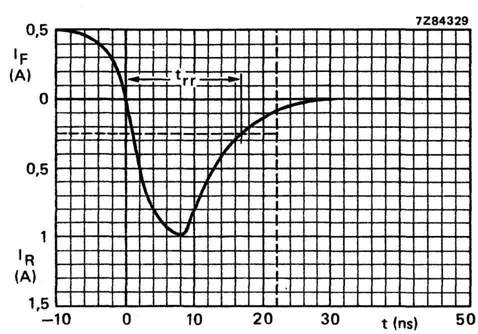


Fig. 4 Reverse recovery time characteristic.

* Measured under pulse conditions to avoid excessive dissipation.

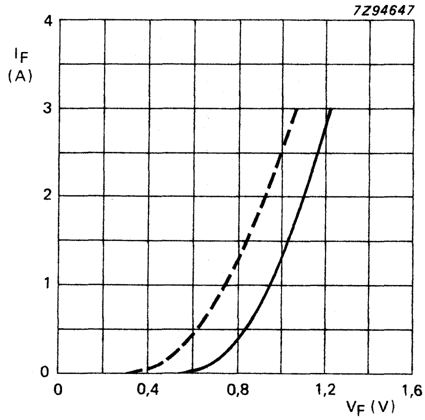


Fig. 5 **BYD73A; B; C; D.**
Maximum forward voltage.
—— T_j = 25 °C; – – – T_j = 175 °C.

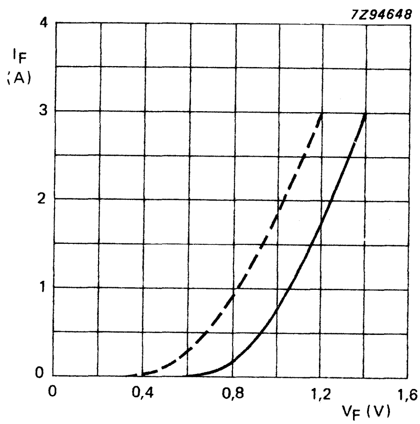


Fig. 6 **BYD73E; F; G.**
Maximum forward voltage.
—— T_j = 25 °C; – – – T_j = 175 °C.

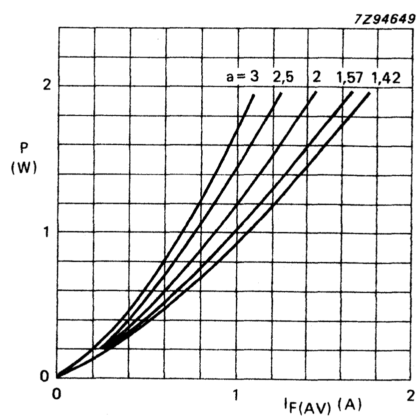


Fig. 7 **BYD73A; B; C; D.**
Maximum values steady state power dissipation as a function of the average forward current.

$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$.
Pulsed reverse voltage, δ = 0,5.

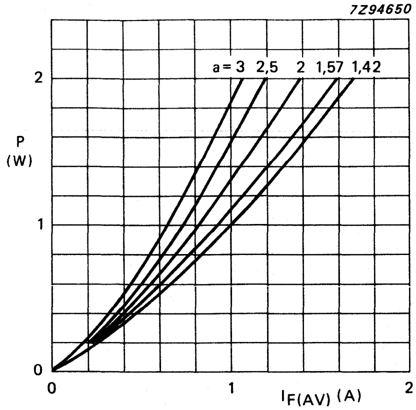


Fig. 8 **BYD73E; F; G.**
Maximum values steady state power dissipation as a function of the average forward current.

$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$.
Pulsed reverse voltage, $\delta = 0{,}5$.

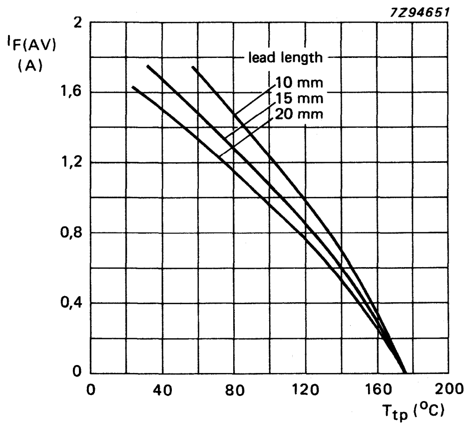


Fig. 9 **BYD73A; B; C; D.**
Maximum average forward current versus tie-point temperature; the curves include losses due to reverse leakage.

Pulsed reverse voltage, $\delta = 0{,}5$;
$V_R = V_{RRMmax}$; square-wave current, a = 1,42.

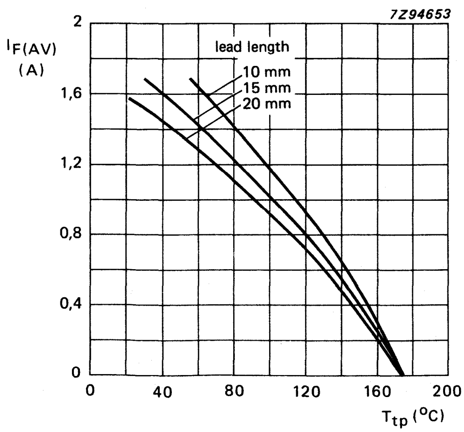


Fig. 10 **BYD73E; F; G.**
Maximum average forward current versus tie-point temperature; the curves include losses due to reverse leakage.

Pulsed reverse voltage, $\delta = 0{,}5$;
$V_R = V_{RRMmax}$; square-wave current, a = 1,42.

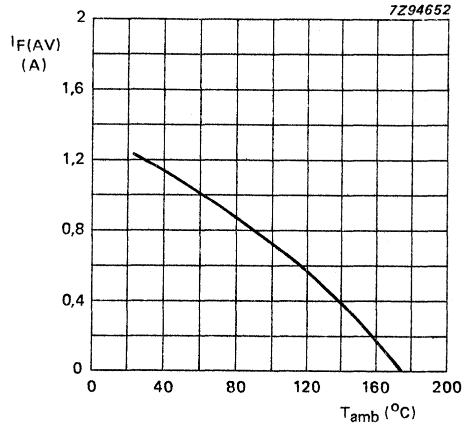


Fig. 11 **BYD73A; B; C; D.**
Maximum average forward current versus ambient temperature; the curves include losses due to reverse leakage.

Pulsed reverse voltage, δ = 0,5;
$V_R = V_{RRMmax}$; square-wave current, a = 1,42.

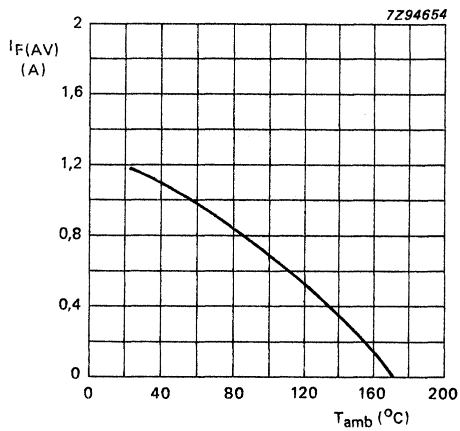


Fig. 12 **BYD73E; F; G.**
Maximum average forward current versus ambient temperature; the curves include losses due to reverse leakage.

Pulsed reverse voltage, δ = 0,5;
$V_R = V_{RRMmax}$; square-wave current, a = 1,42.

EPITAXIAL AVALANCHE DIODES

Glass passivated rectifier diodes in hermetically sealed axial-leaded ID* envelopes. They feature low forward voltage drop, very fast recovery, very low stored charge, non-snap-off switching characteristics and are capable of absorbing reverse transient energy (e.g. during flashover in a picture tube). These properties make the diodes very suitable for use in switched-mode power supplies and in general high-frequency circuits, where low conduction and switching losses are essential.

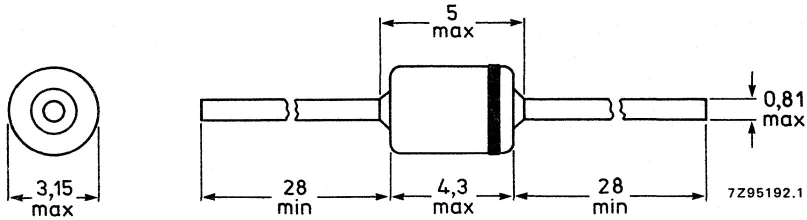
QUICK REFERENCE DATA

			BDY74A	B	C	D	E	F	G	
Repetitive peak reverse voltage	V_{RRM}	max.	50	100	150	200	250	300	400	V
Continuous reverse voltage	V_R	max.	50	100	150	200	250	300	400	V
Average forward current	$I_{F(AV)}$	max.	2,4	2,4	2,4	2,4	2,15	2,15	2,15	A
Non-repetitive peak forward current	I_{FSM}	max.	50	50	50	50	50	50	50	A
Non-repetitive peak reverse energy	E_{RSM}	max.	40	40	40	40	40	40	40	mJ
Reverse recovery time	t_{rr}	<	25	25	25	25	50	50	50	ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-84.



The marking band indicates the cathode.

* Implosion diode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BDY74A	B	C	D	E	F	G	
Repetitive peak reverse voltage	V_{RRM}	max.	50	100	150	200	250	300	400	V
Continuous reverse voltage	V_R	max.	50	100	150	200	250	300	400	V
Average forward current square wave; δ = 0,5										
T_{tp} = 55 °C; lead length = 10 mm	$I_{F(AV)}$	max.	2,4	2,4	2,4	2,4	2,15	2,15	2,15	A
T_{amb} = 60 °C; Fig. 2	$I_{F(AV)}$	max.	1,35	1,35	1,35	1,35	1,2	1,2	1,2	A
Repetitive peak forward current										
T_{tp} = 55 °C; see Figs 11 and 13	I_{FRM}	max.	21	21	21	21	21	21	21	A
T_{amb} = 60 °C; see Figs 12 and 14	I_{FRM}	max.	13	13	13	13	12	12	12	A

Non-repetitive peak forward current (t = 10 ms; half sine-wave) $T_j = T_{j\,max}$ prior to surge; with reapplied V_{RRM}	I_{FSM}	max.	50	A
Non-repetitive peak reverse avalanche energy; with inductive load switched-off:				
I_R = 820 mA at T_j = 25 °C prior to surge	E_{RSM}	max.	40	mJ
I_R = 580 mA at $T_j = T_{j\,max}$ prior to surge	E_{RSM}	max.	20	mJ
Storage temperature	T_{stg}		−65 to + 175	°C
Junction temperature	T_j	max.	175	°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\,j\text{-}tp}$	=	50	K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ⩾ 40 µm (see "Thermal model")	$R_{th\,j\text{-}a}$	=	105	K/W

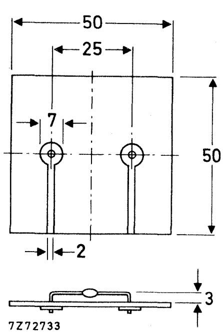
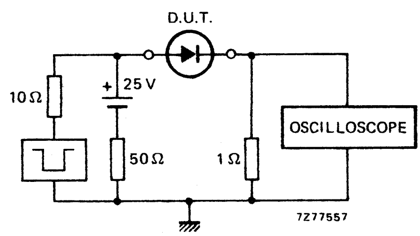


Fig. 2 Mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BDY74A	B	C	D	E	F	G	
Reverse avalanche breakdown voltage										
I_R = 0,1 mA	$V_{(BR)R}$	>	55	110	165	220	275	330	440	V
Forward voltage*										
I_F = 2 A; $T_j = T_{j\ max}$	V_F	<	0,72	0,72	0,72	0,72	0,82	0,82	0,82	V
I_F = 2 A	V_F	<	0,94	0,94	0,94	0,94	1,05	1,05	1,05	V
Reverse current										
$V_R = V_{RRMmax}$; T_j = 25 °C	I_R	<	1	1	1	1	1	1	1	µA
$V_R = V_{RRMmax}$; T_j = 165 °C	I_R	<	150	150	150	150	150	150	150	µA
Reverse recovery time when switched from I_F = 0,5 A to I_R = 1 A; measured at I_R = 0,25 A. For definition see Figs 3 and 4	t_{rr}	<	25	25	25	25	50	50	50	ns



Input impedance oscilloscope 1 MΩ; 22 pF. Rise time ≤ 7 ns.
Source impedance 50 Ω. Rise time ≤ 15 ns.

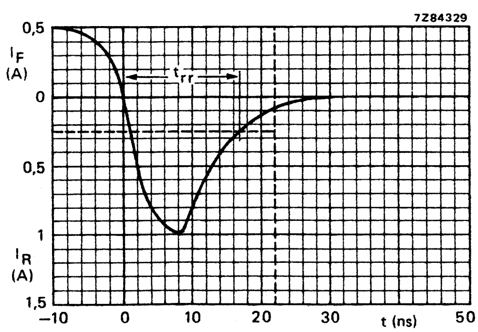


Fig. 4 Reverse recovery time characteristic.

* Measured under pulse conditions to avoid excessive dissipation.

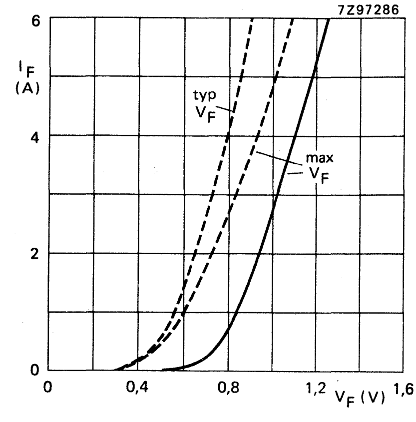


Fig. 5 **BYD74A; B; C; D.** Forward voltage;
—— T_j = 25 °C; – – – $T_j = T_{j\,max}$.

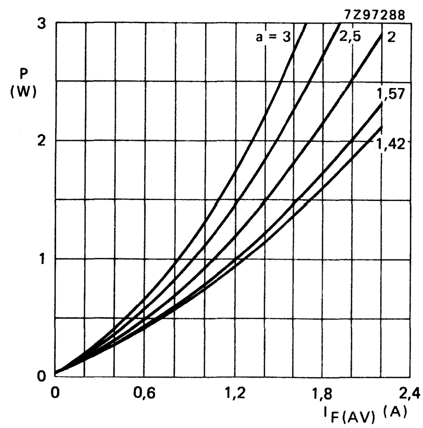


Fig. 6 **BYD74A; B; C; D.** Maximum values steady state power dissipation (forward plus leakage current) excluding switching losses as a function of the average forward current.

The graph is for switched-mode application.

$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$, $\delta = 0,5$.

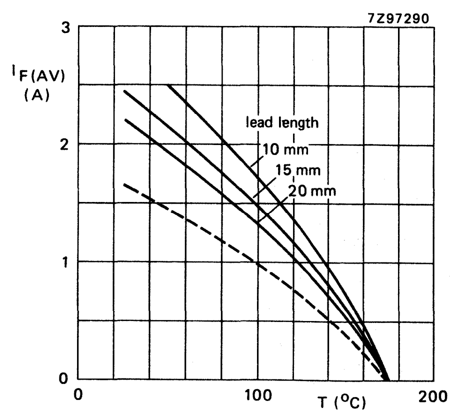


Fig. 7 **BYD74A; B; C; D.** Maximum average forward current as a function of temperature; the curves include losses due to reverse leakage.

The graph is for switched-mode application.

$V_R = V_{RRMmax}$, $\delta = 0,5$; a = 1,42.

– – – = ambient temperature and device mounted as shown in Fig. 2

—— = tie-point temperature

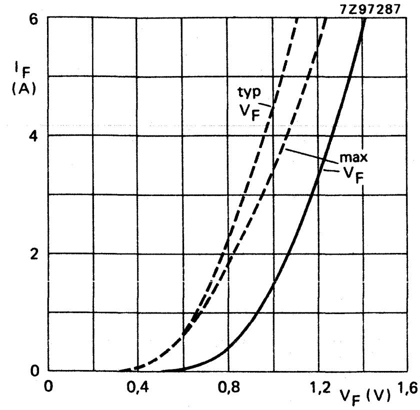


Fig. 8 **BYD74E; F; G.** Forward voltage;
—— T_j = 25 °C; – – – $T_j = T_{j\,max}$.

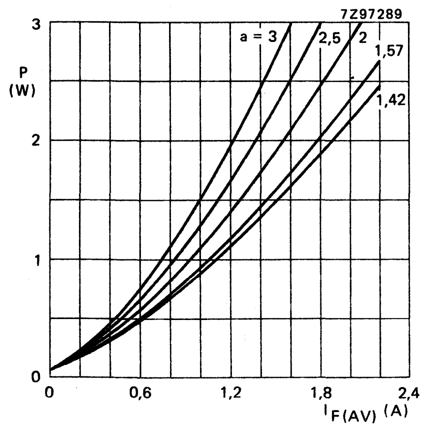


Fig. 9 **BYD74E; F; G.** Maximum values steady state power dissipation (forward plus leakage current) excluding switching losses as a function of the average forward current.

The graph is for switched-mode application.

$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$, δ = 0,5.

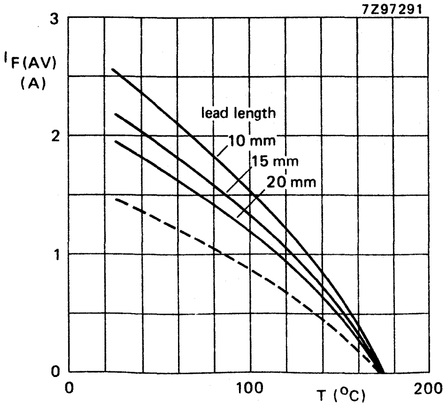


Fig. 10 **BYD74E; F; G.** Maximum average forward current as a function of temperature; the curves include losses due to reverse leakage.

The graph is for switched-mode application.

$V_R = V_{RRMmax}$, δ = 0,5; a = 1,42.

– – – = ambient temperature and device mounted as shown in Fig. 2

—— = tie-point temperature

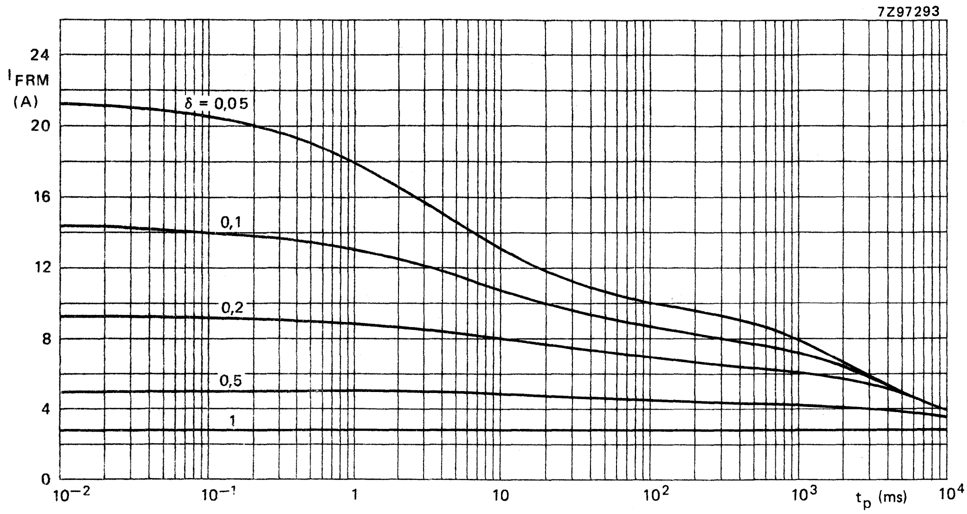


Fig. 11 **BYD74A; B; C; D.** Maximum repetitive peak forward current as a function of the pulse time (square pulse) and duty-factor δ at $T_{tie\text{-}point}$ = 55 °C; $R_{th\ j\text{-}tp}$ = 50 K/W; V_{RRM} during 1 – δ; the curves include derating for $T_{j\ max}$ at V_{RRM} = 200 V.

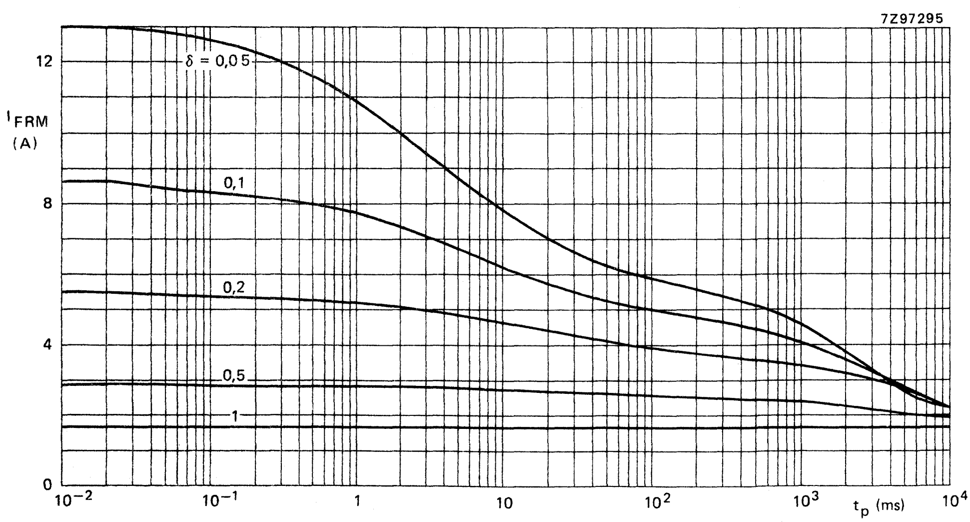


Fig. 12 **BYD74A; B; C; D.** Maximum repetitive peak forward current as a function of the pulse time (square pulse) and duty factor δ at T_{amb} = 60 °C; $R_{th\ j\text{-}a}$ = 105 K/W; V_{RRM} during 1 – δ; the curves include derating for $T_j\ _{max}$ at V_{RRM} = 200 V.

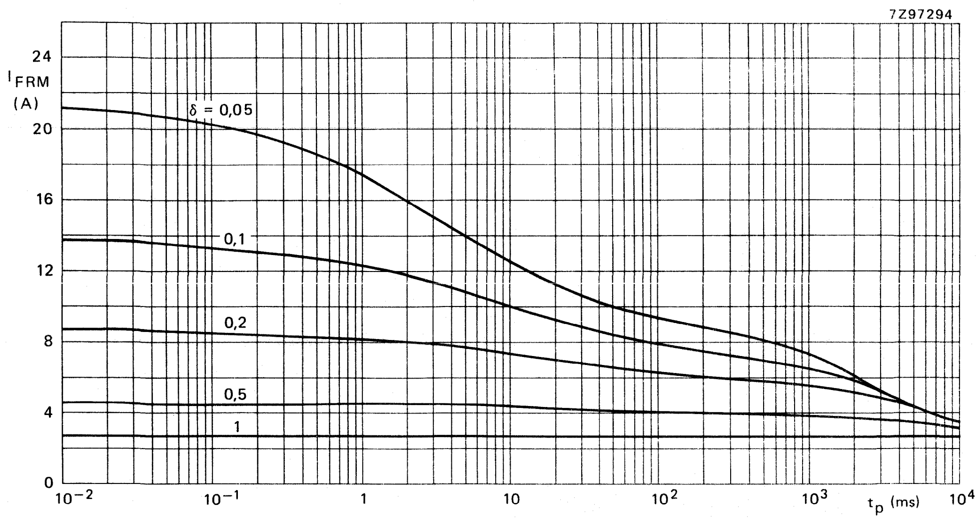


Fig. 13 **BYD74E; F; G.** Maximum repetitive peak forward current as a function of the pulse time (square pulse) and duty-factor δ at $T_{tie\text{-}point}$ = 55 °C; $R_{th\ j\text{-}tp}$ = 50 K/W; V_{RRM} during $1 - \delta$; the curves include derating for $T_{j\ max}$ at V_{RRM} = 400 V.

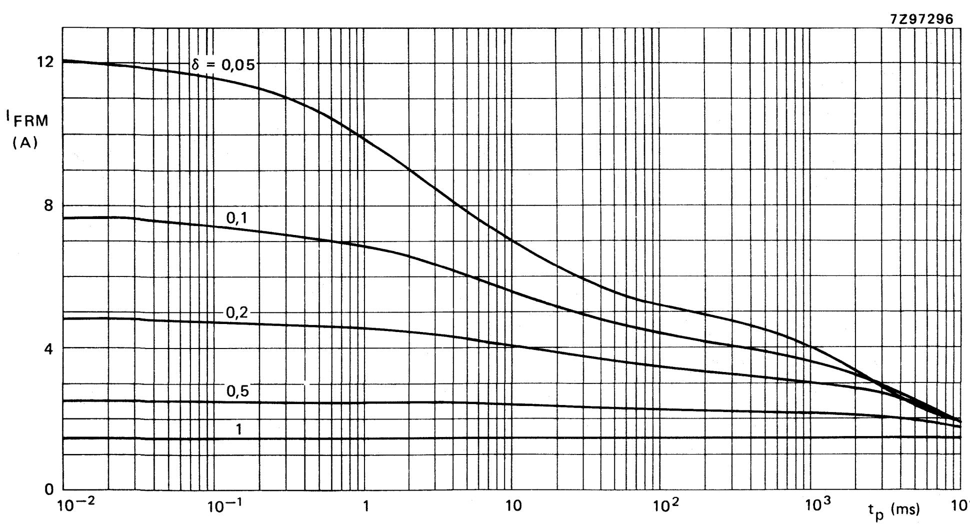


Fig. 14 **BYD74E; F; G.** Maximum repetitive peak forward current as a function of the pulse time (square pulse) and duty-factor δ at T_{amb} = 60 °C; $R_{th\ j\text{-}a}$ = 105 K/W; V_{RRM} during $1 - \delta$; the curves include derating for $T_{j\ max}$ at V_{RRM} = 400 V.

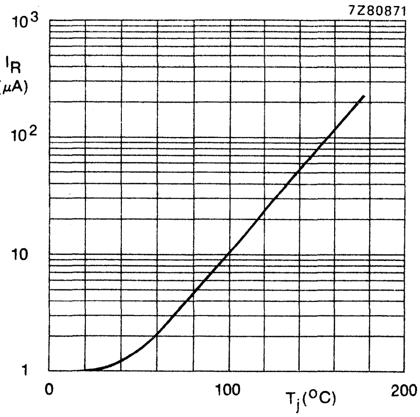


Fig. 15 Maximum values reverse current as a function of junction temperature; $V_R = V_{RRMmax}$.

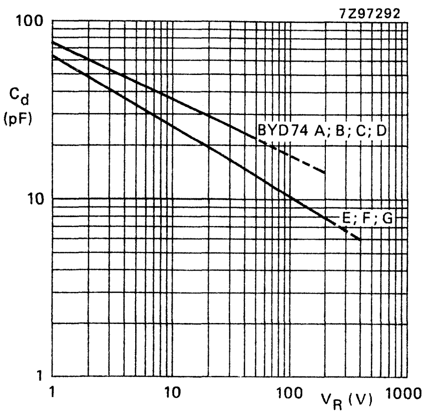


Fig. 16 Capacitance as a function of reverse voltage; f = 1 MHz; T_j = 25 °C; typical values.

OPERATING NOTES

The various components of junction temperature rise above ambient, for mounting with symmetrical lead length, are illustrated below.

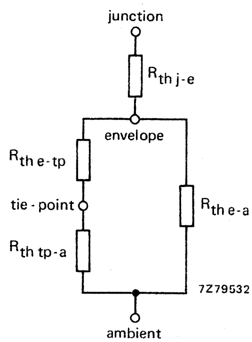


Fig. 12 Thermal model ($R_{th\ j\text{-}e}$ = 22 K/W).

By using this thermal model and the dissipation graph (Fig. 6), any temperature can be calculated.

The thermal resistances between envelope and tie-point, and between envelope and ambient depend on lead length.

thermal resistance	lead length					unit
	5	10	15	20	25	mm
$R_{th\ e\text{-}tp}$	15	30	45	60	75	K/W
$R_{th\ e\text{-}a}$	440	350	300	265	240	K/W

The thermal resistance between tie-point and ambient depends on the mounting method. For components on a 1,5 mm thick epoxy-glass printed-circuit board with a copper-thickness > 40 μm, the following values apply:

1. Mounted as given in Fig. 2 the thermal resistance $R_{th\ tp\text{-}a}$ = 70 K/W.
2. Mounted with copper laminate of 1 cm^2 per lead $R_{th\ tp\text{-}a}$ = 55 K/W.
3. Mounted with copper laminate of 2,25 cm^2 per lead $R_{th\ tp\text{-}a}$ = 45 K/W.

EPITAXIAL AVALANCHE DIODES

Rectifier diodes in hermetically sealed leadless SMID*-envelopes. They feature low forward voltage drop, very fast recovery, very low stored charge, non-snap-off switching characteristics and are capable of absorbing reverse transient energy (e.g. during flashover in a picture tube). These properties make the diodes very suitable for use in switched-mode power supplies and in general high-frequency circuits, where low conduction and switching losses are essential.

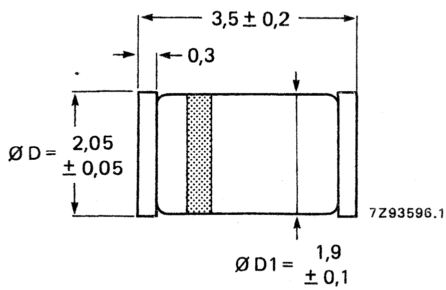
QUICK REFERENCE DATA

			BYD77A	B	C	D	E	F	G	
Repetitive peak reverse voltage	V_{RRM}	max.	50	100	150	200	250	300	400	V
Continuous reverse voltage	V_R	max.	50	100	150	200	250	300	400	V
Average forward current	$I_{F(AV)}$	max.	2	2	2	2	1,85	1,85	1,85	A
Non-repetitive peak forward current	I_{FSM}	max.	25	25	25	25	25	25	25	A
Non-repetitive peak reverse energy	E_{RSM}	max.	20	20	20	20	20	20	20	mJ
Reverse recovery time	t_{rr}	<	25	25	25	25	50	50	50	ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-87.



* Surface-mounted implosion diode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYD77A	B	C	D	E	F	G	
Repetitive peak reverse voltage	V_{RRM}	max.	50	100	150	200	250	300	400	V
Continuous reverse voltage	V_R	max.	50	100	150	200	250	300	400	V
Average forward current square wave; δ = 0,5										
T_{tp} = 105 °C	$I_{F(AV)}$	max.	2	2	2	2	1,85	1,85	1,85	A
T_{amb} = 60 °C; p.c.b. mounting	$I_{F(AV)}$	max.	0,85	0,85	0,85	0,85	0,8	0,8	0,8	A
Repetitive peak forward current	I_{FRM}	max.	15	15	15	15	13	13	13	A
Non-repetitive peak forward current (t = 10 ms; half sine-wave) $T_j = T_{j\,max}$ prior to surge; with reapplied V_{RRM}	I_{FSM}	max.				25				A
Non-repetitive peak reverse avalanche energy; with inductive load switched off:										
I_R = 600 mA at T_j = 25 °C prior to surge	E_{RSM}	max.				20				mJ
I_R = 400 mA at $T_j = T_{j\,max}$ prior to surge	E_{RSM}	max.				10				mJ
Storage temperature	T_{stg}					−65 to + 175				°C
Junction temperature	T_j	max.				175				°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point	$R_{th\,j\text{-}tp}$	=	30	K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ⩾ 40 μm; Fig 2.	$R_{th\,j\text{-}a}$	=	150	K/W

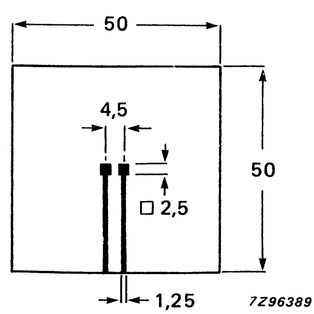


Fig 2. Mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYD77A	B	C	D	E	F	G	
Reverse avalanche breakdown voltage										
I_R = 0,1 mA	$V_{(BR)R}$	>	55	110	165	220	275	330	440	V
Forward voltage*										
I_F = 1 A; $T_j = T_{j\,max}$	V_F	<	0,74	0,74	0,74	0,74	0,83	0,83	0,83	V
I_F = 1 A	V_F	<	0,95	0,95	0,95	0,95	1,05	1,05	1,05	V
Reverse current										
$V_R = V_{RRMmax}$	I_R	<	1	1	1	1	1	1	1	μA
$V_R = V_{RRMmax}$; T_j = 165 °C	I_R	<	100	100	100	100	100	100	100	μA
Reverse recovery time when switched from I_F = 0,5 A to I_R = 1 A; measured at I_R = 0,25 A	t_{rr}	<	25	25	25	25	50	50	50	ns

DEVELOPMENT DATA

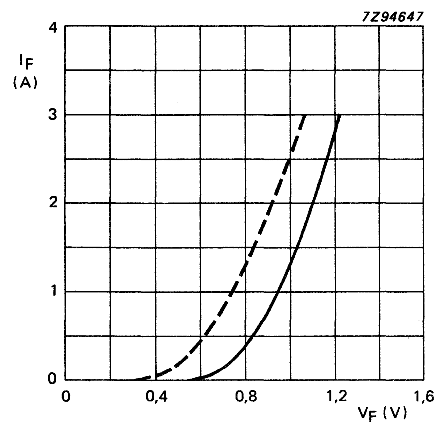


Fig. 3 **BYD77A; B; C; D.**
Maximum forward voltage.
—— T_j = 25 °C; – – – T_j = 175 °C.

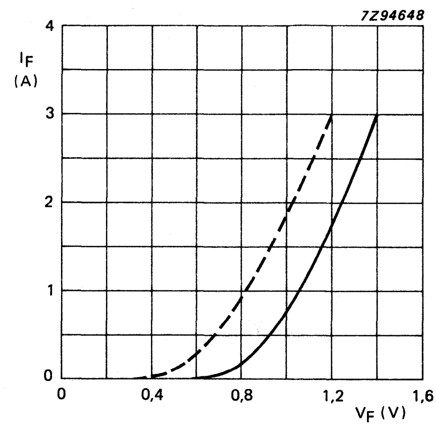


Fig. 4 **BYD77E; F; G.**
Maximum forward voltage.
—— T_j = 25 °C; – – – T_j = 175 °C.

* Measured under pulse conditions to avoid excessive dissipation.

VERY FAST SOFT-RECOVERY AVALANCHE RECTIFIER DIODES

Glass passivated rectifier diodes in hermetically sealed axial-leaded glass envelopes. They are intended for use in switched-mode power supplies and high-frequency inverter circuits. In general, they are used where high output voltages and low switching losses are essential. The devices feature non-snap-off (soft-recovery) switching characteristics and are capable of absorbing reverse transient energy.

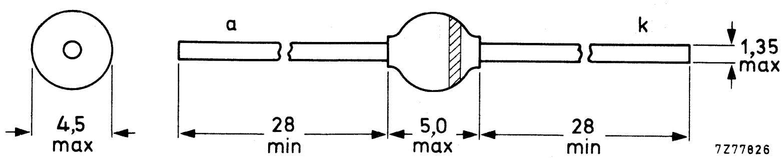
QUICK REFERENCE DATA

			BYM26A	B	C	D	E	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	800	1000	V
Average forward current	$I_{F(AV)}$	max.	2,3	2,3	2,3	2,3	2,3	A
Non-repetitive peak forward current	I_{FSM}	max.	45	45	45	45	45	A
Non-repetitive peak reverse energy	E_{RSM}	max.	10	10	10	10	10	mJ
Reverse recovery time	t_{rr}	<	30	30	30	75	75	ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-64.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYM26A	B	C	D	E	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	800	1000	V
Average forward current (averaged over any 20 ms period); T_{tp} = 55 °C; lead length 10 mm	$I_{F(AV)}$	max.			2,3			A
T_{amb} = 65 °C; see Fig. 2	$I_{F(AV)}$	max.			1			A
Repetitive peak forward current T_{tp} = 55 °C; see Fig. 10	I_{FRM}	max.			19			A
T_{amb} = 65 °C; see Fig. 11	I_{FRM}	max.			8			A
Non-repetitive peak forward current t = 10 ms, half-sine wave; $T_j = T_{j\,max}$ prior to surge; $V_R = V_{RRM\,max}$	I_{FSM}	max.			45			A
Non-repetitive peak reverse avalanche energy; I_R = 400 mA; $T_j = T_{j\,max}$ prior to surge; with inductive load switched off	E_{RSM}	max.			10			mJ
Storage temperature	T_{stg}				−65 to + 175			°C
Junction temperature	T_j	max.			175			°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\,j\text{-}tp}$	=	25	K/W
2. Thermal resistance from junction to ambient; device mounted on an 1,5 mm thick epoxy-glass printed circuit board; Cu-thickness > 40 μm; Fig. 2 (see "Thermal model")	$R_{th\,j\text{-}a}$	=	75	K/W

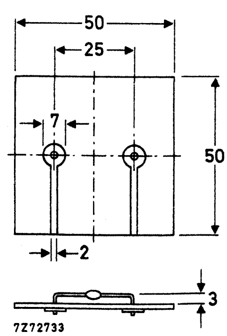


Fig. 2 Device mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYM26A	B	C	D	E	
Forward voltage*								
I_F = 2 A; T_j = 175 °C	V_F	<	1,34	1,34	1,34	1,34	1,34	V
I_F = 2 A	V_F	<	2,65	2,65	2,65	2,65	2,65	V
Reverse avalanche breakdown voltage								
I_R = 0,1 mA	$V_{(BR)R}$	>	300	500	700	900	1100	V
Reverse current								
$V_R = V_{RRM\,max}$	I_R	<	10	10	10	10	10	μA
$V_R = V_{RRM\,max}$; T_j = 165 °C	I_R	<	150	150	150	150	150	μA
Reverse recovery time when switched from I_F = 0,5 A to I_R = 1 A; measured at I_R = 0,25 A (for definition see Figs 3 and 4)	t_{rr}	<	30	30	30	75	75	ns

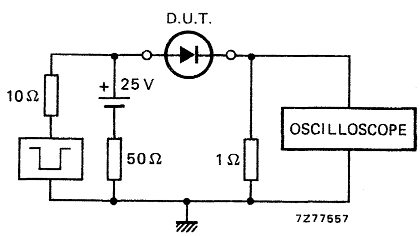


Fig. 3 Test circuit.

Input impedance oscilloscope: 1 MΩ, 22 pF; rise time < 7 ns

Source impedance: 50 Ω; rise time < 15 ns

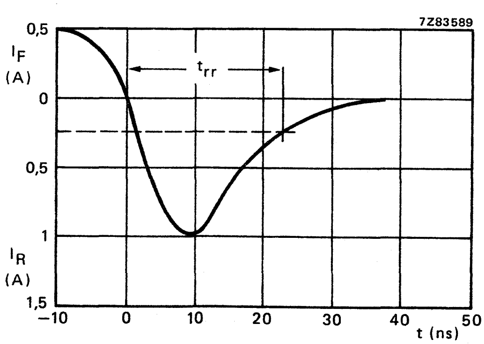


Fig. 4 Reverse recovery time characteristic.

* Measured under pulse conditions to avoid excessive dissipation.

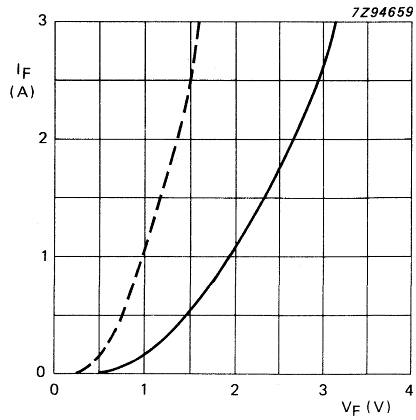


Fig. 5 Maximum forward voltage at
—— T_j = 25 °C; – – – T_j = 175 °C.

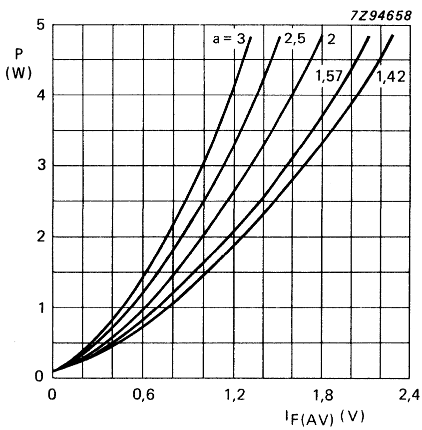


Fig. 6 Maximum steady state power dissipation (forward plus leakage current) excluding switching losses versus average forward current.

The graph is for switched-mode application. $a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRM\,max}$, $\delta = 0,5$.

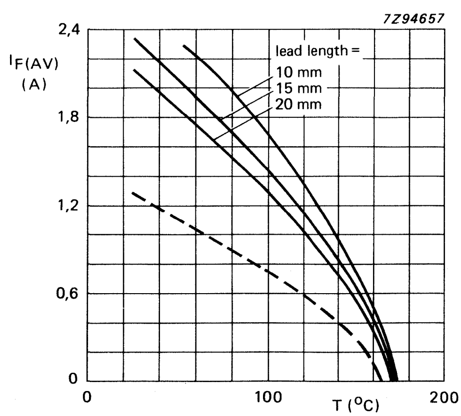


Fig. 7 Maximum average forward current vs. temperature; the curves include losses due to reverse leakage.

The graph is for switched-mode application. $V_R = V_{RRM\,max}$, $\delta = 0,5$; a = 1,42.

—— tie-point temperature

– – – ambient temperature; mounting method see Fig. 2.

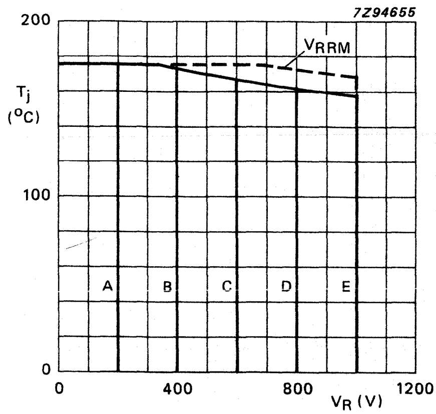


Fig. 8 Maximum permissible junction temperature versus applied reverse voltage.

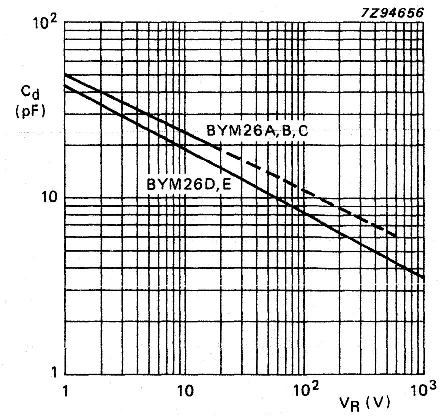


Fig. 9 Capacitance versus reverse voltage; f = 1 MHz; T_j = 25 °C.

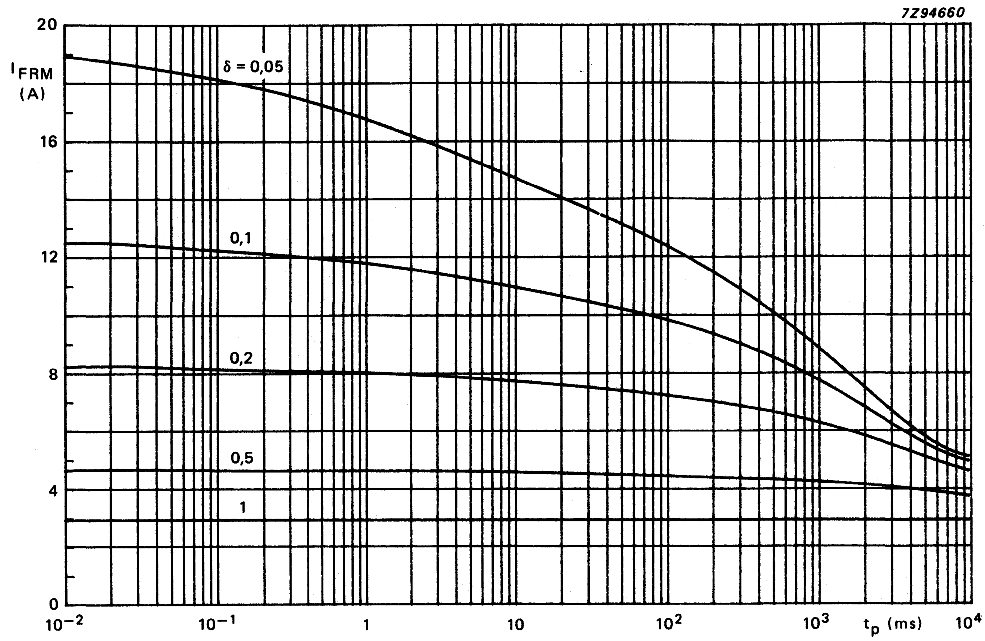


Fig. 10 Maximum repetitive peak forward current versus pulse time (square pulse) and duty-factor δ at $T_{tie\text{-}point}$ = 55 °C; $R_{th\,j\text{-}tp}$ = 25 K/W; V_{RRM} during $1-\delta$; the curves include derating for $T_{j\,max}$ at V_{RRM} = 1000 V.

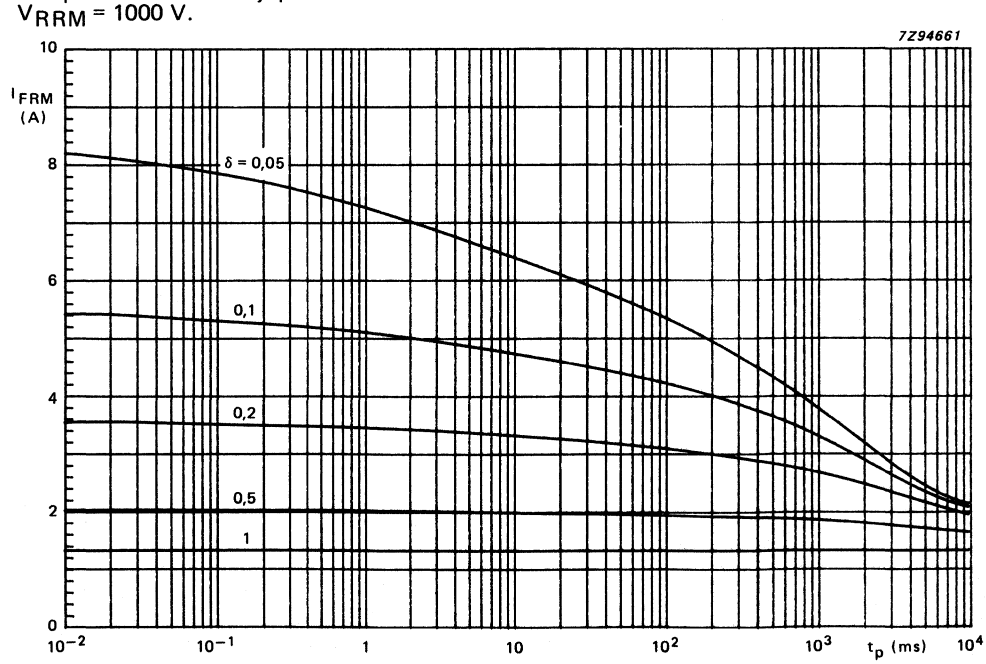


Fig. 11 Maximum repetitive peak forward current versus pulse time (square pulse) and duty-factor δ at $T_{tie\text{-}point}$ = 65 °C; $R_{th\,j\text{-}tp}$ = 75 K/W; V_{RRM} during $1-\delta$; the curves include derating for $T_{j\,max}$ at V_{RRM} = 1000 V.

VERY FAST SOFT-RECOVERY AVALANCHE RECTIFIER DIODES

Glass passivated rectifier diodes in hermetically sealed axial-leaded glass envelopes. They are intended for use in switched-mode power supplies and high-frequency inverter circuits. In general, they are used where high output voltages and low switching losses are essential. The devices feature non-snap-off (soft-recovery) switching characteristics and are capable of absorbing reverse transient energy.

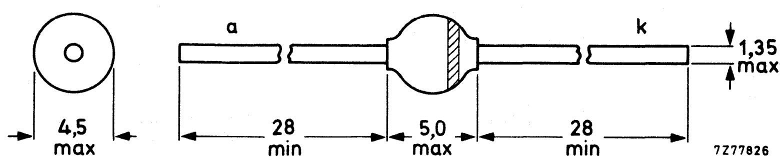
QUICK REFERENCE DATA

			BYM36A	B	C	D	E	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	800	1000	V
Average forward current	$I_{F(AV)}$	max.	3	3	3	2,9	2,9	A
Non-repetitive peak forward current	I_{FSM}	max.	65	65	65	65	65	A
Non-repetitive peak reverse energy	E_{RSM}	max.	10	10	10	10	10	mJ
Reverse recovery time	t_{rr}	<	100	100	100	150	150	ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-64.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYM36A	B	C	D	E	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	800	1000	V
Average forward current (averaged over any 20 ms period); T_{tp} = 55 °C; lead length 10 mm	$I_{F(AV)}$	max.	3	3	3	2,9	2,9	A
T_{amb} = 65 °C; see Fig. 2	$I_{F(AV)}$	max.	1,25	1,25	1,25	1,2	1,2	A
Repetitive peak forward current T_{tp} = 55 °C; see Figs 10, 11	I_{FRM}	max.	37	37	37	33	33	A
T_{amb} = 65 °C; see Figs 12, 13	I_{FRM}	max.	13	13	13	11	11	A
Non-repetitive peak forward current t = 10 ms, half-sine wave; $T_j = T_{j\,max}$ prior to surge; $V_R = V_{RRM\,max}$	I_{FSM}	max.	65					A
Non-repetitive peak reverse avalanche energy; I_R = 400 mA; $T_j = T_{j\,max}$ prior to surge; with inductive load switched off	E_{RSM}	max.	10					mJ
Storage temperature	T_{stg}		−65 to + 175					°C
Junction temperature	T_j	max.	175					°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\,j\text{-}tp}$	=	25	K/W
2. Thermal resistance from junction to ambient; device mounted on an 1,5 mm thick epoxy-glass printed circuit board; Cu-thickness > 40 μm; Fig. 2 (see "Thermal model")	$R_{th\,j\text{-}a}$	=	75	K/W

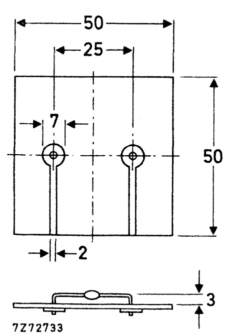


Fig. 2 Device mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYM36A	B	C	D	E
Forward voltage*							
I_F = 3 A; T_j = 175 °C	V_F	<	1,22	1,22	1,22	1,28	1,28 V
I_F = 3 A	V_F	<	1,6	1,6	1,6	1,78	1,78 V
Reverse avalanche breakdown voltage I_R = 0,1 mA	$V_{(BR)R}$	>	300	500	700	900	1100 V
Reverse current							
$V_R = V_{RRM\,max}$	I_R	<	5	5	5	5	5 μA
$V_R = V_{RRM\,max}$; T_j = 165 °C	I_R	<	150	150	150	150	150 μA
Reverse recovery time when switched from I_F = 0,5 A to I_R = 1 A; measured at I_R = 0,25 A (for definition see Figs 3 and 4)	t_{rr}	<	100	100	100	150	150 ns

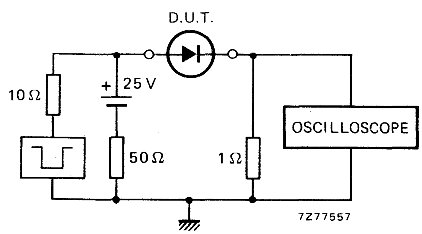


Fig. 3 Test circuit.

Input impedance oscilloscope: 1 MΩ, 22 pF; rise time < 7 ns

Source impedance: 50 Ω; rise time < 15 ns

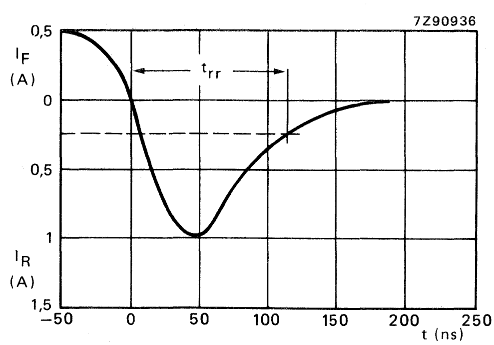


Fig. 4 Reverse recovery time characteristic.

* Measured under pulse conditions to avoid excessive dissipation.

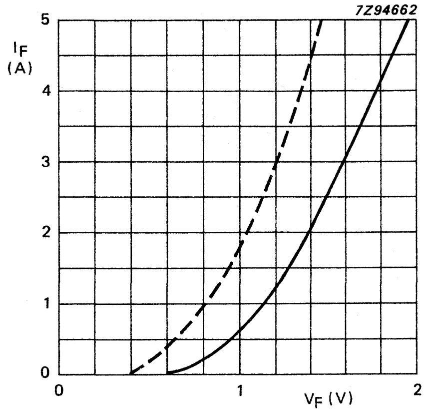


Fig. 5a **BYM36A; B; C.**
Maximum forward voltage at
——— T_j = 25 °C;
– – – T_j = 175 °C.

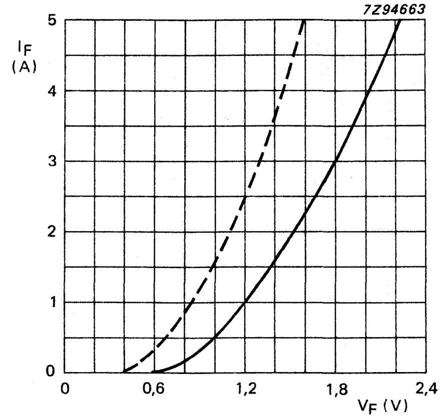


Fig. 5b **BYM36D; E.**
Maximum forward voltage at
——— T_j = 25 °C;
– – – T_j = 175 °C.

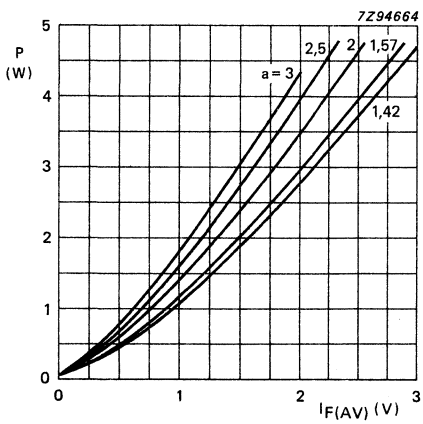


Fig. 6a **BYM36A; B; C.**

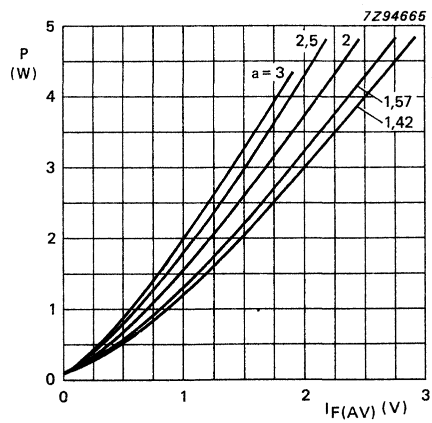


Fig. 6b **BYM36B; C.**

Conditions for Figs 6a and 6b:

Maximum steady state power dissipation (forward plus leakage current) excluding switching losses versus average forward current.

The graph is for switched-mode application. a = $I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRM\,max}$, δ = 0,5.

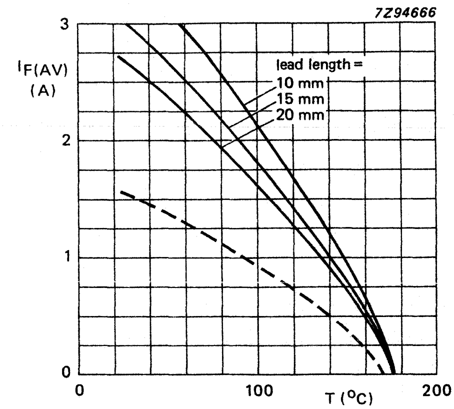


Fig. 7a **BYM36A; B; C.**

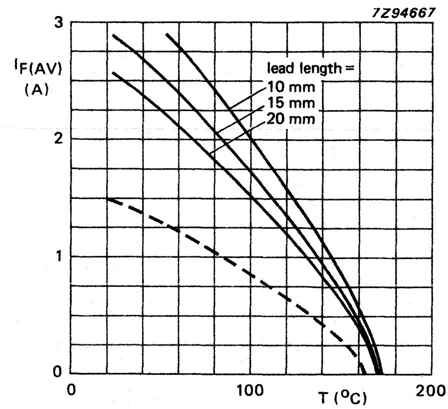


Fig. 7b **BYM36D; E.**

Conditions for Figs 7a and 7b:

Maximum average forward current versus temperature; the curves include losses due to reverse leakage.

The graph is for switched-mode application. $V_R = V_{RRM\ max}$, $\delta = 0{,}5$; a = 1,42.

——— = tie-point temperature
– – – = ambient temperature and device mounted as in Fig. 2.

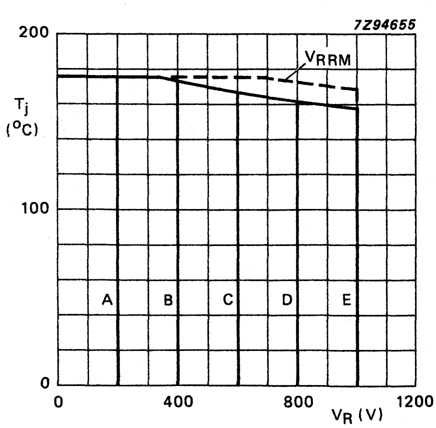


Fig. 8 Maximum permissible junction temperature versus applied reverse voltage.

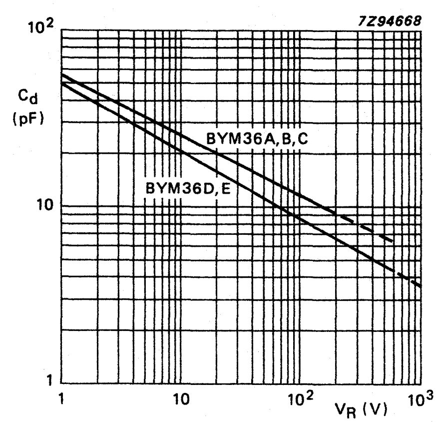


Fig. 9 Capacitance versus reverse voltage; f = 1 MHz; T_j = 25 °C.

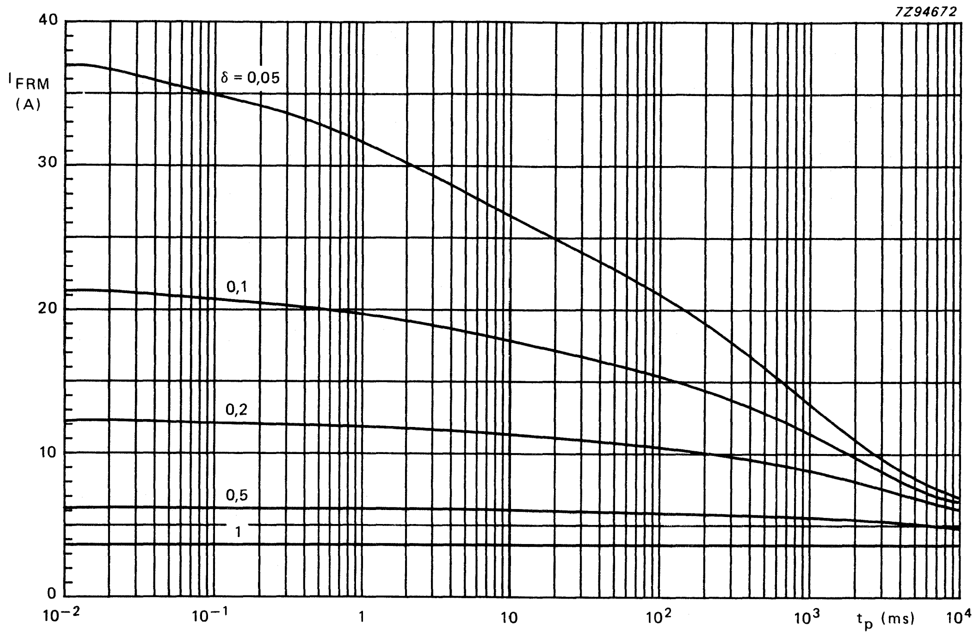


Fig. 10 **BYM36A; B; C.** Maximum repetitive peak forward current versus pulse time (square pulse) and duty-factor δ at $T_{tie\text{-}point}$ = 55 °C; $R_{th\,j\text{-}tp}$ = 25 K/W; V_{RRM} during $1-\delta$; the curves include derating for $T_{j\,max}$ at V_{RRM} = 600 V.

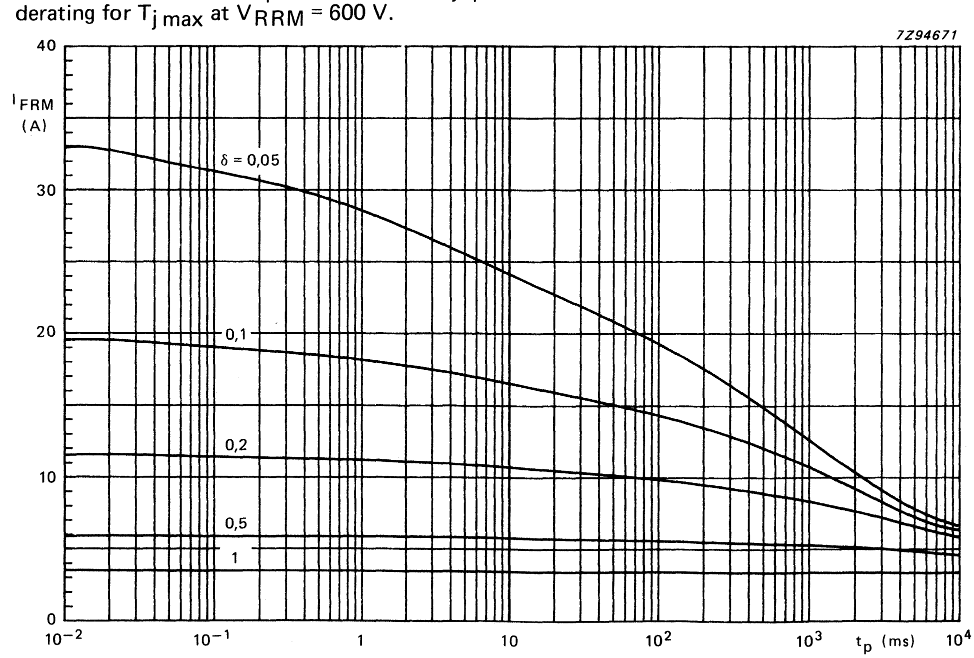


Fig. 11 **BYM36D; E.** Maximum repetitive peak forward current versus pulse time (square pulse) and duty-factor δ at $T_{tie\text{-}point}$ = 55 °C; $R_{th\,j\text{-}tp}$ = 25 K/W; V_{RRM} during $1-\delta$; the curves include derating for $T_{j\,max}$ at V_{RRM} = 1000 V.

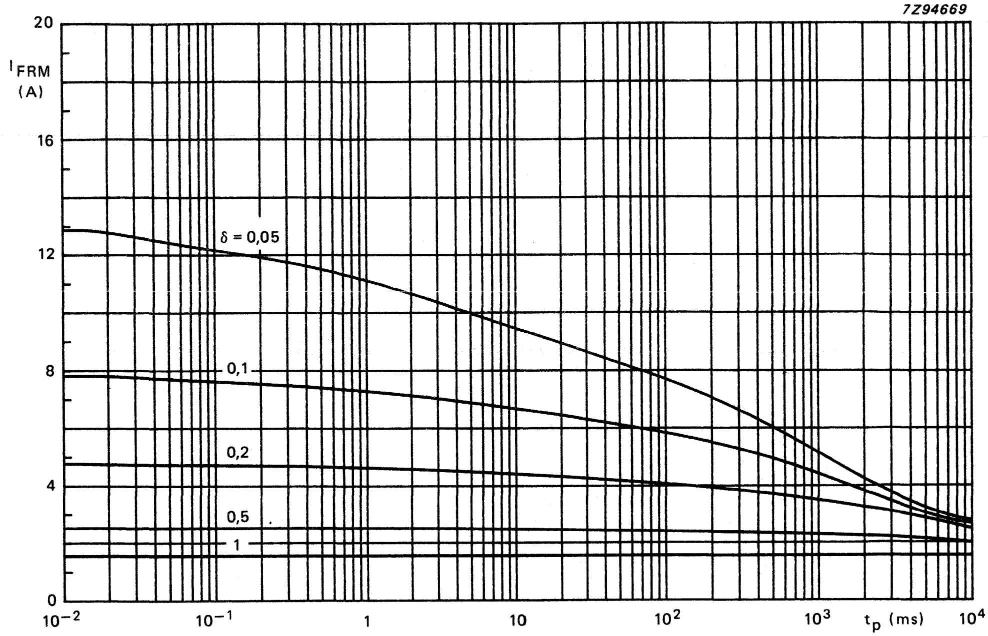


Fig. 12 **BYM36A; B; C.** Maximum repetitive peak forward current versus pulse time (square pulse) and duty-factor δ at T_{amb} = 65 °C; $R_{th\,j\text{-}a}$ = 75 K/W; V_{RRM} during $1 - \delta$; the curves include derating for $T_{j\,max}$ at V_{RRM} = 600 V.

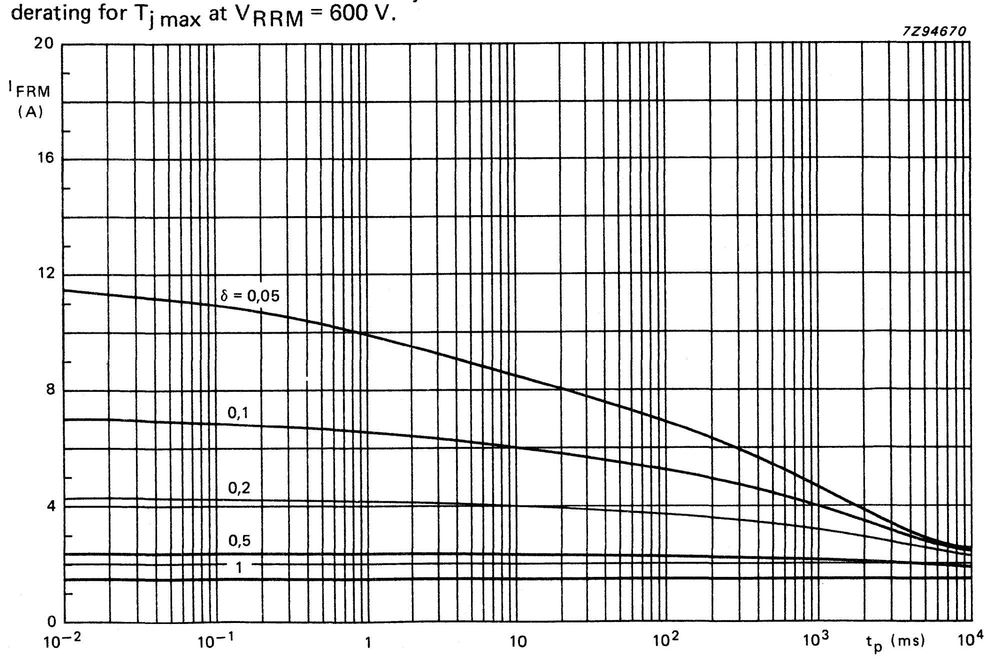


Fig. 13 **BYM36D; E.** Maximum repetitive peak forward current versus pulse time (square pulse) and duty-factor δ at T_{amb} = 65 °C; $R_{th\,j\text{-}a}$ = 75 K/W; V_{RRM} during $1 - \delta$; the curves include derating for $T_{j\,max}$ at V_{RRM} = 1000 V.

CONTROLLED AVALANCHE RECTIFIER DIODES

Double-diffused glass passivated rectifier diodes in hermetically sealed axial-leaded glass envelopes, capable of absorbing reverse transients.

They are intended for rectifier applications in television circuits as well as general purpose applications e.g. in telephony equipment.

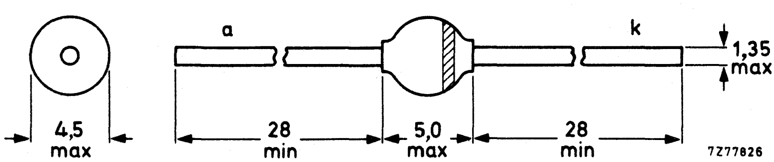
QUICK REFERENCE DATA

			BYM56A	B	C	D	E	
Crest working reverse voltage	V_{RWM}	max.	200	400	600	800	1000	V
Reverse avalanche breakdown voltage	$V_{(BR)R}$	>	225	450	650	900	1100	V
		<	1600	1600	1600	1600	1600	V
Average forward current	$I_{F(AV)}$	max.			3,5			A
Non-repetitive peak forward current	I_{FSM}	max.			80			A
Non-repetitive peak reverse power dissipation	P_{RSM}	max.			1			kW
Junction temperature	T_j	max.			175			^oC

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-64.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYM56A	B	C	D	E	
Crest working reverse voltage	V_{RWM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	800	1000	V

Average forward current (averaged over any 20 ms period)				
T_{tp} = 50 °C, lead length 10 mm	$I_{F(AV)}$	max.	3,5	A
T_{amb} = 55 °C; Fig. 2	$I_{F(AV)}$	max.	1,4	A
Repetitive peak forward current	I_{FRM}	max.	20	A
Non-repetitive peak forward current t = 10 ms; half sine-wave; $T_j = T_{j\ max}$ prior to surge; $V_R = V_{RWMmax}$	I_{FSM}	max.	80	A
Non-repetitive peak reverse power dissipation t = 20 μs (half sine-wave) $T_j = T_{j\ max}$ prior to surge	P_{RSM}	max.	1	kW
Non-repetitive peak reverse avalanche energy; I_R = 1 A; $T_j = T_{j\ max}$ prior to surge; with inductive load switched off	E_{RSM}	max.	20	mJ
Storage temperature	T_{stg}		−65 to + 175	°C
Junction temperature	T_j	max.	175	°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\ j\text{-}tp}$	=	25	K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ≥ 40 μm; Fig. 2 (see "Thermal model")	$R_{th\ j\text{-}a}$	=	75	K/W

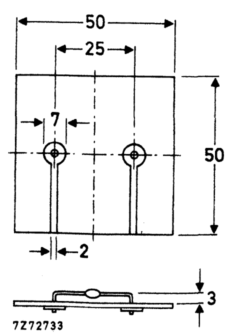


Fig. 2 Device mounted on a printed circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYM56A	B	C	D	E	
Forward voltage*								
I_F = 5 A	V_F	<	1,25	1,25	1,25	1,25	1,25	V
I_F = 3 A; $T_j = T_{j\,max}$	V_F	<	0,95	0,95	0,95	0,95	0,95	V
Reverse avalanche breakdown voltage								
I_R = 0,1 mA	$V_{(BR)R}$	>	225	450	650	900	1100	V
		<	1600	1600	1600	1600	1600	V
Reverse current								
$V_R = V_{RWMmax}$**	I_R	<			1			μA
$V_R = V_{RWMmax}$; T_j = 165 °C	I_R	<			150			μA
Diode capacitance								
V_R = 0; f = 1 MHz	C_d	typ.			90			pF

* Measured under pulse conditions to avoid excessive dissipation.

** Illuminance ⩽ 500 lux (daylight); relative humidity < 65%.

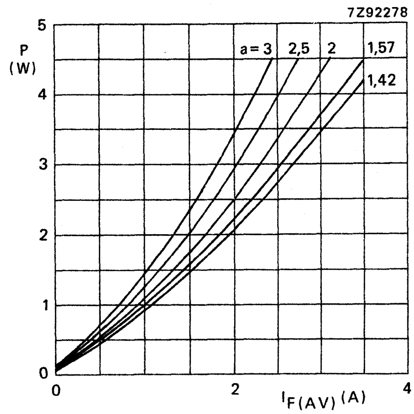


Fig. 3 Steady state power dissipation (forward plus leakage current) excluding losses in avalanche region as a function of the average forward current.

$a = I_{F(RMS)}/I_{F(AV)}$; V_{RWMmax}.

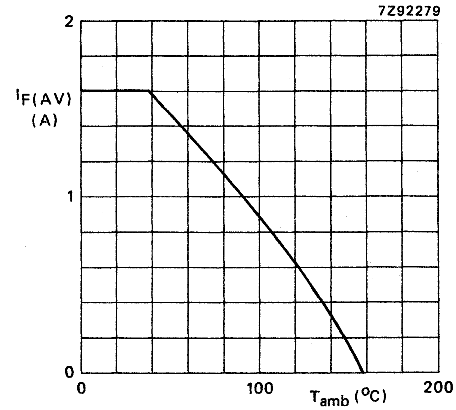


Fig. 4 Maximum average forward current as a function of the ambient temperature; the curve includes losses due to reverse leakage. Mounting method see Fig. 2.

$a = 1{,}57$; $V_R = V_{RWMmax}$.

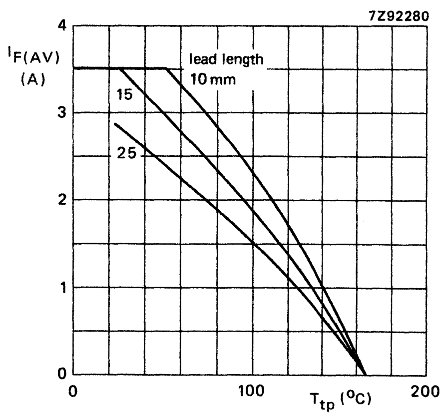


Fig. 5 Maximum average forward current as a function of the tie-point temperature; the curves include losses due to reverse leakage.

$V_R = V_{RWMmax}$; $a = 1{,}57$.

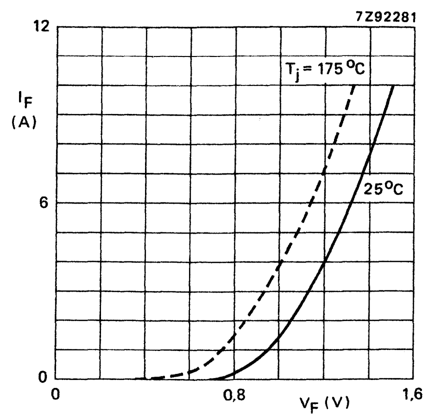


Fig. 6 Maximum V_F curves.

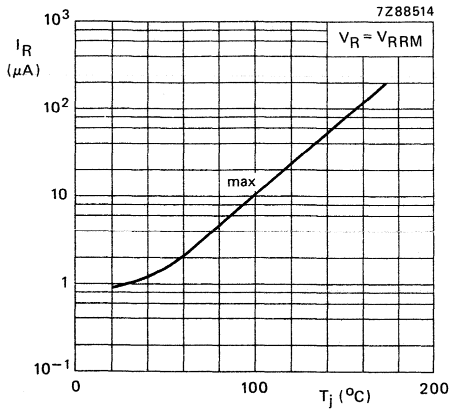


Fig. 7 I_R vs. T_j.

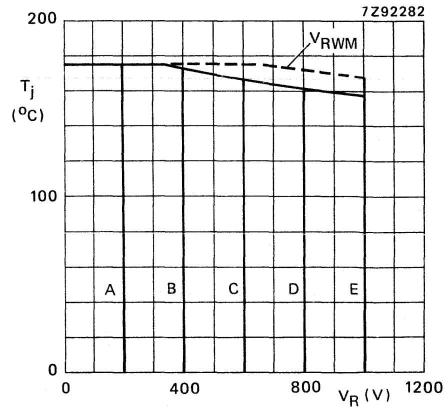


Fig. 8 Maximum values of T_j vs. V_R.

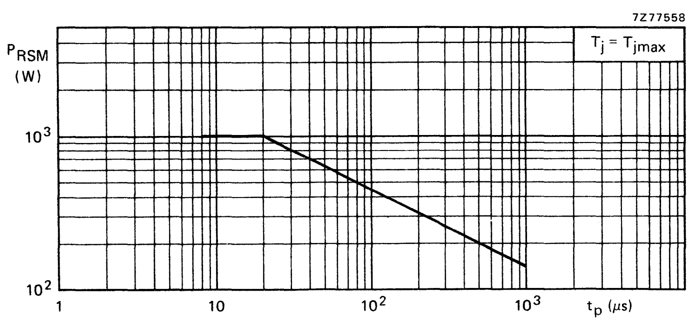
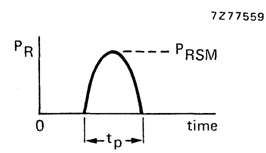


Fig. 9 Maximum permissible non-repetitive peak reverse power dissipation in the avalanche region.



SCHOTTKY BARRIER DIODE

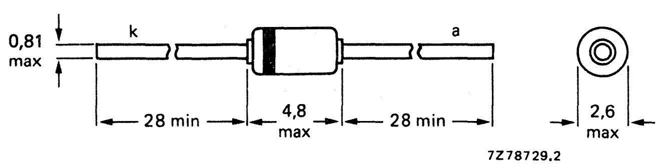
Schottky barrier diode with an integrated p-n junction protection ring in a DO-41 glass envelope and intended for use in low output voltage, low-power switch-mode power supplies and, in general, in circuits, where low forward voltage values are important.

This diode is available in three reverse-voltage groups.

QUICK REFERENCE DATA

			BYV10-20	-30	-40	
Repetitive peak reverse voltage	V_{RRM}	max.	20	30	40	V
Reverse current	I_R	<		1		mA
Average forward current (d.c.)	$I_{F(AV)}$	max.		1		A
Forward voltage $I_F = 1$ A	V_F	<		0,55		V
Reverse recovery time	t_{rr}	<		30		ns
Junction temperature	T_j	max.		125		^oC

Fig. 1 DO-41 (SOD-66). Dimensions in mm



The cathode is indicated by a coloured band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYV10-20	-30	-40	
Repetitive peak reverse voltage	V_{RRM}	max.	20	30	40	V
at T_{amb} = . . .		max.	100	75	50	°C
Average forward current (d.c.)	$I_{F(AV)}$	max.		1		A
Storage temperature	T_{stg}			−65 to + 200		°C
Operating junction temperature	T_j			−65 to + 125		°C

THERMAL RESISTANCE

From junction to tie-point at 4 mm from the body	$R_{th\ j\text{-}tp}$	110	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage				
I_F = 0,1 A	V_F	<	0,39	V
I_F = 1 A	V_F	<	0,55	V
I_F = 3 A	V_F	<	0,85	V
Reverse current $V_R = V_{RRM}$	I_R	<	1	mA
Diode capacitance f = 1 MHz; V_R = 0	C_d	typ.	220	pF
Reverse recovery time when switched from I_F = 200 mA to I_R = 200 mA; R_L = 100 Ω; measured at I_R = 20 mA	t_{rr}	<	30	ns

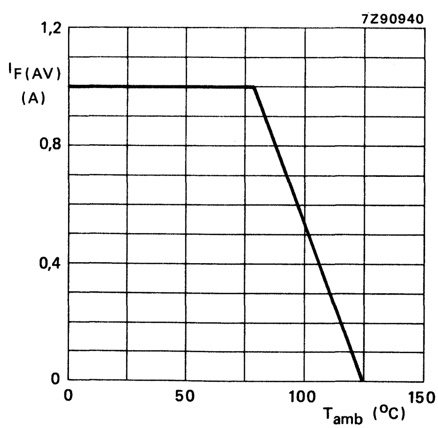


Fig. 2 Derating curve maximum ambient temperature.

VERY FAST SOFT-RECOVERY AVALANCHE RECTIFIER DIODES

Glass passivated rectifier diodes in hermetically sealed axial-leaded glass envelopes. They are intended for use in switched-mode power supplies and high-frequency inverter circuits. In general, they are used where high output voltages and low switching losses are essential. The devices feature non-snap-off (soft-recovery) switching characteristics and are capable of absorbing reverse transient energy.

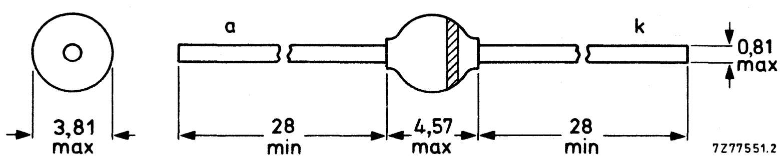
QUICK REFERENCE DATA

			BYV26A	26B	26C	26D	26E	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	800	1000	V
Average forward current	$I_{F(AV)}$	max.	1	1	1	1	1	A
Non-repetitive peak forward current	I_{FSM}	max.	30	30	30	30	30	A
Non-repetitive peak reverse energy	E_{RSM}	max.	10	10	10	10	10	mJ
Reverse recovery time	t_{rr}	<	30	30	30	75	75	ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-57.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYV26A	26B	26C	26D	26E	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	800	1000	V

Average forward current averaged over any 20 ms period				
T_{tp} = 85 °C; lead length 10 mm	$I_{F(AV)}$	max.	1	A
T_{amb} = 60 °C; see Fig. 2	$I_{F(AV)}$	max.	0,65	A
Repetitive peak forward current; see Figs 11 and 12	I_{FRM}	max.	10	A
Non-repetitive peak forward current t = 10 ms; half-sinewave; $T_j = T_{j\,max}$ prior to surge; $V_R = V_{RRMmax}$	I_{FSM}	max.	30	A
Non-repetitive peak reverse avalanche energy I_R = 400 mA; $T_j = T_{j\,max}$ prior to surge; with inductive load switched off	E_{RSM}	max.	10	mJ
Storage temperature	T_{stg}		−65 to + 175	°C
Junction temperature	T_j	max.	175	°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\ j\text{-}tp}$	=	46	K/W
2. Thermal resistance from junction to ambient; device mounted on an 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness > 40 μm; Fig. 2	$R_{th\ j\text{-}a}$	=	100	K/W

(see "Thermal model")

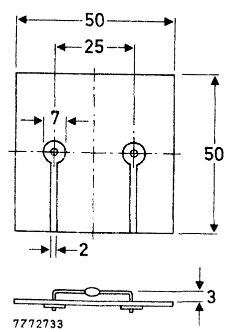


Fig. 2 Mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYV26A	26B	26C	26D	26E	
Forward voltage*								
I_F = 1 A; T_j = 175 °C	V_F	<	1,3	1,3	1,3	1,3	1,3	V*
I_F = 1 A	V_F	<	2,5	2,5	2,5	2,5	2,5	V
Reverse avalanche breakdown voltage								
I_R = 0,1 mA	$V_{(BR)R}$	>	300	500	700	900	1100	V
Reverse current								
$V_R = V_{RRMmax}$	I_R	<	5	5	5	5	5	μA
$V_R = V_{RRMmax}$; T_j = 165 °C	I_R	<	150	150	150	150	150	μA
Reverse recovery time when switched from I_F = 0,5 A to I_R = 1 A; measured at I_R = 0,25 A; for definition see Figs 3 and 4	t_{rr}	<	30	30	30	75	75	ns

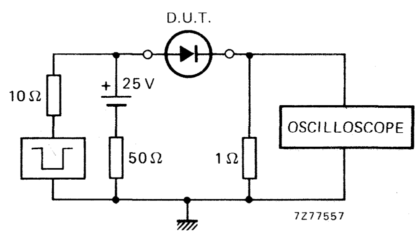


Fig. 3 Test circuit. Input impedance oscilloscope: 1 MΩ; 22 pF; rise time < 7 ns. Source impedance: 50 Ω; rise time < 15 ns.

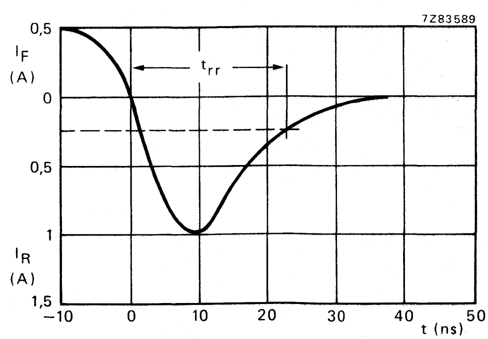


Fig. 4 Reverse recovery time characteristic.

* Measured under pulse conditions to avoid excessive dissipation.

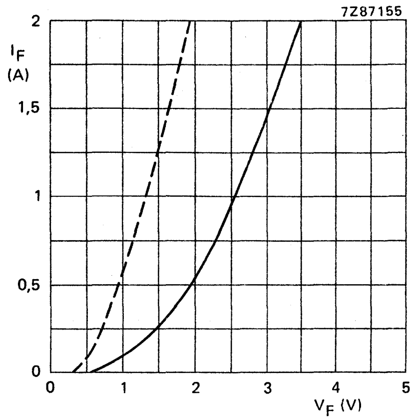
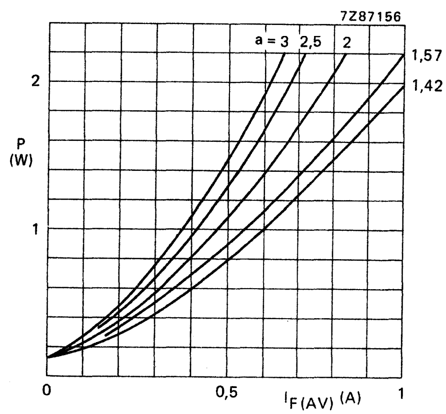


Fig. 5 Maximum forward voltage at
—— T_j = 25 °C
– – – T_j = 175 °C.



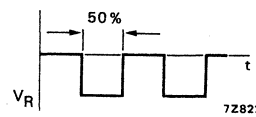


Fig. 6 Maximum steady state power dissipation (forward plus leakage current) excluding switching losses as a function of the average forward current.

The graph is for switched-mode application.

$a = I_{F(RMS)}/I_{F(AV)}$;

$V_R = V_{RRMmax}$, $\delta = 0,5$.

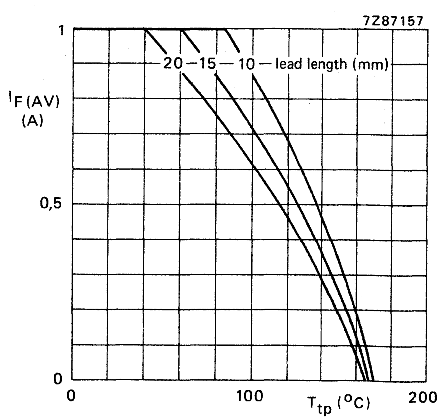


Fig. 7 Maximum average forward current as a function of the tie-point temperature; the curves include losses due to reverse leakage.

The graph is for switched-mode application. $V_R = V_{RRMmax}$, $\delta = 0,5$; a = 1,42.

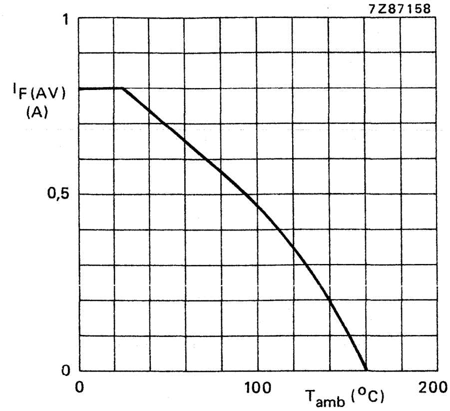


Fig. 8 Maximum average forward current as a function of the ambient temperature; the curve includes losses due to reverse leakage. Mounting method see Fig. 2. The graph is for switched-mode application. $V_R = V_{RRMmax}$, $\delta = 0,5$; a = 1,42.

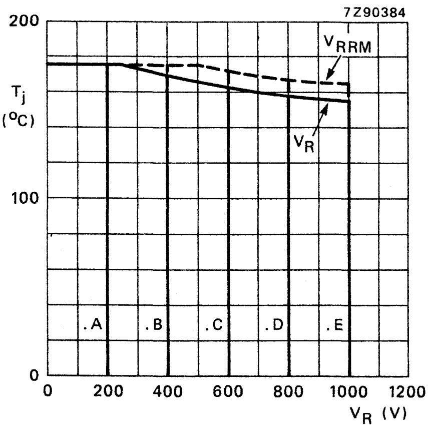


Fig. 9 Maximum permissible junction temperature as a function of the applied reverse voltage.

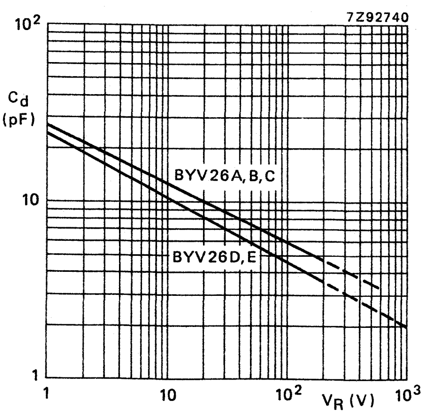


Fig. 10 Capacitance versus voltage; typical values.

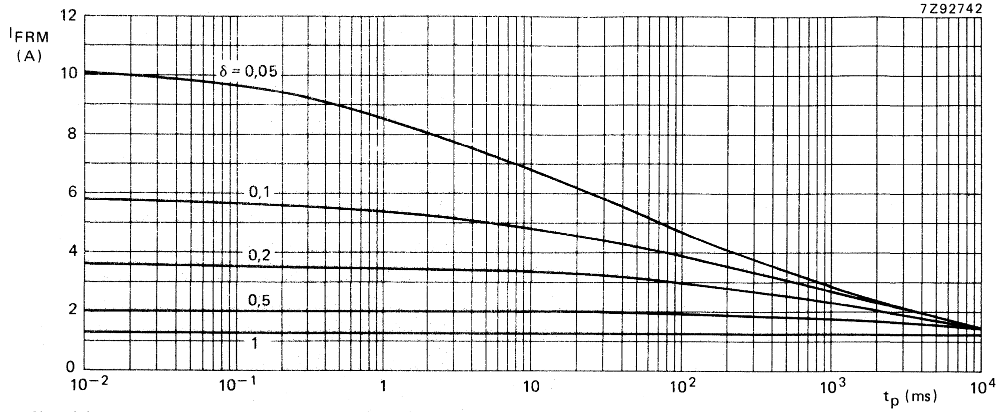


Fig. 11 Maximum repetitive peak forward current versus pulse time (square pulse) and duty factor δ at T_{tp} = 85 °C; $R_{th\ j\text{-}tp}$ = 46 K/W; V_{RRM} during 1 - δ; the curves include derating for $T_{j\ max}$ at V_{RRM} = 1000 V.

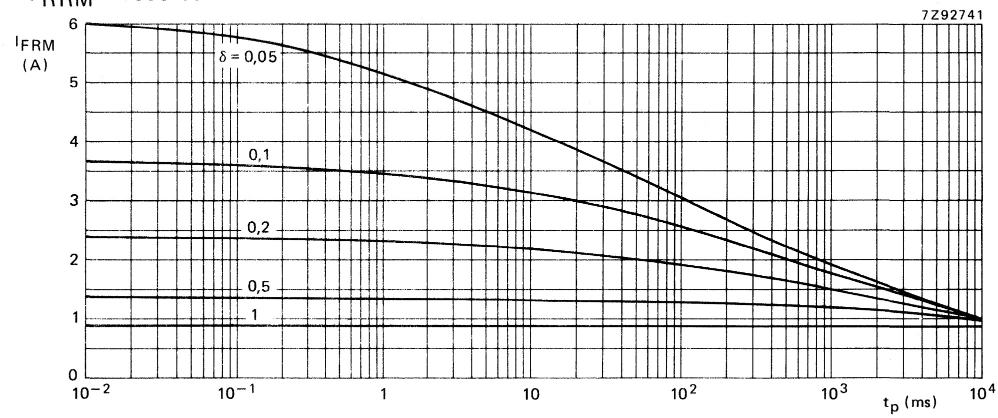


Fig. 12 Maximum repetitive peak forward current versus pulse time (square pulse) and duty factor δ at T_{amb} = 60 °C; $R_{th\ j\text{-}a}$ = 100 K/W; V_{RRM} during 1 - δ; the curves include derating for $T_{j\ max}$ at V_{RRM} = 1000 V.

EPITAXIAL AVALANCHE DIODES

Glass passivated epitaxial rectifier diodes in hermetically sealed axial-leaded glass envelopes. They feature low forward voltage drop, very fast recovery, very low stored charge, non-snap-off switching characteristics and are capable of absorbing reverse transient energy (e.g. during flashover in a picture tube). These properties make the diodes very suitable for use in switched-mode power supplies and in general high-frequency circuits, where low conduction and switching losses are essential.

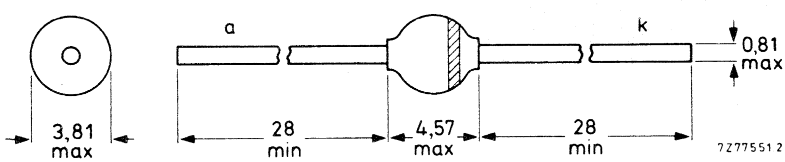
QUICK REFERENCE DATA

			BYV27-50	100	150	200	
Repetitive peak reverse voltage	V_{RRM}	max.	50	100	150	200	V
Continuous reverse voltage	V_R	max.	50	100	150	200	V
Average forward current	$I_{F(AV)}$	max.		2			A
Non-repetitive peak reverse energy	E_{RSM}	max.		40			mJ
Reverse recovery time	t_{rr}	<		25			ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-57.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYV27-50	100	150	200	
Repetitive peak reverse voltage	V_{RRM}	max.	50	100	150	200	V
Continuous reverse voltage	V_R	max.	50	100	150	200	V

Average forward current (switching losses negligible up to 200 kHz) square wave, δ = 0,5				
T_{tp} = 85 °C; lead length = 10 mm	$I_{F(AV)}$	max.	2	A
T_{amb} = 60 °C; Fig. 2	$I_{F(AV)}$	max.	1,3	A
Repetitive peak forward current	I_{FRM}	max.	15	A
Non-repetitive peak forward current (t = 10 ms; half sine-wave) $T_j = T_{j\,max}$ prior to surge; with reapplied V_{RRM}	I_{FSM}	max.	50	A
Non-repetitive peak reverse avalanche energy with inductive load switched off:				
I_R = 820 mA at T_j = 25 °C, prior to surge	E_{RSM}	max.	40	mJ
I_R = 580 mA at $T_j = T_{j\,max}$, prior to surge	E_{RSM}	max.	20	mJ
Storage temperature	T_{stg}		−65 to +175	°C
Junction temperature	T_j	max.	175	°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\,j\text{-}tp}$	=	46	K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ≥40 μm; Fig. 2 (see "Thermal model")	$R_{th\,j\text{-}a}$	=	100	K/W

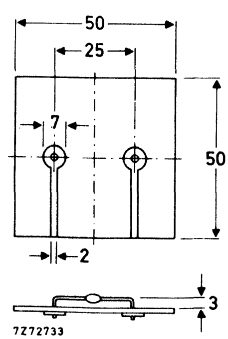


Fig. 2 Mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYV27-50	100	150	200	
Reverse avalanche breakdown voltage							
I_R = 0,1 mA	$V_{(BR)R}$	>	55	110	165	220	V
Forward voltage*							
I_F = 3 A; $T_j = T_{j\,max}$	V_F	<		0,88			V
I_F = 3 A	V_F	<		1,07			V
Reverse current							
$V_R = V_{RRMmax}$	I_R	<		1			μA
$V_R = V_{RRMmax}$; T_j = 165 °C	I_R	<		150			μA
Reverse recovery time when switched from I_F = 0,5 A to I_R = 1 A; measured at I_R = 0,25 A for definition see Figs 3 and 4	t_{rr}	<		25			ns

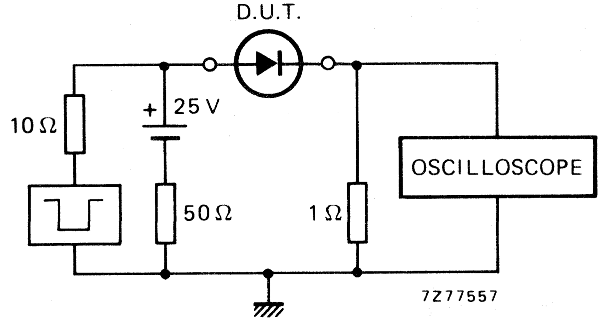


Fig. 3 Test circuit.
Input impedance oscilloscope 1 MΩ; 22 pF. Rise time ≤ 7 ns.
Source impedance 50 Ω. Rise time ≤ 15 ns.

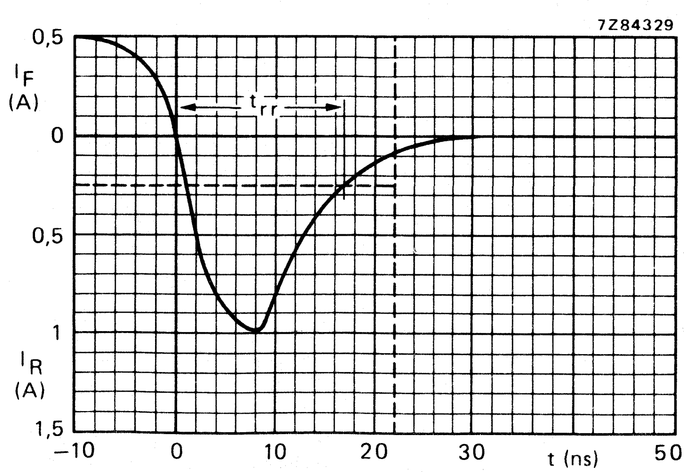


Fig. 4 Reverse recovery time characteristic.

* Measured under pulse conditions to avoid excessive dissipation.

Reverse recovery when switched from
I_F = 1 A to $V_R \geqslant$ 30 V with
$-dI_F/dt$ = 20 A/μs (see Fig. 5)

recovered charge	Q_s	<	15 nC
recovery time	t_{rr}	<	50 ns

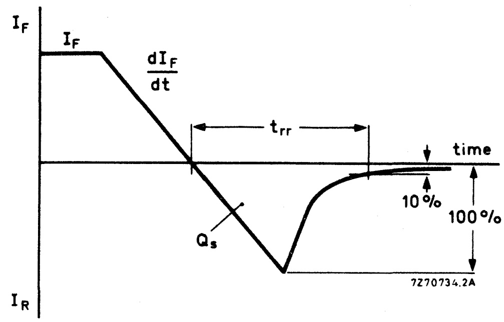


Fig. 5 Definitions of t_{rr} and Q_s.

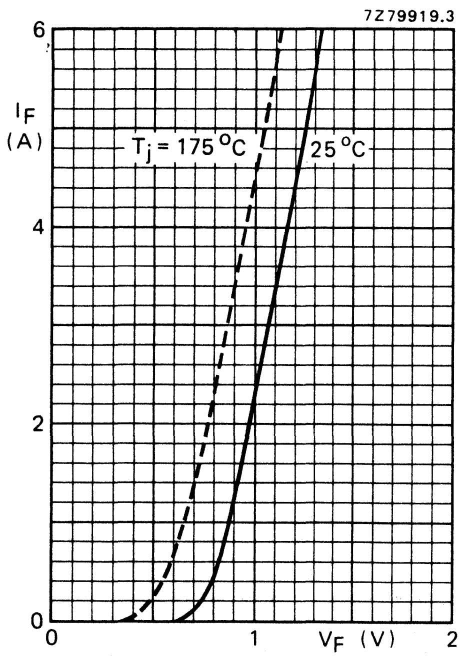


Fig. 6 Maximum forward voltage (V_F) curve.

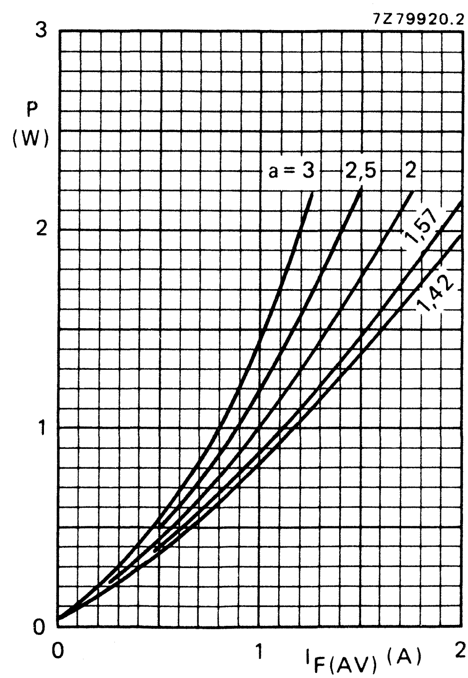


Fig. 7 $a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$.
Pulsed reverse voltage; δ = 0,5.
(Including reverse current losses and switching losses up to f = 200 kHz).

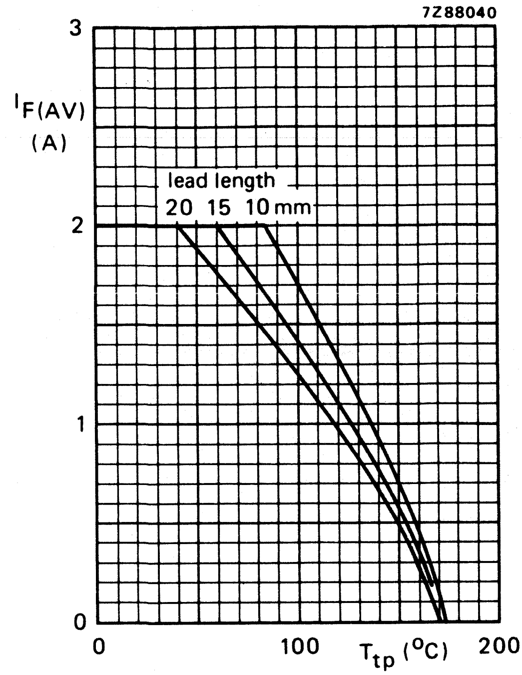


Fig. 8 Maximum average forward current.
The curves include losses due to reverse current and switching up to f = 200 kHz.
Pulsed reverse voltage, δ = 0,5.
$V_R = V_{RRMmax}$.
Square wave current, a = 1,42.

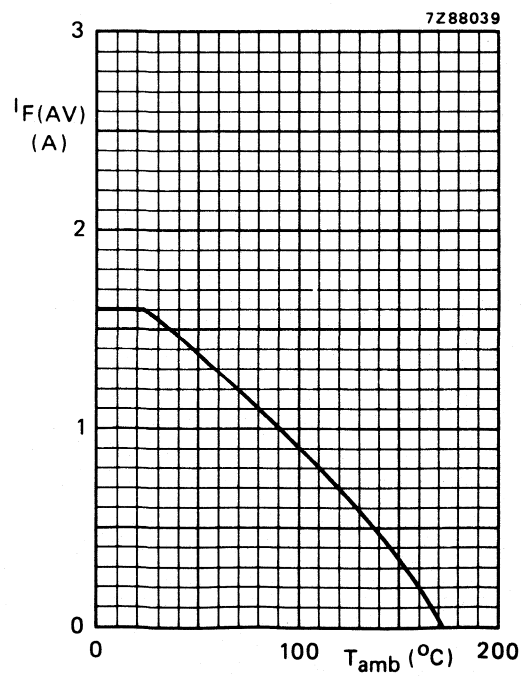


Fig. 9 Maximum average forward current.
The curve includes losses due to reverse current and switching up to f = 200 kHz.
Mounting method see Fig. 2.
Pulsed reverse voltage, δ = 0,5
$V_R = V_{RRMmax}$.
Square wave current, a = 1,42.

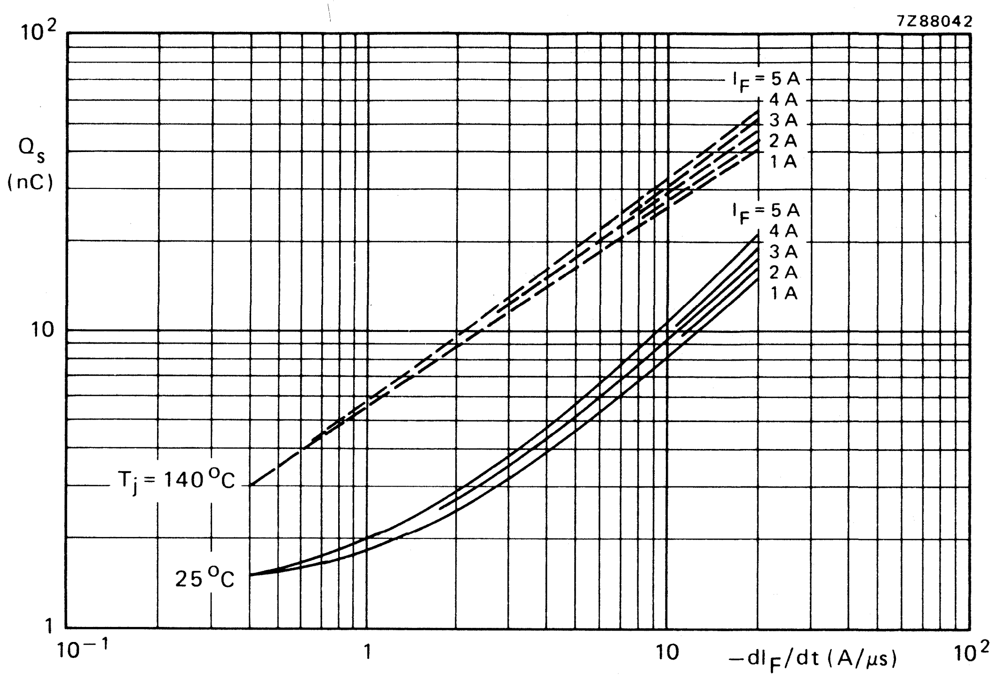


Fig. 10 Maximum values reverse recovery charge. For definition see Fig. 5.

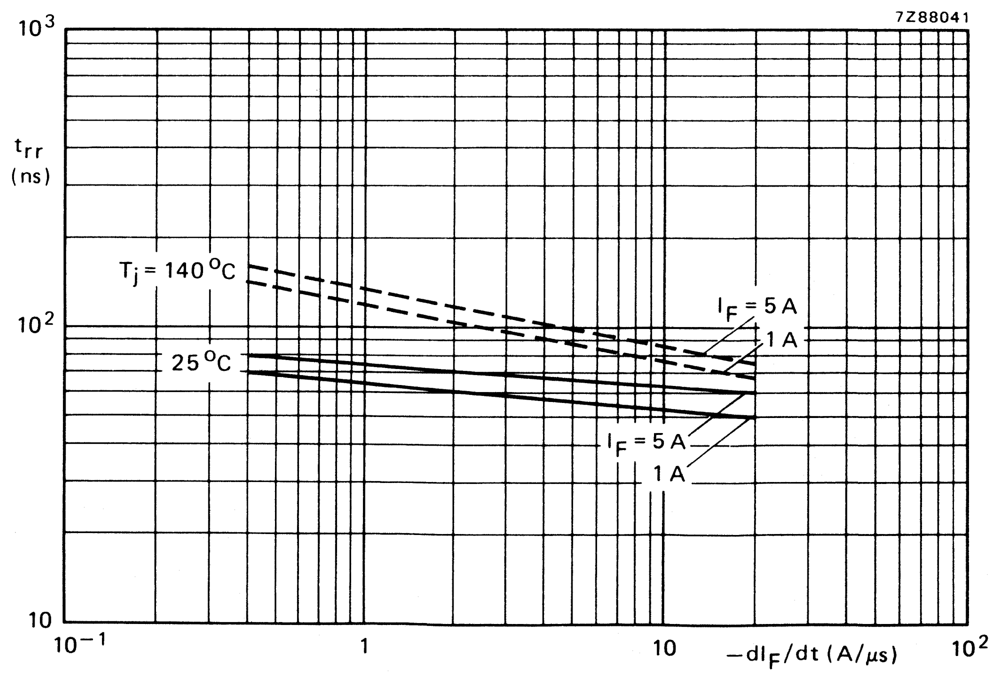


Fig. 11 Maximum values reverse recovery time. For definition see Fig. 5.

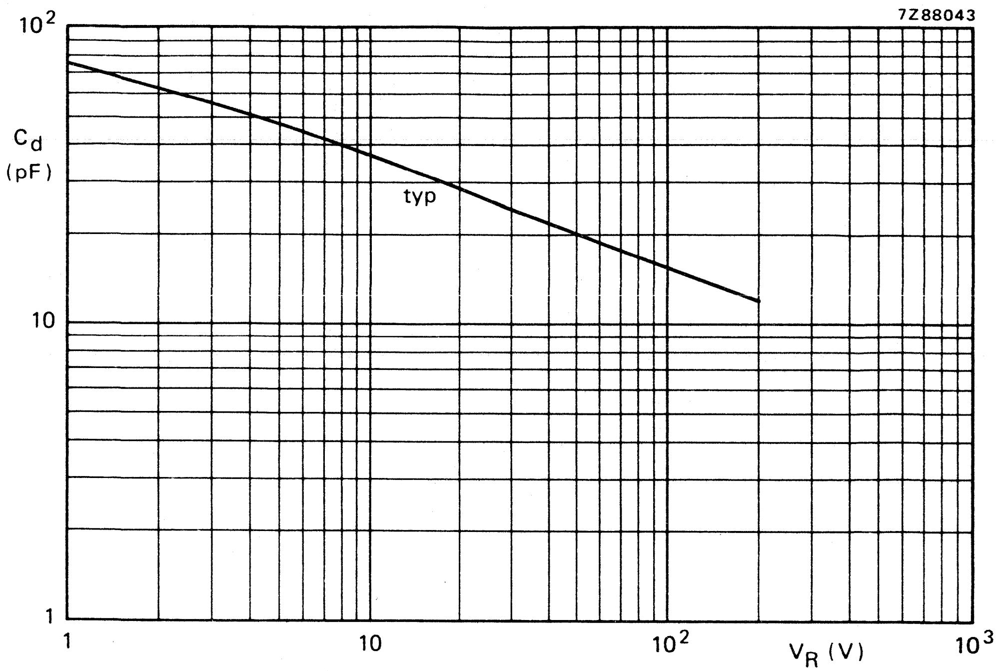


Fig. 12 Typical values diode capacitance at f = 1 MHz; T_j = 25 °C.

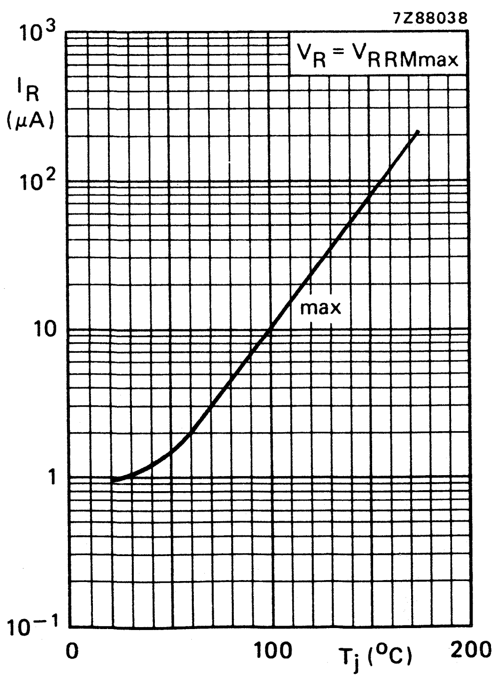


Fig. 13 Maximum values reverse current.

EPITAXIAL AVALANCHE DIODES

Glass passivated epitaxial rectifier diodes in hermetically sealed axial-leaded glass envelopes. They feature low forward voltage drop, very fast recovery, very low stored charge, non-snap-off switching characteristics and are capable of absorbing reverse transient energy (e.g. during flashover in a picture tube). These properties make the diodes very suitable for use in switched-mode power supplies and in general in high-frequency circuits, where low conduction and switching losses are essential.

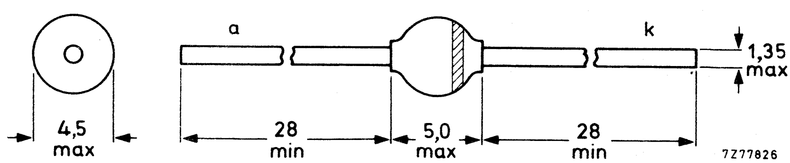
QUICK REFERENCE DATA

			BYV28-50	100	150	200	
Repetitive peak reverse voltage	V_{RRM}	max.	50	100	150	200	V
Continuous reverse voltage	V_R	max.	50	100	150	200	V
Average forward current	$I_{F(AV)}$	max.		3,5			A
Non-repetitive peak reverse energy	E_{RSM}	max.		40			mJ
Reverse recovery time	t_{rr}	<		30			ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-64.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYV28-50	100	150	200	
Repetitive peak reverse voltage	V_{RRM}	max.	50	100	150	200	V
Continuous reverse voltage	V_R	max.	50	100	150	200	V

Average forward current (averaged over any 20 ms period)				
T_{tp} = 85 °C; lead length = 10 mm	$I_{F(AV)}$	max.	3,5	A
T_{amb} = 60 °C; p.c.b. mounting (see Fig. 2)	$I_{F(AV)}$	max.	1,9	A
Repetitive peak forward current	I_{FRM}	max.	25	A
Non-repetitive peak forward current (t = 10 ms; half sine-wave) $T_j = T_{j\,max}$ prior to surge; with reapplied V_{RRM}	I_{FSM}	max.	90	A
Non-repetitive peak reverse avalanche energy; with inductive load switched off				
I_R = 820 mA at T_j = 25 °C, prior to surge	E_{RSM}	max.	40	mJ
I_R = 580 mA at $T_j = T_{j\,max}$, prior to surge	E_{RSM}	max.	20	mJ
Storage temperature	T_{stg}		−65 to +175	°C
Junction temperature	T_j	max.	175	°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\,j\text{-}tp}$	=	25	K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ⩾ 40 μm; Fig. 2 (see "Thermal model")	$R_{th\,j\text{-}a}$	=	75	K/W

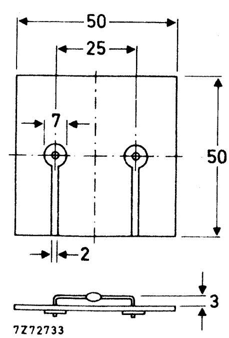


Fig. 2 Mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C, unless otherwise specified

			BYV28-50	100	150	200	
Reverse avalanche breakdown voltage I_R = 0,1 mA	$V_{(BR)R}$	>	55	110	165	220	V
Forward voltage* I_F = 5 A;	V_F	<	1,10				V
I_F = 5 A; $T_j = T_{j\,max}$	V_F	<	0,89				V
Reverse current $V_R = V_{RRMmax}$	I_R	<	1				μA
$V_R = V_{RRMmax}$; T_j = 165 °C	I_R	<	150				μA
Reverse recovery time when switched from I_F = 0,5 A to I_R = 1 A; measured at I_R = 0,25 A for definition see Figs 3 and 4	t_{rr}	<	30				ns

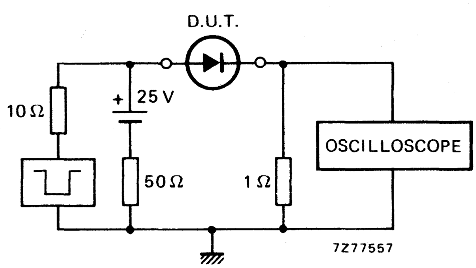


Fig. 3 Test circuit.
Input impedance oscilloscope 1 MΩ; 22 pF; Rise time ≤ 7 ns.
Source impedance 50 Ω. Rise time ≤ 15 ns.

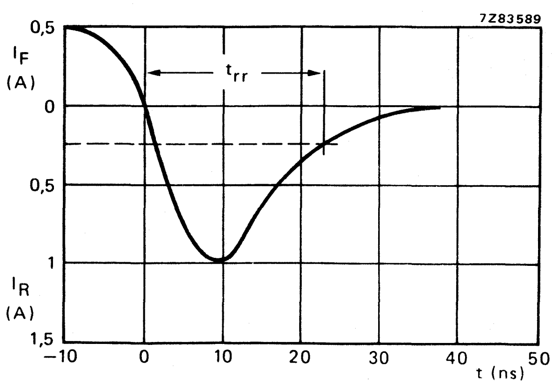


Fig. 4 Reverse recovery time characteristic.

* Measured under pulse conditions to avoid excessive dissipation.

Reverse recovery when switched from
I_F = 1 A to $V_R \geqslant$ 30 V with
$-dI_F/dt$ = 20 A/μs (see Fig. 5)

recovered charge	Q_s	<	20 nC
recovery time	t_{rr}	<	50 ns

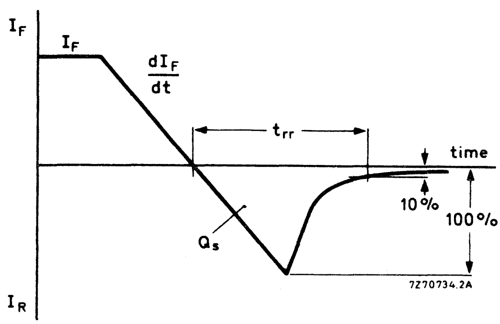


Fig. 5 Definitions of t_{rr} and Q_s.

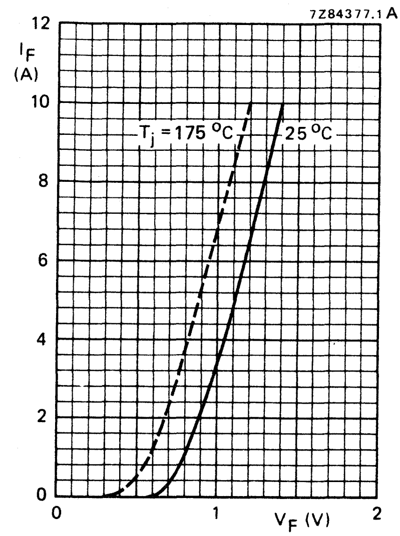


Fig. 6 Maximum forward voltage (V_F) curve.

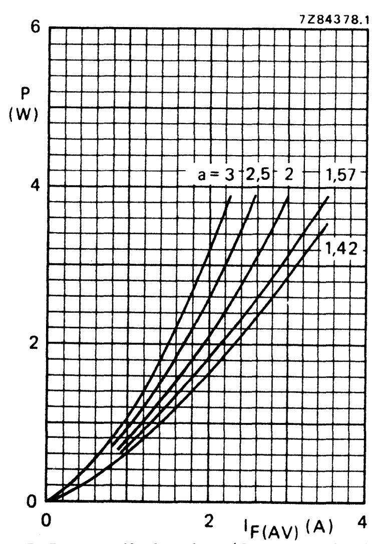


Fig. 7 Power dissipation (forward plus leakage current) as a function of the average forward current. Pulsed reverse voltage; δ = 50%.
$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$.

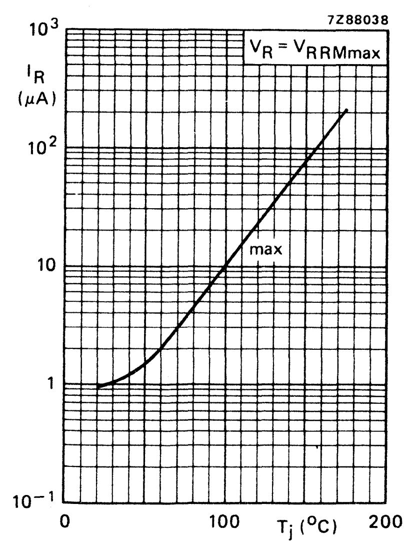


Fig. 8 Reverse current as a function of the junction temperature

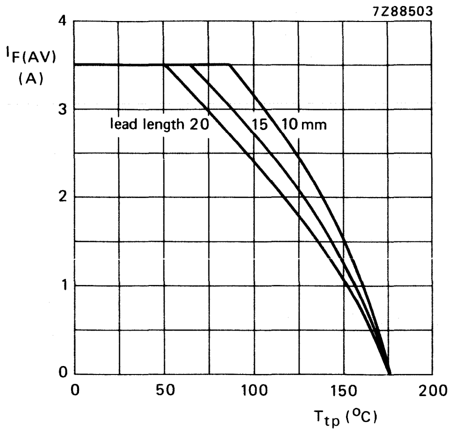


Fig. 9 Maximum average forward current. The curves include losses due to reverse current and switching up to f = 200 kHz.
Pulsed reverse voltage; δ = 0,5 V_R = $V_{RRM\,max}$.
Square-wave current; a = 1,42.

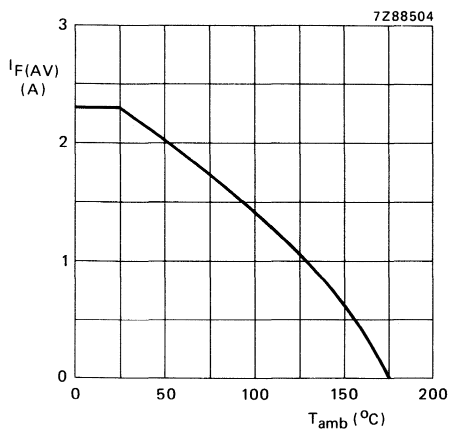


Fig. 10 Maximum average forward current. The curve includes losses due to reverse current and switching up to f = 200 kHz; mounting method see Fig. 2.
Pulsed reverse voltage; δ = 0,5 V_R = $V_{RRM\,max}$.
Square-wave current; a = 1,42.

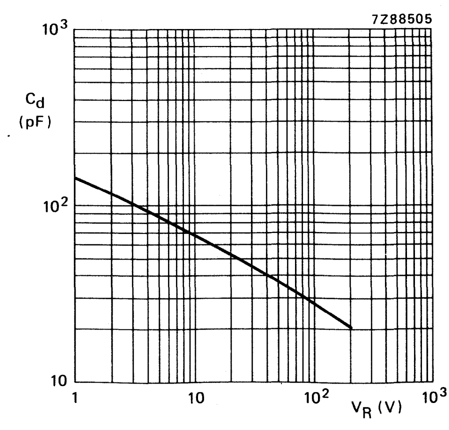


Fig. 11 Typical values diode capacitance at f = 1 MHz. T_j = 25 °C.

VERY FAST SOFT-RECOVERY AVALANCHE RECTIFIER DIODES

Glass passivated rectifier diodes in hermetically sealed axial-leaded glass envelopes. The are intended for use in switched-mode power supplies and high-frequency inverter circuits. In general, they are used where high output voltages and low switching losses are essential. The devices feature non-snap-off (soft-recovery) switching characteristics and are capable of absorbing reverse transient energy.

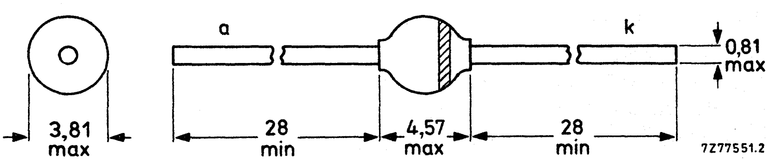
QUICK REFERENCE DATA

		BYV36	A	B	C	D	E	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	800	1000	V
Average forward current	$I_{F(AV)}$	max.	1,6	1,6	1,6	1,5	1,5	A
Non-repetitive peak forward current	I_{FSM}	max.	30	30	30	30	30	A
Non-repetitive peak reverse energy	E_{RSM}	max.	10	10	10	10	10	mJ
Reverse recovery time	t_{rr}	$<$	100	100	100	150	150	ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-57.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYV36 A	B	C	D	E	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	800	1000	V
Average forward current (averaged over any 20 ms period); T_{tp} = 60 °C; lead length 10 mm	$I_{F(AV)}$	max.	1,6	1,6	1,6	1,5	1,5	A
T_{amb} = 60 °C; see Fig. 2	$I_{F(AV)}$	max.	0,87	0,87	0,87	0,81	0,81	A
Repetitive peak forward current T_{tp} = 60 °C; see Figs 11, 12	I_{FRM}	max.	24	24	24	21	21	A
T_{amb} = 60 °C; see Figs 13, 14	I_{FRM}	max.	10	10	10	9	9	A
Non-repetitive peak forward current t = 10 ms, half sine-wave; $T_j = T_{j\,max}$ prior to surge $V_R = V_{RRMmax}$	I_{FSM}	max.			30			A
Non-repetitive peak reverse avalanche energy; I_R = 400 mA; $T_j = T_{j\,max}$ prior to surge; with inductive load switched off	E_{RSM}	max.			10			mJ
Storage temperature	T_{stg}				−65 to +175			°C
Junction temperature	T_j	max.			175			°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\,j\text{-}tp}$	=	46	K/W
2. Thermal resistance from junction to ambient; device mounted on an 1,5 mm thick epoxy-glass printed circuit board; Cu-thickness > 40 µm; Fig. 2 (see "Thermal Model")	$R_{th\,j\text{-}a}$	=	100	K/W

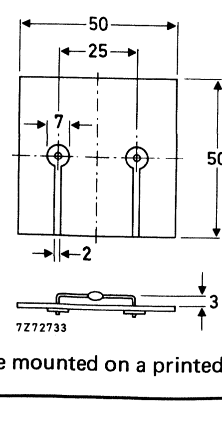


Fig. 2 Device mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYV36 A	B	C	D	E	
Forward voltage *								
I_F = 1 A	V_F	<	1,35	1,35	1,35	1,45	1,45	V
I_F = 1 A; T_j = 175 °C	V_F	<	1,00	1,00	1,00	1,05	1,05	V
Reverse avalanche breakdown voltage								
I_R = 0,1 mA	$V_{(BR)R}$	>	300	500	700	900	1100	V
Reverse current								
$V_R = V_{RRMmax}$	I_R	<	5	5	5	5	5	μA
$V_R = V_{RRMmax}$; T_j = 165 °C	I_R	<	150	150	150	150	150	μA
Reverse recovery time when switched from I_F = 0,5 A to I_R = 1 A; measured at I_R = 0,25 A (for definition see Figs 3 and 4)	t_{rr}	<	100	100	100	150	150	ns

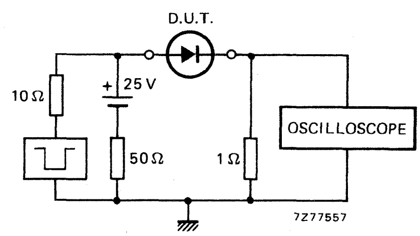


Fig. 3 Test circuit. Input impedance oscilloscope: 1 MΩ; 22 pF; rise time < 7 ns. Source impedance: 50 Ω; rise time < 15 ns.

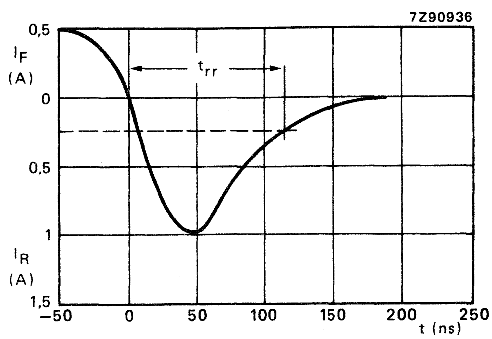


Fig. 4 Reverse recovery time characteristic.

* Measured under pulse conditions to avoid excessive dissipation.

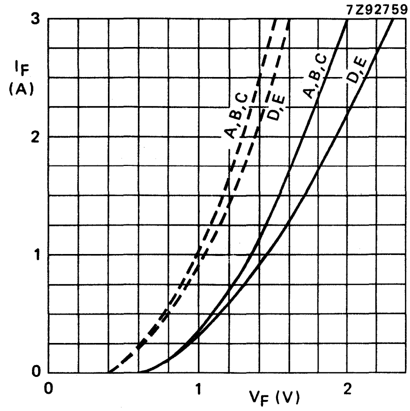


Fig. 5 Maximum forward voltage at
—— T_j = 25 °C; – – – T_j = 175 °C.

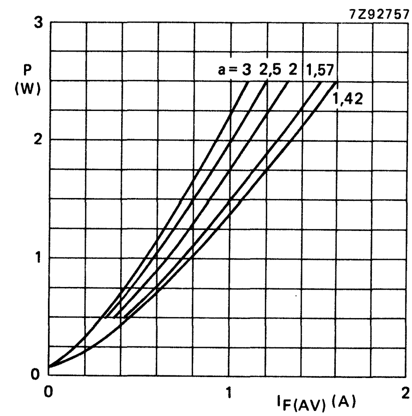
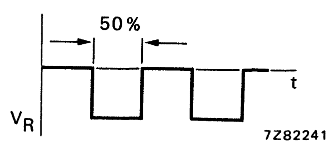


Fig. 6a **BYV36A; B; C.**

Conditions for Figs 6a and 6b:

Maximum steady state power dissipation (forward plus leakage current) excluding switching losses versus average forward current.
The graph is for switched-mode application.
$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$, δ = 0,5.



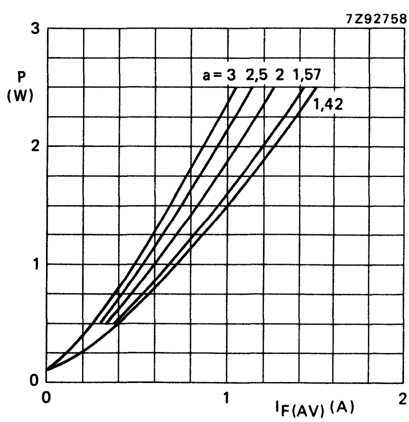


Fig. 6b **BYV36D; E.**

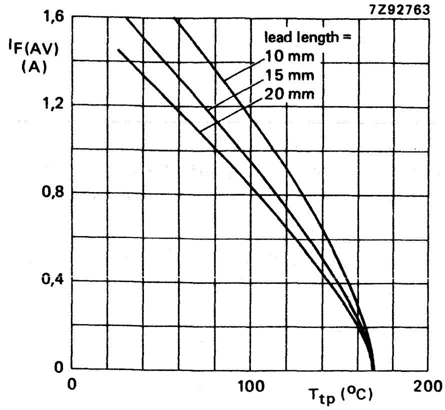
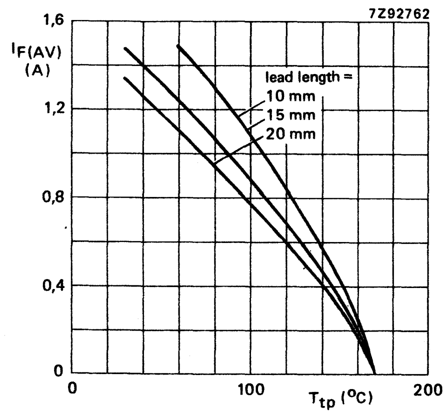


Fig. 7a **BYV36A; B; C.**



Conditions for Figs 7a and 7b:

Maximum average forward current versus tie-point temperature; the curves include losses due to reverse leakage.

The graph is for switched-mode application.
$V_R = V_{RRMmax}$, $\delta = 0,5$; a = 1,42.

Fig. 7b **BYV36D; E.**

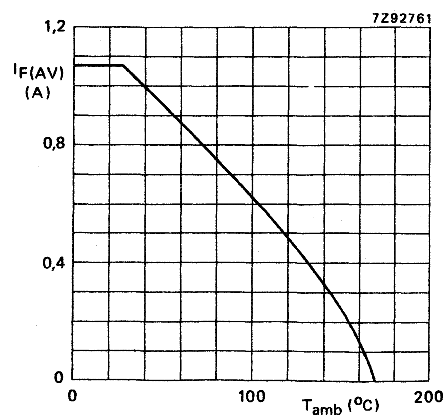


Fig. 8a **BYV36A; B; C.** Maximum average forward current versus ambient temperature; the curve includes losses due to reverse leakage. Mounting method see Fig. 2.

The graph is for switched-mode application.
$V_R = V_{RRMmax}$, $\delta = 0,5$; a = 1,42.

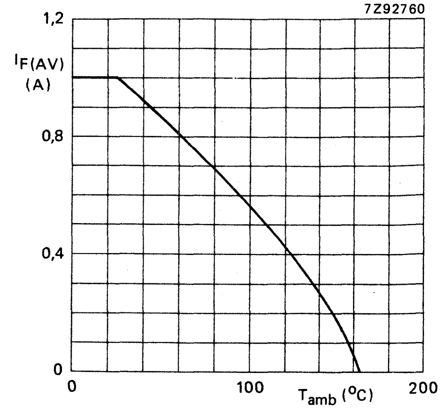


Fig. 8b **BYV36D; E.** Maximum average forward current versus ambient temperature; the curve includes losses due to reverse leakage. Mounting method see Fig. 2.

The graph is for switched-mode application. $V_R = V_{RRMmax}$, $\delta = 0,5$; $a = 1,42$.

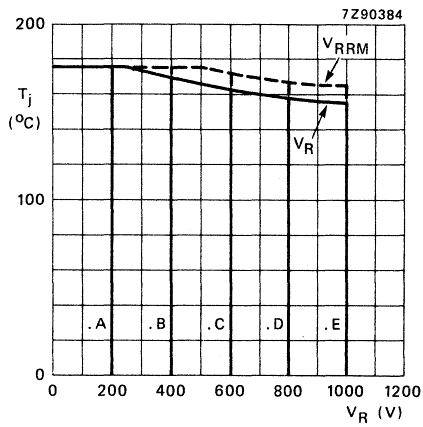


Fig. 9 Maximum permissible junction temperature versus applied reverse voltage.

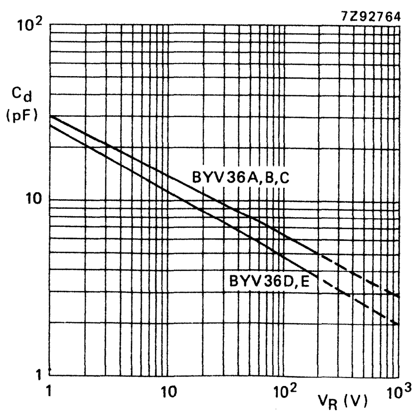


Fig. 10 Capacitance versus reverse voltage; $f = 1$ MHz; $T_j = 25$ °C.

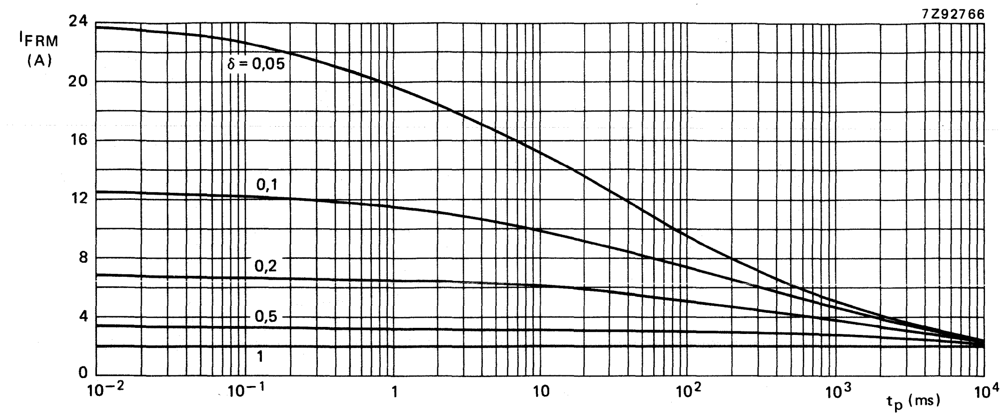


Fig. 11 **BYV36A; B; C.** Maximum repetitive peak forward current versus pulse time (square pulse) and duty factor δ at $T_{tie\text{-}point}$ = 60 °C; $R_{th\ j\text{-}tp}$ = 46 K/W; V_{RRM} during $1 - \delta$; the curves include derating for $T_{j\ max}$ at V_{RRM} = 600 V.

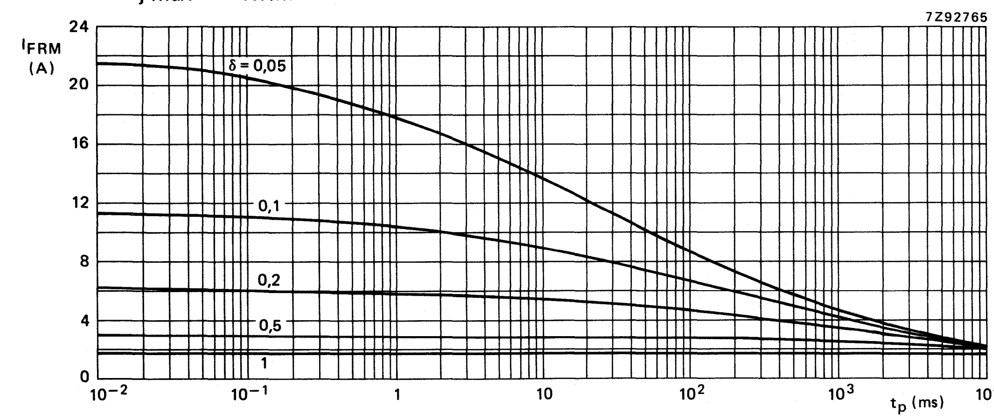


Fig. 12 **BYV36D; E.** Maximum repetitive peak forward current versus pulse time (square pulse) and duty factor δ at $T_{tie\text{-}point}$ = 60 °C; $R_{th\ j\text{-}tp}$ = 46 K/W; V_{RRM} during $1 - \delta$; the curves include derating for $T_{j\ max}$ at V_{RRM} = 1000 V.

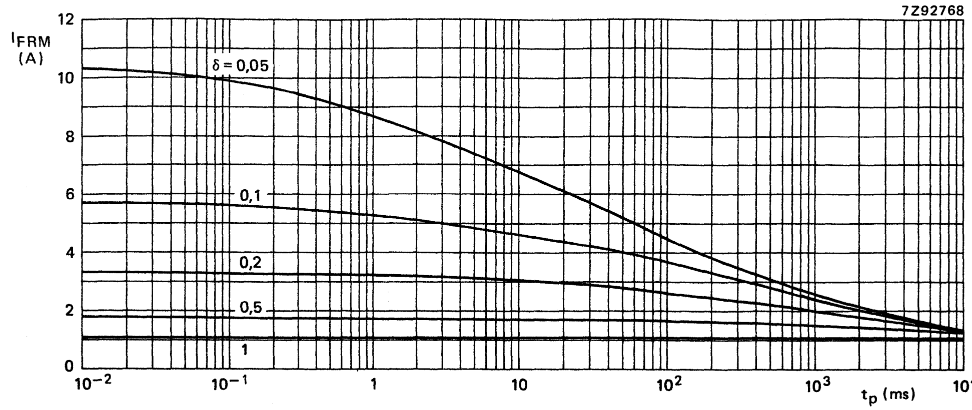


Fig. 13 **BYV36A; B; C.** Maximum repetitive peak forward current versus pulse time (square pulse) and duty factor δ at T_{amb} = 60 °C; $R_{th\ j\text{-}a}$ = 100 K/W; V_{RRM} during $1 - \delta$; the curves include derating for $T_{j\ max}$ at V_{RRM} = 600 V.

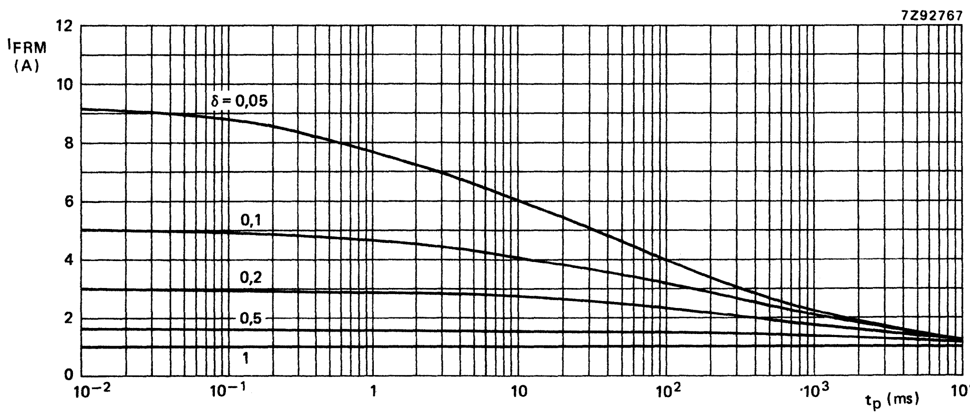


Fig. 14 **BYV36D; E.** Maximum repetitive peak forward current versus pulse time (square pulse) and duty factor δ at T_{amb} = 60 °C; $R_{th\ j\text{-}a}$ = 100 K/W; V_{RRM} during $1 - \delta$; the curves include derating for $T_{j\ max}$ at V_{RRM} = 1000 V.

AVALANCHE FAST SOFT-RECOVERY RECTIFIER DIODES

Glass passivated rectifier diodes in hermetically sealed axial-leaded glass envelopes. They are intended for television and industrial applications, such as switched-mode power supplies, scan rectifiers in TV receivers, and also for use in inverter and converter applications. The devices feature non-snap-off (soft-recovery) switching characteristics and are capable of absorbing reverse transient energy (e.g. during flashover in the picture tube).

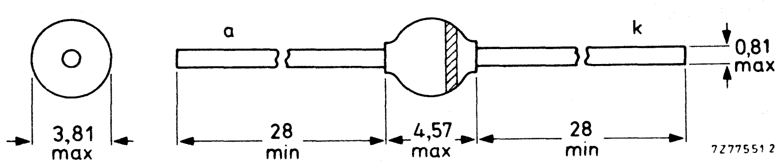
QUICK REFERENCE DATA

			BYV95A	B	C	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	V
Continuous reverse voltage	V_R	max.	200	400	600	V
Average forward current	$I_{F(AV)}$	max.		1,5		A
Non-repetitive peak forward current	I_{FSM}	max.		35		A
Non-repetitive peak reverse energy	E_{RSM}	max.		10		mJ
Reverse recovery time	t_{rr}	<		250		ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-57.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYV95A	B	C	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	V
Continuous reverse voltage	V_R	max.	200	400	600	V
Average forward current (averaged over any 20 ms period)						
T_{tp} = 65 °C; lead length 10 mm	$I_{F(AV)}$	max.		1,5		A
T_{amb} = 65 °C; Fig. 2	$I_{F(AV)}$	max.		0,8		A
Repetitive peak forward current	I_{FRM}	max.		10		A
Non-repetitive peak forward current (t = 10 ms; half sine-wave) $T_j = T_{j\,max}$ prior to surge; $V_R = V_{RRMmax}$	I_{FSM}	max.		35		A
Non-repetitive peak reverse avalanche energy; I_R = 400 mA; $T_j = T_{j\,max}$ prior to surge; with inductive load switched off	E_{RSM}	max.		10		mJ
Storage temperature	T_{stg}			−65 to + 175		°C
Operating junction temperature	T_j	max.		175		°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\ j\text{-}tp}$	=	46	K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ⩾ 40 μm; Fig. 2 (see "Thermal model")	$R_{th\ j\text{-}a}$	=	100	K/W

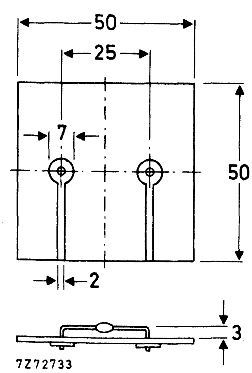


Fig. 2 Mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYV95A	B	C	
Forward voltage						
I_F = 3 A	V_F	<	1,6	1,6	1,6	V *
I_F = 3 A; $T_j = T_{j\,max}$	V_F	<	1,35	1,35	1,35	V *
Reverse avalanche breakdown voltage						
I_R = 0,1 mA	$V_{(BR)R}$	>	300	500	700	V
Reverse current						
$V_R = V_{RRMmax}$; T_j = 165 °C	I_R	<		150		μA
Reverse recovery when switched from I_F = 1 A to $V_R \geq$ 30 V with $-dI_F/dt$ = 20 A/μs						
recovered charge	Q_s	<		250		nC
recovery time	t_{rr}	<		250		ns
Maximum slope of reverse recovery current when switched from I_F = 1 A to $V_R \geq$ 30 V with $-dI_F/dt$ = 1 A/μs	$\lvert dI_R/dt \rvert$	<		6		A/μs

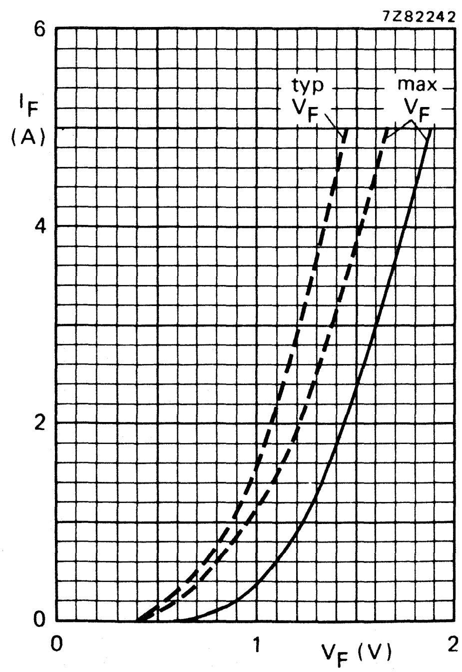


Fig. 3 —— T_j = 25 °C; – – – $T_j = T_{j\,max}$.

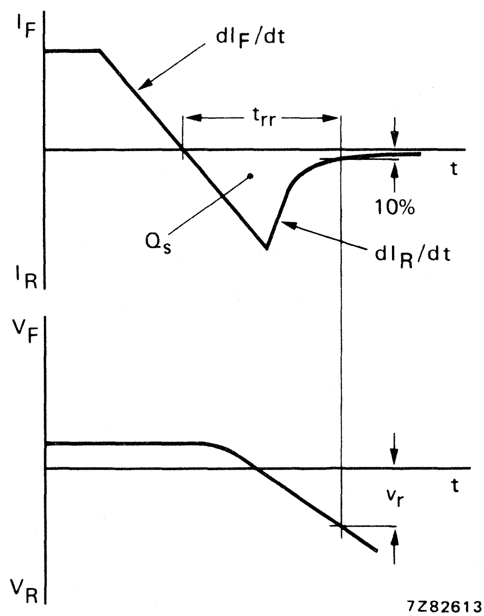


Fig. 4 Definitions.

* Measured under pulse conditions to avoid excessive dissipation.

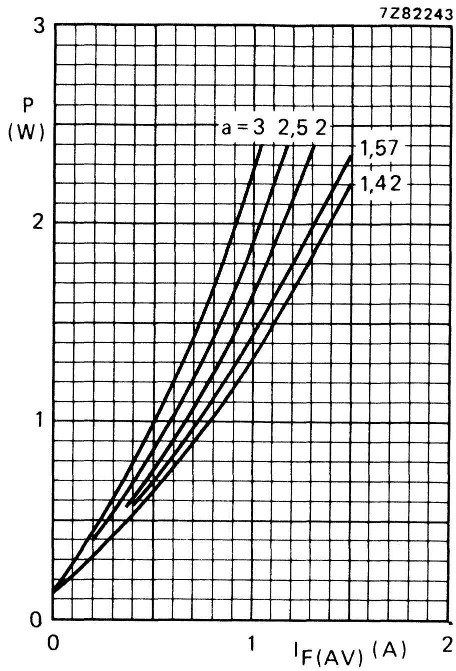
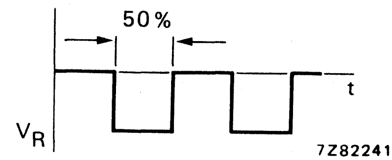


Fig. 5 Steady state power dissipation (forward plus leakage current) excluding switching losses as a function of the average forward current.

The graph is for switched-mode application.

$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$



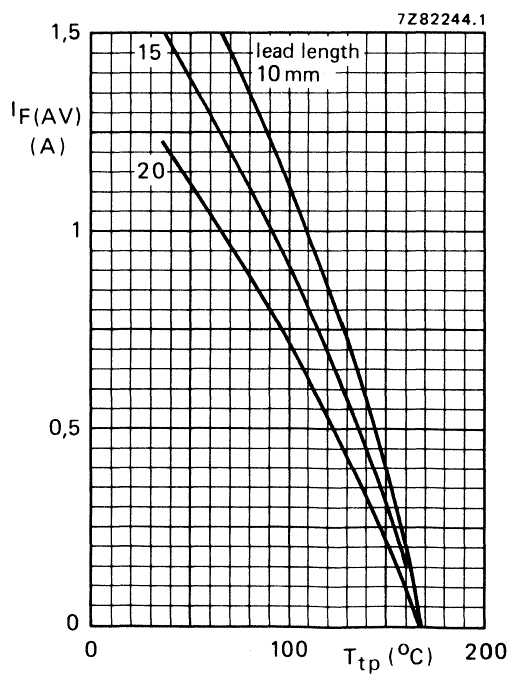


Fig. 6 Maximum average forward current as a function of the tie-point temperature; the curves include losses due to reverse leakage.

The graph is for switched-mode application; $V_R = V_{RRMmax}$; $\delta = 50\%$; a = 1,57.

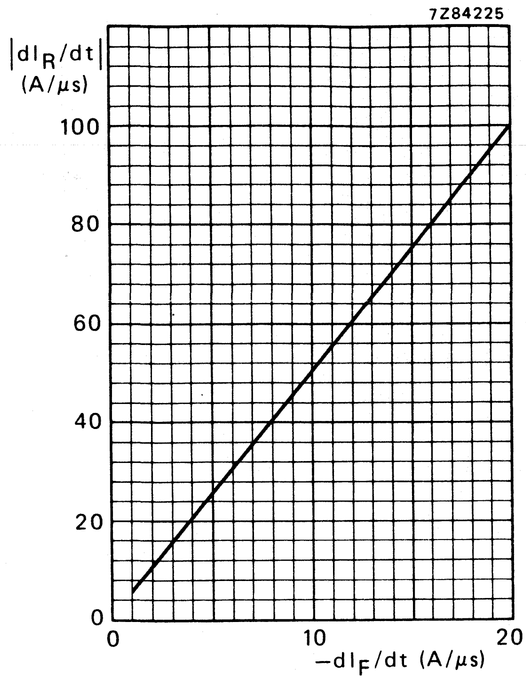


Fig. 7 Maximum slope of reverse recovery current. T_j = 25 °C

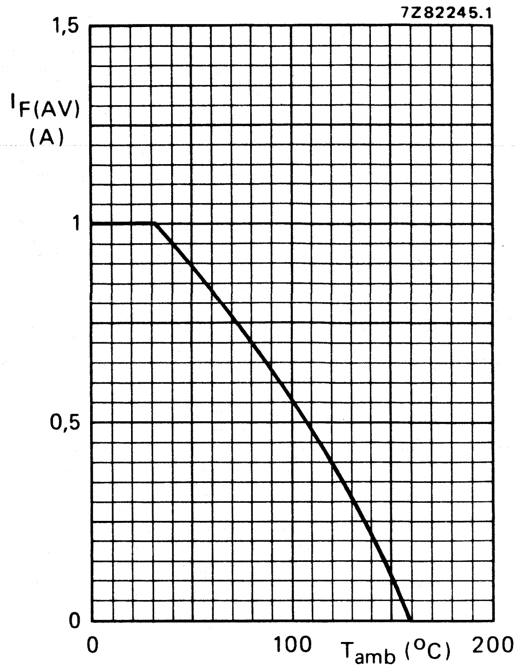


Fig. 8 Maximum average forward current as a function of the ambient temperature; the curve includes losses due to reverse leakage.
Mounting method see Fig. 2.
The graph is for switched-mode application.
$V_R = V_{RRMmax}$; δ = 50%; a = 1,57.

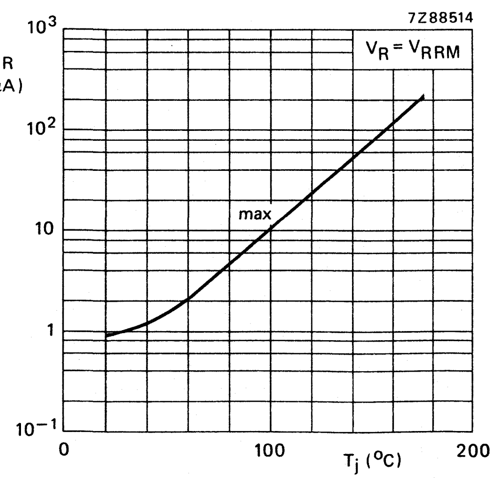


Fig. 9 Reverse current as a function of junction temperature. $V_R = V_{RRM}$.

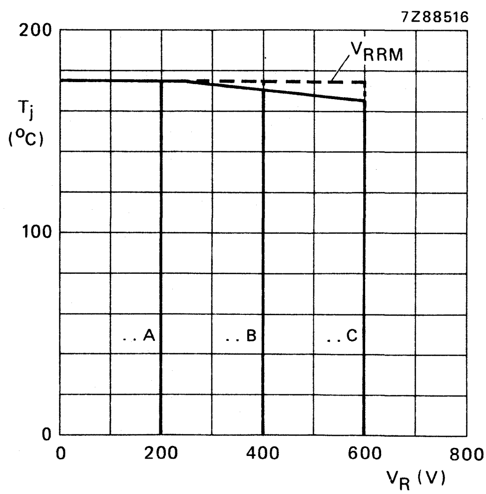


Fig. 10 Maximum junction temperature as a function of reverse voltage.

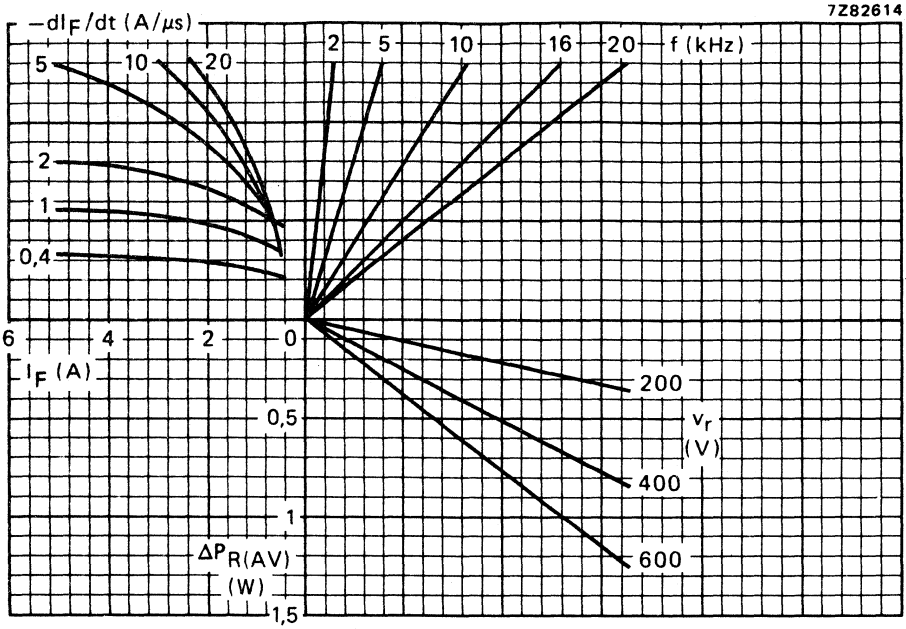


Fig. 11 Nomogram: power loss ($\Delta P_{R(AV)}$) due to switching only. To be added to steady state power losses (see also Fig. 4).

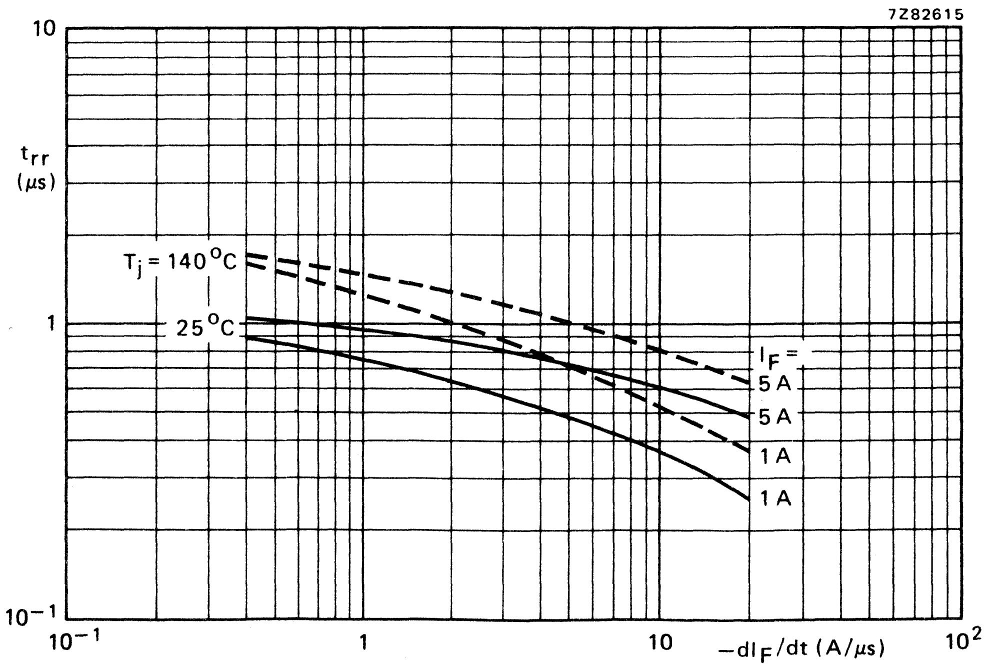


Fig. 12 Maximum values (see also Fig. 4).

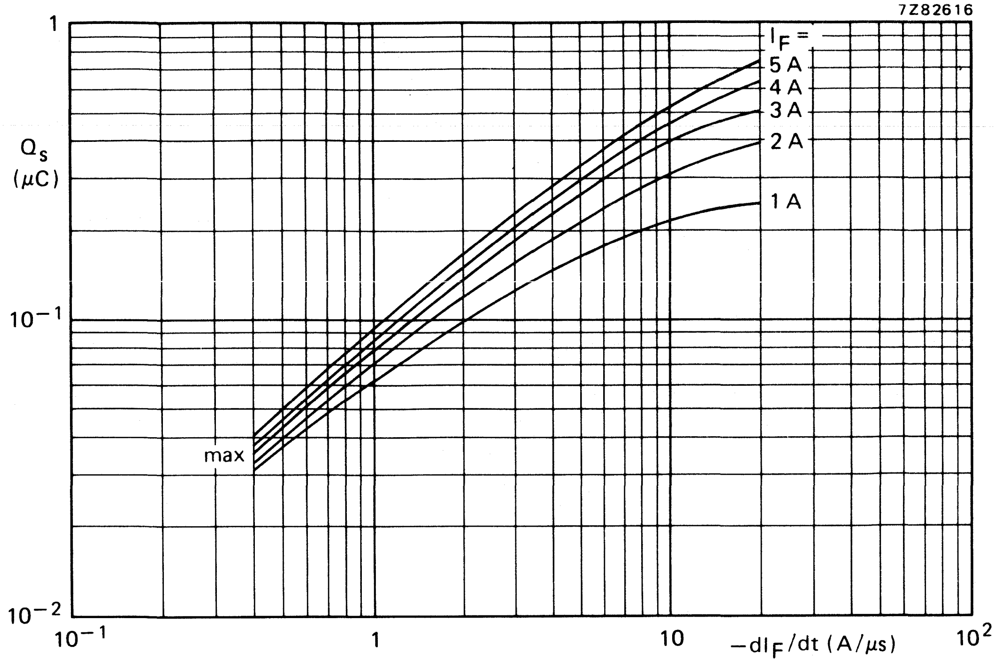


Fig. 13 Maximum values at T_j = 25 °C (see also Fig. 4).

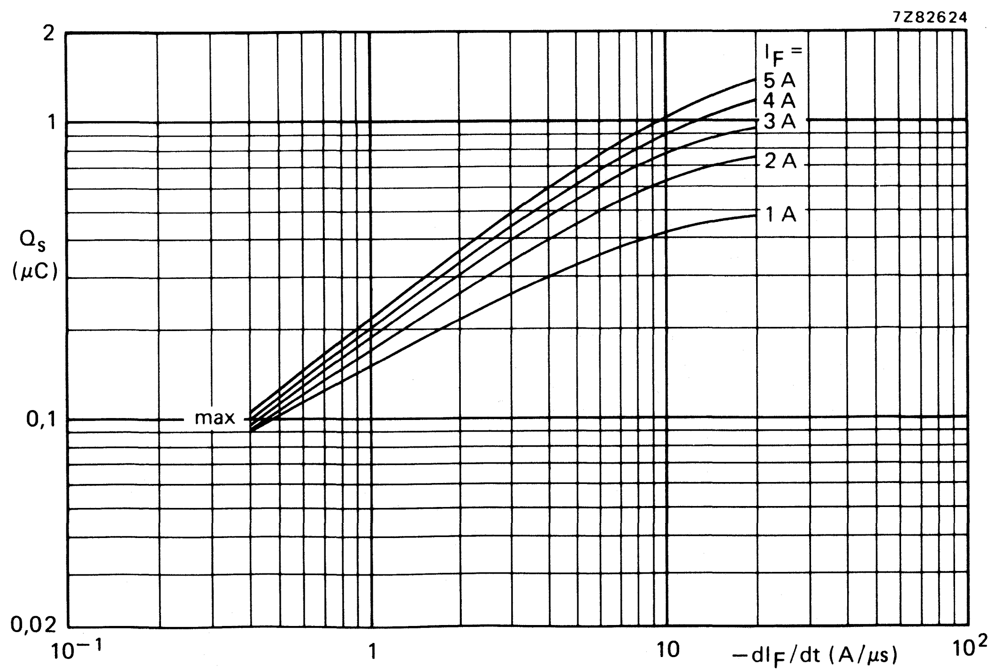


Fig. 14 Maximum values at T_j = 140 °C (see also Fig. 4).

AVALANCHE FAST SOFT-RECOVERY RECTIFIER DIODES

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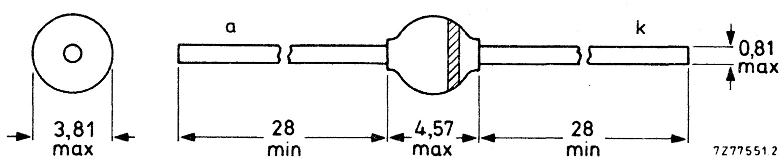
QUICK REFERENCE DATA

			BYV96D	BYV96E	
Repetitive peak reverse voltage	V_{RRM}	max.	800	1000	V
Continuous reverse voltage	V_R	max.	800	1000	V
Average forward current	$I_{F(AV)}$	max.	1,5		A
Non-repetitive peak forward current	I_{FSM}	max.	35		A
Non-repetitive peak reverse energy	E_{RSM}	max.	10		mJ
Reverse recovery time	t_{rr}	<	300		ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-57.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYV96D	BYV96E	
Repetitive peak reverse voltage	V_{RRM}	max.	800	1000	V
Continuous reverse voltage	V_R	max.	800	1000	V
Average forward current (averaged over any 20 ms period)					
T_{tp} = 55 °C; lead length 10 mm	$I_{F(AV)}$	max.	1,5		A
T_{amb} = 55 °C; Fig. 2	$I_{F(AV)}$	max.	0,8		A
Repetitive peak forward current	I_{FRM}	max.	10		A
Non-repetitive peak forward current (t = 10 ms; half sine-wave) $T_j = T_{j\,max}$ prior to surge; $V_R = V_{RRM\,max}$	I_{FSM}	max.	35		A
Non-repetitive peak reverse avalanche energy; I_R = 400 mA; $T_j = T_{j\,max}$ prior to surge; with inductive load switched off	E_{RSM}	max.	10		mJ
Storage temperature	T_{stg}		−65 to + 175		°C
Operating junction temperature	T_j	max.	175		°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm — $R_{th\,j\text{-}tp}$ = 46 K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ≥ 40 μm; Fig. 2 (see "Thermal model") — $R_{th\,j\text{-}a}$ = 100 K/W

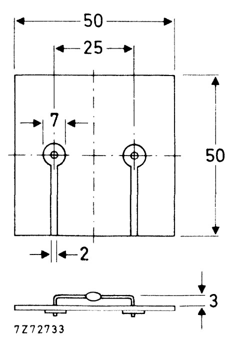


Fig. 2 Mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYV96D	BYV96E	
Forward voltage					
I_F = 3 A	V_F	<	1,6	1,6	V*
I_F = 3 A; $T_j = T_{j\,max}$	V_F	<	1,35	1,35	V*
Reverse avalanche breakdown voltage					
I_R = 0,1 mA	$V_{(BR)R}$	>	900	1100	V
Reverse current					
$V_R = V_{RRM\,max}$; T_j = 165 °C	I_R	<	150		μA
Reverse recovery when switched from I_F = 1 A to $V_R \geqslant$ 30 V with $-dI_F/dt$ = 20 A/μs					
recovered charge	Q_s	<	400		nC
recovery time	t_{rr}	<	300		ns
Maximum slope of reverse recovery current when switched from I_F = 1 A to $V_R \geqslant$ 30 V; $-dI_F/dt$ = 1 A/μs	$\lvert dI_R/dt \rvert$	<	5		A/μs

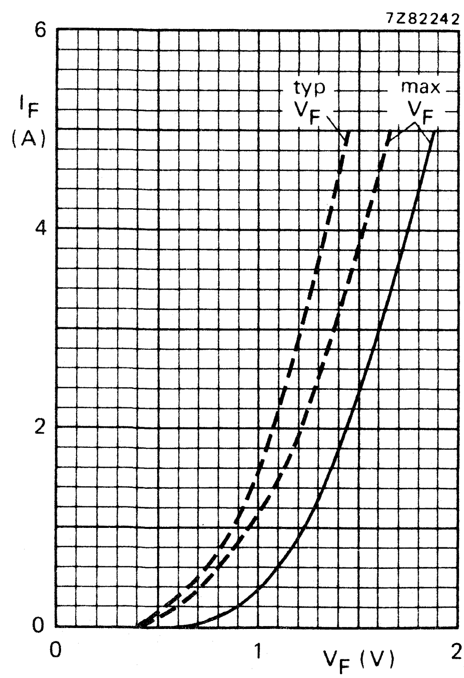


Fig. 3 ——— T_j = 25 °C; — — — $T_j = T_{j\,max}$.

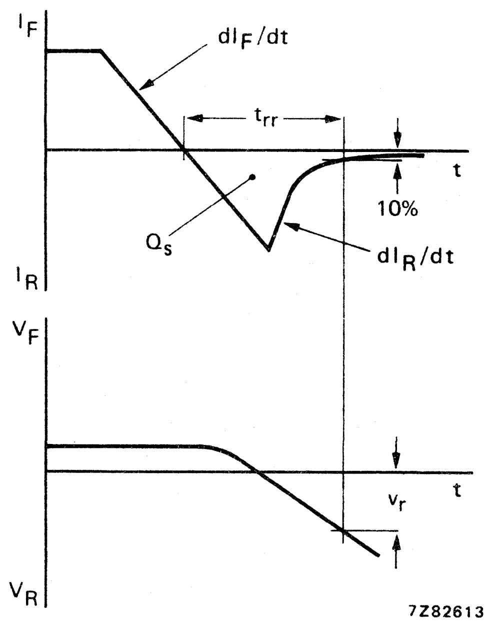
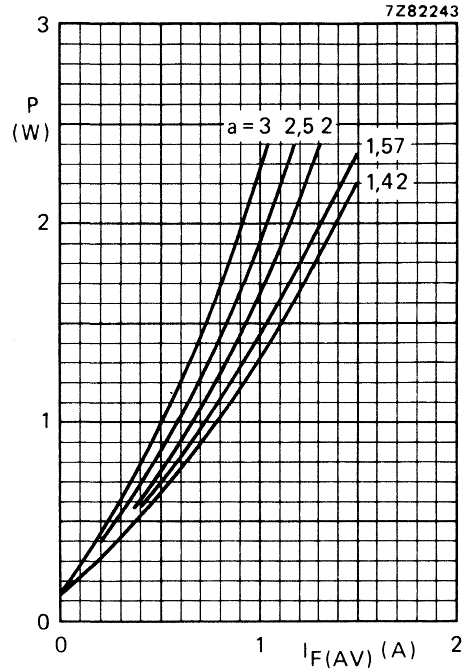


Fig. 4 Definitions of t_{rr} and Q_s.

* Measured under pulse conditions to avoid excessive dissipation.



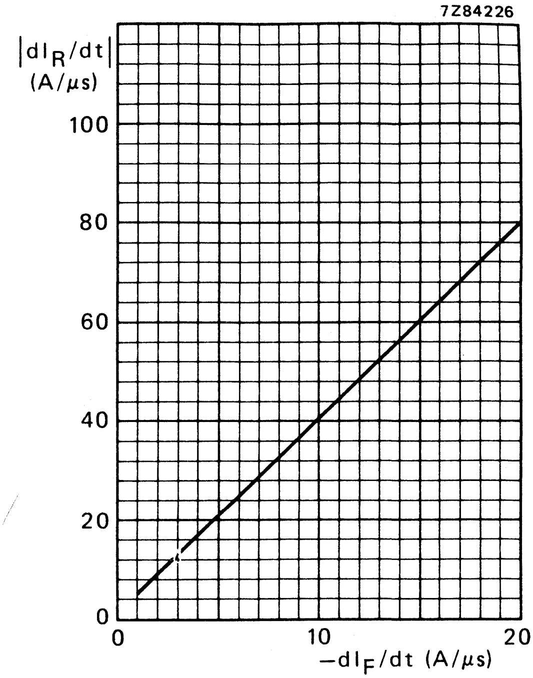


Fig. 5 Steady state power dissipation (forward plus leakage current) excluding switching losses as a function of the average forward current.
The graph is for switched-mode application.

$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRM\,max}$

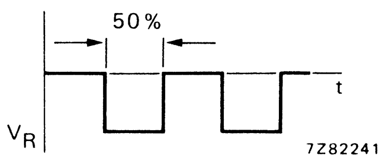


Fig. 6 Maximum slope of reverse recovery current. T_j = 25 °C.

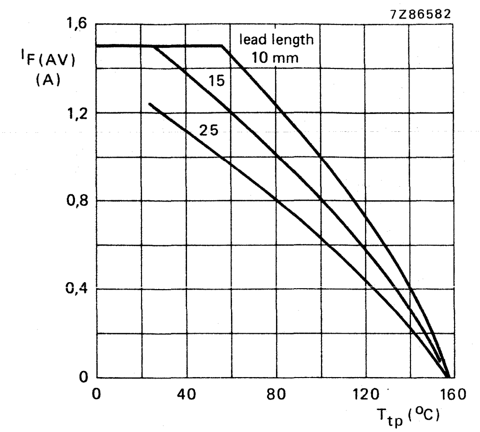


Fig. 7 Maximum average forward current as a function of the tie-point temperature; the curves include losses due to reverse leakage.

The graph is for switched-mode application; $V_R = V_{RRM\,max}$; $\delta = 50\%$; a = 1,57.

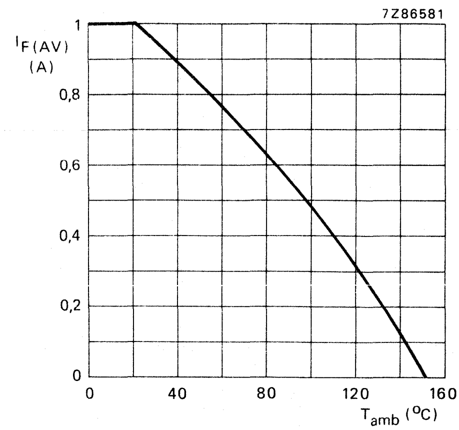


Fig. 8 Maximum average forward current as a function of the ambient temperature; the curve includes losses due to reverse leakage.
Mounting method see Fig. 2.

The graph is for switched-mode application. $V_R = V_{RRM\,max}$; $\delta = 50\%$; a = 1,57.

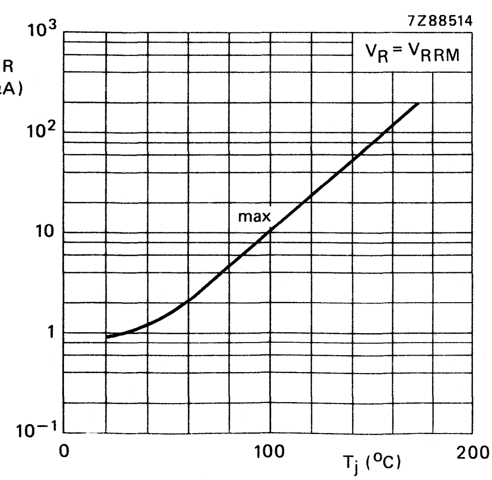


Fig. 9 Reverse current as a function of junction temperature. $V_R = V_{RRMmax}$.

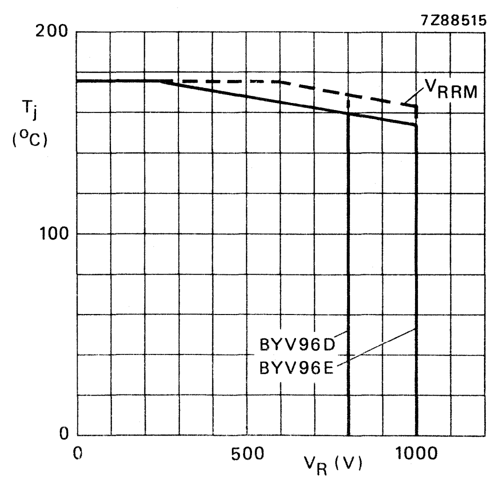


Fig. 10 Maximum values junction temperature.

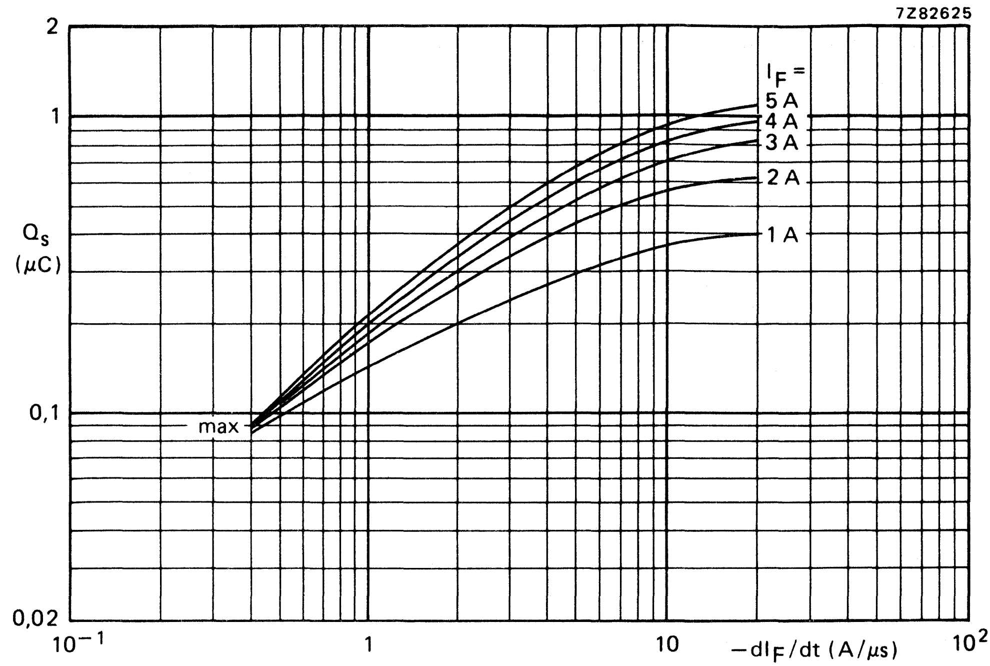


Fig. 11 Maximum values; T_j = 25 ^oC (see also Fig. 4).

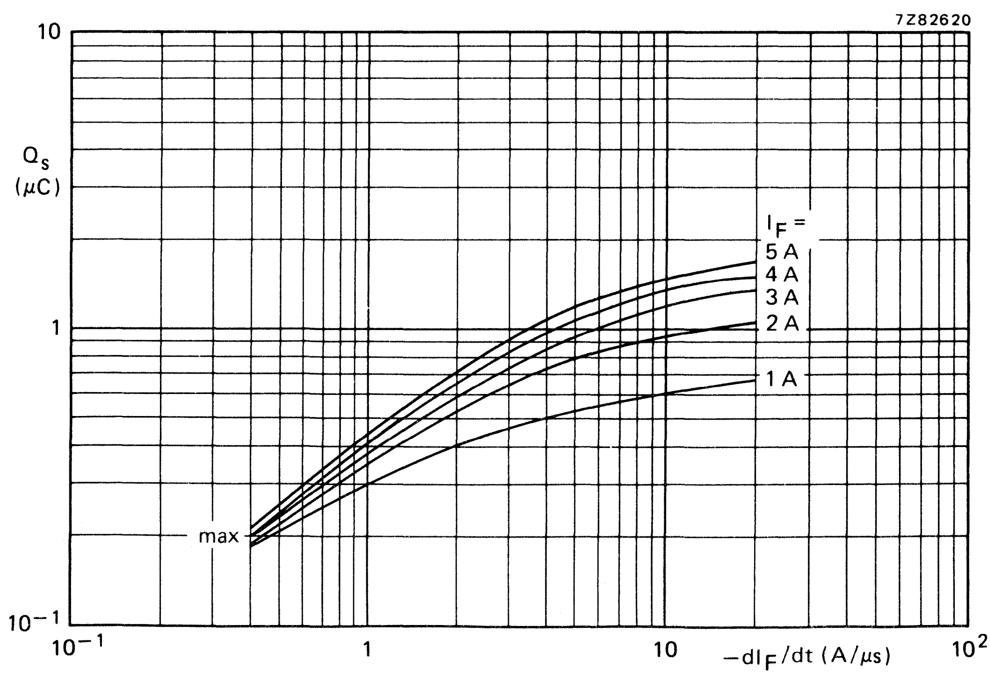


Fig. 12 Maximum values; T_j = 140 ^oC (see also Fig. 4).

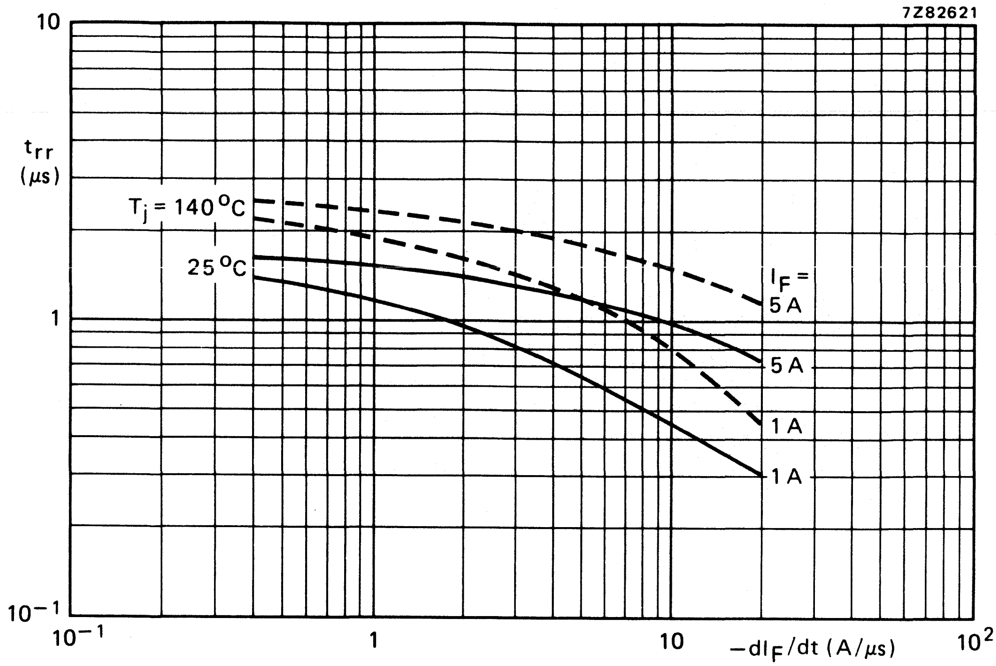


Fig. 13 Maximum values (see also Fig. 4).

CONTROLLED AVALANCHE RECTIFIER DIODES

Double-diffused glass passivated rectifier diodes in hermetically sealed axial-leaded glass envelopes, capable of absorbing reverse transients.

They are intended for rectifier applications in colour television circuits as well as general purpose applications in telephony equipment.

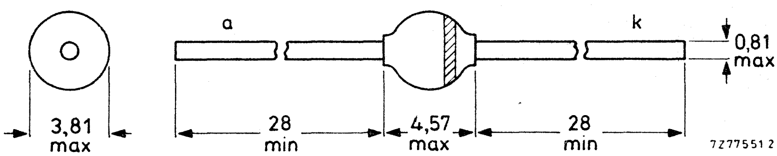
QUICK REFERENCE DATA

			BYW54	BYW55	BYW56	
Crest working reverse voltage	V_{RWM}	max.	600	800	1000	V
Reverse avalanche breakdown voltage	$V_{(BR)R}$	>	650	900	1100	V
		<	1000	1300	1600	V
Average forward current	$I_{F(AV)}$	max.	2	2	2	A
Non-repetitive peak forward current	I_{FSM}	max.		50		A
Non-repetitive peak reverse power dissipation	P_{RSM}	max.		1		kW
Junction temperature	T_j	max.		175		°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-57.



The marking band indicates the cathode.

Products approved to CECC 50 008-015 available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYW54	BYW55	BYW56	
Crest working reverse voltage	V_{RWM}	max.	600	800	1000	V
Continuous reverse voltage (Fig. 9)	V_R	max.	600	800	1000	V
Average forward current (averaged over any 20 ms period); T_{tp} = 35 °C; lead length 10 mm	$I_{F(AV)}$	max.		2		A
T_{amb} = 75 °C; Fig. 2 mounting	$I_{F(AV)}$	max.		0,8		A
Repetitive peak forward current	I_{FRM}	max.		12		A
Non-repetitive peak forward current (Figs 7 and 12) t = 10 ms, half sinewave	I_{FSM}	max.		50		A
Non-repetitive peak reverse power dissipation (t = 20 μs; half sine-wave); $T_j = T_{j\,max}$ prior to surge	P_{RSM}	max.		1		kW
Non-repetitive peak reverse avalanche mode pulse energy; I_R = 1 A; $T_j = T_{j\,max}$ prior to surge; with inductive load switched off	E_{RSM}	max.		20		mJ
Storage temperature	T_{stg}			−65 to +175		°C
Junction temperature	T_j	max.		175		°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm — $R_{th\,j\text{-}tp}$ = 46 K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ⩾ 40 μm; Fig. 2 (see "Thermal model") — $R_{th\,j\text{-}a}$ = 100 K/W

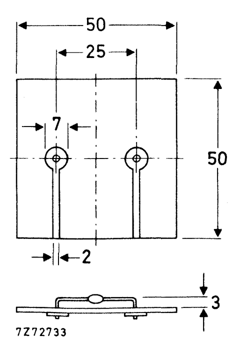


Fig. 2 Device mounted on a printed circuit board.

CHARACTERISTICS

			BYW54	BYW55	BYW56	
Forward voltage; $T_j = 25\ ^oC$ *						
$I_F = 1$ A	V_F	<	1	1	1	V
$I_F = 10$ A	V_F	<	1,65	1,65	1,65	V
Reverse avalanche breakdown voltage						
$I_R = 0,1$ mA; $T_j = 25\ ^oC$	$V_{(BR)R}$	>	650	900	1100	V
		<	1000	1300	1600	V
Reverse current						
$V_R = V_{RWM\ max}$; $T_j = 25\ ^oC$**	I_R	<		1,0		μA
$V_R = V_{RWM\ max}$; $T_j = 100\ ^oC$	I_R	<		10		μA
Reverse recovery charge when switched from $I_F = 1$ A to $V_R \geq 30$ V with $-dI_F/dt = 5$ A/μs; $T_j = 25\ ^oC$	Q_s	typ.		3		μC
Reverse recovery time when switched from $I_F = 1$ A to $V_R \geq 30$ V with $-dI_F/dt = 5$ A/μs; $T_j = 25\ ^oC$	t_{rr}	typ.		2,5		μs
Diode capacitance						
$V_R = 0$ V; f = 1 MHz; $T_j = 25\ ^oC$	C_d	typ.		50		pF

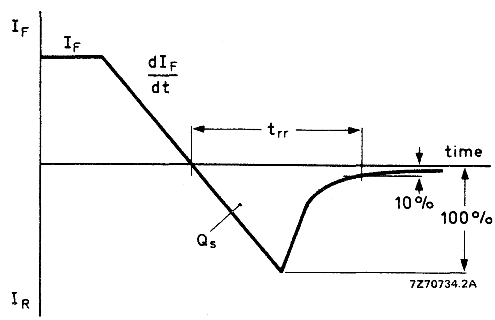


Fig. 3 Definitions of t_{rr} and Q_s.

* Measured under pulse conditions to avoid excessive dissipation.
** Illuminance ≤ 500 lux (daylight); relative humidity < 65%.

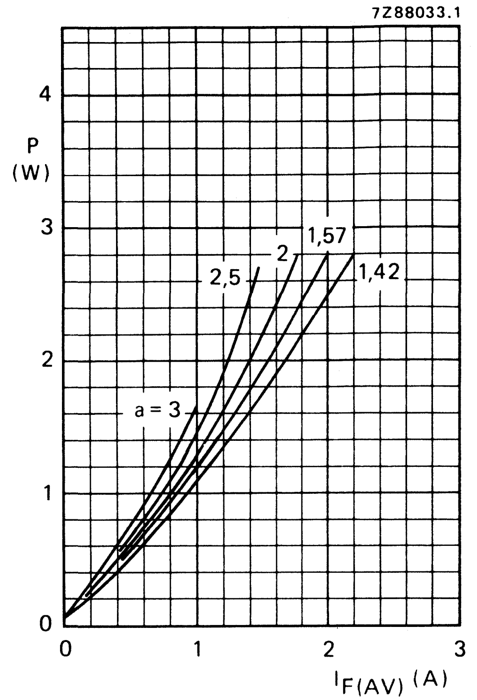


Fig. 4 Steady state power dissipation (forward plus leakage current excluding switching losses) as a function of the average forward current.

$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RWMmax}$.

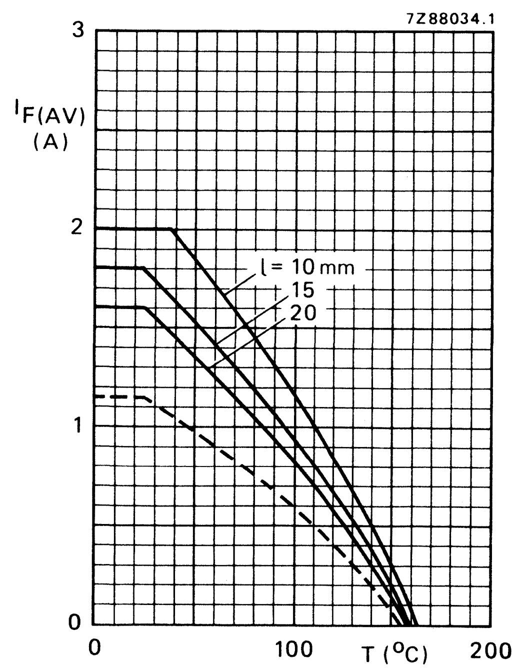


Fig. 5 Maximum average forward current as a function of the temperature. The curves include losses due to reverse current.

a = 1,57; $V_R = V_{RWMmax}$; l = lead length

——— T = tie-point temperature

– – – – T = ambient temperature and device mounted as shown in Fig. 2.

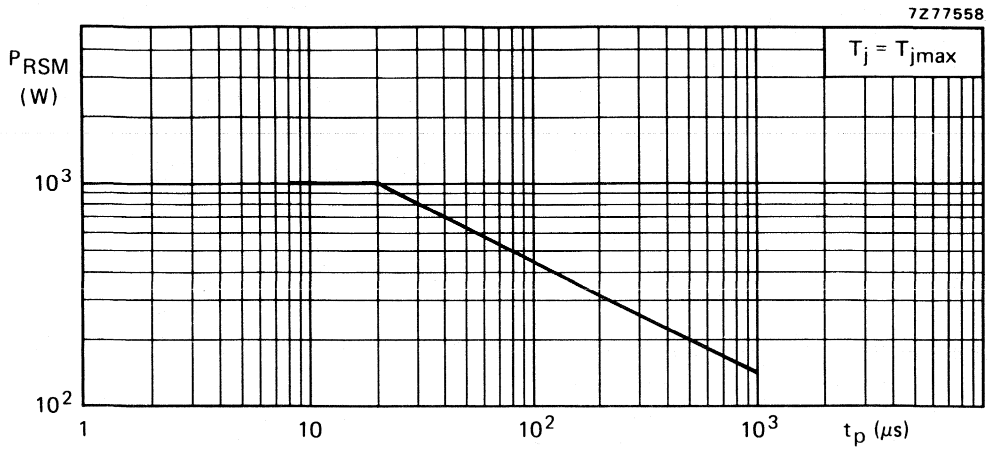
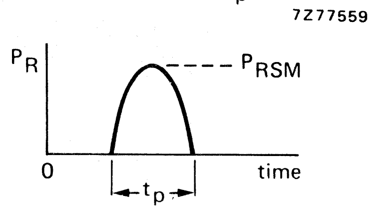


Fig. 6 Maximum permissible non-repetitive peak reverse power dissipation in the avalanche region.



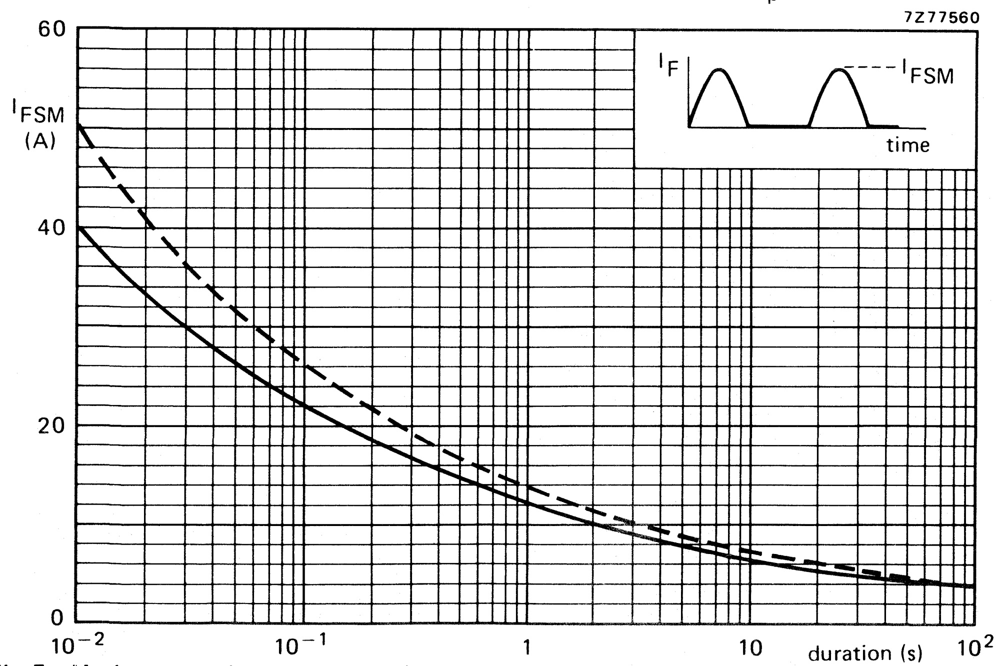


Fig. 7 Maximum permissible non-repetitive peak forward current based on sinusoidal currents (f = 50 Hz) ·

– – – – – T_j = 25 °C; V_R = 0.

——— $T_j = T_{j\,max}$ prior to surge; $V_R = V_{RWM\,max}$.

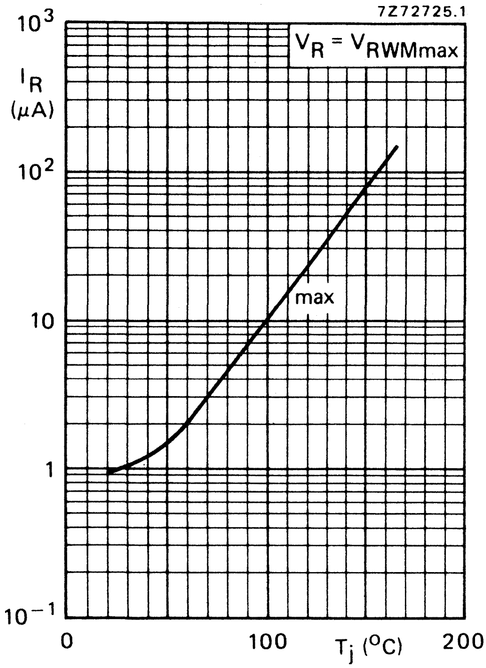


Fig. 8.

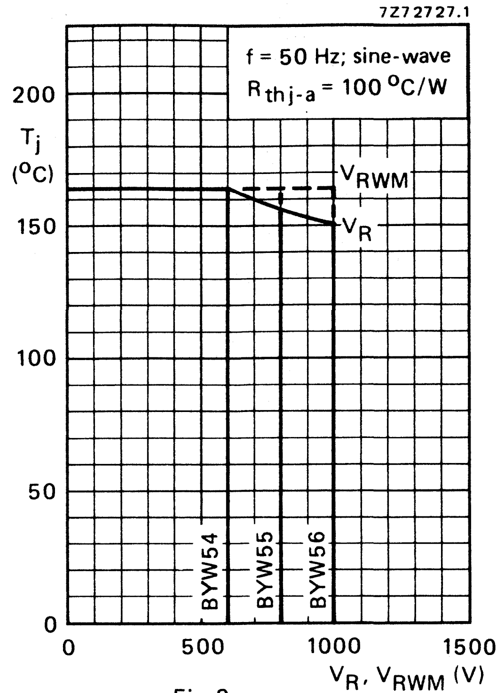


Fig. 9.

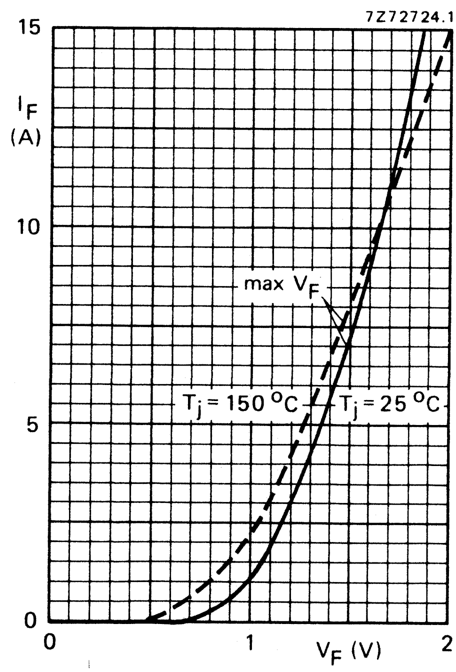


Fig. 10.

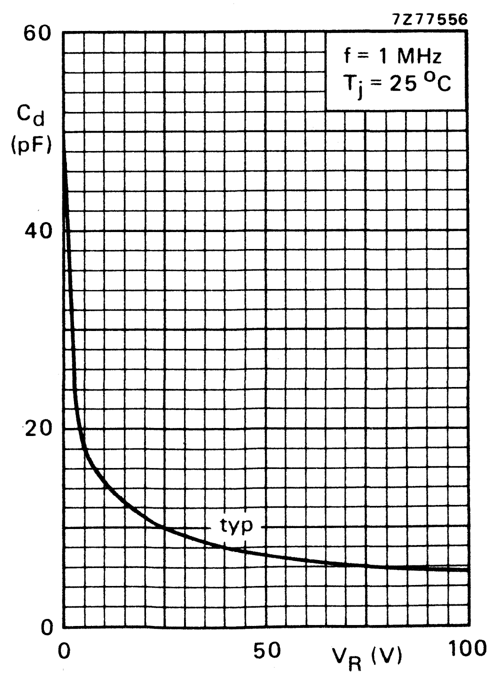


Fig. 11.

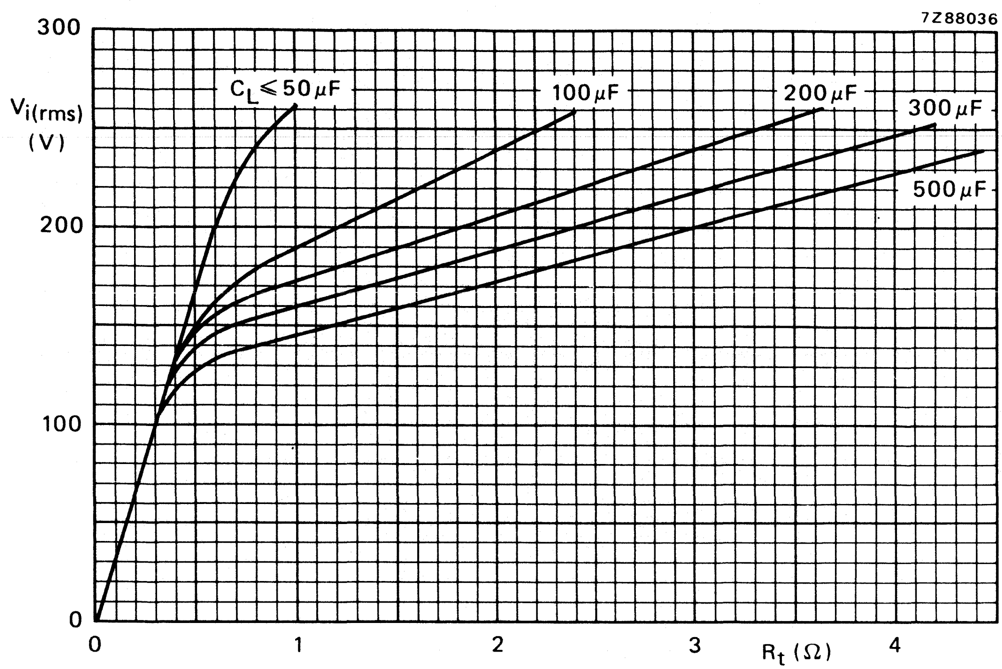


Fig. 12 Minimum values of series resistance (R_t), including the transformer resistance, required to limit the initial peak rectifier current with capacitive load. The possibility of the following spreads are taken into account: mains voltage + 10%; capacitance + 50%, resistance −10%.

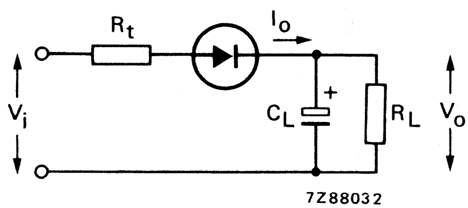


Fig. 13 Test circuit series resistance (R_t).

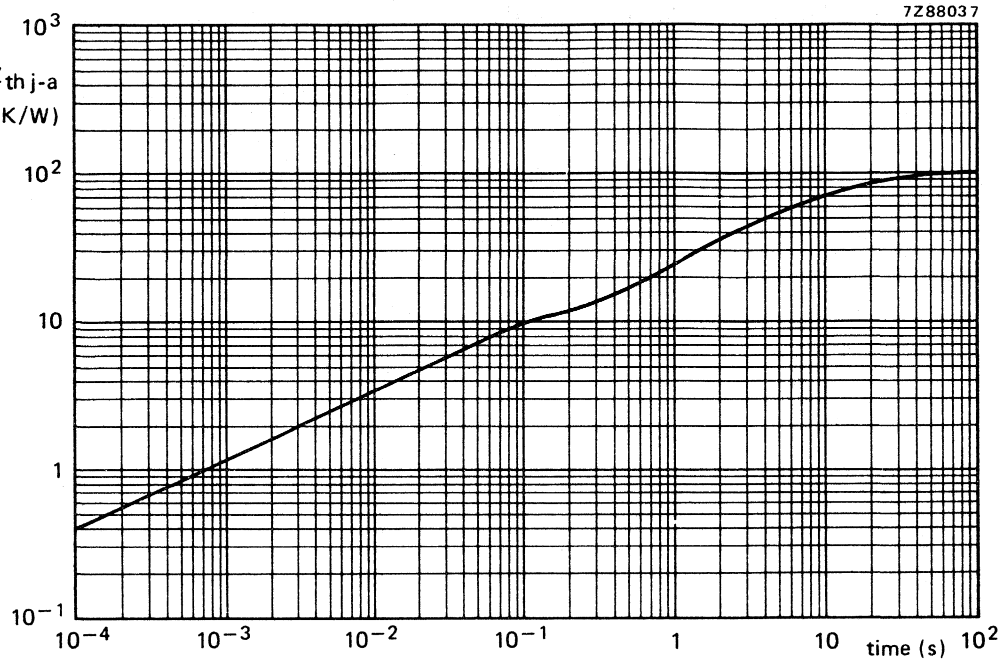


Fig. 14.
Device mounted on a printed circuit board (see Fig. 2).

AVALANCHE FAST SOFT-RECOVERY RECTIFIER DIODES

Glass passivated rectifier diodes in hermetically sealed axial-leaded glass envelopes. They are intended for television and industrial applications, such as switched-mode power supplies, scan rectifiers, in TV receivers, and also for use in inverter and converter applications. The devices feature non-snap-off (soft-recovery) switching characteristics and are capable of absorbing reverse transient energy (e.g. during flashover in the picture tube).

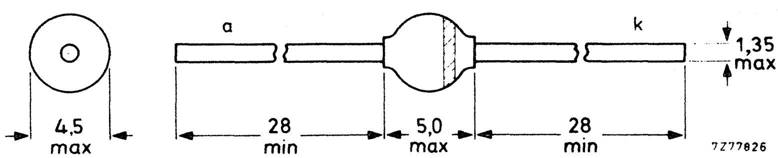
QUICK REFERENCE DATA

			BYW95A	B	C	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	V
Continuous reverse voltage	V_R	max.	200	400	600	V
Average forward current	$I_{F(AV)}$	max.		3		A
Non-repetitive peak forward current	I_{FSM}	max.		70		A
Non-repetitive peak reverse energy	E_{RSM}	max.		10		mJ
Reverse recovery time	t_{rr}	<		250		ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-64.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYW95A	B	C	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	V
Continuous reverse voltage	V_R	max.	200	400	600	V
Average forward current (averaged over any 20 ms period)						
T_{tp} = 60 °C; lead length 10 mm	$I_{F(AV)}$	max.		3		A
T_{amb} = 65 °C; Fig. 2	$I_{F(AV)}$	max.		1,25		A
Repetitive peak forward current	I_{FRM}	max.		15		A
Non-repetitive peak forward current (t = 10 ms; half sine-wave) $T_j = T_{j\,max}$ prior to surge; $V_R = V_{RRMmax}$	I_{FSM}	max.		70		A
Non-repetitive peak reverse avalanche energy; I_R = 400 mA; $T_j = T_{j\,max}$ prior to surge; with inductive load switched off	E_{RSM}	max.		10		mJ
Storage temperature	T_{stg}			−65 to + 175		°C
Operating junction temperature	T_j	max.		175		°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\,j\text{-}tp}$	=	25	K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ⩾ 40 μm; Fig. 2 (see "Thermal model")	$R_{th\,j\text{-}a}$	=	75	K/W

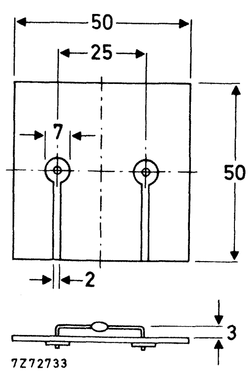


Fig. 2 Mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYW95A	B	C	
Forward voltage						
I_F = 5 A	V_F	<	1,5	1,5	1,5	V *
I_F = 5 A; $T_j = T_{j\,max}$	V_F	<	1,25	1,25	1,25	V *
Reverse avalanche breakdown voltage						
I_R = 0,1 mA	$V_{(BR)R}$	>	300	500	700	V
Reverse current						
$V_R = V_{RRMmax}$; T_j = 165°	I_R	<		150		μA
Reverse recovery when switched from I_F = 1 A to $V_R \geqslant$ 30 V with $-dI_F/dt$ = 20 A/μs						
recovered charge	Q_s	<		250		nC
recovery time	t_{rr}	<		250		ns
Maximum slope of reverse recovery current when switched from I_F = 1 A to $V_R \geqslant$ 30 V with $-dI_F/dt$ = 1 A/μs	$\lvert dI_R/dt \rvert$	<		6		A/μs

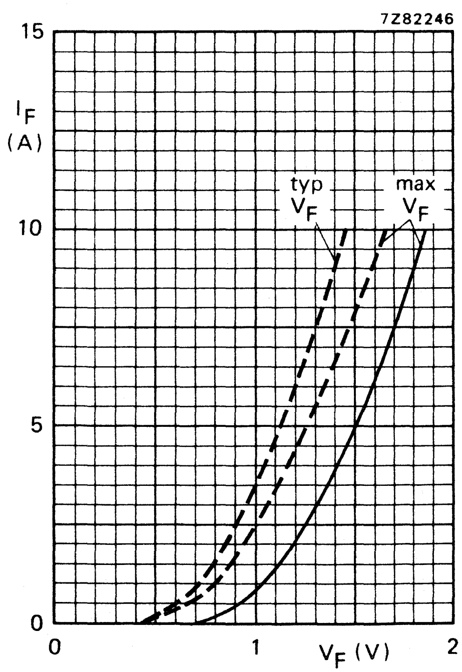


Fig. 3 —— T_j = 25 °C; – – – $T_j = T_{j\,max}$.

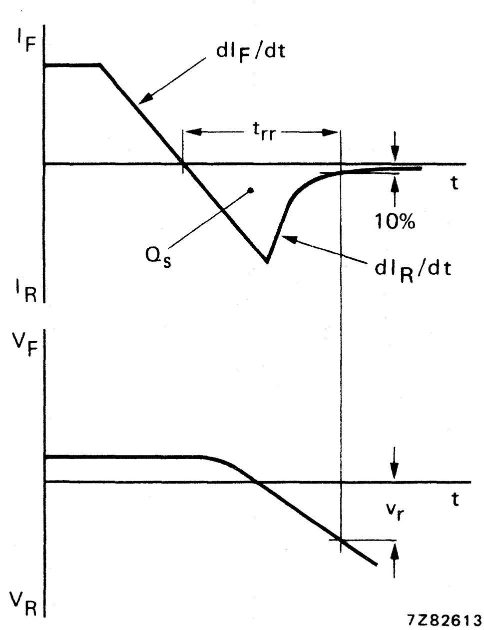


Fig. 4 Definitions.

* Measured under pulse conditions to avoid excessive dissipation.

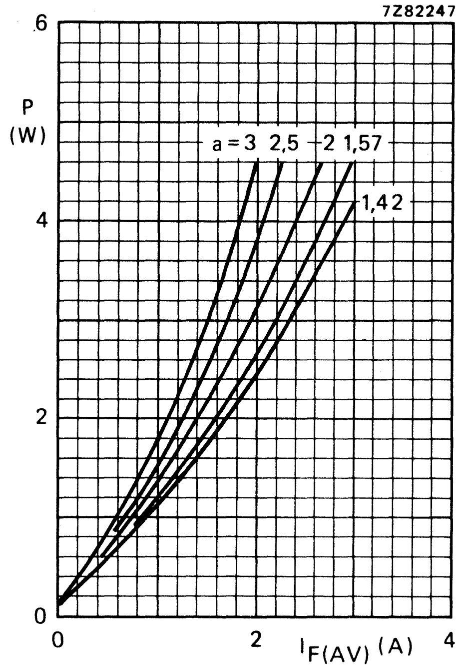


Fig. 5.

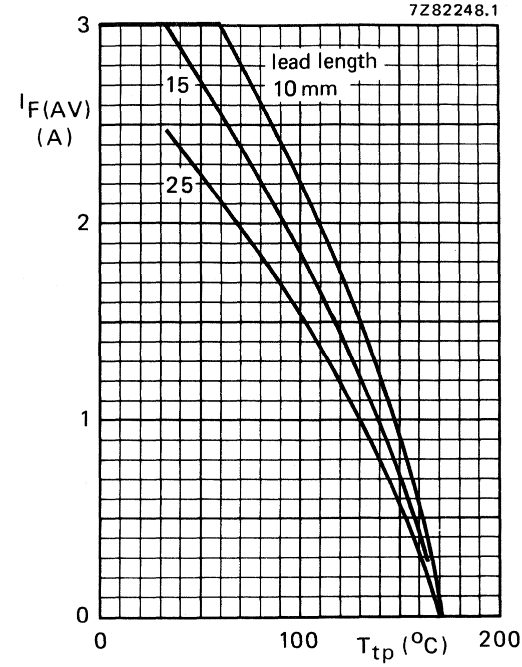


Fig. 6.

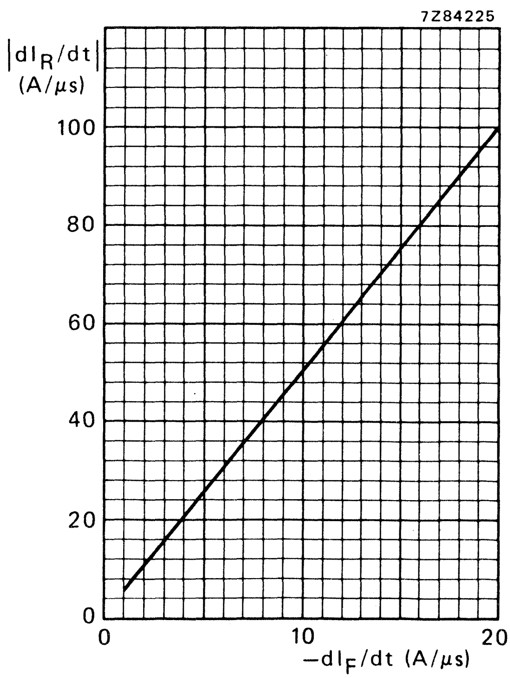


Fig. 7.

Fig. 5 Steady state power dissipation (forward plus leakage current) excluding switching losses as a function of the average forward current.

The graph is for switched-mode application.

$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$

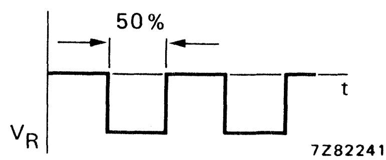


Fig. 6 Maximum average forward current as a function of the tie-point temperature; the curves include losses due to reverse leakage.

The graph is for switched-mode application; $V_R = V_{RRMmax}$; $\delta = 50\%$; a = 1,57.

Fig. 7 Maximum slope of reverse recovery current. $T_j = 25\ ^{\circ}C$.

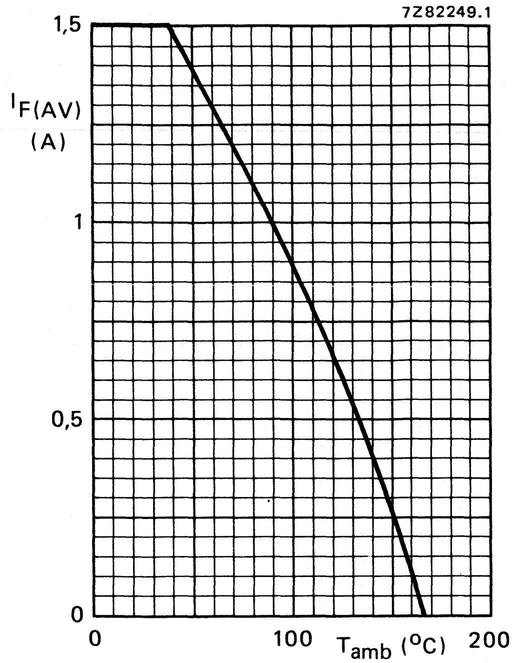


Fig. 8 Maximum average forward current as a function of the ambient temperature; the curve includes losses due to reverse leakage.
Mounting method see Fig. 2.

The graph is for switched-mode application; $V_R = V_{RRMmax}$; δ = 50%; a = 1,57.

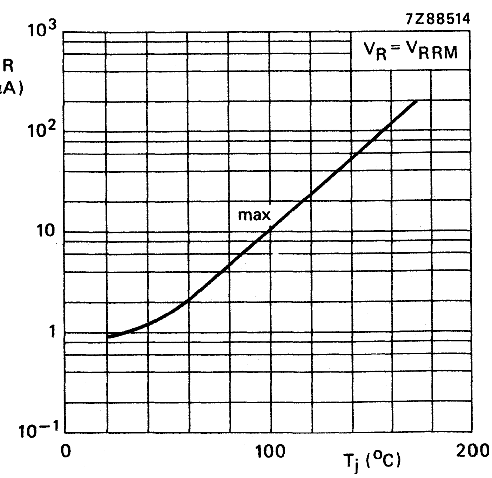


Fig. 9 Reverse current as a function of junction temperature. $V_R = V_{RRM\,max}$.

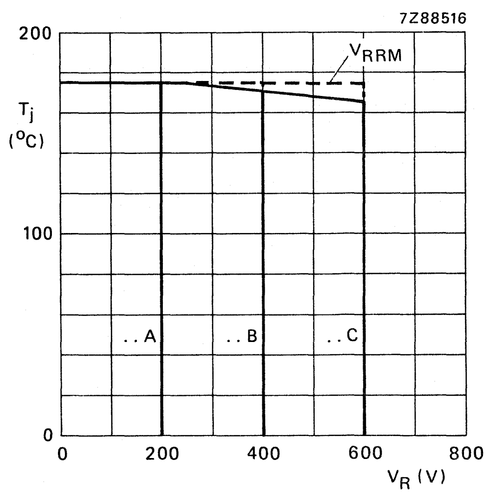


Fig. 10 Maximum values junction temperature as a function of reverse voltage.

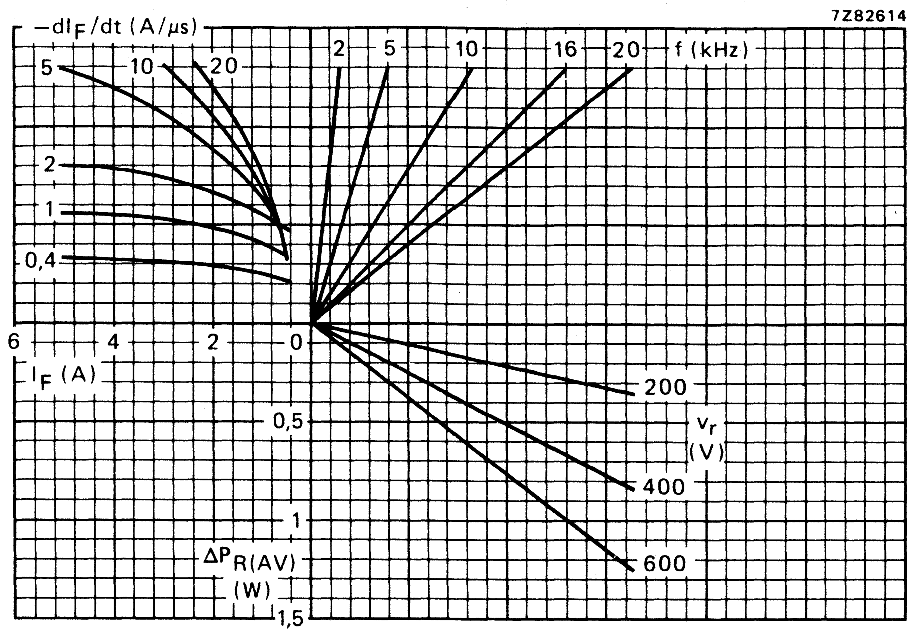


Fig. 11 Nomogram: power loss ($\Delta P_{R(AV)}$) due to switching only. To be added to steady state power losses (see also Fig. 4).

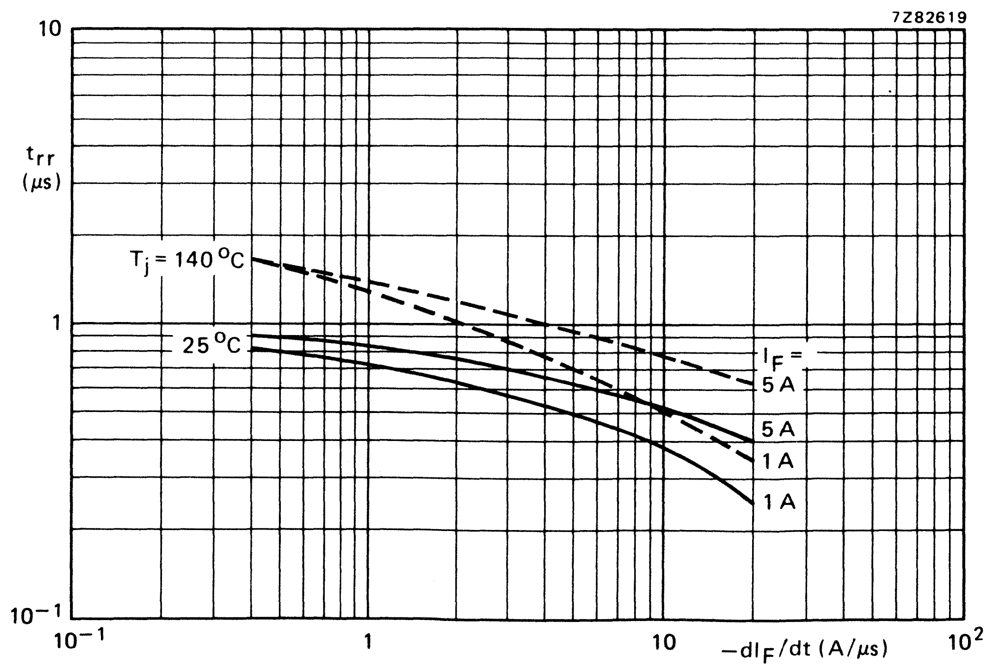


Fig. 12 Maximum values; for definitions see Fig. 4.

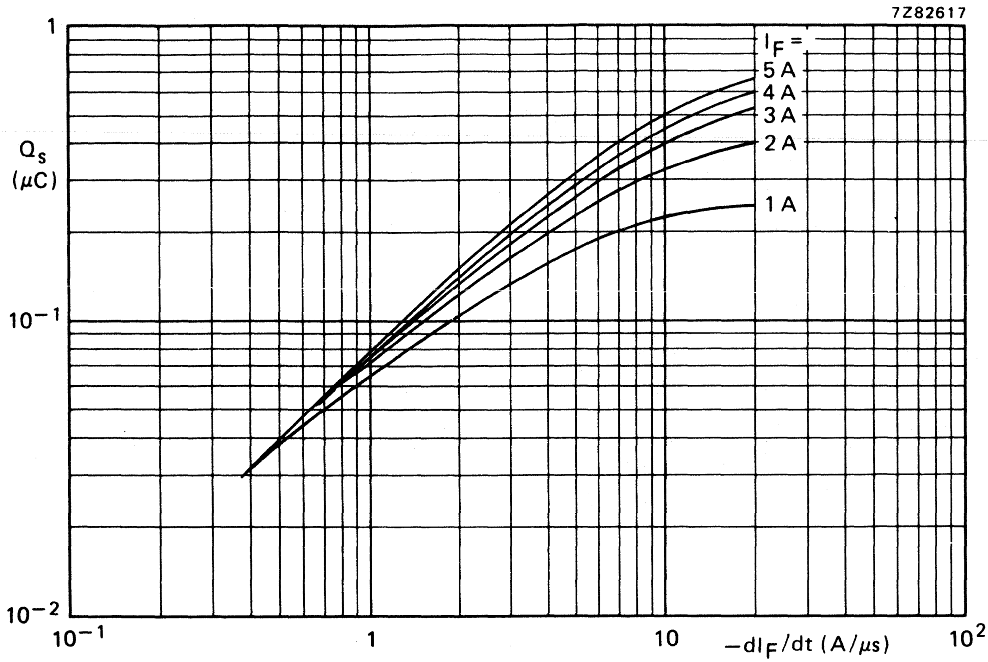


Fig. 13 Maximum values; T_j = 25 °C. For definitions see Fig. 4.

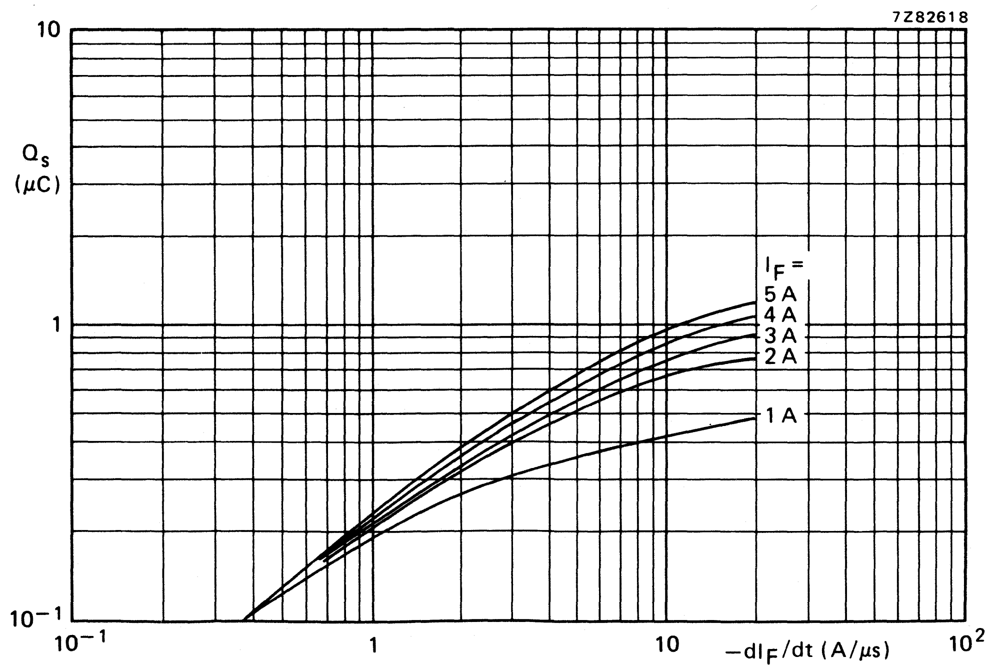


Fig. 14 Maximum values; T_j = 140 °C. For definitions see Fig. 4.

AVALANCHE FAST SOFT-RECOVERY RECTIFIER DIODES

Glass passivated rectifier diodes in hermetically sealed axial-leaded glass envelopes. They are intended for television and industrial applications, such as switched-mode power supplies, scan rectifiers, in TV receivers, and also for use in inverter and converter applications. The devices feature non-snap-off (soft-recovery) switching characteristics and are capable of absorbing reverse transient energy (e.g. during flashover in the picture tube).

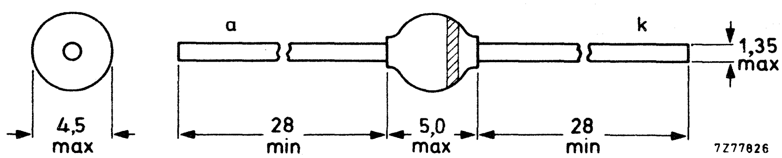
QUICK REFERENCE DATA

			BYW96D	BYW96E	
Repetitive peak reverse voltage	V_{RRM}	max.	800	1000	V
Continuous reverse voltage	V_R	max.	800	1000	V
Average forward current	$I_{F(AV)}$	max.	3		A
Non-repetitive peak forward current	I_{FSM}	max.	70		A
Non-repetitive peak reverse energy	E_{RSM}	max.	10		mJ
Reverse recovery time	t_{rr}	<	300		ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-64.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYW96D	BYW96E	
Repetitive peak reverse voltage	V_{RRM}	max.	800	1000	V
Continuous reverse voltage	V_R	max.	800	1000	V
Average forward current (averaged over any 20 ms period)					
T_{tp} = 50 °C; lead length 10 mm	$I_{F(AV)}$	max.	3		A
T_{amb} = 55 °C; Fig. 2	$I_{F(AV)}$	max.	1,25		A
Repetitive peak forward current	I_{FRM}	max.	15		A
Non-repetitive peak forward current (t = 10 ms; half sine-wave) $T_j = T_{j\,max}$ prior to surge; $V_R = V_{RRMmax}$	I_{FSM}	max.	70		A
Non-repetitive peak reverse avalanche energy; I_R = 400 mA; $T_j = T_{j\,max}$ prior to surge; with inductive load switched off	E_{RSM}	max.	10		mJ
Storage temperature	T_{stg}		−65 to + 175		°C
Operating junction temperature	T_j	max.	175		°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm — $R_{th\,j\text{-}tp}$ = 25 K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ⩾ 40 μm; Fig. 2 (see "Thermal model") — $R_{th\,j\text{-}a}$ = 75 K/W

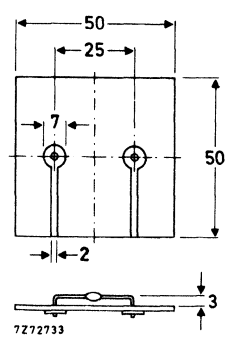


Fig. 2 Mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYW96D	BYW96E	
Forward voltage					
I_F = 5 A	V_F	<	1,5	1,5	V *
I_F = 5 A; $T_j = T_{j\,max}$	V_F	<	1,25	1,25	V *
Reverse avalanche breakdown voltage					
I_R = 0,1 mA	$V_{(BR)R}$	>	900	1100	V
Reverse current					
$V_R = V_{RRMmax}$; T_j = 165 °C	I_R	<	150		μA
Reverse recovery when switched from I_F = 1 A to $V_R \geq 30$ V with $-dI_F/dt$ = 20 A/μs					
recovered charge	Q_s	<	400		nC
recovery time	t_{rr}	<	300		ns
Maximum slope of reverse recovery current when switched from I_F = 1 A to $V_R \geq 30$ V with $-dI_F/dt$ = 1 A/μs	$\lvert dI_R/dt \rvert$	<	5		A/μs

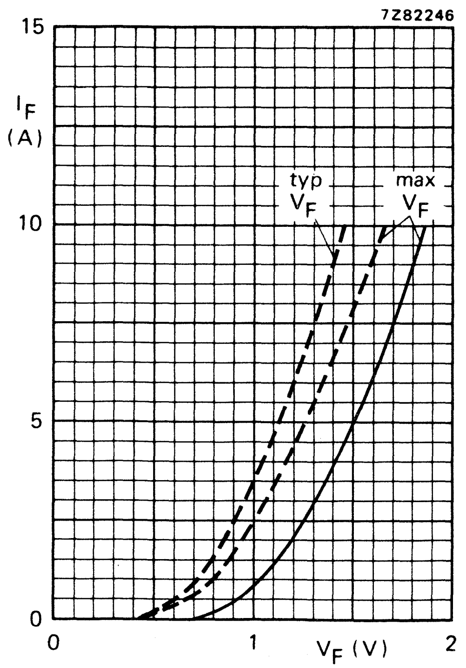


Fig. 3 —— T_j = 25 °C; – – – $T_j = T_{j\,max}$

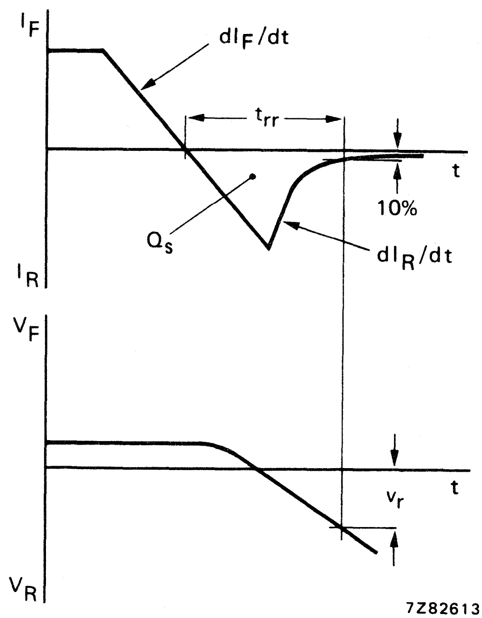


Fig. 4 Definitions.

* Measured under pulse conditions to avoid excessive dissipation.

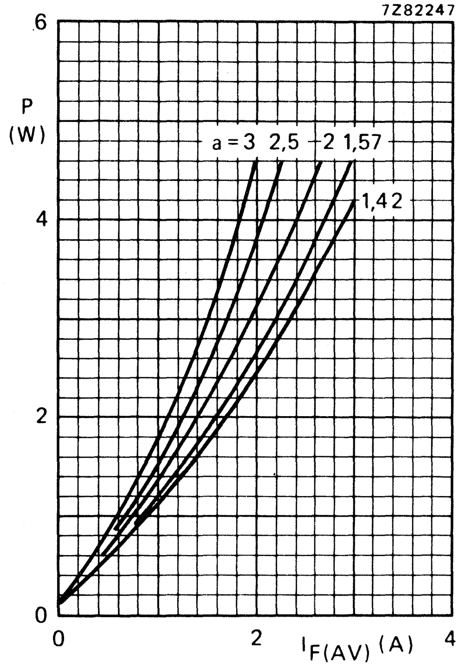
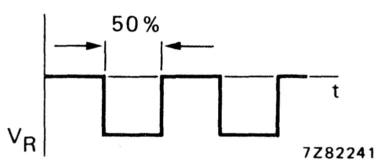


Fig. 5 Steady state power dissipation (forward plus leakage current) excluding switching losses as a function of the average forward current.

The graph is for switched-mode application.

$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$



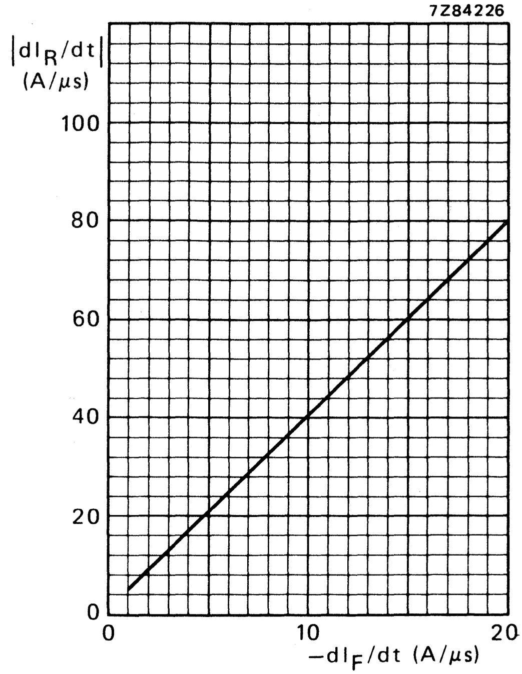


Fig. 6 Maximum slope of reverse recovery current. $T_j = 25\ ^oC$.

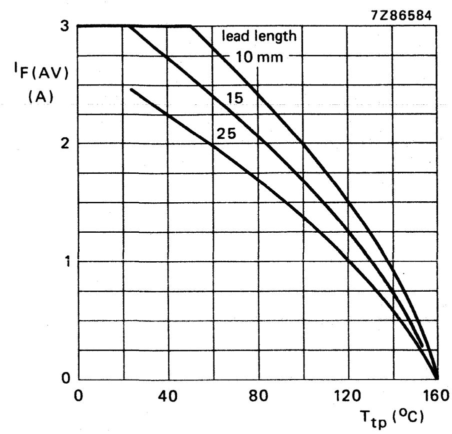


Fig. 7 Maximum average forward current as a function of the tie-point temperature; the curves include losses due to reverse leakage.

The graph is for switched-mode application; $V_R = V_{RRMmax}$; δ = 50%; a = 1,57 .

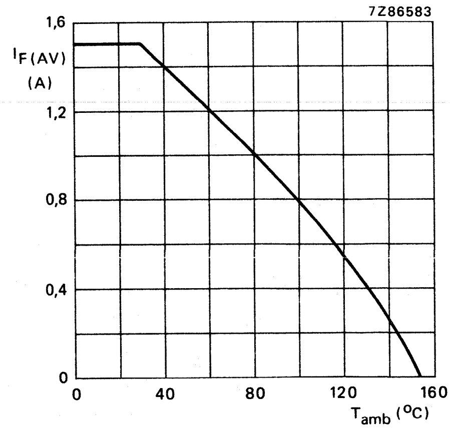


Fig. 8 Maximum average forward current as a function of the ambient temperature; the curve includes losses due to reverse leakage. Mounting method see Fig. 2.

The graph is for switched-mode application; $V_R = V_{RRMmax}$; δ = 50%; a = 1,57.

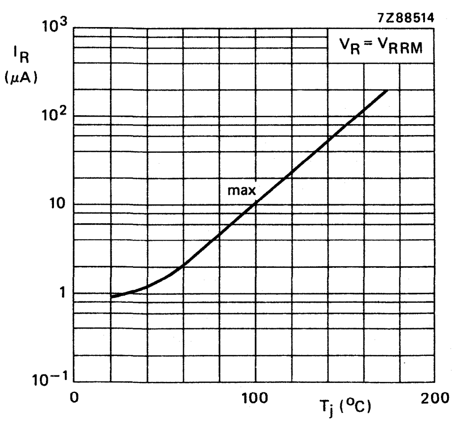


Fig. 9 Reverse current as a function of junction temperature. $V_R = V_{RRM\ max}$.

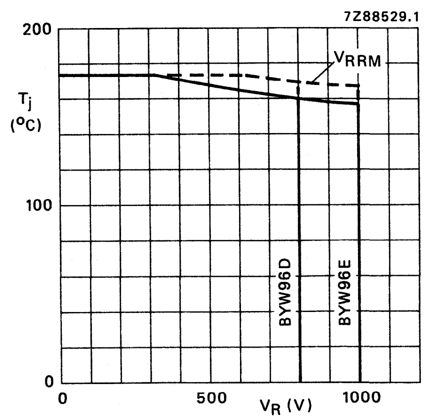


Fig. 10 Maximum values junction temperature as a function of reverse voltage.

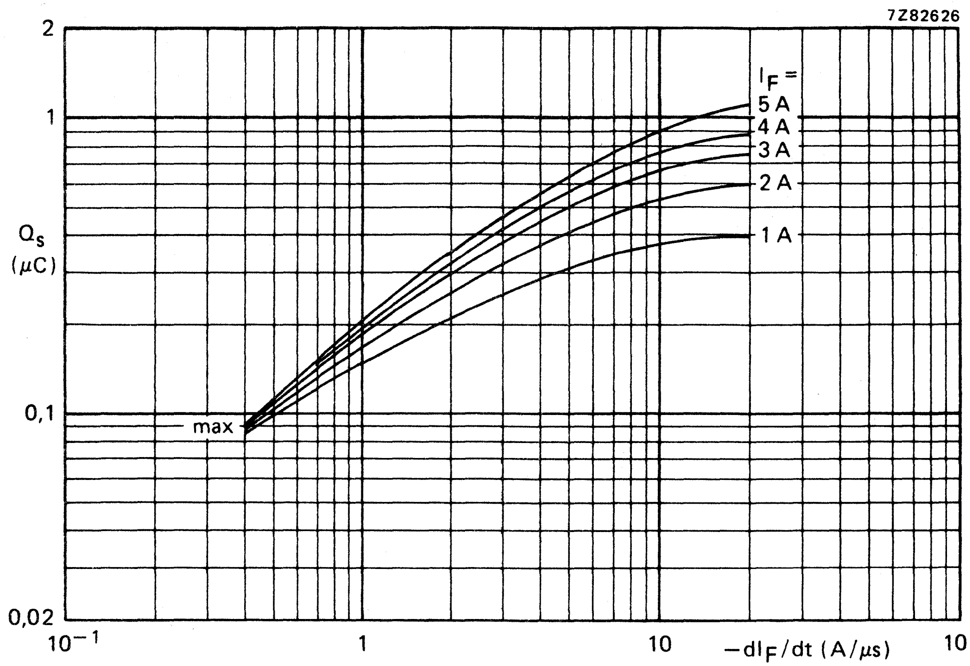


Fig. 11 Maximum values at T_j = 25 °C (see also Fig. 4).

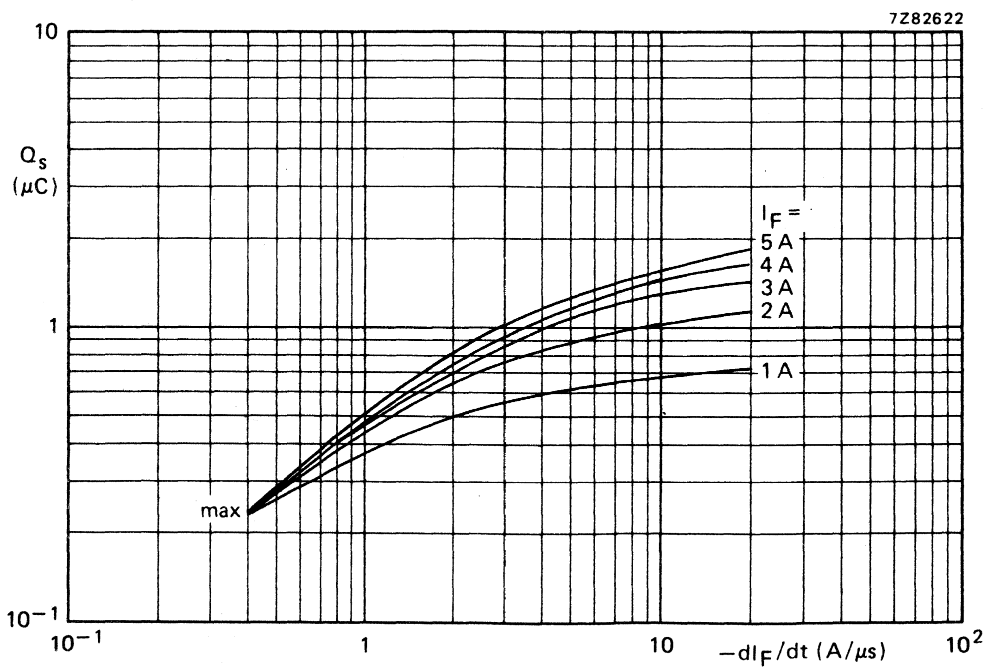


Fig. 12 Maximum values at T_j = 140 °C (see also Fig. 4).

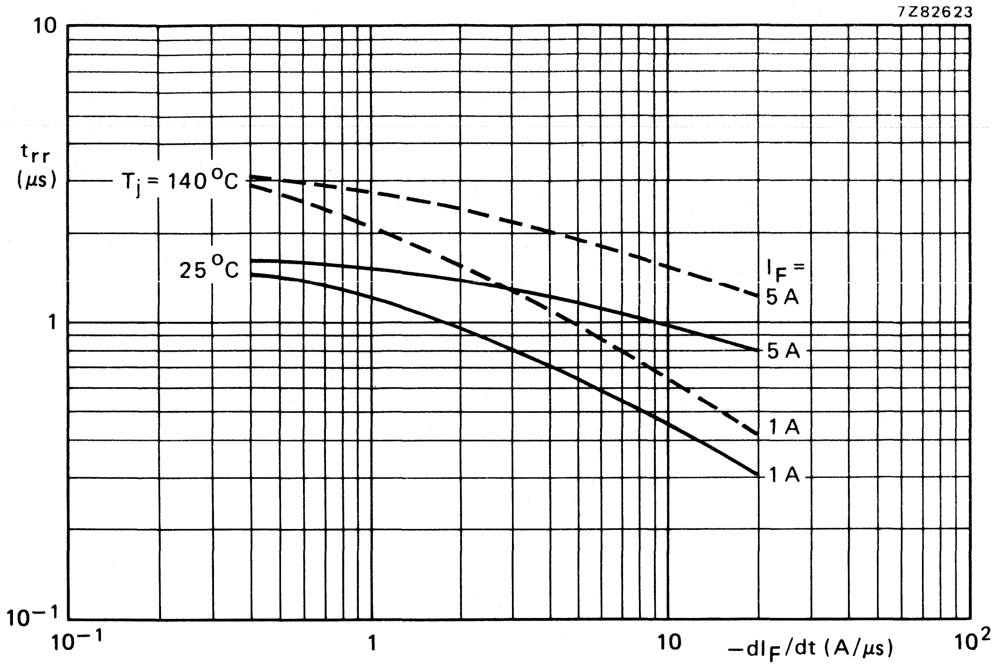


Fig. 13 Maximum values. For definitions see Fig. 4.

RECTIFIER DIODE

Double-diffused glass-passivated rectifier diode in hermetically sealed axial-leaded glass envelope, intended for use in general industrial applications where a high repetitive peak reverse voltage is required.

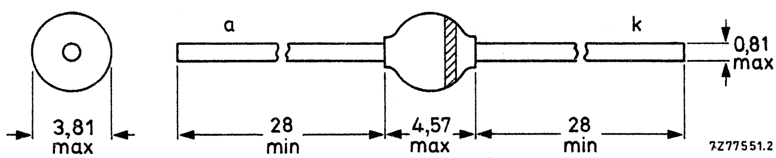
QUICK REFERENCE DATA

Crest working reverse voltage	V_{RWM}	max.	800	V
Repetitive peak reverse voltage	V_{RRM}	max.	1600	V
Average forward current	$I_{F(AV)}$	max.	1,2	A
Non-repetitive peak forward current	I_{FSM}	max.	25	A
Junction temperature	T_j	max.	175	°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-57.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Crest working reverse voltage	V_{RWM}	max.	800	V
Repetitive peak reverse voltage ($\delta \leq 1\%$)	V_{RRM}	max.	1600	V
Average forward current (averaged over any 20 ms period);				
T_{tp} = 50 °C; lead length 10 mm	$I_{F(AV)}$	max.	1,2	A
T_{amb} = 60 °C; see Fig. 2	$I_{F(AV)}$	max.	0,6	A
Repetitive peak forward current	I_{FRM}	max.	5	A
Non-repetitive peak forward current t = 10 ms, half-sine wave; $T_j = T_{jmax}$ prior to surge; $V_R = V_{RWMmax}$	I_{FSM}	max.	25	A
Storage temperature	T_{stg}		−65 to +175	°C
Junction temperature	T_j	max.	175	°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\ j\text{-}tp}$	=	46	K/W
2. Thermal resistance from junction to ambient; device mounted on an 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness $\geq$ 40 μm; Fig. 2 (See „Thermal model”)	$R_{th\ j\text{-}a}$	=	100	K/W

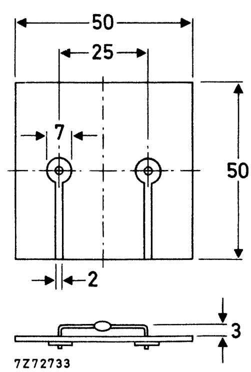


Fig. 2 Device mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage *			
I_F = 2 A	V_F	<	1,5 V
Reverse current			
$V_R = V_{RWMmax}$	I_R	<	1 μA
$V_R = V_{RWMmax}$; T_j = 150 °C	I_R	<	200 μA

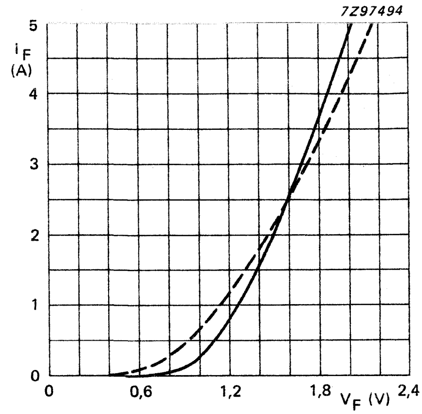


Fig. 3 Maximum forward voltage at ——— T_j = 25 °C; ------ T_j = 175 °C.

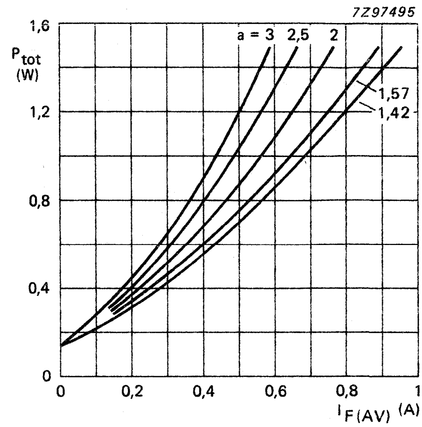


Fig. 4 Maximum steady state power dissipation (forward plus leakage current) versus average forward current.

a $= I_{F(RMS)}/I_{F(AV)}$;
$V_R = V_{RWMmax}$, δ = 0,5.

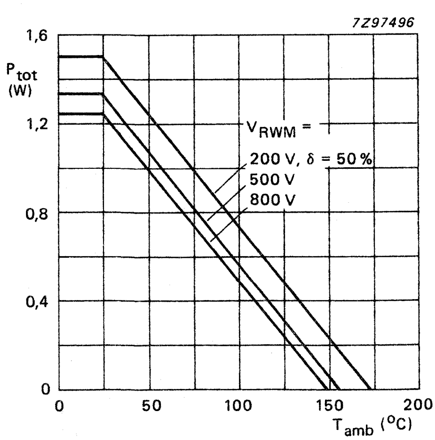


Fig. 5 Maximum steady state power dissipation (forward plus leakage current) versus ambient temperature.

a $= I_{F(RMS)}/I_{F(AV)}$;
$V_R = V_{RWMmax}$, δ = 0,5.

* Measured under pulse conditions to avoid excessive dissipation.

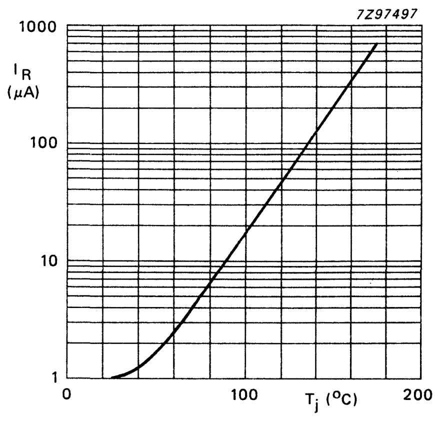


Fig. 6 Maximum reverse current versus junction temperature; $V_R = V_{RWMmax}$.

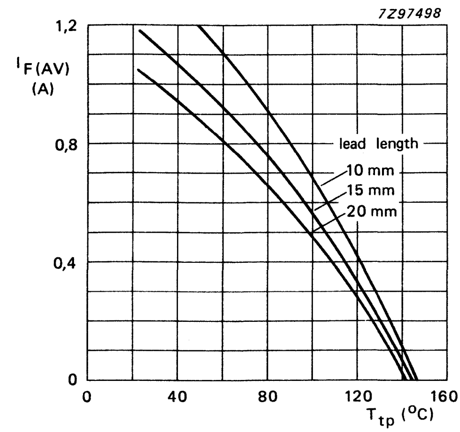


Fig. 7 Maximum average forward current vs. tie-point temperature; the curves include losses due to reverse leakage.
$V_R = V_{RWMmax}$; a = 1,57.

E.H.T. AVALANCHE FAST SOFT-RECOVERY DIODE *

E.H.T. rectifier diode in glass envelope intended for general purpose high-voltage rectifying and also designed as sub-component for very high voltage stacks, for example, in X-ray equipment with frequencies up to 20 kHz and in radar apparatus and microwave ovens.

Because of the smallness of the envelope, the diodes should be used in a suitable insulating medium (resin, oil or special arrangements in test cases).

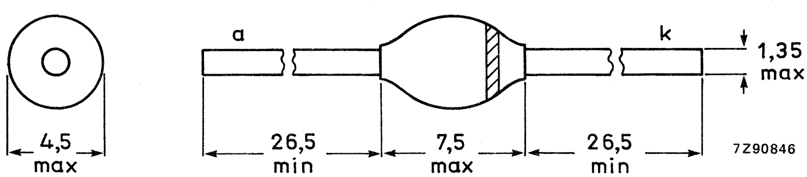
QUICK REFERENCE DATA

Crest working reverse voltage	V_{RWM}	max.	6 kV
Repetitive peak reverse voltage	V_{RRM}	max.	7,5 kV
Average forward current up to T_{oil} = 45 °C	$I_{F(AV)}$	max.	550 mA
Non-repetitive peak forward current	I_{FSM}	max.	20 A
Non-repetitive peak reverse power dissipation	P_{RSM}	max.	5 kW
Junction temperature	T_j	max.	165 °C
Reverse recovery time	t_{rr}	<	350 ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-83.



The marking band indicates the cathode.

*See also "Custom made E.H.T. stacks" in section "General".

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Crest working reverse voltage	V_{RWM}	max.	6 kV
Repetitive peak reverse voltage; $\delta \leqslant 0{,}01$	V_{RRM}	max.	7,5 kV
Non-repetitive peak reverse voltage; $t \leqslant 10$ ms	V_{RSM}	max.	8 kV
Average forward current (averaged over any 20 ms period) up to $T_{oil} = 45\ ^oC$; continuous operation	$I_{F(AV)}$	max.	550 mA
Repetitive peak forward current; intermittent operation	I_{FRM}	max.	5 A
Non-repetitive peak forward current; t = 10 ms, half-sinewave; $T_j = 165\ ^oC$ prior to surge	I_{FSM}	max.	20 A
Non-repetitive peak reverse power dissipation; t = 10 μs, triangular pulse; $T_j = 165\ ^oC$ prior to surge	P_{RSM}	max.	5 kW
Storage temperature	T_{stg}		−65 to +165 ^oC
Junction temperature	T_j	max.	165 ^oC

THERMAL RESISTANCE

From junction to oil	$R_{th\ j\text{-}o}$	=	20 K/W

CHARACTERISTICS

$T_j = 25\ ^oC$ unless otherwise specified

Forward voltage $I_F = 2$ A	V_F	<	14,5 V
Peak reverse current $V_R = 6$ kV; $T_j = 165\ ^oC$	I_R	<	50 μA
Reverse recovery time when switched from $I_F = 0{,}5$ A to $I_R = 1$ A; measured at $I_R = 0{,}25$ A	t_{rr}	<	350 ns

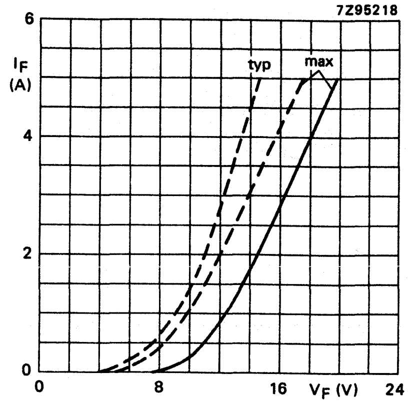


Fig. 2 ——— T_j = 25 °C
------------ T_j = 165 °C.

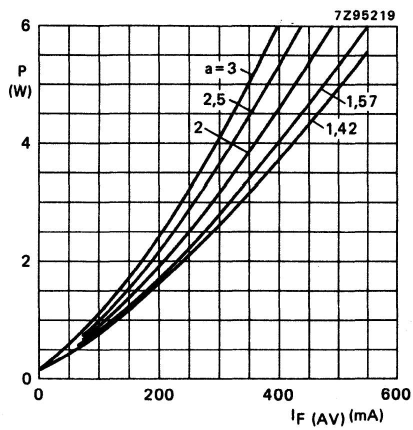


Fig. 3 Steady-state power dissipation (forward plus leakage current) versus average forward current; $V_R = V_{RWMmax}$; δ = 50%; $a = I_{F(RMS)}/I_{F(AV)}$.

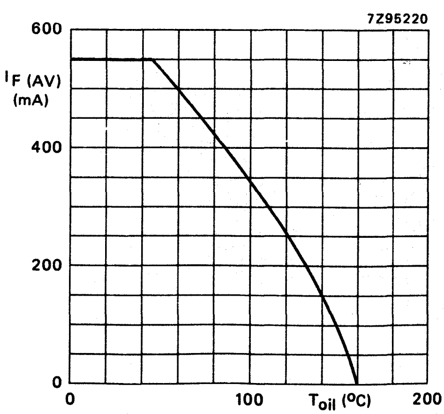


Fig. 4 Maximum average forward current versus oil temperature; curve includes losses due to reverse leakage; $V_R = V_{RWMmax}$; δ = 50%; a = 1,57.

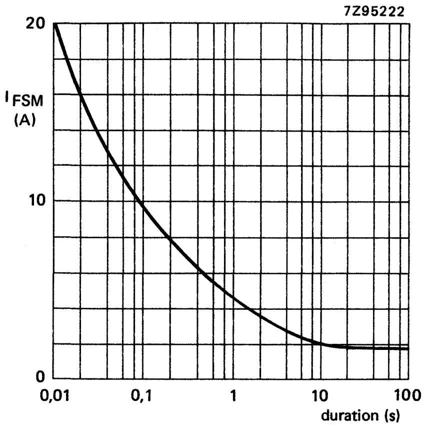
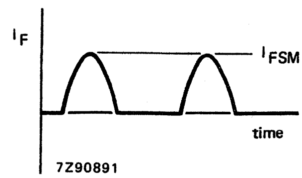


Fig. 5 Maximum permissible non-repetitive peak forward current based on sinusoidal currents (f = 50 Hz); $V_R = V_{RWMmax}$; T_j = 165 °C prior to surge.



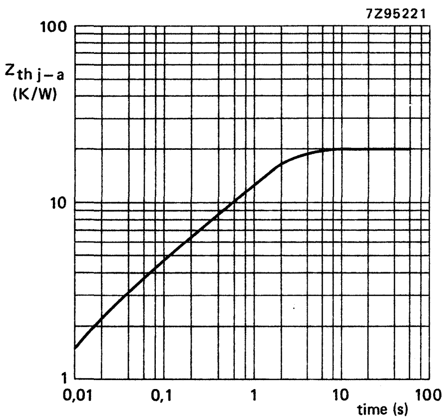


Fig. 6.

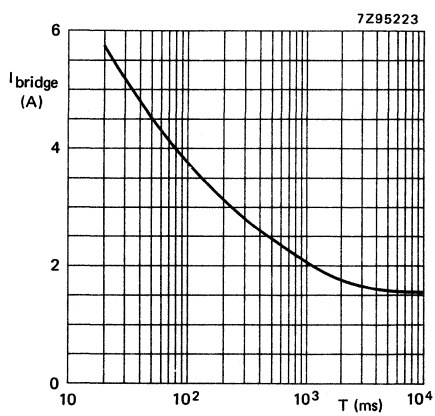
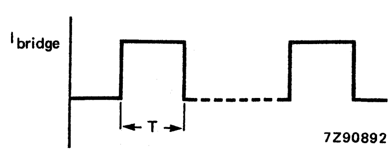


Fig. 7 Maximum permissible output current in a 3-phase rectifier bridge with a minimum time between exposures of 20 s; T_{oil} = 50 °C.



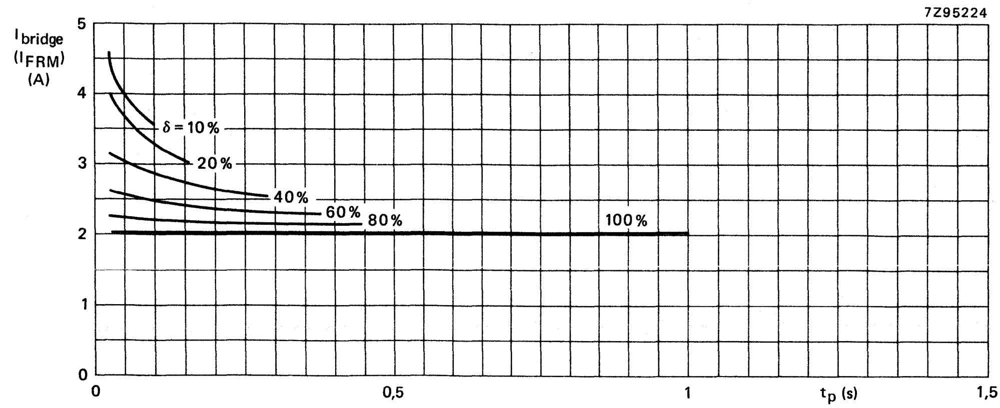


Fig. 8 Maximum current through a 3-phase rectifier bridge versus pulse duration; exposure time T = 1 s; T_{oil} = 50 °C; (see Fig. 10).

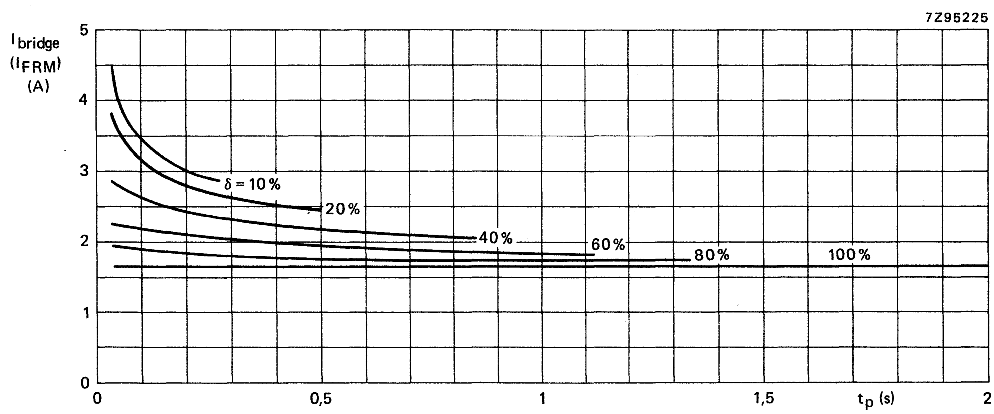


Fig. 9 Maximum current through a 3-phase rectifier bridge versus pulse duration; exposure time T = 3 s; T_{oil} = 50 °C; (see Fig. 10).

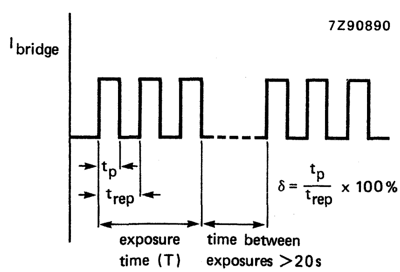


Fig. 10.

REGULATOR DIODES

Glass passivated diodes in hermetically sealed axial leaded ID* glass envelopes. They are intended for use as voltage regulator and transient suppressor diodes in medium power regulation and transient suppression circuits.

The series consists of BZD23-C7V5 to BZD-C510 in the normalized E24 range.

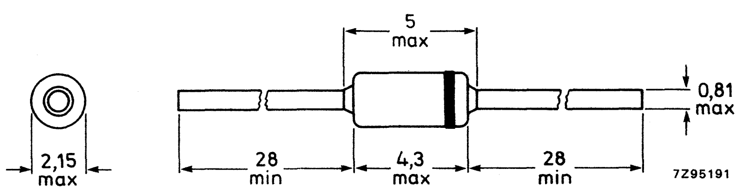
QUICK REFERENCE DATA

Working voltage range (voltage regulator)	V_Z	nom.	7,5 to 270	V
Stand-off voltage (transient suppressor)	V_R		6,2 to 430	V
Total power dissipation	P_{tot}	max.	2,5	W
Non-repetitive peak reverse power dissipation $T_j = 25\ ^oC$; $t_p = 100\ \mu s$	P_{RSM}	max.	300	W

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-81



The marking band indicates the cathode.

* Implosion diode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Total power dissipation			
T_{tp} = 25 °C; lead length 10 mm	P_{tot}	max.	2.5 W
T_{amb} = 55 °C; pc board mounting (Fig. 2)	P_{tot}	max.	1.0 W
Non-repetitive peak reverse power dissipation			
t_p = 100 μs, square pulse; T_j = 25 °C (prior to surge)	P_{RSM}	max.	300 W
waveform 10/1000 exponential pulse (Fig. 3); T_j = 25 °C (prior to surge)	P_{RSM}	max.	150 W
Storage temperature	T_{stg}	−65 to + 175 °C	
Junction temperature	T_j	max.	175 °C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\ j\text{-}tp}$	=	60 K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ≥ 40 μm; Fig. 2	$R_{th\ j\text{-}a}$	=	120 K/W

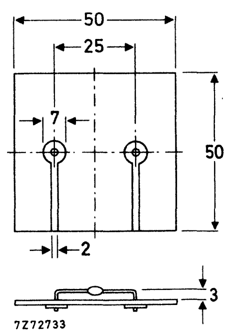


Fig. 2 Mounted on a printed-circuit board.

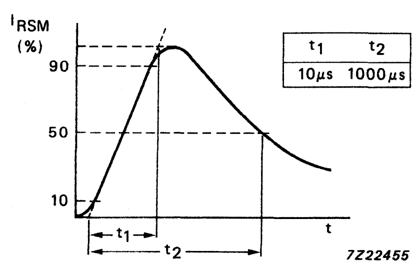


Fig. 3 Current pulse according to IEC 60-2, Section 6.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage I_F = 0.2 A	V_F	<	1.2 V

CHARACTERISTICS (continued)

BZD23-XXXX	working voltage V_Z (V)			differential resistance r_{diff} (Ω)		temperature coefficient S_Z (%/K)		test current I_Z (mA)	reverse current I_R (μA) at	reverse voltage V_R (V)
	min.	typ.	max.	typ.	max.	min.	max.		max.	
C7V5	7,0	7,5	7,9	1	2	0	0,07	100	50	3
C8V2	7,7	8,2	8,7	1	2	0,03	0,08	100	10	3
C9V1	8,5	9,1	9,6	2	4	0,03	0,08	50	10	5
C10	9,4	10,0	10,6	2	4	0,05	0,09	50	7	7,5
C11	10,4	11,0	11,6	4	7	0,05	0,10	50	3	8,2
C12	11,4	12,0	12,7	4	7	0,05	0,10	50	2	9,1
C13	12,4	13,0	14,1	5	10	0,05	0,10	50	2	10
C15	13,8	15,0	15,6	5	10	0,05	0,10	50	1	11
C16	15,3	16,0	17,1	6	15	0,06	0,11	25	1	12
C18	16,8	18,0	19,1	6	15	0,06	0,11	25	1	13
C20	18,8	20,0	21,2	6	15	0,06	0,11	25	1	15
C22	20,8	22,0	23,3	6	15	0,06	0,11	25	1	16
C24	22,8	24,0	25,6	7	15	0,06	0,11	25	1	18
C27	25,1	27,0	28,9	7	15	0,06	0,11	25	1	20
C30	28	30	32	8	15	0,06	0,11	25	1	22
C33	31	33	35	8	15	0,06	0,11	25	1	24
C36	34	36	38	21	40	0,06	0,11	10	1	27
C39	37	39	41	21	40	0,06	0,11	10	1	30
C43	40	43	46	24	45	0,07	0,12	10	1	33
C47	44	47	50	24	45	0,07	0,12	10	1	36
C51	48	51	54	25	60	0,07	0,12	10	1	39
C56	52	56	60	25	60	0,07	0,12	10	1	43
C62	58	62	66	25	80	0,08	0,13	10	1	47
C68	64	68	72	25	80	0,08	0,13	10	1	51
C75	70	75	79	30	100	0,08	0,13	10	1	56
C82	77	82	87	30	100	0,08	0,13	10	1	62
C91	85	91	96	60	200	0,09	0,13	5	1	68
C100	94	100	106	60	200	0,09	0,13	5	1	75
C110	104	110	116	80	250	0,09	0,13	5	1	82
C120	114	120	127	80	250	0,09	0,13	5	1	91
C130	124	130	141	110	300	0,09	0,13	5	1	100
C150	138	150	156	130	300	0,09	0,13	5	1	110
C160	153	160	171	150	350	0,09	0,13	5	1	120
C180	168	180	191	180	400	0,09	0,13	5	1	130
C200	188	200	212	200	500	0,09	0,13	5	1	150
C220	208	220	233	350	750	0,09	0,13	2	1	160
C240	228	240	256	400	850	0,09	0,13	2	1	180
C270	251	270	289	450	1000	0,09	0,13	2	1	200

CHARACTERISTICS when used as transient suppressor diodes; T_j = 25 °C

BZD23 XXXX	clamping voltage (10/1000 pulse) $V_{(CL)R}$ V max.	at	non-repetitive peak reverse current I_{RSM} A	reverse current at recommended stand-off voltage I_R μA max.	V_R V
C7V5	11.3		13.3	1500	6.2
C8V2	12.3		12.2	1200	6.8
C9V1	13.3		11.3	100	7.5
C10	14.8		10.1	20	8.2
C11	15.7		9.6	5	9.1
C12	17.0		8.8	5	10
C13	18.9		7.9	5	11
C15	20.9		7.2	5	12
C16	22.9		6.6	5	13
C18	25.6		5.9	5	15
C20	28.4		5.3	5	16
C22	31.0		4.8	5	18
C24	33.8		4.4	5	20
C27	38.1		3.9	5	22
C30	42.2		3.6	5	24
C33	46.2		3.2	5	27
C36	50.1		3.0	5	30
C39	54.1		2.8	5	33
C43	60.7		2.5	5	36
C47	65.5		2.3	5	39
C51	70.8		2.1	5	43
C56	78.6		1.9	5	47
C62	86.5		1.7	5	51
C68	94.4		1.6	5	56
C75	103.5		1.5	5	62
C82	114.0		1.3	5	68
C91	126		1.2	5	75
C100	139		1.1	5	82
C110	152		1.0	5	91
C120	167		0.90	5	100
C130	185		0.81	5	110
C150	204		0.73	5	120
C160	224		0.67	5	130
C180	249		0.60	5	150
C200	276		0.54	5	160
C220	305		0.50	5	180
C240	336		0.45	5	200
C270	380		0.40	5	220
C300	419		0.36	5	240
C330	459		0.33	5	270
C360	498		0.30	5	300
C390	537		0.28	5	330
C430	603		0.25	5	360
C470	655		0.23	5	390
C510	707		0.21	5	430

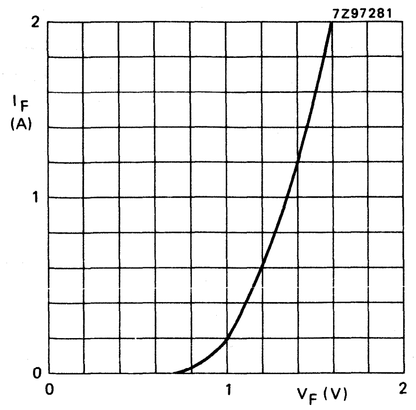


Fig. 4 Forward voltage;
T_j = 25 °C; typical values.

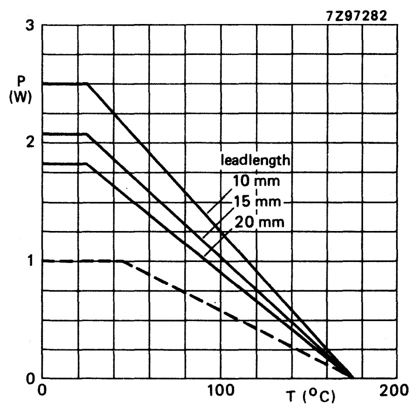


Fig. 5 Maximum total power dissipation versus temperature;
——— = tie-point temperature
– – – = ambient temperature and device mounted as shown in Fig. 2.

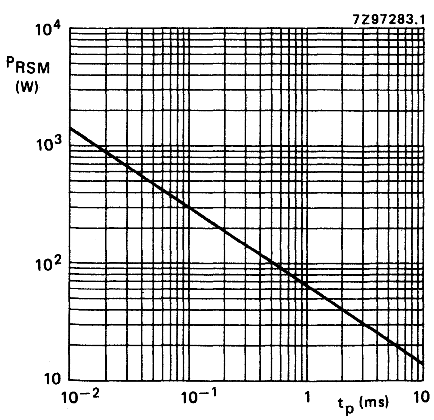


Fig. 6 Maximum non-repetitive peak reverse power dissipation (square pulse); T_j = 25 °C prior to surge.

REGULATOR DIODES

Diodes in hermetically sealed leadless SMID* glass envelopes.
They are intended for use as voltage regulator and transient suppressor diodes in medium power regulation and transient suppression circuits.
The series consists of BZD27-C7V5 to BZD27-C510 in the normalized E24 range.

QUICK REFERENCE DATA

			voltage regulator	transient suppressor	
Working voltage range	V_Z	nom.	7.5 to 270		V
Stand-off voltage	V_R			6.2 to 430	V
Total power dissipation	P_{tot}	max.	2.3		W
Non-repetitive peak reverse power dissipation $T_j = 25\ ^{o}C$; $t_p = 100\ \mu s$	P_{RSM}	max.	300		W

MECHANICAL DATA

Dimensions in mm

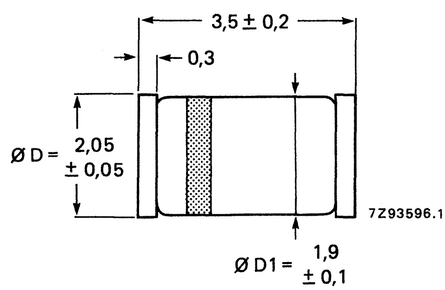


Fig. 1 SOD-87.

* Surface mounted implosion diode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Total power dissipation			
T_{tp} = 105 °C	P_{tot}	max.	2.3 W
T_{amb} = 55 °C; PCB mounting (Fig. 2)	P_{tot}	max.	0.8 W
Non-repetitive peak reverse power dissipation			
t_p = 100 μs, square pulse; T_j = 25 °C (prior to surge) waveforms	P_{RSM}	max.	300 W
waveform 10/1000 exponential pulse (Fig. 3); T_j = 25 °C (prior to surge)	P_{RSM}	max.	150 W
Storage temperature	T_{stg}		−65 to + 175 °C
Junction temperature	T_j	max.	175 °C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point	$R_{th\,j\text{-}tp}$	=	30 K/W
2. Thermal resistance from junction to ambient when mounted on a 1.5 mm thick epoxy glass PCB; Cu-thickness ⩾ 40 μm; Fig. 2.			

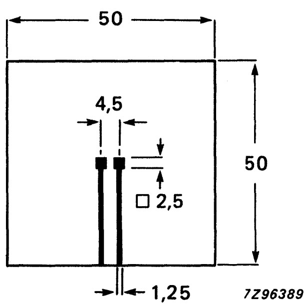


Fig. 2 Mounted on a printed-circuit board.

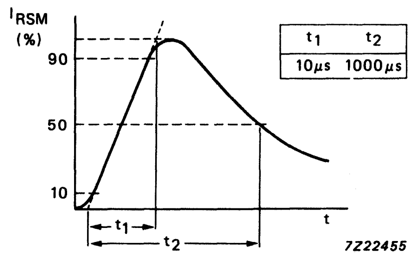


Fig. 3 Current pulse in accordance with IEC 60-2, Section 6.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage			
I_F = 0.2 A	V_F	<	1.2 V

	temperature coefficient S_Z %/K		test current I_Z mA	reverse current at μA	reverse voltage V	working voltage V_Z V			differential resistance r_{diff} Ω	
	min.	max.		max		min.	nom.	max.	typ.	max.
C7V5	0	0.07	100	50	3	7.0	7.5	7.9	1	2
C8V2	0.03	0.08	100	10	3	7.7	8.2	8.7	1	2
C9V1	0.03	0.08	50	10	5	8.5	9.1	9.6	2	4
C10	0.05	0.09	50	7	7.5	9.4	10.0	10.6	2	4
C11	0.05	0.10	50	3	8.2	10.4	11.0	11.6	4	7
C12	0.05	0.10	50	2	9.1	11.4	12.0	12.7	4	7
C13	0.05	0.10	50	2	10	12.4	13.0	14.1	5	10
C15	0.05	0.10	50	1	11	13.8	15.0	15.6	5	10
C16	0.06	0.11	25	1	12	15.3	16.0	17.1	6	15
C18	0.06	0.11	25	1	13	16.8	18.0	19.1	6	15
C20	0.06	0.11	25	1	15	18.8	20.0	21.2	6	15
C22	0.06	0.11	25	1	16	20.8	22.0	23.3	6	15
C24	0.06	0.11	25	1	18	22.8	24.0	25.6	7	15
C27	0.06	0.11	25	1	20	25.1	27.0	28.9	7	15
C30	0.06	0.11	25	1	22	28	30	32	8	15
C33	0.06	0.11	25	1	24	31	33	35	8	15
C36	0.06	0.11	10	1	27	34	36	38	21	40
C39	0.06	0.11	10	1	30	37	39	41	21	40
C43	0.07	0.12	10	1	33	40	43	46	24	45
C47	0.07	0.12	10	1	36	44	47	50	24	45
C51	0.07	0.12	10	1	39	48	51	54	25	60
C56	0.07	0.12	10	1	43	52	56	60	25	60
C62	0.08	0.13	10	1	47	58	62	66	25	80
C68	0.08	0.13	10	1	51	64	68	72	25	80
C75	0.08	0.13	10	1	56	70	75	79	30	100
C82	0.08	0.13	10	1	62	77	82	87	30	100
C91	0.09	0.13	5	1	68	85	91	96	60	200
C100	0.09	0.13	5	1	75	94	100	106	60	200
C110	0.09	0.13	5	1	82	104	110	116	80	250
C120	0.09	0.13	5	1	91	114	120	127	80	250
C130	0.09	0.13	5	1	100	124	130	141	110	300
C150	0.09	0.13	5	1	110	138	150	156	130	300
C160	0.09	0.13	5	1	120	153	160	171	150	350
C180	0.09	0.13	5	1	130	168	180	191	180	400
C200	0.09	0.13	5	1	150	188	200	212	200	500
C220	0.09	0.13	2	1	160	208	220	233	350	750
C240	0.09	0.13	2	1	180	228	240	256	400	850
C270	0.09	0.13	2	1	200	251	270	289	450	1000

CHARACTERISTICS when used as transient suppressor diodes; T_j = 25 °C

BZD27	clamping voltage (10/1000 pulse) $V_{(CL)R}$ V	non-repetitive at peak reverse I_{RSM} A	reverse current at recommended stand-off voltage I_R µA	V_R V
	max.		max.	
C7V5	11.3	13.3	1500	6.2
C8V2	12.3	12.2	1200	6.8
C9V1	13.3	11.3	100	7.5
C10	14.8	10.1	20	8.2
C11	15.7	9.6	5	9.1
C12	17.0	8.8	5	10
C13	18.9	7.9	5	11
C15	20.9	7.2	5	12
C16	22.9	6.6	5	13
C18	25.6	5.9	5	15
C20	28.4	5.3	5	16
C22	31.0	4.8	5	18
C24	33.8	4.4	5	20
C27	38.1	3.9	5	22
C30	42.2	3.6	5	24
C33	46.2	3.2	5	27
C36	50.1	3.0	5	30
C39	54.1	2.8	5	33
C43	60.7	2.5	5	36
C47	65.5	2.3	5	39
C51	70.8	2.1	5	43
C56	78.6	1.9	5	47
C62	86.5	1.7	5	51
C68	94.4	1.6	5	56
C75	103.5	1.5	5	62
C82	114.0	1.3	5	68
C91	126	1.2	5	75
C100	139	1.1	5	82
C110	152	1.0	5	91
C120	167	0.90	5	100
C130	185	0.81	5	110
C150	204	0.73	5	120
C160	224	0.67	5	130
C180	249	0.60	5	150
C200	276	0.54	5	160
C220	305	0.50	5	180
C240	336	0.45	5	200
C270	380	0.40	5	220
C300	419	0.36	5	240
C330	459	0.33	5	270
C360	498	0.30	5	300
C390	537	0.28	5	330
C430	603	0.25	5	360
C470	655	0.23	5	390
C510	707	0.21	5	430

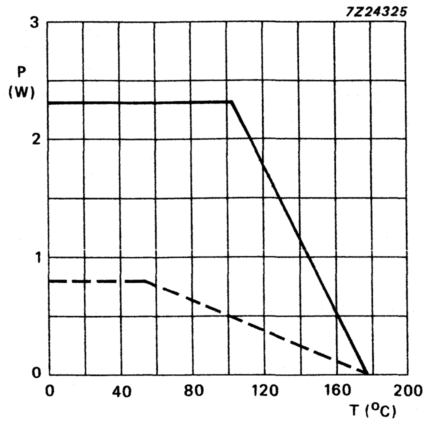


Fig. 4 Maximum total power dissipation as a function of temperature.

——— = tie-point temperature
– – – = ambient temperature and device mounted ans shown in Fig. 2.

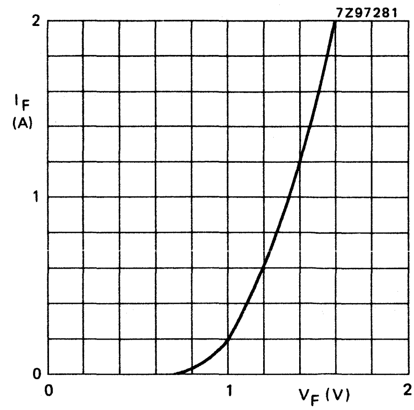


Fig. 5 Forward voltage; T_j = 25 °C; typical values.

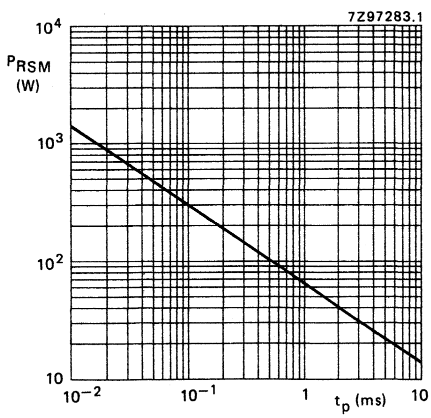


Fig. 6 Maximum non-repetitive peak reverse power dissipation (square pulse); T_j = 25 °C prior to surge.

REGULATOR DIODES

Glass passivated diodes in hermetically sealed axial-leaded glass envelopes. They are intended for use as voltage regulator and transient suppressor diode in medium power regulation and transient suppression circuits.

The series consists of BZT03-C7V5 to BZT03-C270 in the normalized E24 range.

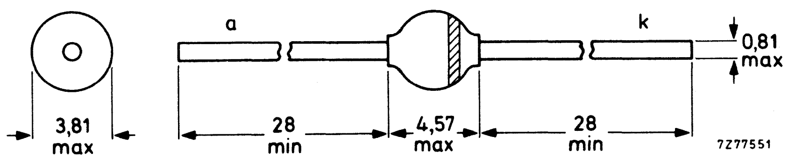
QUICK REFERENCE DATA

			voltage regulator	transient suppressor	
Working voltage range	V_Z	nom.	7,5 to 270		V
Stand-off voltage	V_R			6,2 to 220	V
Total power dissipation	P_{tot}	max.	3,25		W
Non-repetitive peak reverse power dissipation $T_j = 25\ ^oC$; $t_p = 100\ \mu s$	P_{RSM}	max.		600	W

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-57.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Total power dissipation				
T_{tp} = 25 °C; lead length 10 mm	P_{tot}	max.	3,25	W
T_{amb} = 45 °C; p.c.b. mounting (Fig. 2)	P_{tot}	max.	1,3	W
Repetitive peak reverse power dissipation	P_{ZRM}	max.	10	W
Non-repetitive peak reverse power dissipation;				
t_p = 100 μs, square pulse; T_j = 25 °C (prior to surge)	P_{RSM}	max.	600	W
waveform 10/1000 exponential pulse (Fig. 3); T_j = 25 °C (prior to surge)	P_{RSM}	max.	300	W
Storage temperature	T_{stg}	−65 to + 175		°C
Junction temperature	T_j	max.	175	°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\ j\text{-}tp}$	=	46	K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ⩾ 40 μm; Fig. 2	$R_{th\ j\text{-}a}$	=	100	K/W

(see "Thermal model")

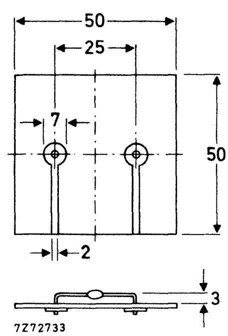


Fig. 2 Mounted on a printed-circuit board.

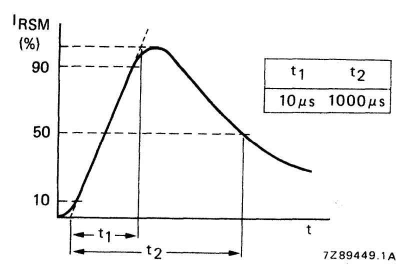


Fig. 3 Current pulse according to IEC 60-2, Section 6.

CHARACTERISTICS

Forward voltage				
I_F = 0,5 A; T_j = 25 °C	V_F	<	1,2	V

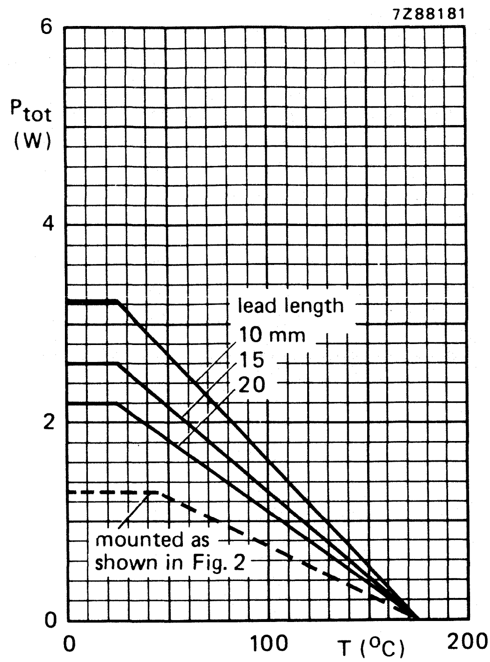


Fig. 4 Maximum total power dissipation as a function of temperature.
——— = T_{tp}; – – – – – = T_{amb}; Fig. 2.

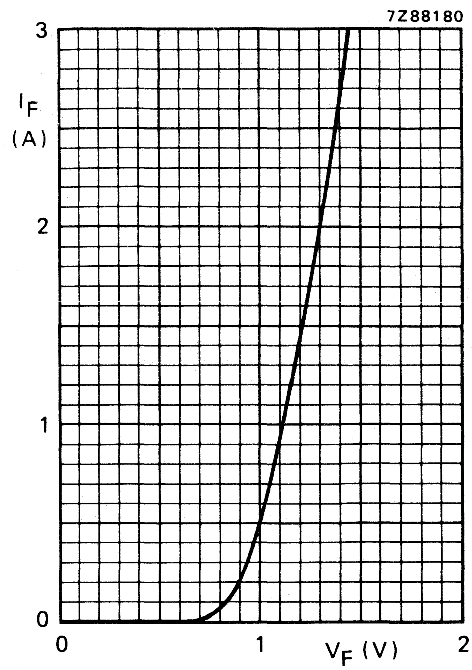


Fig. 5 Typical forward voltage drop T_j = 25 °C.

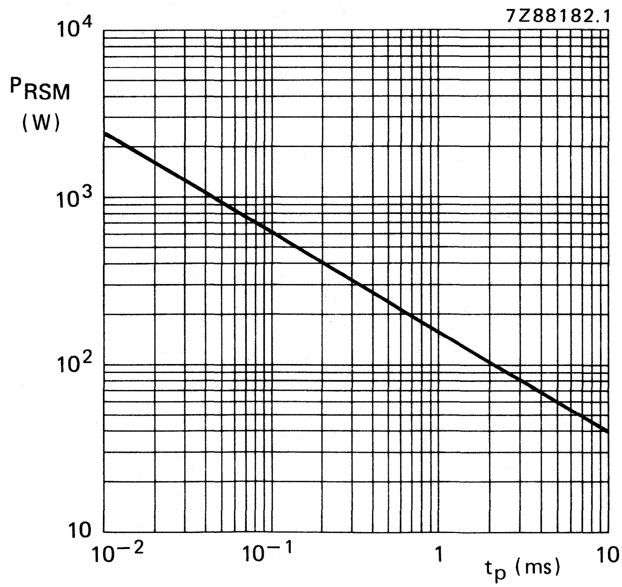


Fig. 6 Maximum non-repetitive peak reverse power dissipation; square current pulse; T_j = 25 °C prior to surge.

CHARACTERISTICS when used as voltage regulator diodes; T_j = 25 °C

BZT03-XXXX	working voltage V_Z V			differential resistance r_{diff} Ω		temperature coefficient S_Z %/K		test current I_Z mA	reverse current I_R µA	at reverse voltage V_R V
	min.	typ.	max.	typ.	max.	min.	max.		max.	
C7V5	7,0	7,5	7,9	1	2	0	0,07	100	750	5,6
C8V2	7,7	8,2	8,7	1	2	0,03	0,08	100	600	6,2
C9V1	8,5	9,1	9,6	2	4	0,03	0,08	50	20	6,8
C10	9,4	10,0	10,6	2	4	0,05	0,09	50	10	7,5
C11	10,4	11,0	11,6	4	7	0,05	0,10	50	4	8,2
C12	11,4	12,0	12,7	4	7	0,05	0,10	50	3	9,1
C13	12,4	13,0	14,1	5	10	0,05	0,10	50	2	10
C15	13,8	15,0	15,6	5	10	0,05	0,10	50	1	11
C16	15,3	16,0	17,1	6	15	0,06	0,11	25	1	12
C18	16,8	18,0	19,1	6	15	0,06	0,11	25	1	13
C20	18,8	20,0	21,2	6	15	0,06	0,11	25	1	15
C22	20,8	22,0	23,3	6	15	0,06	0,11	25	1	16
C24	22,8	24,0	25,6	7	15	0,06	0,11	25	1	18
C27	25,1	27,0	28,9	7	15	0,06	0,11	25	1	20
C30	28	30	32	8	15	0,06	0,11	25	1	22
C33	31	33	35	8	15	0,06	0,11	25	1	24
C36	34	36	38	21	40	0,06	0,11	10	1	27
C39	37	39	41	21	40	0,06	0,11	10	1	30
C43	40	43	46	24	45	0,07	0,12	10	1	33
C47	44	47	50	24	45	0,07	0,12	10	1	36
C51	48	51	54	25	60	0,07	0,12	10	1	39
C56	52	56	60	25	60	0,07	0,12	10	1	43
C62	58	62	66	25	80	0,08	0,13	10	1	47
C68	64	68	72	25	80	0,08	0,13	10	1	51
C75	70	75	79	30	100	0,08	0,13	10	1	56
C82	77	82	87	30	100	0,08	0,13	10	1	62
C91	85	91	96	60	200	0,09	0,13	5	1	68
C100	94	100	106	60	200	0,09	0,13	5	1	75
C110	104	110	116	80	250	0,09	0,13	5	1	82
C120	114	120	127	80	250	0,09	0,13	5	1	91
C130	124	130	141	110	300	0,09	0,13	5	1	100
C150	138	150	156	130	300	0,09	0,13	5	1	110
C160	153	160	171	150	350	0,09	0,13	5	1	120
C180	168	180	191	180	400	0,09	0,13	5	1	130
C200	188	200	212	200	500	0,09	0,13	5	1	150
C220	208	220	233	350	750	0,09	0,13	2	1	160
C240	228	240	256	400	850	0,09	0,13	2	1	180
C270	251	270	289	450	1000	0,09	0,13	2	1	200

CHARACTERISTICS **when used as transient suppressor diodes;** T_j = 25 °C

clamping voltage (10/1000 pulse) $V_{(CL)R}$ V	at	non-repetitive peak reverse current I_{RSM} A	reverse current at recommended stand-off voltage I_R μA	V_R V	BZT03-XXXX
max.			max.		
11,3		26,5	1500	6,2	C7V5
12,3		24,4	1200	6,8	C8V2
13,3		22,7	50	7,5	C9V1
14,8		20,3	20	8,2	C10
15,7		19,1	5	9,1	C11
17,0		17,7	5	10	C12
18,9		15,9	5	11	C13
20,9		14,4	5	12	C15
22,9		13,1	5	13	C16
25,6		11,7	5	15	C18
28,4		10,6	5	16	C20
31		9,7	5	18	C22
33,8		8,9	5	20	C24
38,1		7,9	5	22	C27
42,2		7,1	5	24	C30
46,2		6,5	5	27	C33
50,1		6,0	5	30	C36
54,1		5,5	5	33	C39
60,7		4,9	5	36	C43
65,5		4,6	5	39	C47
70,8		4,2	5	43	C51
78,6		3,8	5	47	C56
86,5		3,5	5	51	C62
94,4		3,2	5	56	C68
103,5		2,9	5	62	C75
114,0		2,6	5	68	C82
126		2,4	5	75	C91
139		2,2	5	82	C100
152		2,0	5	91	C110
167		1,8	5	100	C120
185		1,6	5	110	C130
204		1,5	5	120	C150
224		1,3	5	130	C160
249		1,2	5	150	C180
276		1,1	5	160	C200
305		1,0	5	180	C220
336		0,9	5	200	C240
380		0,8	5	220	C270

VOLTAGE REFERENCE DIODES

The BZV10 to 14 are temperature compensated voltage reference diodes in a DO-34 envelope. They are primarily intended for use as voltage reference sources in measuring instruments such as digital voltmeters.

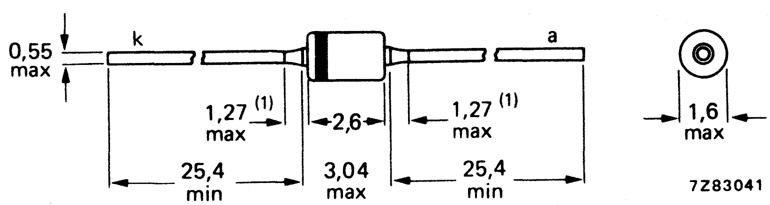
QUICK REFERENCE DATA

			min.	nom.	max.	
Reference voltage at I_Z = 2,0 mA		V_{ref}	6,175	6,5	6,825	V
Temperature coefficient at I_Z = 2,0 mA (see notes 1 and 2 and Fig. 3)	**BZV10**	$\|S_Z\|$		< 0,01		%/K
	BZV11	$\|S_Z\|$		< 0,005		%/K
	BZV12	$\|S_Z\|$		< 0,002		%/K
	BZV13	$\|S_Z\|$		< 0,001		%/K
	BZV14	$\|S_Z\|$		< 0,0005		%/K
Operating ambient temperature		T_{amb}		0 to + 70		°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 DO-34 (SOD-68).



Cathode indicated by coloured band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Working current (d.c.)	I_Z	max.	50	mA
Working current (peak value)	I_{ZM}	max.	50	mA
Total power dissipation up to T_{amb} = 50 °C	P_{tot}	max.	400	mW
Storage temperature	T_{stg}		−65 to +200	°C
Operating ambient temperature	T_{amb}		0 to +70	°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0,375	K/mW

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

			min.	nom.	max.	
Reference voltage at I_Z = 2,0 mA		V_{ref}	6,175	6,5	6,825	V

Reference voltage excursion at I_Z = 2,0 mA*

Ambient temperature test points: 0; +25 °C and +70 °C (see notes 1 and 2 on the next page)

BZV10	$\lvert\Delta V_{ref}\rvert$	<	46,0	mV
BZV11	$\lvert\Delta V_{ref}\rvert$	<	23,0	mV
BZV12	$\lvert\Delta V_{ref}\rvert$	<	9,0	mV
BZV13	$\lvert\Delta V_{ref}\rvert$	<	4,6	mV
BZV14	$\lvert\Delta V_{ref}\rvert$	<	2,3	mV

Temperature coefficient at I_Z = 2,0 mA*
(see notes 1 and 2 on the next page)

BZV10	$\lvert S_Z\rvert$	<	± 0,01	%/K
BZV11	$\lvert S_Z\rvert$	<	± 0,005	%/K
BZV12	$\lvert S_Z\rvert$	<	± 0,002	%/K
BZV13	$\lvert S_Z\rvert$	<	± 0,001	%/K
BZV14	$\lvert S_Z\rvert$	<	± 0,0005	%/K

Differential resistance at I_Z = 2,0 mA	r_{diff}	typ.	30	Ω
		<	50	Ω

* For accuracy of I_Z see Fig. 3.

Notes

1. I_Z tolerance and stability of I_Z.

   The quoted values of ΔV_{ref} are based on a constant current I_Z. Two factors can cause V_{ref} to change, namely the differential resistance r_{diff} and the temperature coefficient S_Z.

   a. As the max. r_{diff} of the device can be 50 Ω, a change of 0,01 mA in the current through the reference diode will result in a ΔV_{ref} of 0,01 mA x 50 Ω = 0,5 mV. This level of ΔV_{ref} is not significant on a BZV10 ($\Delta V_{ref} < 46$ mV), it is however very significant on a BZV14 ($\Delta V_{ref} < 2{,}3$ mV).

   b. The temperature coefficient of the reference voltage S_Z is a function of I_Z. Reference diodes are classified at the specified test current and the S_Z of the reference diode will be different at the different levels of I_Z. The absolute value of I_Z is important, however, the stability of I_Z, once the level has been set, is far more significant. This applies particularly to the BZV13 and BZV14. The effect of I_Z stability on S_Z is shown in Fig. 3.

2. Voltage excursion (ΔV_{ref} and temperature coefficient).

   All reference diodes are characterized by the 'box method'. This guarantees a maximum voltage excursion (ΔV_{ref}) over the specified temperature range, at the specified test current (I_Z), verified by tests at indicated temperature points within the range. V_Z is measured and recorded at each temperature specified. The ΔV_{ref} between the highest and lowest values must not exceed the maximum ΔV_{ref} given. The temperature coefficient, therefore is given only as a reference; but may be derived from:

$$S_Z = \frac{(V_{ref\,1} - V_{ref\,2}) \times 100}{(T_{amb2} - T_{amb1}) \times V_{ref\,nom}} \ \%/K.$$

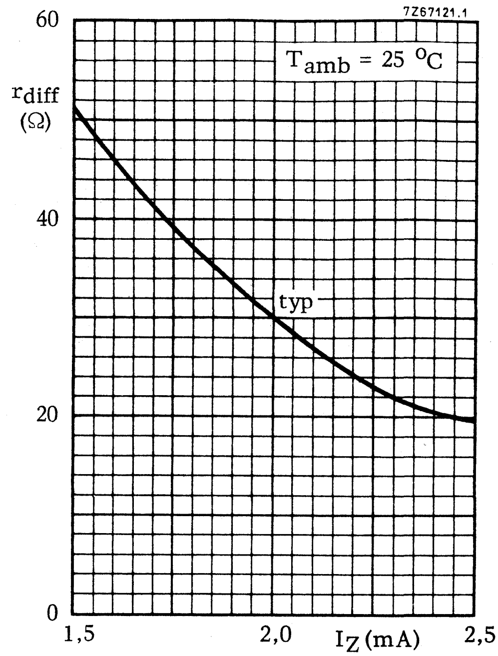


Fig. 2 Typical values differential resistance.

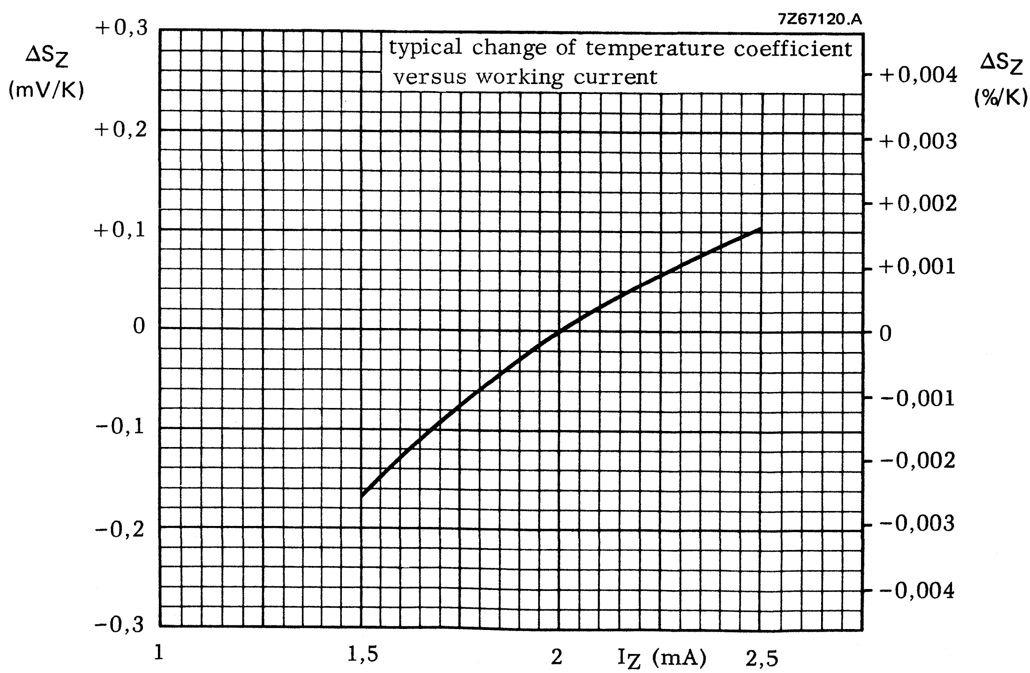


Fig. 3 Typical change of temperature coefficient.

SYMMETRICAL VOLTAGE REGULATOR DIODE

Silicon planar symmetrical regulator diode in DO-34 (SOD-68) envelope, intended for use as voltage stabilizer and transient protection element.

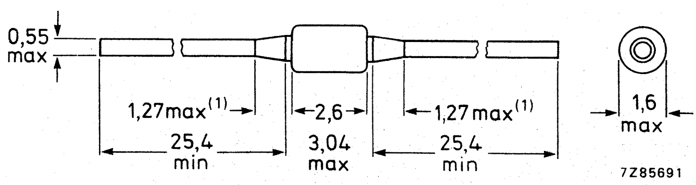
QUICK REFERENCE DATA

Working voltage	V_Z	nom.	6,5	V
Total power dissipation	P_{tot}	max.	400	mW
Non-repetitive peak reverse power dissipation	P_{ZSM}	max.	40	W
Non-repetitive peak reverse current	I_{RSM}	max.	7	A
Junction temperature	T_j	max.	200	°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 DO-34 (SOD-68).



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Working current (d.c.)	I_Z	max.	50 mA
Non-repetitive peak reverse current			
t = 30 s, T_j = 25 °C prior to surge (Fig. 2)			
t_1/t_2 = 8/20 μs	I_{RSM}	max.	7 A
t_1/t_2 = 10/1000 μs	I_{RSM}	max.	2 A
Total power dissipation			
$T_{amb} < 50$ °C	P_{tot}	max.	400 mW
Non-repetitive peak reverse power dissipation			
(t = 100 μs, rectangular pulse)			
T_j = 25 °C prior to surge	P_{ZSM}	max.	40 W
T_j = 150 °C prior to surge	P_{ZSM}	max.	30 W
Storage temperature	T_{stg}	−65 to +200	°C
Junction temperature	T_j	max.	200 °C

THERMAL RESISTANCE

from junction to ambient	$R_{th\ j\text{-}a}$	=	0,38 K/mW

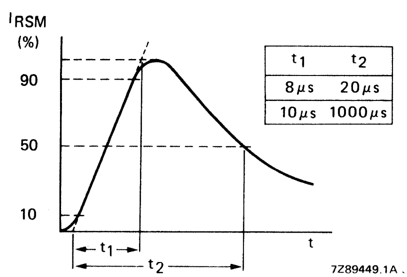


Fig. 2 Current pulse according to IEC 60-2, Section 6.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Working voltage					
I_Z = 5 mA	V_Z	6,2	to	6,8	V
		typ.		6,5	V
Clamping voltage					
I_{RSM} = 7 A (t_1/t_2 = 8/20 μs)	$V_{(CL)R}$	<		25	V
I_{RSM} = 2 A (t_1/t_2 = 10/1000 μs)	$V_{(CL)R}$	<		15	V
Reverse current					
V_R = 4 V	I_R	<		10	μA
V_R = 4 V; T_j = 150 °C	I_R	<		30	μA
V_R = 2 V	I_R	<		3	μA
Differential resistance					
I_Z = 5 mA	r_{diff}	<		20	Ω
Diode capacitance					
V_R = 0; f = 1 MHz	C_d	<		150	pF
Temperature coefficient of the working voltage at I_Z = 5 mA	$\lvert S_Z \rvert$	<		0,1	%/K

SILICON PLANAR VOLTAGE REGULATOR DIODES

Silicon planar voltage regulator diodes, in a SOT-89 plastic envelope, intended for stabilization applications in thick and thin-film circuits.

The series covers the normalized range of nominal working voltages from 2,4 V to 75 V with a tolerance of ± 5% (international standard E24 range).

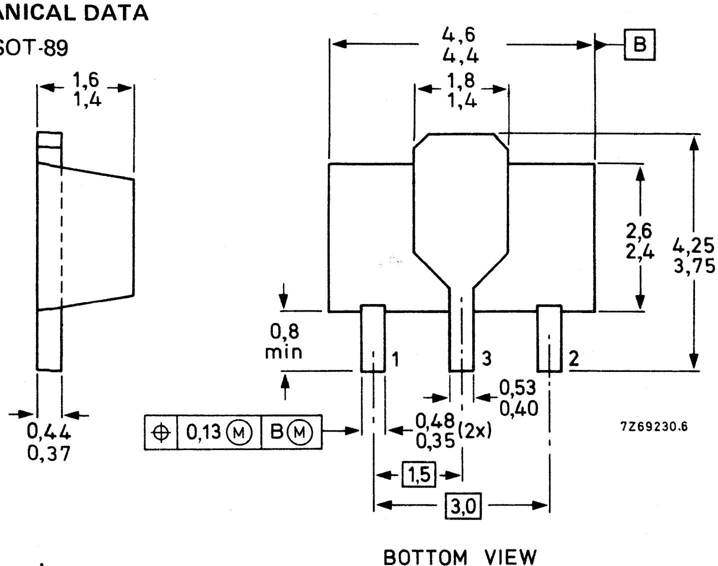
QUICK REFERENCE DATA

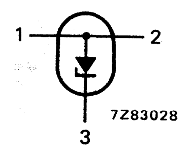
Working voltage range	V_Z	nom.	2,4 to 75	V
Working voltage tolerance (E24 range)			±5	%
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1	W
Junction temperature	T_j	max.	150	°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-89





Marking code

BZV49- C2V4 = 2Y4	C5V1 = 5Y1	C12 = 12Y	C33 = 33Y
C2V7 = 2Y7	C5V6 = 5Y6	C13 = 13Y	C36 = 36Y
C3V0 = 3Y0	C6V2 = 6Y2	C15 = 15Y	C39 = 39Y
C3V3 = 3Y3	C6V8 = 6Y8	C16 = 16Y	C43 = 43Y
C3V6 = 3Y6	C7V5 = 7Y5	C18 = 18Y	C47 = 47Y
C3V9 = 3Y9	C8V2 = 8Y2	C20 = 20Y	C51 = 51Y
C4V3 = 4Y3	C9V1 = 9Y1	C22 = 22Y	C56 = 56Y
C4V7 = 4Y7	C10 = 10Y	C24 = 24Y	C62 = 62Y
	C11 = 11Y	C27 = 27Y	C68 = 68Y
		C30 = 30Y	C75 = 75Y

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Repetitive peak forward current	I_{FRM}	max.	250 mA
Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	250 mA
Working current (d.c.)	I_Z	limited by $P_{tot\ max}$	
Total power dissipation * up to T_{amb} = 25 °C	P_{tot}	max.	1 W
Non-repetitive peak reverse power dissipation * T_j = 25 °C; t_p = 100 μs	P_{ZSM}	max.	40 W
Storage temperature	T_{stg}		−65 to +150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to collector tab	$R_{th\ j\text{-}tab}$	=	15 K/W
From junction to ambient in free air *	$R_{th\ j\text{-}a}$	=	125 K/W

CHARACTERISTICS

T_j = 25 °C

Forward voltage I_F = 50 mA		V_F	<	1,0 V
Reverse current				
BZV49- C2V4	V_R = 1 V	I_R	<	50 μA
C2V7	V_R = 1 V	I_R	<	20 μA
C3V0	V_R = 1 V	I_R	<	10 μA
C3V3	V_R = 1 V	I_R	<	5 μA
C3V6	V_R = 1 V	I_R	<	5 μA
C3V9	V_R = 1 V	I_R	<	3 μA
C4V3	V_R = 1 V	I_R	<	3 μA
C4V7	V_R = 2 V	I_R	<	3 μA
C5V1	V_R = 2 V	I_R	<	2 μA
C5V6	V_R = 2 V	I_R	<	1 μA
C6V2	V_R = 4 V	I_R	<	3 μA
C6V8	V_R = 4 V	I_R	<	2 μA
C7V5	V_R = 5 V	I_R	<	1 μA
C8V2	V_R = 5 V	I_R	<	700 nA
C9V1	V_R = 6 V	I_R	<	500 nA
C10	V_R = 7 V	I_R	<	200 nA
C11 to C13	V_R = 8 V	I_R	<	100 nA
C15 to C75	V_R = 0,7 V_{Znom}	I_R	<	50 nA

* Device mounted on a ceramic substrate: area = 2,5 cm^2; thickness = 0,7 mm.

T_j = 25 °C

E24 logarithmic range (tolerance ± 5%)

BZV49-...	working voltage V_Z (V) at I_{Ztest} = 5 mA		differential resistance r_{diff} (Ω) at I_{Ztest} = 5 mA		temperature coefficient S_Z (mV/K) at I_{Ztest} = 5 mA			diode capacitance C_d(pF); f = 1 MHz V_R = 0	
	min.	max.	typ.	max.	min.	typ.	max.	typ.	max.
C2V4	2,2	2,6	70	100	–3,5	–1,6	0	375	450
C2V7	2,5	2,9	75	100	–3,5	–2,0	0	350	450
C3V0	2,8	3,2	80	95	–3,5	–2,1	0	350	450
C3V3	3,1	3,5	85	95	–3,5	–2,4	0	325	450
C3V6	3,4	3,8	85	90	–3,5	–2,4	0	300	450
C3V9	3,7	4,1	85	90	–3,5	–2,5	0	300	450
C4V3	4,0	4,6	80	90	–3,5	–2,5	0	275	450
C4V7	4,4	5,0	50	80	–3,5	–1,4	0,2	130	180
C5V1	4,8	5,4	40	60	–2,7	–0,8	1,2	110	160
C5V6	5,2	6,0	15	40	–2,0	1,2	2,5	95	140
C6V2	5,8	6,6	6	10	0,4	2,3	3,7	90	130
C6V8	6,4	7,2	6	15	1,2	3,0	4,5	85	110
C7V5	7,0	7,9	6	15	2,5	4,0	5,3	80	100
C8V2	7,7	8,7	6	15	3,2	4,6	6,2	75	95
C9V1	8,5	9,6	6	15	3,8	5,5	7,0	70	90
C10	9,4	10,6	8	20	4,5	6,4	8,0	70	90
C11	10,4	11,6	10	20	5,4	7,4	9,0	65	85
C12	11,4	12,7	10	25	6,0	8,4	10,0	65	85
C13	12,4	14,1	10	30	7,0	9,4	11,0	60	80
C15	13,8	15,6	10	30	9,2	11,4	13,0	55	75
C16	15,3	17,1	10	40	10,4	12,4	14,0	52	75
C18	16,8	19,1	10	45	12,4	14,4	16,0	47	70
C20	18,8	21,2	15	55	14,4	16,4	18,0	36	60
C22	20,8	23,3	20	55	16,4	18,4	20,0	34	60
C24	22,8	25,6	25	70	18,4	20,4	22,0	33	55
	at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA				
C27	25,1	28,9	25	80	21,4	23,4	25,3	30	50
C30	28,0	32,0	30	80	24,4	26,6	29,4	27	50
C33	31,0	35,0	35	80	27,4	29,7	33,4	25	45
C36	34,0	38,0	35	90	30,4	33,0	37,4	23	45
C39	37,0	41,0	40	130	33,4	36,4	41,2	21	45
C43	40,0	46,0	45	150	37,6	41,2	46,6	21	40
C47	44,0	50,0	50	170	42,0	46,1	51,8	19	40
C51	48,0	54,0	60	180	46,6	51,0	57,2	19	40
C56	52,0	60,0	70	200	52,2	57,0	63,8	18	40
C62	58,0	66,0	80	215	58,8	64,4	71,6	17	35
C68	64,0	72,0	90	240	65,6	71,7	79,8	17	35
C75	70,0	79,0	95	255	73,4	80,2	88,6	16,5	35

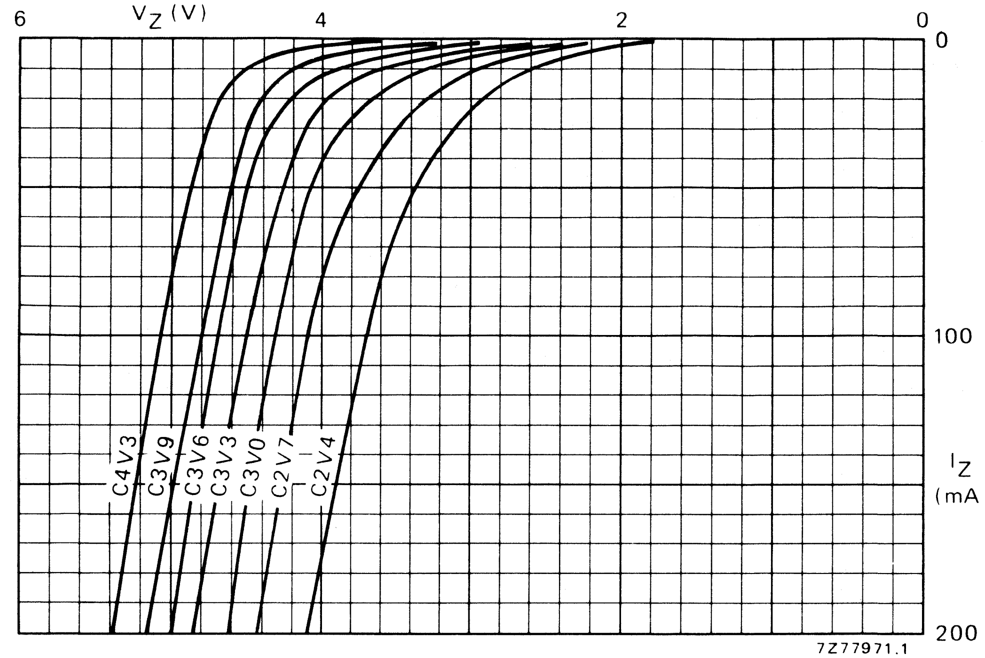


Fig. 2 Dynamic characteristics; typical values; T_j = 25 °C.

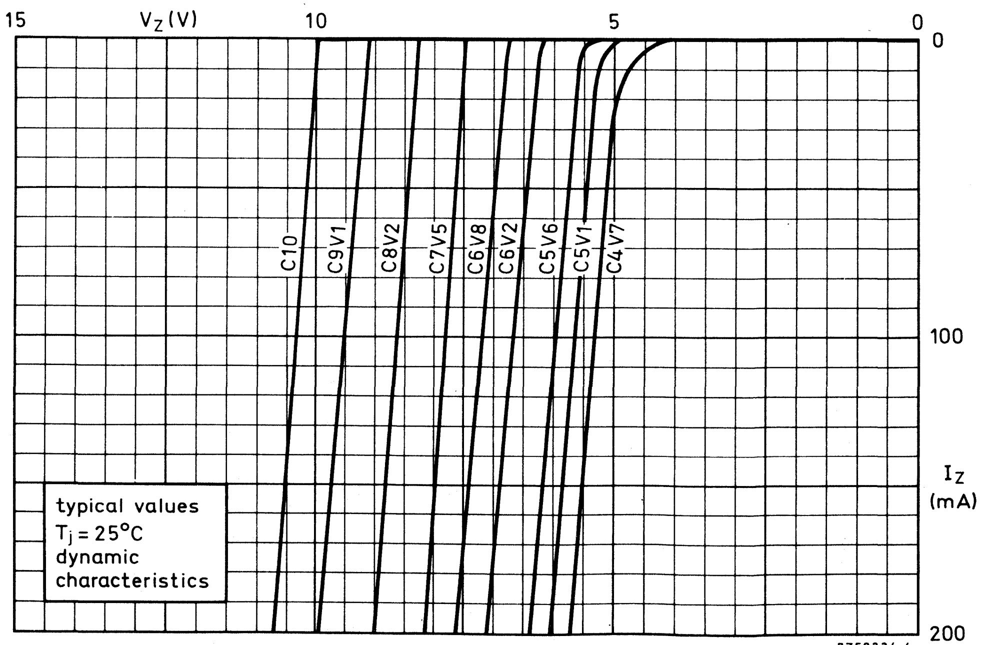


Fig. 3 Dynamic characteristics; typical values at T_j = 25 °C.

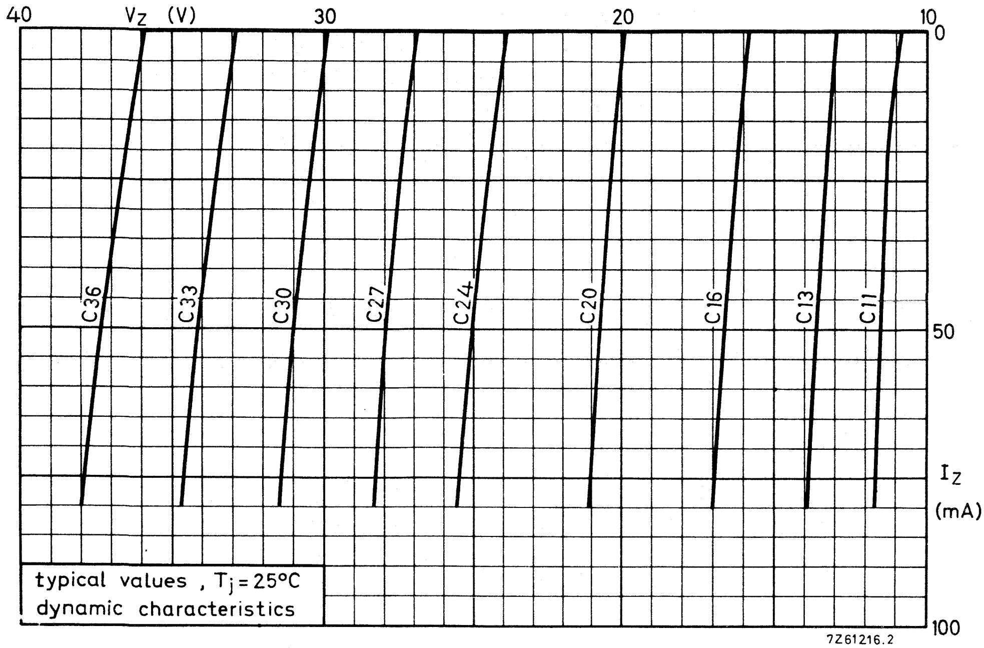


Fig. 4 Dynamic characteristics; typical values; T_j = 25 °C.

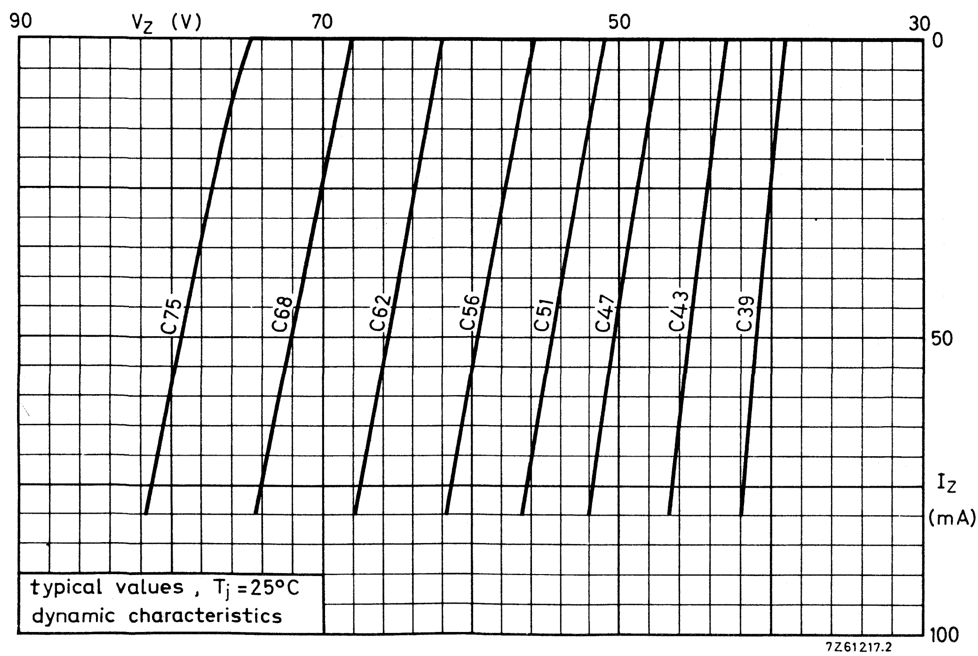


Fig. 5 Dynamic characteristics; typical values at T_j = 25 °C.

Model for calculating the static working voltage ($V_{Z\ stat}$).

This model can be derived from $V_{Z\ stat} = V_{Z\ dyn} + \Delta V_Z$ of which $V_{Z\ dyn}$ is given in the preceding tables and can be derived from the typical dynamic characteristic curves (Figs 2, 3, 4 and 5)
$\Delta V_Z = \Delta T \times S_Z$. For S_Z see tables and graphs S_Z versus T_j.
$\Delta T = P_{tot} \times R_{th\ j\text{-}a} = I_Z \times V_{Z\ dyn} \times R_{th\ j\text{-}a}$.
Following $\Delta V_Z = I_Z \times V_{Z\ dyn} \times R_{th\ j\text{-}a} \times S_Z$ and the model will be:

$$V_{Z\ stat} = V_{Z\ dyn} + I_Z \times V_{Z\ dyn} \times R_{th\ j\text{-}a} \times S_Z$$

Calculating example

BZV49-C24 mounted on a ceramic substrate of 7 x 5 x 0,6 mm; at I_Z = 7 mA.

$$V_{Z\ stat} = 24 + \left(\frac{7}{1000} \times 24 \times \frac{125}{1000} \times 20{,}3\right)$$

$$= 24 + 0{,}4 = 24{,}4\ \text{V}.$$

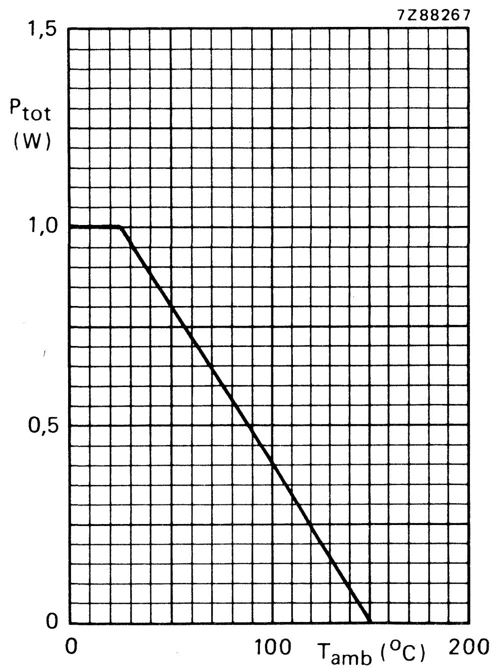


Fig. 6 Power derating curve.

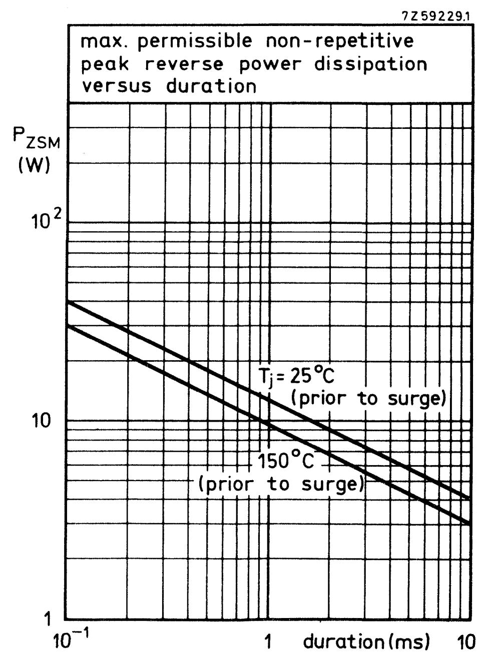


Fig. 7.

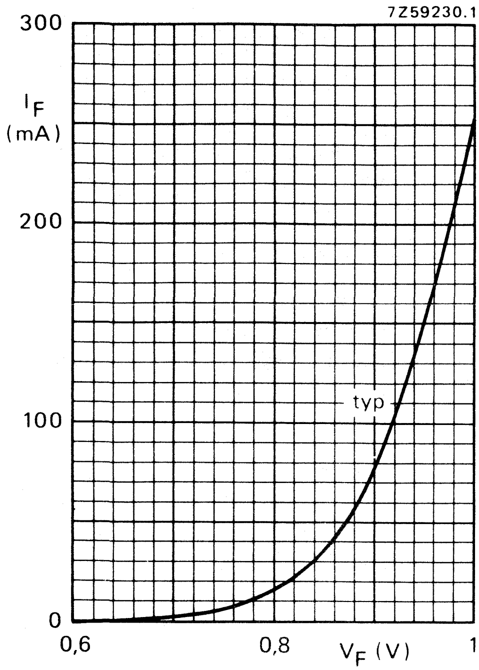


Fig. 8 $T_j = 25\ ^oC$.

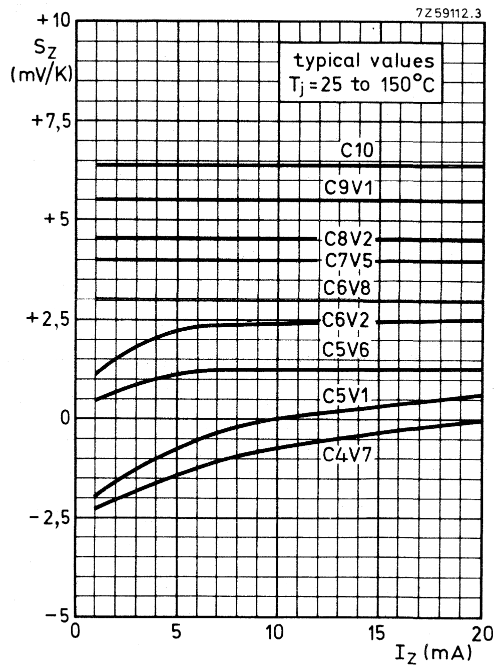


Fig. 9.

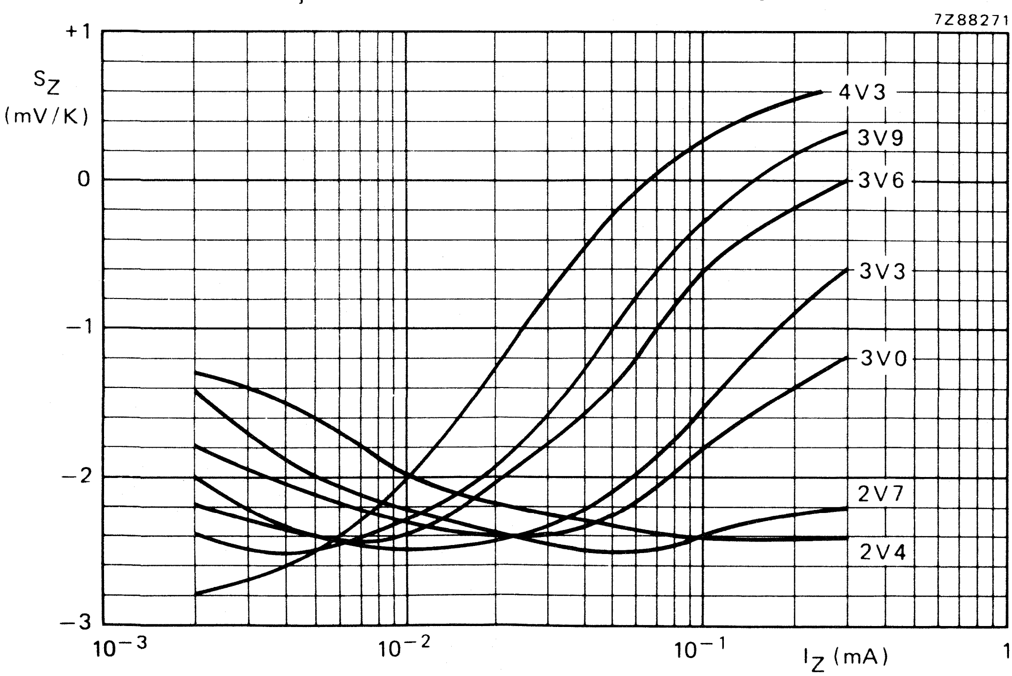


Fig. 10 Typical values temperature coefficient.

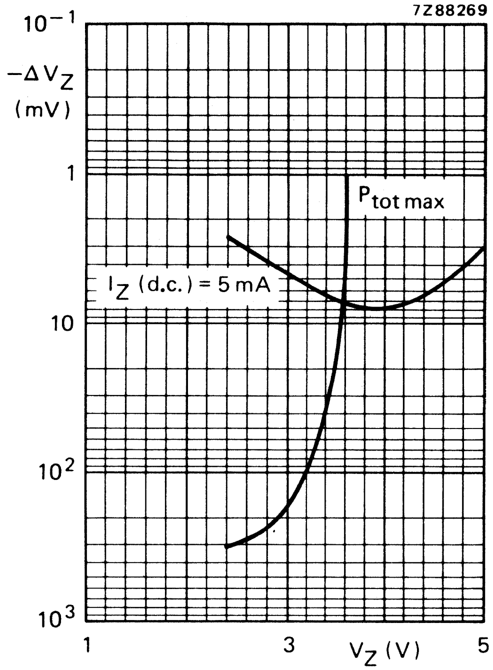


Fig. 11 Typical change of working voltage; T_j = 25 °C.

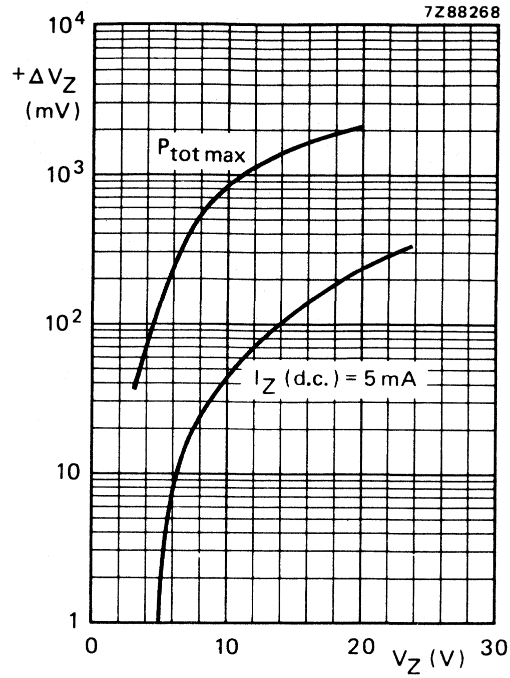


Fig. 12 Typical change of working voltage; T_{amb} = 25 °C.

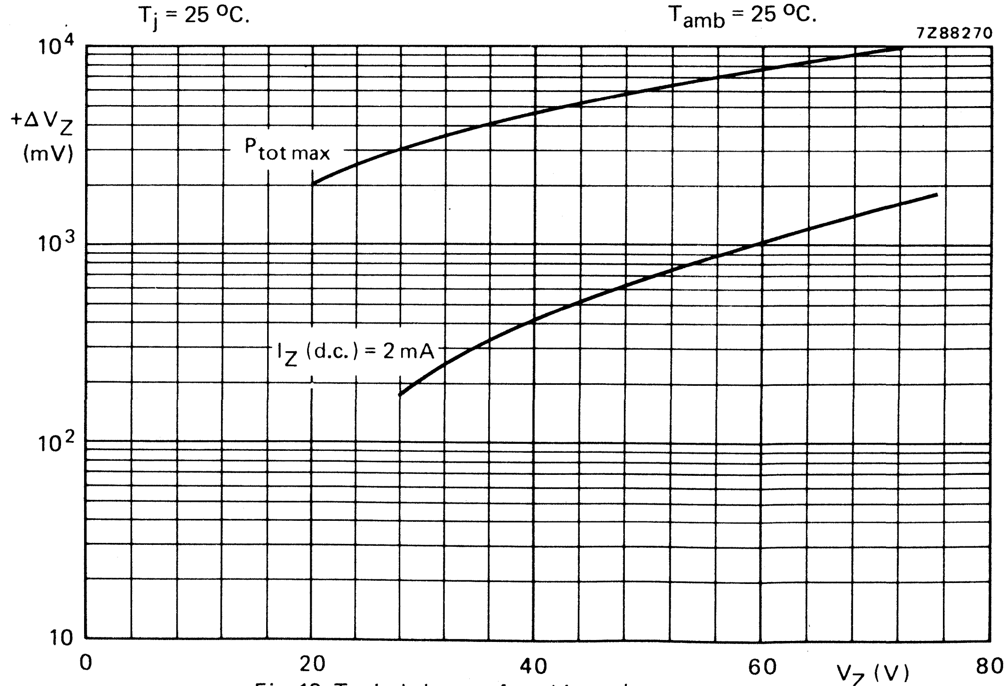


Fig. 13 Typical change of working voltage.

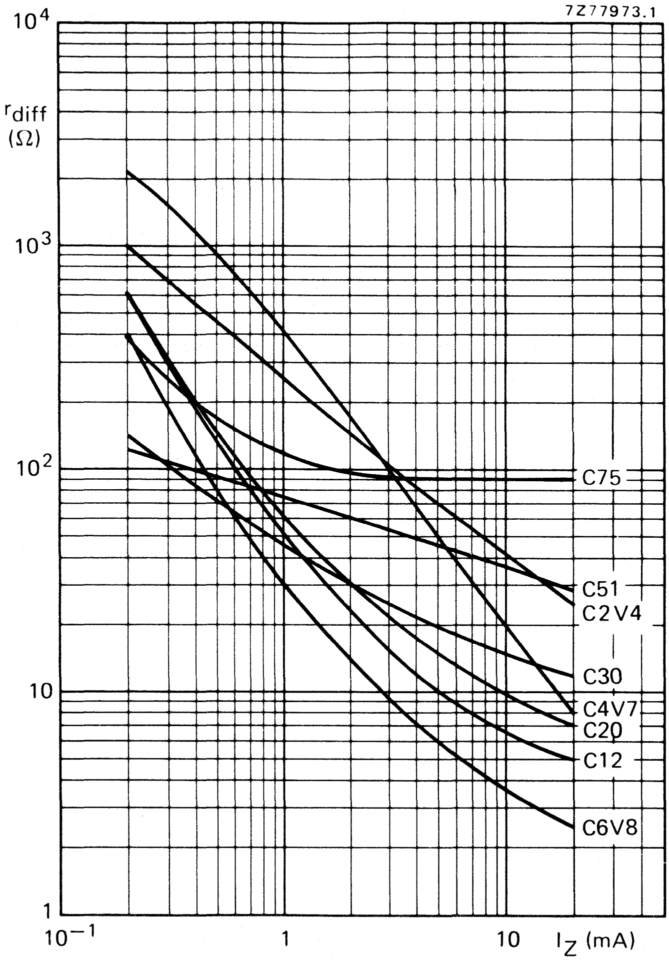


Fig. 14 Typical values; T_j = 25 °C; f = 1 kHz.

VOLTAGE REGULATOR DIODES FOR SURFACE MOUNTING

Silicon planar diodes designed for use as low-voltage stabilizers or voltage references. They are available in the international standardized E24 (± 5%) range, and also in tolerance ranges of 2% and 3%. The series consists of 37 types with nominal working voltages ranging from 2,4 V to 75 V.

The SM diode is a leadless diode in a hermetically sealed glass SOD-80 envelope with tin plated metal discs at each end. It is suitable for "automatic placement" and as such it can withstand immersion soldering.

The diodes are delivered in "super 8" tape.

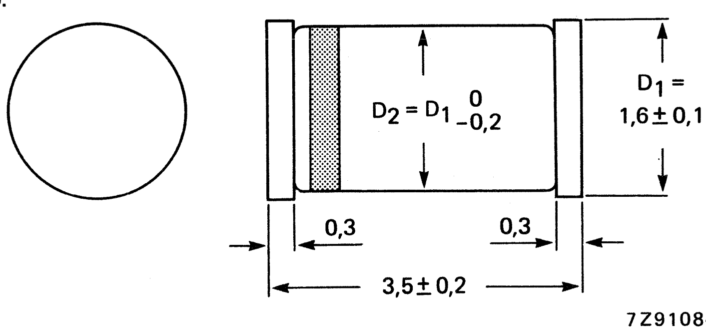
QUICK REFERENCE DATA

Working voltage range	V_Z	nom.	2,4 to 75	V
Total power dissipation up to flange temperature of 50 °C	P_{tot}	max.	500	mW
Non-repetitive peak reverse power dissipation	P_{ZSM}	max.	30	W
Junction temperature	T_j	max.	200	°C
Thermal resistance from junction to tie-point	$R_{th\ j\text{-}tp}$	=	0,30	K/mW

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



The BZV55 cathode is indicated by a yellow band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134).

Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	250 mA
Repetitive peak forward current	I_{FRM}	max.	250 mA
Total power dissipation up to T_{flange} = 50 °C	P_{tot}	max.	500 mW
up to T_{amb} = 50 °C and mounted on a ceramic substrate of 10 mm x 10 mm x 0,6 mm	P_{tot}	max.	400 mW
Non-repetitive peak reverse power dissipation t = 100 μs; T_j = 150 °C	P_{ZSM}	max.	30 W
Storage temperature	T_{stg}	−65 to +200 °C	
Junction temperature	T_j	max.	200 °C

THERMAL RESISTANCE

From junction to tie-point (flanges)	$R_{th\ j\text{-}tp}$	=	0,30 K/mW
From junction to ambient when mounted on a ceramic substrate of 10 mm x 10 mm x 0,6 mm	$R_{th\ j\text{-}a}$	=	0,38 K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage I_F = 10 mA		V_F	<	0,9 V
Reverse current				
BZV55-.2V4	V_R = 1 V	I_R	<	50 μA
.2V7	V_R = 1 V	I_R	<	20 μA
.3V0	V_R = 1 V	I_R	<	10 μA
.3V3	V_R = 1 V	I_R	<	5 μA
.3V6	V_R = 1 V	I_R	<	5 μA
.3V9	V_R = 1 V	I_R	<	3 μA
.4V3	V_R = 1 V	I_R	<	3 μA
.4V7	V_R = 2 V	I_R	<	3 μA
.5V1	V_R = 2 V	I_R	<	2 μA
.5V6	V_R = 2 V	I_R	<	1 μA
.6V2	V_R = 4 V	I_R	<	3 μA
.6V8	V_R = 4 V	I_R	<	2 μA
.7V5	V_R = 5 V	I_R	<	1 μA
.8V2	V_R = 5 V	I_R	<	700 nA
.9V1	V_R = 6 V	I_R	<	500 nA
.10	V_R = 7 V	I_R	<	200 nA
.11 to .13	V_R = 8 V	I_R	<	100 nA
.15 to .75	V_R = 0,7 V_{Znom}	I_R	<	50 nA

. = C for E24 (± 5%) tolerance
. = B for ± 2%
. = F for ± 3%.

± 2% tolerance range

BZV55B	working voltage V_Z (V) at I_{Ztest} = 5 mA		differential resistance r_{diff} (Ω) at I_{Ztest} = 5 mA		temperature coefficient S_Z (mV/K) at I_{Ztest} = 5 mA			differential resistance r_{diff} (Ω) at I_Z = 1 mA	
	min.	max.	typ.	max.	min.	typ.	max.	typ.	max.
B2V4	2,35	2,45	70	100	−3,5	−1,6	0	275	600
B2V7	2,65	2,75	75	100	−3,5	−2,0	0	300	600
B3V0	2,94	3,06	80	95	−3,5	−2,1	0	325	600
B3V3	3,23	3,37	85	95	−3,5	−2,4	0	350	600
B3V6	3,53	3,67	85	90	−3,5	−2,4	0	375	600
B3V9	3,82	3,98	85	90	−3,5	−2,5	0	400	600
B4V3	4,21	4,39	80	90	−3,5	−2,5	0	410	600
B4V7	4,61	4,79	50	80	−3,5	−1,4	0,2	425	500
B5V1	5,00	5,20	40	60	−2,7	−0,8	1,2	400	480
B5V6	5,49	5,71	15	40	−2,0	1,2	2,5	80	400
B6V2	6,08	6,32	6	10	0,4	2,3	3,7	40	150
B6V8	6,66	6,94	6	15	1,2	3,0	4,5	30	80
B7V5	7,35	7,65	6	15	2,5	4,0	5,3	30	80
B8V2	8,04	8,36	6	15	3,2	4,6	6,2	40	80
B9V1	8,92	9,28	6	15	3,8	5,5	7,0	40	100
B10	9,80	10,20	8	20	4,5	6,4	8,0	50	150
B11	10,80	11,20	10	20	5,4	7,4	9,0	50	150
B12	11,80	12,20	10	25	6,0	8,4	10,0	50	150
B13	12,70	13,30	10	30	7,0	9,4	11,0	50	170
B15	14,70	15,30	10	30	9,2	11,4	13,0	50	200
B16	15,70	16,30	10	40	10,4	12,4	14,0	50	200
B18	17,60	18,40	10	45	12,4	14,4	16,0	50	225
B20	19,60	20,40	15	55	14,4	16,4	18,0	60	225
B22	21,60	22,40	20	55	16,4	18,4	20,0	60	250
B24	23,50	24,50	25	70	18,4	20,4	22,0	60	250
	at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA			at I_Z = 0,5 mA	
B27	26,50	27,50	25	80	21,4	23,4	25,3	65	300
B30	29,40	30,60	30	80	24,4	26,6	29,4	70	300
B33	32,30	33,70	35	80	27,4	29,7	33,4	75	325
B36	35,30	36,70	35	90	30,4	33,0	37,4	80	350
B39	38,20	39,80	40	130	33,4	36,4	41,2	80	350
B43	42,10	43,90	45	150	37,6	41,2	46,6	85	375
B47	46,10	47,90	50	170	42,0	46,1	51,8	85	375
B51	50,00	51,00	60	180	46,6	51,0	57,2	90	400
B56	54,90	57,10	70	200	52,2	57,0	63,8	100	425
B62	60,80	63,20	80	215	58,8	64,4	71,6	120	450
B68	66,60	69,40	90	240	65,6	71,7	79,8	150	475
B75	73,50	76,50	95	255	73,4	80,02	88,6	170	500

T_j = 25 °C
± 3% tolerance range

BZV55F	working voltage V_Z (V) at I_{Ztest} = 5 mA min.	max.	differential resistance r_{diff} (Ω) at I_{Ztest} = 5 mA typ.	max.	temperature coefficient S_Z (mV/K) at I_{Ztest} = 5 mA typ.	leakage current I_R at V_R μA	V
F2V	2,33	2,47	70	100	−1,6	50	1
F2V7	2,62	2,78	75	100	−2,0	20	1
F3V0	2,91	3,09	80	100	−2,1	10	1
F3V3	3,20	3,40	85	100	−2,4	5	1
F3V6	3,49	3,71	85	100	−2,4	5	1
F3V9	3,78	4,02	85	100	−2,5	3	1
F4V3	4,17	4,43	80	100	−2,5	3	1
F4V7	4,56	4,84	50	100	−1,4	3	2
F5V1	4,95	5,25	40	80	−0,8	2	2
F5V6	5,43	5,77	15	40	1,2	1	2
F6V2	6,01	6,39	6	30	2,3	3	4
F6V8	6,60	7,00	6	20	3,0	2	4
F7V5	7,28	7,72	6	20	4,0	1	5
F8V2	7,95	8,45	6	20	4,6	0,7	5
F9V1	8,83	9,37	6	20	5,5	0,5	6
F10	9,7	10,30	8	25	6,4	0,2	7
F11	10,67	11,33	10	25	7,4	0,1	8
F12	11,64	12,36	10	25	8,4	0,1	8
F13	12,61	13,39	10	35	9,4	0,1	8
F15	14,55	15,45	10	40	11,4	0,05	10
F16	15,50	16,50	10	45	12,4	0,05	
F18	17,50	18,50	10	50	14,4	0,05	
F20	19,40	20,60	15	60	16,4	0,05	
F22	21,30	22,70	20	70	18,4	0,05	
F24	23,30	24,70	25	80	20,4	0,05	
	at I_{Ztest} = 2 mA		**at I_{Ztest} = 2 mA**		**at I_{Ztest} = 2 mA**	**at I_Z = 0,5 mA**	
F27	26,20	27,80	25	80	23,4	0,05	0,7
F30	29,10	30,90	30	100	26,6	0,05	0,7
F33	32,00	34,00	35	120	29,7	0,05	0,7
F36	34,90	37,10	35	140	33,0	0,05	0,7
F39	37,80	40,20	40	150	36,4	0,05	0,7
F43	41,70	44,30	45	160	41,2	0,05	0,7
F47	45,60	48,40	50	170	46,1	0,05	0,7
F51	49,50	52,50	60	180	51,0	0,05	0,7
F56	54,30	57,70	70	200	57,0	0,05	0,7
F62	60,10	63,90	80	220	64,4	0,05	0,7
F68	66,00	70,00	90	240	71,7	0,05	0,7
F75	72,80	77,20	95	255	80,02	0,05	0,7

T_j = 25 °C

T_j = 25 °C
± 5% tolerance range

BZV55C	working voltage V_Z (V) at I_{Ztest} = 5 mA		differential resistance r_{diff} (Ω) at I_{Ztest} = 5 mA		temperature coefficient S_Z (mV/K) at I_{Ztest} = 5 mA			differential resistance r_{diff} (Ω) at I_Z = 1 mA	
	min.	max.	typ.	max.	min.	typ.	max.	typ.	max.
C2V4	2,20	2,60	70	100	−3,5	−1,6	0	275	600
C2V7	2,50	2,90	75	100	−3,5	−2,0	0	300	600
C3V0	2,80	3,20	80	95	−3,5	−2,1	0	325	600
C3V3	3,10	3,50	85	95	−3,5	−2,4	0	350	600
C3V6	3,40	3,80	85	90	−3,5	−2,4	0	375	600
C3V9	3,70	4,10	85	90	−3,5	−2,5	0	400	600
C4V3	4,00	4,60	80	90	−3,5	−2,5	0	410	600
C4V7	4,40	5,00	50	80	−3,5	−1,4	0,2	425	500
C5V1	4,80	5,40	40	60	−2,7	−0,8	1,2	400	480
C5V6	5,20	6,00	15	40	−2,0	2,5	2,5	80	400
C6V2	5,80	6,60	6	10	0,4	2,3	3,7	40	150
C6V8	6,40	7,20	6	15	1,2	3,0	4,5	30	80
C7V5	7,00	7,90	6	15	2,5	4,0	5,3	30	80
C8V2	7,70	8,90	6	15	3,2	4,6	6,2	40	80
C9V1	9,50	9,60	6	15	3,8	5,5	7,0	40	100
C10	9,40	10,60	8	20	4,5	6,4	8,0	50	150
C11	10,40	11,60	10	20	5,4	7,4	9,0	50	150
C12	11,40	12,70	10	25	6,0	8,4	10,0	50	150
C13	12,40	14,10	10	30	7,0	9,4	11,0	50	170
C15	13,80	15,60	10	30	9,2	11,4	13,0	50	200
C16	15,30	17,10	10	40	10,4	12,4	14,0	50	200
C18	16,80	19,10	10	45	12,4	14,4	16,0	50	225
C20	18,80	21,20	15	55	14,4	16,4	18,0	60	225
C22	20,80	23,30	20	55	16,4	18,4	20,0	60	250
C24	22,80	25,60	25	70	18,4	20,4	22,0	60	250
	at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA			at I_Z = 0,5 mA	
C27	25,10	28,90	25	80	21,4	23,4	25,3	65	300
C30	28,00	32,00	30	80	24,4	26,6	29,4	70	300
C33	31,00	35,00	35	80	27,4	29,7	33,4	75	325
C36	34,00	38,00	35	90	30,4	33,0	37,4	80	350
C39	37,00	41,00	40	130	33,4	36,4	41,2	80	350
C43	40,00	46,00	45	150	37,6	41,2	46,6	85	375
C47	44,00	50,00	50	170	42,0	46,1	51,8	85	375
C51	48,00	54,00	60	180	46,6	51,0	57,2	90	400
C56	52,00	60,00	70	200	52,2	57,0	63,8	100	425
C62	58,00	66,00	80	215	58,8	64,4	71,6	120	450
C68	64,00	72,00	90	240	65,6	71,7	79,8	150	475
C75	70,00	79,00	95	255	73,4	80,02	88,6	170	500

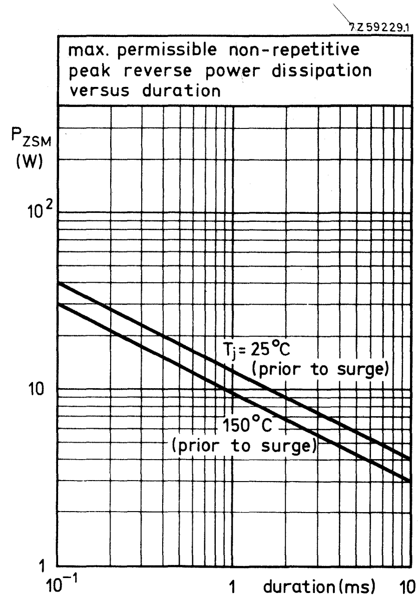

7Z59229.1
max. permissible non-repetitive peak reverse power dissipation versus duration
P_{ZSM} (W)
10^2
10
1
10^{-1}
1
duration (ms)
10
T_j = 25 °C (prior to surge)
150 °C (prior to surge)

Fig. 2.

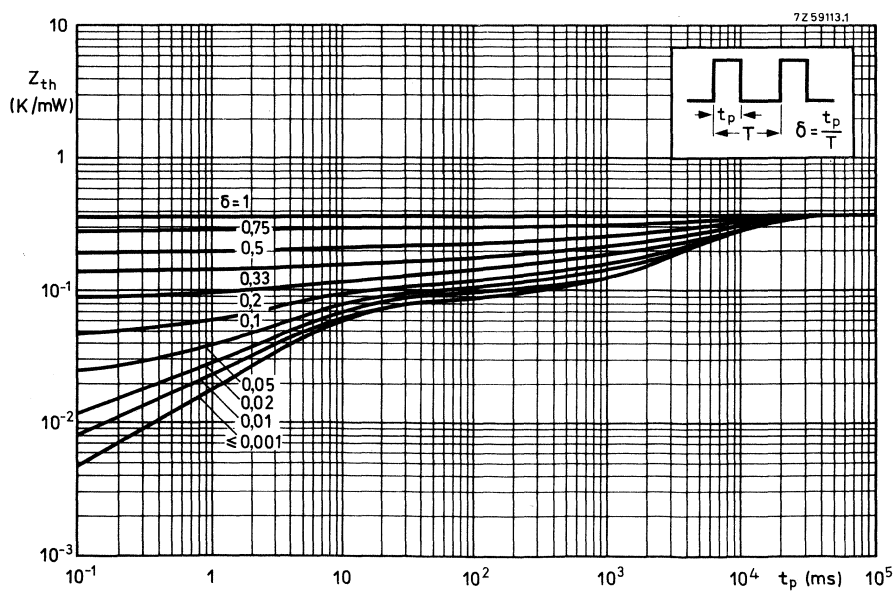

7Z59113.1
Z_{th} (K/mW)
10
1
10^{-1}
10^{-2}
10^{-3}
10^{-1}
1
10
10^2
10^3
10^4
t_p (ms)
10^5
δ = 1
0,75
0,5
0,33
0,2
0,1
0,05
0,02
0,01
≤ 0,001
t_p
T
$\delta = \frac{t_p}{T}$

Fig. 3.

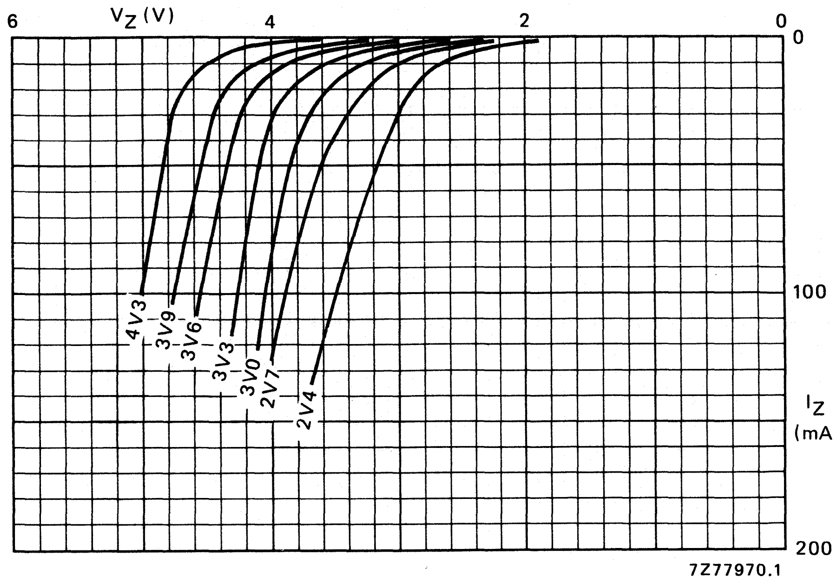


Fig. 4 Static characteristics; typical values; T_{amb} = 25 °C.

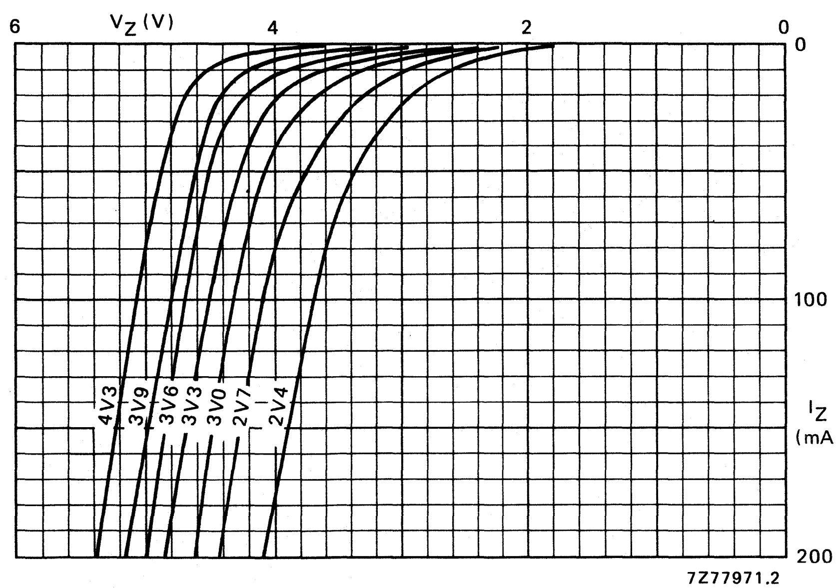


Fig. 5 Dynamic characteristics; typical values; T_j = 25 °C.

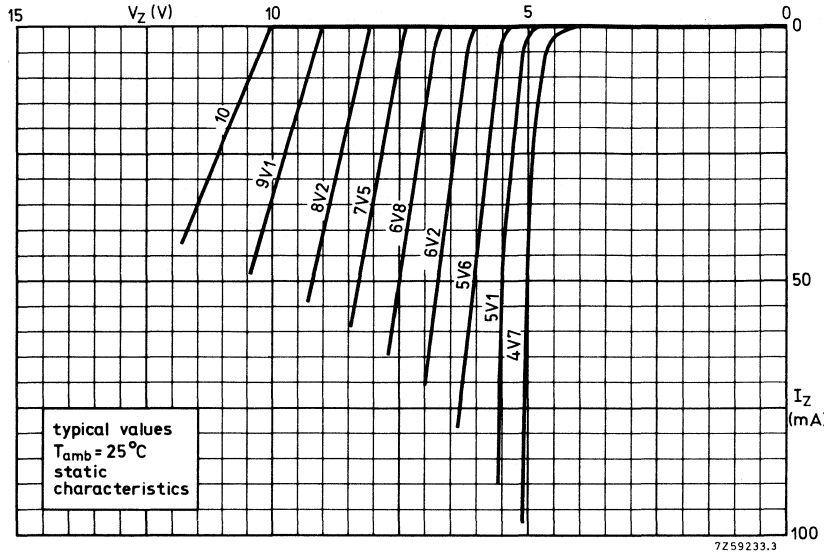

15
V_Z (V)
10
5
0
0
10
9V1
8V2
7V5
6V8
6V2
5V6
5V1
4V7
50
100
I_Z
(mA)
typical values
T_{amb} = 25 °C
static
characteristics
7Z59233.3

Fig. 6.

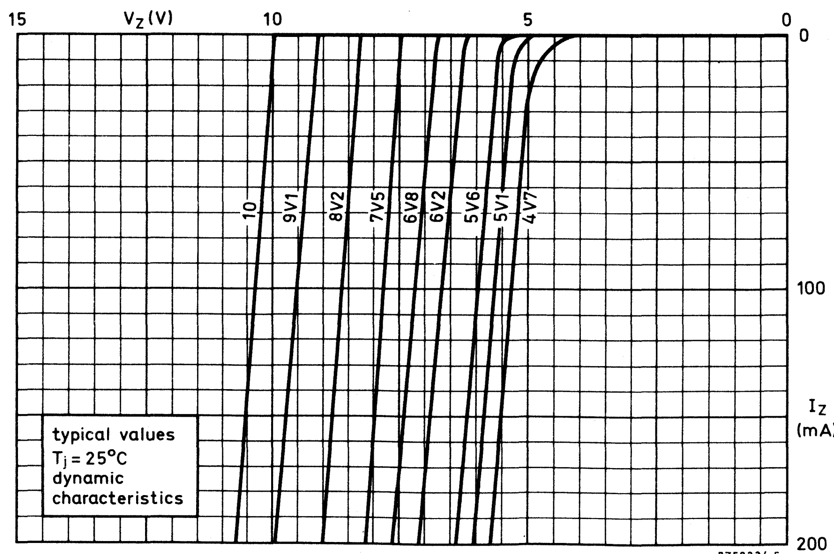

15
V_Z (V)
10
5
0
0
10
9V1
8V2
7V5
6V8
6V2
5V6
5V1
4V7
100
200
I_Z
(mA)
typical values
T_j = 25 °C
dynamic
characteristics
7Z59234.5

Fig. 7.

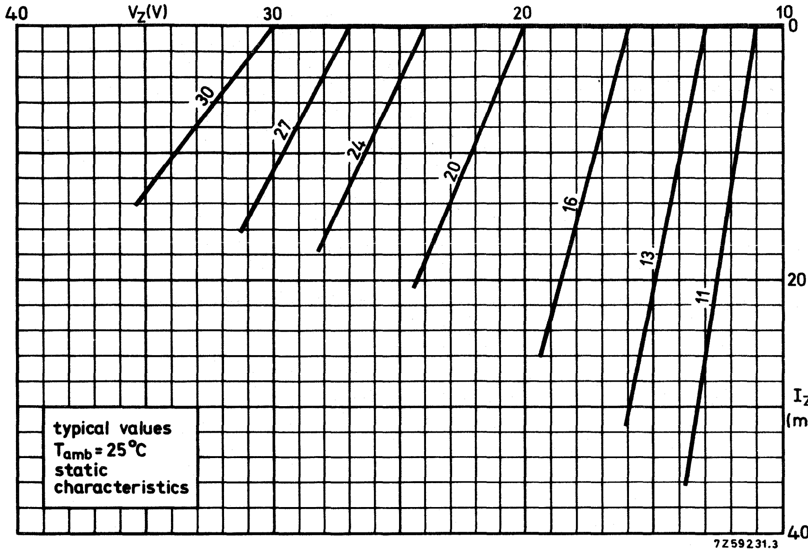

40
V_Z(V)
30
20
10
0
30
27
24
20
16
13
11
20
I_Z
(mA)
40
typical values
T_{amb} = 25 °C
static
characteristics
7Z59231.3

Fig. 8.

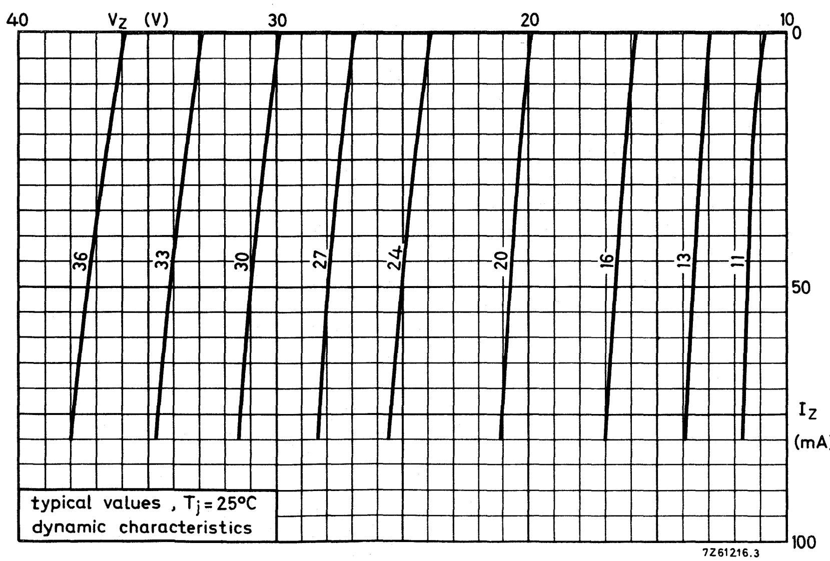

40
V_Z (V)
30
20
10
0
36
33
30
27
24
20
16
13
11
50
I_Z
(mA)
100
typical values , T_j = 25°C
dynamic characteristics
7Z61216.3

Fig. 9.

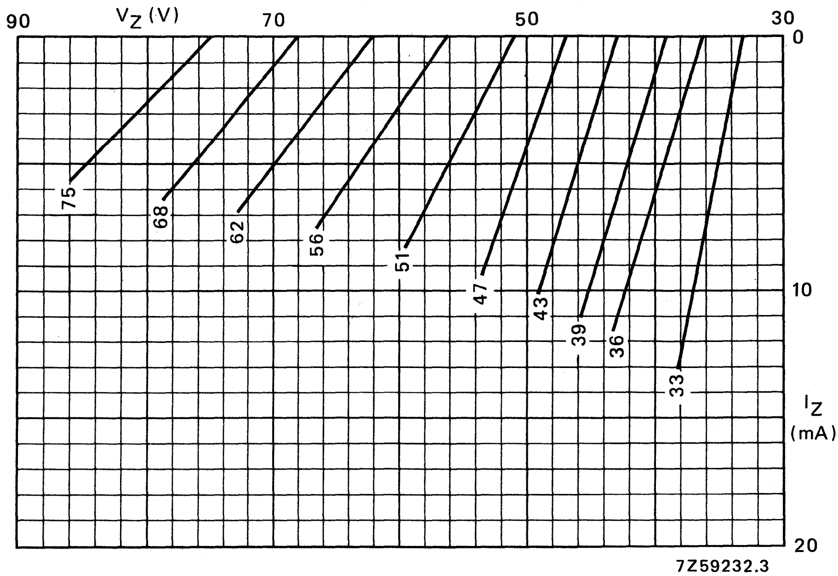


Fig. 10 Static characteristics; typical values; T_{amb} = 25 °C.

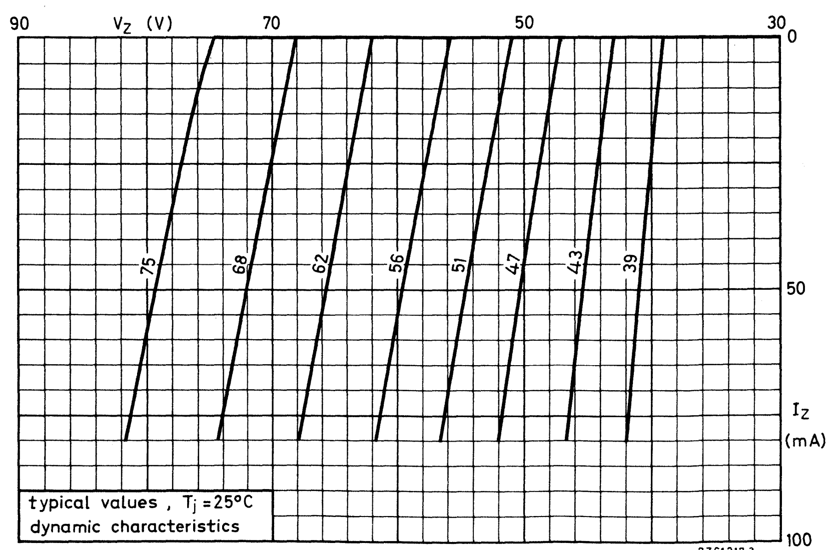


Fig. 11.

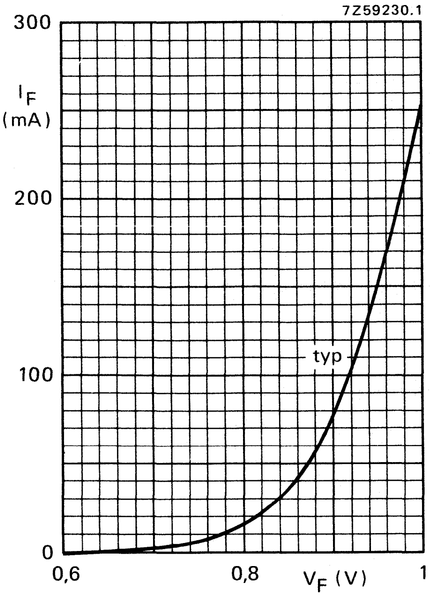


Fig. 12 T_j = 25 °C.

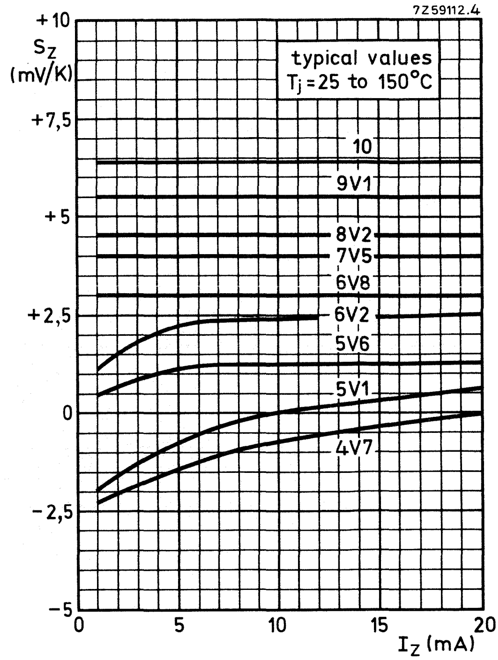


Fig. 13.

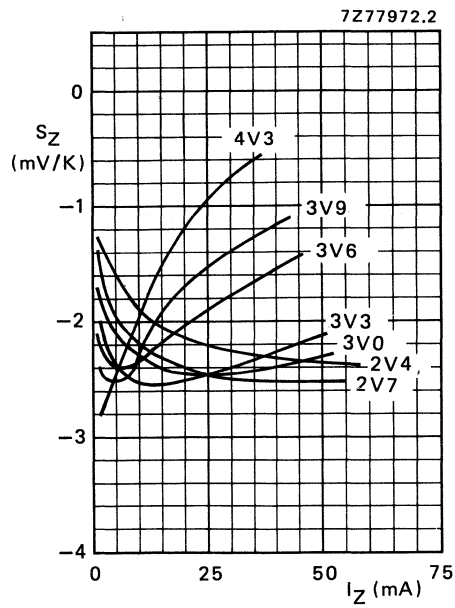


Fig. 14 Typical values; T_j = 25 to 150 °C.

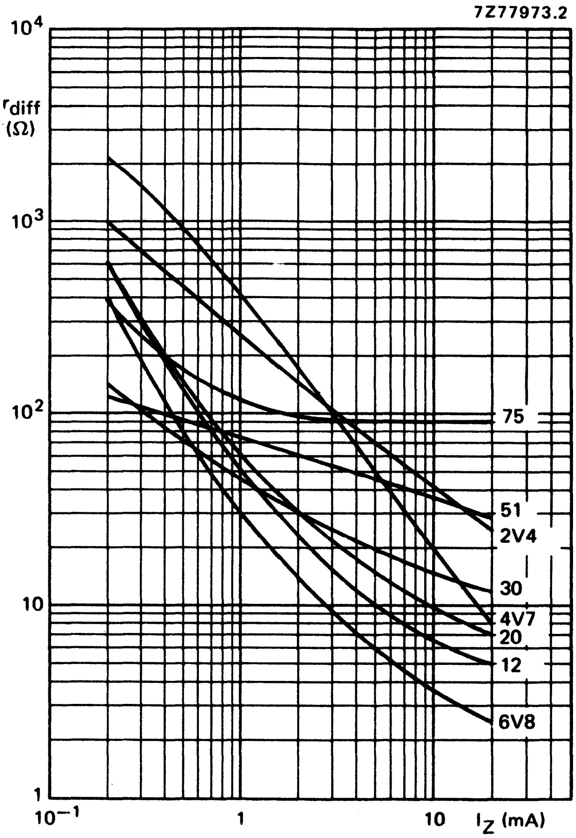


Fig. 15 Typical values; $T_j = 25\ ^oC$; f = 1 kHz.

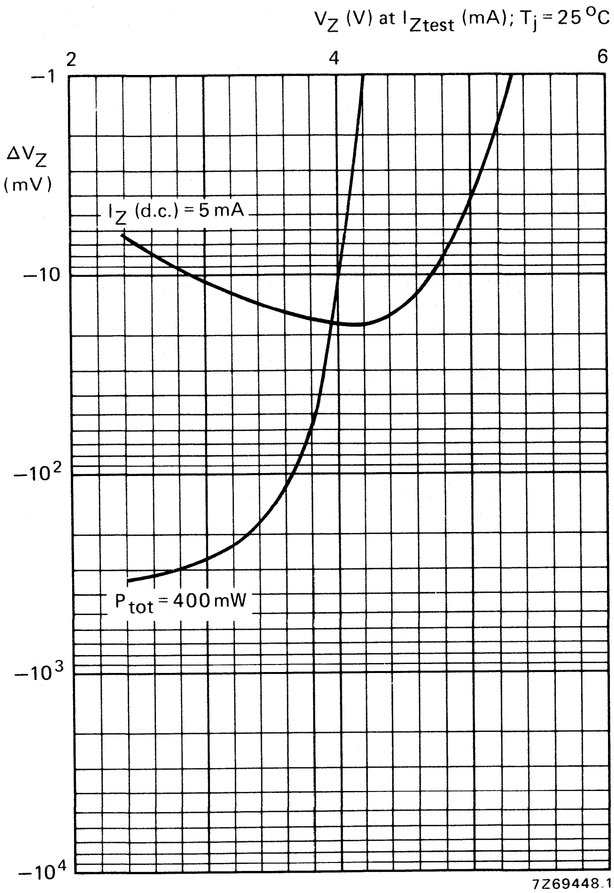


Fig. 16 Typical change of working voltage under operating conditions at T_{amb} = 25 °C.

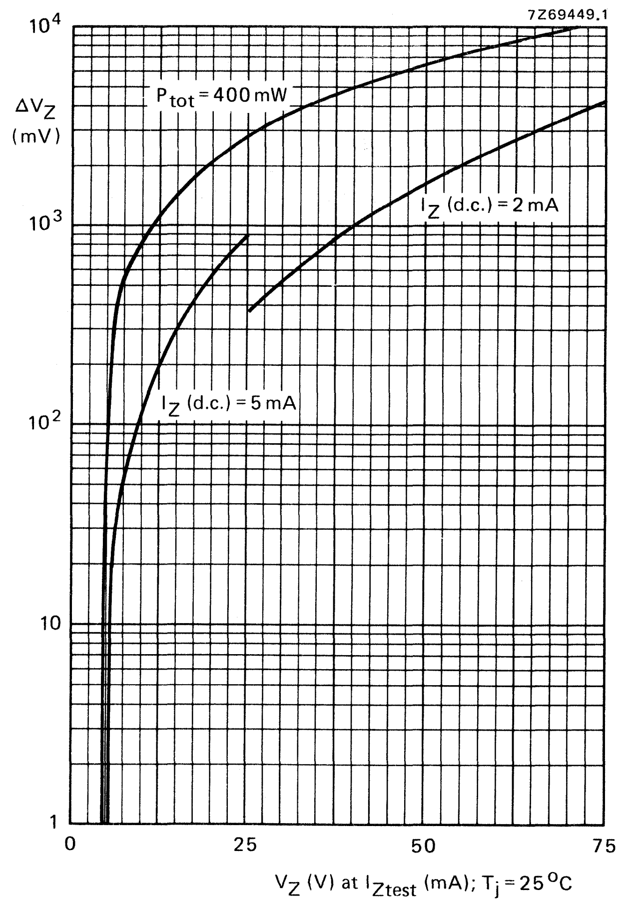


Fig. 17 Typical change of working voltage under operating conditions at T_{amb} = 25 °C.

VOLTAGE REGULATOR DIODES

Silicon planar diodes in DO-34 envelopes intended for use as low voltage stabilizers or voltage references. They are available in international standardized E24 (± 5%) range and ± 2% tolerance range. The series consists of 37 types with nominal working voltages ranging from 2,4 V to 75 V.

QUICK REFERENCE DATA

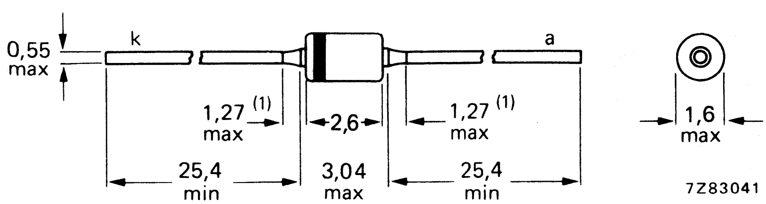
Working voltage range	V_Z	nom.	2,4 to 75	V
Total power dissipation	P_{tot}	max.	500	mW*
Non-repetitive peak reverse power dissipation	P_{ZSM}	max.	30	W
Junction temperature	T_j	max.	200	°C
Thermal resistance from junction to tie-point	$R_{th\ j\text{-}tp}$	=	0,30	K/mW

* If leads are kept at T_{tp} = 50 °C at 8 mm from body.

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-68 (DO-34).



(1) Lead diameter in this zone uncontrolled.
The marking band indicates the cathode.
The diodes are type branded.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	250	mA
Repetitive peak forward current	I_{FRM}	max.	250	mA
Total power dissipation	P_{tot}	max.	500	mW*
		max.	400	mW**
Non-repetitive peak reverse power dissipation $t = 100\ \mu s$; $T_j = 150\ ^oC$	P_{ZSM}	max.	30	W
Storage temperature	T_{stg}	−65 to + 200		^oC
Junction temperature	T_j	max.	200	^oC

THERMAL RESISTANCE

From junction to tie-point	$R_{th\ j\text{-}tp}$		0,30	K/mW*
From junction to ambient	$R_{th\ j\text{-}a}$	=	0,38	K/mW**

CHARACTERISTICS

$T_j = 25\ ^oC$

Forward voltage $I_F = 100$ mA		V_F	<	1,0	V
Reverse current					
BZV60-.2V4	$V_R = 1$ V	I_R	<	50	μA
.2V7	$V_R = 1$ V	I_R	<	20	μA
.3V0	$V_R = 1$ V	I_R	<	10	μA
.3V3	$V_R = 1$ V	I_R	<	5	μA
.3V6	$V_R = 1$ V	I_R	<	5	μA
.3V9	$V_R = 1$ V	I_R	<	3	μA
.4V3	$V_R = 1$ V	I_R	<	3	μA
.4V7	$V_R = 2$ V	I_R	<	3	μA
.5V1	$V_R = 2$ V	I_R	<	2	μA
.5V6	$V_R = 2$ V	I_R	<	1	μA
.6V2	$V_R = 4$ V	I_R	<	3	μA
.6V8	$V_R = 4$ V	I_R	<	2	μA
.7V5	$V_R = 5$ V	I_R	<	1	μA
.8V2	$V_R = 5$ V	I_R	<	700	nA
.9V1	$V_R = 6$ V	I_R	<	500	nA
.10	$V_R = 7$ V	I_R	<	200	nA
.11 to .13	$V_R = 8$ V	I_R	<	100	nA
.15 to .75	$V_R = 0{,}7\ V_{Znom}$	I_R	<	50	nA

. = B for 2% tolerance range

→ . = C for E24 (+/−5%) tolerance range

* If leads are kept at $T_{tp} = 50\ ^oC$ at max. 8 mm from body. For the types 2V4 and 2V7 the power dissipation is limited by $T_{j\ max} = 150\ ^oC$.

** In still air at maximum lead length up to $T_{amb} = 50\ ^oC$.

$T_j = 25\ ^oC$

E24 (± 5%) logarithmic range

BZV60-C	working voltage V_Z (V) at I_{Ztest} = 5 mA		differential resistance r_{diff} (Ω) at I_{Ztest} = 5 mA		temperature coefficient S_Z (mV/K) at I_{Ztest} = 5 mA			differential resistance r_{diff} (Ω) at I_Z = 1 mA	
	min.	max.	typ.	max.	min.	typ.	max.	typ.	max.
C2V4	2,2	2,6	70	100	−3,5	−1,6	0	275	600
C2V7	2,5	2,9	75	100	−3,5	−2,0	0	300	600
C3V0	2,8	3,2	80	95	−3,5	−2,1	0	325	600
C3V3	3,1	3,5	85	95	−3,5	−2,4	0	350	600
C3V6	3,4	3,8	85	90	−3,5	−2,4	0	375	600
C3V9	3,7	4,1	85	90	−3,5	−2,5	0	400	600
C4V3	4,0	4,6	80	90	−3,5	−2,5	0	410	600
C4V7	4,4	5,0	50	80	−3,5	−1,4	0,2	425	500
C5V1	4,8	5,4	40	60	−2,7	−0,8	1,2	400	480
C5V6	5,2	6,0	15	40	−2,0	1,2	2,5	80	400
C6V2	5,8	6,6	6	10	0,4	2,3	3,7	40	150
C6V8	6,4	7,2	6	15	1,2	3,0	4,5	30	80
C7V5	7,0	7,9	6	15	2,5	4,0	5,3	30	80
C8V2	7,7	8,7	6	15	3,2	4,6	6,2	40	80
C9V1	8,5	9,6	6	15	3,8	5,5	7,0	40	100
C10	9,4	10,6	8	20	4,5	6,4	8,0	50	150
C11	10,4	11,6	10	20	5,4	7,4	9,0	50	150
C12	11,4	12,7	10	25	6,0	8,4	10,0	50	150
C13	12,4	14,1	10	30	7,0	9,4	11,0	50	170
C15	13,8	15,6	10	30	9,2	11,4	13,0	50	200
C16	15,3	17,1	10	40	10,4	12,4	14,0	50	200
C18	16,8	19,1	10	45	12,4	14,4	16,0	50	225
C20	18,8	21,2	15	55	14,4	16,4	18,0	60	225
C22	20,8	23,3	20	55	16,4	18,4	20,0	60	250
C24	22,8	25,6	25	70	18,4	20,4	22,0	60	250
	at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA			at I_Z = 0,5 mA	
C27	25,1	28,9	25	80	21,4	23,4	25,3	65	300
C30	28,0	32,0	30	80	24,4	26,6	29,4	70	300
C33	31,0	35,0	35	80	27,4	29,7	33,4	75	325
C36	34,0	38,0	35	90	30,4	33,0	37,4	80	350
C39	37,0	41,0	40	130	33,4	36,4	41,2	80	350
C43	40,0	46,0	45	150	37,6	41,2	46,6	85	375
C47	44,0	50,0	50	170	42,0	46,1	51,8	85	375
C51	48,0	54,0	60	180	46,6	51,0	57,2	90	400
C56	52,0	60,0	70	200	52,2	57,0	63,8	100	425
C62	58,0	66,0	80	215	58,8	64,4	71,6	120	450
C68	64,0	72,0	90	240	65,6	71,7	79,8	150	475
C75	70,0	79,0	95	255	73,4	80,2	88,6	170	500

T_j = 25 °C
± 2% tolerance range.

BZV60-B	working voltage V_Z (V)		differential resistance r_{diff} (Ω)		temperature coefficient S_Z (mV/K)			differential resistance r_{diff} (Ω)	
	at I_{Ztest} = 5 mA		at I_{Ztest} = 5 mA		at I_{Ztest} = 5 mA			at I_Z = 1 mA	
	min.	max.	typ.	max.	min.	typ.	max.	typ.	max.
B2V4	2,35	2,45	70	100	−3,5	−1,6	0	275	600
B2V7	2,65	2,75	75	100	−3,5	−2,0	0	300	600
B3V0	2,94	3,06	80	95	−3,5	−2,1	0	325	600
B3V3	3,23	3,37	85	95	−3,5	−2,4	0	350	600
B3V6	3,53	3,67	85	90	−3,5	−2,4	0	375	600
B3V9	3,82	3,98	85	90	−3,5	−2,5	0	400	600
B4V3	4,21	4,39	80	90	−3,5	−2,5	0	410	600
B4V7	4,61	4,79	50	80	−3,5	−1,4	0,2	425	500
B5V1	5,00	5,20	40	60	−2,7	−0,8	1,2	400	480
B5V6	5,49	5,71	15	40	−2,0	1,2	2,5	80	400
B6V2	6,08	6,32	6	10	0,4	2,3	3,7	40	150
B6V8	6,66	6,94	6	15	1,2	3,0	4,5	30	80
B7V5	7,35	7,65	6	15	2,5	4,0	5,3	30	80
B8V2	8,04	8,36	6	15	3,2	4,6	6,2	40	80
B9V1	8,92	9,28	6	15	3,8	5,5	7,0	40	100
B10	9,80	10,20	8	20	4,5	6,4	8,0	50	150
B11	10,80	11,20	10	20	5,4	7,4	9,0	50	150
B12	11,80	12,20	10	25	6,0	8,4	10,0	50	150
B13	12,70	13,30	10	30	7,0	9,4	11,0	50	170
B15	14,70	15,30	10	30	9,2	11,4	13,0	50	200
B16	15,70	16,30	10	40	10,4	12,4	14,0	50	200
B18	17,60	18,40	10	45	12,4	14,4	16,0	50	225
B20	19,60	20,40	15	55	14,4	16,4	18,0	60	225
B22	21,60	22,40	20	55	16,4	18,4	20,0	60	250
B24	23,50	24,50	25	70	18,4	20,4	22,0	60	250
	at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA			at I_Z = 0,5 mA	
B27	26,50	27,50	25	80	21,4	23,4	25,3	65	300
B30	29,40	30,60	30	80	24,4	26,6	29,4	70	300
B33	32,30	33,70	35	80	27,4	29,7	33,4	75	325
B36	35,30	36,70	35	90	30,4	33,0	37,4	80	350
B39	38,20	39,80	40	130	33,4	36,4	41,2	80	350
B43	42,10	43,90	45	150	37,6	41,2	46,6	85	375
B47	46,10	47,90	50	170	42,0	46,1	51,8	85	375
B51	50,00	52,00	60	180	46,6	51,0	57,2	90	400
B56	54,90	57,10	70	200	52,2	57,0	63,8	100	425
B62	60,80	63,20	80	215	58,8	64,4	71,6	120	450
B68	66,60	69,40	90	240	65,6	71,7	79,8	150	475
B75	73,50	76,50	95	255	73,4	80,2	88,6	170	500

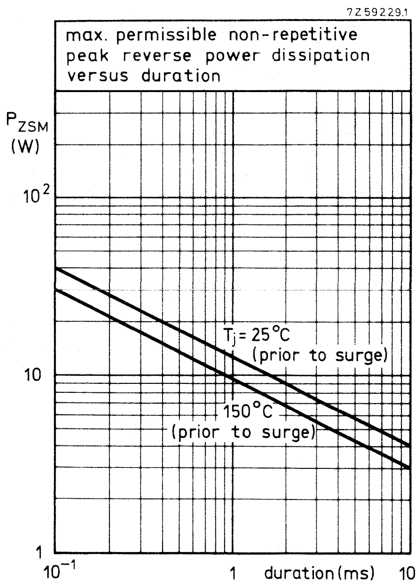

7Z59229.1
max. permissible non-repetitive
peak reverse power dissipation
versus duration
P_{ZSM}
(W)
10^2
10
1
T_j = 25 °C
(prior to surge)
150 °C
(prior to surge)
10^{-1}
1
duration (ms)
10

Fig. 2.

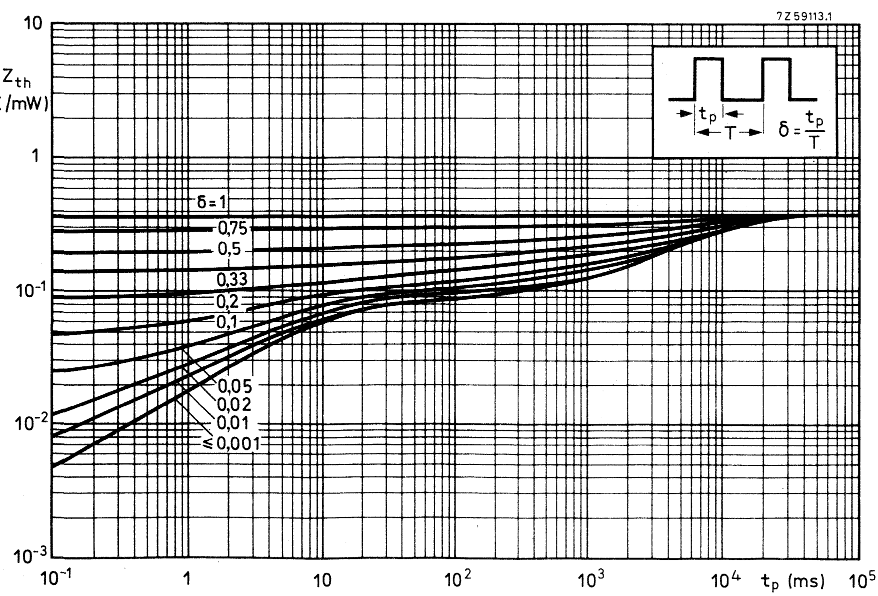

7Z59113.1
Z_{th}
(K/mW)
10
1
10^{-1}
10^{-2}
10^{-3}
δ = 1
0,75
0,5
0,33
0,2
0,1
0,05
0,02
0,01
≤ 0,001
t_p
T
$\delta = \frac{t_p}{T}$
10^{-1}
1
10
10^2
10^3
10^4
t_p (ms)
10^5

Fig. 3.

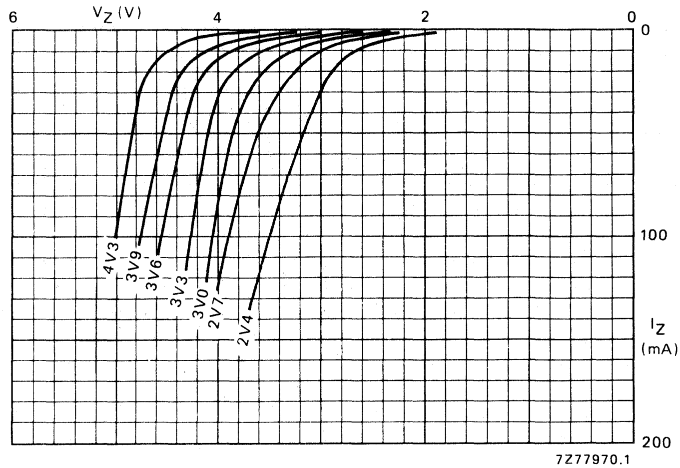


Fig. 4 Static characteristics; typical values; T_{amb} = 25 °C.

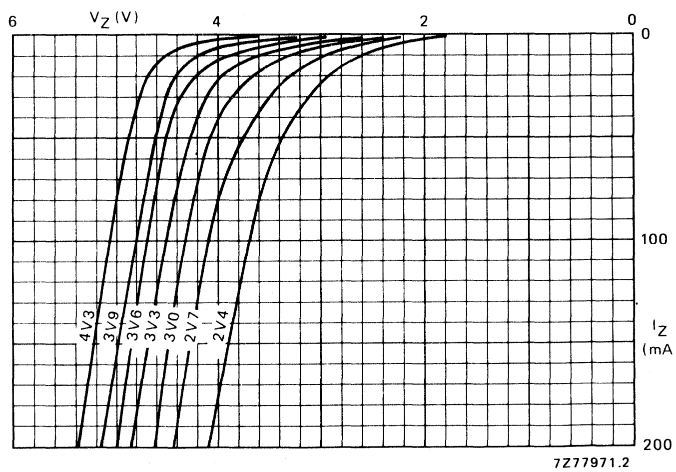


Fig. 5 Dynamic characteristics; typical values; T_j = 25 °C.

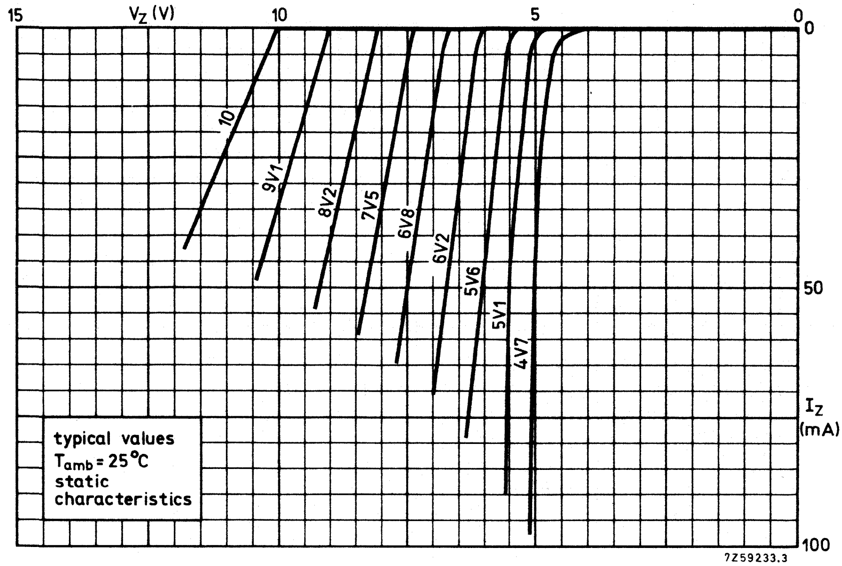

15
V_Z (V)
10
5
0
0
50
100
I_Z (mA)
10
9V1
8V2
7V5
6V8
6V2
5V6
5V1
4V7
typical values
T_{amb} = 25 °C
static
characteristics
7Z59233.3

Fig. 6.

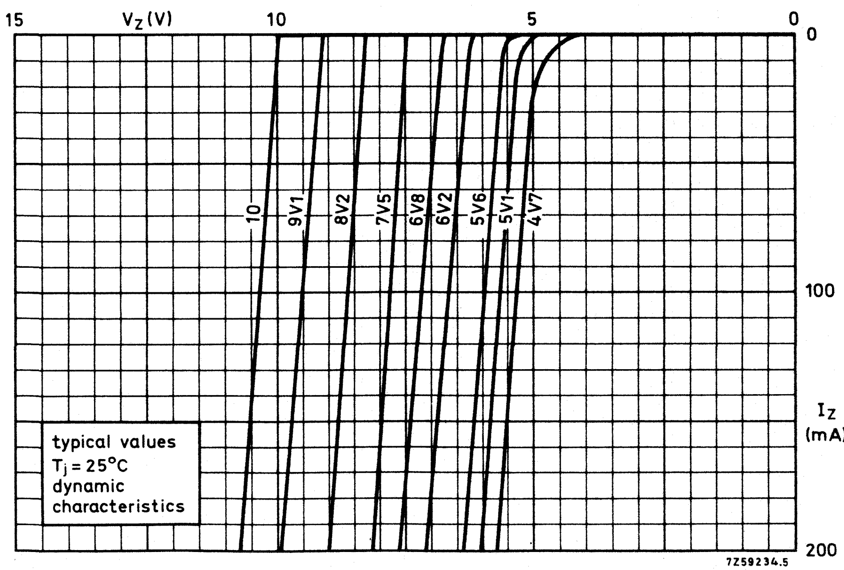

15
V_Z (V)
10
5
0
0
100
200
I_Z (mA)
10
9V1
8V2
7V5
6V8
6V2
5V6
5V1
4V7
typical values
T_j = 25 °C
dynamic
characteristics
7Z59234.5

Fig. 7.

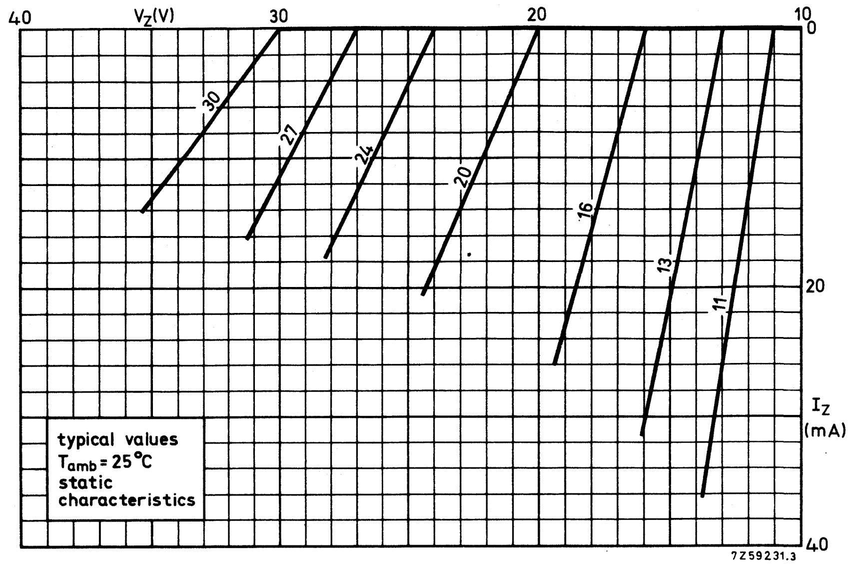

40
V_Z(V)
30
20
10
0
30
27
24
20
16
13
11
20
I_Z
(mA)
40
typical values
T_{amb} = 25 °C
static
characteristics
7Z59231.3

Fig. 8.

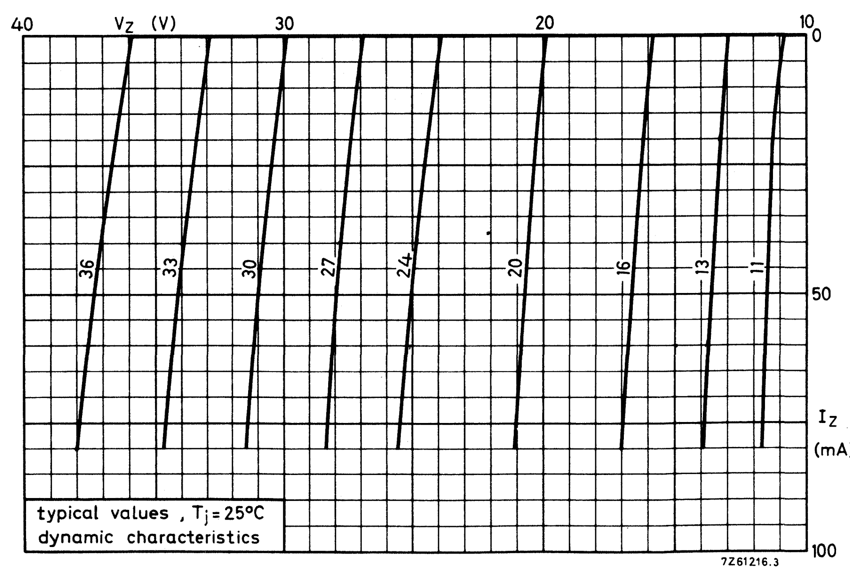

40
V_Z (V)
30
20
10
0
36
33
30
27
24
20
16
13
11
50
I_Z
(mA)
100
typical values , T_j = 25 °C
dynamic characteristics
7Z61216.3

Fig. 9.

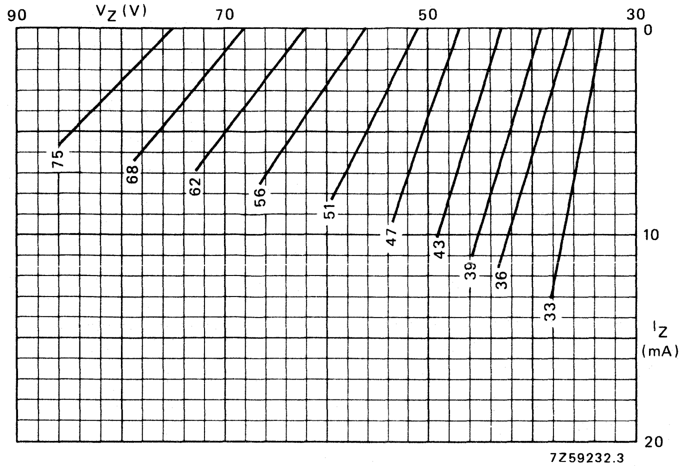


Fig. 10 Static characteristics; typical values; T_{amb} = 25 °C.

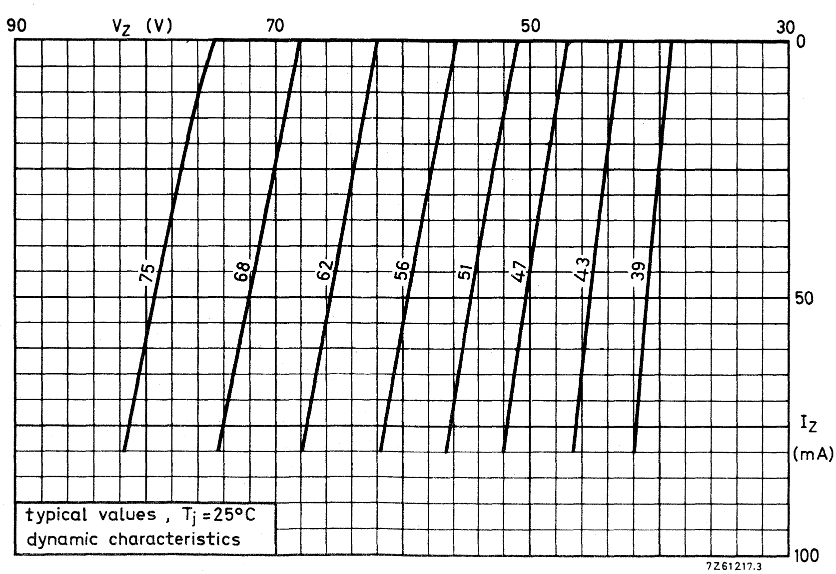


Fig. 11.

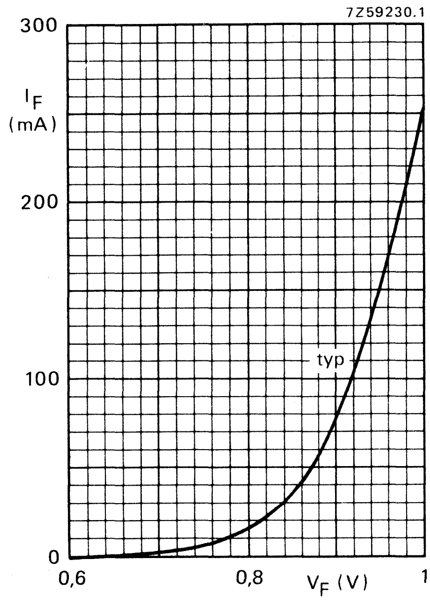


Fig. 12 T_j = 25 °C.

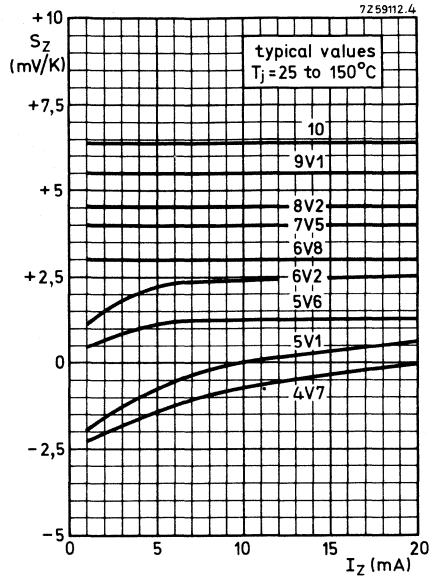


Fig. 13.

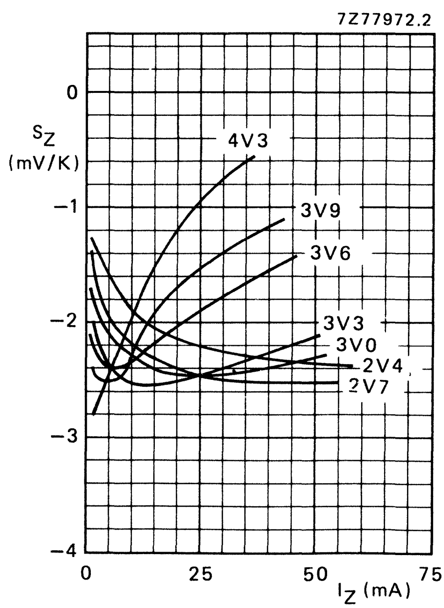


Fig. 14 Typical values; T_j = 25 to 150 °C.

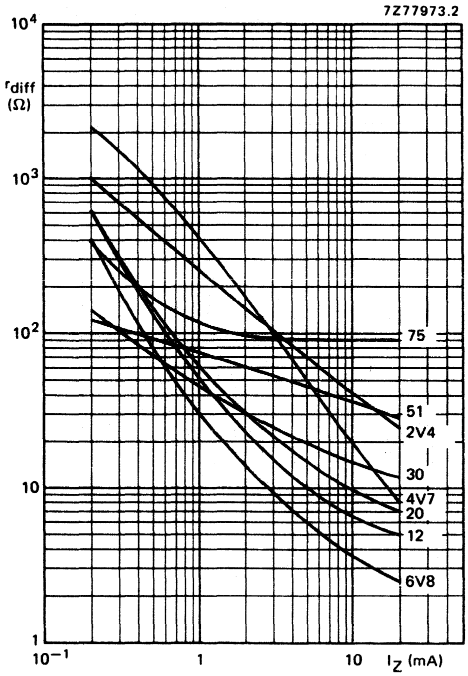


Fig. 15 Typical values; T_j = 25 °C; f = 1 kHz.

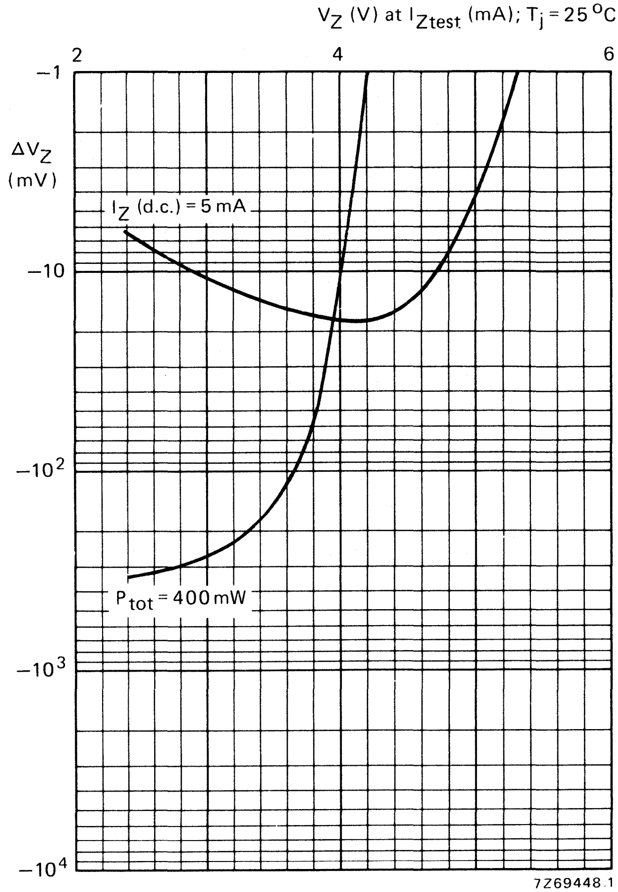


Fig. 16 Typical change of working voltage under operating conditions at $T_{amb} = 25\ ^oC$.

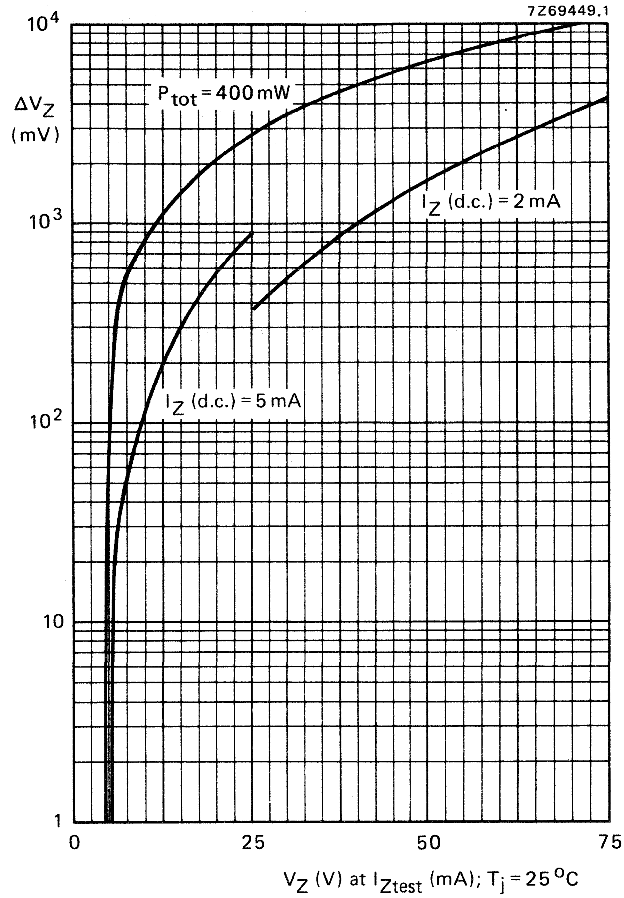


Fig. 17 Typical change of working voltage under operating conditions at $T_{amb} = 25\,^{o}C$.

VOLTAGE REFERENCE DIODES FOR SURFACE MOUNTING

Voltage reference diodes in a SOD-80 envelope. They have a low temperature coefficient and are primarily intended for use as voltage reference sources.

The SM diode is a leadless diode in a hermetically sealed glass SOD-80 envelope with tinplated metal discs at each end. It is suitable for "automatic placement" and as such it can withstand immersion soldering.

The diodes are delivered in bulk or in "super 8" tape.

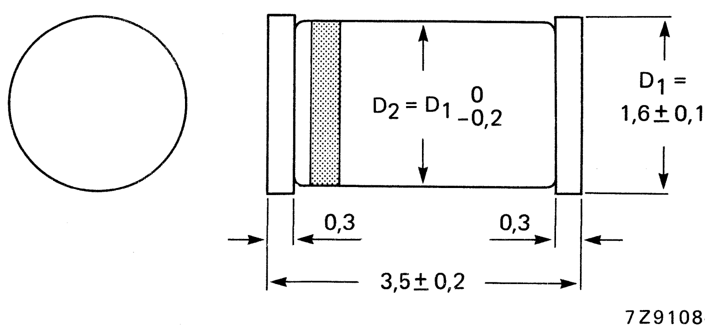
QUICK REFERENCE DATA

Reference voltage at I_Z = 7,5 mA		V_{ref}	>	5,89	V
			typ.	6,20	V
			<	6,51	V
Temperature coefficient at I_Z = 7,5 mA	BZV80	$\|S_Z\|$	<	0,01	%/K
	BZV81	$\|S_Z\|$	<	0,005	%/K
Operating temperature		T_{amb}		−20 to + 80	°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80



Cathode indicated by yellow band

BZV80 second band: black

BZV81 second band: brown

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Working current (d.c.)	I_Z	max.	50 mA
Working current (peak value)	I_{ZM}	max.	50 mA
Total power dissipation up to T_{amb} = 50 °C	P_{tot}	max.	400 mW
Storage temperature	T_{stg}		−65 to + 200 °C
Operating ambient temperature	T_{amb}		−20 to + 80 °C

THERMAL RESISTANCE

From junction to ambient mounted on a ceramic substrate of 10 x 10 x 0,6 mm	$R_{th\ j\text{-}a}$	=	380 K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

			>	5,89 V
Reference voltage at I_Z = 7,5 mA		V_{ref}	typ.	6,20 V
			<	6,51 V
Reference voltage excursion at I_Z = 7,5 mA ambient temperature test points	BZV80	$\lvert\Delta V_{ref}\rvert$	<	62 mV
−20; + 25; + 55; + 80 °C	BZV81	$\lvert\Delta V_{ref}\rvert$	<	31 mV
Effective temperature coefficient at I_Z = 7,5 mA	BZV80	$\lvert S_Z\rvert$	<	0,01 %/K
	BZV81	$\lvert S_Z\rvert$	<	0,005 %/K
Differential resistance at I_Z = 7,5 mA		r_{diff}	<	15 Ω

Notes

1. Tolerance and stability of I_Z.
   The quoted values of ΔV_{ref} are based on a constant current I_Z. Two factors can cause V_{ref} to change with I_Z, namely the differential resistance r_{diff} and the temperature coefficient S_Z.
   a. Each change of I_Z can result in a maximum change of V_{ref} as follows:
   $$\Delta V_{ref}\ (\text{mV}) = \Delta I_Z\ (\text{mA}) \times 15\ \Omega$$
   taking into account r_{diff} is max. 15 Ω.
   b. The temperature coefficient of the reference voltage is also a function of I_Z. However, for these reference diodes S_Z varies max. ± 0,05 mV/K or ± 0,001 %/K when I_Z is between 6 and 10 mA, so this effect can be neglected in practice for these types.

2. The temperature coefficient of the reference voltage is obtained from the following equation.
$$S_Z = \frac{(V_{ref\,1} - V_{ref\,2})}{(T_{amb\,2} - T_{mab\,1})} \times \frac{100}{V_{ref\,nom}}\ \%/\text{K}$$

VOLTAGE REGULATOR DIODES

Silicon planar voltage regulator diodes in hermetically sealed DO-41 glass envelopes intended for stabilization purposes. The series covers the normalized E24 (± 5%) range of nominal working voltages ranging from 3,6 V to 75 V.

QUICK REFERENCE DATA

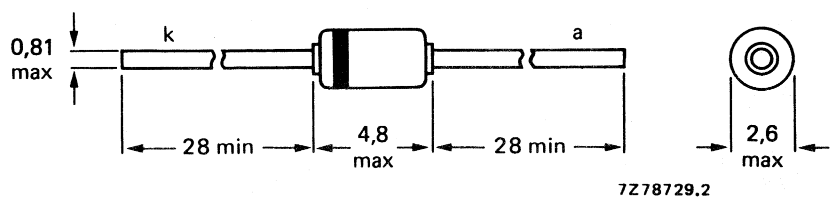
Working voltage range	V_Z	nom.	3,6 to 75	V
Total power dissipation	P_{tot}	max.	1,3	W*
Non-repetitive peak reverse power dissipation t_p = 100 μs; T_j = 25 °C	P_{ZSM}	max.	60	W
Junction temperature	T_j	max.	200	°C
Thermal resistance from junction to tie-point	$R_{th\ j\text{-}tp}$	=	110	K/W*

* If leads are kept at T_{tp} = 55 °C at 4 mm from body.

MECHANICAL DATA

Dimensions in mm

Fig. 1 DO-41 (SOD-66).



Cathode indicated by coloured band.

Products approved to CECC 50 005-010 available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Working current (d.c.)	I_Z	limited by $P_{tot\,max}$		
Non-repetitive peak reverse current t_p = 10 ms; half sine-wave; T_{amb} = 25 °C	I_{ZSM}	see table below		
Repetitive peak forward current	I_{FRM}	max.	250	mA
Total power dissipation (see also Fig. 2)	P_{tot}	max.	1,30	W*
		max.	1	W**
Non-repetitive peak reverse power dissipation t_p = 100 μs; T_j = 25 °C	P_{ZSM}	max.	60	W
Storage temperature	T_{stg}	−65 to + 200		°C
Junction temperature	T_j	max.	200	°C

THERMAL RESISTANCE

From junction to tie-point	$R_{th\,j\text{-}tp}$	=	110	K/W*
From junction to ambient mounted on a printed-circuit board	$R_{th\,j\text{-}a}$	=	175	K/W**

BZV85–. . . .	Non-repetitive peak reverse current I_{ZSM} (mA) max.
C3V6	2000
C3V9	1950
C4V3	1850
C4V7	1800
C5V1	1750
C5V6	1700
C6V2	1620
C6V8	1550
C7V5	1500
C8V2	1400
C9V1	1340
C10	1200
C11	1100
C12	1000
C13	900
C15	760
C16	700

BZV85–. . .	Non-repetitive peak reverse current I_{ZSM} (mA) max.
C18	600
C20	540
C22	500
C24	450
C27	400
C30	380
C33	350
C36	320
C39	296
C43	270
C47	246
C51	226
C56	208
C62	186
C68	171
C75	161

* If the temperature of the leads at 4 mm from the body are kept up to T_{tp} = 55 °C.
** Measured in still air up to T_{amb} = 25 °C and mounted on printed-circuit board with lead length of 10 mm and print copper area of 1 cm² per lead.

CHARACTERISTICS

T_j = 25 °C

Forward voltage at I_F = 50 mA V_F < 1,0 V

	working voltage V_Z (V) at I_{Ztest} = 5 mA		differential resistance r_{diff} (Ω) at I_{Ztest} = 5 mA		temperature coefficient S_Z (mV/K) at I_{Ztest} = 5 mA			differential resistance r_{diff} (Ω) at I_{Ztest} = 1 mA	
	min.	max.	typ.	max.	min.	typ.	max.	typ.	max.
BZV85–									
C2V4	2,20	2,60	70	100	–3,5	–1,6	0	275	600
C2V7	2,50	2,90	75	100	–3,5	–2,0	0	300	600
C3V0	2,80	3,20	80	95	–3,5	–2,1	0	325	600
C3V3	3,10	3,50	85	95	–3,5	–2,4	0	350	600
C3V6	3,40	3,80	85	90	–3,5	–2,4	0	375	600
C3V9	3,70	4,10	85	90	–3,5	–2,5	0	400	600
C4V3	4,00	4,60	80	90	–3,5	–2,5	0	410	600
C4V7	4,40	5,00	50	80	–3,5	–1,4	0,2	425	500
C5V1	4,80	5,40	40	60	–2,7	–0,8	1,2	400	480
C5V6	5,20	6,00	15	40	–2,0	1,2	2,5	80	400
C6V2	5,80	6,60	6	10	0,4	2,3	3,7	40	150
C6V8	6,40	7,20	6	15	1,2	3,0	4,5	30	80
C7V5	7,00	7,90	6	15	2,5	4,0	5,3	30	80
C8V2	7,70	8,90	6	15	3,2	4,6	6,2	40	80
C9V1	9,50	9,60	6	15	3,8	5,5	7,0	40	100
C10	9,40	10,60	8	20	4,5	6,5	8,0	50	150
C11	10,40	11,60	10	20	5,4	7,4	9,0	50	150
C12	11,40	12,70	10	25	6,0	8,4	10,0	50	150
C13	12,40	14,10	10	30	7,0	9,4	11,0	50	170
C15	13,80	15,60	10	30	9,2	11,4	13,0	50	200
C16	15,30	17,10	10	40	10,4	12,4	14,0	50	200
C18	16,80	19,10	10	45	12,4	14,4	16,0	50	225
C20	18,80	21,20	15	55	14,4	16,4	18,0	60	225
C22	20,80	23,30	20	55	16,4	18,4	20,0	60	250
C24	22,80	25,60	25	70	18,4	20,4	22,0	60	250
	at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA			at I_{Ztest} = 0,5 mA	
C27	25,10	28,90	25	80	21,4	23,4	25,3	65	300
C30	28,00	32,00	30	80	24,4	26,6	29,4	70	300
C33	31,00	35,00	35	80	27,4	29,7	33,4	75	325
C36	34,00	38,00	35	90	30,4	33,0	37,4	80	350
C39	37,00	41,00	40	130	33,4	36,4	41,2	80	350
C43	40,00	46,00	45	150	37,6	41,2	46,6	85	375
C47	44,00	50,00	50	170	42,0	46,1	51,8	85	375
C51	48,00	54,00	60	180	46,6	51,0	57,2	90	400
C56	52,00	60,00	70	200	52,2	57,0	63,8	100	425
C62	58,00	66,00	80	215	58,8	64,4	71,6	120	450
C68	64,00	72,00	90	240	65,6	71,7	79,8	150	475
C75	70,00	79,00	95	255	73,4	80,02	88,6	170	500

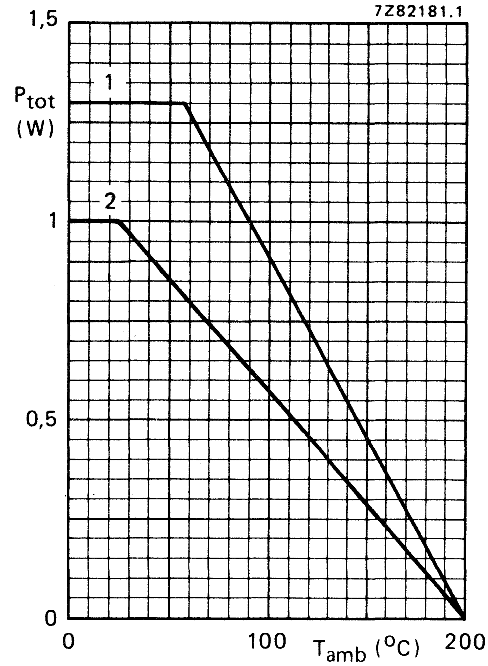


Fig. 2 Maximum permissible power dissipation versus ambient temperature.

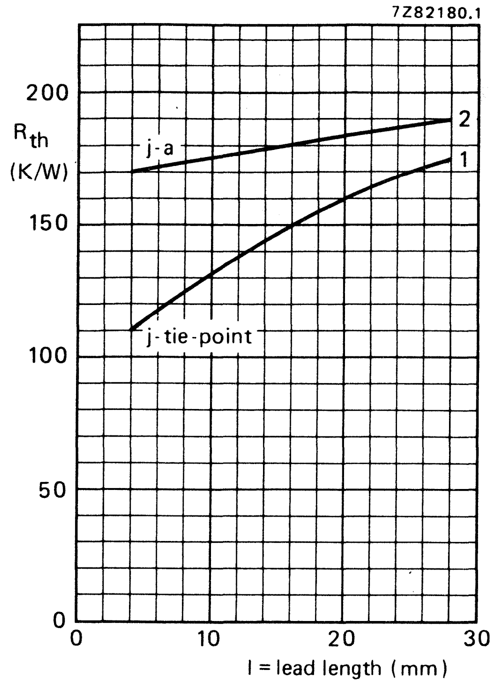
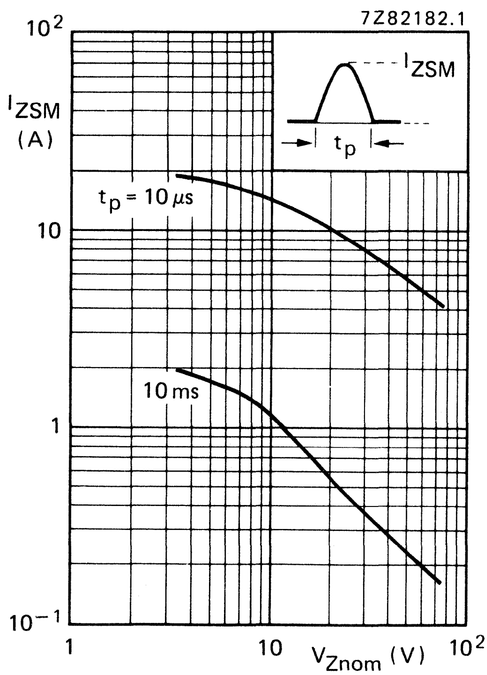


Fig. 3 Thermal resistance versus lead length.



Mounting methods (see Figs 2 and 3)

1. To tie-points (lead length = 4 mm in Fig. 2).
2. Mounted on a printed-circuit board (with lead length of 10 mm in Fig. 2) and print copper area of 1 cm^2 per lead.

Fig. 4 Half sine-wave; T_{amb} = 25 °C.

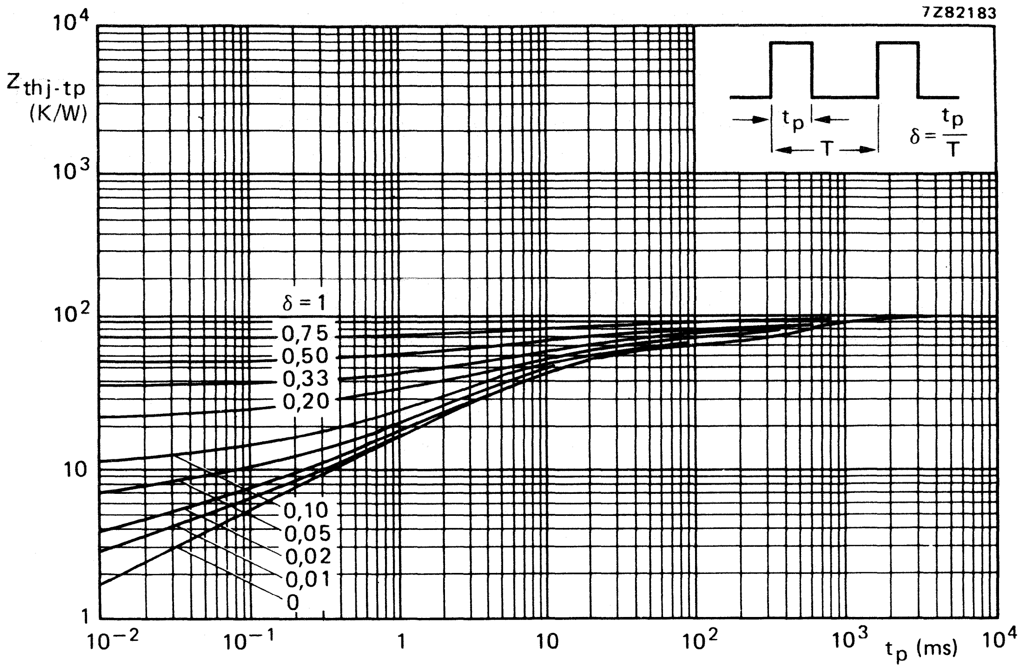


Fig. 5 Thermal impedance from junction to tie-point with a lead length of 4 mm.

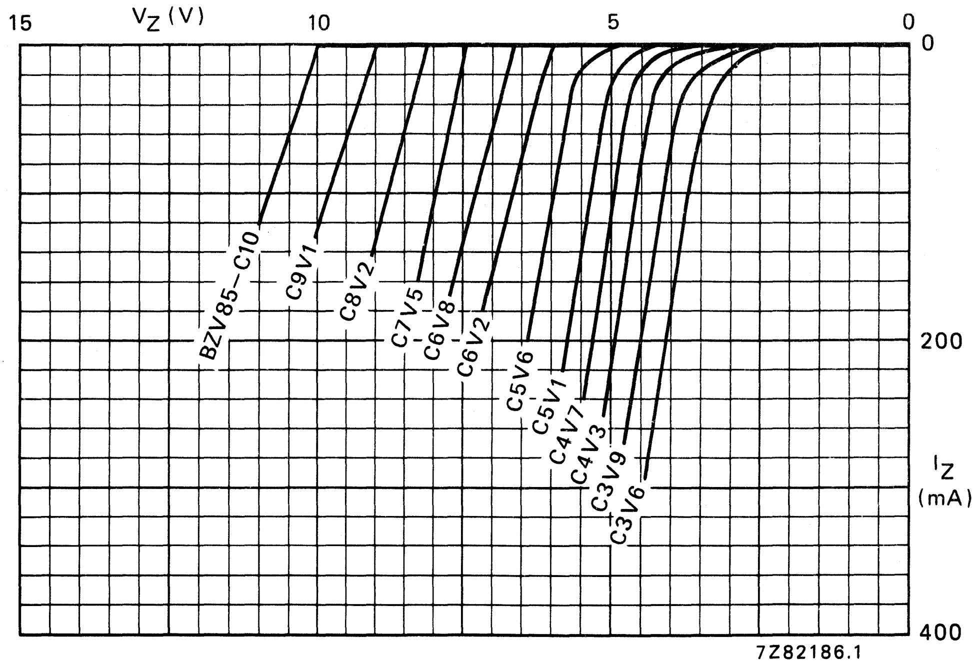


Fig. 6 Static characteristics; typical values; T_{amb} = 25 °C.

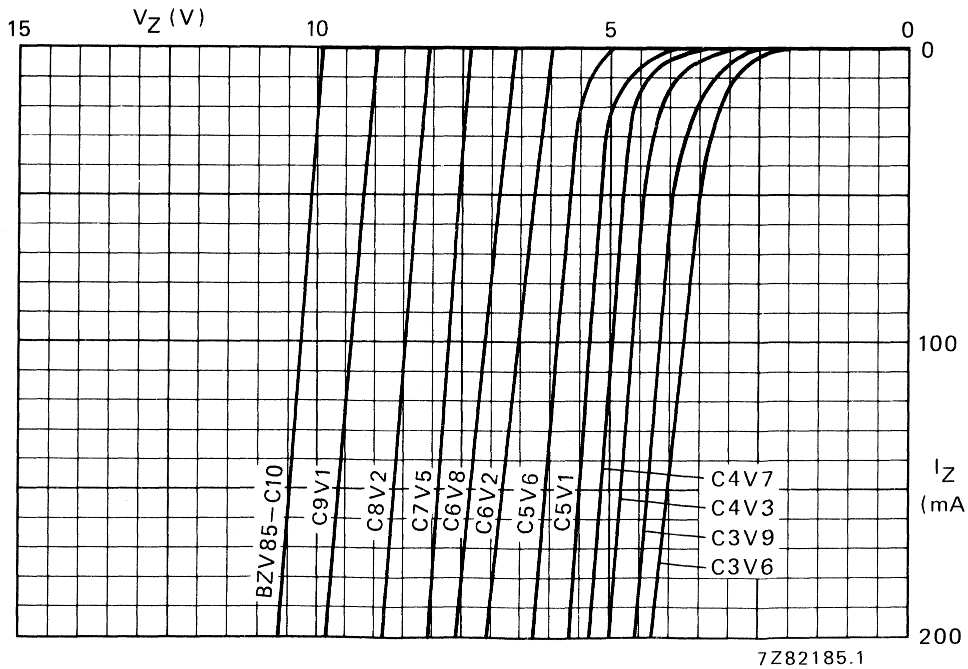


Fig. 7 Dynamic characteristics; typical values; T_j = 25 °C.

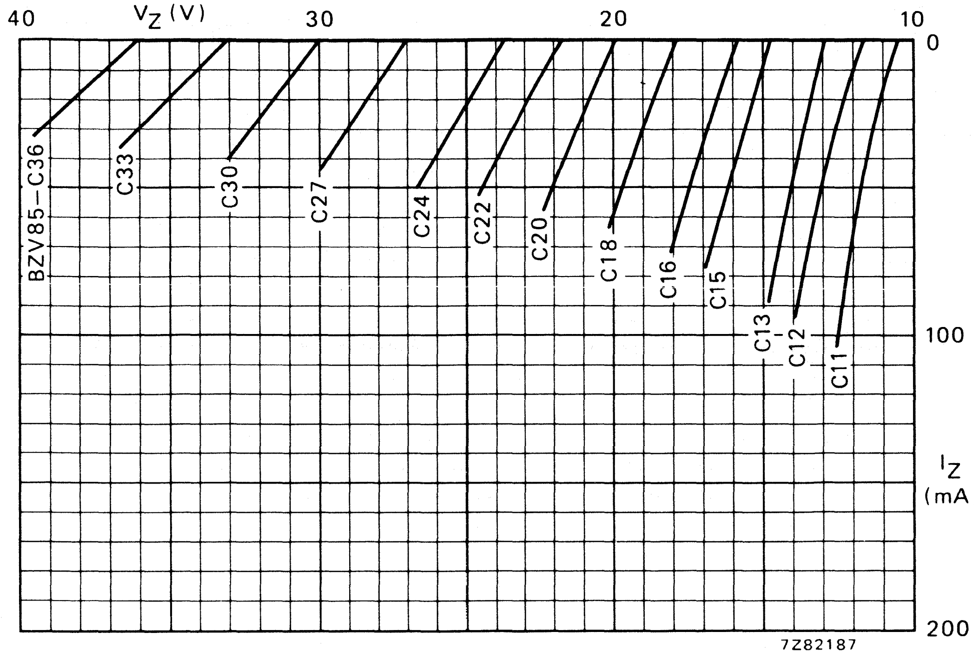


Fig. 8 Static characteristics; typical values; T_{amb} = 25 °C.

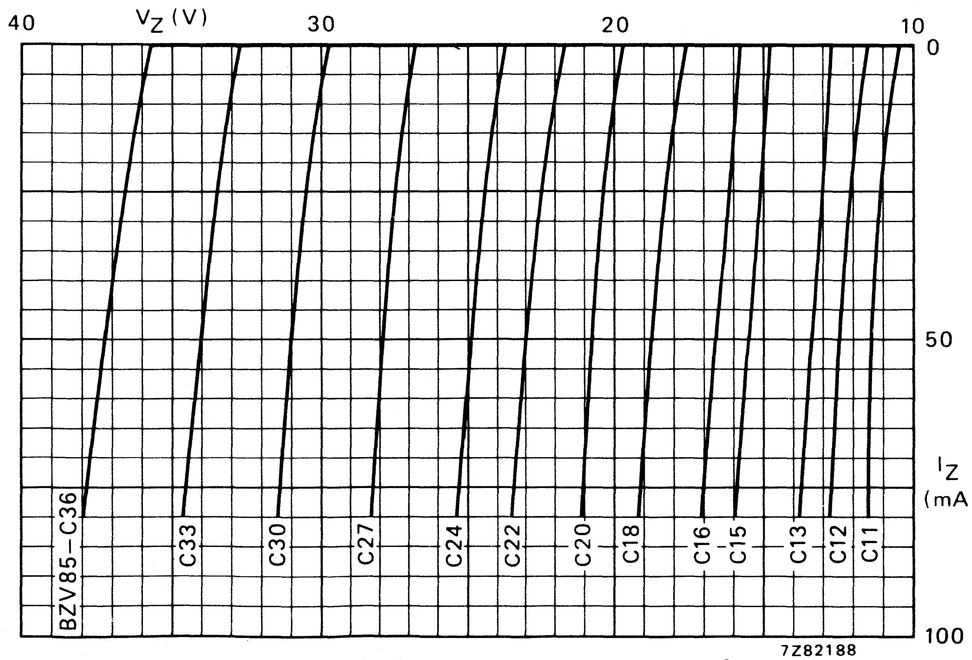


Fig. 9 Dynamic characteristics; typical values; T_j = 25 °C.

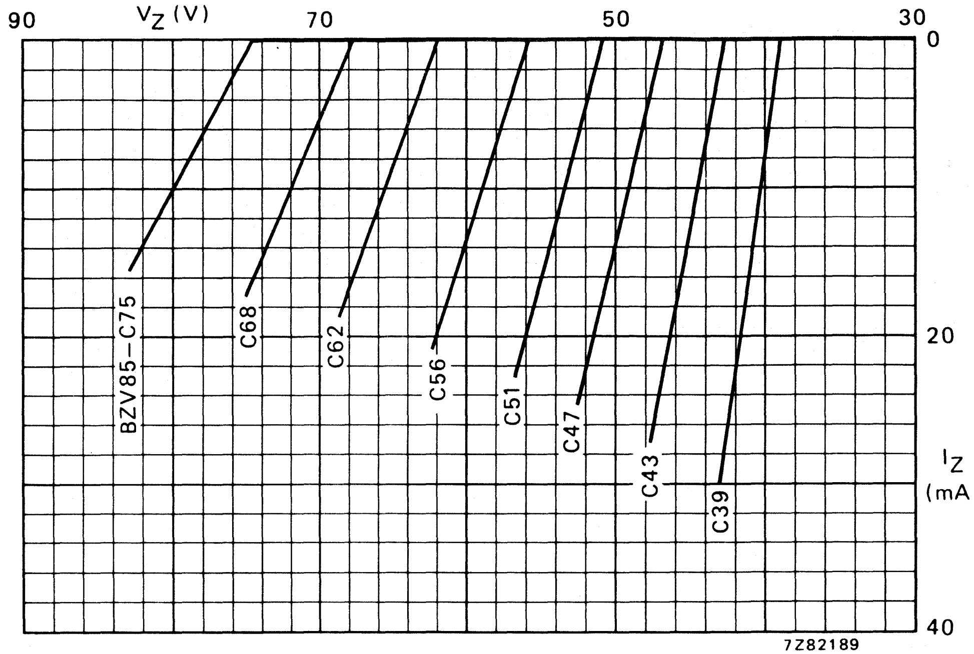


Fig. 10 Static characteristics; typical values; T_{amb} = 25 °C.

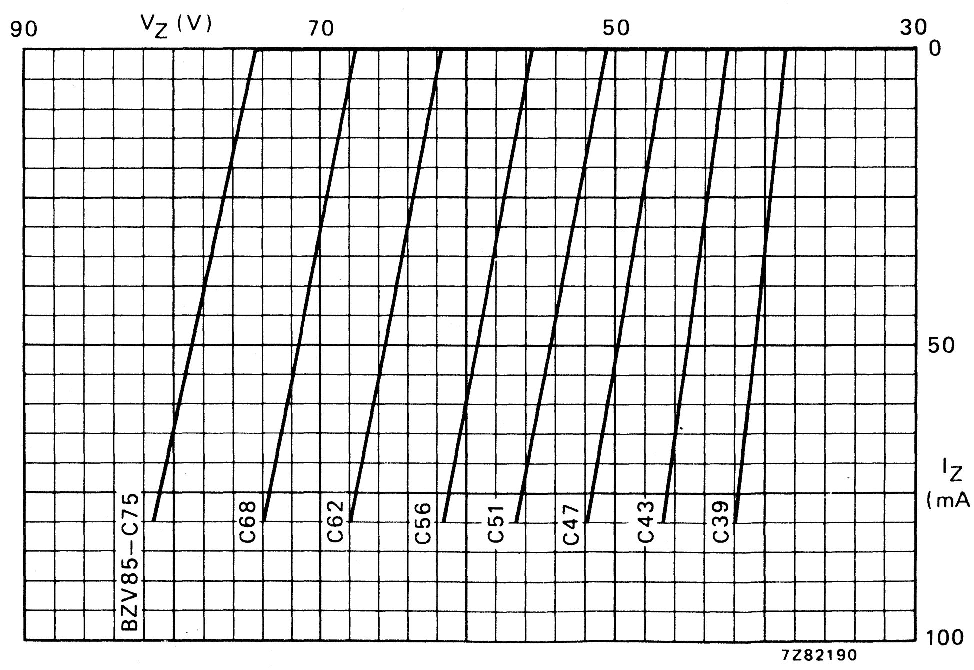


Fig. 11 Dynamic characteristics; typical values; T_j = 25 °C.

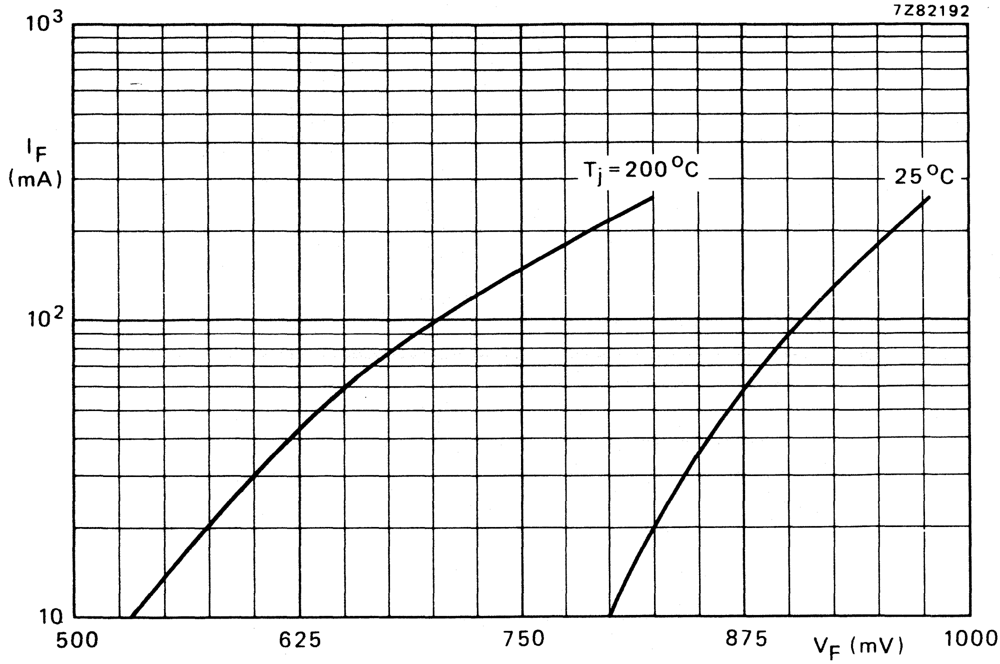


Fig. 12 Typical values.

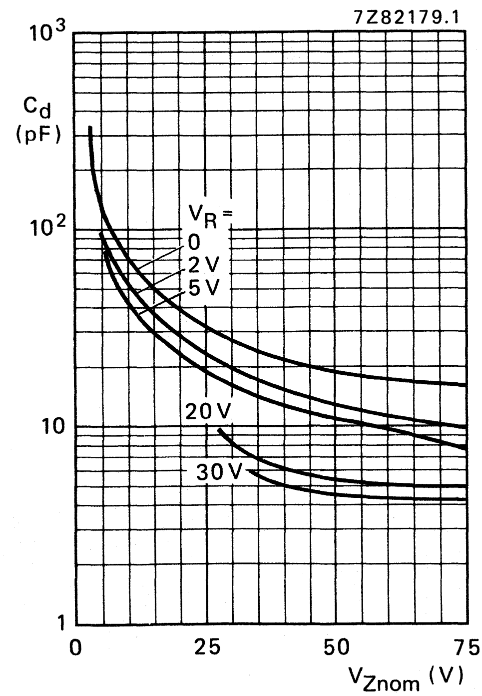


Fig. 13 f = 1 MHz; T_j = 25 ^oC; typical values.

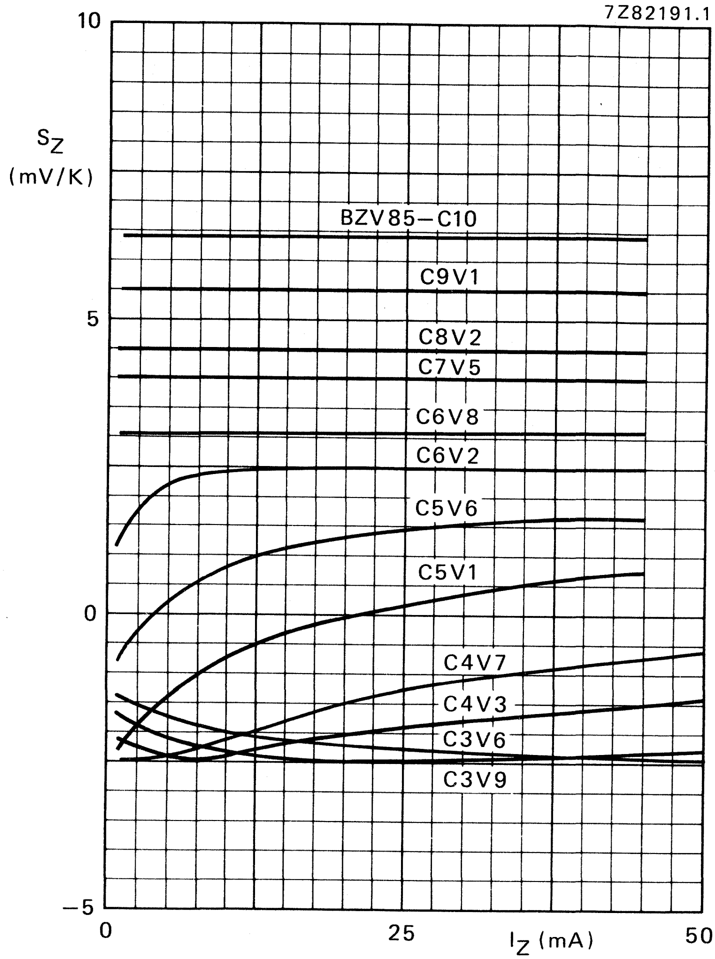


Fig. 14 T_j = 25 °C to 150 °C; typical values.

For types above 7,5 V the temperature coefficient is independent of current and can be read from the CHARACTERISTICS.

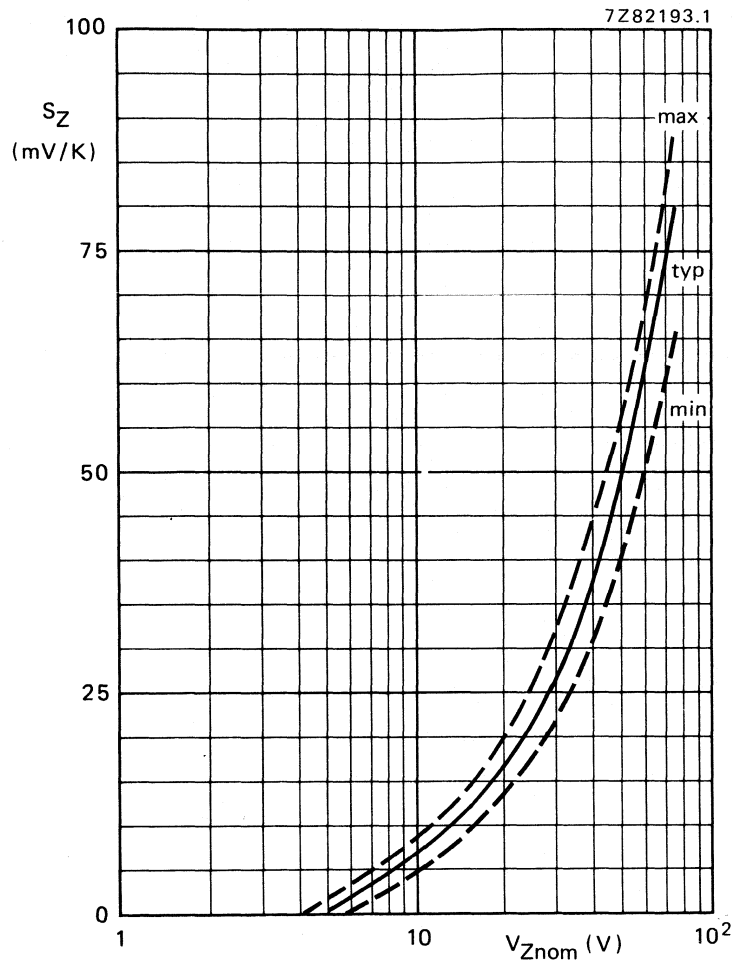


Fig. 15 $I_Z = I_{Ztest}$; T_j = 25 °C to 150 °C.

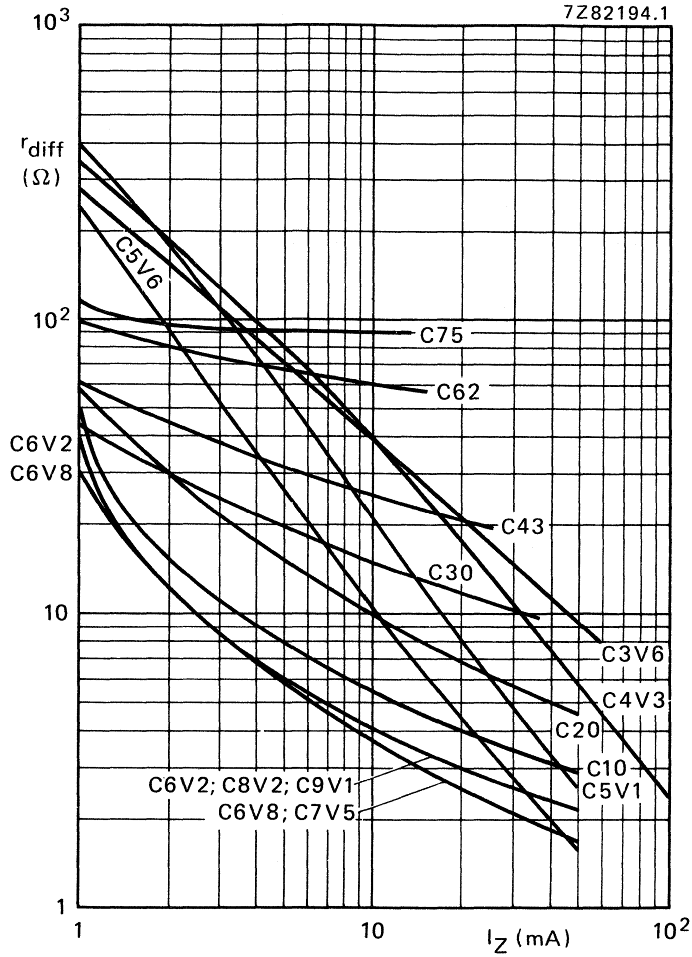


Fig. 16 f = 1 kHz; T_j = 25 °C; typical values.

LOW VOLTAGE STABISTORS

Silicon planar integrated voltage regulator diodes in hermetically sealed SOD-27 glass envelopes, intended for low power clipping, level shifting, voltage regulation, temperature stabilization of transistor base-emitter biasing network and in many other applications where tight tolerances and low voltage levels are required.
The series consists of four types with nominal voltage ranging from 1,4 V to 3,2 V.

QUICK REFERENCE DATA

Regulation voltage range	V_F	nom.	1V4	2V0	2V6	3V2	V
Continuous reverse voltage	V_R	max.			10		V
Repetitive peak reverse voltage	V_{RRM}	max.			10		V
Total power dissipation up to $T_a = 25\ ^oC$	P_{tot}	max.			330		mW
Junction temperature	T_j	max.			150		^oC
Differential resistance at $I_F = 5$ mA; f = 1 kHz	r_{diff}	typ.	10	15	18	20	Ω
		max.	20	30	32,5	35	Ω

MECHANICAL DATA

Dimensions in mm

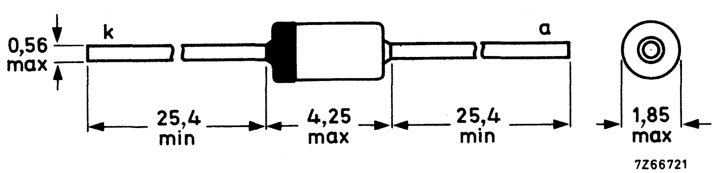


Fig. 1 SOD-27.

Cathode indicated by coloured band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			1V4	2V0	2V6	3V2	
Repetitive peak forward current	I_{FRM}	max.	250		150		mA
Continuous reverse voltage	V_R	max.	10				V
Repetitive peak reverse voltage	V_{RRM}	max.	10				V
Total power dissipation up to T_a = 25 °C	P_{tot}	max.	330				mW
Storage temperature	T_{stg}		−65 to 150				°C
Junction temperature	T_j	max.	150				°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	380	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			1V4	2V0	2V6	3V2	
Regulation voltage range at I_F = 5 mA	V_F	min.	1,3	1,85	2,35	2,85	V
		max.	1,5	2,15	2,8	3,45	V
Differential resistance at I_F = 1 mA; f = 1 kHz	r_{diff}	typ.	55	80	90	100	Ω
at I_F = 5 mA; f = 1 kHz	r_{diff}	typ.	10	15	18	20	Ω
		max.	20	30	32,5	35	Ω
at I_F = 10 mA; f = 1 kHz	r_{diff}	typ.	6,0	8,0	9,0	10	Ω
		max.	10	15	17,5	20	Ω
Negative temperature coefficient at I_F = 5 mA	S_F	typ.	3,8	6,0	8,5	11,5	mV/K
Reverse current at V_R = 5 V	I_R	max.	200				nA
Diode capacitance at V_R = 0; f = 1 MHz	C_d	typ.	15				pF
		max.	25				pF

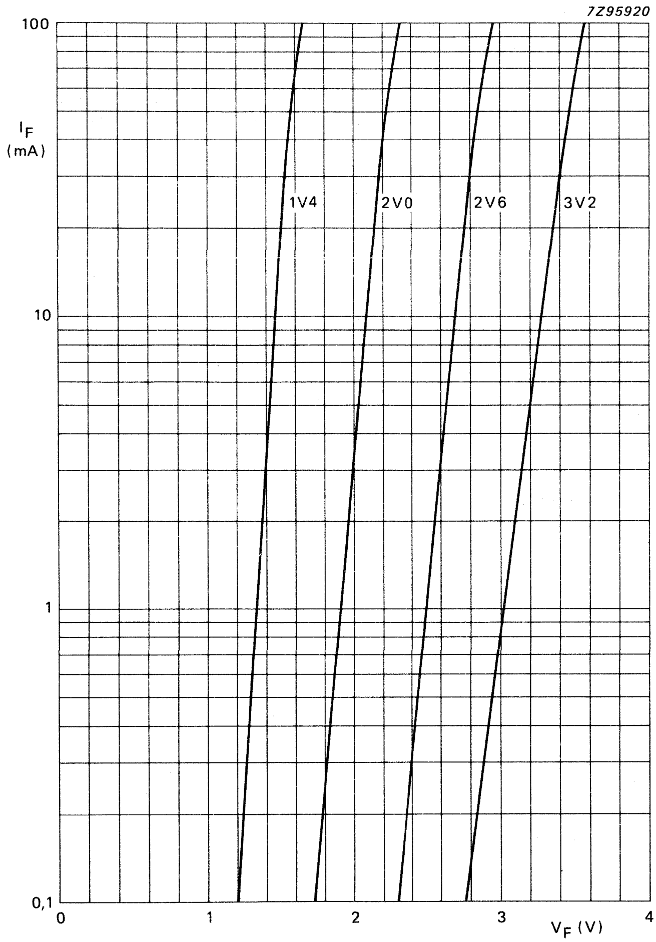


Fig. 2 Forward current as a function of forward voltage; T_j = 25 °C; typical values.

REGULATOR DIODES

Glass passivated diodes in hermetically sealed axial-leaded glass envelopes. They are intended for use as voltage regulator and transient suppressor diode in medium power regulation and transient suppression circuits.

The series consists of BZW03-C7V5 to BZW03-C510 in the normalized E24 range.

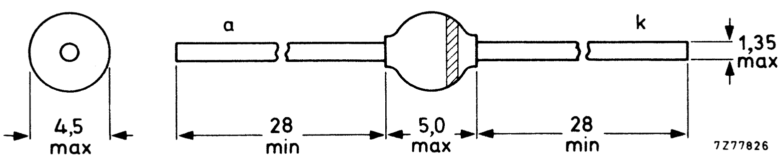
QUICK REFERENCE DATA

			voltage regulator	transient suppressor	
Working voltage range	V_Z	nom.	7,5 to 270		V
Stand-off voltage	V_R			6,2 to 430	V
Total power dissipation	P_{tot}	max.	6		W
Non-repetitive peak reverse power dissipation $T_j = 25\ ^oC$; $t_p = 100\ \mu s$	P_{RSM}			1000	W

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-64.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Total power dissipation			
T_{tp} = 25 °C; lead length 10 mm	P_{tot}	max.	6 W
T_{amb} = 45 °C; p.c.b. mounting (Fig. 2)	P_{tot}	max.	1,75 W
Repetitive peak reverse power dissipation	P_{ZRM}	max.	20 W
Non-repetitive peak reverse power dissipation			
t_p = 100 μs square pulse; T_j = 25 °C (prior to surge)	P_{RSM}	max.	1000 W
waveform 10/1000 exponential pulse (see Fig. 3), T_j = 25 °C (prior to surge)	P_{RSM}	max.	500 W
Storage temperature	T_{stg}		−65 to +175 °C
Junction temperature	T_j	max.	175 °C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\ j\text{-}tp}$	=	25 K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ≥ 40 μm; Fig. 2 (see "Thermal model")	$R_{th\ j\text{-}a}$	=	75 K/W

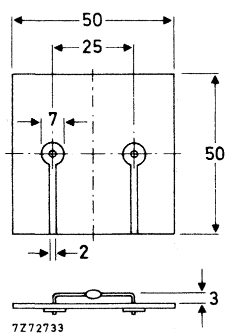


Fig. 2 Mounted on a printed-circuit board.

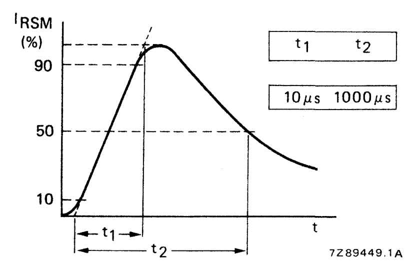


Fig. 3 Current pulse according to IEC 60-2, Section 6.

CHARACTERISTICS

Forward voltage			
I_F = 1 A; T_j = 25 °C	V_F	<	1,2 V

CHARACTERISTICS when used as voltage regulator diodes; $T_j = 25\ ^oC$

	working voltage V_Z V			differential resistance r_{diff} Ω		temperature coefficient S_Z %/K		test current I_Z mA	reverse current I_R µA	at reverse voltage V_R V
BZW03-	min.	nom.	max.	typ.	max.	min.	max.		max.	
C7V5	7,0	7,5	7,9	0,7	1,5	0	0,07	175	1500	5,6
C8V2	7,7	8,2	8,7	0,8	1,5	0,03	0,08	150	1200	6,2
C9V1	8,5	9,1	9,6	0,9	2,0	0,03	0,08	150	40	6,8
C10	9,4	10,0	10,6	1,0	2,0	0,05	0,09	125	20	7,5
C11	10,4	11,0	11,6	1,1	2,5	0,05	0,10	125	15	8,2
C12	11,4	12,0	12,7	1,1	2,5	0,05	0,10	100	10	9,1
C13	12,4	13,0	14,1	1,2	2,5	0,05	0,10	100	4	10
C15	13,8	15,0	15,6	1,2	2,5	0,05	0,10	75	2	11
C16	15,3	16,0	17,1	1,3	2,5	0,06	0,11	75	2	12
C18	16,8	18,0	19,1	1,3	2,5	0,06	0,11	65	2	13
C20	18,8	20,0	21,2	1,5	3	0,06	0,11	65	2	15
C22	20,8	22,0	23,3	1,6	3,5	0,06	0,11	50	2	16
C24	22,8	24,0	25,6	1,8	3,5	0,06	0,11	50	2	18
C27	25,1	27,0	28,9	2,5	5	0,06	0,11	50	2	20
C30	28	30	32	4	8	0,06	0,11	40	2	22
C33	31	33	35	5	10	0,06	0,11	40	2	24
C36	34	36	38	6	11	0,06	0,11	30	2	27
C39	37	39	41	7	14	0,06	0,11	30	2	30
C43	40	43	46	10	20	0,07	0,12	30	2	33
C47	44	47	50	12	25	0,07	0,12	25	2	36
C51	48	51	54	14	27	0,07	0,12	25	2	39
C56	52	56	60	18	35	0,07	0,12	20	2	43
C62	58	62	66	20	42	0,08	0,13	20	2	47
C68	64	68	72	22	44	0,08	0,13	20	2	51
C75	70	75	79	25	45	0,08	0,13	20	2	56
C82	77	82	87	30	65	0,08	0,13	15	2	62
C91	85	91	96	40	75	0,09	0,13	15	2	68
C100	94	100	106	45	90	0,09	0,13	12	2	75
C110	104	110	116	65	125	0,09	0,13	12	2	82
C120	114	120	127	90	170	0,09	0,13	10	2	91
C130	124	130	141	100	190	0,09	0,13	10	2	100
C150	138	150	156	150	330	0,09	0,13	8	2	110
C160	153	160	171	180	350	0,09	0,13	8	2	120
C180	168	180	191	210	430	0,09	0,13	5	2	130
C200	188	200	212	250	500	0,09	0,13	5	2	150
C220	208	220	233	350	700	0,09	0,13	5	2	160
C240	228	240	256	450	900	0,09	0,13	5	2	180
C270	251	270	289	600	1200	0,09	0,13	5	2	200

CHARACTERISTICS when used as transient suppressor diodes; $T_j = 25\ ^oC$

clamping voltage at non-repetitive peak reverse current 10/1000 pulse $V_{(CL)R}$ V	I_{RSM} A	reverse current at recommended stand-off voltage I_R μA	V_R V	
max.	max.	max.		BZW03-
11,3	44,2	3000	6,2	C7V5
12,3	40,6	2400	6,8	C8V2
13,3	37,6	100	7,5	C9V1
14,8	34,0	40	8,2	C10
15,7	31,8	30	9,1	C11
17,0	29,4	20	10	C12
18,9	26,4	10	11	C13
20,9	23,9	10	12	C15
22,9	21,8	10	13	C16
25,6	19,5	10	15	C18
28,4	17,6	10	16	C20
31	16,1	10	18	C22
33,8	14,8	10	20	C24
38,1	13,1	10	22	C27
42,2	11,8	10	24	C30
46,2	10,8	10	27	C33
50,1	10,0	10	30	C36
54,1	9,2	10	33	C39
60,7	8,2	10	36	C43
65,5	7,6	10	39	C47
70,8	7,0	10	43	C51
78,6	6,3	10	47	C56
86,5	5,8	10	51	C62
94,4	5,3	10	56	C68
103,5	4,8	10	62	C75
114,0	4,3	10	68	C82
126	3,9	10	75	C91
139	3,6	10	82	C100
152	3,3	10	91	C110
167	3,0	10	100	C120
185	2,7	10	110	C130
204	2,4	10	120	C150
224	2,2	10	130	C160
249	2,0	10	150	C180
276	1,8	10	160	C200
305	1,6	10	180	C220
336	1,5	10	200	C240
380	1,3	10	220	C270
419	1,2	10	240	C300
459	1,1	10	270	C330
498	1,0	10	300	C360
→ 537	0,93	10	330	C390
603	0,83	10	360	C430
655	0,76	10	390	C470
707	0,71	10	430	C510

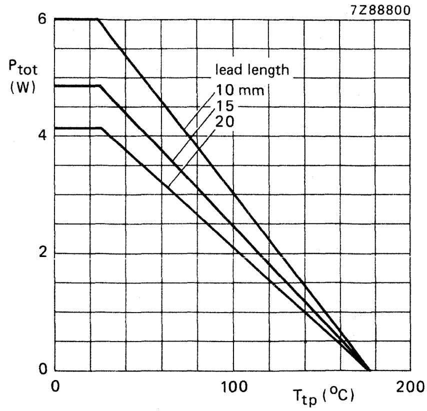


Fig. 4 Maximum total power dissipation as a function of tie-point temperature.

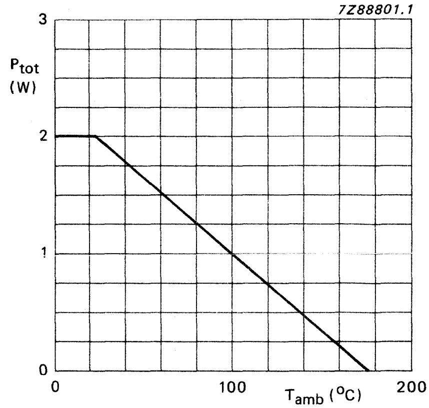


Fig. 5 Maximum total power dissipation as a function of ambient temperature, mounted as shown in Fig. 2.

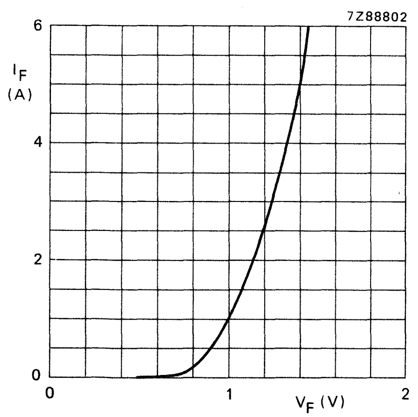


Fig. 6 Typical forward voltage drop at $T_j = 25\ ^oC$.

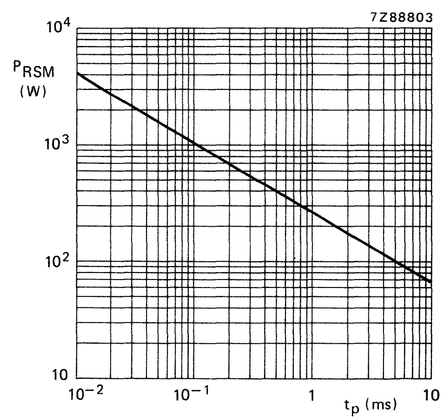


Fig. 7 Maximum non-repetitive peak reverse power dissipation; square current pulse; $T_j = 25\ ^oC$ prior to surge.

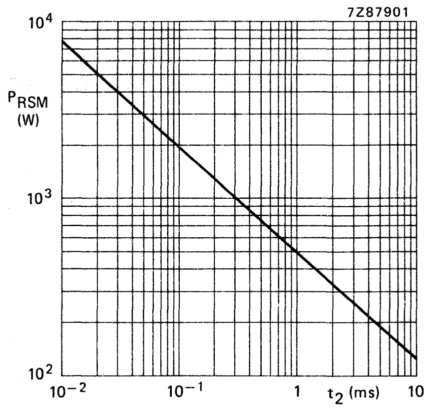


Fig. 8 Maximum non-repetitive peak reverse power dissipation; exponential pulse; T_j = 25 °C prior to surge.

TRANSIENT SUPPRESSOR DIODE

A double-diffused silicon glass passivated diode in a hermetically sealed axial-leaded glass envelope intended for transient suppression in telephony equipment.

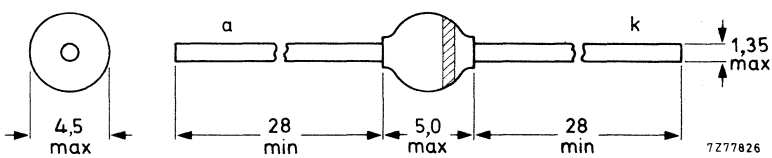
QUICK REFERENCE DATA

Stand-off voltage	V_R	max.	12 V
Non-repetitive peak reverse current	I_{RSM}	max.	50 A
Clamping voltage	$V_{(CL)R}$	<	28 V

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-64.



The marking band indicates the cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Stand-off voltage	V_R	max.	12	V
Average forward current	$I_{F(AV)}$	max.	250	mA
Non-repetitive peak reverse current (Fig. 3)	I_{RSM}	max.	50	A
Storage temperature	T_{stg}	−55 to +150		°C
Operating ambient temperature	T_{amb}	−25 to +85		°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\ j\text{-}tp}$	=	25	K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ⩾ 40 μm; Fig. 2 (see "Thermal model")	$R_{th\ j\text{-}a}$	=	75	K/W

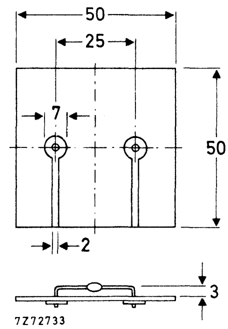


Fig. 2 Dimensions of printed-circuit board.

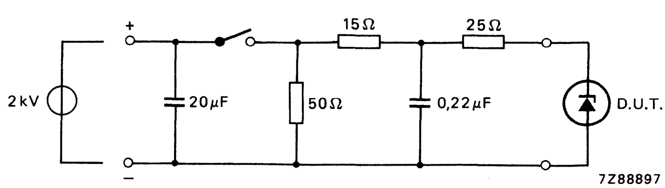


Fig. 3 Test set-up in accordance with FTZ 10/700.

CHARACTERISTICS

T_{amb} = −25 to +85 °C

Forward voltage I_F = 1 A	V_F	<	1,3 V
Clamping voltage I_{RSM} = 50 A; see Fig. 3 waveform 6/320 μs exponential pulse (Fig. 4)	$V_{(CL)R}$	<	28 V
Reverse current V_R = 12 V	I_R	<	40 μA

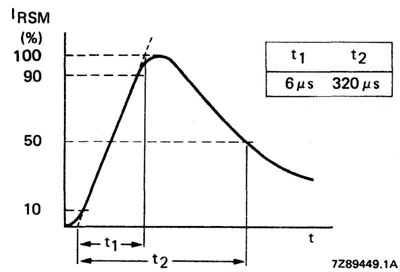


Fig. 4 Peak reverse current as a function of time.

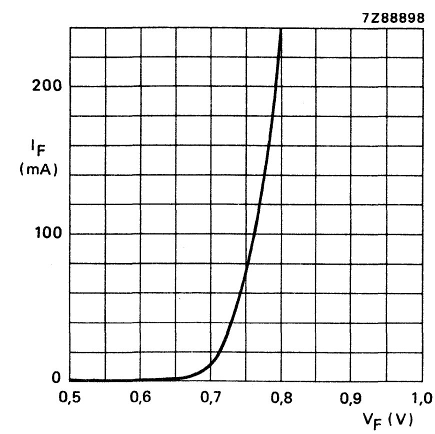


Fig. 5 Typical values forward voltage. T_j = 25 °C.

VOLTAGE REGULATOR DIODES

Silicon planar diodes in a DO-35 envelope intended for use as low-voltage stabilizers or voltage references. The series covers the normalized range of nominal working voltages from 2,4 V to 75 V with a tolerance of ± 5% (international standard E24).

QUICK REFERENCE DATA

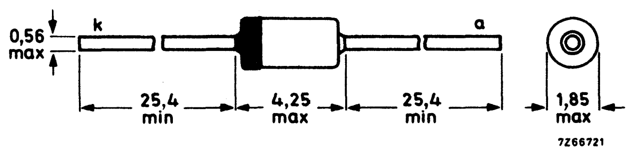
Working voltage range	V_Z	nom.	2,4 to 75	V
Total power dissipation*	P_{tot}	max.	500	mW
Non-repetitive peak reverse power dissipation	P_{ZSM}	max.	30	W
Junction temperature	T_j	max.	200	°C
Thermal resistance from junction to tie-point*	$R_{th\ j\text{-}tp}$	=	0,30	K/mW

* If leads are kept at T_{tp} = 50 °C at 8 mm from body.

MECHANICAL DATA

Fig. 1 DO-35 (SOD-27).

Dimensions in mm



Cathode indicated by coloured band

Products, approved to CECC 50 005-005, available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	250	mA
Repetitive peak forward current	I_{FRM}	max.	250	mA
Total power dissipation	P_{tot}	max.	400	mW*
		max.	500	mW**
Non-repetitive peak reverse power dissipation $t = 100\ \mu s$; $T_j = 150\ ^oC$	P_{ZSM}	max.	30	W
Storage temperature	T_{stg}		−65 to + 200	^oC
Junction temperature	T_j	max.	200	^oC

THERMAL RESISTANCE

From junction to tie-point	$R_{th\ j\text{-}tp}$	=	0,30	K/mW**
From junction to ambient	$R_{th\ j\text{-}a}$	=	0,38	K/mW*

CHARACTERISTICS

$T_j = 25\ ^oC$ unless otherwise specified

Forward voltage
$I_F = 100$ mA — V_F < 1,0 V

Reverse current

Type	Condition			at T_j = 25	150 ^oC
BZX55-C2V4	$V_R = 1$ V	I_R	<	50	100 μA
C2V7	$V_R = 1$ V	I_R	<	10	50 μA
C3V0	$V_R = 1$ V	I_R	<	4	40 μA
C3V3	$V_R = 1$ V	I_R	<	2	40 μA
C3V6	$V_R = 1$ V	I_R	<	2	40 μA
C3V9	$V_R = 1$ V	I_R	<	2	40 μA
C4V3	$V_R = 1$ V	I_R	<	1	20 μA
C4V7	$V_R = 1$ V	I_R	<	0,5	10 μA
C5V1	$V_R = 1$ V	I_R	<	0,1	2 μA
C5V6	$V_R = 1$ V	I_R	<	0,1	2 μA
C6V2	$V_R = 2$ V	I_R	<	0,1	2 μA
C6V8	$V_R = 3$ V	I_R	<	0,1	2 μA
C7V5	$V_R = 5$ V	I_R	<	0,1	2 μA
C8V2 to C75	$V_R = 0,75\ V_{Znom}$	I_R	<	0,1	2 μA

* In still air at maximum lead length up to $T_{amb} = 25\ ^oC$. For the types of 2V4 and 2V7 the power dissipation is limited by $T_j = 175\ ^oC$.

** If leads are kept at $T_{amb} = 50\ ^oC$ at 8 mm from body.

BZX55- . . .	working voltage V_Z (V)		differential resistance r_{diff} (Ω)		temperature coefficient S_Z (mV/K)
	at I_Z = 5 mA		at I_Z = 5 mA	at I_Z = 1 mA	at I_Z = 5 mA
	min.	max.	max.	max.	typ.
C2V4	2,28	2,56	85	600	−1,8
C2V7	2,5	2,9	85	600	−1,9
C3V0	2,8	3,2	85	600	−2,1
C3V3	3,1	3,5	85	600	−2,2
C3V6	3,4	3,8	85	600	−2,4
C3V9	3,7	4,1	85	600	−2,4
C4V3	4,0	4,6	75	600	−2,4
C4V7	4,4	5,0	60	600	−1,4
C5V1	4,8	5,4	35	550	−0,8
C5V6	5,2	6,0	25	450	1,6
C6V2	5,8	6,6	10	200	2,2
C6V8	6,4	7,2	8	150	3,0
C7V5	7,0	7,9	7	50	3,8
C8V2	7,7	8,7	7	50	4,5
C9V1	8,5	9,6	10	50	5,5
C10	9,4	10,6	15	70	6,5
C11	10,4	11,6	20	70	7,7
C12	11,4	12,7	20	90	8,4
C13	12,4	14,1	26	110	9,8
C15	13,8	15,6	30	110	11,3
C16	15,3	17,1	40	170	12,8
C18	16,8	19,1	50	170	14,4
C20	18,8	21,2	55	220	16,0
C22	20,8	23,3	55	220	18,7
C24	22,8	25,6	80	220	20,4
C27	25,1	28,9	80	220	22,9
C30	28,0	32,0	80	220	27,0
C33	31,0	35,0	80	220	29,7
C36	34,0	38,0	80	220	32,4
	at I_Z = 2,5 mA		at I_Z = 2,5 mA	at I_Z = 0,5 mA	at I_Z = 2,5 mA
	min.	max.	max.	max.	
C39	37,0	41,0	90	500	35,1
C43	40,0	46,0	90	600	38,7
C47	44,0	50,0	110	700	44,0
C51	48,0	54,0	125	700	49,0
C56	52,0	60,0	135	1000	55,0
C62	58,0	66,0	150	1000	62,0
C68	64,0	72,0	200	1000	70,0
C75	70,0	79,0	250	1500	78,0

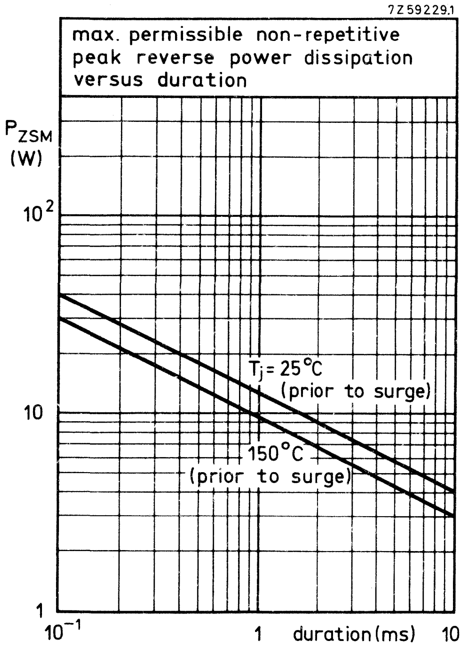


Fig. 2.

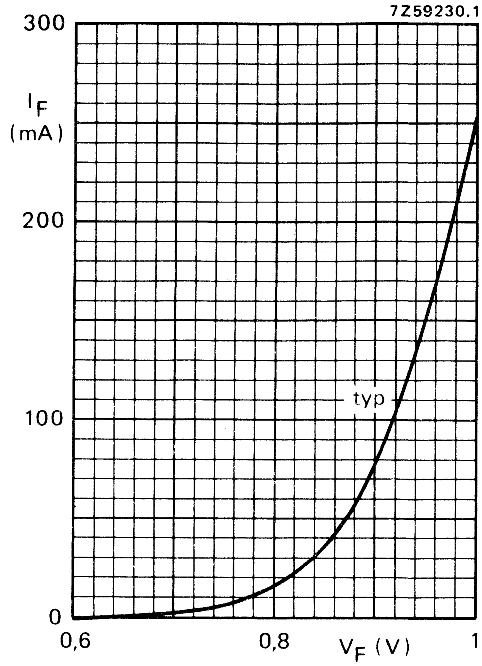


Fig. 3 T_j = 25 °C.

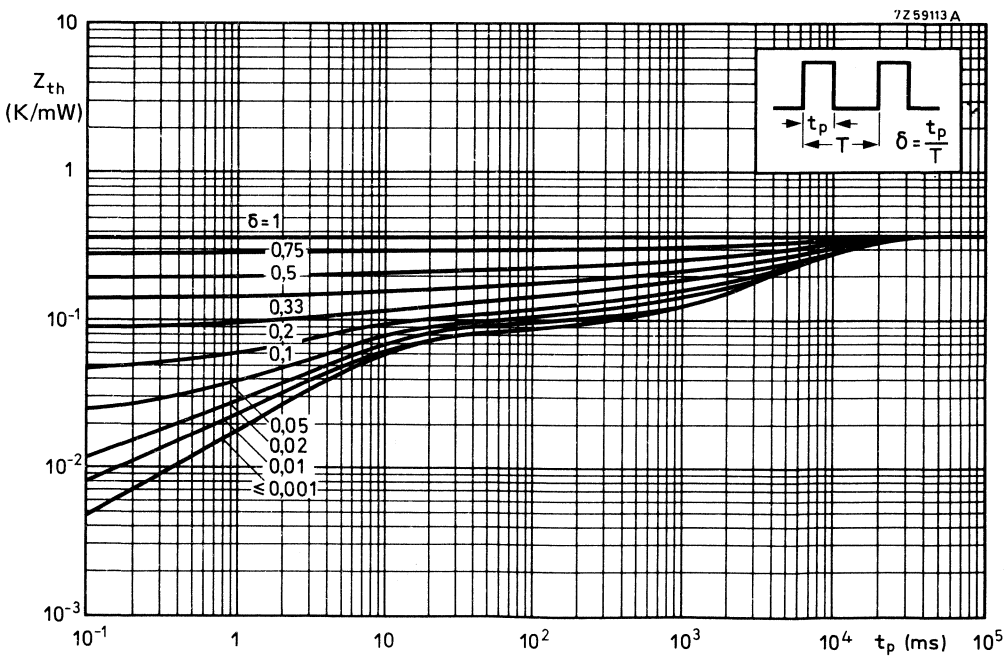


Fig. 4.

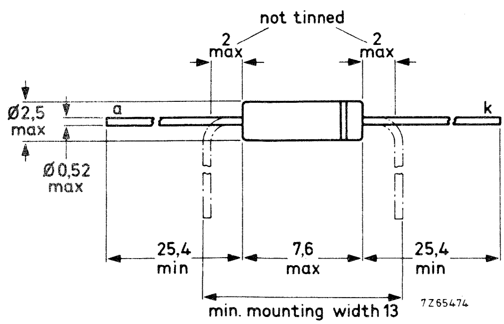
STABISTORS

Diodes with controlled conductance in a all-glass DO-7 envelope intended for low voltage regulation in circuits for clipping, coupling, clamping, meter protection, bias regulation and in many applications which require tight tolerances and low voltage levels.
The series consists of 4 types with nominal voltages ranging from 1,4 to 3,6 V with a tolerance of ±5%.

QUICK REFERENCE DATA				
Regulation voltage range	V_F	nom.	1,4 to 3,6	V
Regulation voltage tolerance			±5	%
Continuous reverse voltage	V_R	max.	10	V
Repetitive peak reverse voltage	V_{RRM}	max.	10	V
Repetitive peak forward current	I_{FRM}	max.	250	mA
Total power dissipation up to T_{amb} = 32 °C	P_{tot}	max.	400	mW
Operating junction temperature	T_j	max.	200	°C

MECHANICAL DATA Dimensions in mm

DO-7



Cathode indicated by coloured band

RATINGS Limiting values in accordance with the Absolute Maximum System (IEC134)

Continuous reverse voltage	V_R	max.	10	V
Repetitive peak reverse voltage	V_{RRM}	max.	10	V
Repetitive peak forward current	I_{FRM}	max.	250	mA
Total power dissipation up to T_{amb} = 32 °C	P_{tot}	max.	400	mW
Storage temperature	T_{stg}	-65 to +175		°C
Operating junction temperature	T_j	max.	200	°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j-a}$	=	0, 42	K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

	Regulation voltage V_F (V) at I_F = 1 mA		Temperature coefficient S_F (mV/K) at I_F = 1 mA	Differential resistance r_{diff} (Ω); f = 1 kHz at I_F = 1 mA
BZX75-....	min.	max.	typ.	typ.
C1V4	1,16	1,34	-4	60
C2V1	1,75	2,05	-6	90
C2V8	2,33	2,70	-8	120
C3V6	3,02	3,45	-10	150

	at I_F = 10 mA			at I_F = 10 mA	at I_F = 10 mA	
	min.	nom.	max.	typ.	typ.	max.
C1V4	1,33	1,40	1,47	-3,3	6	10
C2V1	1,99	2,10	2,21	-5,0	9	15
C2V8	2,66	2,80	2,94	-6,6	12	20
C3V6	3,42	3,60	3,78	-8,2	15	25

Reverse current

V_R = 5 V

BZX75-C1V4, BZX75-C2V1: I_R < 500 nA

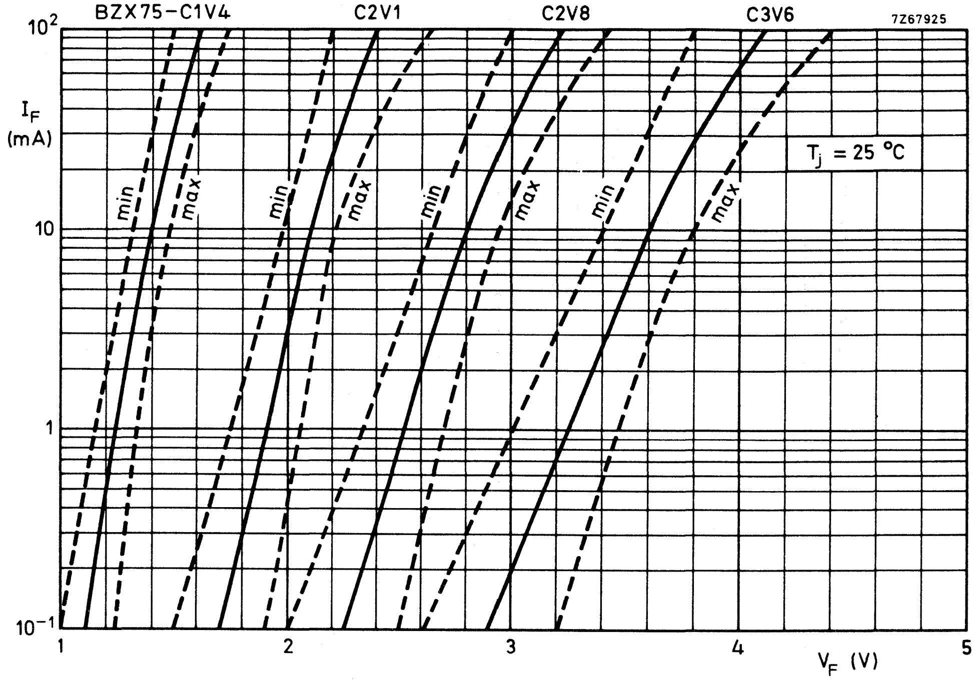
BZX75-C2V8, BZX75-C3V6: I_R < 200 nA

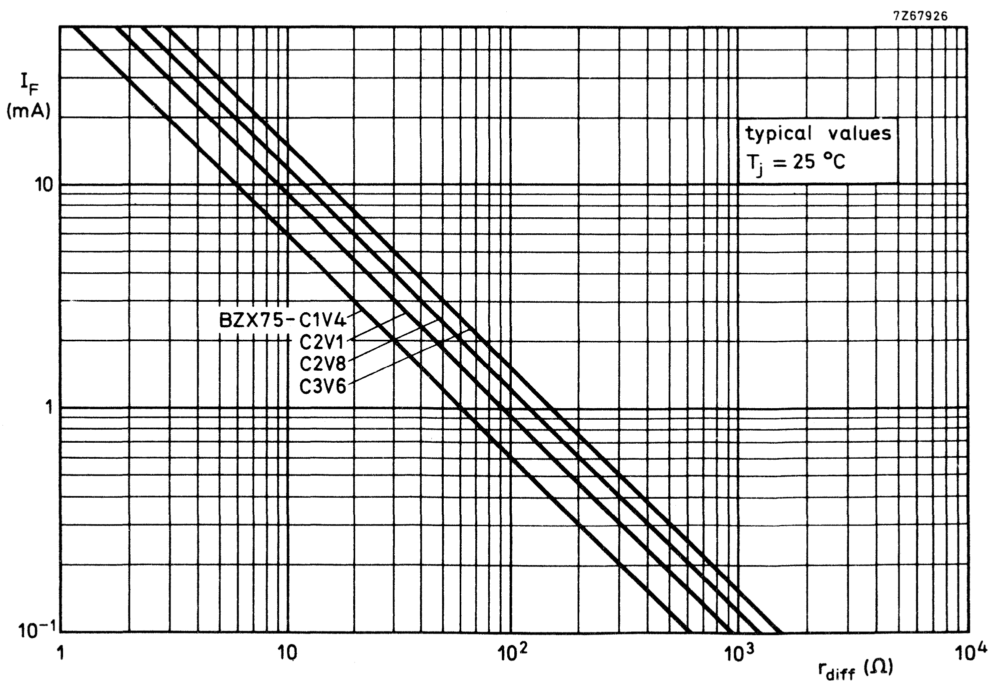
Recovered charge when switched from

I_F = 10 mA to V_R = 5 V; R_L = 500 Ω — Q_s > 600 pC

Diode capacitance

V_R = 0; f = 1 MHz — C_d < 250 pF


7Z67925
BZX75-C1V4
C2V1
C2V8
C3V6
I_F (mA)
10^2
10
1
10^{-1}
min
max
T_j = 25 °C
1
2
3
4
5
V_F (V)


7Z67926
I_F (mA)
10
1
10^{-1}
typical values
T_j = 25 °C
BZX75-C1V4
C2V1
C2V8
C3V6
1
10
10^2
10^3
10^4
r_{diff} (Ω)

VOLTAGE REGULATOR DIODES

Silicon planar diodes in DO-35 envelopes intended for use as low voltage stabilizers or voltage references. They are available in four series; each series having a different tolerance rating, one series is to the international standardized E24 (± 5%) range, the other three have tolerances of 1%, 2% and 3% on working voltage. Each series consists of 37 types with nominal working voltages ranging from 2,4 V to 75 V.

QUICK REFERENCE DATA

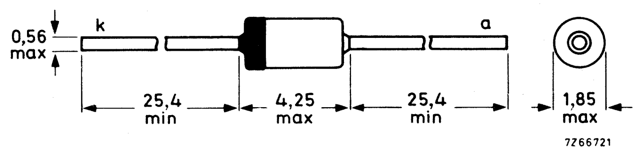
Working voltage range	V_Z	nom.	2,4 to 75	V
Total power dissipation	P_{tot}	max.	500	mW *
Non-repetitive peak reverse power dissipation	P_{ZSM}	max.	30	W
Junction temperature	T_j	max.	200	°C
Thermal resistance from junction to tie-point	$R_{th\ j\text{-}tp}$	=	0,30	K/mW *

* If leads are kept at T_{tp} = 50 °C at 8 mm from body.

MECHANICAL DATA

Dimensions in mm

Fig. 1 DO-35.



Cathode indicated by coloured band.

Products approved to CECC 50 005-005, available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	250	mA
Repetitive peak forward current	I_{FRM}	max.	250	mA
Total power dissipation	P_{tot}	max.	500	mW *
		max.	400	mW **
Non-repetitive peak reverse power dissipation t = 100 μs; T_j = 150 °C	P_{ZSM}	max.	30	W
Storage temperature	T_{stg}	−65 to +	200	°C
Junction temperature	T_j	max.	200	°C

THERMAL RESISTANCE

From junction to tie-point	$R_{th\ j\text{-}tp}$	=	0,30	K/mW*
From junction to ambient	$R_{th\ j\text{-}a}$	=	0,38	K/mW**

CHARACTERISTICS

T_j = 25 °C

Forward voltage I_F = 10 mA		V_F	<	0,9	V
Reverse current					
BZX79-.2V4	V_R = 1 V	I_R	<	50	μA
.2V7	V_R = 1 V	I_R	<	20	μA
.3V0	V_R = 1 V	I_R	<	10	μA
.3V3	V_R = 1 V	I_R	<	5	μA
.3V6	V_R = 1 V	I_R	<	5	μA
.3V9	V_R = 1 V	I_R	<	3	μA
.4V3	V_R = 1 V	I_R	<	3	μA
.4V7	V_R = 2 V	I_R	<	3	μA
.5V1	V_R = 2 V	I_R	<	2	μA
.5V6	V_R = 2 V	I_R	<	1	μA
.6V2	V_R = 4 V	I_R	<	3	μA
.6V8	V_R = 4 V	I_R	<	2	μA
.7V5	V_R = 5 V	I_R	<	1	μA
.8V2	V_R = 5 V	I_R	<	700	nA
.9V1	V_R = 6 V	I_R	<	500	nA
.10	V_R = 7 V	I_R	<	200	nA
.11 to .13	V_R = 8 V	I_R	<	100	nA
.15 to .75	V_R = 0,7 V_{Znom}	I_R	<	50	nA

. = A for 1% tolerance range
→ . = B for 2% tolerance range
. = F for 3% tolerance range
. = C for E24 (± 5%) tolerance range

* If leads are kept at T_{tp} = 50 °C at 8 mm from body. For the types 2V4 and 2V7 the power dissipation is limited by $T_{j\ max}$ = 150 °C.

** In still air at maximum lead length up to T_{amb} = 50 °C.

T_j = 25 °C
± 1% tolerance range

BZX79A	working voltage V_Z (V) at I_{Ztest} = 5 mA		differential resistance r_{diff} (Ω) at I_{Ztest} = 5 mA		temperature coefficient S_Z (mV/K) at I_{Ztest} = 5 mA			differential resistance r_{diff} (Ω) at I_Z = 1 mA	
	min.	max.	typ.	max.	min.	typ.	max.	typ.	max.
A2V4	2,37	2,43	70	100	−3,5	−1,6	0	275	600
A2V7	2,67	2,73	75	100	−3,5	−2,0	0	300	600
A3V0	2,97	3,03	80	95	−3,5	−2,1	0	325	600
A3V3	3,26	3,34	85	95	−3,5	−2,4	0	350	600
A3V6	3,56	3,64	85	90	−3,5	−2,4	0	375	600
A3V9	3,86	3,94	85	90	−3,5	−2,5	0	400	600
A4V3	4,25	4,35	80	90	−3,5	−2,5	0	410	600
A4V7	4,65	4,75	50	80	−3,5	−1,4	0,2	425	500
A5V1	5,04	5,16	40	60	−2,7	−0,8	1,2	400	480
A5V6	5,54	5,66	15	40	−2,0	1,2	2,5	80	400
A6V2	6,13	6,27	6	10	0,4	2,3	3,7	40	150
A6V8	6,73	6,87	6	15	1,2	3,0	4,5	30	80
A7V5	7,42	7,58	6	15	2,5	4,0	5,3	30	80
A8V2	8,11	8,29	6	15	3,2	4,6	6,2	40	80
A9V1	9,0	9,2	6	15	3,8	5,5	7,0	40	100
A10	9,9	10,10	8	20	4,5	6,4	8,0	50	150
A11	10,8	11,11	10	20	5,4	7,4	9,0	50	150
A12	11,88	12,12	10	25	6,0	8,4	10,0	50	150
A13	12,87	13,13	10	30	7,0	9,4	11,0	50	170
A15	14,85	15,15	10	30	9,2	11,4	13,0	50	200
A16	15,84	16,16	10	40	10,4	12,4	14,0	50	200
A18	17,82	18,18	10	45	12,4	14,4	16,0	50	225
A20	19,80	20,20	15	55	14,4	16,4	18,0	60	225
A22	21,78	22,22	20	55	16,4	18,4	20,0	60	250
A24	23,76	24,24	25	70	18,4	20,4	22,0	60	250
	at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA			at I_Z = 0,5 mA	
A27	26,73	27,27	25	80	21,4	23,4	25,3	65	300
A30	29,70	30,30	30	80	24,4	26,6	29,4	70	300
A33	32,67	33,33	35	80	27,4	29,7	33,4	75	325
A36	35,64	36,36	35	90	30,4	33,0	37,4	80	350
A39	38,61	39,39	40	130	33,4	36,4	41,2	80	350
A43	42,57	43,43	45	150	37,6	41,2	46,6	85	375
A47	46,53	47,47	50	170	42,0	46,1	51,8	85	375
A51	50,49	51,51	60	180	46,6	51,0	57,2	90	400
A56	55,44	56,56	70	200	52,2	57,0	63,8	100	425
A62	61,38	62,62	80	215	58,8	64,4	71,6	120	450
A68	74,25	75,75	90	240	65,6	71,7	79,8	150	475
A75	90,09	91,91	95	255	73,4	80,02	88,6	170	500

T_j = 25 °C
± 2% tolerance range.

BZX79-...	working voltage V_Z (V) at I_{Ztest} = 5 mA		differential resistance r_{diff} (Ω) at I_{Ztest} = 5 mA		temperature coefficient S_Z (mV/K) at I_{Ztest} = 5 mA			differential resistance r_{diff} (Ω) at I_Z = 1 mA	
	min.*	max.*	typ.	max.	min.	typ.	max.	typ.	max.
B2V4	2,35	2,45	70	100	–3,5	–1,6	0	275	600
B2V7	2,65	2,75	75	100	–3,5	–2,0	0	300	600
B3V0	2,94	3,06	80	95	–3,5	–2,1	0	325	600
B3V3	3,23	3,37	85	95	–3,5	–2,4	0	350	600
B3V6	3,53	3,67	85	90	–3,5	–2,4	0	375	600
B3V9	3,82	3,98	85	90	–3,5	–2,5	0	400	600
B4V3	4,21	4,39	80	90	–3,5	–2,5	0	410	600
B4V7	4,61	4,79	50	80	–3,5	–1,4	0,2	425	500
B5V1	5,00	5,20	40	60	–2,7	–0,8	1,2	400	480
B5V6	5,49	5,71	15	40	–2,0	1,2	2,5	80	400
B6V2	6,08	6,32	6	10	0,4	2,3	3,7	40	150
B6V8	6,66	6,94	6	15	1,2	3,0	4,5	30	80
B7V5	7,35	7,65	6	15	2,5	4,0	5,3	30	80
B8V2	8,04	8,36	6	15	3,2	4,6	6,2	40	80
B9V1	8,92	9,28	6	15	3,8	5,5	7,0	40	100
B10	9,80	10,20	8	20	4,5	6,4	8,0	50	150
B11	10,80	11,20	10	20	5,4	7,4	9,0	50	150
B12	11,80	12,20	10	25	6,0	8,4	10,0	50	150
B13	12,70	13,30	10	30	7,0	9,4	11,0	50	170
B15	14,70	15,30	10	30	9,2	11,4	13,0	50	200
B16	15,70	16,30	10	40	10,4	12,4	14,0	50	200
B18	17,60	18,40	10	45	12,4	14,4	16,0	50	225
B20	19,60	20,40	15	55	14,4	16,4	18,0	60	225
B22	21,60	22,40	20	55	16,4	18,4	20,0	60	250
B24	23,50	24,50	25	70	18,4	20,4	22,0	60	250
	at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA			at I_Z = 0,5 mA	
B27	26,50	27,50	25	80	21,4	23,4	25,3	65	300
B30	29,40	30,60	30	80	24,4	26,6	29,4	70	300
B33	32,30	33,70	35	80	27,4	29,7	33,4	75	325
B36	35,30	36,70	35	90	30,4	33,0	37,4	80	350
B39	38,20	39,80	40	130	33,4	36,4	41,2	80	350
B43	42,10	43,90	45	150	37,6	41,2	46,6	85	375
B47	46,10	47,90	50	170	42,0	46,1	51,8	85	375
B51	50,00	52,00	60	180	46,6	51,0	57,2	90	400
B56	54,90	57,10	70	200	52,2	57,0	63,8	100	425
B62	60,80	63,20	80	215	58,8	64,4	71,6	120	450
B68	66,60	69,40	90	240	65,6	71,7	79,8	150	475
B75	73,50	76,50	95	255	73,4	80,2	88,6	170	500

*When the real value is beyond this limit it is regulated as acceptable when it is within the 2% tolerance range.

T_j = 25 °C
± 3% tolerance range

BZX79	working voltage V_Z (V) at I_{Ztest} = 5 mA min.	max.	differential resistance r_{diff} (Ω) at I_{Ztest} = 5 mA typ.	max.	temperature coefficient S_Z (mV/K) at I_{Ztest} = 5 mA typ.	leakage current I_R at V_R μA	V
F2V	2,33	2,47	70	100	−1,6	50	1
F2V7	2,62	2,78	75	100	−2,0	20	1
F3V0	2,91	3,09	80	100	−2,1	10	1
F3V3	3,20	3,40	85	100	−2,4	5	1
F3V6	3,49	3,71	85	100	−2,4	5	1
F3V9	3,78	4,02	85	100	−2,5	3	1
F4V3	4,17	4,43	80	100	−2,5	3	1
F4V7	4,56	4,84	50	100	−1,4	3	2
F5V1	4,95	5,25	40	80	−0,8	2	2
F5V6	5,43	5,77	15	40	1,2	1	2
F6V2	6,01	6,39	6	30	2,3	3	4
F6V8	6,60	7,00	6	20	3,0	2	4
F7V5	7,28	7,72	6	20	4,0	1	5
F8V2	7,95	8,45	6	20	4,6	0,7	5
F9V1	8,83	9,37	6	20	5,5	0,5	6
F10	9,7	10,30	8	25	6,4	0,2	7
F11	10,67	11,33	10	25	7,4	0,1	8
F12	11,64	12,36	10	25	8,4	0,1	8
F13	12,61	13,39	10	35	9,4	0,1	8
F15	14,55	15,45	10	40	11,4	0,05	10
F16	15,50	16,50	10	45	12,4	0,05	
F18	17,50	18,50	10	50	14,4	0,05	
F20	19,40	20,60	15	60	16,4	0,05	
F22	21,30	22,70	20	70	18,4	0,05	
F24	23,30	24,70	25	80	20,4	0,05	
	at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA	at I_Z = 0,5 mA	
F27	26,20	27,80	25	80	23,4	0,05	0,7
F30	29,10	30,90	30	100	26,6	0,05	0,7
F33	32,00	34,00	35	120	29,7	0,05	0,7
F36	34,90	37,10	35	140	33,0	0,05	0,7
F39	37,80	40,20	40	150	36,4	0,05	0,7
F43	41,70	44,30	45	160	41,2	0,05	0,7
F47	45,60	48,40	50	170	46,1	0,05	0,7
F51	49,50	52,50	60	180	51,0	0,05	0,7
F56	54,30	57,70	70	200	57,0	0,05	0,7
F62	60,10	63,90	80	220	64,4	0,05	0,7
F68	66,00	70,00	90	240	71,7	0,05	0,7
F75	72,80	77,20	95	255	80,02	0,05	0,7

$T_j = 25\ ^oC$

E24 (± 5%) logarithmic range (for ± 2% tolerance range see page 5).

BZX79-...	working voltage V_Z (V) at I_{Ztest} = 5 mA		differential resistance r_{diff} (Ω) at I_{Ztest} = 5 mA		temperature coefficient S_Z (mV/K) at I_{Ztest} = 5 mA			differential resistance r_{diff} (Ω) at I_Z = 1 mA	
	min.	max.	typ.	max.	min.	typ.	max.	typ.	max.
C2V4	2,2	2,6	70	100	–3,5	–1,6	0	275	600
C2V7	2,5	2,9	75	100	–3,5	–2,0	0	300	600
C3V0	2,8	3,2	80	95	–3,5	–2,1	0	325	600
C3V3	3,1	3,5	85	95	–3,5	–2,4	0	350	600
C3V6	3,4	3,8	85	90	–3,5	–2,4	0	375	600
C3V9	3,7	4,1	85	90	–3,5	–2,5	0	400	600
C4V3	4,0	4,6	80	90	–3,5	–2,5	0	410	600
C4V7	4,4	5,0	50	80	–3,5	–1,4	0,2	425	500
C5V1	4,8	5,4	40	60	–2,7	–0,8	1,2	400	480
C5V6	5,2	6,0	15	40	–2,0	1,2	2,5	80	400
C6V2	5,8	6,6	6	10	0,4	2,3	3,7	40	150
C6V8	6,4	7,2	6	15	1,2	3,0	4,5	30	80
C7V5	7,0	7,9	6	15	2,5	4,0	5,3	30	80
C8V2	7,7	8,7	6	15	3,2	4,6	6,2	40	80
C9V1	8,5	9,6	6	15	3,8	5,5	7,0	40	100
C10	9,4	10,6	8	20	4,5	6,4	8,0	50	150
C11	10,4	11,6	10	20	5,4	7,4	9,0	50	150
C12	11,4	12,7	10	25	6,0	8,4	10,0	50	150
C13	12,4	14,1	10	30	7,0	9,4	11,0	50	170
C15	13,8	15,6	10	30	9,2	11,4	13,0	50	200
C16	15,3	17,1	10	40	10,4	12,4	14,0	50	200
C18	16,8	19,1	10	45	12,4	14,4	16,0	50	225
C20	18,8	21,2	15	55	14,4	16,4	18,0	60	225
C22	20,8	23,3	20	55	16,4	18,4	20,0	60	250
C24	22,8	25,6	25	70	18,4	20,4	22,0	60	250
	at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA			at I_Z = 0,5 mA	
C27	25,1	28,9	25	80	21,4	23,4	25,3	65	300
C30	28,0	32,0	30	80	24,4	26,6	29,4	70	300
C33	31,0	35,0	35	80	27,4	29,7	33,4	75	325
C36	34,0	38,0	35	90	30,4	33,0	37,4	80	350
C39	37,0	41,0	40	130	33,4	36,4	41,2	80	350
C43	40,0	46,0	45	150	37,6	41,2	46,6	85	375
C47	44,0	50,0	50	170	42,0	46,1	51,8	85	375
C51	48,0	54,0	60	180	46,6	51,0	57,2	90	400
C56	52,0	60,0	70	200	52,2	57,0	63,8	100	425
C62	58,0	66,0	80	215	58,8	64,4	71,6	120	450
C68	64,0	72,0	90	240	65,6	71,7	79,8	150	475
C75	70,0	79,0	95	255	73,4	80,2	88,6	170	500

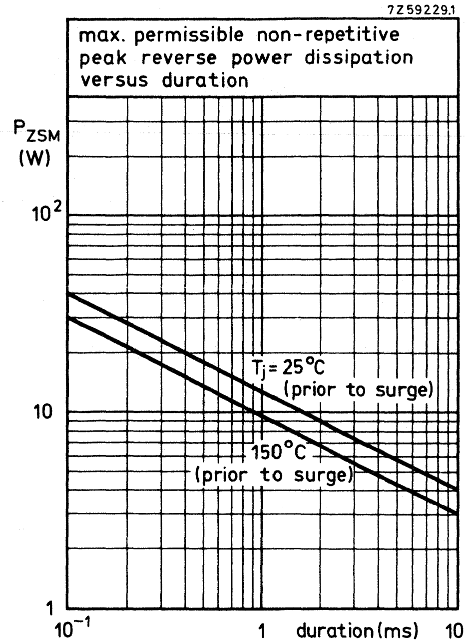

7Z59229.1
max. permissible non-repetitive
peak reverse power dissipation
versus duration
P_ZSM
(W)
10^2
10
1
10^-1
1
duration (ms)
10
Tj = 25 °C
(prior to surge)
150 °C
(prior to surge)

Fig. 2.

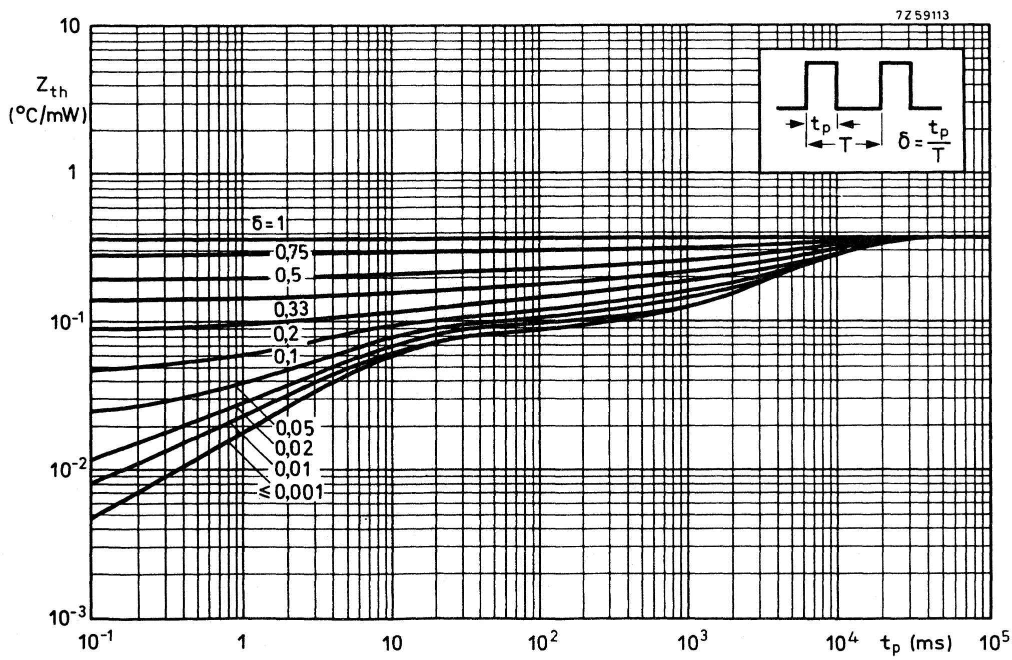

7Z59113
10
Z_th
(°C/mW)
1
10^-1
10^-2
10^-3
10^-1
1
10
10^2
10^3
10^4
t_p (ms)
10^5
δ = 1
0,75
0,5
0,33
0,2
0,1
0,05
0,02
0,01
≤ 0,001
t_p
T
δ = t_p/T

Fig. 3.

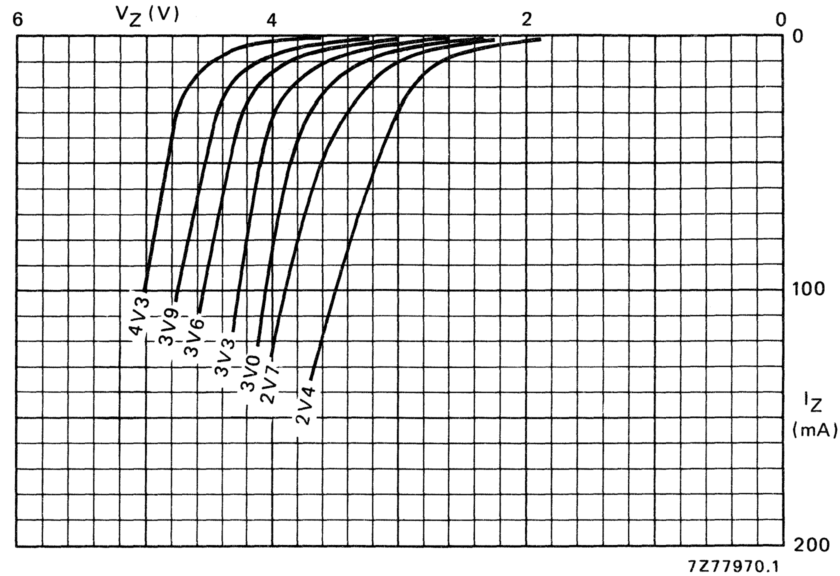


Fig. 4 Static characteristics; typical values; T_{amb} = 25 °C.

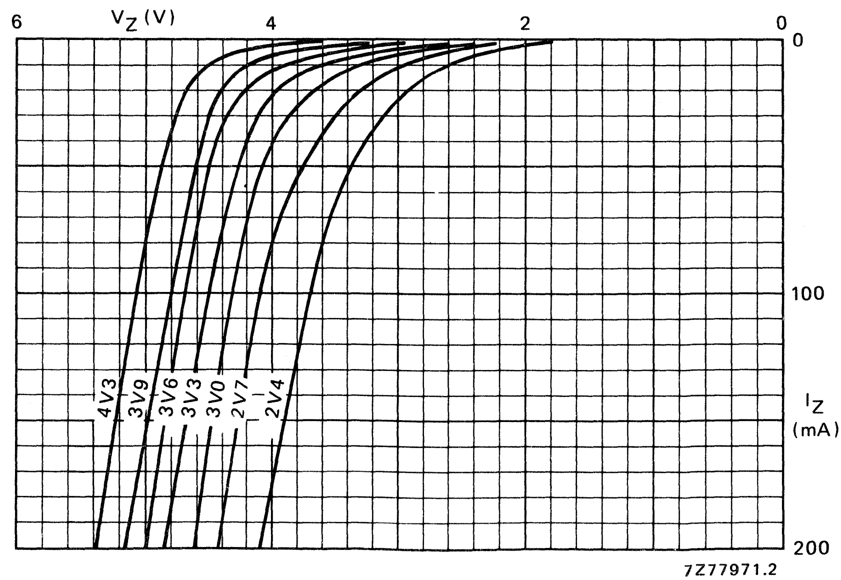


Fig. 5 Dynamic characteristics; typical values; T_j = 25 °C.

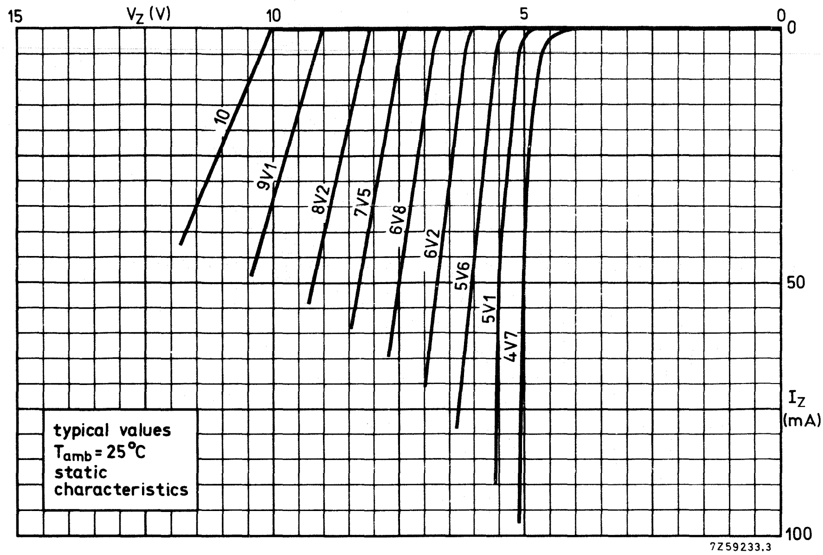

15
V_Z (V)
10
5
0
0
50
100
I_Z (mA)
10
9V1
8V2
7V5
6V8
6V2
5V6
5V1
4V7
typical values
T_{amb} = 25°C
static
characteristics
7Z59233.3

Fig. 6.

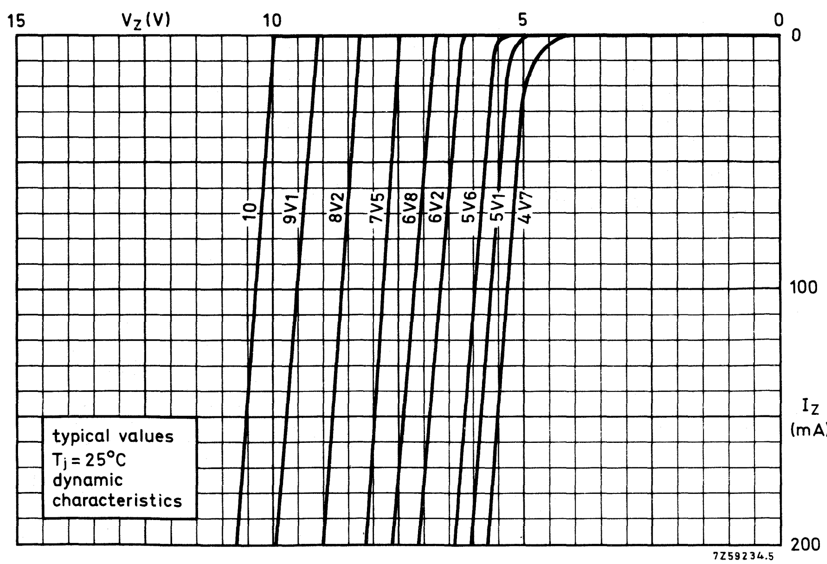

15
V_Z (V)
10
5
0
0
100
200
I_Z (mA)
10
9V1
8V2
7V5
6V8
6V2
5V6
5V1
4V7
typical values
T_j = 25°C
dynamic
characteristics
7Z59234.5

Fig. 7.

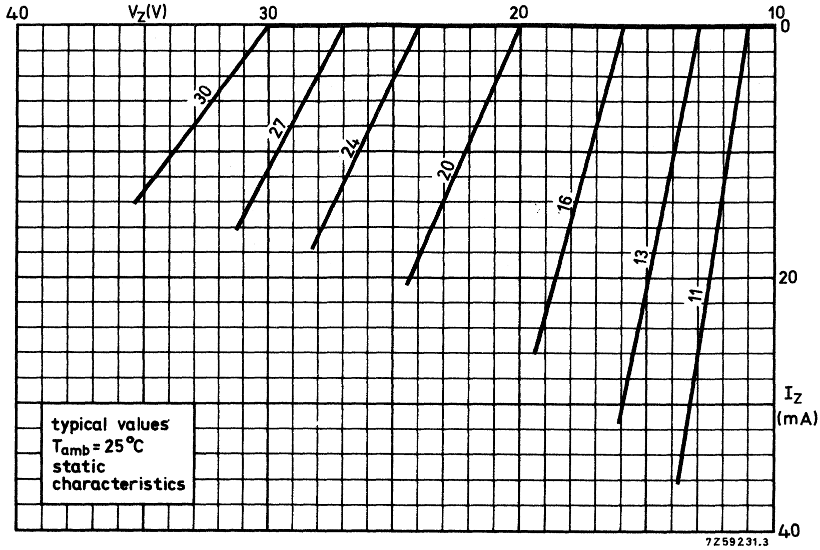

40
V_Z(V)
30
20
10
0
30
27
24
20
16
13
11
20
I_Z
(mA)
40
typical values
T_{amb} = 25 °C
static
characteristics
7Z59231.3

Fig. 8.

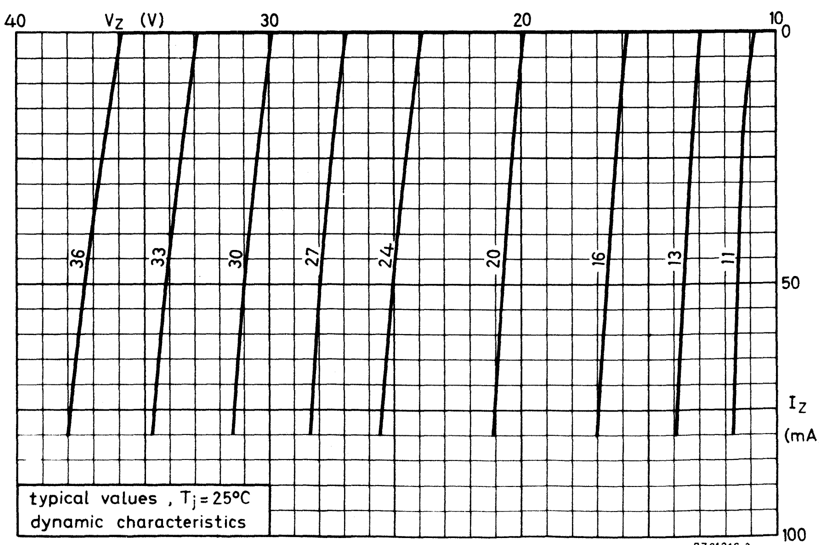

40
V_Z (V)
30
20
10
0
36
33
30
27
24
20
16
13
11
50
I_Z
(mA)
100
typical values, T_j = 25 °C
dynamic characteristics
7Z61216.3

Fig. 9.

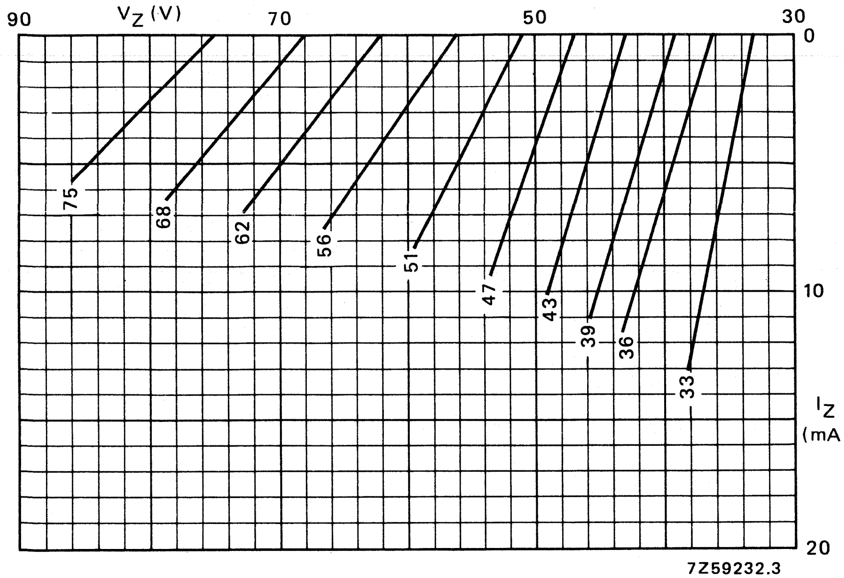


Fig. 10 Static characteristics; typical values; T_{amb} = 25 °C.

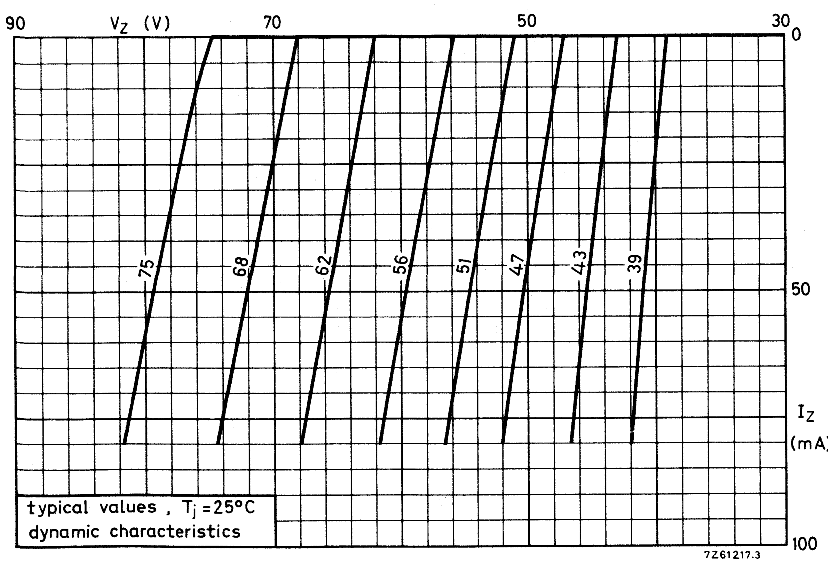


Fig. 11.

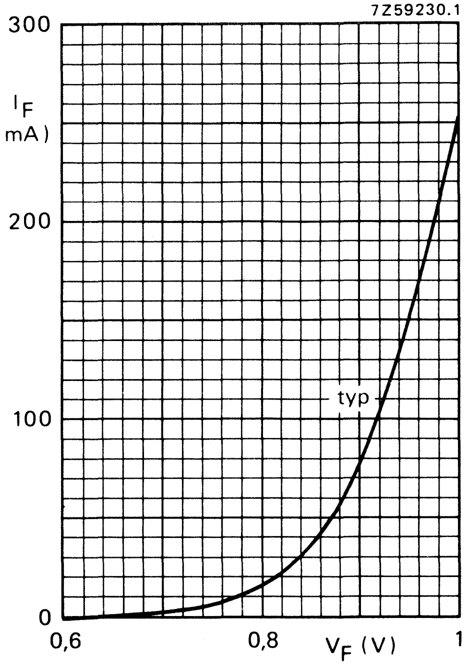


Fig. 12 T_j = 25 °C.

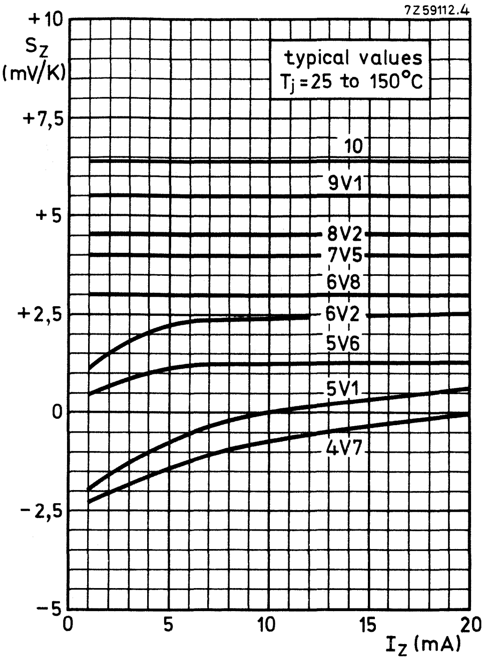


Fig. 13.

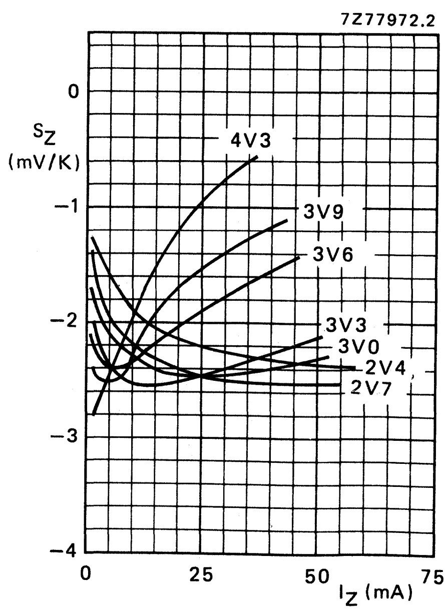


Fig. 14 Typical values; T_j = 25 to 150 °C.

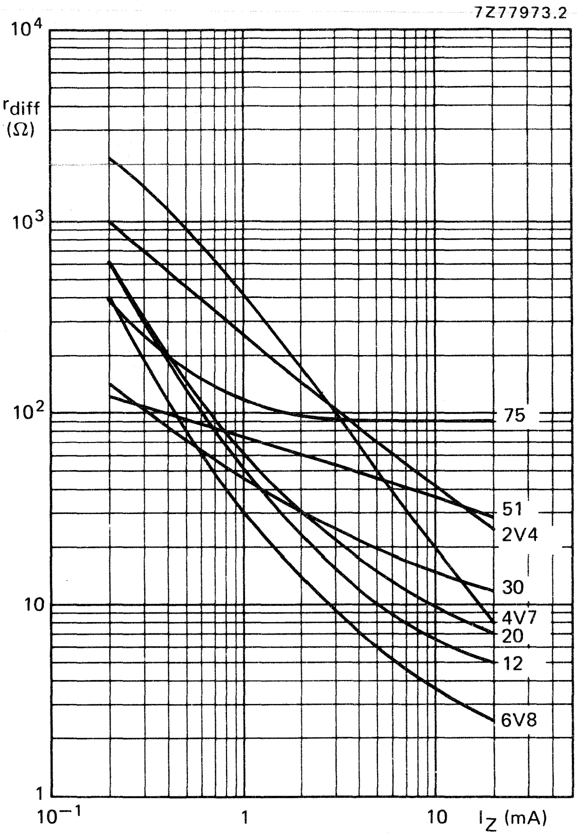


Fig. 15 Typical values; $T_j = 25\ ^oC$; f = 1 kHz.

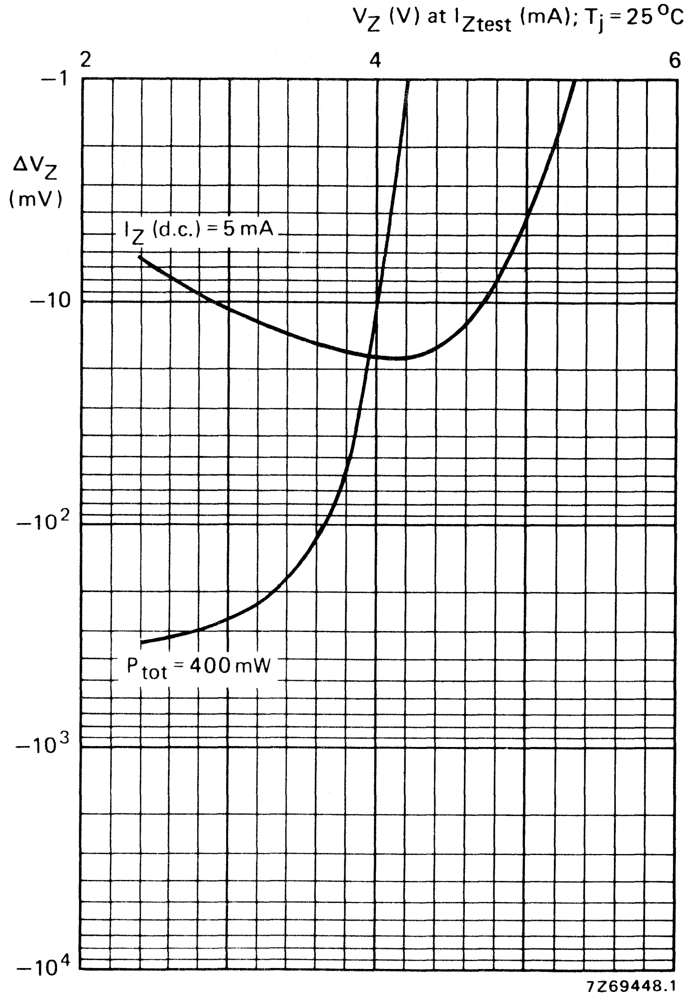


Fig. 16 Typical change of working voltage under operating conditions at T_{amb} = 25 °C.

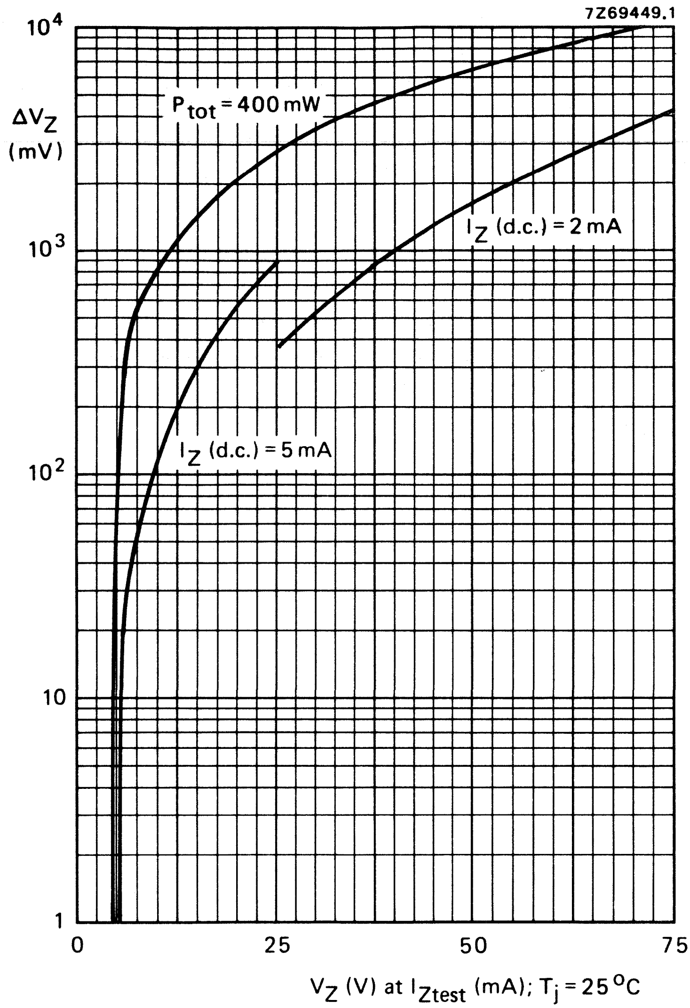


Fig. 17 Typical change of working voltage under operating conditions at T_{amb} = 25 °C.

SILICON PLANAR VOLTAGE REGULATOR DIODES

Low power general purpose voltage regulator diodes in a micro miniature plastic envelope. They are available in three series; one to the international standardized E24 (± 5%) range, one in a tolerance of ± 2% and the other in a tolerance of ± 1%.
Each series consists of 37 types with nominal working voltages from 2.4 V to 75 V.

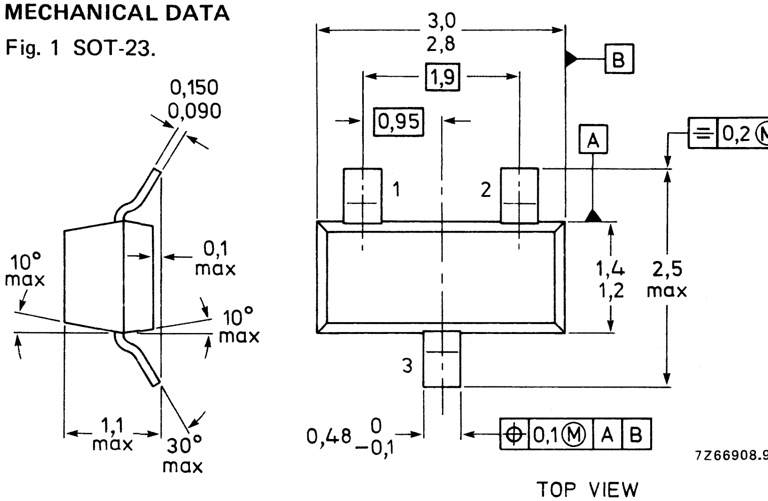
QUICK REFERENCE DATA

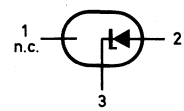
Working voltage range	V_Z	nom.	2.4 to 75	V
Working voltage tolerance			± 5	%
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300	mW
Junction temperature	T_j	max.	175	°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.





See also *Soldering recommendations.*

Marking code

BZX84-C2V4 = Z11	BZX84-C5V6 = Z3	BZX84-C13 = Y3	BZX84-C33 = Y12
C2V7 = Z12	C6V2 = Z4	C15 = Y4	C36 = Y13
C3V0 = Z13	C6V8 = Z5	C16 = Y5	C39 = Y14
C3V3 = Z14	C7V5 = Z6	C18 = Y6	C43 = Y15
C3V6 = Z15	C8V2 = Z7	C20 = Y7	C47 = Y16
C3V9 = Z16	C9V1 = Z8	C22 = Y8	C51 = Y17
C4V3 = Z17	C10 = Z9	C24 = Y9	C56 = Y18
C4V7 = Z1	C11 = Y1	C27 = Y10	C62 = Y19
C5V1 = Z2	C12 = Y2	C30 = Y11	C68 = Y20
			C75 = Y21

Marking for B and A types available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Repetitive peak forward current	I_{FRM}	max.	250 mA
Repetitive peak working current	I_{ZRM}	max.	250 mA
Total power dissipation up to T_{amb} = 25 °C**	P_{tot}	max.	300 mW
→ Storage temperature	T_{stg}		−65 to + 150 °C
→ Junction temperature	T_j	max.	150 °C

THERMAL CHARACTERISTICS*

Thermal resistance**

→ From junction to ambient	$R_{th\ j\text{-}t}$	=	420 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage I_F = 10 mA		V_F	<	0.9 V
Reverse current				
BZX84–.2V4	V_R = 1 V	I_R	<	50 μA
2V7	V_R = 1 V	I_R	<	20 μA
3V0	V_R = 1 V	I_R	<	10 μA
3V3	V_R = 1 V	I_R	<	5 μA
3V6	V_R = 1 V	I_R	<	5 μA
3V9	V_R = 1 V	I_R	<	3 μA
4V3	V_R = 1 V	I_R	<	3 μA
4V7	V_R = 2 V	I_R	<	3 μA
5V1	V_R = 2 V	I_R	<	2 μA
5V6	V_R = 2 V	I_R	<	1 μA
6V2	V_R = 4 V	I_R	<	3 μA
6V8	V_R = 4 V	I_R	<	2 μA
7V5	V_R = 5 V	I_R	<	1 μA
8V2	V_R = 5 V	I_R	<	700 nA
9V1	V_R = 6 V	I_R	<	500 nA
10	V_R = 7 V	I_R	<	200 nA
11	V_R = 8 V	I_R	<	100 nA
12	V_R = 8 V	I_R	<	100 nA
13	V_R = 8 V	I_R	<	100 nA
15 to 75	V_R = 0.7 V_{Znom}	I_R	<	50 nA

. = A for 1%
. = B for 2%
.. = C for (E24), 5%

* See *Thermal characteristics* in chapter GENERAL.
** Device mounted on a ceramic substrate of 7 mm x 5 mm x 0.6 mm.

T_j = 25 °C
± 5% tolerance range

BZX84	working voltage V_Z (V) at I_{Ztest} = 5 mA		differential resistance r_{diff} (Ω) at I_{Ztest} = 5 mA		temperature coefficient S_Z (mV/K) at I_{Ztest} = 5 mA			differential resistance r_{diff} (Ω) at I_Z = 1 mA	
	min.	max.	typ.	max.	min.	typ.	max.	typ.	max.
C2V4	2.20	2.60	70	100	−3.5	−1.6	0	275	600
C2V7	2.50	2.90	75	100	−3.5	−2.0	0	300	600
C3V0	2.80	3.20	80	95	−3.5	−2.1	0	325	600
C3V3	3.10	3.50	85	95	−3.5	−2.4	0	350	600
C3V6	3.40	3.80	85	90	−3.5	−2.4	0	375	600
C3V9	3.70	4.10	85	90	−3.5	−2.5	0	400	600
C4V3	4.00	4.60	80	90	−3.5	−2.5	0	410	600
C4V7	4.40	5.00	50	80	−3.5	−1.4	0.2	425	500
C5V1	4.80	5.40	40	60	−2.7	−0.8	1.2	400	480
C5V6	5.20	6.00	15	40	−2.0	1.2	2.5	80	400
C6V2	5.80	6.60	6	10	0.4	2.3	3.7	40	150
C6V8	6.40	7.20	6	15	1.2	3.0	4.5	30	80
C7V5	7.00	7.90	6	15	2.5	4.0	5.3	30	80
C8V2	7.70	8.90	6	15	3.2	4.6	6.2	40	80
C9V1	9.50	9.60	6	15	3.8	5.5	7.0	40	100
C10	9.40	10.60	8	20	4.5	6.4	8.0	50	150
C11	10.40	11.60	10	20	5.4	7.4	9.0	50	150
C12	11.40	12.70	10	25	6.0	8.4	10.0	50	150
C13	12.40	14.10	10	30	7.0	9.4	11.0	50	170
C15	13.80	15.60	10	30	9.2	11.4	13.0	50	200
C16	15.30	17.10	10	40	10.4	12.4	14.0	50	200
C18	16.80	19.10	10	45	12.4	14.4	16.0	50	225
C20	18.80	21.20	15	55	14.4	16.4	18.0	60	225
C22	20.80	23.30	20	55	16.4	18.4	20.0	60	250
C24	22.80	25.60	25	70	18.4	20.4	22.0	60	250
	at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA			at I_Z = 0.5 mA	
C27	25.10	28.90	25	80	21.4	23.4	25.3	65	300
C30	28.00	32.00	30	80	24.4	26.6	29.4	70	300
C33	31.00	35.00	35	80	27.4	29.7	33.4	75	325
C36	34.00	38.00	35	90	30.4	33.0	37.4	80	350
C39	37.00	41.00	40	130	33.4	36.4	41.2	80	350
C43	40.00	46.00	45	150	37.6	41.2	46.6	85	375
C47	44.00	50.00	50	170	42.0	46.1	51.8	85	375
C51	48.00	54.00	60	180	46.6	51.0	57.2	90	400
C56	52.00	60.00	70	200	52.2	57.0	63.8	100	425
C62	58.00	66.00	80	215	58.8	64.4	71.6	120	450
C68	64.00	72.00	90	240	65.6	71.7	79.8	150	475
C75	70.00	79.00	95	255	73.4	80.02	88.6	170	500

± 2% tolerance range

BZX84	working voltage V_Z (V) at I_{Ztest} = 5 mA min.	max.	differential resistance r_{diff} (Ω) at I_{Ztest} = 5 mA typ.	max.	temperature coefficient S_Z (mV/K) at I_{Ztest} = 5 mA min.	typ.	max.	differential resistance r_{diff} (Ω) at I_Z = 1 mA typ.	max.
B2V4	2.35	2.45	70	100	−3.5	−1.6	0	275	600
B2V7	2.65	2.75	75	100	−3.5	−2.0	0	300	600
B3V0	2.94	3.06	80	95	−3.5	−2.1	0	325	600
B3V3	3.23	3.37	85	95	−3.5	−2.4	0	350	600
B3V6	3.53	3.67	85	90	−3.5	−2.4	0	375	600
B3V9	3.82	3.98	85	90	−3.5	−2.5	0	400	600
B4V3	4.21	4.39	80	90	−3.5	−2.5	0	410	600
B4V7	4.61	4.79	50	80	−3.5	−1.4	0.2	425	500
B5V1	5.00	5.20	40	60	−2.7	−0.8	1.2	400	480
B5V6	5.49	5.71	15	40	−2.0	1.2	2.5	80	400
B6V2	6.08	6.32	6	10	0.4	2.3	3.7	40	150
B6V8	6.66	6.94	6	15	1.2	3.0	4.5	30	80
B7V5	7.35	7.65	6	15	2.5	4.0	5.3	30	80
B8V2	8.04	8.36	6	15	3.2	4.6	6.2	40	80
B9V1	8.92	9.28	6	15	3.8	5.5	7.0	40	100
B10	9.80	10.20	8	20	4.5	6.4	8.0	50	150
B11	10.80	11.20	10	20	5.4	7.4	9.0	50	150
B12	11.80	12.20	10	25	6.0	8.4	10.0	50	150
B13	12.70	13.30	10	30	7.0	9.4	11.0	50	170
B15	14.70	15.30	10	30	9.2	11.4	13.0	50	200
B16	15.70	16.30	10	40	10.4	12.4	14.0	50	200
B18	17.60	18.40	10	45	12.4	14.4	16.0	50	225
B20	19.60	20.40	15	55	14.4	16.4	18.0	60	225
B22	21.60	22.40	20	55	16.4	18.4	20.0	60	250
B24	23.50	24.50	25	70	18.4	20.4	22.0	60	250
	at I_{Ztest} = 2 mA		**at I_{Ztest} = 2 mA**		**at I_{Ztest} = 2 mA**			**at I_Z = 0.5 mA**	
B27	26.50	27.50	25	80	21.4	23.4	25.3	65	300
B30	29.40	30.60	30	80	24.4	26.6	29.4	70	300
B33	32.30	33.70	35	80	27.4	29.7	33.4	75	325
B36	35.30	36.70	35	90	30.4	33.0	37.4	80	350
B39	38.20	39.80	40	130	33.4	36.4	41.2	80	350
B43	42.10	43.90	45	150	37.6	41.2	46.6	85	375
B47	46.10	47.90	50	170	42.0	46.1	51.8	85	375
B51	50.00	51.00	60	180	46.6	51.0	57.2	90	400
B56	54.90	57.10	70	200	52.2	57.0	63.8	100	425
B62	60.80	63.20	80	215	58.8	64.4	71.6	120	450
B68	66.60	69.40	90	240	65.6	71.7	79.8	150	475
B75	73.50	76.50	95	255	73.4	80.02	88.6	170	500

T_j = 25 °C
± 1% tolerance range

BZX84	working voltage V_Z (V) at I_{Ztest} = 5 mA		differential resistance r_{diff} (Ω) at I_{Ztest} = 5 mA		temperature coefficient S_Z (mV/K) at I_{Ztest} = 5 mA			differential resistance r_{diff} (Ω) at I_Z = 1 mA	
	min.	max.	typ.	max.	min.	typ.	max.	typ.	max.
A2V4	2.37	2.43	70	100	−3.5	−1.6	0	275	600
A2V7	2.67	2.73	75	100	−3.5	−2.0	0	300	600
A3V0	2.97	3.03	80	95	−3.5	−2.1	0	325	600
A3V3	3.26	3.34	85	95	−3.5	−2.4	0	350	600
A3V6	3.56	3.64	85	90	−3.5	−2.4	0	375	600
A3V9	3.86	3.94	85	90	−3.5	−2.5	0	400	600
A4V3	4.25	4.35	80	90	−3.5	−2.5	0	410	600
A4V7	4.65	4.75	50	80	−3.5	−1.4	0.2	425	500
A5V1	5.04	5.16	40	60	−2.7	−0.8	1.2	400	480
A5V6	5.54	5.66	15	40	−2.0	1.2	2.5	80	400
A6V2	6.13	6.27	6	10	0.4	2.3	3.7	40	150
A6V8	6.73	6.87	6	15	1.2	3.0	4.5	30	80
A7V5	7.42	7.58	6	15	2.5	4.0	5.3	30	80
A8V2	8.11	8.29	6	15	3.2	4.6	6.2	40	80
A9V1	9.0	9.2	6	15	3.8	5.5	7.0	40	100
A10	9.9	10.10	8	20	4.5	6.4	8.0	50	150
A11	10.8	11.11	10	20	5.4	7.4	9.0	50	150
A12	11.88	12.12	10	25	6.0	8.4	10.0	50	150
A13	12.87	13.13	10	30	7.0	9.4	11.0	50	170
A15	14.85	15.15	10	30	9.2	11.4	13.0	50	200
A16	15.84	16.16	10	40	10.4	12.4	14.0	50	200
A18	17.82	18.18	10	45	12.4	14.4	16.0	50	225
A20	19.80	20.20	15	55	14.4	16.4	18.0	60	225
A22	21.78	22.22	20	55	16.4	18.4	20.0	60	250
A24	23.76	24.24	25	70	18.4	20.4	22.0	60	250
	at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA		at I_{Ztest} =.2 mA			at I_Z = 0.5 mA	
A27	26.73	27.27	25	80	21.4	23.4	25.3	65	300
A30	29.70	30.30	30	80	24.4	26.6	29.4	70	300
A33	32.67	33.33	35	80	27.4	29.7	33.4	75	325
A36	35.64	36.36	35	90	30.4	33.0	37.4	80	350
A39	38.61	39.39	40	130	33.4	36.4	41.2	80	350
A43	42.57	43.43	45	150	37.6	41.2	46.6	85	375
A47	46.53	47.47	50	170	42.0	46.1	51.8	85	375
A51	50.49	51.51	60	180	46.6	51.0	57.2	90	400
A56	55.44	56.56	70	200	52.2	57.0	63.8	100	425
A62	61.38	62.62	80	215	58.8	64.4	71.6	120	450
A68	74.25	75.75	90	240	65.6	71.7	79.8	150	475
A75	90.09	91.91	95	255	73.4	80.02	88.6	170	500

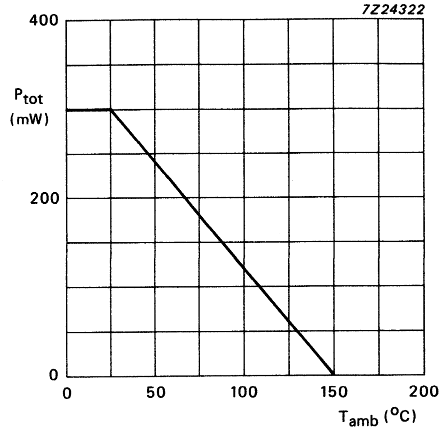


Fig. 2 Power derating curve.

Model for calculating the static working voltage ($V_{Z\ stat}$).

This model can be derived from $V_{Z\ stat} = V_{Z\ dyn} + \Delta V_Z$ of which $V_{Z\ dyn}$ is given in the preceding tables and can be derived from the typical dynamic characteristic curves in Figs 3 to 6.
$\Delta V_Z = \Delta T \times S_Z$. For S_Z see tables and graphs S_Z versus T_j.
$\Delta T = P_{tot} \times R_{th\ j\text{-}a} = I_Z \times V_{Z\ dyn} \times R_{th\ j\text{-}a}$.
Following $\Delta V_Z = I_Z \times V_{Z\ dyn} \times R_{th\ j\text{-}a} \times S_Z$ and the model will be:

$$V_{Z\ stat} = V_{Z\ dyn} + I_Z \times V_{Z\ dyn} \times R_{th\ j\text{-}a} \times S_Z$$

Calculating example

BZX84-C24 mounted on a ceramic substrate of 7 x 5 x 0.6 mm; at I_Z = 7 mA.

$$V_{Z\ stat} = 24 + \left(\frac{7}{1000} \times 24 \times \frac{430}{1000} \times 20.3\right)$$

$$= 24 + 1.47 = 25.47\ \text{V}.$$

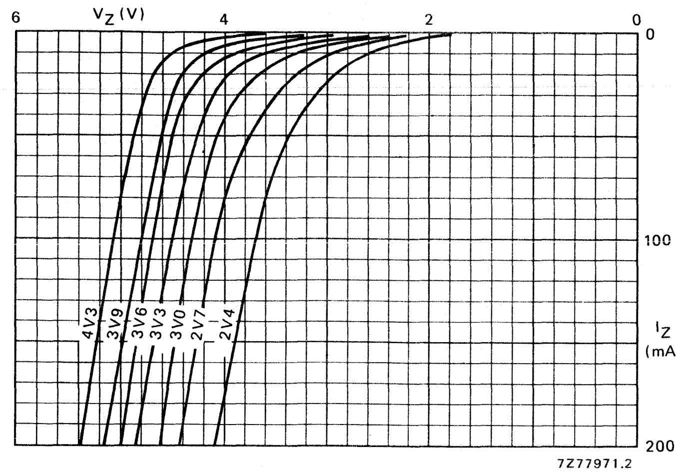


Fig. 3 Dynamic characteristics; typical values; T_j = 25 °C.

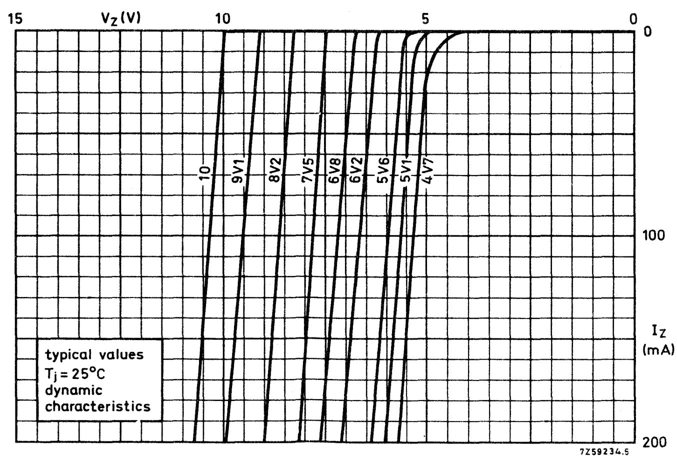


Fig. 4 Dynamic characteristics; typical values; T_j = 25 °C.

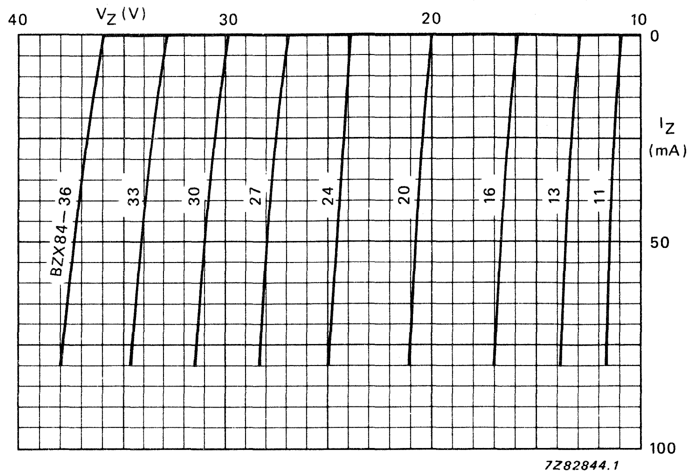


Fig. 5 Dynamic characteristics; typical values; T_j = 25 °C.

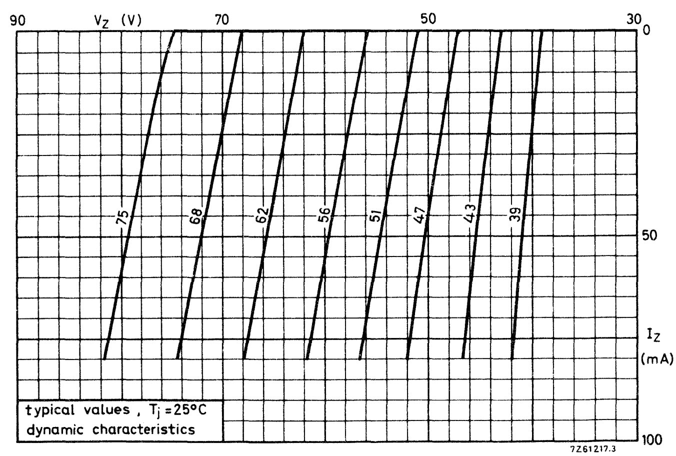


Fig. 6 Dynamic characteristics; typical values; T_j = 25 °C.

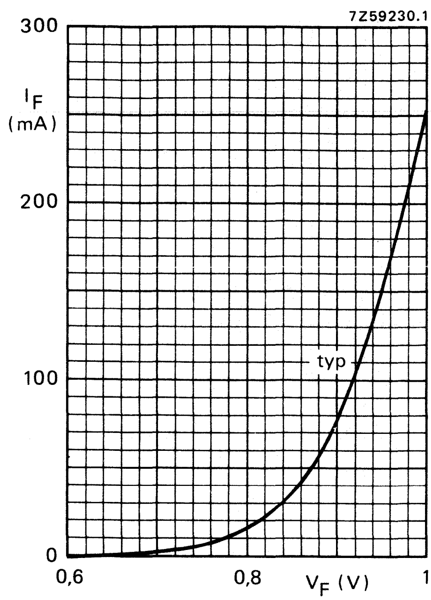


Fig. 7 Typical values at T_j = 25 °C.

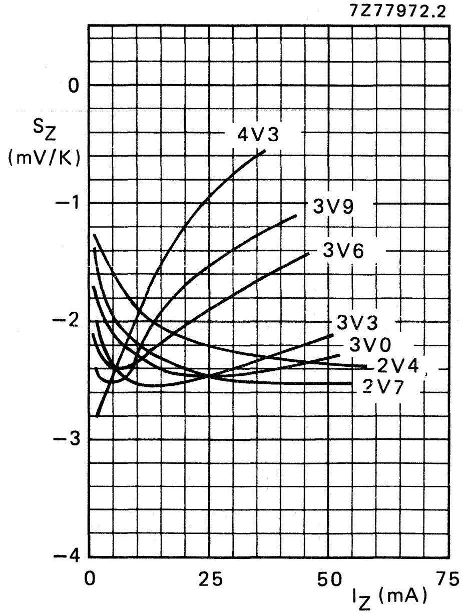


Fig. 8 Typical values; T_j = 25 to 175 °C.

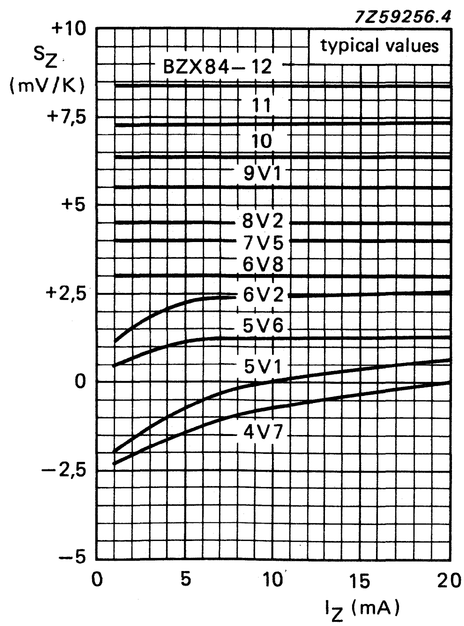


Fig. 9 Typical values; T_j = 25 to 175 °C.

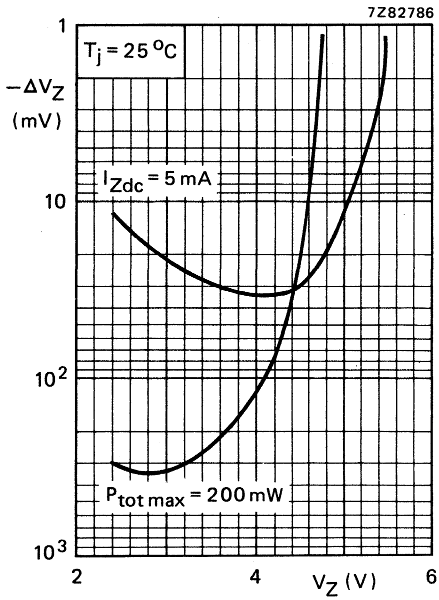


Fig. 10 Typical values; T_j = 25 °C.

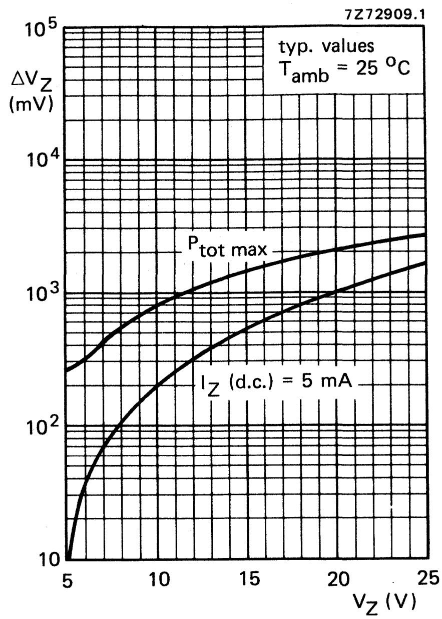


Fig. 11 Typical values; T_{amb} = 25 °C.

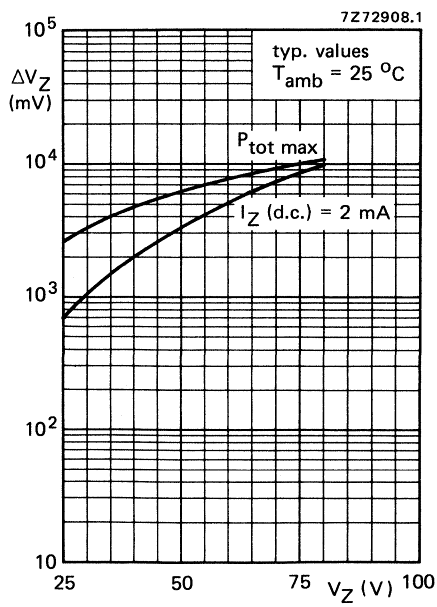


Fig. 12 Typical values; T_{amb} = 25 °C.

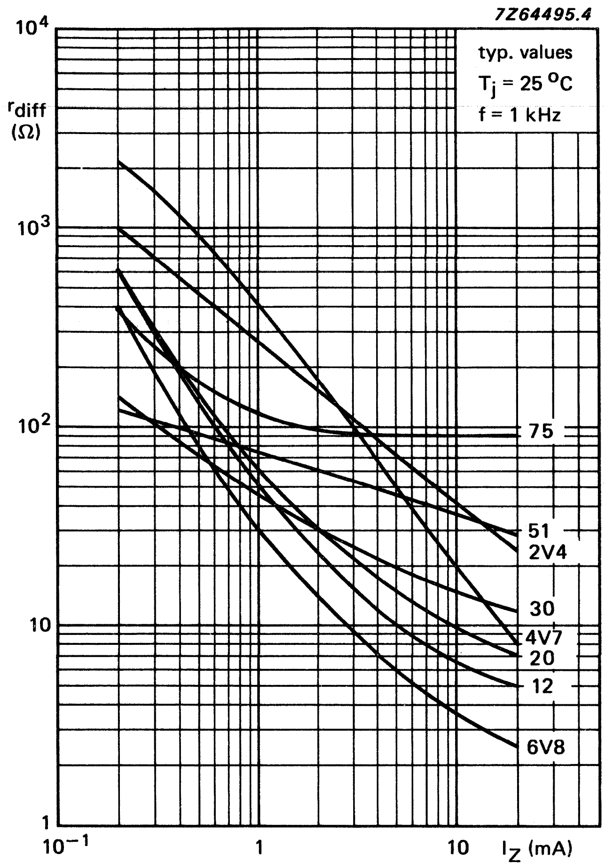

7Z64495.4
typ. values
T_j = 25 °C
f = 1 kHz
r_{diff} (Ω)
10^4
10^3
10^2
10
1
10^{-1}
1
10
I_Z (mA)
75
51
2V4
30
4V7
20
12
6V8

Fig. 13.

SILICON PLANAR EPITAXIAL HIGH SPEED DIODES

Silicon epitaxial high speed diodes in a microminiature plastic envelope. It is intended for high-speed switching in thick and thin-film circuits.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	70	V
Forward current (DC)	I_F	max.	200	mA
Non-repetitive peak forward current	I_{FSM}	max.	500	mA
Total power dissipation at T_{amb} = 25 °C	P_{tot}	max.	300	mW
Junction temperature	T_j	max.	150	°C
Forward voltage at I_F = 10 mA	V_F	<	1	V
Reverse recovery time I_F = 10 mA to I_R = 10 mA measured at I_R = 1 mA	t_{rr}	<	15	ns

MECHANICAL DATA

Dimensions in mm

Marking code:
PMBD914: 5D

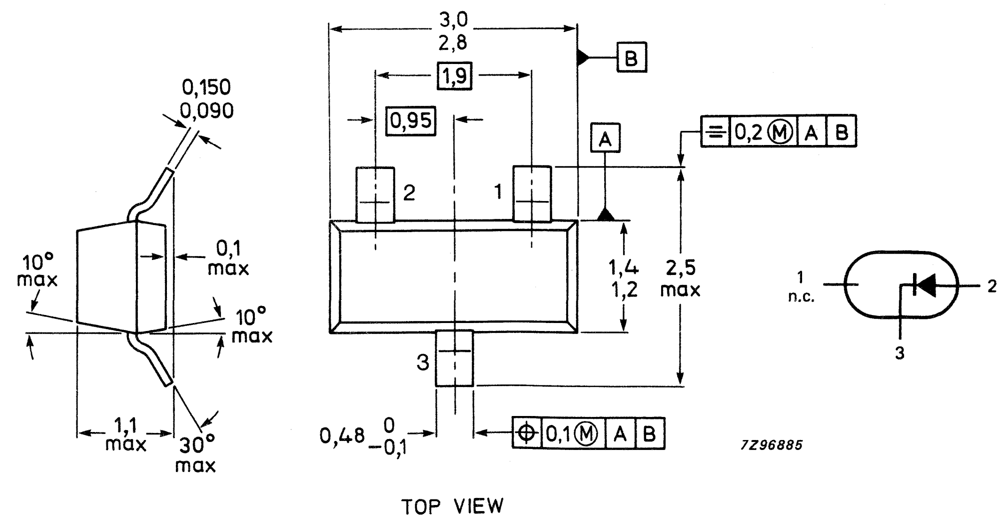


Fig. 1 SOT-23.

See also soldering recommendations.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	70 V
Forward current (DC)	I_F	max.	200 mA
Non-repetitive peak forward current	I_{FSM}	max.	500 mA
Total power dissipated up to T_{amb} = 25 °C	P_{tot}	max.	300 mW
Storage temperature	T_{stg}		−65 to +150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE*

From junction to ambient**	$R_{th\ j\text{-}a}$		430 K/W

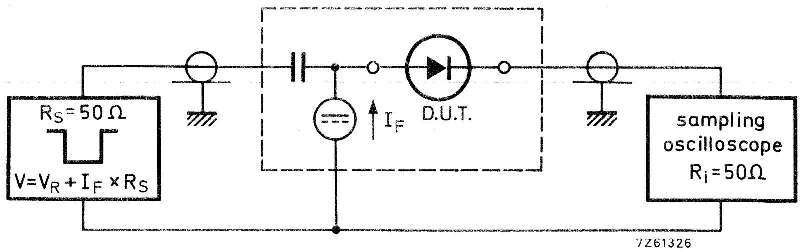
CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Forward voltage I_F = 10 mA	V_F	<	1.0 V
Reverse breakdown voltage I_R = 100 μA	$V_{(br)r}$	>	100 V
Reverse current V_R = 25 V	I_R	<	25 nA
V_R = 75 V	I_R	<	5 μA
Diode capacitance V_R = 0 V; f = 1 MHz	C_d	<	4.0 pF
Reverse recovery time switched from I_F = 10 mA to I_R = 10 mA; measured at I_R = 1 mA (see Fig. 2)	t_{rr}	<	15 ns

* See Thermal Resistance.

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm.



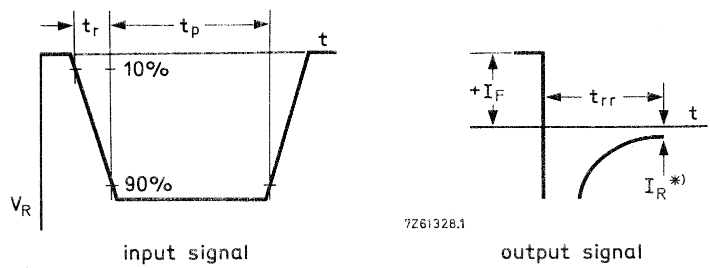


Fig. 2 Test circuit and waveforms; reverse recovery time.

SILICON PLANAR EPITAXIAL HIGH SPEED DIODES

The PMBD2835 and 2836 consist of two diodes in a microminiature plastic envelope. The anodes are commoned and the unit is intended for high speed switching.

QUICK REFERENCE DATA (per diode)

			PMBD2835	PMBD2836	
Continuous reverse voltage	V_R	max.	30	70	V
Forward current (DC)	I_F	max.	100		mA
Total power dissipation at T_{amb} = 25 °C	P_{tot}	max.	300		mW
Junction temperature	T_j	max.	150		°C
Forward voltage at I_F = 50 mA	V_F	<	1.0		V
Reverse recovery time I_F = 10 mA to I_R = 10 mA measured at I_R = 1 mA	t_{rr}	<	15		ns

MECHANICAL DATA

Dimensions in mm

Marking code:
PMBD2835: A3
PMBD2836: A2

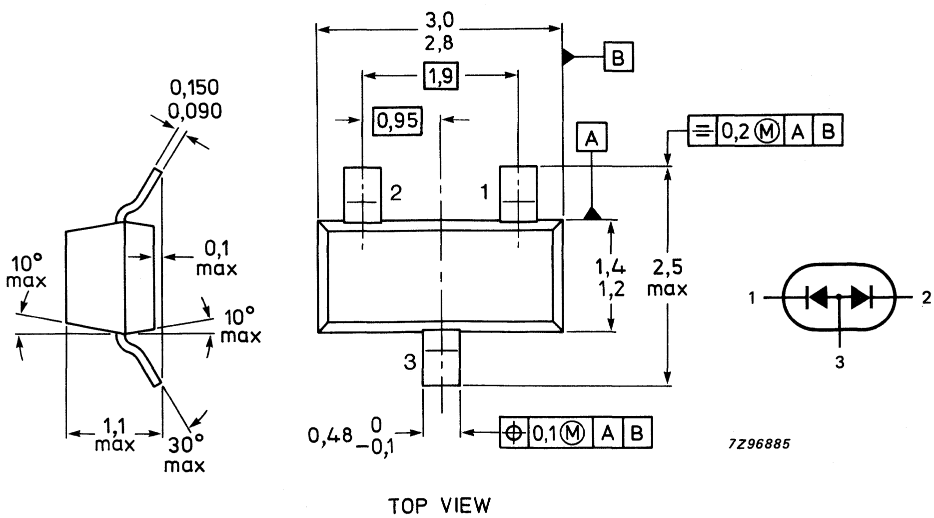


Fig. 1 SOT-23.

See also soldering recommendations.

RATINGS (per diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			PMBD2835	PMBD2836	
Continuous reverse voltage	V_R	max.	30	70	V
Forward current (DC)	I_F	max.	100		mA
Total power dissipated up to T_{amb} = 25 °C	P_{tot}	max.	300		mW
Storage temperature	T_{stg}		−65 to + 150		°C
Junction temperature	T_j	max.	150		°C

THERMAL RESISTANCE*

From junction to ambient**	$R_{th\ j\text{-}a}$	430	K/W

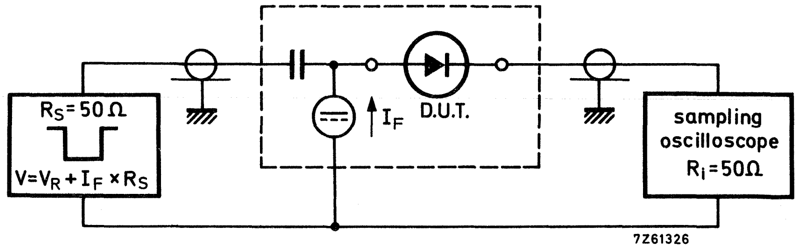
CHARACTERISTICS (per diode)

T_{amb} = 25 °C unless otherwise specified

Forward voltage					
I_F = 10 mA		V_F	<	1.0	V
I_F = 50 mA		V_F	<	1.0	V
I_F = 100 mA		V_F	<	1.2	V
Reverse breakdown voltage					
I_R = 100 μA	PMBD2835	$V_{(br)r}$	>	35	V
	PMBD2836	$V_{(br)r}$	>	75	V
Reverse current					
V_R = 30 V	PMBD2835	I_R	<	100	nA
V_R = 50 V	PMBD2836	I_R	<	100	nA
Diode capacitance					
V_R = 0 V; f = 1 MHz		C_d	<	4.0	pF
Reverse recovery time switched from I_F = 10 mA to I_R = 10 mA; measured at I_R = 1 mA (see Fig. 2)		t_{rr}	<	15	ns

* See Thermal Resistance.

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm.



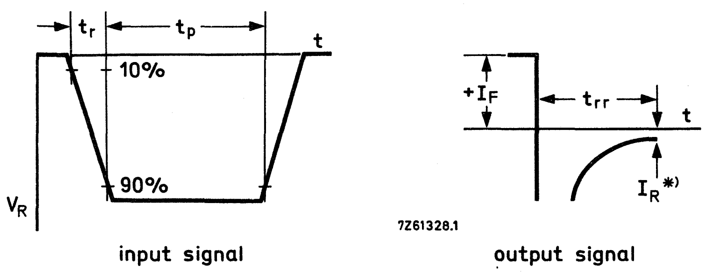


Fig. 2 Test circuit and waveforms; reverse recovery time.

DEVELOPMENT DATA

SILICON PLANAR EPITAXIAL HIGH SPEED DIODES

The PMBD2837 and 2838 consist of two diodes in a microminiature plastic envelope. The cathodes are commoned and the unit is intended for high speed switching.

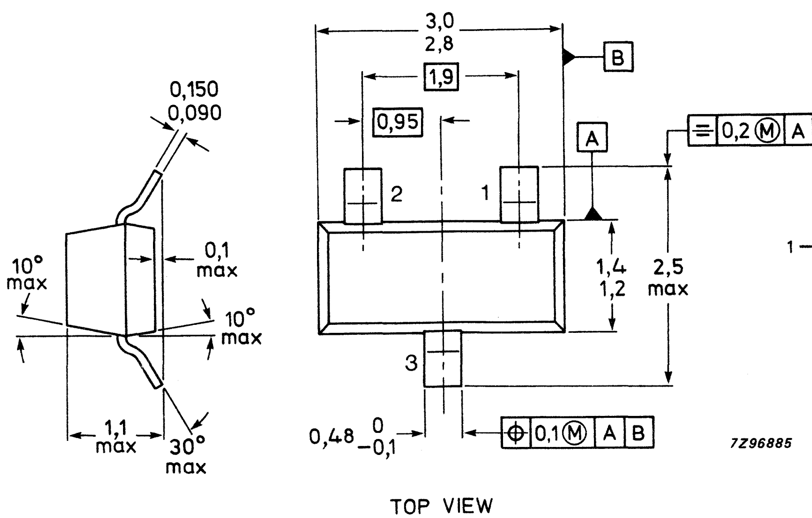
QUICK REFERENCE DATA (per diode)

			PMBD2837	PMBD2838	
Continuous reverse voltage	V_R	max.	30	50	V
Repetitive peak reverse voltage	V_{RRM}	max.	35	75	V
Repetitive peak forward current	I_{FRM}	max.	300		mA
Total power dissipation at T_{amb} = 25 °C	P_{tot}	max.	300		mW
Junction temperature	T_j	max.	150		°C
Forward voltage at I_F = 50 mA	V_F	<	1.0		V
Reverse recovery time I_F = 10 mA to I_R = 10 mA measured at I_R = 1 mA	t_{rr}	<	15		ns

MECHANICAL DATA

Dimensions in mm

Marking code:
PMBD2837: A5
PMBD2838: A6



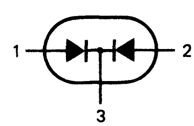


Fig. 1 SOT-23.

See also soldering recommendations.

RATINGS (per diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			PMBD2837	PMBD2838	
Continuous reverse voltage	V_R	max.	30	50	V
Repetitive peak reverse voltage	V_{RRM}	max.	35	75	V
Average rectified forward current	I_{Fav}	max.	150		mA
Repetitive peak forward current	I_{FRM}	max.	300		mA
Total power dissipated up to T_{amb} = 25 °C	P_{tot}	max.	300		mW
Storage temperature	T_{stg}		−65 to + 150		°C
Junction temperature	T_j	max.	150		°C

THERMAL RESISTANCE*

From junction to ambient**	$R_{th\ j\text{-}a}$	430	K/W

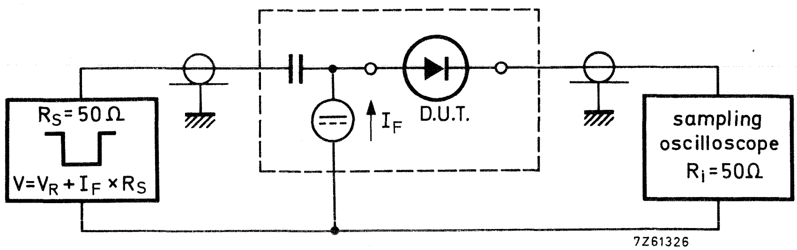
CHARACTERISTICS (per diode)

T_{amb} = 25 °C unless otherwise specified

Forward voltage					
I_F = 10 mA		V_F	<	1.0	V
I_F = 50 mA		V_F	<	1.0	V
I_F = 100 mA		V_F	<	1.2	V
Reverse breakdown voltage					
I_R = 100 μA	PMBD2837	$V_{(br)r}$	>	35	V
	PMBD2838	$V_{(br)r}$	>	75	V
Reverse current					
V_R = 30 V	PMBD2837	I_R	<	100	nA
V_R = 50 V	PMBD2838	I_R	<	100	nA
Diode capacitance					
V_R = 0 V; f = 1 MHz		C_d	<	4.0	pF
Reverse recovery time switched from I_F = 10 mA to I_R = 10 mA; measured at I_R = 1 mA (see Fig. 2)		t_{rr}	<	15	ns

* See Thermal Resistance.

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm.



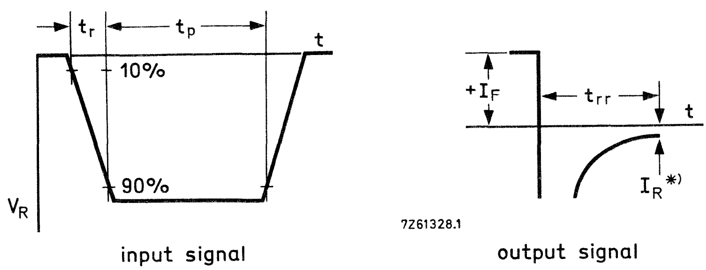


Fig. 2 Test circuit and waveforms; reverse recovery time.

SILICON PLANAR EPITAXIAL HIGH SPEED DIODES

Silicon epitaxial high speed diodes in a microminiature plastic envelope. It is intended for high-speed switching in thick and thin-film circuits.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	70	V
Forward current (DC)	I_F	max.	200	mA
Non-repetitive peak forward current	I_{FSM}	max.	500	mA
Total power dissipation at T_{amb} = 25 °C	P_{tot}	max.	300	mW
Junction temperature	T_j	max.	150	°C
Forward voltage at I_F = 100 mA	V_F	>	0.85	V
		<	1.1	V
Reverse recovery time I_F = 10 mA to I_R = 10 mA measured at I_R = 1 mA	t_{rr}	<	15	ns

MECHANICAL DATA

Dimensions in mm

Marking code:
PMBD6050: 5A

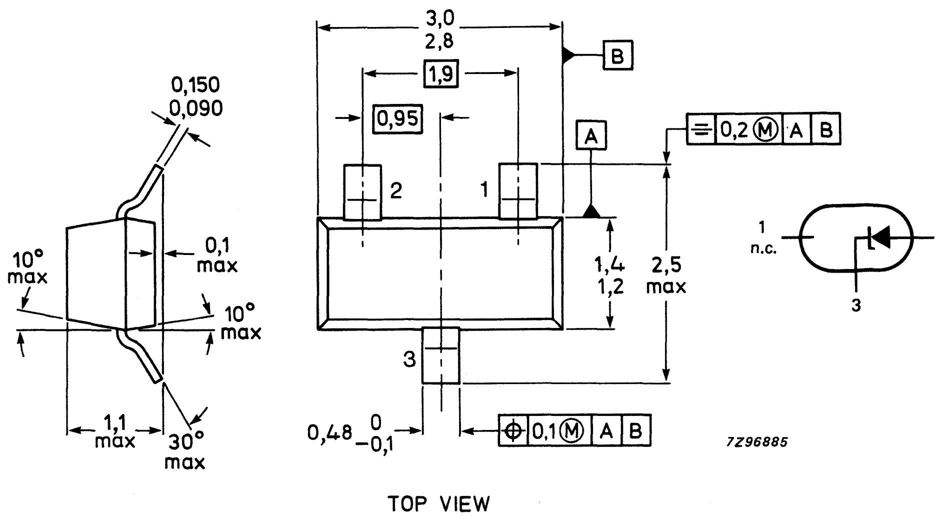


Fig. 1 SOT-23.

See also soldering recommendations.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	70 V
Forward current (DC)	I_F	max.	200 mA
Non-repetitive peak forward current	I_{FSM}	max.	500 mA
Total power dissipated up to T_{amb} = 25 °C	P_{tot}	max.	300 mW
Storage temperature	T_{stg}		−65 to + 150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE*

From junction to ambient**	$R_{th\ j\text{-}a}$		430 K/W

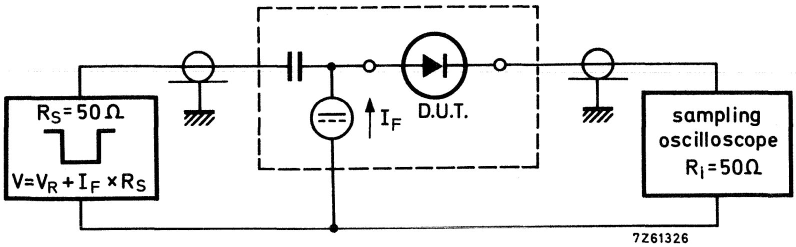
CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Forward voltage			
I_F = 1 mA	V_F	>	0.55 V
		<	0.70 V
I_F = 100 mA	V_F	>	0.85 V
		<	1.10 V
Reverse breakdown voltage I_R = 100 μA	$V_{(br)r}$	>	70 V
Reverse current V_R = 50 V	I_R	<	100 nA
Diode capacitance V_R = 0 V; f = 1 MHz	C_d	<	2.5 pF
Reverse recovery time switched from I_F = 10 mA to I_R = 10 mA; measured at I_R = 1 mA (see Fig. 2)	t_{rr}	<	15 ns

* See Thermal Resistance

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm.



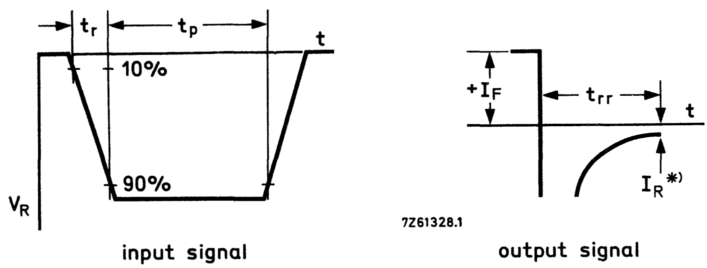


Fig. 2 Test circuit and waveforms; reverse recovery time.

DEVELOPMENT DATA

SILICON PLANAR EPITAXIAL HIGH SPEED DIODES

The PMBD6100 consists of two diodes in a microminiature plastic envelope. The cathodes are commoned and the unit is intended for high speed switching.

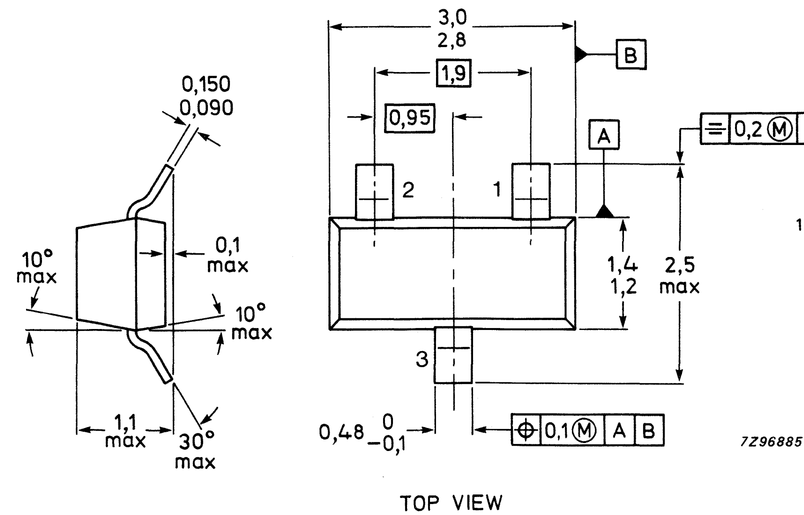
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	70	V
Forward current (DC)	I_F	max.	200	mA
Non-repetitive peak forward current	I_{FSM}	max.	500	mA
Total power dissipation at T_{amb} = 25 °C	P_{tot}	max.	300	mW
Junction temperature	T_j	max.	150	°C
Forward voltage at I_F = 1 mA	V_F	>	0.85	V
		<	1.1	V
Reverse recovery time I_F = 10 mA to I_R = 10 mA measured at I_R = 1 mA	t_{rr}	<	15	ns

MECHANICAL DATA

Dimenions in mm

Marking code:
PMBD6100: 5B



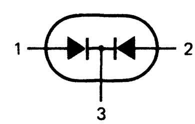


Fig. 1 SOT-23.

See also soldering recommendations.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	70	V
Forward current (DC)	I_F	max.	200	mA
Non-repetitive peak forward current	I_{FSM}	max.	500	mA
Total power dissipated up to T_{amb} = 25 °C	P_{tot}	max.	300	mW
Storage temperature	T_{stg}	–65 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE*

From junction to ambient**	$R_{th\ j\text{-}a}$	430	430	K/W

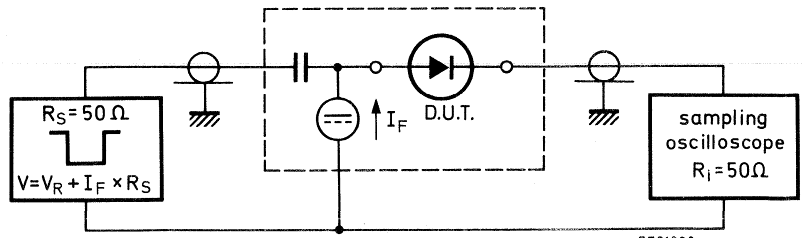
CHARACTERISTICS (per diode)

T_{amb} = 25 °C unless otherwise specified

Forward voltage				
I_F = 1 mA	V_F	>	0.55	V
		<	0.70	V
I_F = 100 mA	V_F	>	0.85	V
		<	1.10	V
Reverse breakdown voltage				
I_R = 100 μA	$V_{(br)r}$	>	70	V
Reverse current V_R = 50 V	I_R	<	100	nA
Diode capacitance				
V_R = 0 V; f = 1 MHz	C_d	<	2.5	pF
Reverse recovery time switched from I_F = 10 mA to I_R = 10 mA; measured at I_R = 1 mA (see Fig. 2)	t_{rr}	<	15	ns

* See Thermal Resistance

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm.



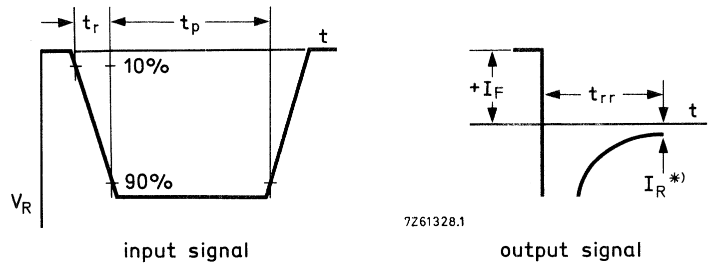


Fig. 2 Test circuit and waveforms; reverse recovery time.

DEVELOPMENT DATA

SILICON PLANAR EPITAXIAL HIGH SPEED DIODES

The PMBD7000 consists of two diodes in a microminiature plastic envelope. The diodes are connected in series and the unit is intended for high speed switching.

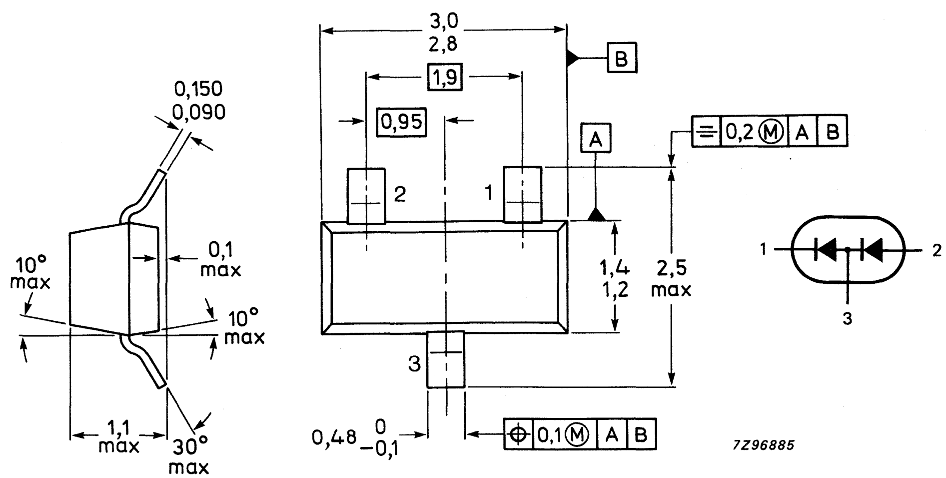
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	100	V
Forward current (DC)	I_F	max.	200	mA
Non-repetitive peak forward current	I_{FSM}	max.	500	mA
Total power dissipation at T_{amb} = 25 °C	P_{tot}	max.	300	mW
Junction temperature	T_j	max.	150	°C
Forward voltage at I_F = 100 mA	V_F	<	1.10	V
Reverse recovery time I_F = 10 mA to I_R = 10 mA measured at I_R = 1 mA	t_{rr}	<	15	ns

MECHANICAL DATA

Dimensions in mm

Marking code:
PMBD7000: 5C



TOP VIEW

Fig. 1 SOT-23.

See also soldering recommendations.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	100	V
Forward current (DC)	I_F	max.	200	mA
Non-repetitive peak forward current	I_{FSM}	max.	500	mA
Total power dissipated up to T_{amb} = 25 °C	P_{tot}	max.	300	mW
Storage temperature	T_{stg}		−65 to + 150	°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE*

From junction to ambient**	$R_{th\ j\text{-}a}$		430	K/W

CHARACTERISTICS (per diode)

T_{amb} = 25 °C unless otherwise specified

Forward voltage				
I_F = 1 mA	V_F	>	0.55	V
		<	0.70	V
I_F = 10 mA	V_F	>	0.67	V
		<	0.82	V
I_F = 100 mA	V_F	>	0.75	V
		<	1.10	V
Reverse breakdown voltage				
I_R = 100 µA	$V_{(br)r}$	>	100	V
Reverse current				
V_R = 50 V	I_R	<	300	nA
V_R = 100 V	I_R	<	500	nA
V_R = 50 V; T_{amb} = 125 °C	I_R	<	100	µA
Diode capacitance				
V_R = 0 V; f = 1 MHz	C_d	<	1.5	pF
Reverse recovery time switched from I_F = 10 mA to I_R = 10 mA; measured at I_R = 1 mA (see Fig. 2)	t_{rr}	<	15	ns

* See Thermal Resistance.

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm.

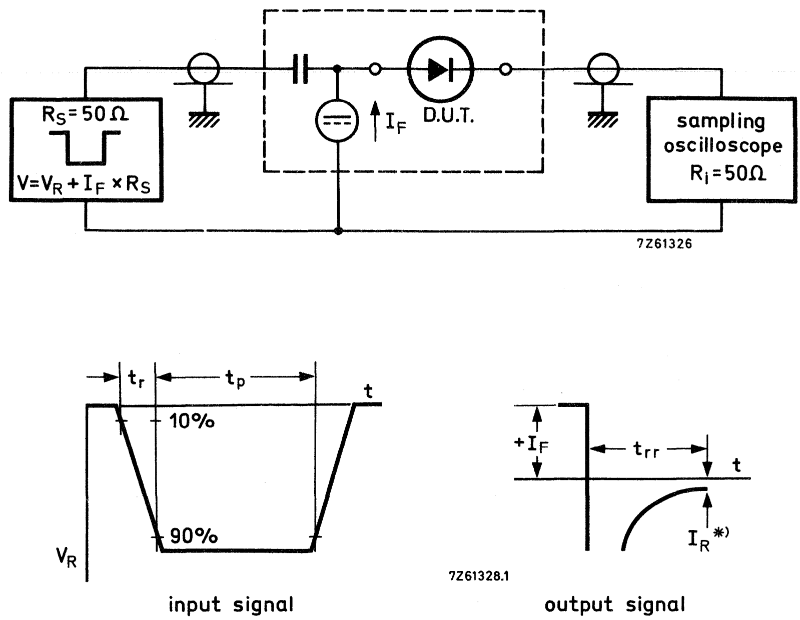


Fig. 2 Test circuit and waveforms; reverse recovery time.

SILICON PLANAR VOLTAGE REGULATIOR DIODES

Low power general purpose voltage regulator diodes in a microminiature plastic envelope intended for application in thick and thin film circuits. The series covers the range of nominal working voltages from 3.3 to 33 V with a working voltage tolerance of ± 5%.

QUICK REFERENCE DATA

Working voltage range	V_Z	nom.	3.3 to 33	V
Working voltage tolerance			± 5	%
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300	mW
Junction temperature	T_j	max.	150	°C

MECHANICAL DATA

Dimensions in mm

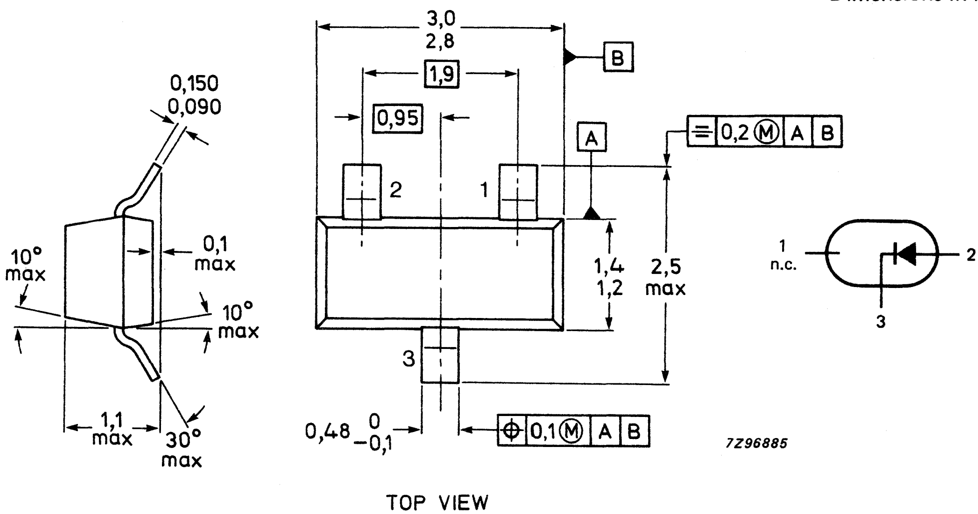


Fig. 1 SOT-23.

See also *Soldering recommendations*

Marking code

PMBZ 5226B = 8A
PMBZ 5227B = 8B
PMBZ 5228B = 8C
PMBZ 5229B = 8D
PMBZ 5230B = 8E
PMBZ 5231B = 8F
PMBZ 5232B = 8G
PMBZ 5233B = 8H
PMBZ 5234B = 8J
PMBZ 5235B = 8K
PMBZ 5236B = 8L
PMBZ 5237B = 8M
PMBZ 5238B = 8N
PMBZ 5239B = 8P
PMBZ 5240B = 8Q
PMBZ 5241B = 8R
PMBZ 5242B = 8S
PMBZ 5243B = 8T
PMBZ 5244B = 8U
PMBZ 5245B = 8V
PMBZ 5246B = 8W
PMBZ 5247B = 8X
PMBZ 5248B = 8Y
PMBZ 5249B = 8Z
PMBZ 5250B = 81A
PMBZ 5251B = 81B
PMBZ 5252B = 81C
PMBZ 5253B = 81D
PMBZ 5254B = 81E
PMBZ 5255B = 81F
PMBZ 5256B = 81G
PMBZ 5257B = 81H

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Repetitive peak forward current	I_{FRM}	max.	250 mA
Repetitive peak working current	I_{ZRM}	max.	250 mA
Total power dissipation up to T_{amb} = 25 °C**	P_{tot}	max.	300 mW
Storage temperature	T_{stg}		−65 to + 150 °C
Junction temperature	T_j	max.	150 °C

THERMAL CHARACTERISTICS*

Thermal resistance
from junction to ambient $R_{th\ j\text{-}a}$ = 420 K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise stated

Forward voltage
I_F = 200 mA V_F max. 1.1 V

type number	working voltage V_Z (V) at I_{ztest} (note 1) nom.	test current I_{Ztest} (mA)	max. Zener impedance Z_{ZT} (Ω) at I_{Ztest} (note 2)	differential resistance r_{diff} (Ω) at I_{ZK} = 0.25 mA (note 2) max.	reverse current I_R (μA) at V_R max.	test voltage V_R (V)	temp. coeff. S_Z (%/K) (note 3) typ.
PMBZ 5226B	3.3	20	28	1600	25	1.0	−0.064
PMBZ 5227B	3.6	20	26	1700	15	1.0	−0.065
PMBZ 5228B	3.9	20	25	1900	10	1.0	−0.063
PMBZ 5229B	4.3	20	22	2000	5	1.0	−0.058
PMBZ 5230B	4.7	20	19	2000	5	1.0	−0.047
PMBZ 5231B	5.1	20	17	2000	5	2.0	−0.013
PMBZ 5232B	5.6	20	11	1600	5	3.0	+0.023
→ PMBZ 5233B	6.0	20	7	1600	5	3.5	+0.023
PMBZ 5234B	6.2	20	7	1000	5	4.0	+0.039
PMBZ 5235B	6.8	20	5	750	3	5.0	+0.040
PMBZ 5236B	7.5	20	6	500	3	6.0	+0.047
PMBZ 5237B	8.2	20	8	500	3	6.5	+0.052
PMBZ 5238B	8.7	20	8	600	3	6.5	+0.053
PMBZ 5239B	9.1	20	10	600	3	7.0	+0.055
PMBZ 5240B	10	20	17	600	3	8.0	+0.055
PMBZ 5241B	11	20	22	600	2	8.4	+0.058
PMBZ 5242B	12	20	30	600	1	9.1	+0.062
PMBZ 5243B	13	9.5	13	600	0.5	9.9	+0.065
PMBZ 5244B	14	9.0	15	600	0.1	10	+0.067

* See *Thermal characteristics.*
** Device mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm.

type number	working voltage V_Z (V) at I_{ztest} (note 1) nom.	test current I_{Ztest} (mA)	max. Zener impedance Z_{ZT} (Ω) at I_{Ztest} (note 2)	differential resistance r_{diff} (Ω) at I_{ZK} = 0.25 mA (note 2) max.	reverse current I_R (μA) at V_R max.	test voltage V_R (V)	temp. coeff. S_Z (%/K) (note 3) (typ.
PMBZ 5245B	15	8.5	16	600	0.1	11	+0.073
PMBZ 5246B	16	7.8	17	600	0.1	12	+0.073
PMBZ 5247B	17	7.4	19	600	0.1	13	+0.073
PMBZ 5248B	18	7.0	21	600	0.1	14	+0.078
PMBZ 5249B	19	6.6	23	600	0.1	14	+0.078 ←
PMBZ 5250B	20	6.2	25	600	0.1	15	+0.080
PMBZ 5251B	22	5.6	29	600	0.1	17	+0.080
PMBZ 5252B	24	5.2	33	600	0.1	18	+0.081
PMBZ 5253B	25	5.0	35	600	0.1	19	+0.082
PMBZ 5254B	27	4.6	41	600	0.1	21	+0.085
PMBZ 5255B	28	4.5	44	600	0.1	21	+0.085
PMBZ 5256B	30	4.2	49	600	0.1	23	+0.085
PMBZ 5257B	33	3.8	58	700	0.1	25	+0.085

DEVELOPMENT DATA

Notes

1. V_Z is measured with device at thermal equilibrium while mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm.
2. $I_{(ac\ rms)}$ = 10% of I_{Ztest} resp. I_{ZK}; 1 kHz superimposed; thermal equilibrium see note 1.
3. For types PMBZ 5226B to PMBZ 5242B the current I_Z = 7.5 mA; for PMBZ 5243B and higher $I_Z = I_{Ztest}$. Testpoints at T_1 = 25 °C, T_2 = 125 °C. ←

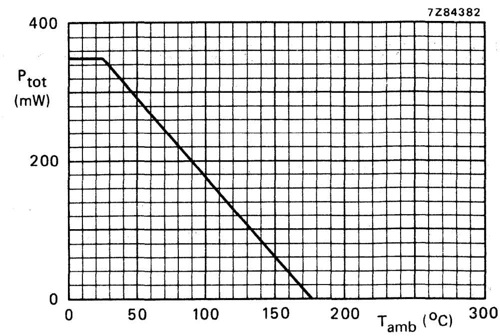


Fig. 2 Power derating curve.

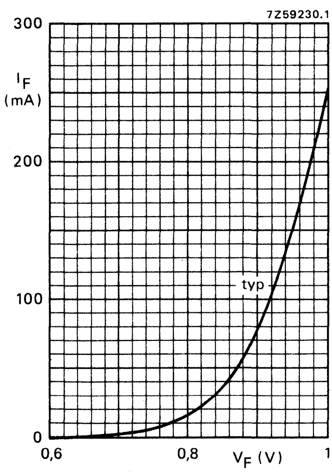


Fig. 3 Typical values at T_j = 25 °C.
Forward current as a function of forward voltage.

HIGH-SPEED SILICON DIODES FOR SURFACE MOUNTING

These diodes are primarily designed for fast logic applications.

These SM diodes are leadless diodes in a hermetically sealed SOD-80 envelope with tin-plated metal discs at each end. They are suitable for "automatic placement" and as such it can withstand immersion soldering.

The diodes can be delivered in "super 8" tape.

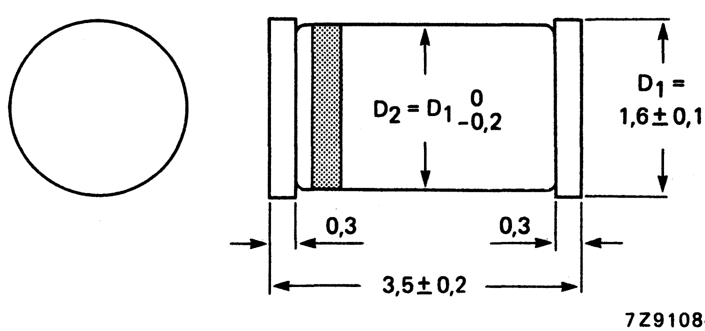
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	75	V
Repetitive peak reverse voltage	V_{RRM}	max.	75	V
Repetitive peak forward current	I_{FRM}	max.	450	mA
Forward voltage PMLL4148: I_F = 10 mA PMLL4446: I_F = 20 mA PMLL4448: I_F = 100 mA	V_F	<	1	V
Reverse recovery time when switched from I_F = 10 mA to I_R = 60 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	4	ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



Cathode indicated by black band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	75	V
Repetitive peak reverse voltage	V_{RRM}	max.	75	V
Average rectified forward current	$I_{F(AV)}$	max.	150	mA
Forward current (d.c.)	I_F	max.	200	mA
Repetitive peak forward current	I_{FRM}	max.	450	mA
Non-repetitive peak forward current				
t = 1 μs	I_{FSM}	max.	2000	mA
t = 1 s	I_{FSM}	max.	500	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	500	mW
Derating factor			2,85	mW/K
Storage temperature	T_{stg}		−65 to + 200	°C
Junction temperature	T_j	max.	200	°C

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltages					
PMLL4148: I_F = 10 mA; PMLL4446: I_F = 20 mA; PMLL4448: I_F = 100 mA		V_F	<	1	V
PMLL4448: I_F = 5 mA		V_F		0,62 to 0,72	V
Reverse avalanche breakdown voltage					
I_R = 100 μA		$V_{(BR)R}$	>	100	V
I_R = 5 μA		$V_{(BR)R}$	>	75	V
Reverse currents					
V_R = 20 V		I_R	<	25	nA
V_R = 20 V; T_j = 100 °C	PMLL4448	I_R	<	3	μA
V_R = 20 V; T_j = 150 °C		I_R	<	50	μA
Diode capacitance					
V_R = 0; f = 1 MHz		C_d	<	4	pF
Forward recovery voltage when switched to I_F = 50 mA; t_r = 20 ns		V_{fr}	<	2,5	V

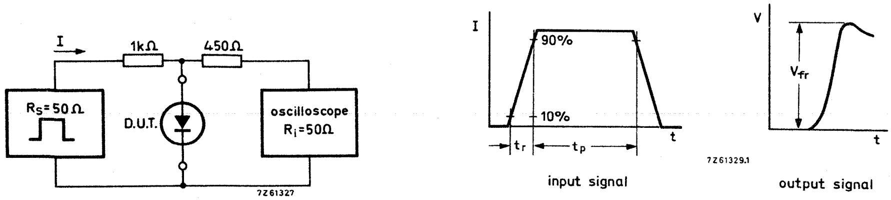


Fig. 2 Forward recovery voltage test circuit and waveforms.

Input signal: Rise time of the forward pulse t_r = 20 ns
Forward current pulse duration t_p = 120 ns
Duty factor δ = 0,01

Oscilloscope: Rise time t_r = 0,35 ns

Circuit capacitance C ⩽ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

Reverse recovery time when switched from
I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω;
measured at I_R = 1 mA t_{rr} < 4 ns

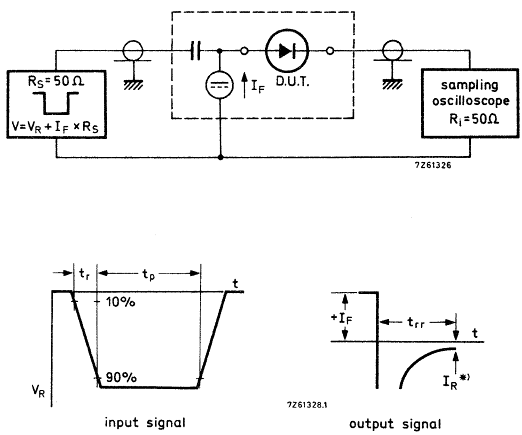


Fig. 3 Reverse recovery time test circuit and waveforms.

Input signal: Rise time of the reverse pulse t_r = 0,6 ns * I_R = 1 mA
Reverse pulse duration t_p = 100 ns
Duty factor δ = 0,05

Oscilloscope: Rise time t_r = 0,35 ns

Circuit capacitance C ⩽ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

ULTRA-HIGH-SPEED SILICON DIODES FOR SURFACE MOUNTING

Whiskerless diodes in SOD-80 envelopes.
The PMLL4150 is primarily intended for general purpose use in computer and industrial applications.
The PMLL4151 and PMLL4153 are intended for military and industrial applications.

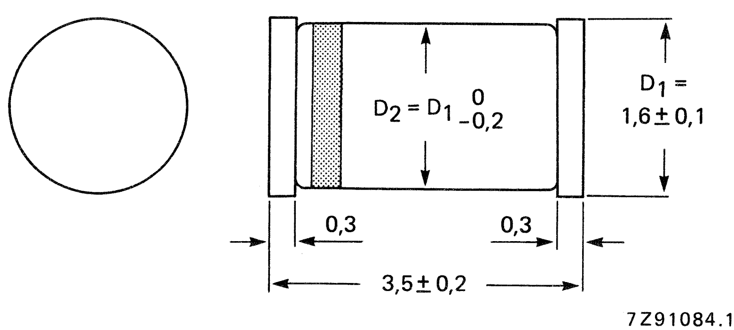
QUICK REFERENCE DATA

			PMLL4150	4151	4153	
Continuous reverse voltage	V_R	max.	50	50	50	V
Repetitive peak reverse voltage	V_{RRM}	max.	–	75	75	V
Repetitive peak forward current	I_{FRM}	max.	0,60	0,45	0,45	A
Non-repetitive peak forward current						
t = 1 μs	I_{FSM}	max.	4,0	–	–	A
t = 1 s	I_{FSM}	max.	0,5	–	–	A
Forward voltage						
I_F = 20 mA	V_F	<	–	–	0,88	V
I_F = 50 mA	V_F	<	–	1	–	V
I_F = 200 mA	V_F	<	1	–	–	V
Reverse recovery time when switched from						
I_F = 400 mA to I_R = 400 mA; R_L = 100 Ω; measured at I_R = 40 mA	t_{rr}	<	6	–	–	ns
I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	–	4	4	ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



Cathode indicated by black band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

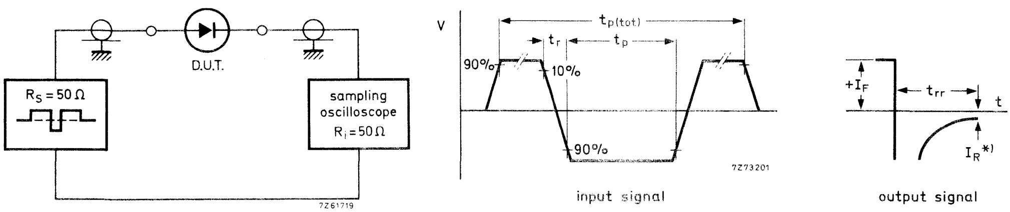
			PMLL4150	4151	4153	
Continuous reverse voltage	V_R	max.	50	50	50	V
Repetitive peak reverse voltage	V_{RRM}	max.	–	75	75	V
Forward current (d.c.)	I_F	max.	0,30	0,20	0,20	A
Repetitive peak forward current	I_{FRM}	max.	0,60	0,45	0,45	A
Non-repetitive peak forward current						
t = 1 μs	I_{FSM}	max.	4,0	–	–	A
t = 1 s	I_{FSM}	max.	0,5	–	–	A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.		500		mW
Derating factor				2,85		mW/K
Storage temperature	T_{stg}			−65 to + 200		°C
Junction temperature	T_j	max.		200		°C

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			PMLL4150	4151	4153	
Forward voltage						
I_F = 0,1 mA	V_F	>	–	–	0,49	V
		<	–	–	0,55	V
I_F = 0,25 mA	V_F	>	–	–	0,53	V
		<	–	–	0,59	V
I_F = 1 mA	V_F	>	0,54	–	0,59	V
		<	0,62	–	0,67	V
I_F = 2 mA	V_F	>	–	–	0,62	V
		<	–	–	0,70	V
I_F = 10 mA	V_F	>	0,66	–	0,70	V
		<	0,74	–	0,81	V
I_F = 20 mA	V_F	>	–	–	0,74	V
		<	–	–	0,88	V
I_F = 50 mA	V_F	>	0,76	–	–	V
		<	0,86	1	–	V
I_F = 100 mA	V_F	>	0,82	–	–	V
		<	0,92	–	–	V
I_F = 200 mA	V_F	>	0,87	–	–	V
		<	1,00	–	–	V
Reverse avalanche breakdown voltage						
I_R = 5 μA	$V_{(BR)R}$	>	–	75	75	V
Reverse current						
V_R = 50 V	I_R	<	0,1	0,05	0,05	μA
V_R = 50 V; T_{amb} = 150 °C	I_R	<	100	50	50	μA

			PMLL4150	4151	4153	
Diode capacitance $V_R = 0$; f = 1 MHz	C_d	<	2,5	2	2	pF
Reverse recovery time when switched from I_F = 10 to 200 mA to I_R = 10 to 200 mA; R_L = 100 Ω; measured at $I_R = 0{,}1 \times I_F$	t_{rr}	<	4	–	–	ns
I_F = 200 to 400 mA to I_R = 200 to 400 mA; R_L = 100 Ω; measured at $I_R = 0{,}1 \times I_F$	t_{rr}	<	6	–	–	ns
I_F = 10 mA to I_R = 1 mA; R_L = 100 Ω; measured at I_R = 0,1 mA	t_{rr}	<	6	–	–	ns
I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	–	4	4	ns
I_F = 10 mA to I_R = 60 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	–	2	2	ns



*) value at which t_{rr} is measured

Fig. 2 Test circuit and waveforms.

Input signal:	Total pulse duration	$t_{p(tot)}$	=	0,2 μs
	Duty factor	δ	=	0,0025
	Rise time of the reverse pulse	t_r	=	0,6 ns
	Reverse pulse duration	t_p	=	30 ns
Oscilloscope:	Rise time	t_r	=	0,35 ns

Circuit capacitance $C \leqslant 1$ pF (C = oscilloscope input capacitance + parasitic capacitance)

Forward recovery time when switched from
$I = 0$ to I_F = 200 mA; t_r = 0,4 ns; t_p = 100 ns; $\delta < 0{,}01$;
measured at V_f = 1 V — t_{fr} < 10 ns

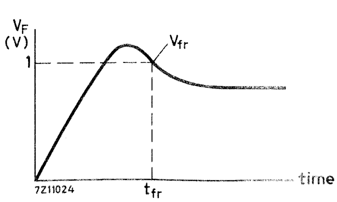


Fig. 3 PMLL4150.

VOLTAGE REGULATOR DIODES FOR SURFACE MOUNTING

Silicon planar diodes in a SOD-80 envelope intended for use as low-power voltage stabilizers or voltage references.

The series consists of 43 types with nominal working voltages in the range 3,0 V to 75 V with a tolerance of ± 5%. The SM diode is a leadless diode in a hermetically sealed glass SOD-80 envelope with tin plated metal discs at each end. It is suitable for "automatic placement" and as such can withstand immersion soldering.

The diodes are delivered on "super 8" tape.

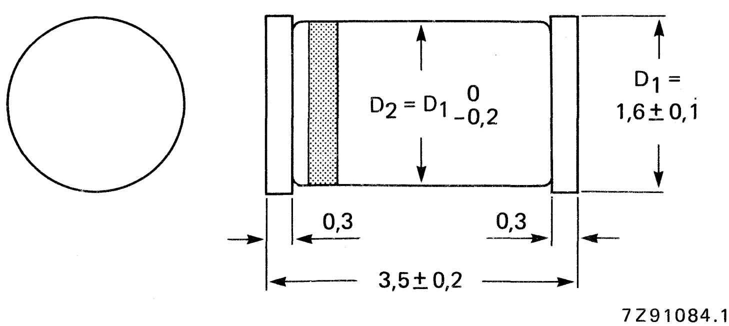
QUICK REFERENCE DATA

Working voltage range	V_Z	nom.	3,0 to 75	V
Working voltage tolerance			± 5	%
Total power dissipation	P_{tot}	max.	500	mW
Non-repetitive peak reverse power dissipation T_j = 55 °C; t_p = 8,3 ms, square wave	P_{ZSM}	max.	10	W
Junction temperature	T_j		−65 to + 200	°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



Cathode indicated by yellow band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	250 mA
Repetitive peak forward current	I_{FRM}	max.	250 mA
Total power dissipation if flanges are kept at T_{flange} = 75 °C	P_{tot}	max.	500 mW
Derating factor			4 mW/K
Non-repetitive peak reverse power dissipation T_j = 55 °C; t_p = 8,3 ms, square wave	P_{ZSM}	max.	10 W
Storage temperature	T_{stg}		−65 to + 200 °C
Junction temperature	T_j		−65 to + 200 °C

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise stated

Forward voltage I_F = 200 mA	V_F	max.	1,1 V

type number	working voltage V_Z (V) at I_{ztest} (note 1) nom.	test current I_{Ztest} (mA)	max. Zener impedance Z_{ZT} (Ω) at I_{Ztest} (note 2)	differential resistance r_{diff} (Ω) at I_{ZK} = 0,25 mA (note 2) max.	reverse current I_R (μA) at V_R max.	test voltage V_R (V)	temp. coeff. S_Z (%/K) (note 3) max.
PMLL5225B	3,0	20	29	1600	50	1,0	−0,075
PMLL5226B	3,3	20	28	1600	25	1,0	−0,070
PMLL5227B	3,6	20	24	1700	15	1,0	−0,065
PMLL5228B	3,9	20	23	1900	10	1,0	−0,060
PMLL5229B	4,3	20	22	2000	5	1,0	± 0,055
PMLL5230B	4,7	20	19	1900	5	2,0	± 0,030
PMLL5231B	5,1	20	17	1600	5	2,0	± 0,030
PMLL5232B	5,6	20	11	1600	5	3,0	+ 0,038
PMLL5233B	6,0	20	7	1600	5	3,5	+ 0,038
PMLL5234B	6,2	20	7	1000	5	4,0	+ 0,045
PMLL5235B	6,8	20	5	750	3	5,0	+ 0,050
PMLL5236B	7,5	20	6	500	3	6,0	+ 0,058
PMLL5237B	8,2	20	8	500	3	6,5	+ 0,062
PMLL5238B	8,7	20	8	600	3	6,5	+ 0,065
PMLL5239B	9,1	20	10	600	3	7,0	+ 0,068

type number	working voltage V_Z (V) at I_{Ztest} (note 1) nom.	test current I_{Ztest} (mA)	max. Zener impedance Z_{ZT} (Ω) at I_{Ztest} (note 2)	differential resistance r_{diff} (Ω) at I_{ZK} = 0,25 mA (note 2) max.	reverse current I_R (μA) at V_R max.	test voltage V_R (V)	temp. coeff. S_Z (%/K) (note 3) max.
PMLL5240B	10	20	17	600	3	8,0	+ 0,075
PMLL5241B	11	20	22	600	2	8,4	+ 0,076
PMLL5242B	12	20	30	600	1	9,1	+ 0,077
PMLL5243B	13	9,5	13	600	0,5	9,9	+ 0,079
PMLL5244B	14	9,0	15	600	0,1	10	+ 0,082
PMLL5245B	15	8,5	16	600	0,1	11	+ 0,082
PMLL5246B	16	7,8	17	600	0,1	12	+ 0,083
PMLL5247B	17	7,4	19	600	0,1	13	+ 0,084
PMLL5248B	18	7,0	21	600	0,1	14	+ 0,085
PMLL5249B	19	6,6	23	600	0,1	14	+ 0,086
PMLL5250B	20	6,2	25	600	0,1	15	+ 0,086
PMLL5251B	22	5,6	29	600	0,1	17	+ 0,087
PMLL5252B	24	5,2	33	600	0,1	18	+ 0,088
PMLL5253B	25	5,0	35	600	0,1	19	+ 0,089
PMLL5254B	27	4,6	41	600	0,1	21	+ 0,090
PMLL5255B	28	4,5	44	600	0,1	21	+ 0,091
PMLL5256B	30	4,2	49	600	0,1	23	+ 0,091
PMLL5257B	33	3,8	58	700	0,1	25	+ 0,092
PMLL5258B	36	3,4	70	700	0,1	27	+ 0,093
PMLL5259B	39	3,2	80	800	0,1	30	+ 0,094
PMLL5260B	43	3,0	93	900	0,1	33	+ 0,095
PMLL5261B	47	2,7	105	1000	0,1	36	+ 0,095
PMLL5262B	51	2,5	125	1100	0,1	39	+ 0,096
PMLL5263B	56	2,2	150	1300	0,1	43	+ 0,096
PMLL5264B	60	2,1	170	1400	0,1	46	+ 0,097
PMLL5265B	62	2,0	185	1400	0,1	47	+ 0,097
PMLL5266B	68	1,8	230	1600	0,1	52	+ 0,097
PMLL5267B	75	1,7	270	1700	0,1	56	+ 0,098

Notes to the characteristics

1. V_Z is measured with device at thermal equilibrium while held in clips in still air at 25 °C.
2. $I_{(ac\ rms)}$ = 10% of I_{Ztest} resp. I_{ZK}, 60 Hz superimposed.
3. For types PMLL5225B to PMLL5242B the current I_Z = 7,5 mA; for PMLL5243B and higher $I_Z = I_{Ztest}$. Testpoints at T_1 = 25 °C, T_2 = 125 °C.

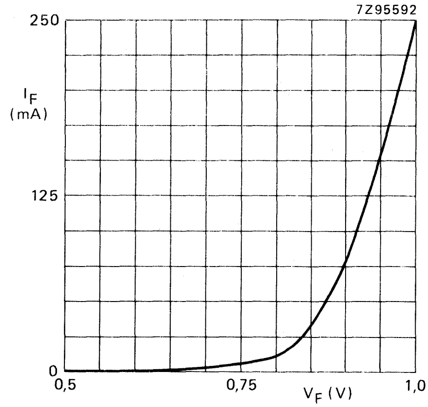


Fig. 2 T_{amb} = 25 °C; typical values.

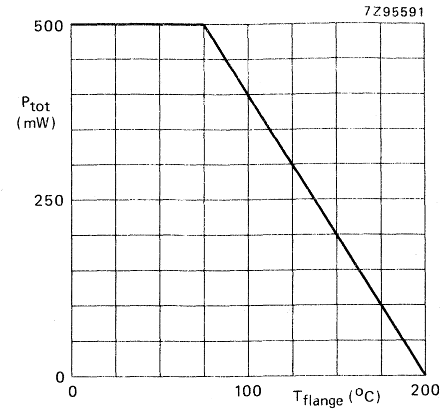


Fig. 3 Total power dissipation versus flange temperature.

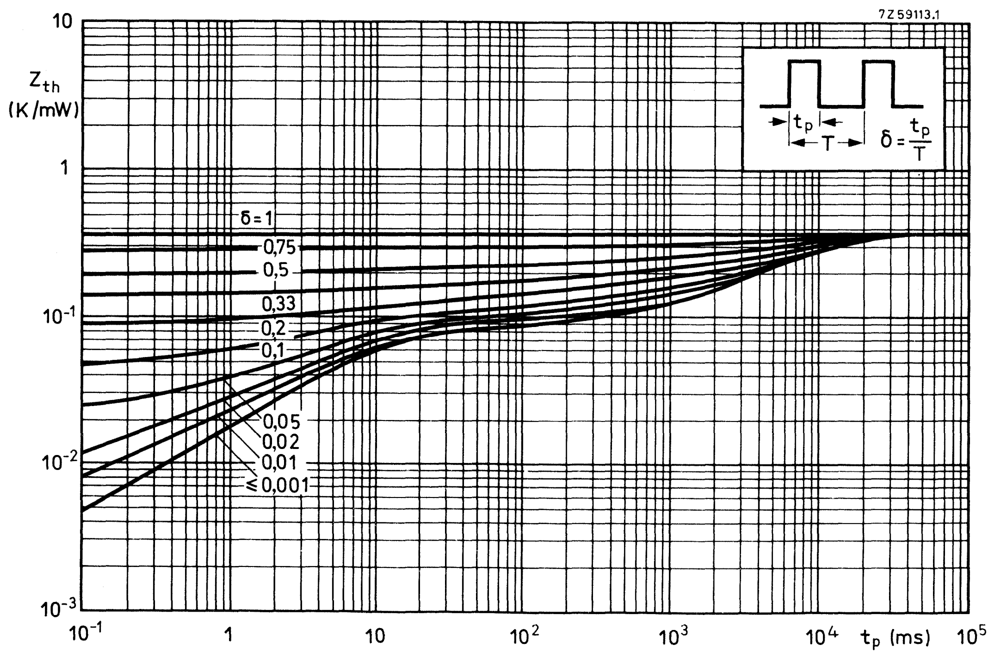


Fig. 4 Thermal impedance versus pulse duration.

VOLTAGE REFERENCE DIODES

Voltage reference diodes in a DO-34 envelope. They have a very low temperature coefficient and are primarily intended for use as voltage reference sources in measuring instruments such as digital voltmeters.

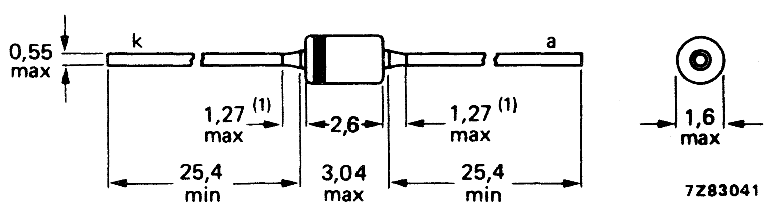
QUICK REFERENCE DATA

			min.	nom.	max.	
Reference voltage at I_Z = 7,5 mA		V_{ref}	5,89	6,20	6,51	V
Effective temperature coefficient at I_Z = 7,5 mA* (see notes 1 and 2 and the relevant graphs)	1N821; A	$\|S_Z\|$	<		0,01	%/K
	1N823; A	$\|S_Z\|$	<		0,005	%/K
	1N825; A	$\|S_Z\|$	<		0,002	%/K
	1N827; A	$\|S_Z\|$	<		0,001	%/K
	1N829; A	$\|S_Z\|$	<		0,0005	%/K
Operating ambient temperature		T_{amb}		−55 to + 100		°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 DO-34 (SOD-68).



(1) Lead diameter in this zone uncontrolled.

Cathode indicated by coloured band

* For accuracy of I_Z see Figs 3 to 5.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Working current (d.c.)	I_Z	max.	50	mA
Working current (peak value)	I_{ZM}	max.	50	mA
Total power dissipation up to T_{amb} = 50 °C	P_{tot}	max.	400	mW
Storage temperature	T_{stg}		−65 to + 200	°C
Operating ambient temperature	T_{amb}		−55 to + 100	°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0,375	K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			min.	nom.	max.	
Reference voltage at I_Z = 7,5 mA		V_{ref}	5,89	6,20	6,51	V

Reference voltage excursion at I_Z = 7,5 mA* ambient temperature test points: −55; + 25; + 75; + 100 °C (see notes 1 and 2 and the relevant graphs)	1N821; A	$\|\Delta V_{ref}\|$	<	96	mV
	1N823; A	$\|\Delta V_{ref}\|$	<	48	mV
	1N825; A	$\|\Delta V_{ref}\|$	<	19	mV
	1N827; A	$\|\Delta V_{ref}\|$	<	9	mV
	1N829; A	$\|\Delta V_{ref}\|$	<	5	mV
Effective temperature coefficient at I_Z = 7,5 mA* (see notes 1 and 2 and the relevant graphs)	1N821; A	$\|S_Z\|$	<	0,01	%/K
	1N823; A	$\|S_Z\|$	<	0,005	%/K
	1N825; A	$\|S_Z\|$	<	0,002	%/K
	1N827; A	$\|S_Z\|$	<	0,001	%/K
	1N829; A	$\|S_Z\|$	<	0,0005	%/K
Differential resistance at I_Z = 7,5 mA					
1N821 to 1N829		r_{diff}	<	15	Ω
1N821A to 1N829A		r_{diff}	<	10	Ω

* For accuracy of I_Z see Figs 3 to 5.

Notes

1. I_Z tolerance and stability of I_Z.

   The quoted values of ΔV_{ref} are based on a constant current I_Z. Two factors can cause V_{ref} to change, namely the differential resistance r_{diff} and the temperature coefficient S_Z.

   a. As the max. r_{diff} of the device can be 15 Ω, a change of 0,01 mA in the current through the reference diode will result in a ΔV_{ref} of 0,01 mA x 15 Ω = 0,15 mV. This level of ΔV_{ref} is not significant on a 1N821 ($\Delta V_{ref} < 96$ mV), it is however very significant on a 1N829 ($\Delta V_{ref} < 5$ mV).

   b. The temperature coefficient of the reference voltage S_Z is a function of I_Z. Reference diodes are classified at the specified test current and the S_Z of the reference diode will be different at different levels of I_Z. The absolute value of I_Z is important, however, the stability of I_Z, once the level has been set, is far more significant. This applies particularly to the 1N829.

   The effect of I_Z stability on S_Z is shown in Fig. 5.

2. Voltage excursion (ΔV_{ref} and temperature coefficient).

   All reference diodes are characterized by the 'box method'. This guarantees a maximum voltage excursion (ΔV_{ref}) over the specified temperature range, at the specified test current (I_Z), verified by tests at indicated temperature points within the range. V_Z is measured and recorded at each temperature specified. The ΔV_{ref} between the highest and lowest values must not exceed the maximum ΔV_{ref} given. The temperature coefficient, therefore is given only as a reference; but may be derived from:

$$S_Z = \frac{(V_{ref\,1} - V_{ref\,2}) \times 100}{(T_{amb\,2} - T_{amb\,1}) \times V_{ref\,nom}} \ \%/K$$

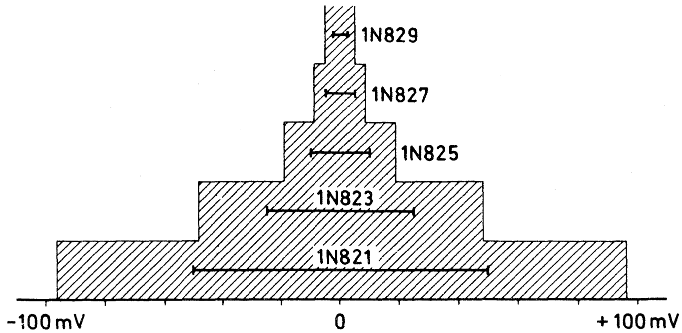


Fig. 2.

Maximum reference voltage variation (line section) caused by temperature variations within the range from −55 °C to + 100 °C at a constant working current of 7,5 mA. The voltage variations may shift horizontally within the shaded area. The zero point may vary from 5890 mV to 6510 mV and differs from diode to diode.

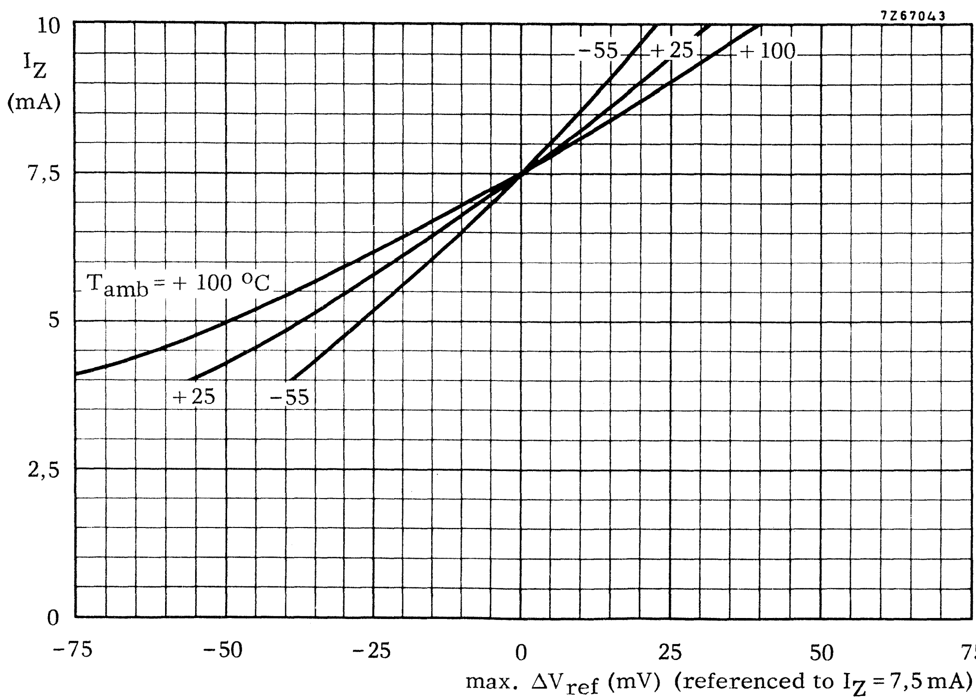


Fig. 3.

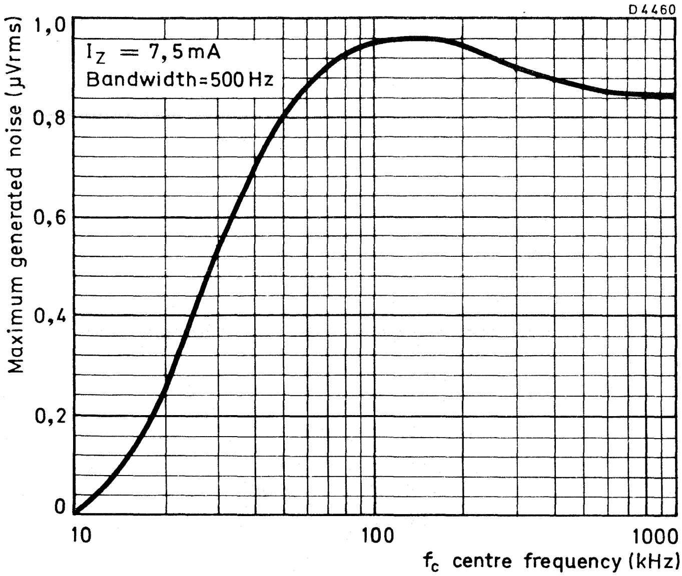

D4460
Maximum generated noise (μVrms)
1,0
0,8
0,6
0,4
0,2
0
I_Z = 7,5 mA
Bandwidth=500 Hz
10
100
1000
f_c centre frequency (kHz)

Fig. 4.

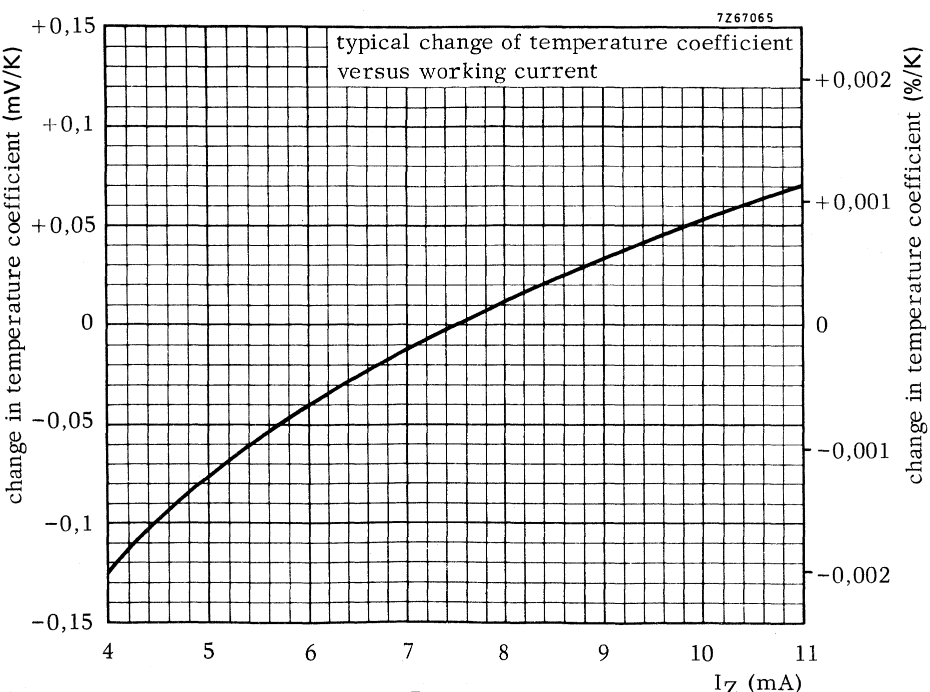

7Z67065
typical change of temperature coefficient
versus working current
change in temperature coefficient (mV/K)
+0,15
+0,1
+0,05
0
−0,05
−0,1
−0,15
change in temperature coefficient (%/K)
+0,002
+0,001
0
−0,001
−0,002
4
5
6
7
8
9
10
11
I_Z (mA)

Fig. 5.

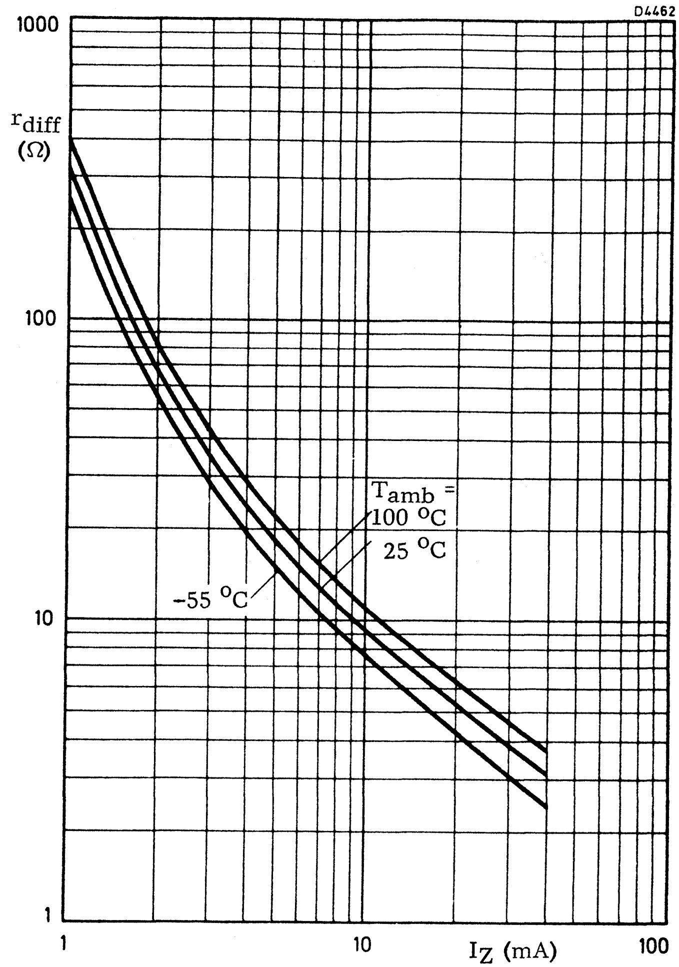


Fig. 6.

HIGH-SPEED SILICON DIODES

Planar epitaxial diodes intended for general purpose applications.

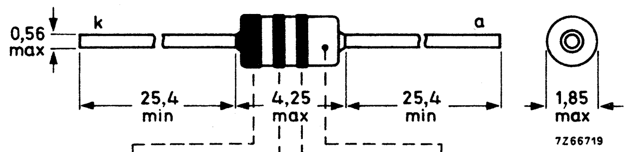
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	75	V
Repetitive peak reverse voltage	V_{RRM}	max.	100	V
Repetitive peak forward current	I_{FRM}	max.	225	mA
Forward voltage $I_F = 10$ mA	V_F	<	1	V
Reverse recovery time when switched from $I_F = 10$ mA to $I_R = 60$ mA; $R_L = 100\ \Omega$; measured at $I_R = 1$ mA	t_{rr}	<	4	ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-27 (DO-35).



1N914:	**white**	**brown**	**yellow**	**natural**
1N916:	**white** **(cathode)**	**brown**	**blue**	**natural**

Products approved to CECC 50 001-21 available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	75 V
Repetitive peak reverse voltage	V_{RRM}	max.	100 V
Average rectified forward current (averaged over any 20 ms period)			
T_{amb} = 25 °C	$I_{F(AV)}$	max.	75 mA
T_{amb} = 150 °C	$I_{F(AV)}$	max.	10 mA
Forward current (d.c.)	I_F	max.	75 mA
Repetitive peak forward current	I_{FRM}	max.	225 mA
Non-repetitive peak forward current (t = 1 s)	I_{FSM}	max.	500 mA
Total power dissipation	P_{tot}	max.	250 mW
Storage temperature	T_{stg}	−65 to + 200	°C
Operating ambient temperature	T_{amb}	−65 to + 175	°C

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltages			
I_F = 10 mA	V_F	<	1 V
Reverse avalanche breakdown voltage			
I_R = 100 μA	$V_{(BR)R}$	>	100 V
Reverse currents			
V_R = 20 V	I_R	<	25 nA
V_R = 75 V	I_R	<	5 μA
V_R = 20 V; T_j = 150 °C	I_R	<	50 μA
Diode capacitance			
V_R = 0; f = 1 MHz			
1N914	C_d	<	4 pF
1N916	C_d	<	2 pF
Forward recovery voltage			
when switched to I_F = 50 mA; t_r = 20 ns	V_{fr}	<	2,5 V

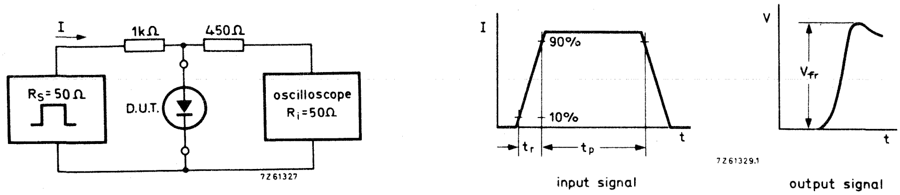
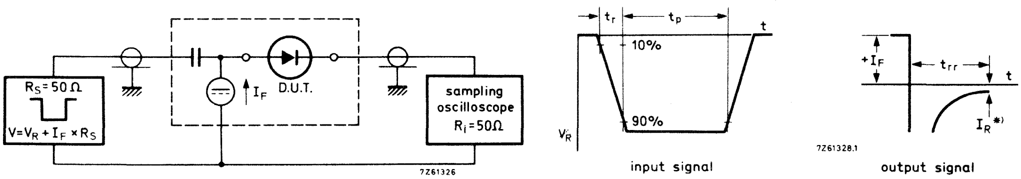


Fig. 2 Test circuit and waveforms forward recovery voltage. Input signal: Rise time of the forward pulse, t_r = 20 ns; forward current pulse duration, t_p = 120 ns; duty factor, d = 0,01. Oscilloscope rise time, t_r = 0,35 ns. Circuit capacitance < 1 pF (oscilloscope input capacitance and parasitic capacitance).

Reverse recovery time when switched from		1N914	1N916	
I_F = 10 mA to I_R = 10 mA, R_L = 100 Ω, measured at I_R = 1 mA	t_{rr}	8	—	ns
I_F = 10 mA to I_R = 60 mA, R_L = 100 Ω, measured at I_R = 1 mA	t_{rr}	4	4	ns



* I_R = 1 mA

Fig. 3 Test circuit and waveform reverse recovery time. Input signal: Rise time of the reverse pulse, t_r = 0,6 ns; reverse pulse duration, t_p = 100 ns; duty factor, d = 0,05. Oscilloscope rise time, t_r = 0,35 ns. Circuit capacitance < 1 pF (oscilloscope input capacitance + parasitic capacitance).

Rectifying efficiency		
f = 100 MHz; $V_{i(rms)}$ = 2 V	η	> 45 %

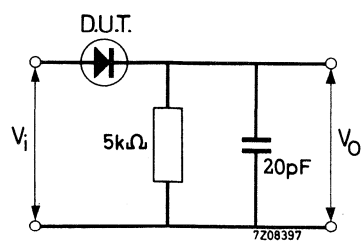


Fig. 4 Test circuit. $\eta = \dfrac{V_O}{V_{i(rms)}\sqrt{2}}$

SILICON DIFFUSED RECTIFIER DIODES

This data sheet contains a range of silicon rectifier diodes for general purpose use.

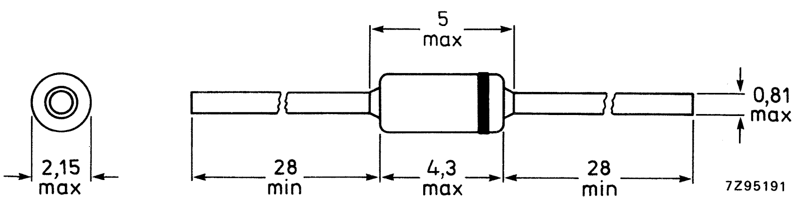
QUICK REFERENCE DATA

			1N4001ID	4002ID	4003ID	4004ID	4005ID	4006ID	4007ID	
Repetitive peak reverse voltage	V_{RRM}	max.	50	100	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	50	100	200	400	600	800	1000	V

Average forward current	$I_{F(AV)}$	max.	1,0	A
Repetitive peak forward current	I_{FRM}	max.	10	A
Non-repetitive peak forward current	I_{FSM}	max.	20	A

MECHANICAL DATA

Dimensions in mm



The marking band indicates cathode.

Fig. 1 SOD-81.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			1N4001ID	4002ID	4003ID	4004ID	4005ID	4006ID	4007ID
Repetitive peak reverse voltage	V_{RRM}	max.	50	100	200	400	600	800	1000 V
Continuous reverse voltage	V_R	max.	50	100	200	400	600	800	1000 V

Average forward current (averaged over any 20 ms period) up to T_{amb} = 75 °C	$I_{F(AV)}$	max.	1,0	A
at T_{amb} = 100 °C	$I_{F(AV)}$	max.	0,75	A
Repetitive peak forward current	I_{FRM}	max.	10	A
Non-repetitive peak forward current (half-cycle sinewave, 60 Hz)	I_{FSM}	max.	20	A
Storage temperature	T_{stg}		−65 to +175	°C
Junction temperature	T_j	max.	175	°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\ j\text{-}tp}$	=	60	K/W
2. Thermal resistance from junction to ambient; device mounted on an 1,5 mm thick epoxy-glass printed circuit board; Cu-thickness ⩾ 40 μm	$R_{th\ j\text{-}a}$	=	120	K/W

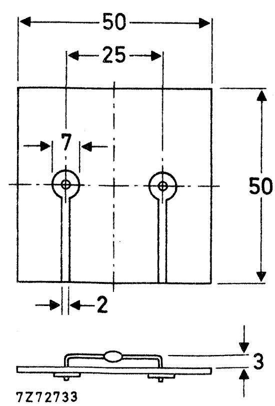


Fig. 2 Device mounted on a printed circuit board.

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise stated

Forward voltage				
I_F = 1 A	V_F	<	1,1	V
Full-cycle average forward voltage				
$I_{F(AV)}$ = 1 A	$V_{F(AV)}$	<	0,8	V
Reverse current				
$V_R = V_{Rmax}$	I_R	<	10	μA
$V_R = V_{Rmax}$; T_{amb} = 100 °C	I_R	<	50	μA
Full-cycle average reverse current				
$V_R = V_{RRMmax}$; T_{amb} = 75 °C	$I_{R(AV)}$	<	30	μA

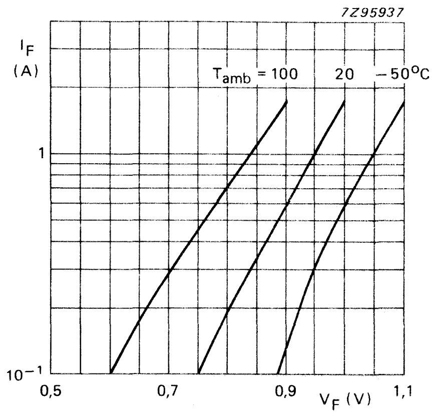


Fig. 3 Typical forward current as a function of forward voltage.

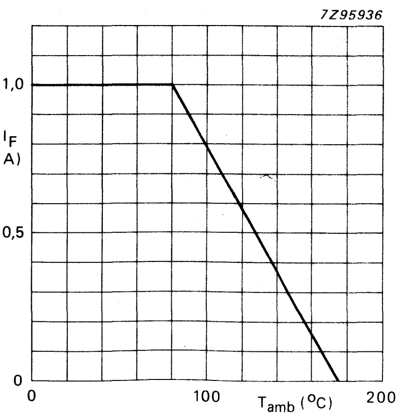


Fig. 4 Maximum forward current as a function of temperature.

SILICON DIFFUSED RECTIFIER DIODES

A range of silicon rectifier diodes for general purpose use.

QUICK REFERENCE DATA

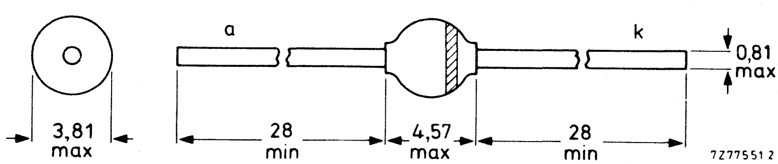
			1N4001G	4002G	4003G	4004G	4005G	4006G	4007G	
Repetitive peak reverse voltage	V_{RRM}	max.	50	100	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	50	100	200	400	600	800	1000	V

Average forward current	$I_{F(AV)}$	max.	1	A
Repetitive peak forward current	I_{FRM}	max.	10	A
Non-repetitive peak forward current	I_{FSM}	max.	30	A

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-57.



The marking band indicates cathode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			1N4001G	4002G	4003G	4004G	4005G	4006G	4007G
Repetitive peak reverse voltage	V_{RRM}	max.	50	100	200	400	600	800	1000 V
Continuous reverse voltage	V_R	max.	50	100	200	400	600	800	1000 V

Average forward current (averaged over any 20 ms period)				
up to T_{amb} = 75 °C	$I_{F(AV)}$	max.	1	A
at T_{amb} = 100 °C	$I_{F(AV)}$	max.	0,75	A
Forward current (d.c.) up to T_{amb} = 75 °C	I_F	max.	1	A
Repetitive peak forward current	I_{FRM}	max.	10	A
Non-repetitive peak forward current (half-cycle sinewave, 60 Hz)	I_{FSM}	max.	30	A
Storage temperature	T_{stg}		−65 to +175	°C
Junction temperature	T_j	max.	175	°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\ j\text{-}tp}$	=	46	K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ≥ 40 μm; (see "Thermal model")	$R_{th\ j\text{-}a}$	=	100	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise stated

Forward voltage I_F = 1 A	V_F	<	1,1	V
Full-cycle average forward voltage $I_{F(AV)}$ = 1 A	$V_{F(AV)}$	<	0,8	V
Reverse current				
$V_R = V_{Rmax}$	I_R	<	10	μA
$V_R = V_{Rmax}$; T_{amb} = 100 °C	I_R	<	50	μA
Full-cycle average reverse current $V_R = V_{RRMmax}$; T_{amb} = 75 °C	$I_{R(AV)}$	<	30	μA

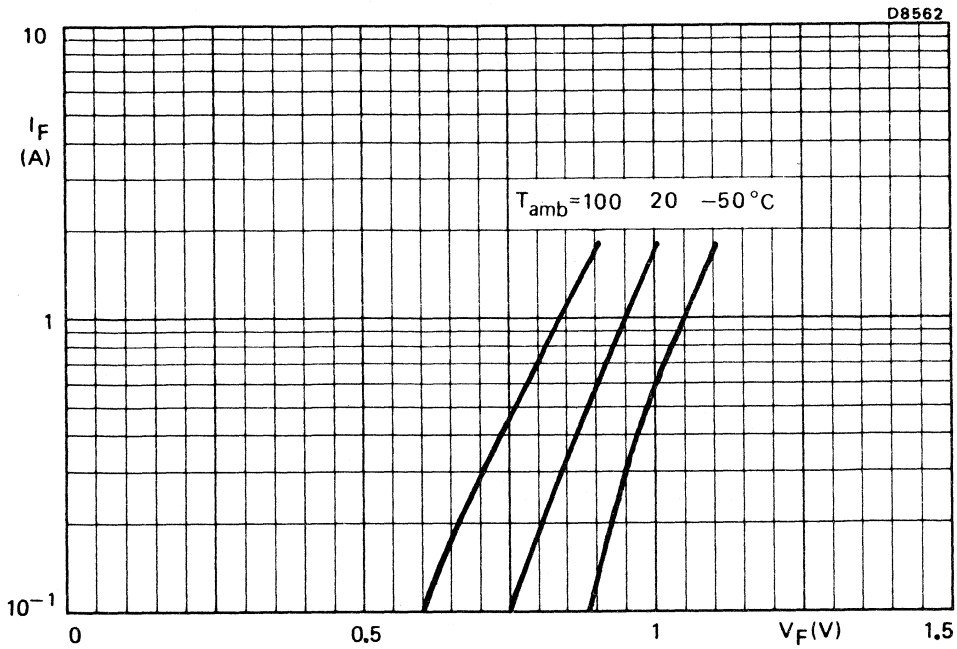


Fig. 2 Typical values.

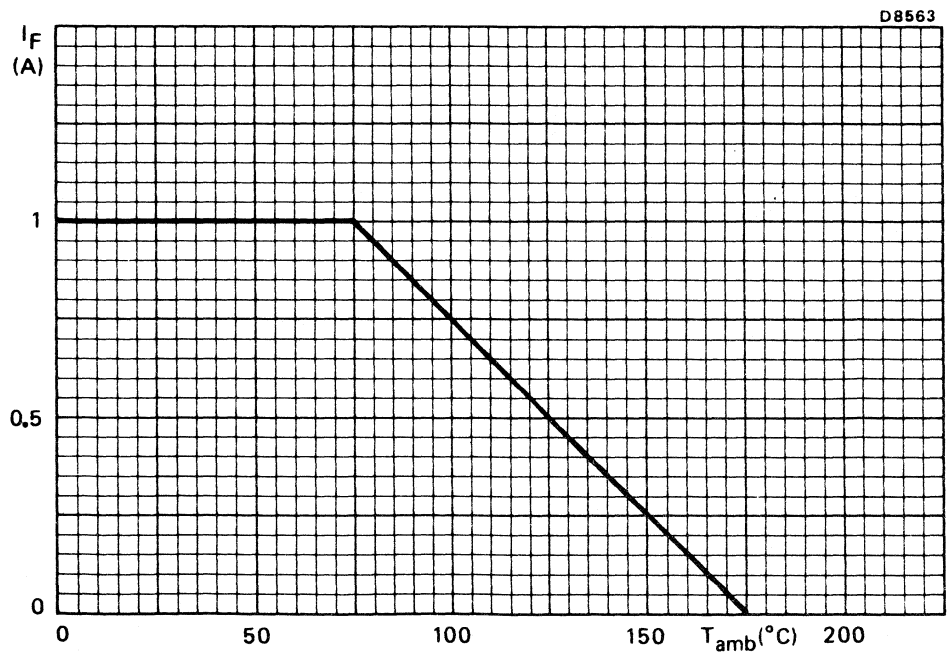


Fig. 3 Maximum permissible d.c. forward current.

HIGH-SPEED SILICON DIODES

Whiskerless diodes in subminiature DO-35 envelopes.
These diodes are primarily intended for fast logic applications.

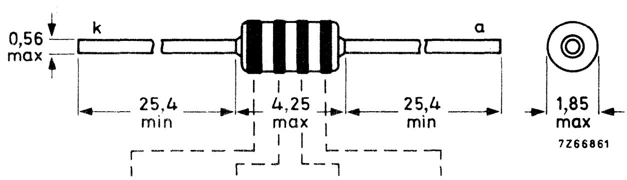
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	75	V
Repetitive peak reverse voltage	V_{RRM}	max.	75	V
Repetitive peak forward current	I_{FRM}	max.	450	mA
Forward voltage **1N4148**: I_F = 10 mA **1N4446**: I_F = 20 mA **1N4448**: I_F = 100 mA	V_F	<	1	V
Reverse recovery time when switched from I_F = 10 mA to I_R = 60 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	4	ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-27 (DO-35).



1N4148:	**yellow**	**brown**	**yellow**	**grey**
1N4446:	**yellow**	**yellow**	**yellow**	**blue**
1N4448:	**yellow** **(cathode)**	**yellow**	**yellow**	**grey**

Note:
Also available with type number markings and cathode side indicated by a coloured band.

Products, available to CECC 50 001-021, available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	75	V
Repetitive peak reverse voltage	V_{RRM}	max.	75	V
Average rectified forward current	$I_{F(AV)}$	max.	150	mA
Forward current (d.c.)	I_F	max.	200	mA
Repetitive peak forward current	I_{FRM}	max.	450	mA
Non-repetitive peak forward current				
t = 1 μs	I_{FSM}	max.	2000	mA
t = 1 s	I_{FSM}	max.	500	mA
Total power dissipation up to T_{amb} = 25 ^oC	P_{tot}	max.	500	mW
Derating factor			2,85	mW/K
Storage temperature	T_{stg}	−65 to + 200		^oC
Junction temperature	T_j	max.	200	^oC

CHARACTERISTICS

T_j = 25 ^oC unless otherwise specified

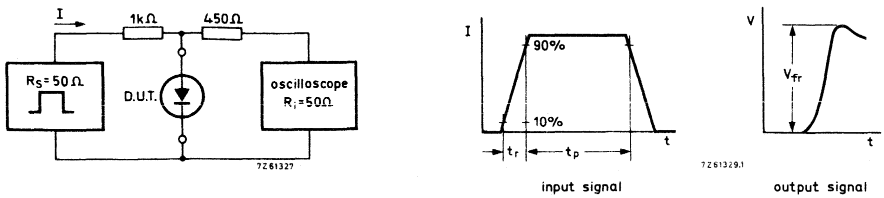
Forward voltages					
1N4148: I_F = 10 mA; **1N4446:** I_F = 20 mA; **1N4448:** I_F = 100 mA		V_F	<	1	V
1N4448: I_F = 5 mA		V_F	0,62 to	0,72	V
Reverse avalanche breakdown voltage					
I_R = 100 μA		$V_{(BR)R}$	>	100	V
I_R = 5 μA		$V_{(BR)R}$	>	75	V
Reverse currents					
V_R = 20 V		I_R	<	25	nA
V_R = 20 V; T_j = 100 ^oC	**1N4448**	I_R	<	3	μA
V_R = 20 V; T_j = 150 ^oC		I_R	<	50	μA
Diode capacitance					
V_R = 0; f = 1 MHz		C_d	<	4	pF

CHARACTERISTICS (continued) $T_j = 25\ ^oC$

Forward recovery voltage when switched to

I_F = 50 mA; t_r = 20 ns V_{fr} < 2,5 V

Test circuit and waveforms:



Input signal : Rise time of the forward pulse t_r = 20 ns

Forward current pulse duration t_p = 120 ns

Duty factor δ = 0,01

Oscilloscope: Rise time t_r = 0,35 ns

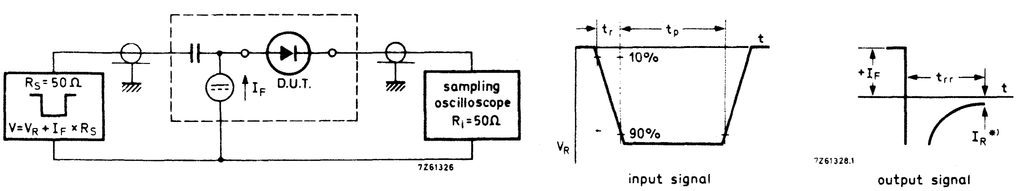
Circuit capacitance C ≤ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

Reverse recovery time when switched from

I_F = 10 mA to I_R = 60 mA; R_L = 100 Ω;

measured at I_R = 1 mA t_{rr} < 4 ns

Test circuit and waveforms:



Input signal : Rise time of the reverse pulse t_r = 0,6 ns *) I_R = 1 mA

Reverse pulse duration t_p = 100 ns

Duty factor δ = 0,05

Oscilloscope: Rise time t_r = 0,35 ns

Circuit capacitance C ≤ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

ULTRA-HIGH-SPEED SILICON DIODES

Whiskerless diodes in subminiature DO-35 envelopes.
The IN4150 is primarily intended for general purpose use in computer and industrial applications.
The IN4151 and IN4153 are intended for military and industrial applications.

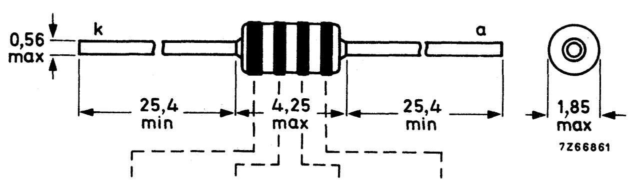
QUICK REFERENCE DATA

			IN4150	IN4151	IN4153	
Continuous reverse voltage	V_R	max.	50	50	50	V
Repetitive peak reverse voltage	V_{RRM}	max.	–	75	75	V
Repetitive peak forward current	I_{FRM}	max.	0,60	0,45	0,45	A
Non-repetitive peak forward current						
t = 1 μs	I_{FSM}	max.	4,0	–	–	A
t = 1 s	I_{FSM}	max.	0,5	–	–	A
Forward voltage						
I_F = 20 mA	V_F	<	–	–	0,88	V
I_F = 50 mA	V_F	<	–	1	–	V
I_F = 200 mA	V_F	<	1	–	–	V
Reverse recovery time when switched from						
I_F = 400 mA to I_R = 400 mA; R_L = 100 Ω; measured at I_R = 40 mA	t_{rr}	<	6	–	–	ns
I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	–	4	4	ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 DO-35.



IN4150 :	yellow	brown	green	black
IN4151 :	yellow	brown	green	brown
IN4153 :	yellow (cathode)	brown	green	orange

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC134)

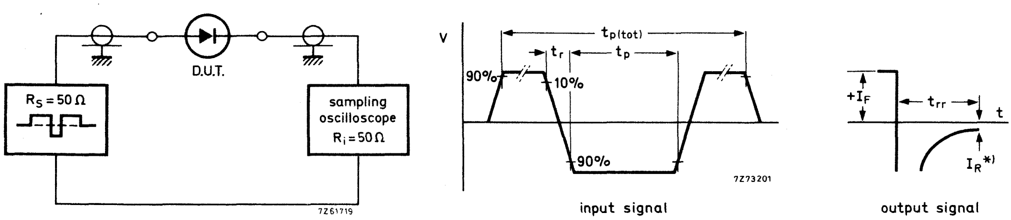
			IN4150	IN4151	IN4153	
Continuous reverse voltage	V_R	max.	50	50	50	V
Repetitive peak reverse voltage	V_{RRM}	max.	–	75	75	V
Forward current (d.c.)	I_F	max.	0,30	0,20	0,20	A
Repetitive peak forward current	I_{FRM}	max.	0,60	0,45	0,45	A
Non-repetitive peak forward current						
t = 1 μs	I_{FSM}	max.	4,0	–	–	A
t = 1 s	I_{FSM}	max.	0,5	–	–	A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.		500		mW
Derating factor				2,85		mW/K
Storage temperature	T_{stg}			–65 to + 200		°C
Junction temperature	T_j	max.		200		°C

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			IN4150	IN4151	IN4153	
Forward voltage						
I_F = 0,1 mA	V_F	>	–	–	0,49	V
		<	–	–	0,55	V
I_F = 0,25 mA	V_F	>	–	–	0,53	V
		<	–	–	0,59	V
I_F = 1 mA	V_F	>	0,54	–	0,59	V
		<	0,62	–	0,67	V
I_F = 2 mA	V_F	>	–	–	0,62	V
		<	–	–	0,70	V
I_F = 10 mA	V_F	>	0,66	–	0,70	V
		<	0,74	–	0,81	V
I_F = 20 mA	V_F	>	–	–	0,74	V
		<	–	–	0,88	V
I_F = 50 mA	V_F	>	0,76	–	–	V
		<	0,86	1	–	V
I_F = 100 mA	V_F	>	0,82	–	–	V
		<	0,92	–	–	V
I_F = 200 mA	V_F	>	0,87	–	–	V
		<	1,00	–	–	V
Reverse avalanche breakdown voltage						
I_R = 5 μA	$V_{(BR)R}$	>	–	75	75	V
Reverse current						
V_R = 50 V	I_R	<	0,1	0,05	0,05	μA
V_R = 50 V; T_{amb} = 150 °C	I_R	<	100	50	50	μA

			IN4150	IN4151	IN4153	
Diode capacitance $V_R = 0$; f = 1 MHz	C_d	<	2,5	2	2	pF
Reverse recovery time when switched from I_F = 10 to 200 mA to I_R = 10 to 200 mA; R_L = 100 Ω; measured at $I_R = 0{,}1 \times I_F$	t_{rr}	<	4	–	–	ns
I_F = 200 to 400 mA to I_R = 200 to 400 mA; R_L = 100 Ω; measured at $I_R = 0{,}1 \times I_F$	t_{rr}	<	6	–	–	ns
I_F = 10 mA to I_R = 1 mA; R_L = 100 Ω; measured at I_R = 0,1 mA	t_{rr}	<	6	–	–	ns
I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	–	4	4	ns
I_F = 10 mA to I_R = 60 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	–	2	2	ns



*) value at which t_{rr} is measured

Fig. 2 Testcircuit and waveforms.

Input signal :	Total pulse duration	$t_{p(tot)}$	=	0,2 μs
	Duty factor	δ	=	0,0025
	Rise time of the reverse pulse	t_r	=	0,6 ns
	Reverse pulse duration	t_p	=	30 ns
Oscilloscope:	Rise time	t_r	=	0,35 ns

Circuit capacitance C ⩽ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

Forward recovery time when switched from
I = 0 to I_F = 200 mA; t_r = 0,4 ns; t_p = 100 ns; $\delta < 0{,}01$;
measured at V_f = 1 V — t_{fr} < 10 ns

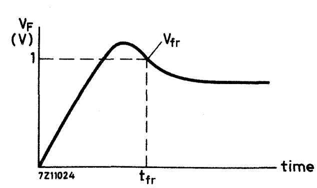


Fig. 3 IN4150.

HIGH-SPEED SILICON DIODES

Diodes in the sub-miniature DO-34 envelope intended for fast logic and general purpose applications. Because of their small size the diodes are especially suitable for mounting in miniature assemblies e.g. as protection diodes in reed relays, etc.

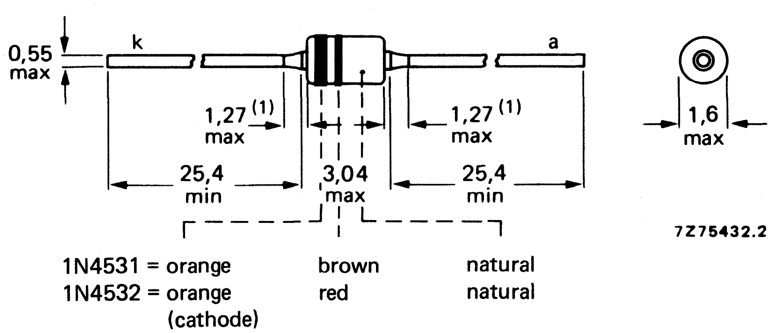
QUICK REFERENCE DATA

			1N4531	1N4532	
Continuous reverse voltage	V_R	max.	75	75	V
Repetitive peak forward current	I_{FRM}	max.	450		mA
Junction temperature	T_j	max.	200		^oC
Forward voltage at I_F = 10 mA	V_F	<	1,0		V
Reverse recovery time					
when switched from I_F = 10 mA to I_R = 60 mA	t_{rr}	<	4	2	ns
when switched from I_F = 10 mA to I_R = 10 mA	t_{rr}	<	–	4	ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 DO-34 (SOD-68).



(1) Lead diameter in this zone uncontrolled.

The diodes are suitable for mounting on a 2E (5,08 mm) pitch.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			1N4531	1N4532	
Continuous reverse voltage	V_R	max.	75	75	V
Repetitive peak reverse voltage	V_{RRM}	max.	75	75	V
Average rectified forward current	$I_{F(AV)}$	max.	150		mA
Forward current (d.c.)	I_F	max.	200		mA
Repetitive peak forward current	I_{FRM}	max.	450		mA
Non-repetitive peak forward current					
(t ≤ 1 μs)	I_{FSM}	max.	2000		mA
(t ≤ 1 s)	I_{FSM}	max.	500		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	500		mW
Storage temperature	T_{stg}		−65 to + 200		°C
Junction temperature	T_j	max.	200		°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0,35	K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			1N4531	1N4532	
Forward voltage					
I_F = 10 mA	V_F	<	1,0		V
Reverse breakdown voltage					
I_R = 100 μA	$V_{(BR)R}$	>	100	–	V
I_R = 5 μA	$V_{(BR)R}$	>	75	75	V
Reverse current					
V_R = 20 V	I_R	<	25	–	nA
V_R = 20 V; T_j = 150 °C	I_R	<	50	–	μA
V_R = 50 V	I_R	<	–	100	nA
V_R = 50 V; T_j = 150 °C	I_R	<	–	100	μA
Diode capacitance					
V_R = 0; f = 1 MHz	C_d	<	4	2	pF

Forward recovery voltage for 1N4532
when switched to I_F = 100 mA at $t_r \leqslant 30$ ns $\quad V_{fr} < 3$ V

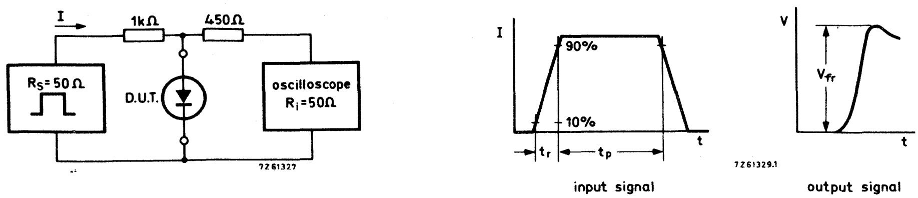


Fig. 2 Test circuit and waveforms.

Input signal:	rise time of the forward pulse	t_r = 30 ns
	forward current pulse duration	t_p = 120 ns
	duty factor	δ = 0,01
Oscilloscope:	rise time	t_r = 0,35 ns

Circuit capacitance C $\leqslant$ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

Reverse recovery time when switched from:

			1N4531	1N4532	
I_F = 10 mA to I_R = 60 mA; R_L = 100 Ω measured at I_R = 1 mA	t_{rr}	<	4	2	ns
I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω measured at I_R = 1 mA	t_{rr}	<	–	4	ns

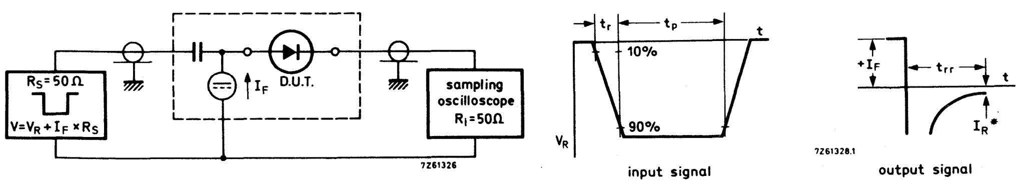


Fig. 3 Test circuit and waveforms.

* I_R = 1 mA

Input signal:	rise time of the reverse pulse	t_r = 0,6 ns
	reverse pulse duration	t_p = 100 ns
	duty factor	δ = 0,05
Oscilloscope:	rise time	t_r = 0,35 ns

Circuit capacitance C $\leqslant$ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

FAST SOFT-RECOVERY RECTIFIER DIODES

Glass passivated rectifier diodes in hermetically sealed axial-leaded ID * envelopes. They are intended for television and industrial applications, such as switched-mode power supplies, scan rectifiers in TV receivers and also for use in inverter and converter applications. The devices feature non-snap-off (soft-recovery) switching characteristics.

QUICK REFERENCE DATA

			1N4933	34	35	36	37	
Repetitive peak reverse voltage	V_{RRM}	max.	50	100	200	400	600	V
Continuous reverse voltage	V_R	max.	50	100	200	400	600	V
Average forward current	$I_{F(AV)}$	max.			1.5			A
Non-repetitive peak forward current	I_{FSM}	max.			30			A
Reverse recovery time	t_{rr}	<			200			ns

MECHANICAL DATA

Dimensions in mm

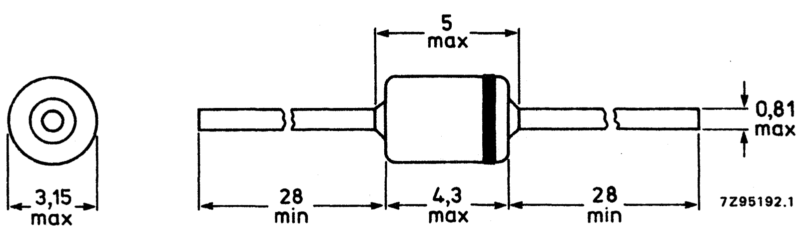


Fig. 1 SOD-84.

The marking band indicates the cathode.

* Implosion Diode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			1N4933	34	35	36	37	
Repetitive peak reverse voltage	V_{RRM}	max.	50	100	200	400	600	V
Continuous reverse voltage	V_R	max.	50	100	200	400	600	V
Average forward current (averaged over any 20 ms period)								
T_{tp} = 75 °C; lead length 10 mm	$I_{F(AV)}$	max.			1.5			A
T_{amb} = 60 °C; see Fig. 2	$I_{F(AV)}$	max.			1.0			A
Non-repetitive peak forward current t = 10 ms; half sinewave (JEDEC method)	I_{FSM}	max.			30			A
Storage temperature range	T_{stg}				−65 to + 175			°C
Junction temperature	T_j	max.			150			°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\ j\text{-}tp}$	=	50	K/W
2. Thermal resistance from junction to ambient; device mounted on an 1.5 mm thick epoxy-glass printed-circuit board; Cu-thickness ⩾ 40 μm; Fig. 2 (see Thermal Model)	$R_{th\ j\text{-}a}$	=	105	K/W

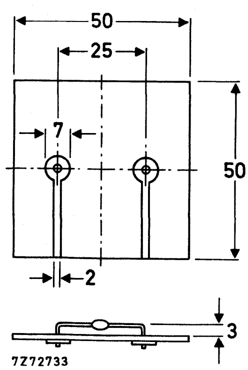


Fig. 2 Mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			1N4933	34	35	36	37	
Forward voltage *								
I_F = 3.14 A; T_j = 150 °C	V_F	<	1.2	1.2	1.2	1.2	1.2	V
I_F = 1 A	V_F	<	1.1	1.1	1.1	1.1	1.1	V
Reverse current								
$V_R = V_{RRMmax}$	I_R	<			2			μA
$V_R = V_{RRMmax}$; T_j = 150 °C	I_R	<			100			μA
Reverse recovery when switched from I_F = 1 A to V_R > 30 V with $-dI_F/dt$ = 50 A/μs								
recovery time	t_{rr}	<			200			ns

DEVELOPMENT DATA

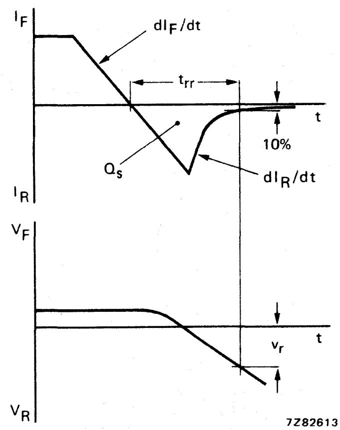


Fig. 3 Definition of t_{rr}.

* Measured under pulse conditions to avoid excessive dissipation.

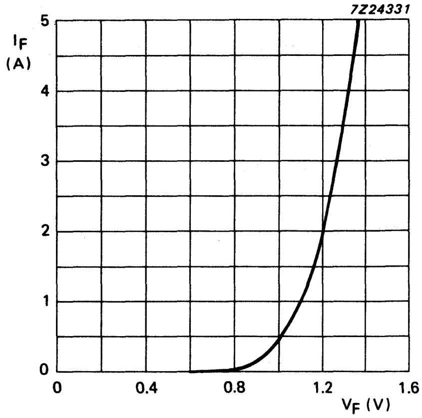


Fig. 4 Maximum forward voltage drop.
(T_j = 25 °C)

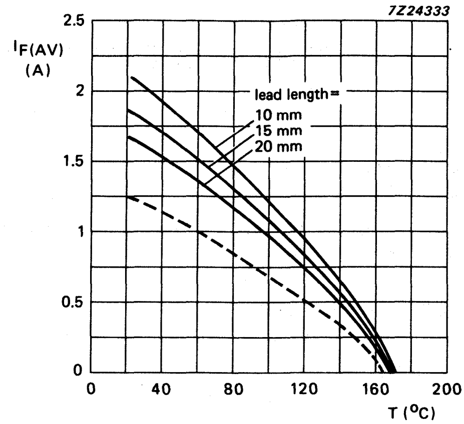
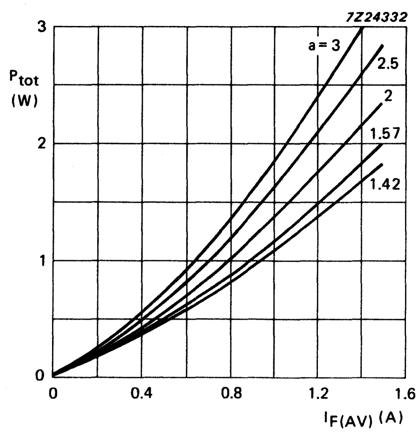


Fig. 5 Maximum average forward current as a function of temperature;
The curves include losses due to reverse leakage.

The graph is for switched-mode application.

$V_R = V_{RRMmax}$; δ = 0.5; a = 1.42.
– – – = ambient temperature and device mounted as shown in Fig. 2.
——— = tie-point temperature.



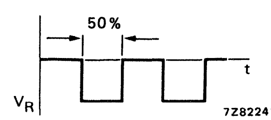


Fig. 6 Maximum values steady state power dissipation (forward plus leakage current) excluding switching losses, as a function of the average forward current.

The graph is for switched-mode application.

a = $I_{F(RMS)} / I_{F(AV)}$; $V_R = V_{RRMmax}$.

CONTROLLED AVALANCHE RECTIFIER DIODES

Double-diffused glass passivated rectifier diodes in hermetically sealed axial-leaded glass envelopes, capable of absorbing reverse transients.

They are intended for rectifier applications as well as general purpose applications in television and communication equipment.

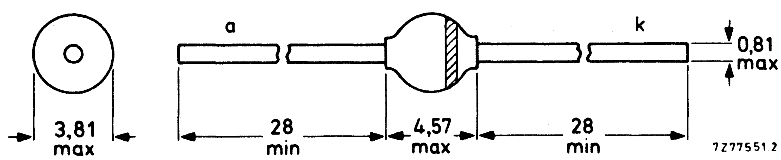
QUICK REFERENCE DATA

			1N5059	5060	5061	5062	
Crest working reverse voltage	V_{RWM}	max.	200	400	600	800	V
Reverse avalanche breakdown voltage	$V_{(BR)R}$	>	225	450	650	900	V
		<	1600	1600	1600	1600	V
Average forward current	$I_{F(AV)}$	max.	2,0				A
Non-repetitive peak forward current	I_{FSM}	max.	50				A
Non-repetitive peak reverse power dissipation	P_{RSM}	max.	1				kW
Junction temperature	T_j	max.	175				°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-57.



The marking band indicates the cathode.

Products approved to CECC 50 008-015 available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			1N5059	5060	5061	5062	
Crest working reverse voltage	V_{RWM}	max.	200	400	600	800	V
Continuous reverse voltage	V_R	max.	200	400	600	800	V
Average forward current (averaged over any 20 ms period)							
T_{tp} = 35 °C; lead length 10 mm	$I_{F(AV)}$	max.	2,0				A
T_{amb} = 75 °C; Fig. 2	$I_{F(AV)}$	max.	0,8				A
Repetitive peak forward current	I_{FRM}	max.	12				A
Non-repetitive peak forward current t = 10 ms; half sine-wave; see Figs 7 and 10	I_{FSM}	max.	50				A
Non-repetitive peak reverse power dissipation							
t = 20 μs (half sine-wave) $T_j = T_{j\,max}$ prior to surge	P_{RSM}	max.	1				kW
t = 100 μs (half sine-wave) $T_j = T_{j\,max}$ prior to surge	P_{RSM}	max.	450				W
Storage temperature	T_{stg}		−65 to + 175				°C
Junction temperature	T_j	max.	175				°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm — $R_{th\,j\text{-}tp}$ = 46 K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ≥ 40 μm; Fig. 2 (see "Thermal model") — $R_{th\,j\text{-}a}$ = 100 K/W

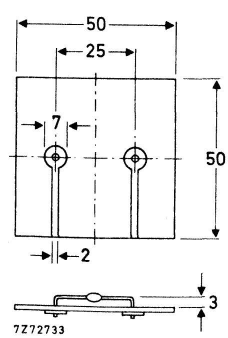


Fig. 2 Device mounted on a printed circuit board.

CHARACTERISTICS

			1N5059	5060	5061	5062	
Forward voltage; T_j = 25 °C *							
I_F = 1 A	V_F	<	1	1	1	1	V
I_F = 2,5 A	V_F	<	1,15	1,15	1,15	1,15	V
Reverse avalanche breakdown voltage		>	225	450	650	900	V
I_R = 0,1 mA; T_j = 25 °C	$V_{(BR)R}$	<	1600	1600	1600	1600	V
Reverse current							
$V_R = V_{RWMmax}$; T_j = 25 °C **	I_R	<	1,0	1,0	1,0	1,0	μA
$V_R = V_{RWMmax}$; T_j = 100 °C	I_R	<	10	10	10	10	μA
$V_R = V_{RWMmax}$; T_j = 165 °C	I_R	<	150	150	150	150	μA
Reverse recovery time when switched from I_F = 0,5 A to I_R = 1 A at i_{rr} = 0,25 A	t_{rr}	<	6				μs
		typ.	3				μs

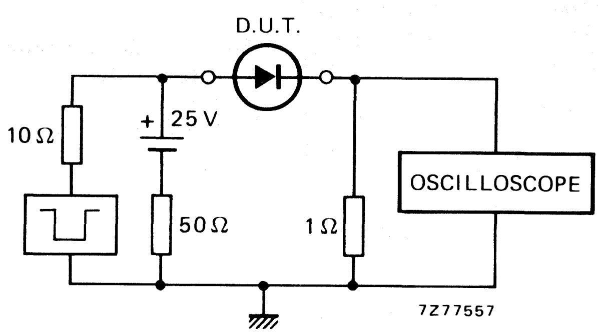


Fig. 3 Test circuit.
Input impedance oscilloscope 1 MΩ; 22 pF. Rise time ⩽ 7 ns.
Source impedance 50 Ω. Rise time ⩽ 15 ns.

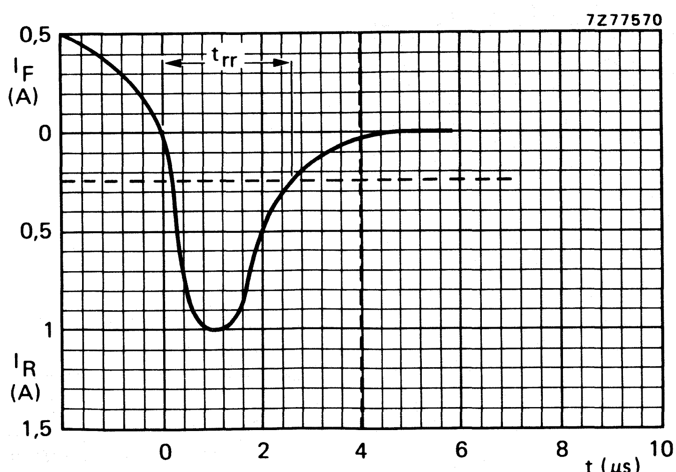


Fig. 4 Reverse recovery time characteristic.

** Measured under pulse conditions to avoid excessive dissipation.
* Illuminance ⩽ 500 lux (daylight); relative humidity < 65%.

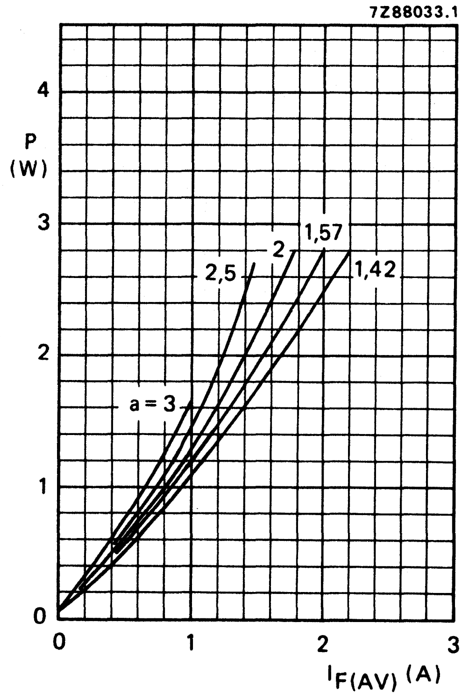


Fig. 5 Steady state power dissipation (forward plus leakage current excluding switching losses) as a function of the average forward current.

$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RWMmax}$.

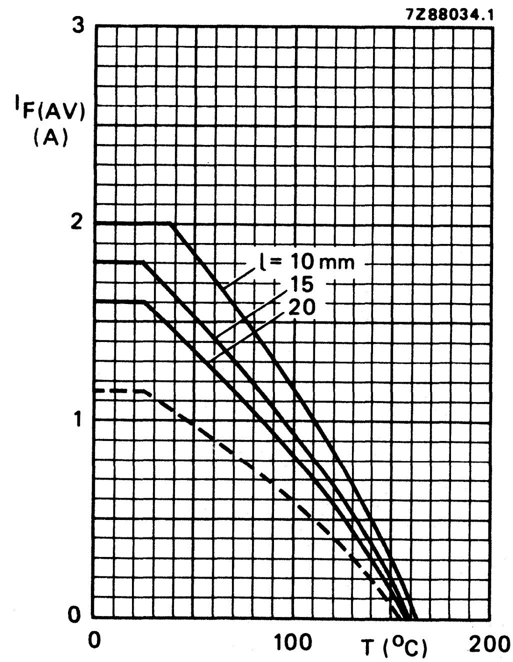


Fig. 6 Maximum average forward current as a function of the temperature.
The curves include losses due to reverse current.
a = 1,57; $V_R = V_{RWMmax}$; l = lead length
——— T = tie-point temperature
– – – – T = ambient temperature and device mounted as shown in Fig. 2.

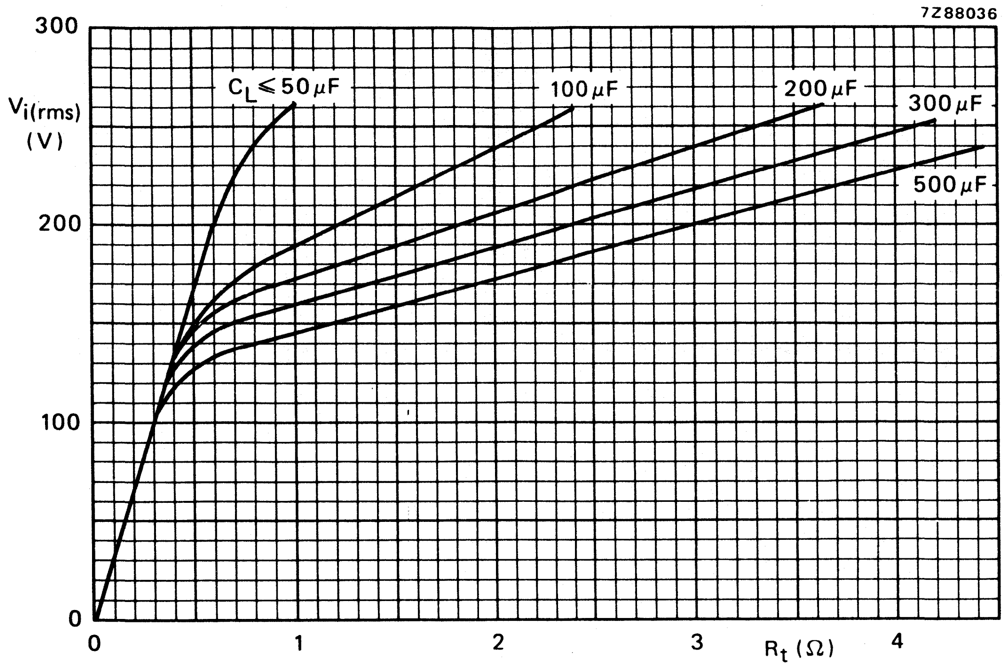


Fig. 7 Minimum values of series resistance (R_t), including the transformer resistance, required to limit the initial peak rectifier current with capacitive load. The possibility of the following spreads are taken into account: mains voltage + 10%; capacitance + 50%, resistance −10%.

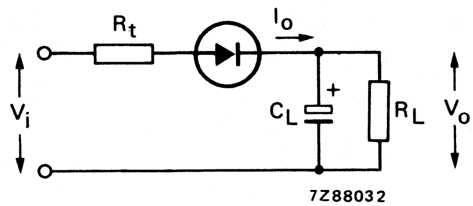


Fig. 8 Test circuit series resistance (R_t).

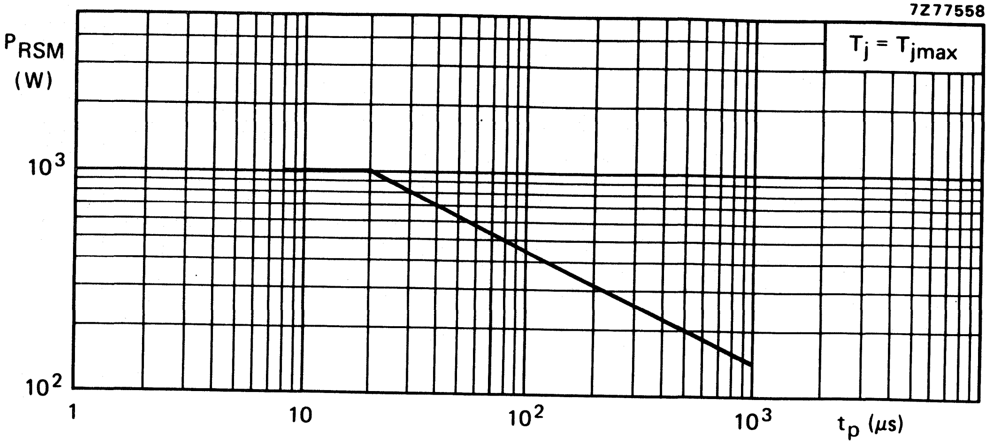
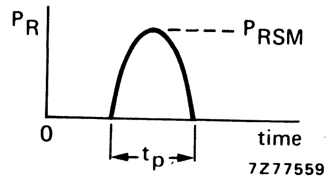


Fig. 9 Maximum permissible non-repetitive peak reverse power dissipation in the avalanche region.



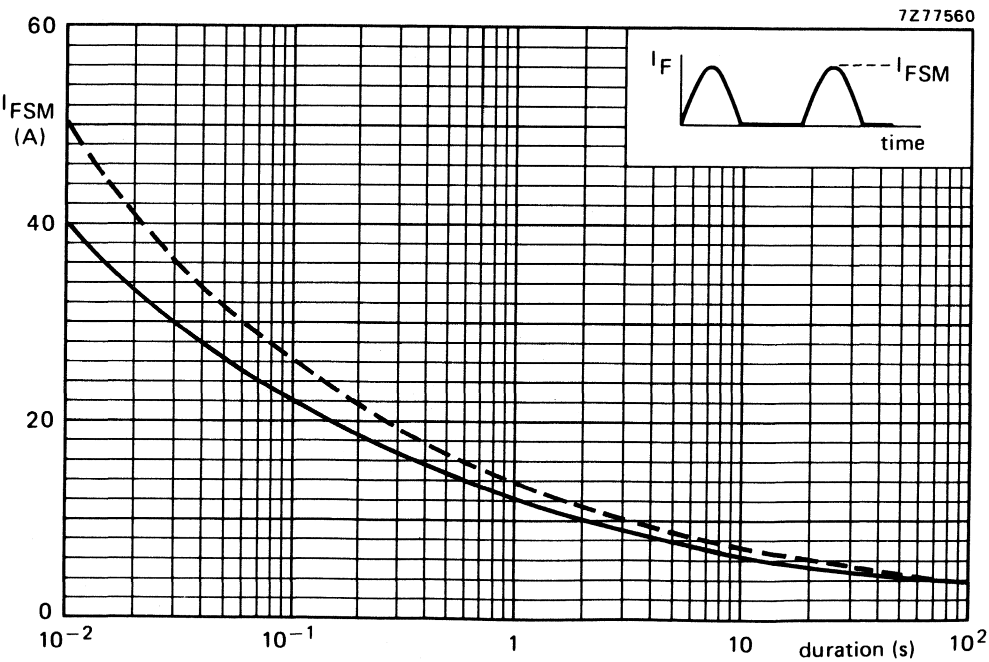


Fig. 10 Maximum permissible non-repetitive peak forward current based on sinusoidal currents (f = 50 Hz).

– – – T_j = 25 °C; V_R = 0

—— $T_j = T_{j\,max}$ prior to surge, $V_R = V_{RWMmax}$.

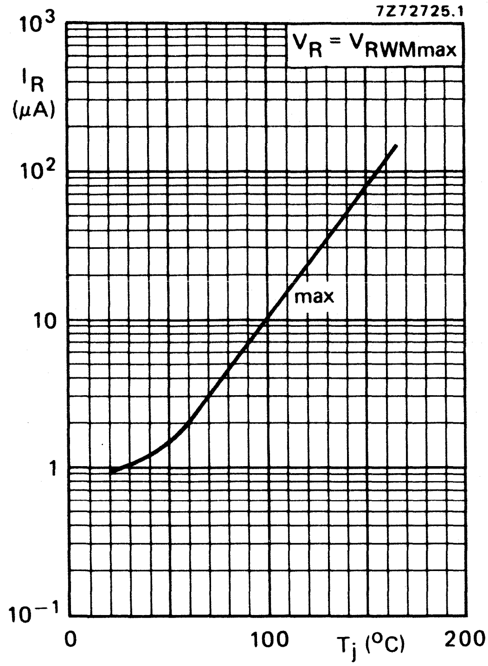


Fig. 11.

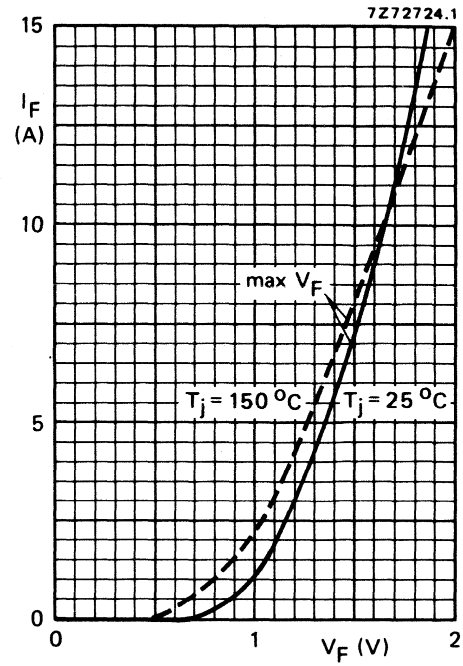


Fig. 12.

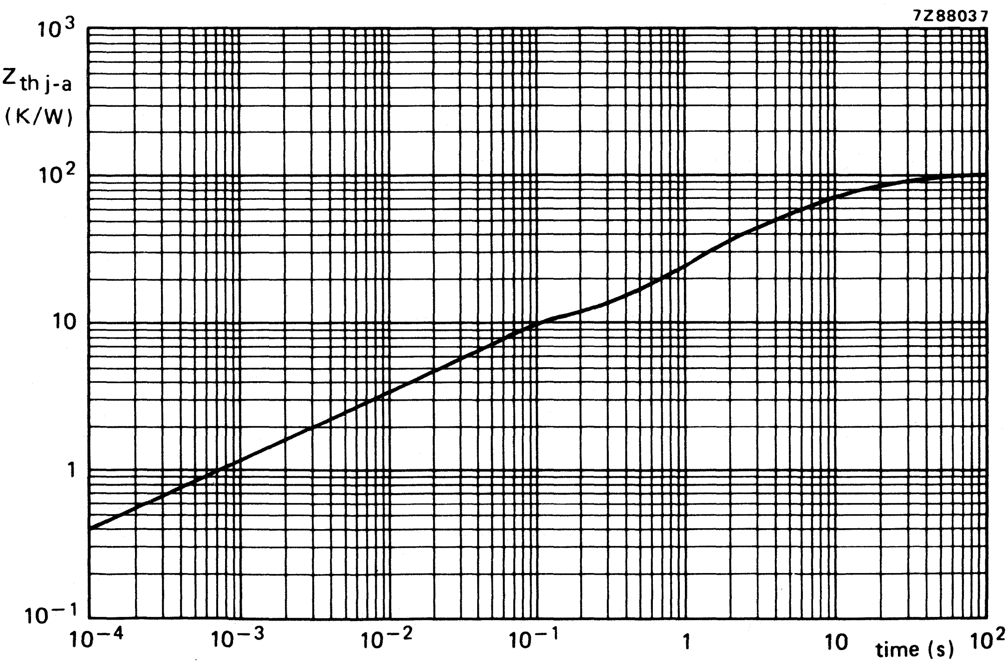


Fig. 13 Device mounted on a printed circuit board (see Fig. 2).

VOLTAGE REGULATOR DIODES

Silicon planar diodes in a DO-35 envelope intended for use as low-power voltage stabilizers or voltage references.
The series consists of 43 types with nominal working voltages ranging from 3,0 V to 75 V.

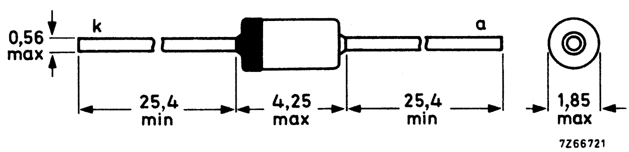
QUICK REFERENCE DATA

Working voltage range	V_Z	nom.	3,0 to 75	V
Working voltage tolerance			± 5	%
Total power dissipation	P_{tot}	max.	500	mW
Non-repetitive peak reverse power dissipation T_j = 55 °C; t_p = 8,3 ms, square wave	P_{ZSM}	max.	10	W
Junction temperature	T_j		−65 to + 200	°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 DO-35 (SOD-27).



Cathode indicated by coloured band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	250 mA
Repetitive peak forward current	I_{FRM}	max.	250 mA
Total power dissipation if leads are kept at T_{lead} = 75 °C at 8 mm from body	P_{tot}	max.	500 mW
Derating factor			4 mW/K
Non-repetitive peak reverse power dissipation T_j = 55 °C; t_p = 8,3 ms, square wave	P_{ZSM}	max.	10 W
Storage temperature	T_{stg}		−65 to + 200 °C
Junction temperature	T_j		−65 to + 200 °C

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise stated

Forward voltage I_F = 200 mA	V_F	max.	1,1 V

type number	working voltage V_Z (V) at I_{ztest} (note 1) nom.	test current I_{Ztest} (mA)	max. Zener impedance Z_{ZT} (Ω) at I_{Ztest} (note 2)	differential resistance r_{diff} (Ω) at I_{ZK} = 0,25 mA (note 2) max.	reverse current I_R (μA) at V_R max.	test voltage V_R (V)	temp. coeff. S_Z (%/K) (note 3) max.
1N5225B	3,0	20	29	1600	50	1,0	−0,075
1N5226B	3,3	20	28	1600	25	1,0	−0,070
1N5227B	3,6	20	24	1700	15	1,0	−0,065
1N5228B	3,9	20	23	1900	10	1,0	−0,060
1N5229B	4,3	20	22	2000	5	1,0	± 0,055
1N5230B	4,7	20	19	1900	5	2,0	± 0,030
1N5231B	5,1	20	17	1600	5	2,0	± 0,030
1N5232B	5,6	20	11	1600	5	3,0	+ 0,038
1N5233B	6,0	20	7	1600	5	3,5	+ 0,038
1N5234B	6,2	20	7	1000	5	4,0	+ 0,045
1N5235B	6,8	20	5	750	3	5,0	+ 0,050
1N5236B	7,5	20	6	500	3	6,0	+ 0,058
1N5237B	8,2	20	8	500	3	6,5	+ 0,062
1N5238B	8,7	20	8	600	3	6,5	+ 0,065
1N5239B	9,1	20	10	600	3	7,0	+ 0,068

type number	working voltage V_Z (V) at I_{ztest} (note 1) nom.	test current I_{Ztest} (mA)	max. Zener impedance Z_{ZT} (Ω) at I_{Ztest} (note 2)	differential resistance r_{diff} (Ω) at I_{ZK} = 0,25 mA (note 2) max.	reverse current I_R (μA) at V_R max.	test voltage V_R (V)	temp. coeff. S_Z (%/K) (note 3) max.
1N5240B	10	20	17	600	3	8,0	+ 0,075
1N5241B	11	20	22	600	2	8,4	+ 0,076
1N5242B	12	20	30	600	1	9,1	+ 0,077
1N5243B	13	9,5	13	600	0,5	9,9	+ 0,079
1N5244B	14	9,0	15	600	0,1	10	+ 0,082
1N5245B	15	8,5	16	600	0,1	11	+ 0,082
1N5246B	16	7,8	17	600	0,1	12	+ 0,083
1N5247B	17	7,4	19	600	0,1	13	+ 0,084
1N5248B	18	7,0	21	600	0,1	14	+ 0,085
1N5249B	19	6,6	23	600	0,1	14	+ 0,086
1N5250B	20	6,2	25	600	0,1	15	+ 0,086
1N5251B	22	5,6	29	600	0,1	17	+ 0,087
1N5252B	24	5,2	33	600	0,1	18	+ 0,088
1N5253B	25	5,0	35	600	0,1	19	+ 0,089
1N5254B	27	4,6	41	600	0,1	21	+ 0,090
1N5255B	28	4,5	44	600	0,1	21	+ 0,091
1N5256B	30	4,2	49	600	0,1	23	+ 0,091
1N5257B	33	3,8	58	700	0,1	25	+ 0,092
1N5258B	36	3,4	70	700	0,1	27	+ 0,093
1N5259B	39	3,2	80	800	0,1	30	+ 0,094
1N5260B	43	3,0	93	900	0,1	33	+ 0,095
1N5261B	47	2,7	105	1000	0,1	36	+ 0,095
1N5262B	51	2,5	125	1100	0,1	39	+ 0,096
1N5263B	56	2,2	150	1300	0,1	43	+ 0,096
1N5264B	60	2,1	170	1400	0,1	46	+ 0,097
1N5265B	62	2,0	185	1400	0,1	47	+ 0,097
1N5266B	68	1,8	230	1600	0,1	52	+ 0,097
1N5267B	75	1,7	270	1700	0,1	56	+ 0,098

Notes

1. V_Z is measured with device at thermal equilibrium while held in clips at 10 mm from body in still air at 25 °C.
2. $I_{(ac\,rms)}$ = 10% of I_{Ztest} resp. I_{ZK}, 60 Hz superimposed.
3. For types 1N5225B to 1N5242B the current I_Z = 7,5 mA; for 1N5243B and higher $I_Z = I_{Ztest}$. Testpoints at T_1 = 25 °C, T_2 = 125 °C.

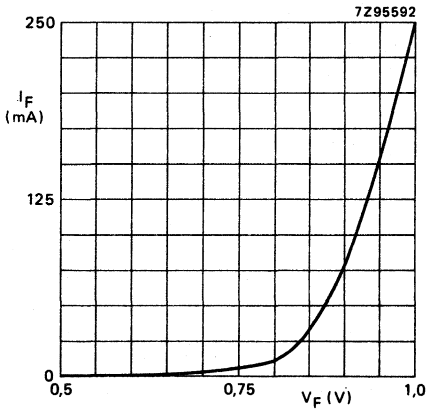


Fig. 2 T_{amb} = 25 °C; typical values.

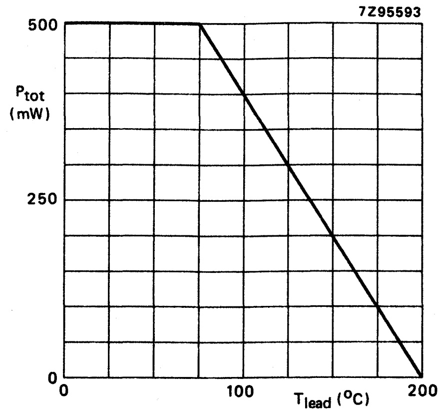


Fig. 3 Total power dissipation versus lead temperature.

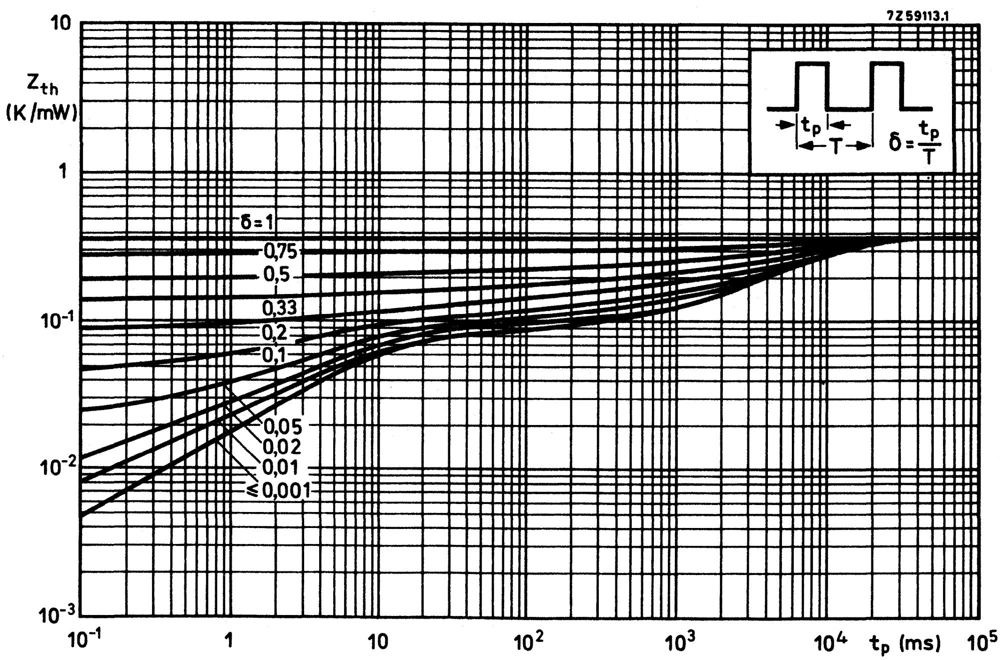
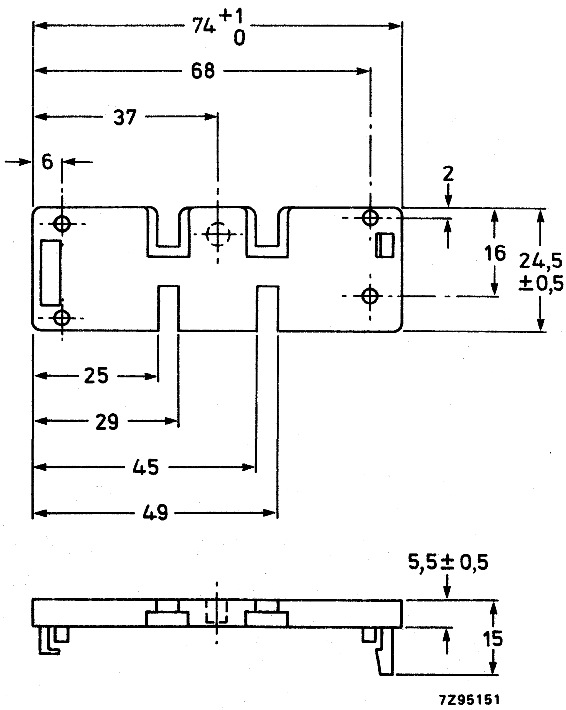


Fig. 4 Thermal impedance versus pulse duration.

ADAPTOR SOCKET
56397

MECHANICAL DATA

Dimensions in mm



This adaptor enables a BG2000 type tripler to be mounted into a BG1895 mounting base. It clips into the BG2000 and has the same fitting holes as a BG1895 tripler.

NOTES

INDEX OF TYPE NUMBERS

The inclusion of a type number in this publication does not necessarily imply its availability.

Key to handbook sections

A = Accessories
FET = Field-effect transistors
I = Infrared devices
LED = Light-emitting diodes
LCD = Liquid crystal displays
Mm = Surface-mounted devices
M = Microwave transistors
P = Low-frequency power transistors and modules
PDT = Photodiodes or transistors
Ph = Photoconductive devices
PhC = Photocouplers
PM = PowerMOS transistors
R = Rectifier diodes
RFP = RF power transistors and modules
RT = Triplers
SEN = Semiconductor sensors
SD = Small-signal diodes
Sm = Small-signal transistors
Sp = Special diodes
SP = Low-frequency switching power diodes
St = Rectifier stacks
T = Tuner diodes
Th = Thyristors
Tri = Triacs
TS = Transient suppressor diodes
Vrf = Voltage reference diodes
Vrg = Voltage regulator diodes
WBT = Wideband hybrid IC transistors
WBM = Wideband hybrid IC modules

* series.

DATA HANDBOOK SYSTEM

DATA HANDBOOK SYSTEM

Our Data Handbook System comprises more than 60 books with specifications on electronic components, subassemblies and materials. It is made up of six series of handbooks:

INTEGRATED CIRCUITS

DISCRETE SEMICONDUCTORS

DISPLAY COMPONENTS

PASSIVE COMPONENTS*

PROFESSIONAL COMPONENTS**

MATERIALS*

The contents of each series are listed on pages iii to viii.

The data handbooks contain all pertinent data available at the time of publication, and each is revised and reissued periodically.

When ratings or specifications differ from those published in the preceding edition they are indicated with arrows in the page margin. Where application is given it is advisory and does not form part of the product specification.

Condensed data on the preferred products of Philips Components is given in our Preferred Type Range catalogue (issued annually).

Information on current Data Handbooks and how to obtain a subscription for future issues is available from any of the Organizations listed on the back cover.
Product specialists are at your service and enquiries will be answered promptly.

* Will replace the Components and materials (green) series of handbooks.
** Will replace the Electron tubes (blue) series of handbooks.

INTEGRATED CIRCUITS

This series of handbooks comprises:

code	handbook title
IC01	**Radio, audio and associated systems** Bipolar, MOS
IC02a/b	**Video and associated systems** Bipolar, MOS
IC03	**ICs for Telecom** Bipolar, MOS Subscriber sets, Cordless Telephones
IC04	**HE4000B logic family** CMOS
IC05N	**HE4000B logic family – uncased ICs** CMOS
IC06	**High-speed CMOS; PC74HC/HCT/HCU** Logic family
IC07	**not yet issued**
IC08	**ECL 10K and 100K logic families**
IC09N	**TTL logic series**
IC10	**Memories** MOS, TTL, ECL
IC11	**Linear Products**
Supplement to IC11	**Linear Products**
IC12	**I^2C-bus compatible ICs**
IC13	**Semi-custom** Programmable Logic Devices (PLD)
IC14	**Microcontroller and peripherals** Bipolar, MOS
IC15	**FAST TTL logic series**
IC16	**CMOS integrated circuits for clocks and watches**
IC17	**ICs for Telecom** Bipolar, MOS Radio pagers Mobile telephones ISDN
IC18	**Microprocessors and peripherals**
IC19	**Data communication products**

DISCRETE SEMICONDUCTORS

This series of data handbooks comprises:

current code	new code	handbook title
S1	**SC01***	**Diodes** High-voltage tripler units
S2a	**SC02***	**Power diodes**
S2b	**SC03***	**Thyristors and triacs**
S3	**SC04***	**Small-signal transistors**
S4a	**SC05***	**Low-frequency power transistors and hybrid modules**
S4b	**SC06**	**High-voltage and switching power transistors**
S5	**SC07***	**Small-signal field-effect transistors**
S6	**SC08*** **SC09***	**RF power transistors** **RF power modules**
S7	**SC10***	**Surface mounted semiconductors**
S8a	**SC11***	**Light emitting diodes**
S8b	**SC12***	**Optocouplers**
S9	**SC13***	**PowerMOS transistors**
S10	**SC14***	**Wideband transistors and wideband hybrid IC modules**
S11	**SC15**	**Microwave transistors**
S15**	**SC16**	**Laser diodes**
S13	**SC17**	**Semiconductor sensors**
S14	**SC18***	**Liquid crystal displays and driver ICs for LEDs**

* Not yet issued with the new code in this series of handbooks.
** New handbook in this series; will be issued shortly.

DISPLAY COMPONENTS

This series of data handbooks comprises:

current code	new code	handbook title
T8	**DC01**	**Colour display systems**
T16	**DC02***	**Monochrome tubes and deflection units**
C2	**DC03***	**Television tuners, coaxial aerial input assemblies**
C3	**DC04***	**Loudspeakers**
C20	**DC05***	**Wire-wound components for TVs and monitors**

* These handbooks are currently issued in another series; they are not yet issued in the Display Components series of handbooks.

PASSIVE COMPONENTS

This series of data handbooks comprises:

current code	new code	handbook title
C14	**PA01**	**Electrolytic capacitors; solid and non-solid**
C11	**PA02***	**Varistors, thermistors and sensors**
C12	**PA03***	**Potentiometers, encoders and switches**
C7	**PA04***	**Variable capacitors**
C22	**PA05***	**Film capacitors**
C15	**PA06***	**Ceramic capacitors**
C9	**PA07***	**Piezoelectric quartz devices**
C13	**PA08***	**Fixed resistors**

* Not yet issued with the new code in this series of handbooks.

PROFESSIONAL COMPONENTS

This series of data handbooks comprises:

current code	new code	handbook title
T1	*	**Power tubes for RF heating and communications**
T2a	*	**Transmitting tubes for communications, glass types**
T2b	*	**Transmitting tubes for communications, ceramic types**
T3	**PC01****	**High-power klystrons**
T4	*	**Magnetrons for microwave heating**
T5	**PC02****	**Cathode-ray tubes**
T6	**PC03****	**Geiger-Müller tubes**
T9	**PC04****	**Photo and electron multipliers**
T10	**PC05****	**Plumbicon camera tubes and accessories**
T11	**PC06****	**Microwave diodes and sub-assemblies**
T12	**PC07****	**Vidicon and Newvicon camera tubes and deflection units**
T13	**PC08****	**Image intensifiers and infrared detectors**
T15	**PC09****	**Dry reed switches**
C8	**PC10**	**Variable mains transformers; annular fixed transformers**

* These handbooks will not be reissued.

** Not yet issued with the new code in this series of handbooks.

MATERIALS

This series of data handbooks comprises:

current code	new code	handbook title
C4 / **C5**	**MA01***	**Soft Ferrites**
C16	**MA02****	**Permanent magnet materials**
C19	**MA03****	**Piezoelectric ceramics**

* Handbooks C4 and C5 will be reissued as one handbook having the new code MA01.

** Not yet issued with the new code in this series of handbooks.

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